

Handbook of X-ray Photoelectron Spectroscopy

A Reference Book of Standard Spectra
for Identification and Interpretation of XPS Data

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Preface

X-ray Photoelectron Spectroscopy (XPS), also known as Electron Spectroscopy for Chemical Analysis (ESCA), is widely used to investigate the chemical composition of surfaces. The use of XPS in analytical laboratories throughout the world attests to the problem-solving capability of this technique. The ability to explore the first few atomic layers and assign chemical states to the detected atoms has shown XPS to be a powerful addition to any analytical laboratory.

A great deal of information has been published on the principles of the technique and the diverse range of applications for which it is used. Volumes of XPS spectra exist in the scientific literature, and international committees are establishing databases with reference spectra that will be made available to the general public. It is not the authors' intent to exclude these spectra or to ignore these databases. Rather the intent is to assemble a concise volume of standard spectra to aid in the identification of XPS data.

The previous version of this handbook, published in 1978, contained data acquired with a cylindrical mirror analyzer (CMA). Since that time, our XPS hardware has evolved. We currently use a spherical capacitance analyzer (SCA) in conjunction with improved detector technology and the choice of either a high-performance Al x-ray monochromator or an achromatic Mg/Al dual anode x-ray source. A 1992 version of this handbook was updated from the previous handbook with data acquired using our current SCA, which has a transmission function different from that of a CMA, and both monochromatic and achromatic x-ray sources. In addition, data are included from several elements not contained in the 1978 version of the handbook. The current 1995 version of the handbook is a reprint of the 1992 version which includes a few minor modifications. This handbook is meant to serve as a guide and reference work for the identification, quantification, calibration and interpretation of XPS spectra for users of Physical Electronics XPS systems equipped with SCAs and Omni Focus™ lenses. It is the authors' hope that this handbook will play a useful role in the practice of XPS.

Physical Electronics, Inc.
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I. X-ray Photoelectron Spectroscopy

A. Introduction

X-ray Photoelectron Spectroscopy (XPS) was developed in the mid-1960s by Kai Siegbahn and his research group at the University of Uppsala, Sweden. The technique was first known by the acronym ESCA (Electron Spectroscopy for Chemical Analysis). The advent of commercial manufacturing of surface analysis equipment in the early 1970s enabled the placement of equipment in laboratories throughout the world. In 1981, Siegbahn was awarded the Nobel Prize for Physics for his work with XPS.

This handbook is meant to furnish the user with much of the information necessary to use XPS for diverse types of surface analysis. Information is provided on methods of sample preparation, data gathering, elemental identification, chemical state identification, quantitative calculation and elemental distribution.

Surface analysis by XPS involves irradiating a solid *in vacuo* with monoenergetic soft x-rays and analyzing the emitted

electrons by energy. The spectrum is obtained as a plot of the number of detected electrons per energy interval versus their kinetic energy. Each element has a unique spectrum. The spectrum from a mixture of elements is approximately the sum of the peaks of the individual constituents. Because the mean free path of electrons in solids is very small, the detected electrons originate from only the top few atomic layers, making XPS a unique surface-sensitive technique for chemical analysis. Quantitative data can be obtained from peak heights or peak areas, and identification of chemical states often can be made from exact measurement of peak positions and separations, as well as from certain spectral features.

Included in this handbook are survey spectra, strong line spectra and x-ray excited Auger spectra for most of the elements and some of their compounds, in addition to plots and tables of energy shift data which aid in the identification of chemical states.

B. Principles of the Technique

Surface analysis by XPS is accomplished by irradiating a sample with monoenergetic soft x-rays and analyzing the energy of the detected electrons. Mg K α (1253.6 eV), Al K α (1486.6 eV), or monochromatic Al K α (1486.7 eV) x-rays are usually used. These photons have limited penetrating power in a solid on the order of 1-10 micrometers. They interact with atoms in the surface region, causing electrons to be emitted by the photoelectric effect. The emitted electrons have measured kinetic energies given by:

$$KE = h\nu - BE - \phi_s \quad (1)$$

where $h\nu$ is the energy of the photon, BE is the binding energy of the atomic orbital from which the electron originates, and ϕ_s is the spectrometer work function.

The binding energy may be regarded as the energy difference between the initial and final states after the photoelectron has left the atom. Because there is a variety of possible final states of the ions from each type of atom, there is a corresponding variety of kinetic energies of the emitted electrons. Moreover, there is a different probability or cross-section for each final state. Relative binding energies and ionization cross-sections for an atom are shown schematically in Figure 1. The Fermi level corresponds to zero binding energy (by definition), and the depth beneath the Fermi level in the figure indicates the relative energy of the ion remaining after electron emission, or the binding energy of the electron. The line lengths indicate the relative probabilities of the various ionization processes. The p, d and f levels become split upon ionization, leading to vacancies in the $p_{1/2}$, $p_{3/2}$, $d_{3/2}$, $d_{5/2}$, $f_{5/2}$ and $f_{7/2}$. The spin-orbit splitting ratio is 1:2 for p levels, 2:3 for d levels and 3:4 for f levels. As an example, the spin-orbit splitting of the Si 2p is shown in Figure 2.

Because each element has a unique set of binding energies, XPS can be used to identify and determine the concentration of the elements in the surface. Variations in the elemental binding energies (the chemical shifts) arise from differences in the

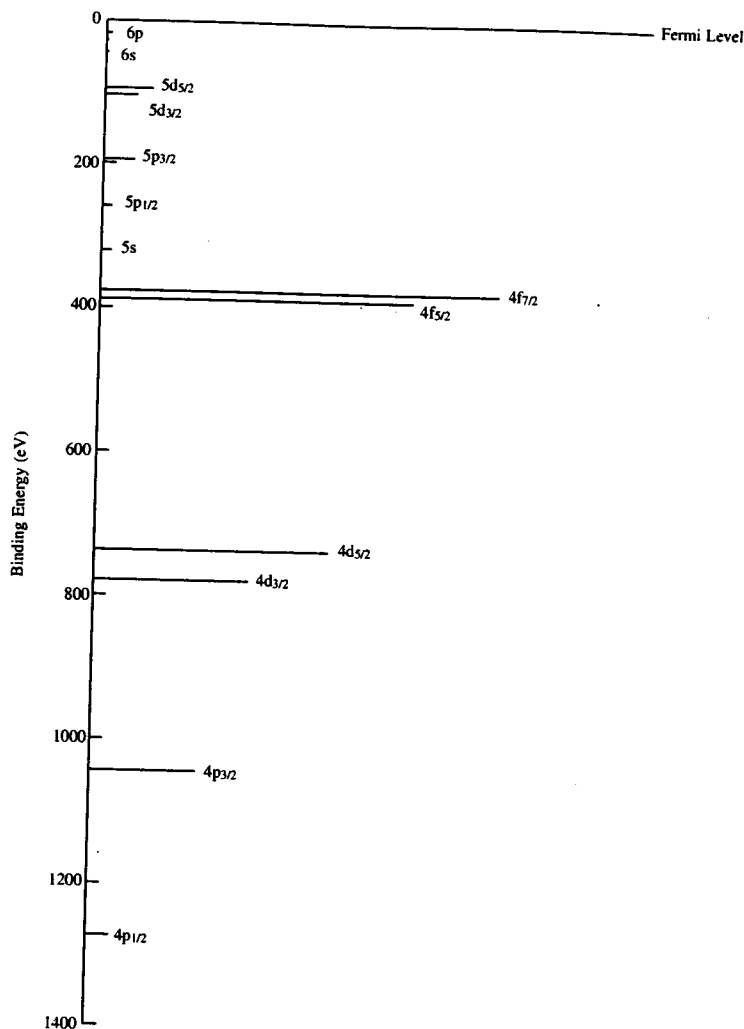


Figure 1. Relative binding energies and ionization cross-sections for U. The binding energy is proportional to the distance below the line indicating the Fermi level, and the ionization cross-section is proportional to the length of the line.

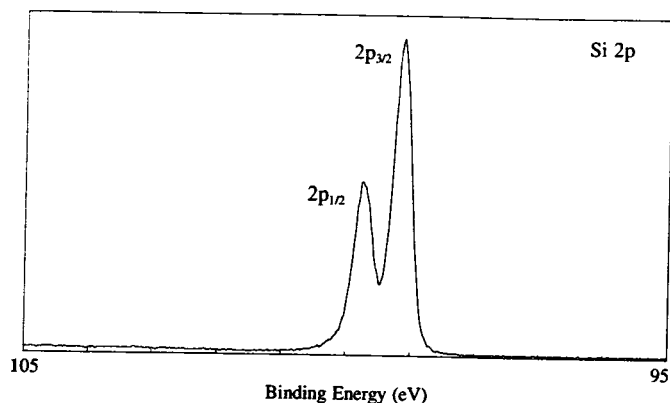


Figure 2. High-resolution spectrum of single-crystal Si showing the spin-orbit splitting of the 2p level.

chemical potential and polarizability of compounds. These chemical shifts can be used to identify the chemical state of the materials being analyzed.

In addition to photoelectrons emitted in the photoelectric process, Auger electrons may be emitted because of relaxation of the excited ions remaining after photoemission. This Auger electron emission occurs roughly 10^{-14} seconds after the photoelectric event. The competing emission of a fluorescent x-ray photon is a minor process in this energy range. In the Auger process (Figure 3), an outer electron falls into the inner orbital vacancy, and a second electron is simultaneously emitted, carrying off the excess energy. The Auger electron possesses kinetic energy equal to the difference between the energy of the initial ion and the doubly charged final ion, and is independent of the mode of the initial ionization. Thus, photoionization normally leads to two emitted electrons — a photoelectron and an Auger electron. The sum of the kinetic energies of the electrons emitted cannot exceed the energy of the ionizing photons.

Probabilities of electron interaction with matter far exceed those of the photons, so while the path length of the photons is of the order of micrometers, that of the electrons is of the order of tens of angstroms. Thus, while ionization occurs to a depth of a few

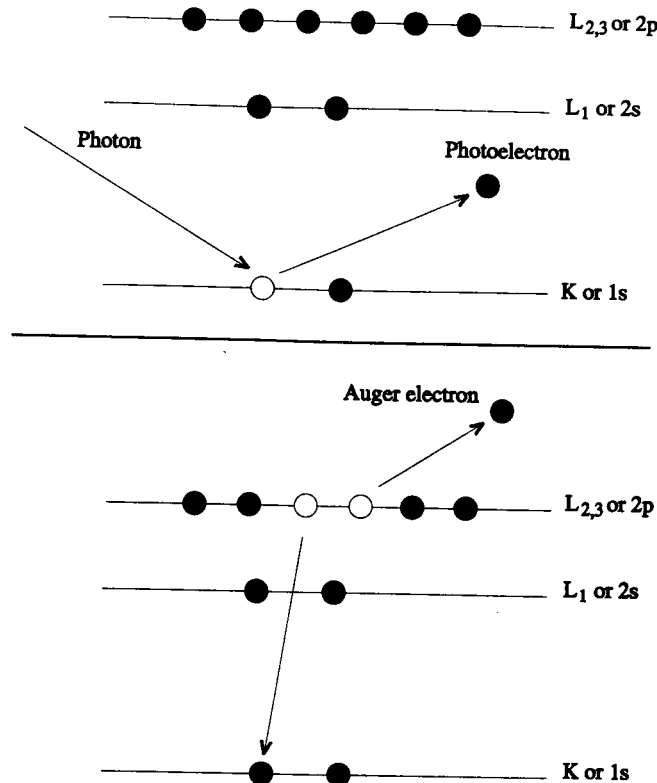


Figure 3. The XPS emission process (top) for a model atom. An incoming photon causes the ejection of the photoelectron. The relaxation process (bottom) for a model atom resulting in the emission of a $KL_{23}L_{23}$ electron. The simultaneous two-electron coulombic rearrangement results in a final state with two electron vacancies.

micrometers, only those electrons that originate within tens of angstroms below the solid surface can leave the surface without energy loss. These electrons which leave the surface without energy loss produce the peaks in the spectra and are the most useful. The electrons that undergo inelastic loss processes before emerging form the background. Calculations of the inelastic mean free paths of electrons in various materials are shown in Figure 4.

The electrons leaving the sample are detected by an electron spectrometer according to their kinetic energy. The analyzer is usually operated as an energy window, referred to as the pass energy, accepting only those electrons having an energy within the range of this window. To maintain a constant energy resolution, the pass energy is fixed. Incoming electrons are adjusted to the pass energy before entering the energy analyzer. Scanning for different energies is accomplished by applying a variable electrostatic field before the analyzer. This retardation voltage may be varied from zero up to and beyond the photon energy. Electrons are detected as discrete events, and the number of electrons for a given detection time and energy is stored and displayed.

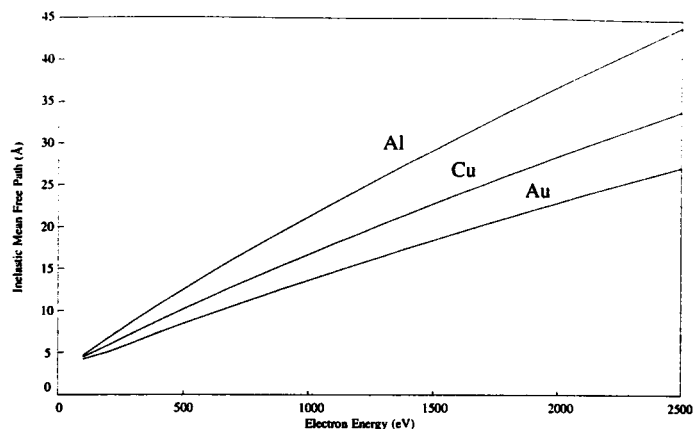


Figure 4. Calculated inelastic electron mean free paths in various metals from the method of S. Tanuma, C.J. Powell and D.R. Penn, *Surf. Interface Anal.* 17, 911 (1991).

C. Preparing and Mounting Samples

In the majority of XPS applications, sample preparation and mounting are not critical. Typically, the sample is mechanically attached to the specimen mount, and analysis is begun with the sample in the as-received condition. Additional sample preparation is discouraged in many cases because any preparation might modify the surface composition. For those samples where special preparation or mounting cannot be avoided, the following techniques are recommended.

1. Removing Volatile Material

Ordinarily, volatile material is removed from the sample before analysis. In exceptional cases, when the volatile layer is of interest, the sample may be cooled for analysis. The cooling must be to a sufficiently low temperature to guarantee that the volatile element is not warmed to evaporation by any heat load that the analysis conditions may impart.

Removal of unwanted volatile materials is usually accomplished by long-term pumping in a separate vacuum system or by washing with a suitable solvent. Use freshly distilled solvent to avoid contamination by high boiling point impurities within the solvent. Choice of the solvent can be critical. Hexane or other light hydrocarbon solvents are probably least likely to alter the surface, providing the solvent properties are satisfactory. Samples may also be washed efficiently in a Soxhlett extractor using a suitable solvent.

2. Removing Nonvolatile Organic Contaminants

When the nature of an organic contaminant is not of interest or when a contaminant obscures underlying material that is of interest, the contaminant may be removed with appropriate organic solvents. As with volatile materials, the choice of solvent can be critical.

3. Surface Etching

Ion sputter-etching or other erosion techniques, such as the use of an oxygen plasma on organic materials (see Section E.5.a.(3), p. 27), may be used to remove surface contaminants. This technique is particularly useful when removing adventitious hydrocarbons from the sample or when the native oxides, formed by exposure to the atmosphere, are not of interest.

Argon ion etching is commonly used to obtain information on composition as a function of the exposure time to ion etching. Calibration of the sputter rates can be used to convert sputter time to information on depth into the specimen. Because sputtering may cause changes in the surface chemistry, identification of the changes in chemical states with depth may not reflect the true composition.

4. Abrasion

Abrasion of a surface can be done without significant contamination by using a laboratory wipe, a cork, a file or a knife blade. This may cause local heating, and reaction with environmental gases may occur (e.g., oxidation in air and formation of nitrides in nitrogen). To prevent oxidation of more active materials, perform abrasion in an inert atmosphere such as a glove box. The abraded material should then be transferred to the ultra-high vacuum (UHV) chamber in a sealed vessel to preserve the clean surface.

5. Fracturing and Scraping

With proper equipment, many materials can be fractured or scraped within the test chamber under UHV conditions. While this obviates contamination by reaction with atmospheric gases, attention must be given to unexpected results which might occur. Fracturing might occur along the grain boundaries which may not be representative of the bulk material. Scraping can cover hard material with soft material when the sample is multiphase.

6. Grinding to Powder

If spectra characteristic of bulk composition are desired, samples may be ground to a powder in a mortar. Protection of the fresh surfaces from the atmosphere is required. When grinding samples, localized high temperatures can be produced, so grinding should be done slowly to minimize heat-induced chemical changes at the newly created surfaces. The mortar should be well cleaned before reuse.

7. Mounting Powders for Analysis

There are a number of methods which can be used to mount powders for analysis. Perhaps the most widely used method is dusting the powder onto a polymer-based adhesive tape with a camel-hair brush. The powder must be dusted across the surface carefully and lightly, with no wiping strokes. Some researchers shun organic tape for UHV work, but others have successfully used certain types of tape in the 10^{-10} Torr range.

Alternative methods for mounting powders include pressing the powder into indium or other soft foils, supporting the powder on a metallic mesh, pressing the powder into pellets or simply depositing the powder by gravity. With the foil method, the powder is pressed between two pieces of pure foil. The pieces are then separated, and one of them is mounted for analysis. Success with this technique has been varied. Sometimes bare foil remains exposed and, if the sample is an insulator, parts of the powder can charge differently. Differential charging can also be a problem when a metallic mesh is used to support the powder. If a press is used to form the powder into a pellet of workable dimensions, a press with hard and extremely clean working surfaces should be used. Gravity can effectively hold some materials in place, particularly if a shallow well or depression is cut in the surface of the sample mount. Allowing a liquid suspension of the powder to dry on the specimen holder is an effective way of producing a

uniform layer. With these methods, care must be taken in pump-down to ensure that gas evolution does not disturb

the sample. A throttled roughing valve is especially effective.

D. Experimental Procedure

1. Technique for Obtaining Spectra

All spectra in this handbook were obtained using a PHI Model 5600 MultiTechnique system. A schematic diagram of the apparatus (Figure 5) illustrates the relationship of major components, including the electron energy analyzer, the x-ray source, and the ion gun used for sputter-etching. The Model 10-360 Electron Energy Analyzer incorporated into the 5600 is an SCA, and the input lens to the analyzer is an Omni Focus III lens. The excitation sources used were a Model 10-550 x-ray source with a Model 10-410 monochromator and a Model 04-548 dual-anode source which was used with a magnesium anode. All of the spectra in the handbook were taken with the x-ray source operating at 400 W (15 kV - 27 mA). The specimens were analyzed at an electron take-off angle of 70°, measured with respect to the surface plane. The monochromatic x-ray source is located perpendicular to the analyzer axis, and the standard x-ray source is located at 54.7° relative to the analyzer axis.

In the PHI Model 5600 MultiTechnique system, energy distribution, energy resolution and analysis area are all a function of the analyzer. For all of the spectra in this handbook, the spectrometer was operated in a standard mode. The Omni Focus III lens was used to scan the spectrum while the SCA was operated at a constant pass energy. This resulted in constant resolution (ΔE) across the entire energy spectrum. The size of the analysis area was defined by the aperture selection of the Omni Focus III lens. Analyzer energy resolution ($\Delta E/E$) was determined by the choice of pass energy and the selected

aperture. All of the spectra in this handbook were obtained using an 800 μm diameter analysis area.

All of the spectra in this handbook were recorded and stored using the PHI ACCESS™ data system. The instrument was calibrated daily, and the calibration was checked several times each day during data acquisition. The analyzer work function was determined assuming the binding energy of the Au 4f_{7/2} peak to be 84.0 eV. All survey spectra scans were taken at a pass energy of 58.7 eV. The narrow scans of strong lines were, in most cases, just wide enough to encompass the peak(s) of interest and were obtained with a pass energy of 23.5 eV. A lower pass energy may show more structure for some materials. The narrow spectra were necessary to accurately determine the energy, shape and spin-orbit splitting of the strong lines. On insulating samples, a high-resolution spectrum was taken of the adventitious hydrocarbon on the surface of the sample to use as a reference for charge correction. The generally accepted binding energy for adventitious carbon is 284.8 eV.

The samples analyzed to obtain the spectra in this handbook are standard materials of known composition. Metal foils and polycrystalline materials with large surface areas were mechanically fastened to the specimen mount. Powder samples were ground with a mortar and pestle to expose fresh surfaces and were dusted onto adhesive tape. Most elemental standards were sputter-etched immediately prior to analysis to remove surface contamination. Most compounds, however, were ground or cleaved, and the freshly exposed surface was analyzed

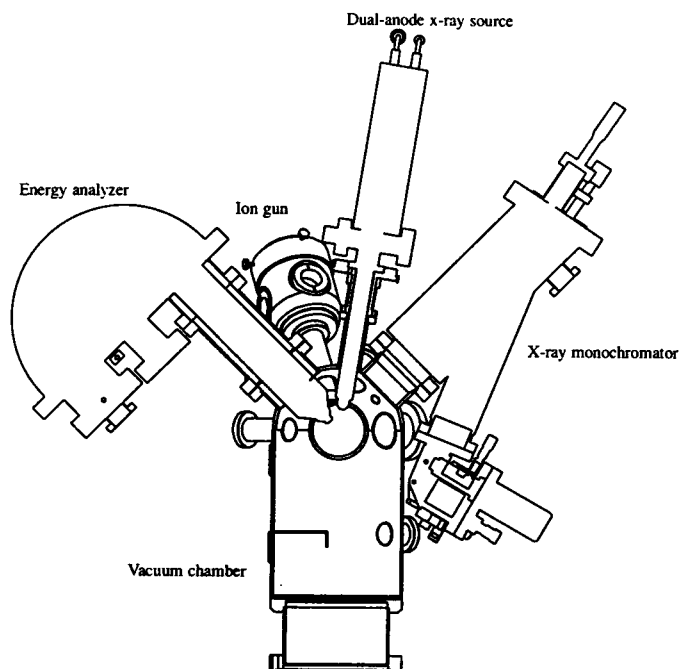


Figure 5. A schematic diagram of the PHI Model 5600 MultiTechnique system.

without etching in order to avoid possible changes in surface chemistry. Ne, Xe and Kr were implanted in graphite and Ar in silicon via ion implantation to unknown concentrations prior to analysis.

2. Instrument Calibration

To ensure the accuracy of the data presented in this handbook, the instrument used to obtain the data was calibrated regularly throughout the data-gathering process. The best way to check calibration, and the method used here, is to record suitable lines from a known, conducting specimen. Typically, the Au 4f or Cu 2p and 3p lines are used. The lines should be recorded with a narrow sweep width in the range of 5-10 eV, and

a pass energy of 23.5 eV or less (corresponding to the pass energy normally used for high resolution scans) should be used.

There is general agreement on accurate values of Cu, Au and Ag standard line energies. The values in Table 1 are recommended for clean Au, Ag and Cu:

Table 1. Reference Binding Energies (eV)

	Al K α	Mg K α
Cu 3p	75.14	75.13
Au 4f _{7/2}	83.98	84.00
Ag 3d _{5/2}	368.26	368.27
Cu L ₃ MM	567.96	334.94
Cu 2p _{3/2}	932.67	932.66
Ag M ₄ NN	1128.78	895.75

from M. P. Seah *Surf. Interface Anal.* **14**, 488 (1989)

Because the 2p_{3/2} and 3p_{3/2} photoelectron peak energies of Cu are widely separated in energy, measurement of these peak binding energies provides a quick and simple means of checking the accuracy of the binding energy scale. Utilizing all of the above standard energies establishes the linearity of the energy scale and its position, i.e., the location of the Fermi level.

3. Programming Scans for an Unknown Sample

For a typical XPS investigation where the surface composition is unknown, a broad scan survey spectrum should be obtained first to identify the elements present. Once the elemental composition has been determined, narrower detailed scans of selected peaks can be used for a more comprehensive picture of the chemical composition. This is the procedure that has been followed in compiling data for this handbook, even though specimen composition was known prior to analysis.

a. Survey Scans. Most elements have major photoelectron peaks below 1100 eV, and a scan range from 1100-0 eV binding energy is usually sufficient to

identify all detectable elements. The spectra in this handbook were recorded with a scan range of 1400-0 eV (Al excitation) or 1200-0 eV (Mg excitation) binding energy. In an unknown sample, if specific elements are suspected at low concentrations, their standard spectra should be consulted before programming the survey scan. If the strongest line occurs above 1100 eV binding energy, the scan range can be modified accordingly.

An analyzer pass energy of 187 eV, in conjunction with the appropriate aperture, is recommended for survey scans with the PHI Model 5600 MultiTechnique system. These settings result in adequate resolution for elemental identification and produce very high signal intensities, minimizing data acquisition time and maximizing elemental detectability.

b. Detail Scans. For purposes of chemical state identification, for quantitative analysis of minor components and for peak deconvolution or other mathematical manipulations of the data, detail scans must be obtained for precise peak location and for accurate registration of line shapes. There are some logical rules for this programming.

- (1) Scans should be wide enough to encompass the background on both sides of the region of in-

terest, yet with small enough step sizes to permit determination of the exact peak position. Sufficient scanning must be done within the time limits of the analysis in order to obtain good counting statistics.

- (2) Peaks from any species thought to be radiation-sensitive or transient should be run first. Otherwise, any convenient order may be chosen.

- (3) No clear guidelines can be given on the maximum duration of data gathering on any one sample. It should be recognized, however, that chemical states have vastly varying degrees of radiation sensitivity and that for any one set of irradiation conditions, there exists for many samples a condition beyond which it is impractical to attempt gathering data.

- (4) With the PHI Model 5600 MultiTechnique system, an analyzer pass energy of 23 eV is normally used for routine detail scans. Where higher energy resolution is needed, lower pass energies can be utilized. For example, the sputter-cleaned Si 2p on p. 56, taken at 23 eV pass energy, can be compared to the chemically etched Si 2p shown in Figure 2 (p. 11).

E. Data Interpretation

1. The Nature of the Spectrum

a. General Features. The spectrum is displayed as a plot of the number of electrons versus electron binding energy in a fixed, small energy interval. The position on the kinetic energy scale equal to the photon excitation energy minus the spectrometer work function cor-

responds to a binding energy of 0 eV with reference to the Fermi level (Equation 1, p. 10). Therefore, a binding energy scale with 0 at that point and increasing to the left is customarily used.

The spectra in this handbook are typical for the various elements. The well-defined peaks are due to electrons

which have not suffered an inelastic energy loss emerging from the sample. Electrons that have lost energy increase the level of the background at binding energies higher than the peak energy. The background is continuous because the energy loss processes are random and multiple. The background in the Mg K α induced spectra is larger than the background in the monochromated Al K α induced spectra because of excitation by Bremsstrahlung radiation of the non-monochromated light.

The "noise" in the spectrum is not instrumental in origin but is the consequence of the collection of single electrons as counts randomly spaced in time. The standard deviation for counts collected in any channel is equal to the square root of the counts so that the percent standard deviation is $100/(\text{counts})^{1/2}$. The signal-to-noise ratio is then proportional to the square root of the counting time. The background level upon which the peak is superimposed is a characteristic of the specimen, the excitation source and the transmission characteristics of the instrument.

b. Types of Lines. Several types of peaks are observed in XPS spectra. Some are fundamental to the technique and are always observed. Others are dependent upon the exact physical and chemical nature of the sample. A third type is the result of instrumental effects. The following describes the various spectral features that are likely to be encountered:

(1) *Photoelectron Lines.* The most intense photoelectron lines are relatively symmetrical and are typically the narrowest lines observed in the spectra. Photoelectron lines of pure metals can, however, exhibit considerable asymmetry due to coupling with conduction electrons. Peak width is a convolution of the natural line width (the lifetime of the "hole" resulting from the photoionization process), the width of the x-ray line which created the photoelectron line and the in-

strumental contribution to the observed line width. Less intense photoelectron lines at higher binding energies are usually wider by 1-4 eV than the lines at lower binding energies. All of the photoelectron lines of insulating solids are of the order of 0.5 eV wider than photoelectron lines of conductors. The approximate binding energies of all photoelectron lines detectable by Al or Mg radiation are cataloged in Appendices G and H.

(2) *Auger Lines.* These are groups of lines in rather complex patterns. There are four main Auger series observable in XPS. They are the KLL, LMM, MNN and NOO series, identified by specifying the initial and final vacancies in the Auger transition. The KLL series, for example, includes those processes with an initial vacancy in the K shell and final double vacancy in the L shell. The symbol V (e.g., KVV) indicates that the final vacancies are in valence levels. The KLL series has, theoretically, nine lines, and others have still more. Because Auger lines have kinetic energies which are independent of the ionizing radiation, they appear on a binding energy plot to be in different positions when ionizing photons of different energies (i.e., different x-ray sources) are used. Core-type Auger lines (with final vacancies deeper than the valence levels) usually have at least one component of intensity similar to the most intense photoelectron line. Positions of the more prominent Auger components are cataloged along with the photoelectron peaks in Appendices G and H.

(3) *X-ray Satellites.* The x-ray emission spectrum from a nonmonochromatic source used for irradiation exhibits not only the characteristic x-ray but also some minor x-ray components at higher photon energies. For each photoelectron peak that results from the routinely used Mg and Al K α x-

ray photons, there is a family of minor peaks at lower binding energies, with intensity and spacing characteristic of the x-ray anode material. The pattern of such satellites for Mg and Al is shown in Table 2. A resultant spectrum using Mg x-rays is shown in Figure 6.

Table 2. X-ray Satellite Energies and Intensities

	$\alpha_{1,2}$	α_3	α_4	α_5	α_6	β
Mg displacement, eV	0	8.4	10.1	17.6	20.6	48.7
relative height	100	8.0	4.1	0.6	0.5	0.5
Al displacement, eV	0	9.8	11.8	20.1	23.4	69.7
relative height	100	6.4	3.2	0.4	0.3	0.6

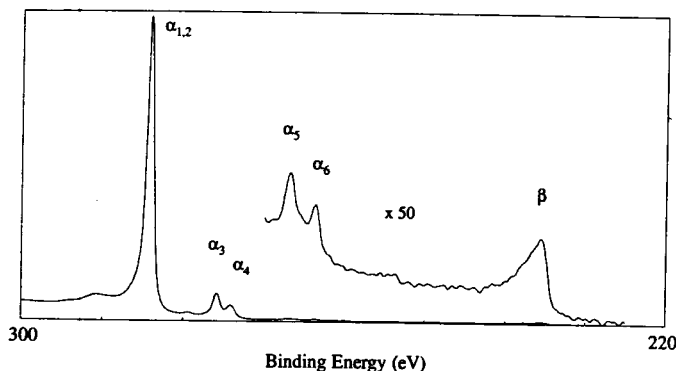


Figure 6. Mg x-ray satellites observed in the C 1s spectrum of graphite.

(4) *X-ray Ghost Lines.* Occasionally, x-radiation from an element other than the x-ray source anode material impinges upon the sample, resulting in small peaks corresponding to the most intense spectral peaks but displaced by a characteristic energy interval. These lines may result from Mg impurity in the Al anode or vice versa, Cu from the anode base structure, oxidation of the anode, or generation of x-ray photons in the Al foil x-ray window. On occasion, such lines can originate via

generation of x-rays within the sample itself. This last possibility is rare because the probability of x-ray emission is low relative to Auger electron emission. Nevertheless, such minor lines can be puzzling. Table 3 indicates where such peaks are most likely to occur relative to the most intense photoelectron lines. Because such ghost lines rarely appear with nonmonochromatic x-ray sources and are not possible with monochromatic x-ray sources, they should not be considered in line identification until all other possibilities are excluded.

Table 3. Displacement of X-ray Ghost Lines (eV)

Contaminating Radiation	Anode Material	
	Mg	Al
O ($K\alpha$)	728.7	961.7
Cu ($L\alpha$)	323.9	556.9
Mg ($K\alpha$)	—	233.0
Al ($K\alpha$)	-233.0	—

(5) *Shake-Up Lines.* Not all photoelectric processes are simple ones which lead to the formation of ions in the ground state, but there is a finite probability that the ion will be left in an excited state a few electron volts above the ground state. In this event, the kinetic energy of the emitted photoelectron is reduced, with the difference corresponding to the energy difference between the ground state and the excited state. This results in the formation of a satellite peak a few electron volts lower in kinetic energy (higher in binding energy) than the main peak. For example, the characteristic shake-up line for carbon in aromatic compounds, a shake-up process involving the energy of the $\pi \rightarrow \pi^*$ transition, is shown in Figure 7.

In some cases, most often with paramagnetic compounds, the intensity of the shake-up satellite may

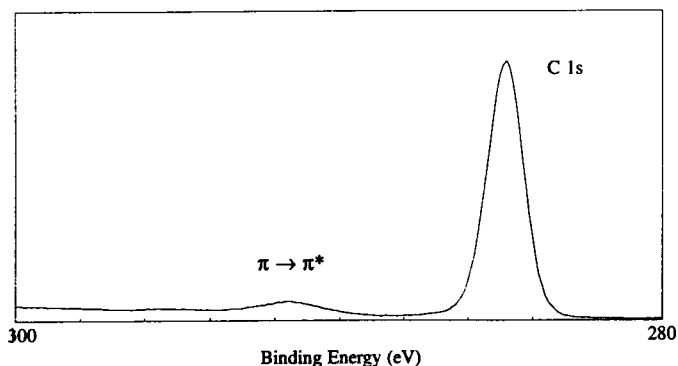


Figure 7. The π bond shake-up satellite for C 1s in polystyrene. The peak is about 6.7 eV higher than the main photopeak.

approach that of the main line. More than one satellite of a principal photoelectron line can also be observed, as shown in Figure 8. The occurrence of such lines is sometimes also apparent in Auger spectral contours (Figure 9). The displacements and relative intensities of shake-up satellites can sometimes be useful in identifying the chemical state of an element, as discussed in Section E.3.d. (p. 24).

(6) *Multiplet Splitting.* Emission of an electron from a core level of an atom that itself has a spin (unpaired electrons in valence levels) can create a vacancy in two or more ways. The coupling of the new unpaired electron left after photoemission from an s-type orbital with other unpaired electrons in the atom can create an ion with several possible final state configurations and as many energies. This results in a photoelectron line which is split asymmetrically into several components similar to the one shown in Figure 10.

Multiplet splitting also occurs in the ionization of p levels, but the result is more complex and subtle. In favorable cases, it results in an apparent slight

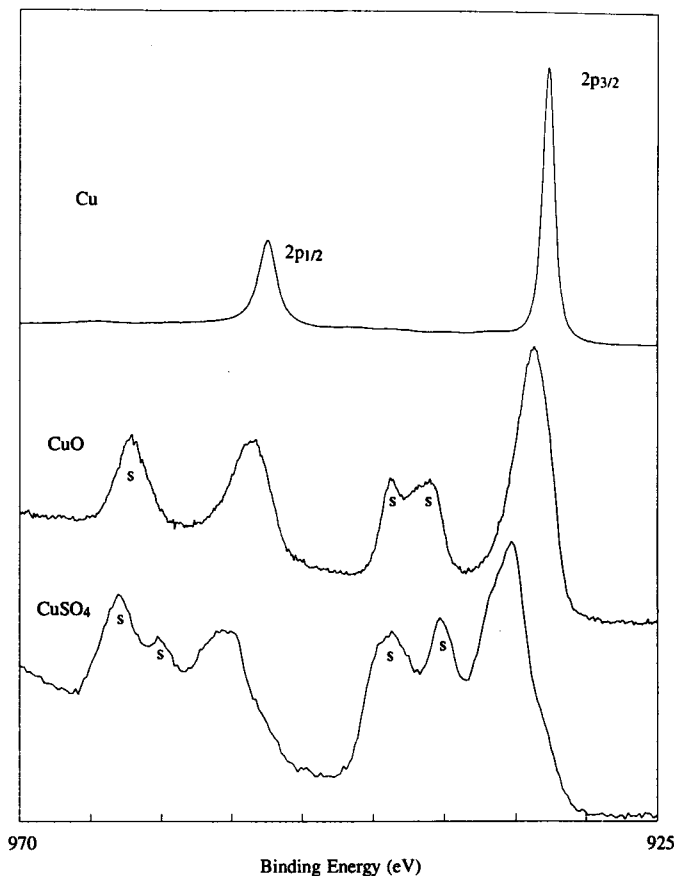


Figure 8. Examples of shake-up lines (s) of the copper 2p observed in copper compounds.

increase in the spin doublet separation, evidenced in the separation of the $2p_{1/2}$ and $2p_{3/2}$ lines in first-row transition metals, and in the generation of a less easily noticed asymmetry in the line shape of the components. Often such effects on the p doublet are obscured by shake-up lines.

(7) *Energy Loss Lines.* With some materials, there is an enhanced probability for loss of a specific

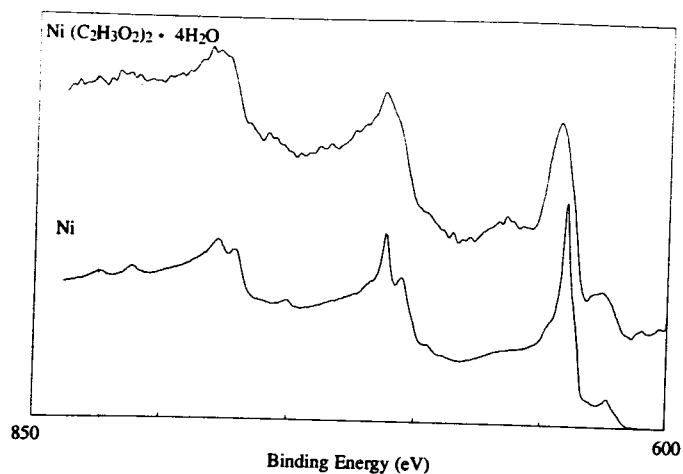


Figure 9. Examples of the effects of chemical states on Auger line shapes in nickel compounds.

amount of energy due to interaction between the photoelectron and other electrons in the surface region of the sample (Figure 11). The energy loss phenomenon produces a distinct and rather sharp hump 20-25 eV above the binding energy of the parent line. Under certain conditions of spectral display, energy loss lines can cause confusion. Such phenomena in insulators are rarely sharper than that shown in Figure 11 and are usually much more muted. They are different in each solid medium.

With metals, the effect is often much more dramatic, as indicated by the loss lines for aluminum shown in Figure 12. Energy loss to the conduction electrons occurs in well-defined quanta characteristic of each metal. These plasmons arise from group oscillations of the conduction electrons. The photoelectron line, or the Auger line, is successively mirrored at intervals of higher binding energy with reduced intensity. The energy

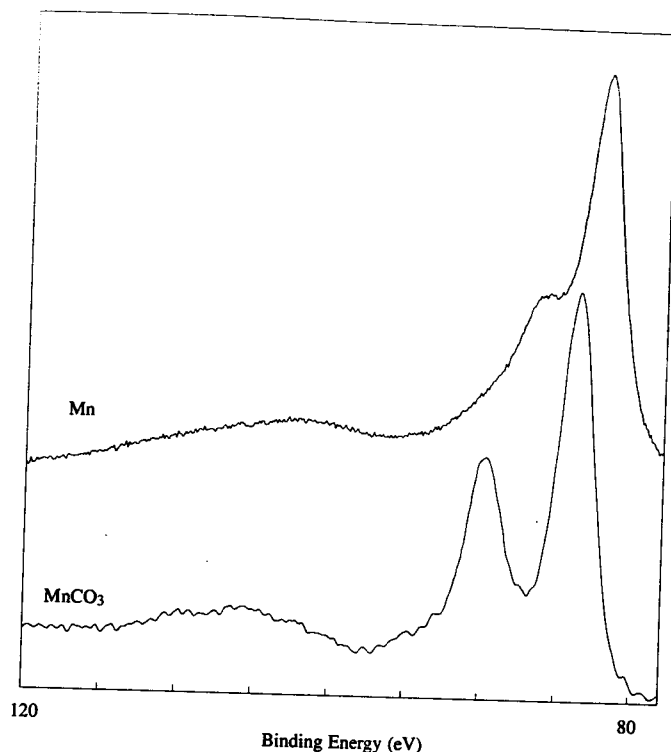


Figure 10. Multiplet splitting of the Mn 3s.

interval between the primary peak and the loss peak is called the plasmon energy. The so-called bulk plasmons are the more prominent of these lines. A second series, the surface plasmons, exists at energy intervals determined approximately by dividing the bulk plasmon energy by the square root of two. The effect is not easily observed in nonconductors, nor is it prominent in all conductors. Plasmon lines are especially prominent in the Groups Ia and IIa metal spectra in this handbook.

(8) *Valence Lines and Bands.* Lines of low intensity occur in the low binding energy region of the

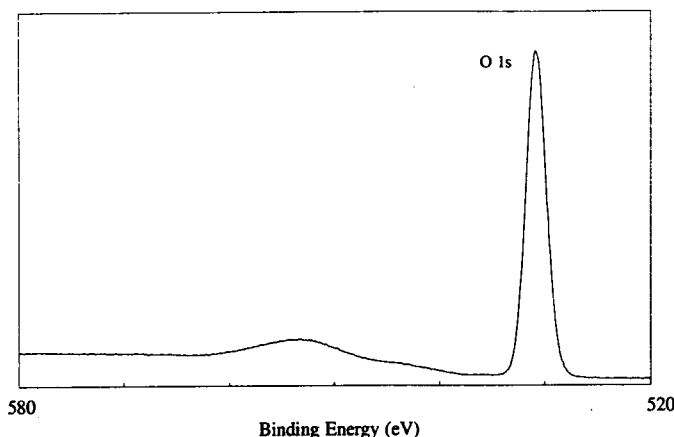


Figure 11. Energy loss envelope from the O 1s line in Al_2O_3 (sapphire).

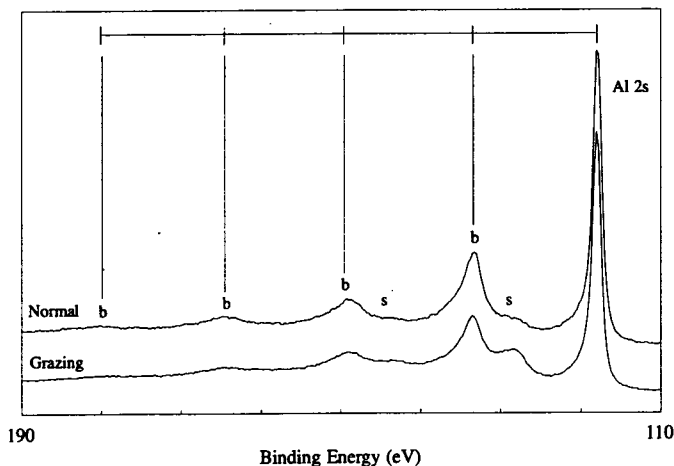


Figure 12. Surface (s) and bulk (b) plasmon lines associated with the Al 2s at normal and grazing take-off angles.

spectrum between the Fermi level and 10-20 eV binding energy. These lines are produced by photoelectron emission from molecular orbitals and from solid state energy bands. Differences be-

tween insulators and conductors are especially noted by the absence or presence of electrons from conduction bands at the Fermi level. Valence bands may also be used to distinguish between materials where the core level XPS photoelectron lines are quite similar in shape and position. Appendix D contains valence band spectra of several materials.

2. Line Identification

In general, interpretation of the XPS spectrum is most readily accomplished first by identifying the lines that are almost always present (specifically those of C and O), then by identifying major lines and associated weaker lines, and lastly by identifying the remaining weak lines. Most modern, commercially available spectrometers have peak identification algorithms within their data reduction packages. Poor signal-to-noise of the data or database limitations may require manual identification of some peaks. The following step-by-step procedure simplifies the data interpretation task and minimizes data ambiguities.

Step 1. The C 1s, O 1s, C (KLL) and O (KLL) lines are usually prominent in any spectrum. Identify these lines first along with all derived x-ray satellites and energy loss envelopes.

Step 2. Identify other intense lines (Appendix J) present in the spectrum, then label any related satellites and other less intense spectral lines associated with those elements. The energy positions of the less intense lines are noted in the line position table with the spectra. Keep in mind that some lines may be interfered with by more intense, overlapping lines from other elements. The most serious interferences by the C and O lines, for example, are Ru 3d by C 1s, V 2p and Sb 3d by O 1s, I (MNN) and Cr (LMM) by O (KLL), and Ru (MNN) by C (KLL).

Step 3. Identify any remaining minor lines. In doing this, assume they are the most intense lines of an unknown element. If not, they should already have been identified in the previous steps. Again, keep in mind possible line interferences. Small lines that seem unidentifiable can be ghost lines. Use Table 3 (p. 18) to check for the more intense parent photoelectron lines.

Step 4. Check the conclusions by noting the spin doublets for p, d and f lines. They should have the right separation (cf. spin orbit splitting for individual elements and Appendices G and H) and should be in the correct intensity ratio. The ratio for p lines should be about 1:2, d lines 2:3 and f lines 3:4. P lines, especially 4p lines, may be less than 1:2.

3. Chemical State Identification

The identification of chemical states primarily depends on the accurate determination of line energies. To determine line energies accurately, the voltage scale of the instrument must be precisely calibrated (cf. Section D.2., p. 15), a line with a narrow sweep range must be recorded with good statistics (of the order of several thousand counts-per-channel above background), and accurate correction must be made for static charge if the sample is an insulator.

a. Determining Static Charge on Insulators. During analysis, insulating samples tend to acquire a steady-state charge of as much as several volts. This steady-state charge is a balance between electron loss from the surface by emission and electron gain by conduction or by acquisition of slow or thermal electrons from the vacuum. The steady-state charge, usually positive, can be minimized with an adjacent neutralizer or flood gun. It is often advantageous to do this to reduce differential charging and sharpen the spectral lines.

A serious problem is exactly determining the extent of charging. Any positive charging retards outgoing

electrons and tends to make the peaks appear at higher binding energies, whereas excessive charge compensation can make the peaks shift to lower binding energies. The following are four methods which are usually valid for charge correction on insulating samples:

(1) Measurement of the position of the C 1s line from adventitious hydrocarbon nearly always present on samples introduced from the laboratory environment or from the glove box. This line, on unsputtered inert metals such as Au or Cu, appears at 284.8 eV, so any shift from this value can be taken as a measure of the static charge. At this time, it is not known whether a reproducible line position exists for C remaining on the surface after ion beam etching.

(2) The use of an internal standard, such as a hydrocarbon moiety of a polymer sample. For the study of supported catalysts or similar materials, one can adopt a suitable value for a constituent of the support and use that to interrelate binding energies of different samples. One must be certain that treatments of the various samples are not so different that the inherent binding energies of support constituents are changed.

(3) The use of a normally insulating sample so thin that it effectively does not insulate. This can be assumed if the spectrum of the underlying conductor appears in good intensity and if line positions are not affected by changes in electron flux from the charge neutralizer.

(4) For the study of insulating polymer films, binding energies of the C functional groups may also be determined by applying a small amount of poly(dimethyl siloxane) solution (10^{-6} M) to the sample surface and charge reference to the Si 2p of the silicone (at about 102.1 eV).

Some precautions should be kept in mind. If the sample is heterogeneous on even a micrometer scale, particles of different materials can be charged to different extents, and interpretation of the spectrum is complicated accordingly. One cannot physically mix a conducting standard like Au or graphite of micron dimensions with a powder and validly use the Au or graphite line in order to correct for static charge. Differential charging can be minimized to a great extent by using a flood source of low-energy electrons.

b. Photoelectron Line Chemical Shifts and Separations. An important advantage of XPS is its ability to obtain information on chemical states from the variations in binding energies, or chemical shifts, of the photoelectron lines. While many attempts have been made to calculate chemical shifts and absolute binding energies, the factors involved (especially in the solid state) are imperfectly understood, and one must rely on experimental data from standard materials. The tables accompanying the spectra in this handbook record considerable data from the literature as well as data obtained specifically for this handbook. All literature data have been carefully evaluated to the instrumental calibration and static charge reference values given above and are, therefore, directly comparable.

Because occasional line interferences do occur, it is sometimes necessary to use a line other than the most intense one in the spectrum. Chemical shifts of a minor line are within 0.2 eV of the chemical shift of the primary line. However, exceptional separations can occur in paramagnetic materials because of multiplet splitting. Separations of photoelectron lines can be determined approximately from the line position tables in Appendices G and H.

c. Auger Line Chemical Shifts and the Auger Parameter. Core-type Auger lines (transitions ending with double vacancies below the valence levels) usually have at least one component that is narrow and intense,

often nearly as intense as the strongest photoelectron line (cf. spectra for F, Na, As, In, Te and Pb). There are four core Auger groups that can be generated by Mg or Al x-rays: the KLL (Na, Mg); the LMM (Cu, Zn, Ga, Ge, As, Se); the MNN (Ag, Cd, In, Sn, Sb, Te, I, Xe, Cs, Ba); and NOO (Th, U). The MNN lines in the rare earths, while accessible, are very broad because of multiplet splitting and shake-up phenomena with most of the compounds. Valence-type Auger lines (final states with vacancies in valence levels) — such as those for O and F (KLL); Mn, Fe, Co and Ni (LMM); and Ru, Rh and Pd (MNN) — can be intense and are, therefore, also useful. Chemical shifts occur with Auger lines as well as with photoelectron lines. The chemical shifts are different from those of the photoelectron lines, but they are often more pronounced. This can be very useful for identifying chemical states, especially in combination with photoelectron chemical shift data. If data for the various chemical states of an element are plotted with the binding energy of the photoelectron line on the abscissa and the kinetic energy of the Auger line on the ordinate, a two-dimensional chemical state plot can be obtained. Such plots are in Appendix A for F, Na, Al, Si, S, Cu, Zn, As, Se, Ag, Cd, In, Sn and Te.

With chemical states displayed in two dimensions, the Auger parameter method becomes more powerful as a tool for identifying the chemical components than using photoelectron chemical shifts alone. In the format adopted for this handbook, the kinetic energy of the Auger line is plotted against the binding energy of the photoelectron line, with the latter plotted in the -x direction (kinetic energy is still, implicitly, +x). The kinetic energy of the Auger electron, referred to the Fermi level, is easily calculated by subtracting from the photon energy the position of the Auger line on the binding energy scale.

With this arrangement, each diagonal line represents all values of equal sums of Auger kinetic energy and

photoelectron binding energy. The Auger parameter, α , is defined as,

$$\alpha = KE_A - KE_P = BE_P - BE_A \quad (2)$$

or as the difference in binding energy between the photoelectron and Auger lines. This difference can be accurately determined because static charge corrections cancel. With all kinetic and binding energies referenced to the Fermi level, and recalling that:

$$KE = h\nu - BE \quad (3)$$

then...

$$KE_A + BE_P = h\nu + \alpha \quad (4)$$

or the sum of the kinetic energy of the Auger line and the binding energy of the photoelectric line equals the Auger parameter plus the photon energy. A plot showing Auger kinetic energy versus photoelectron binding energy then becomes independent of the photon energy.

In general, polarizable materials, especially conductive materials, have a high Auger parameter, while insulating compounds have a lower Auger parameter.

d. Chemical Information from Satellite Lines and Peak Shapes

(1) *Shake-up Lines.* These satellite lines have intensities and separations from the parent photoelectron line that are unique to each chemical state (Figure 8, p. 19). Some Auger lines also exhibit radical changes with chemical state that reflect these processes (Figure 9, p. 20). With transition elements and rare earths, the absence of shake-up satellites is usually characteristic of the elemental or diamagnetic states. Prominent shake-up patterns typically occur with paramagnetic states. Table 4 is a guide to some expected paramagnetic states.

Table 4. General Guide to Paramagnetic Species

Multiplet splitting and shake-up lines are generally expected in the paramagnetic states below:

Atomic No.	Paramagnetic States	Diamagnetic States
22	Ti(II) Ti(III)	Ti(IV)
23	V(II), V(III), V(IV)	V(V)
24	Cr(II), Cr(III), Cr(IV), Cr(V)	Cr(VI)
25	Mn(II), Mn(III), Mn(IV), Mn(V)	Mn(VII)
26	Fe(II), Fe(III)	K ₄ Fe(CN) ₆ , Fe(CO) ₄ Br ₂
27	Co(II), Co(III)	CoB, Co(NO ₂) ₃ NH ₃ , K ₃ Co(CN) ₆ , Co(NH ₃) ₆ Cl ₃
28	Ni(II)	K ₂ Ni(CN) ₄ , square planar complexes
29	Cu(II)	Cu(I)
42	Mo(IV), Mo(V)	Mo(VI), MoS ₂ , K ₄ Mo(CN) ₈
44	Ru(III), Ru(IV), Ru(V)	Ru(II)
47	Ag(II)	Ag(I)
58	Ce(III)	Ce(IV)
59-70	Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb compounds	
74	W(IV), W(V)	W(VI), WO ₂ , WCl ₄ , WC, K ₄ W(CN) ₈
75	Re(II), Re(III), Re(IV), Re(V), Re(VI)	Re(VII), ReO ₃
76	Os(III), Os(IV), Os(V)	Os(II), Os(VI), Os(VIII)
77	Ir(IV)	Ir(III)
92	U(III), U(IV)	U(VI)

(2) *Multiplet Splitting.* On occasion, the multiplet splitting phenomenon can also be helpful in identifying chemical states. The 3s lines in the first series of transition metals, for example, exhibit separations characteristic of each paramagnetic chemical state. The 3s line, however, is weak and therefore is not often useful analytically. The 2p doublet separation is also affected by multiplet splitting, and the lines are more intense. The effect becomes very evident with Co compounds where the separation varies up to 1 eV. When first-row transition metal compounds are under study, it is

useful to accurately record these line separations and make comparisons with model compounds.

(3) *Auger Line Shape.* Valence-type Auger transitions form final-state ions with vacancies in molecular orbitals. The distribution of the group of lines is strongly affected, therefore, by the nature of the molecular orbitals in the different chemical states. Although little has yet been tabulated on this subject, the spectroscopist should bear in mind the possible utility of Auger line shapes.

4. Quantitative Analysis

For many XPS investigations, it is important to determine the relative concentrations of the various constituents. Methods have been developed for quantifying the XPS measurement utilizing peak area and peak height sensitivity factors. The method which utilizes peak area sensitivity factors typically is the more accurate and is discussed below. This approach is satisfactory for quantitative work. For transition metal spectra with prominent shake-up lines, it is best to include the entire 2p region when measuring peak area.

For a sample that is homogeneous in the analysis volume, the number of photoelectrons per second in a specific spectra peak is given by:

$$I = nf\sigma\theta y\lambda AT \quad (5)$$

where n is the number of atoms of the element per cm^3 of the sample, f is the x-ray flux in photons/ $\text{cm}^2\text{-sec}$, σ is the photoelectric cross-section for the atomic orbital of interest in cm^2 , θ is an angular efficiency factor for the instrumental arrangement based on the angle between the photon path and detected electron, y is the efficiency in the photoelectric process for formation of photoelectrons of the normal photoelectron energy, λ is the mean free path of the photoelectrons in the sample, A is the area of the sample from which photoelectrons

are detected, and T is the detection efficiency for electrons emitted from the sample. From Equation 5:

$$n = I/f\sigma\theta y\lambda AT \quad (6)$$

The denominator in Equation 6 can be defined as the atomic sensitivity factor, S . If we consider a strong line from each of two elements, then:

$$\frac{n_1}{n_2} = \frac{I_1/S_1}{I_2/S_2} \quad (7)$$

This expression may be used for all homogeneous samples if the ratio S_1/S_2 is matrix-independent for all materials. It is certainly true that such quantities as σ and λ vary somewhat from material to material (especially λ), but the ratio of each of the two quantities σ_1/σ_2 and λ_1/λ_2 remains nearly constant. Thus, for any spectrometer, it is possible to develop a set of relative values of S for all of the elements. Multiple sets of values may be necessary for instruments with multiple x-ray sources at different angles relative to the analyzer.

A general expression for determining the atom fraction of any constituent in a sample, C_x , can be written as an extension of Equation 7:

$$C_x = \frac{n_x}{\sum n_i} = \frac{I_x/S_x}{\sum I_i/S_i} \quad (8)$$

Values of S based on peak area measurements are indicated in Appendices E and F. The values of S in the appendices are based on empirical data (C.D. Wagner et al. *Surf. Interface Anal.* 3, 211 (1981)) which have been corrected for the transmission function of the spectrometer. The values in the appendix are only valid for and should only be applied when the electron energy analyzer used has the transmission characteristics of the SCA supplied by Physical Electronics. An example of the application of Equation 8 to analysis of a

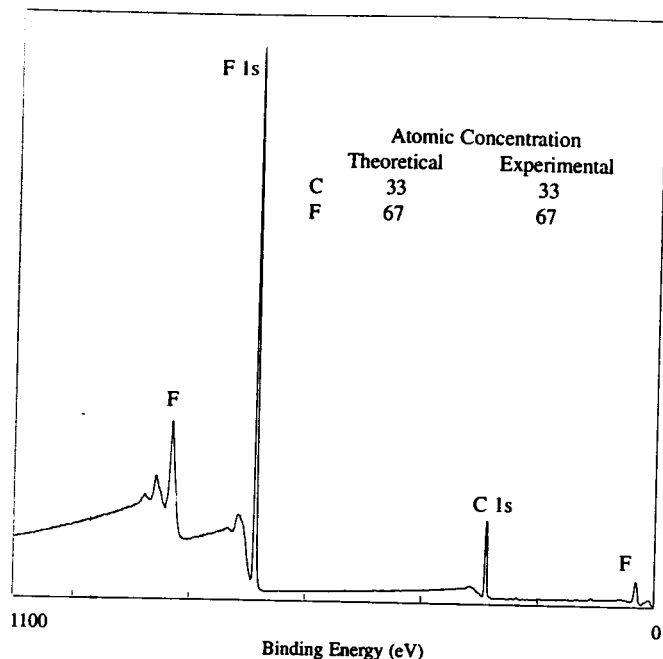


Figure 13. Quantitative analysis of poly(tetrafluoroethylene).

sample of known composition, poly(tetrafluoroethylene), is shown in Figure 13.

The use of atomic sensitivity factors in the manner described will normally furnish semiquantitative results (within 10-20%), except in the following situations:

a. The technique cannot be applied rigorously to heterogeneous samples. It can be useful with heterogeneous samples in measuring the relative number of atoms detected, but one must be conscious that the microscopic character of the heterogeneous system influences the quantitative results. Moreover, an overlying contamination layer has the effect of diminishing the intensity of high binding energy peaks more than that of low binding energy peaks.

b. Transition metals, especially of the first series, have widely varying and low values of γ , whereas γ for the other elements is rather uniform at about 0.8 eV. Thus, a value of S determined on one chemical state for a transition metal may not be valid for another chemical state. This effect can be minimized by including shake-up peaks in the area measurement.

c. When peak interferences occur, alternative lines must sometimes be used. The ratios of spin doublets (except 4p) are rather uniform, and the weaker of the pair can often be substituted. The spectra of the elements should be consulted, but caution must be exercised because the spectra of the elements themselves can be different from the spectra of their compounds.

d. Occasionally, an x-ray satellite from an intense photoelectron line interferes with measurement of a weak component. A mathematical approach can then be used to subtract the x-ray satellite before the measurement.

For quantitative work, check the spectrometer operation frequently to ensure that analyzer response is constant and optimum. A useful test is the recording of the three widely spaced spectral lines from Cu. Measurement of the peak height in counts-per-second should be made on 20-volt-wide scans of the 2p_{3/2}, LMM Auger and 3p lines. Maintenance of such records makes it easy to notice if an instrument change occurs that would affect quantitative analysis.

5. Determining Element Location

a. **Depth.** There are four methods of obtaining information on the depth of an element in the sample. The first two methods described below utilize the characteristics of the spectrum itself but provide limited information. The third provides more detailed information but is attended by certain problems. The fourth utilizes measurements at two or more electron escape angles.

(1) The presence or absence of an energy loss peak or envelope indicates whether the emitting atoms are in the bulk or at the surface. Because electrons from surface atoms do not traverse the bulk, peaks from the surface atoms are symmetrical above level baselines on both sides, and the energy loss peak is absent. For a homogeneous sample, peaks from all elements will have similar inelastic loss structures.

(2) Elements whose spectra exhibit photoelectron lines widely spaced in kinetic energy can be approximately located by noting the intensity ratio of the lines. In the energy range above approximately 100 eV, electrons moving through a solid with lower kinetic energy are attenuated more strongly than those with higher kinetic energy. Thus, for a surface species, the low kinetic energy component will be relatively stronger than the high kinetic energy component, compared to that observed in the pure material. The data for homogeneous bulk solids can be compared with intensity ratios observed on unknowns to determine qualitatively the distribution of the element in the sample. Suitable elements include Na and Mg (1s and 2s); Zn, Ga, Ge and As (2p_{3/2} and 3d); and Cd, In, Sn, Sb, Te, I, Cs and Ba (3p_{3/2} and 4d or 3d_{5/2} and 4d).

When the element is in a bulk homogeneous layer beneath a thin contaminating layer, the characteristic intensity ratio is modified in the opposite direction. Thus, for a pair of lines from subsurface species, the low kinetic energy line will be attenuated more than the high kinetic energy line, distorting the characteristic intensity ratio. By observing such intensity ratios and comparing them with the pure bulk elements, it is possible to deduce whether the observed lines are from predominantly surface-, subsurface- or homogeneously distributed material.

(3) Depth profiling can be accomplished using controlled erosion of the surface by ion sputtering. Table 5 lists some data on sputter rates as a general guide. One can use this technique on organic materials, but few data are available for calibration. Chemical states are often changed by the sputter technique, but useful information on elemental distribution can still be obtained.

Table 5. Relative Sputter Rates at 4 kV.

Target	Sputter Rate
Ta ₂ O ₅	1.00
Si	0.90
SiO ₂	0.85
Pt	2.20
Cr	1.40
Al	0.95
Au	4.10

Another useful method of controlled erosion, especially of organic materials, is reaction with oxygen atoms from a plasma. This technique may also change the chemical states in the affected surface. Further, because the elements differ in their rates of reaction with oxygen atoms, the rate of removal of surface materials will be sample dependent.

(4) In XPS studies, the sample-mounting angle is not usually critical, though it does have some effect on the spectra. Very shallow electron take-off angles accentuate the spectrum of any component segregated on the surface, whereas a sample mounted at an angle normal to the analyzer axis minimizes the contribution from such a component. This effect can be used to estimate the depth of layers on or in the surface. This effect is not limited to flat surfaces, because angular dependence is even observed with powders, though the effects are muted. The spectrometer used to obtain the spectra presented in this handbook in-

tegrates the signal over only a narrow range of take-off angles.

It is possible to change the angle between the plane of the sample surface and the angle of entrance to the analyzer. At 90° with respect to the surface plane, the signal from the bulk is maximized relative to that from the surface layer. At small angles, the signal from the surface becomes greatly enhanced, relative to that from the bulk. The location of an element can thus be deduced by noting how the magnitude of its spectral peaks changes with sample orientation in relation to those from other elements. The analysis depth may be estimated by $d = \lambda \sin \theta$, where d is the analysis depth of the overlayer, λ is the inelastic mean free path, and θ is the take-off angle of the analyzed electrons.

Physical Electronics SCAs permit angle-dependent studies by simply varying the angle of the sample surface with respect to the input lens of the analyzer. The magnification of the lens determines the half-angle acceptance of the analyzer. An example of the information that can be gained through the use of this capability is shown in Figure 14. Data were obtained at normal (near 90°) and grazing (near 15°) take-off angles from a silicon sample with a thin silicon oxide overlayer. The observed intensity ratio of oxidized to elemental Si is much greater at the low take-off angle.

b. Surface Distribution. Many XPS systems have the capability to obtain data from areas as small as $30 \mu\text{m}$ in diameter using lens defined areas. Alternately, analysis areas of $< 10 \mu\text{m}$ can be achieved with a scanning focused photo beam. These relatively high lateral resolutions allow for the acquisition of XPS maps which show both elemental and chemical state information.

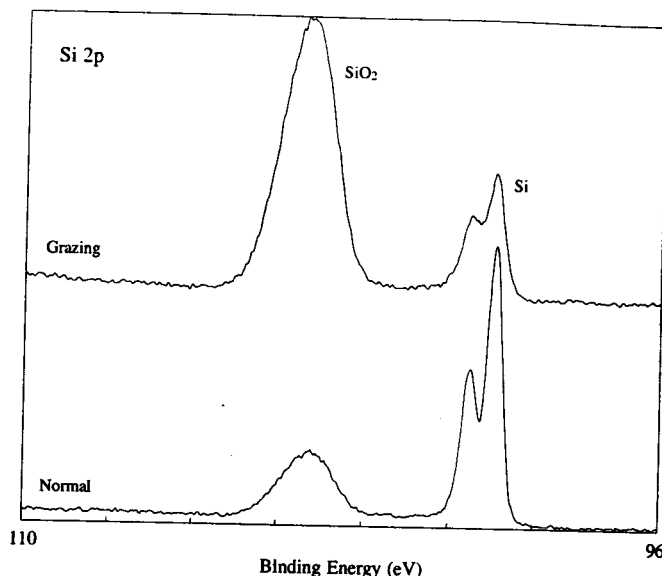


Figure 14. An example of the enhanced surface sensitivity achieved by varying the electron take-off angle. A thin oxide on silicon is enhanced at the low take-off angle.

c. Insulating Domains on a Conductor. The occurrence of steady-state charging of an insulator during analysis sometimes has useful consequences. Microscopic insulating domains on a conductor reach their own steady-state charge, while the conductor remains at spectrometer potential. Thus, an element in the same chemical state in both phases will exhibit two peaks. If a change is made in the supply of low-energy electrons which stabilize the charge (as from the neutralizer filament) or if a bias is applied to the conductor, the spectral peaks from the insulating phase will move relative to those from the conducting phase. For such heterogeneous systems, this can be an extremely useful technique. It makes it possible to determine whether the elements that contribute to the overall spectrum are in the conducting phase, the insulating phase or both.

F. How to Use this Handbook

1. Qualitative Analysis

Elemental and chemical identification of sample constituents can be performed by combining the information in the survey spectra with the binding energy tables of Appendices G, H and J.

a. Identify all major photoelectron peaks by using the line position tables in Appendix J.

b. Compare the elemental identifications with the elemental survey spectra to see that line positions and relative intensities are consistent. Also note the positions of the Auger electron peaks.

c. Review Section E (pp. 16-28) to account for fine structures such as energy loss lines, shake-up peaks, satellite lines, etc., not identified in the handbook spectra or energy tables.

d. Identify any remaining peaks assuming they are intense photoelectron or Auger lines using Appendices G or H.

e. Chemical state identification can be determined from high resolution spectra of the strongest photoelectron and sharpest Auger lines.

(1) Correct binding energies for static charging of insulators. When applicable, charge reference the binding energy scale to the C 1s photoelectron peak at 284.8 eV.

(2) Determine the chemical state from the measured shifts in the photoelectron binding ener-

gies by comparing the binding energy to the charts with the standard spectra and with the tabulated data in Appendix B.

(3) As suggested above, much about the chemical state can be learned from the magnitude and position of shake-up lines as well as from the energy and shape of valence Auger lines.

(4) For the elements F, Na, Al, Si, S, Cu, Zn, As, Se, Ag, Cd, In, Sn and Te, the Auger parameter tables in Appendix A may prove useful. The Auger line positions may be converted to kinetic energy by subtracting from the photon energy ($Al = 1486.6$ eV, $Mg = 1253.6$ eV). Note the location of the points for Auger kinetic energy and photoelectron binding energy on the respective elemental plot. Proximity of the experimental points to those of recorded chemical states should be considered probable identification. Note that experimental error is much greater along the Auger parameter grid than normal to the grid lines.

2. Quantification

The atomic sensitivity factors presented in Appendices E and F are applicable to the Physical Electronics Model 10-360 SCA and the Omni Focus III lens. A simplified expression to determine the atomic concentration of any element is given by Equation 8 (p. 25). However, the accuracy is limited by the assumptions made in Section E.4. (p. 25).

II. Standard XPS Spectra of the Elements

Standard Spectra of the Elements

This section of the handbook contains survey spectra of 81 elements, high resolution spectra of the most useful photoelectron lines, a chart of binding energies for each of the observed photoelectron and major Auger electron peaks, and a photoelectron chemical state binding energy chart for each of the elements. Used in combination with the appendices, the survey spectra aid in elemental identification, while the high-resolution spectra and binding energy data aid in the identification of chemical states.

Survey Spectra

The survey data include all of the lines which are normally useful. For most elements, the survey data were acquired with both a monochromatic Al x-ray source and a nonmonochromatic Mg x-ray source. When survey spectra for two compounds are presented, the monochromatic source is used for both. The photon source for each survey is noted on the survey. The photoelectron and Auger lines for the element of interest are identified. Lines which occur due to other

elements are only designated by the elemental symbol, and x-ray satellites and energy loss lines are not noted. For many elements, the Auger peaks are presented in expanded form.

The ordinate is left undesignated, but the general contours and intensity ratios of the spectra are typical of measurements made using a Physical Electronics Model 10-360 SCA with an Omni Focus lens.

High-Resolution Spectra

The high-resolution spectra of the most useful photoelectron peaks are presented. Unless otherwise noted, the high-resolution data were acquired using the same photon source as the survey on the same page. The binding energy of the main line is noted and when appropriate, the spin orbit separation (Δ) is given. The lines from insulators were charge-corrected to adventitious hydrocarbon at 284.8 eV.

The spectra of the inert gas atoms implanted in graphite or silicon deserve special mention. The high-resolution data often show an asymmetric peak shape or a second resolvable peak when a single symmetric peak is expected. The intensity of the second, high binding energy peak is dependent on the implantation energy and is diminished at lower energies. The spectra are of inert gas atoms implanted at 4 kV.

Photoelectron and Auger Electron Line Position Tables

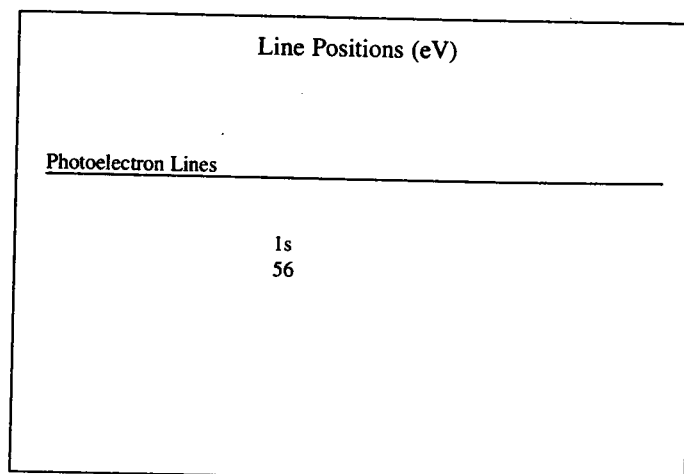
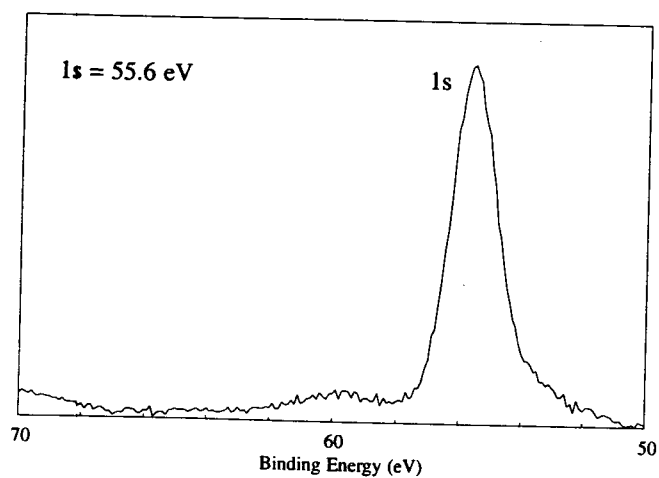
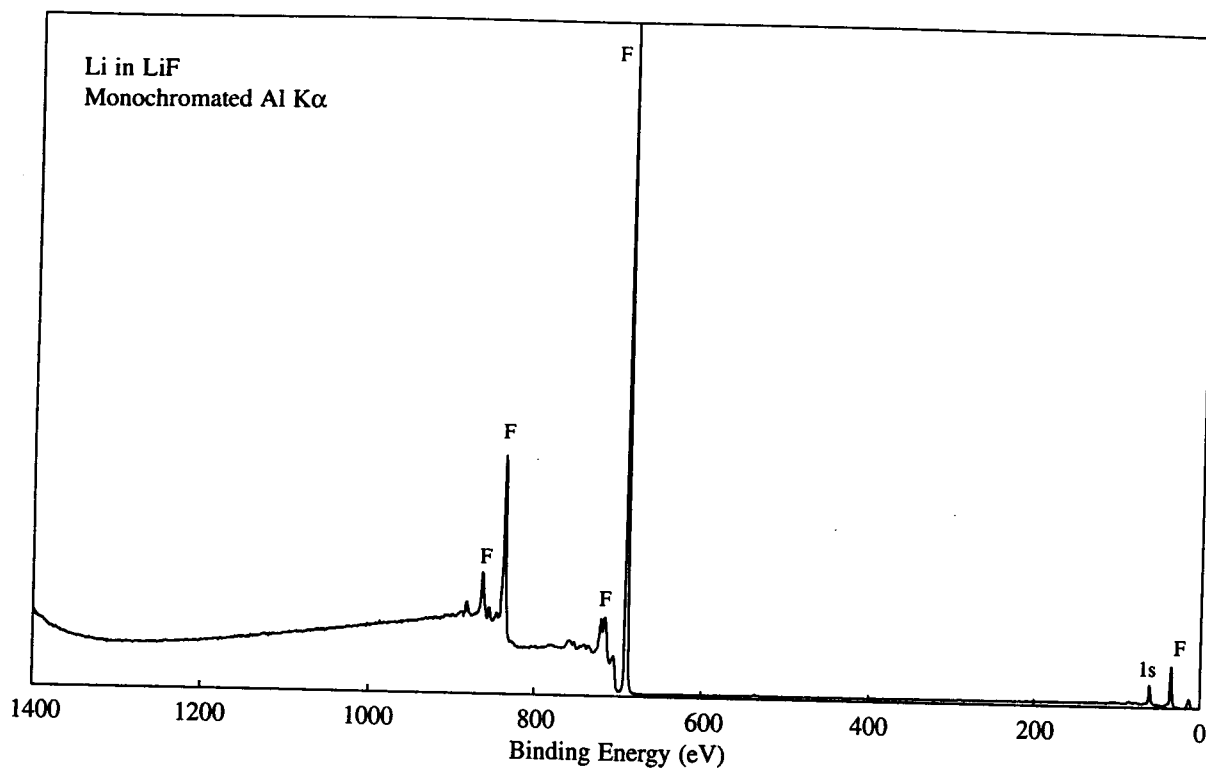
The photoelectron and Auger line position tables reflect the energies of the elemental peaks observed in this handbook. For oxidized or

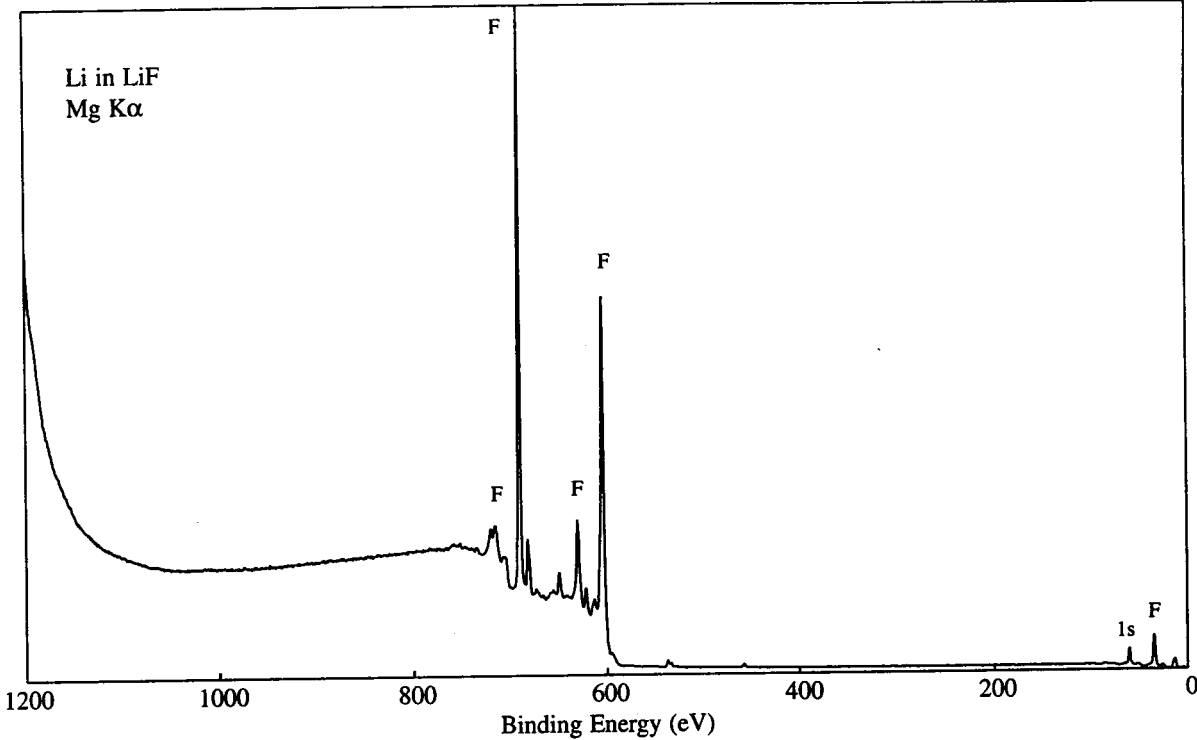
reduced species, the measured values may differ by a few electron volts.

Chemical State Binding Energy Tables

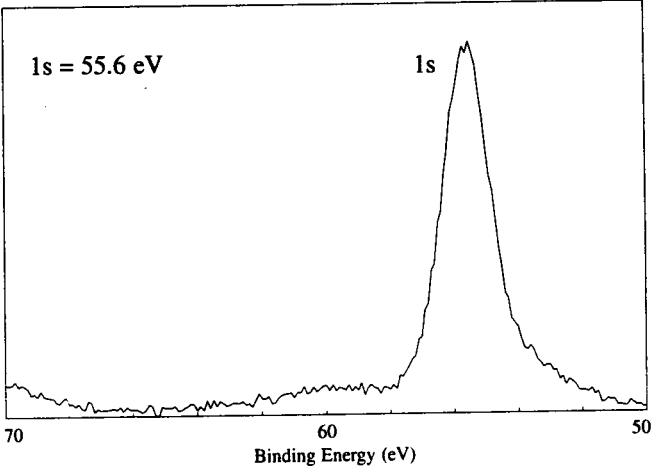
The binding energy tables have been constructed to reflect the general changes in binding energy with change in oxidation state or chemical environment. A more extensive listing with specific binding energy values for more than 1500 compounds is presented in Appendix B.

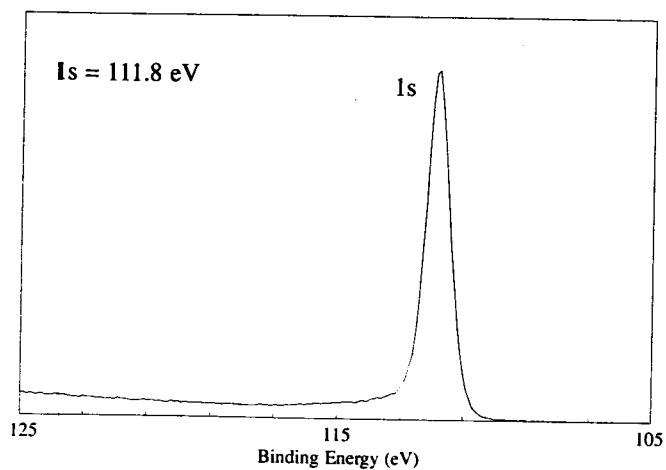
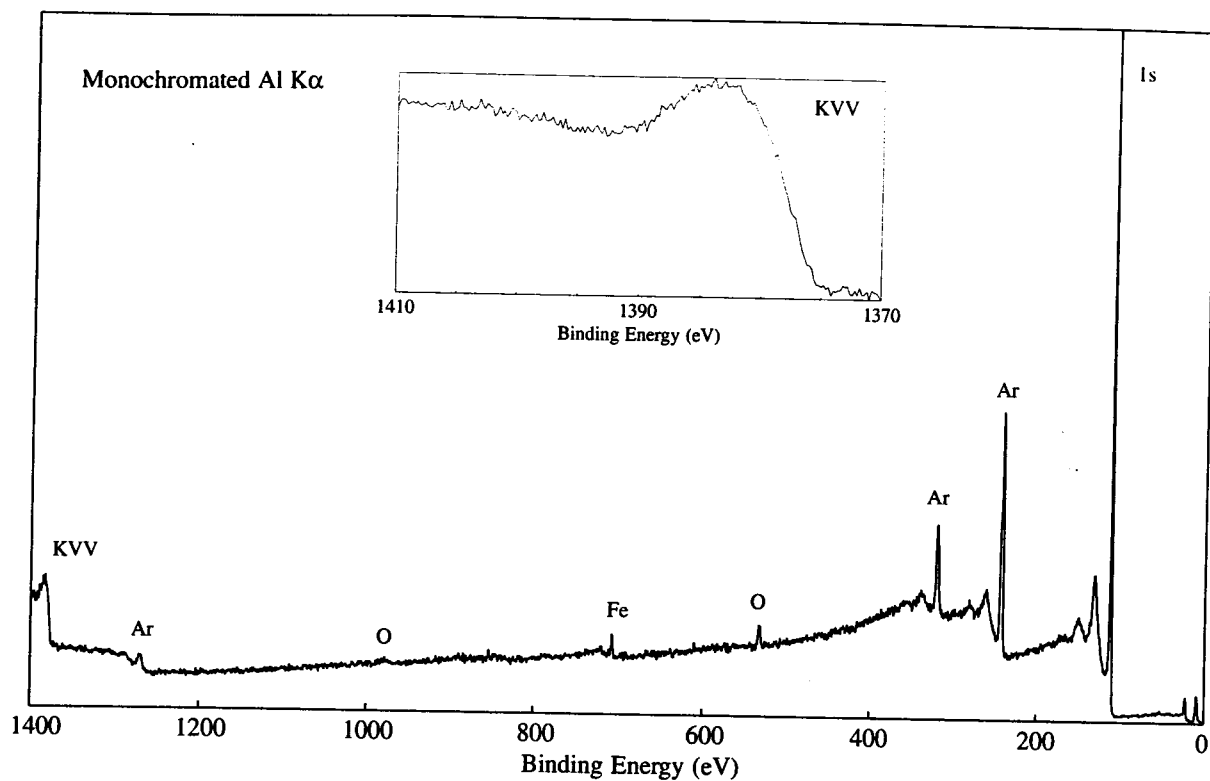
Abbreviations in the chemical state database are as follows: acac = acetyl acetate; metallocene = metal (C_5H_5)₂; Bu = butyl; Et = ethyl; Me = methyl; Ph = phenyl; OAc = acetate.



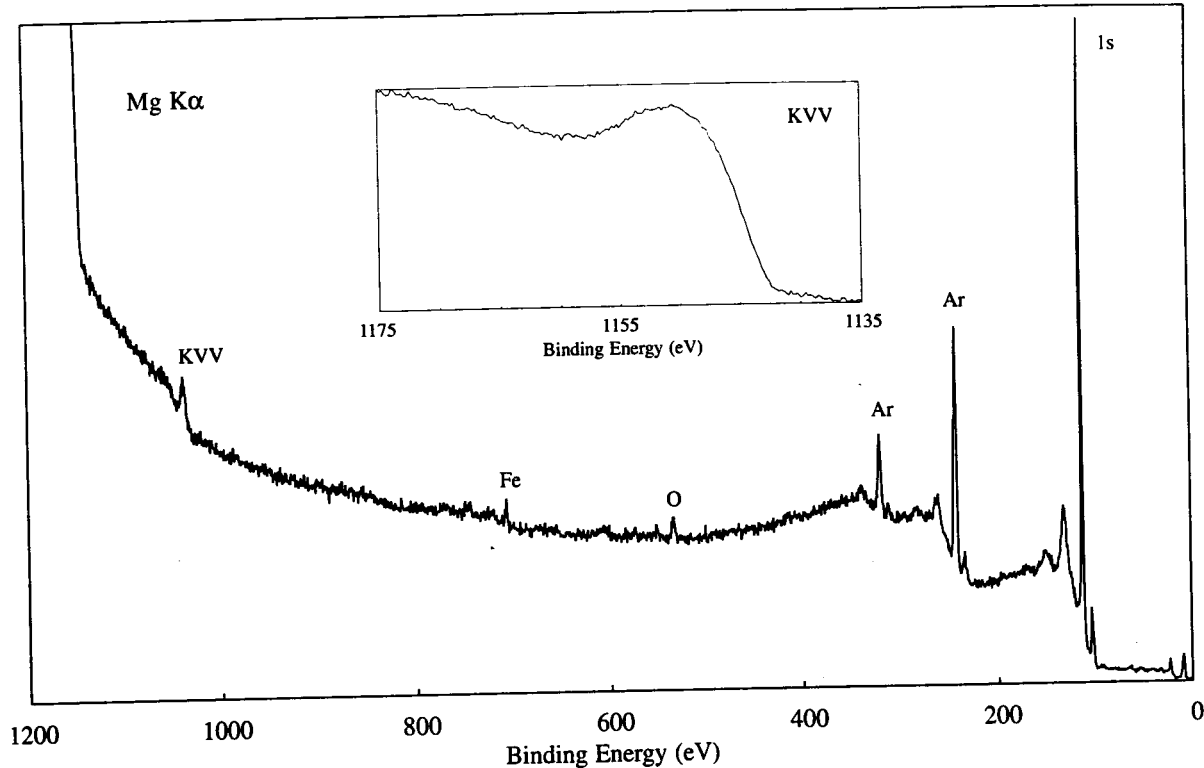


1s Binding Energy (eV)				
Compound Type	54	55	56	57
Li				
LiBr				
LiCl				
LiF				
Li ₂ O				
LiOH				
Li ₂ CO ₃				
Li ₃ PO ₄				
Li ₄ P ₂ O ₇				
LiNbO ₃				

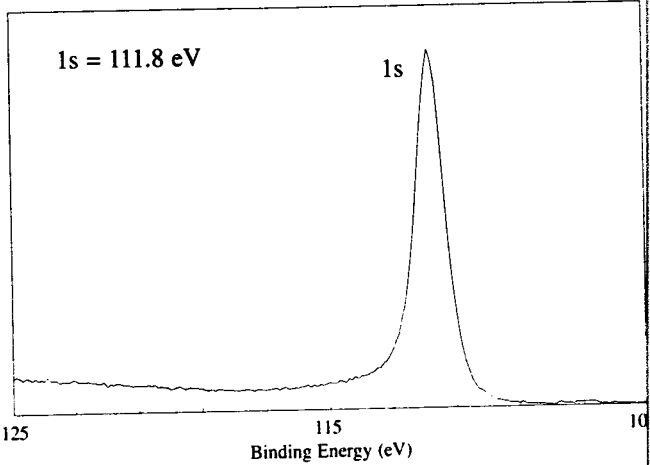


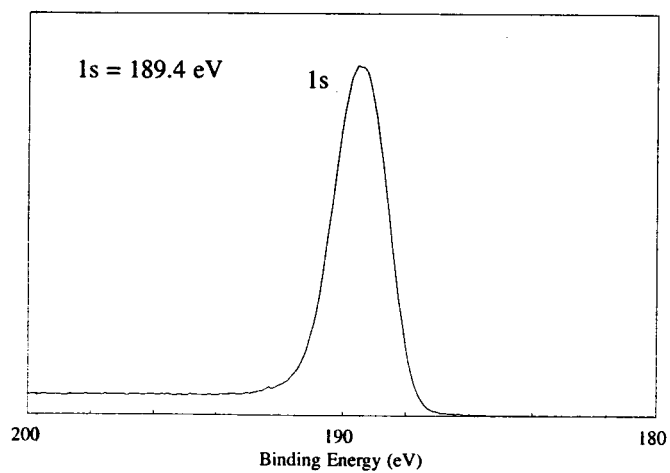
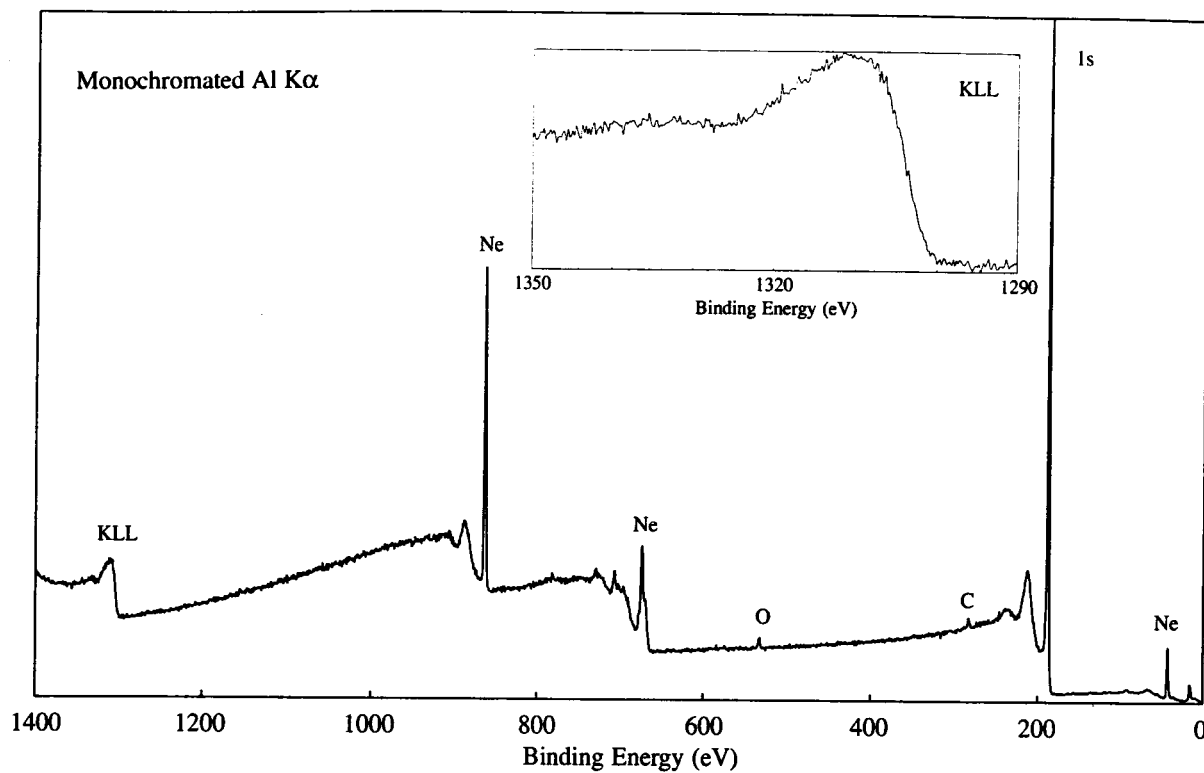


Line Positions (eV)	
<u>Photoelectron Lines</u>	
Is	112
<u>Auger Lines</u>	
KVV	
1384	(Al)
1151	(Mg)

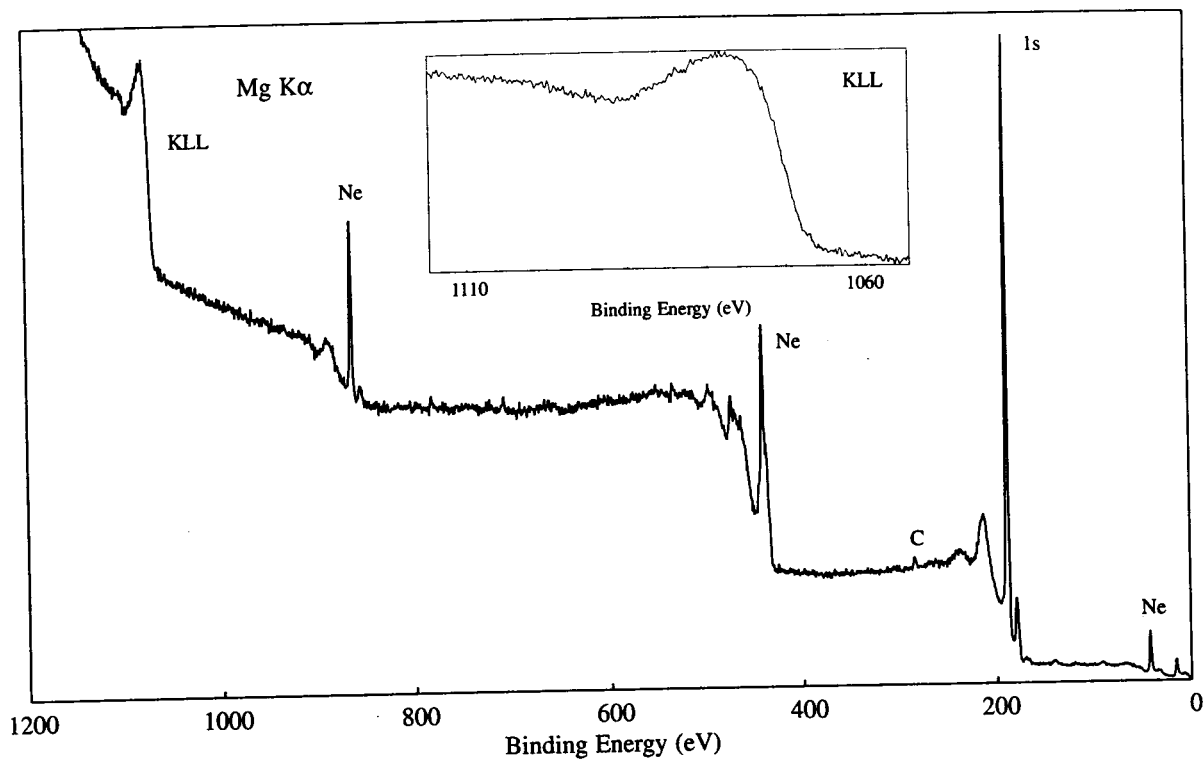


1s Binding Energy (eV)							
Compound Type	111	112	113	114	115	116	117
Be							
BeO							
BeMoO ₄							
BeRh ₂ O ₄							
BeF ₂							
NaBeF ₃							
Na ₂ BeF ₄							

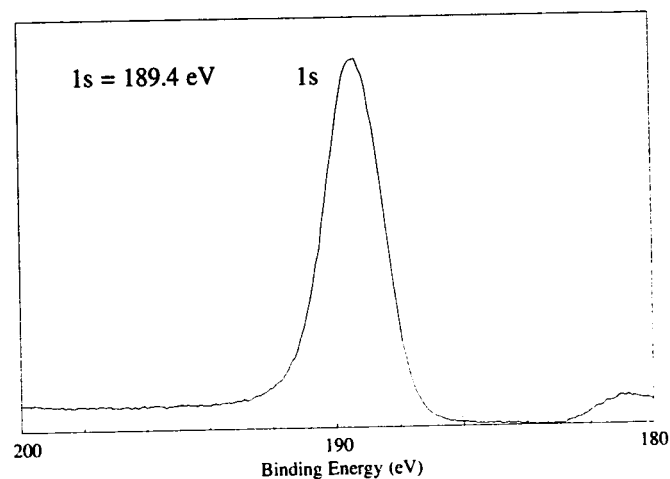


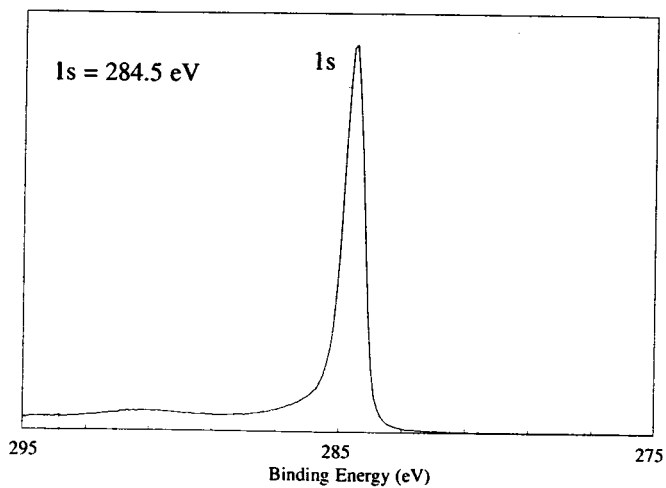
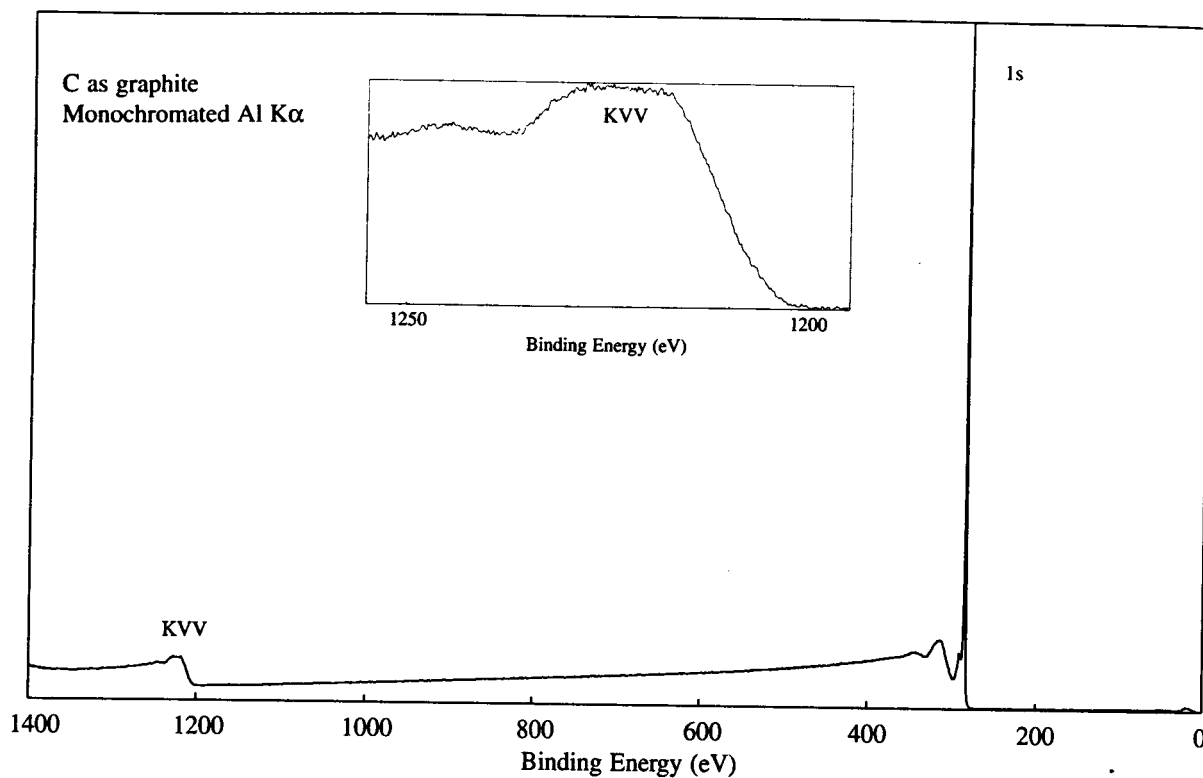


Line Positions (eV)	
<u>Photoelectron Lines</u>	
1s	189
<u>Auger Lines</u>	
KLL	
1310	(Al)
1077	(Mg)

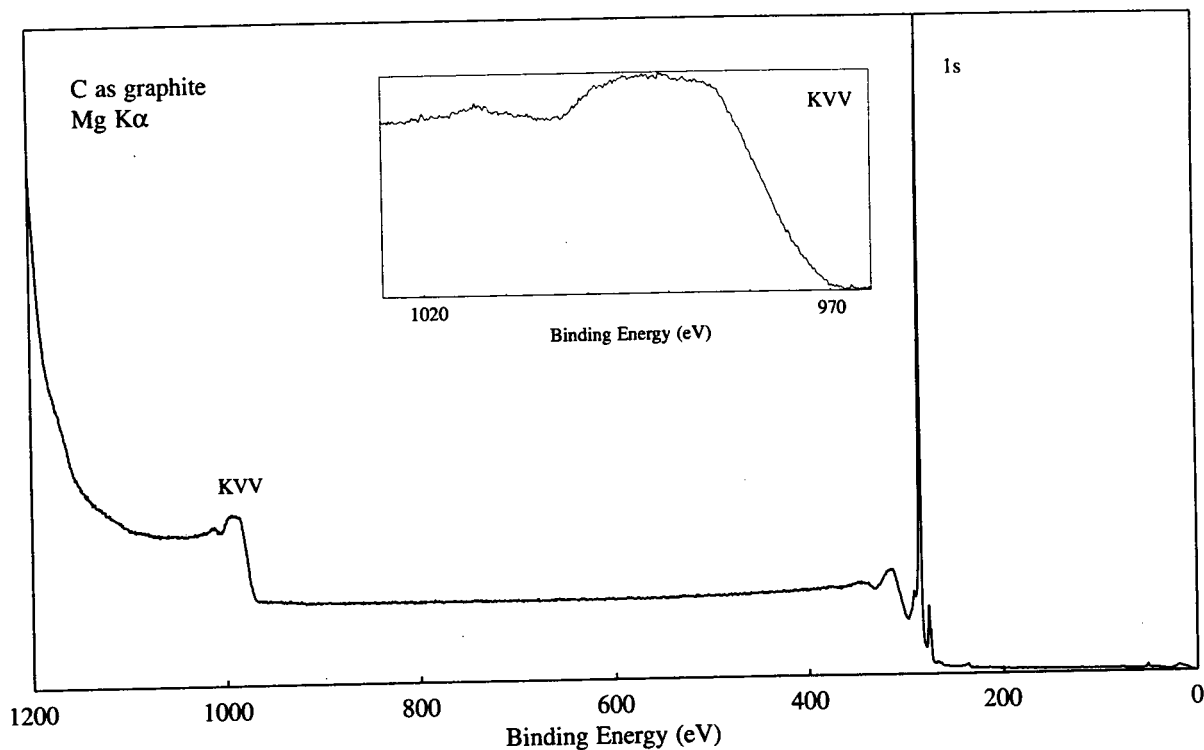


Compound Type	1s Binding Energy (eV)					
	186	188	190	192	194	196
B						
Boride						
BN						
B ₂ O ₃						
NaBF ₄						
NaBH ₄						
H ₃ BO ₃						
Na ₂ B ₄ O ₇ · 10H ₂ O						
B ₁₀ H ₁₄						

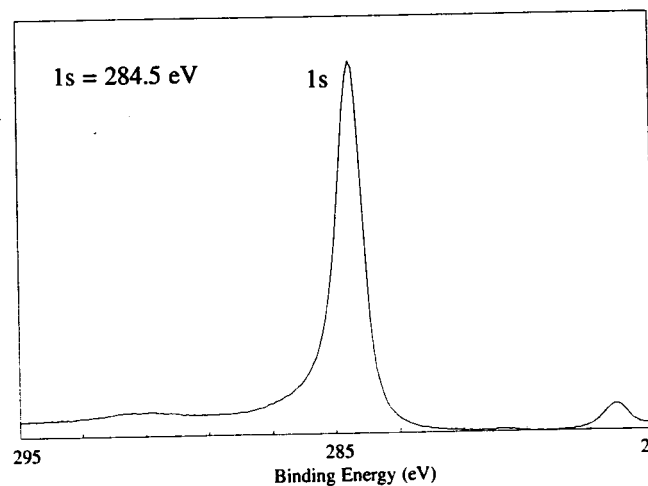


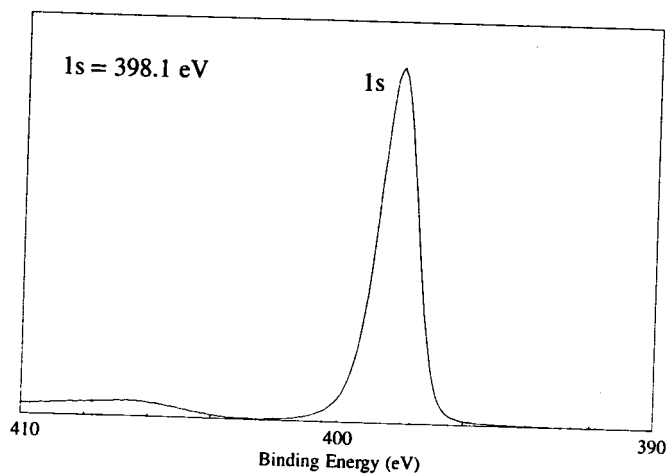
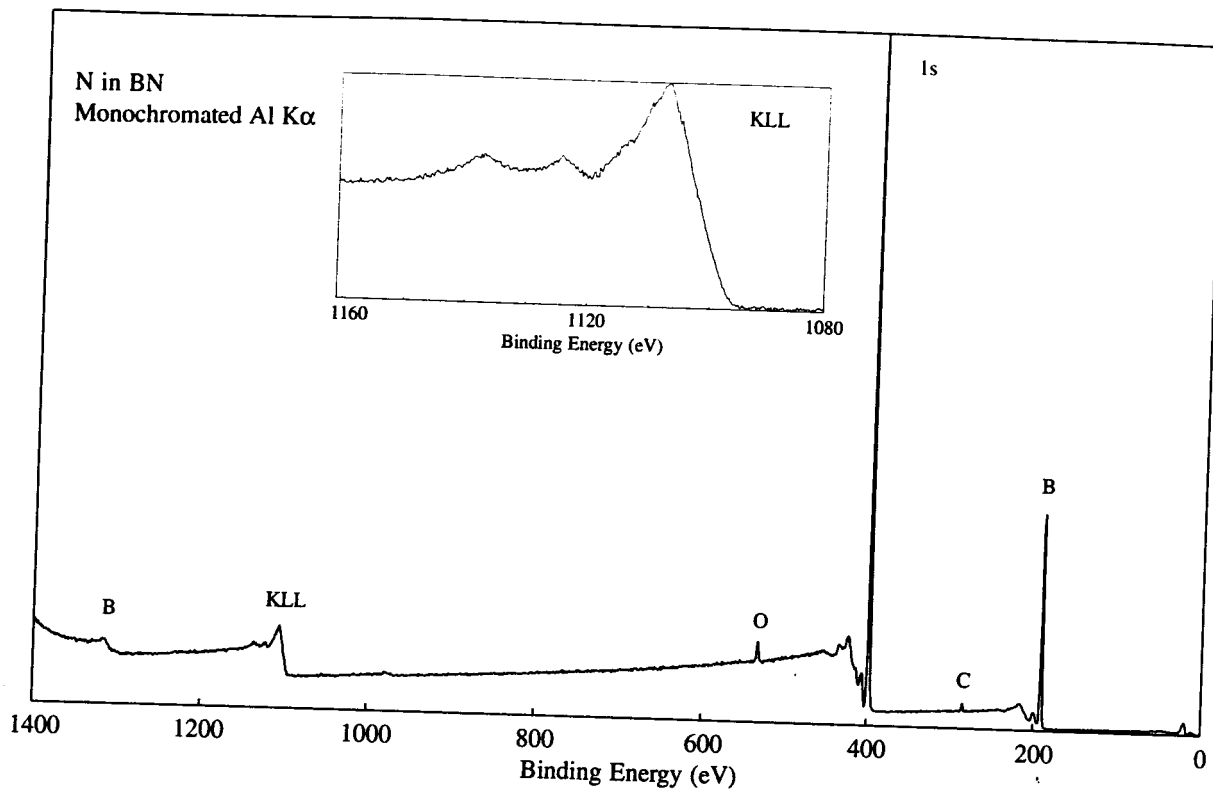


Line Positions (eV)		
<u>Photoelectron Lines</u>		
1s		
285		
<u>Auger Lines</u>		
KVV		
1223	(Al)	
990	(Mg)	

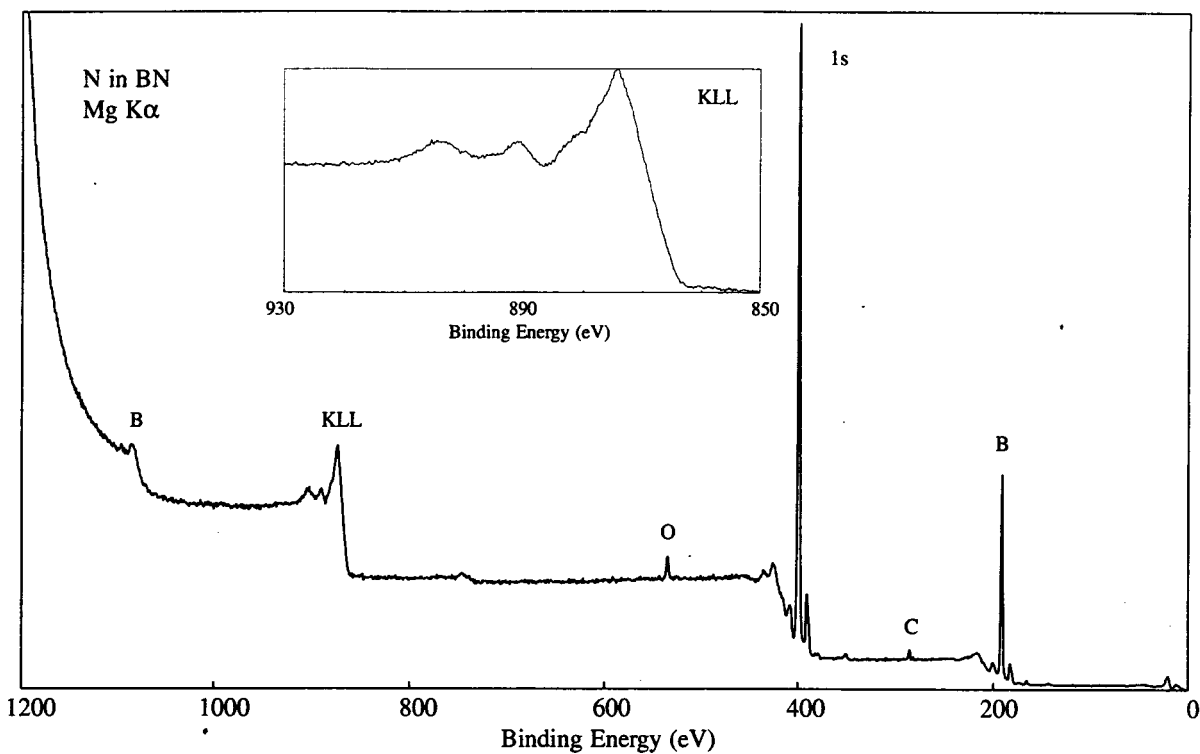


1s Binding Energy (eV)									
Compound Type	280	282	284	286	288	290	292	294	
Carbide									
Carbon									
C with N									
C with S									
C with O									
Alcohols									
Ethers									
Ketones/Aldehydes									
Carboxyls									
Carbonates									
C with Cl									
C with F									
CHF									
CF ₂									
CF ₃									

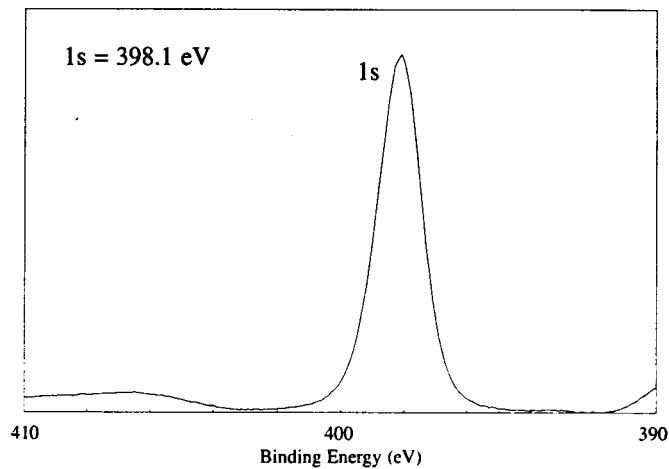


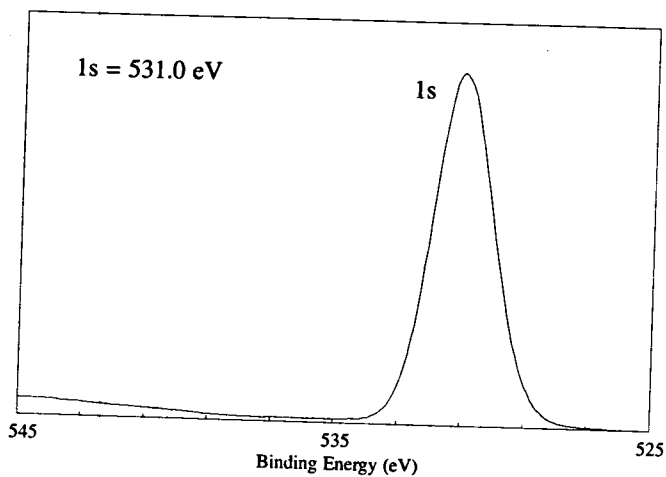
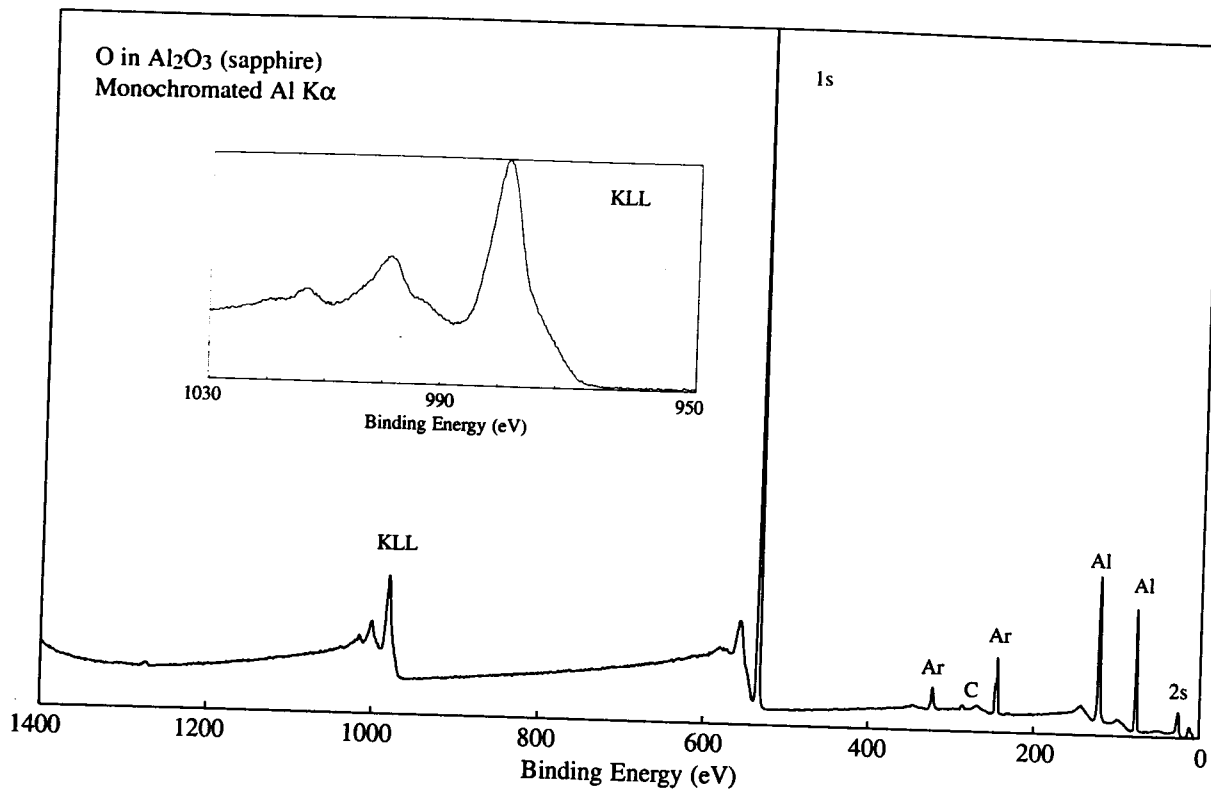


Line Positions (eV)		
<u>Photoelectron Lines</u>		
1s		
398		
<u>Auger Lines</u>		
KLL		
1107	(Al)	
874	(Mg)	

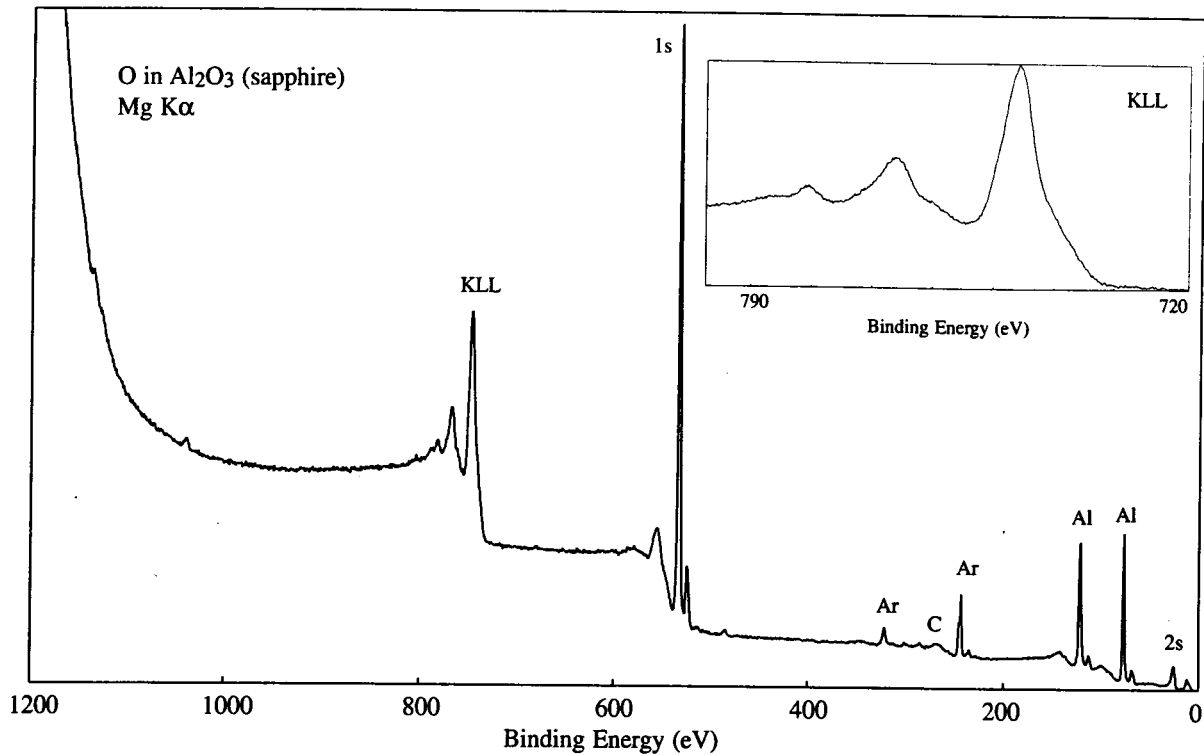


Compound Type	1s Binding Energy (eV)									
	396	398	400	402	404	406	408	410		
NH ₃										
Nitride										
BN										
Si ₃ N ₄										
Cyanides										
Nitrites										
Ammonium Salt										
Azide(N*NN*)										
Azide (NN*N)										
Nitrates										
Organic Matrix										

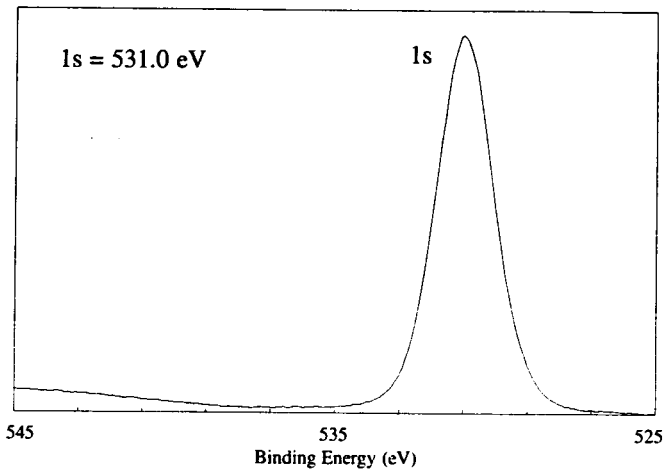


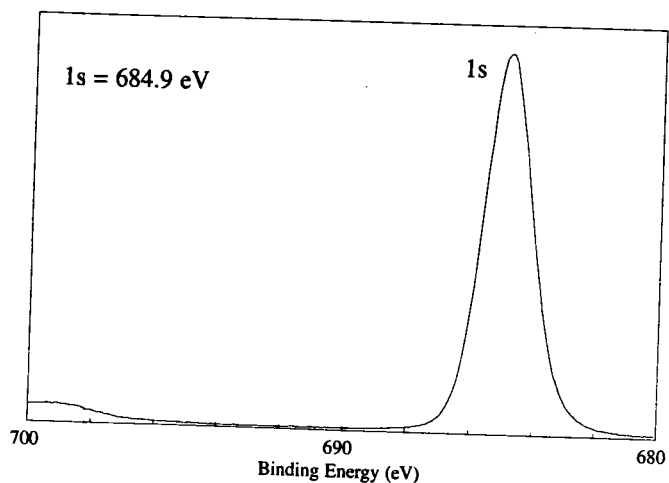
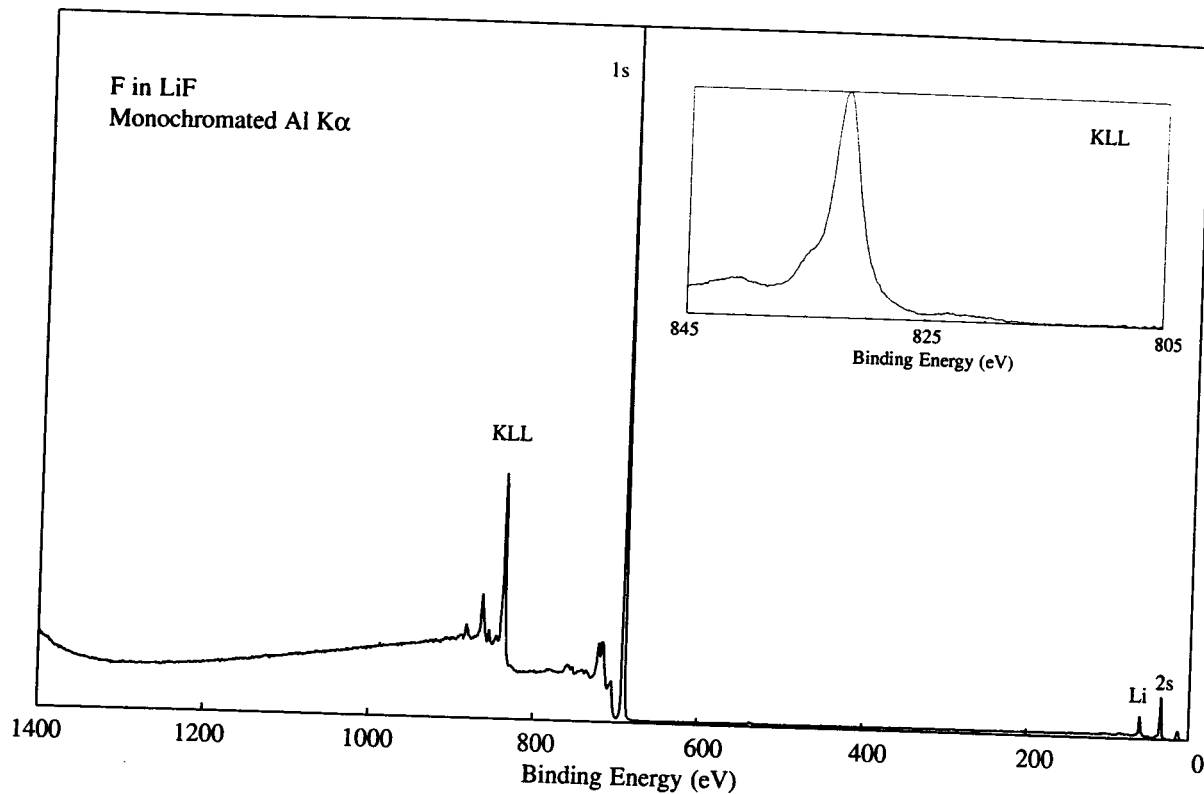


Line Positions (eV)			
Photoelectron Lines			
1s	2s		
531.	23		
Auger Lines			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
1013	999	978	(Al)
780	766	745	(Mg)

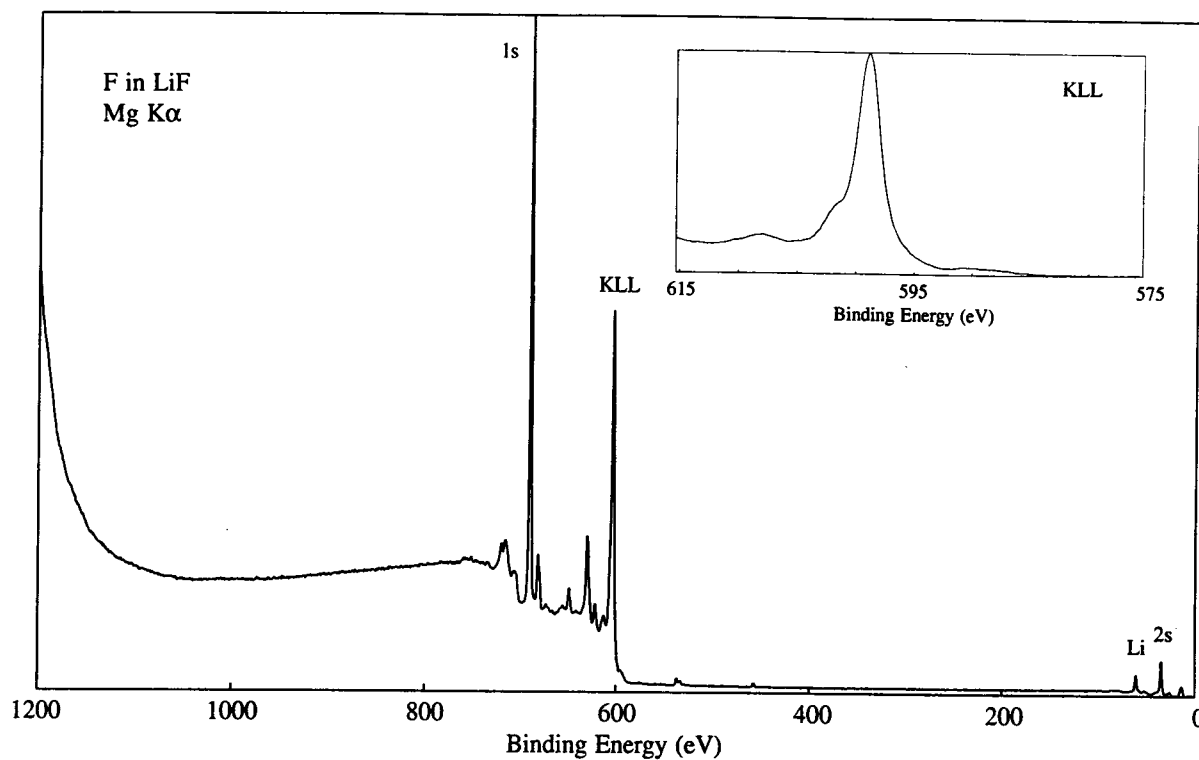


Compound Type	1s Binding Energy (eV)						
	528	529	530	531	532	533	534
Metal Oxides	■						
Fe ₂ O ₃			■				
SiO ₂						■	
Hydroxides				■			
Phosphates				■	■		
Nitrates						■	
Sulfates					■		
Carbonates				■			
Chlorates						■	
Al ₂ O ₃			■	■			
Silicones						■	

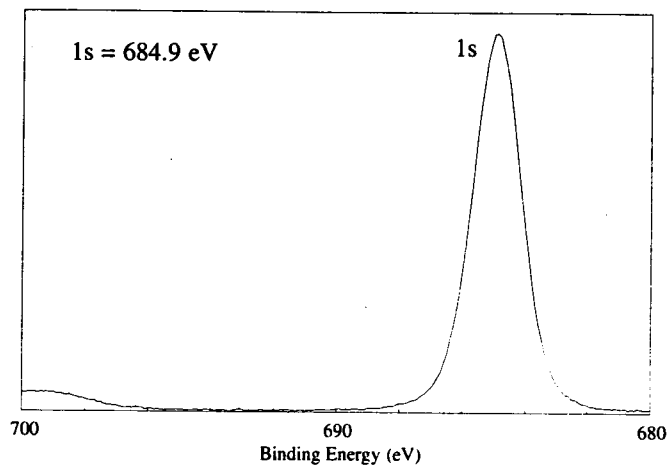


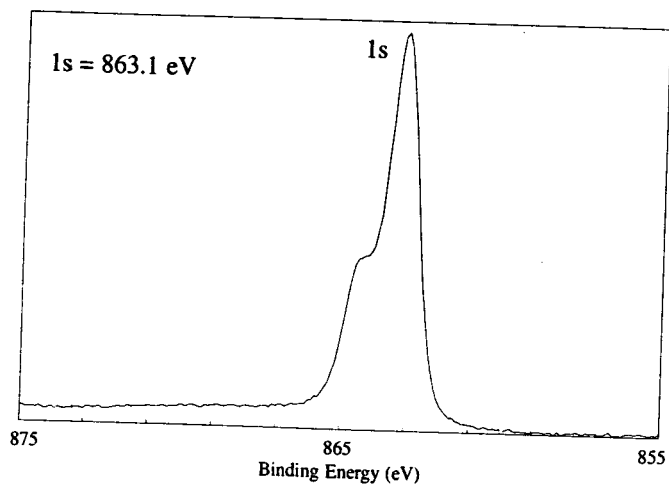
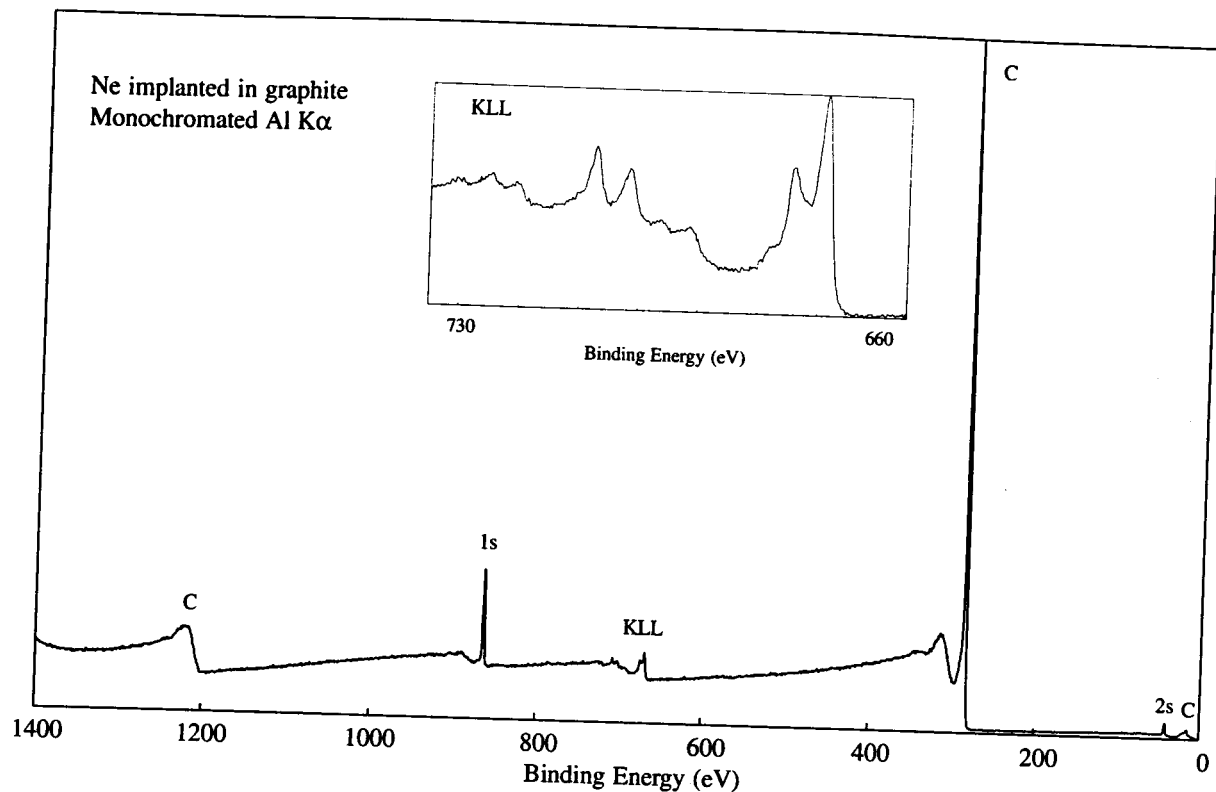


Line Positions (eV)			
Photoelectron Lines			
1s	2s		
685	30		
Auger Lines			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
877	858	832	(Al)
644	625	599	(Mg)

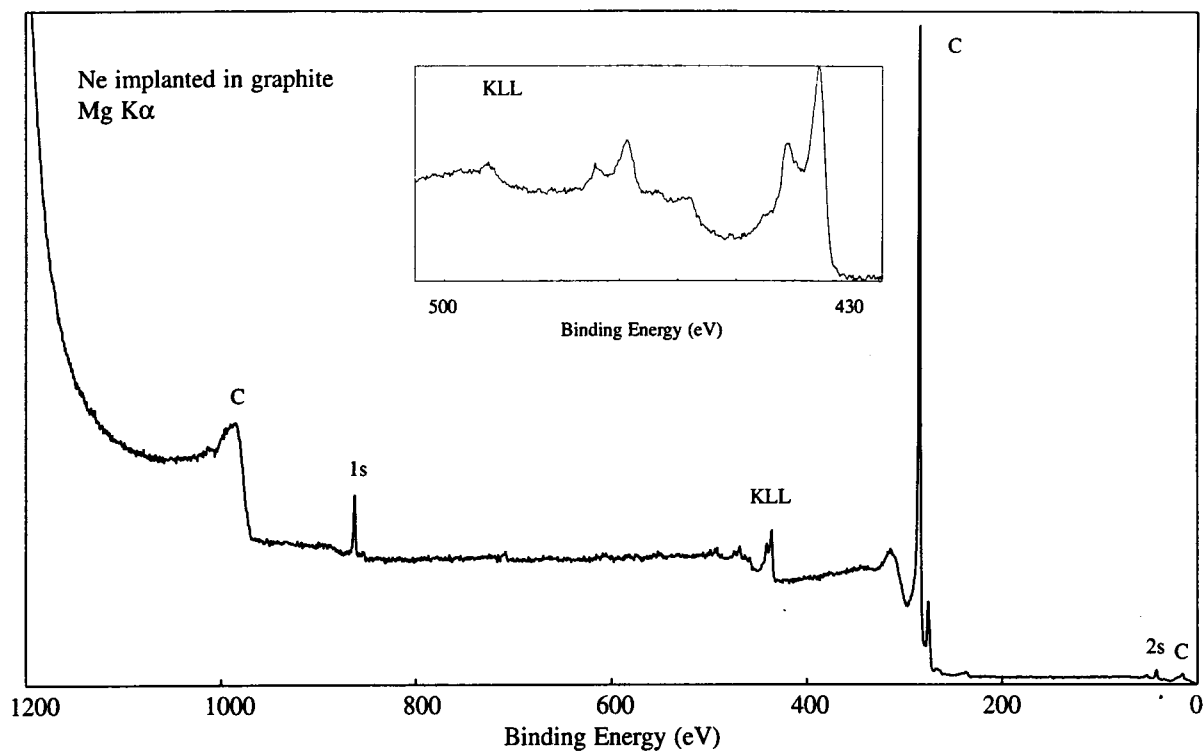


Compound Type	1s Binding Energy (eV)						
	683	684	685	686	687	688	689
KF		■					
LiF			■				
NaF		■					
BaF ₂	■	■					
MgF ₂				■			
AlF ₃ · 3H ₂ O				■			
NaBF ₄					■		
Na ₂ SiF ₆				■			
p-(CF ₂ =CF ₂)							■
EtNH ₂ BF ₃				■			
Ph ₃ PBF ₃			■				

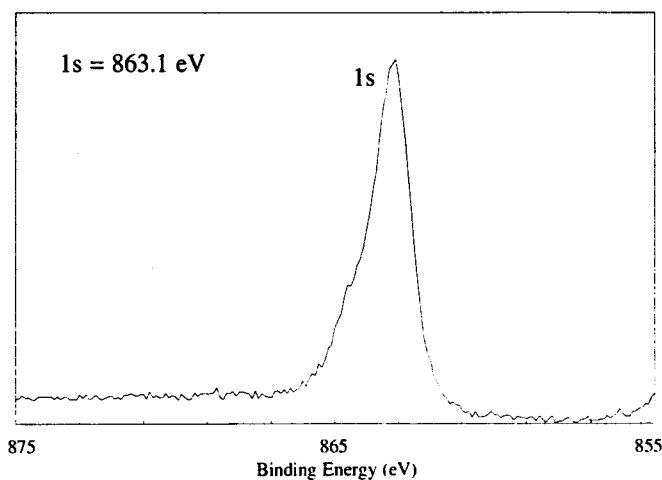


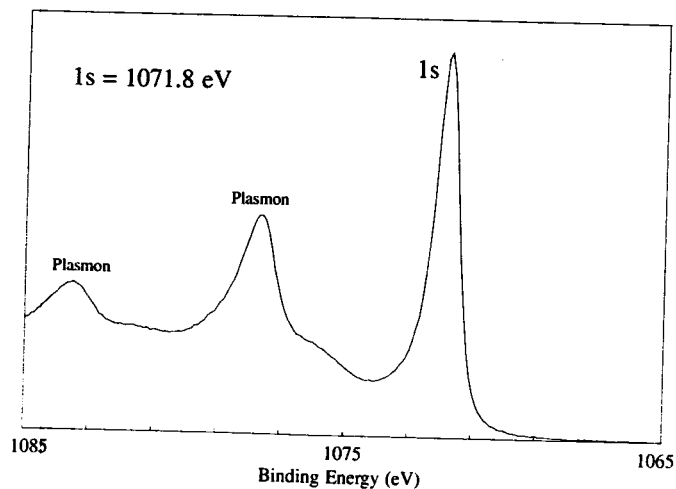
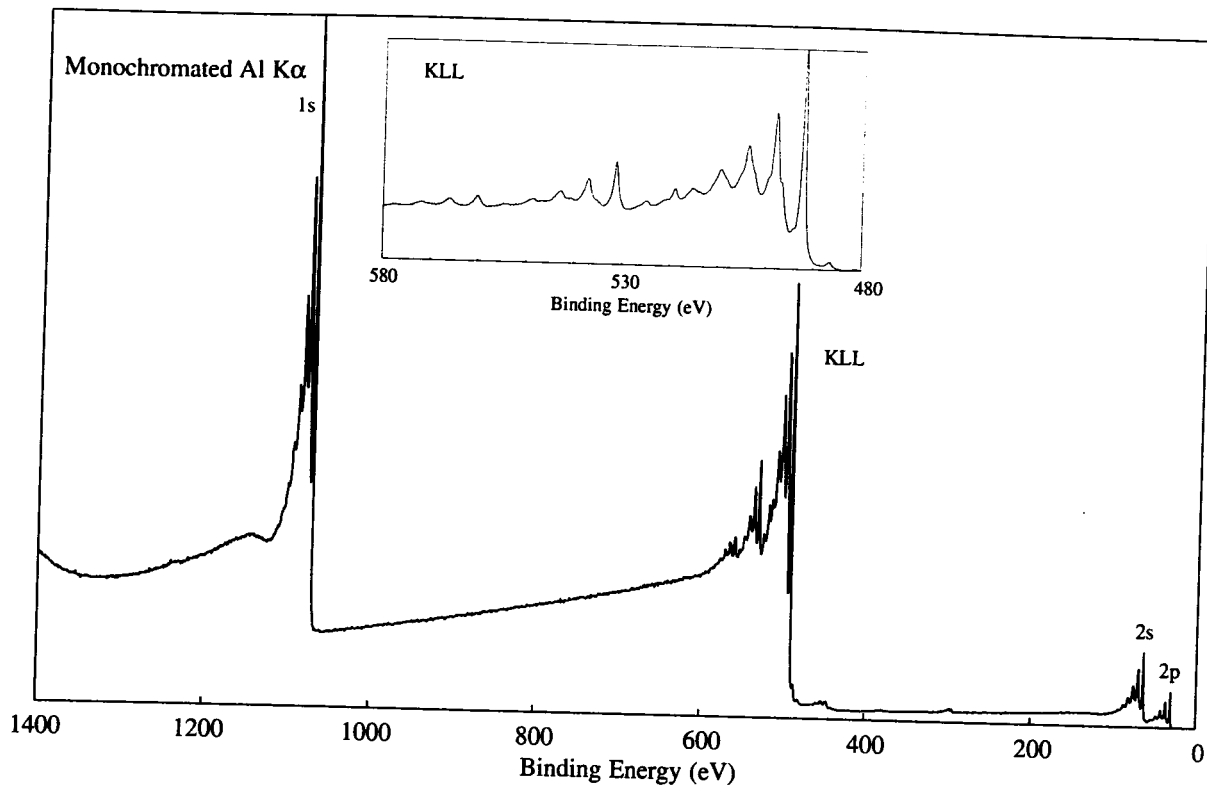


Line Positions (eV)			
Photoelectron Lines			
1s	2s	2p	
863	41	14	
Auger Lines			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
725	702	669	(Al)
492	469	436	(Mg)

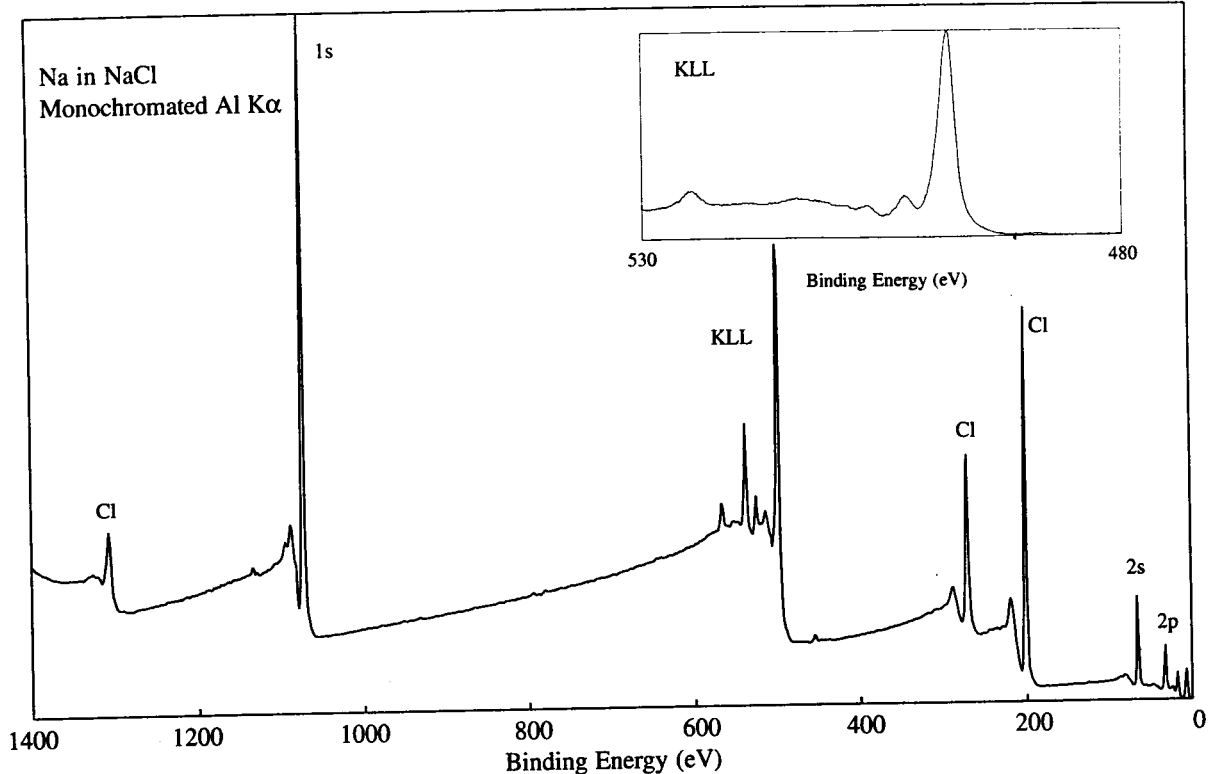


Compound Type	1s Binding Energy (eV)			
	861	862	863	864
Ne in Ag				
Ne in Au				
Ne in Cu				
Ne in Fe				
Ne in graphite				

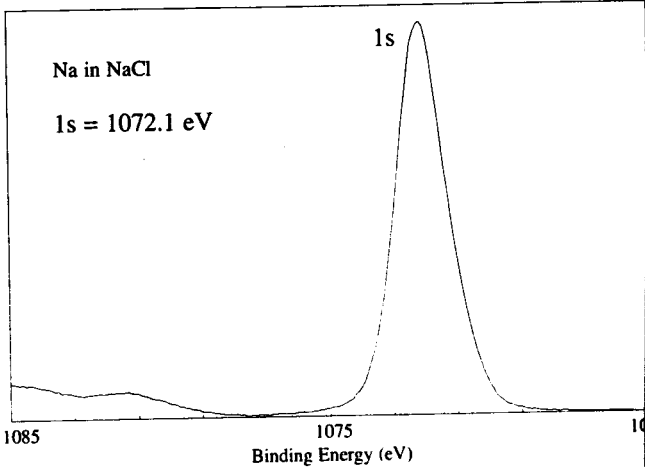


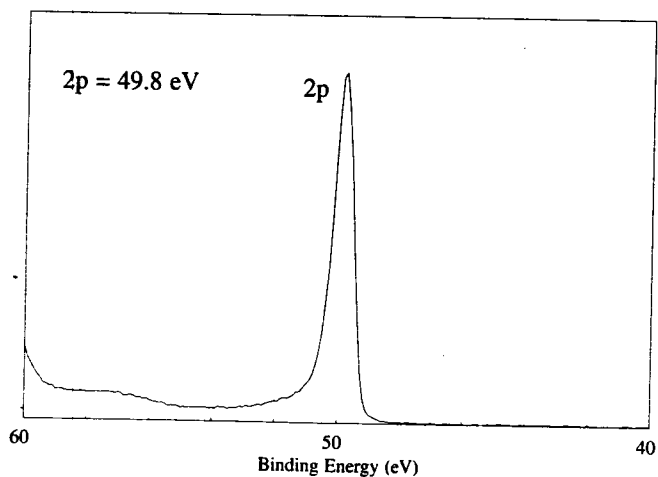
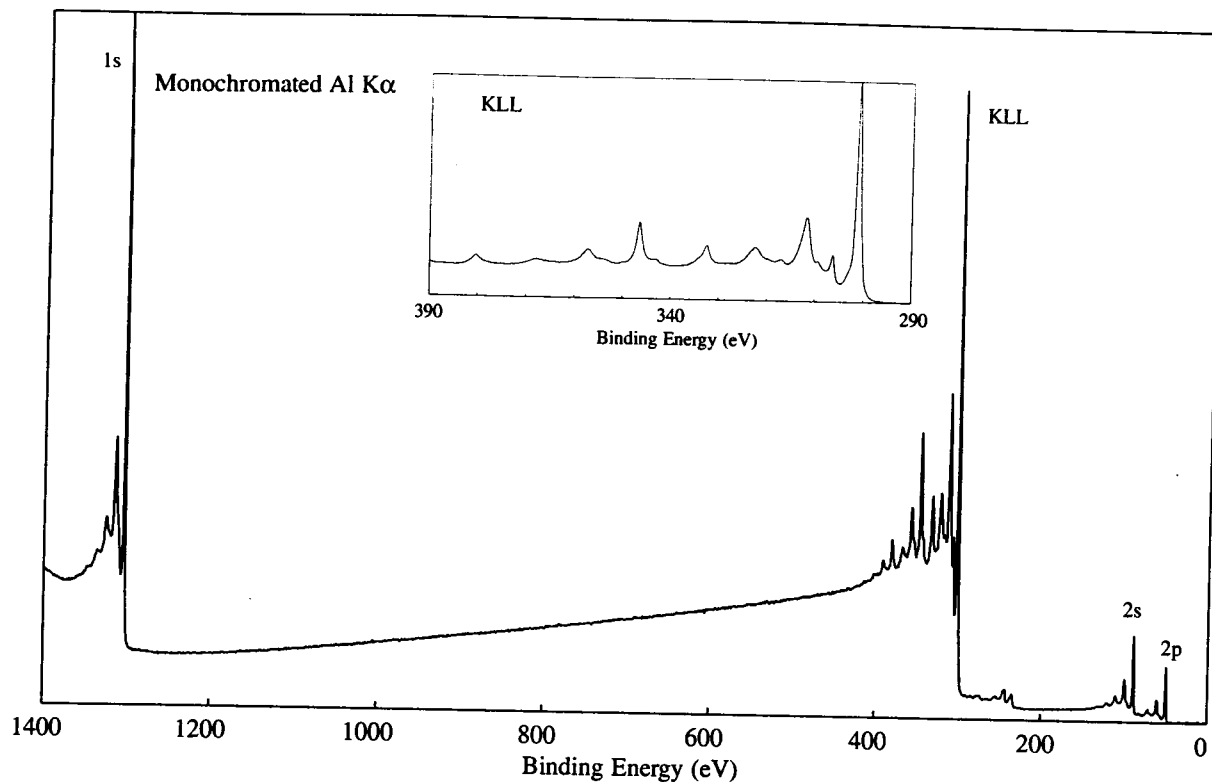


Line Positions (eV)			
Photoelectron Lines			
1s	2s	2p	
1072	64	31	
Auger Lines			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
561	532	493	(Al)
328	299	260	(Mg)

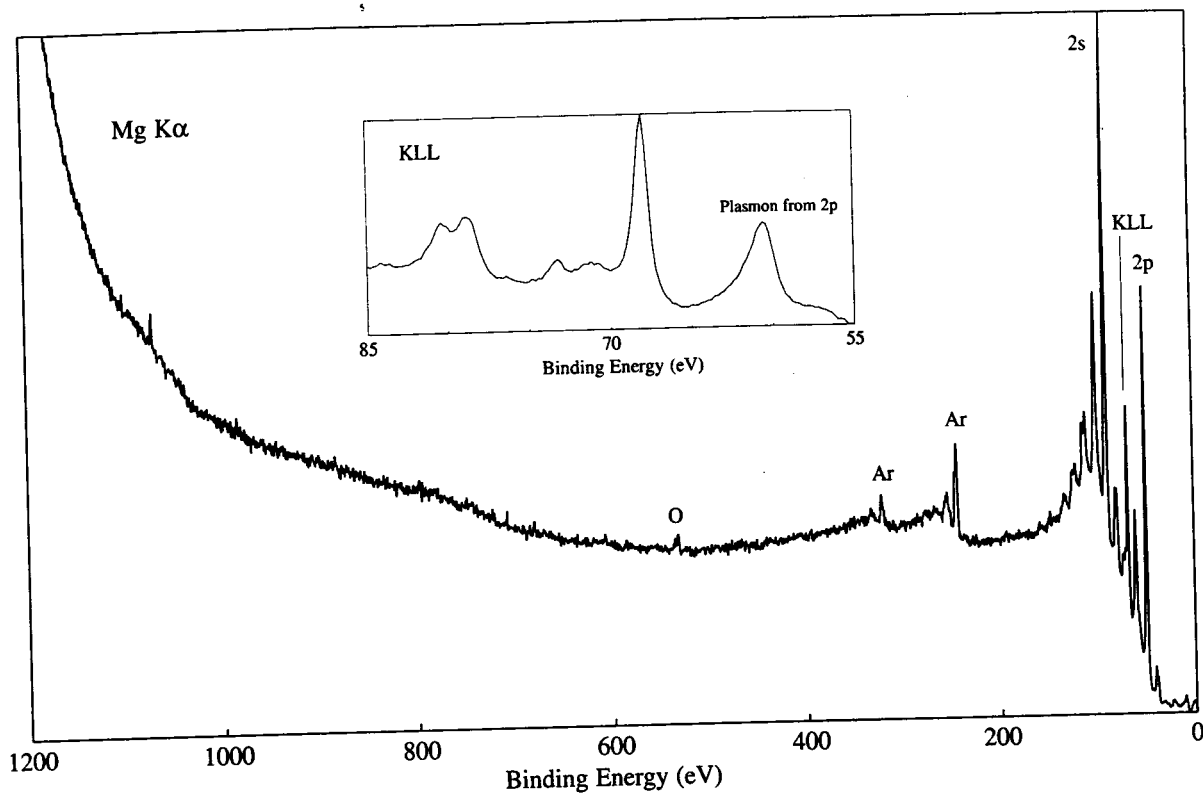


Compound Type	1s Binding Energy (eV)			
	1070	1071	1072	1073
Na				
NaI				
NaBr				
NaCl				
NaF				
Na ₂ CO ₃				
Na ₂ S ₂ O ₃				
Na ₂ SO ₄				
Na ₄ P ₂ O ₇				
NaH ₂ PO ₄				
Mol Sieve				

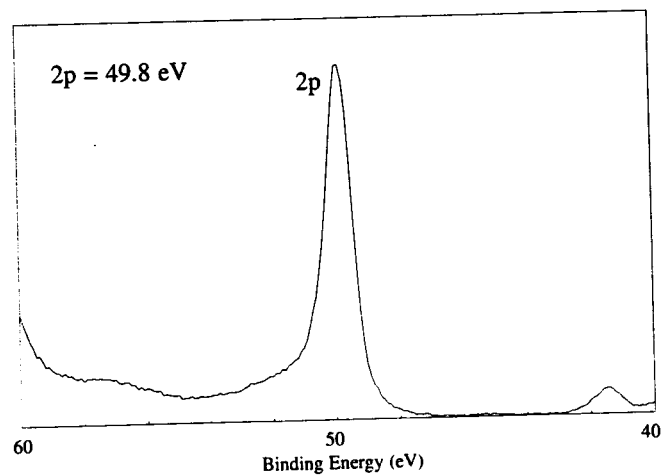


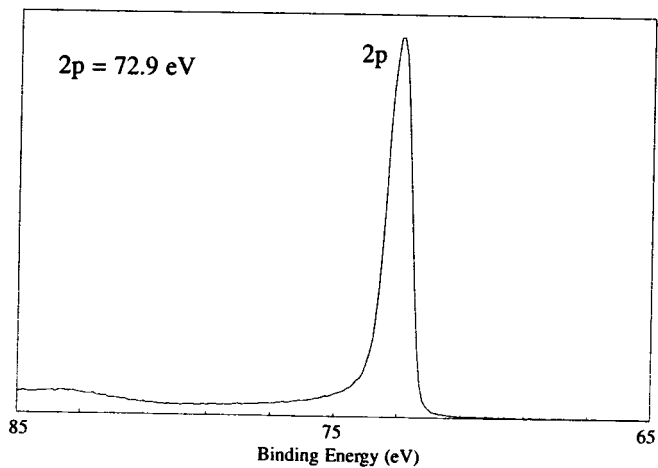
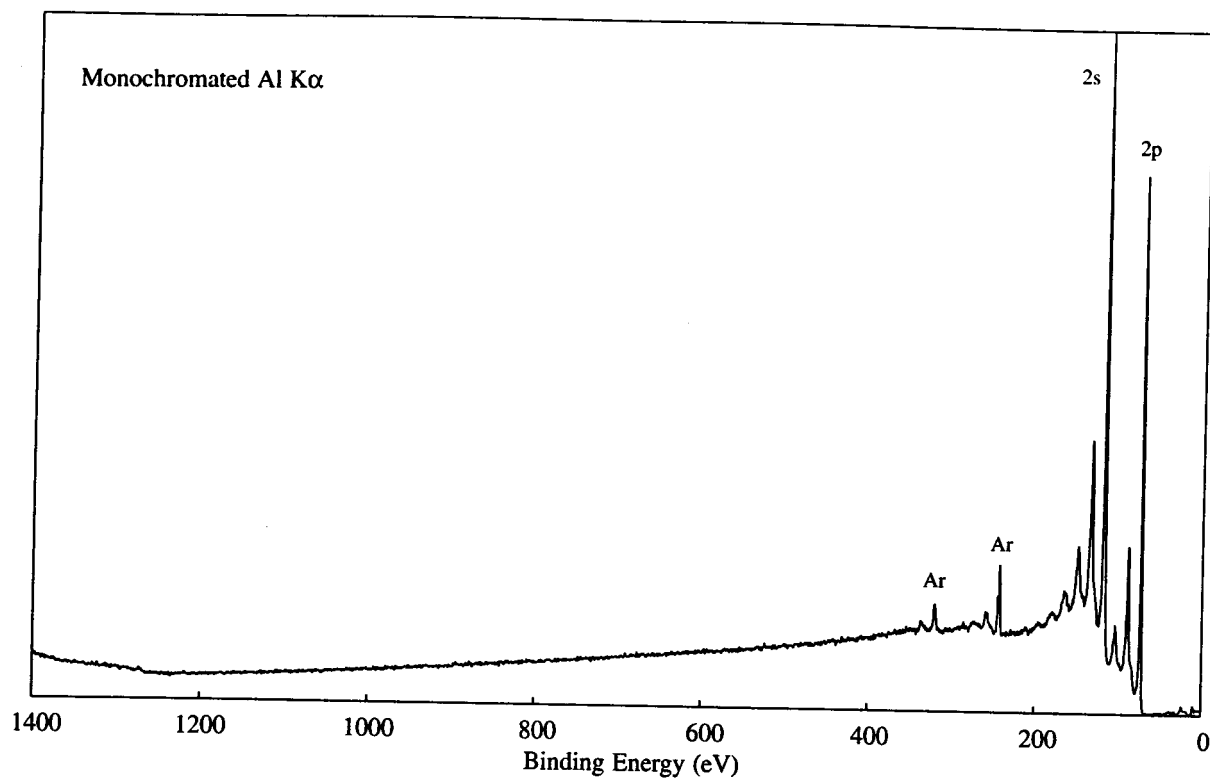


Line Positions (eV)			
Photoelectron Lines			
1s	2s	2p	
1303	89	50	
Auger Lines			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
381	347	301	(Al)
148	114	68	(Mg)

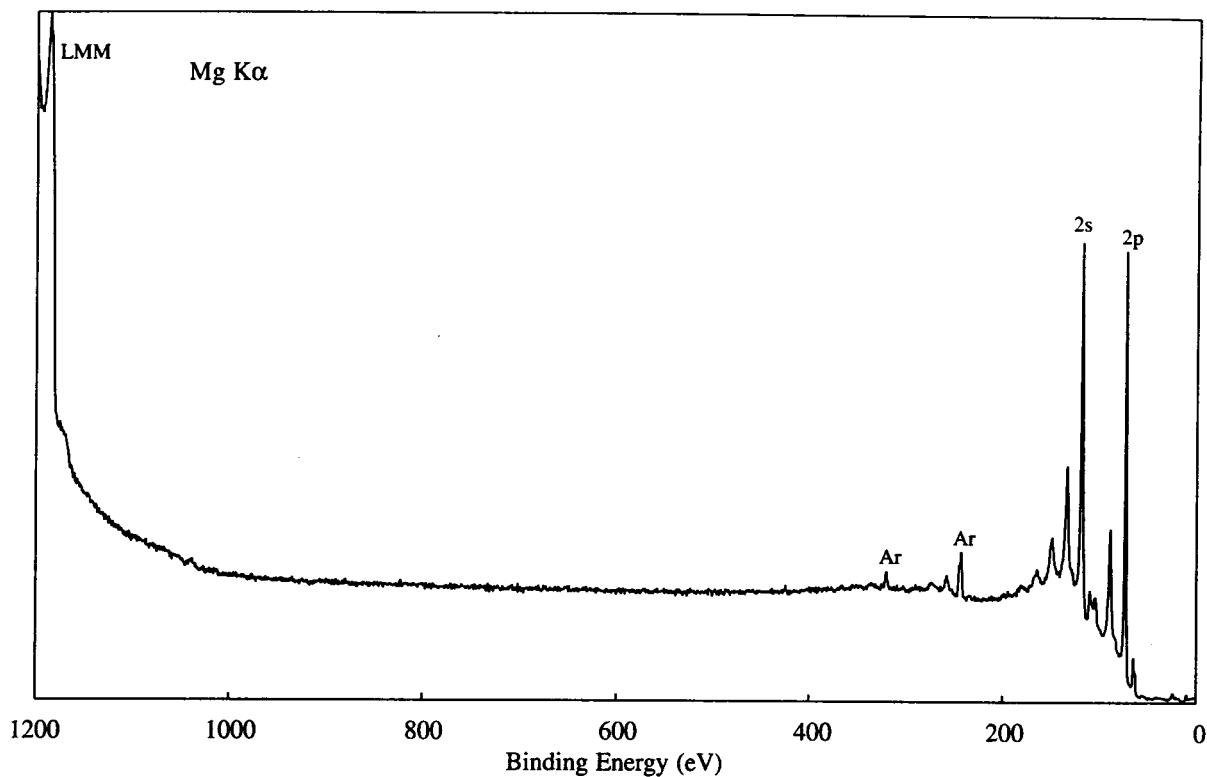


Compound Type	2p Binding Energy (eV)			
	48	49	50	51
Mg				
Mg ₂ Cu				
Mg ₃ Bi ₂				
MgF ₂				
Mg(OH) ₂				
MgAl ₂ O ₄				

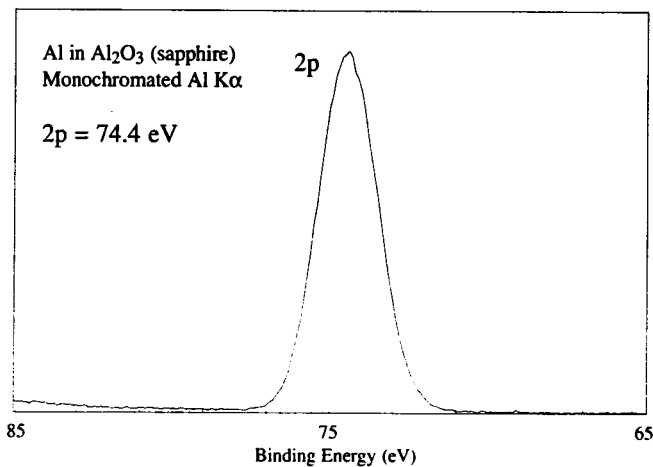


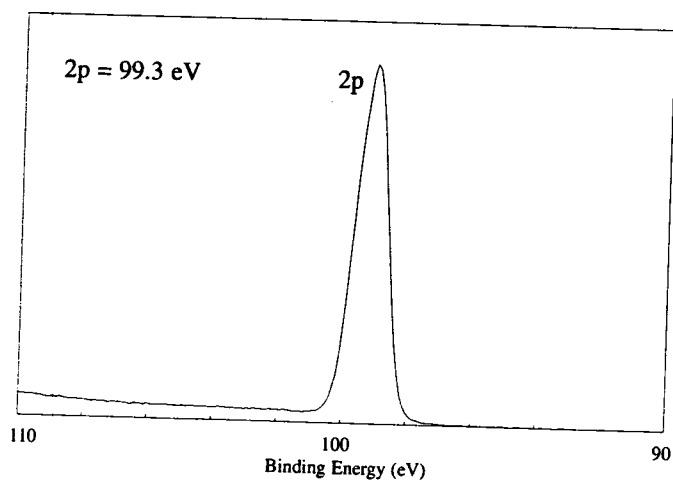
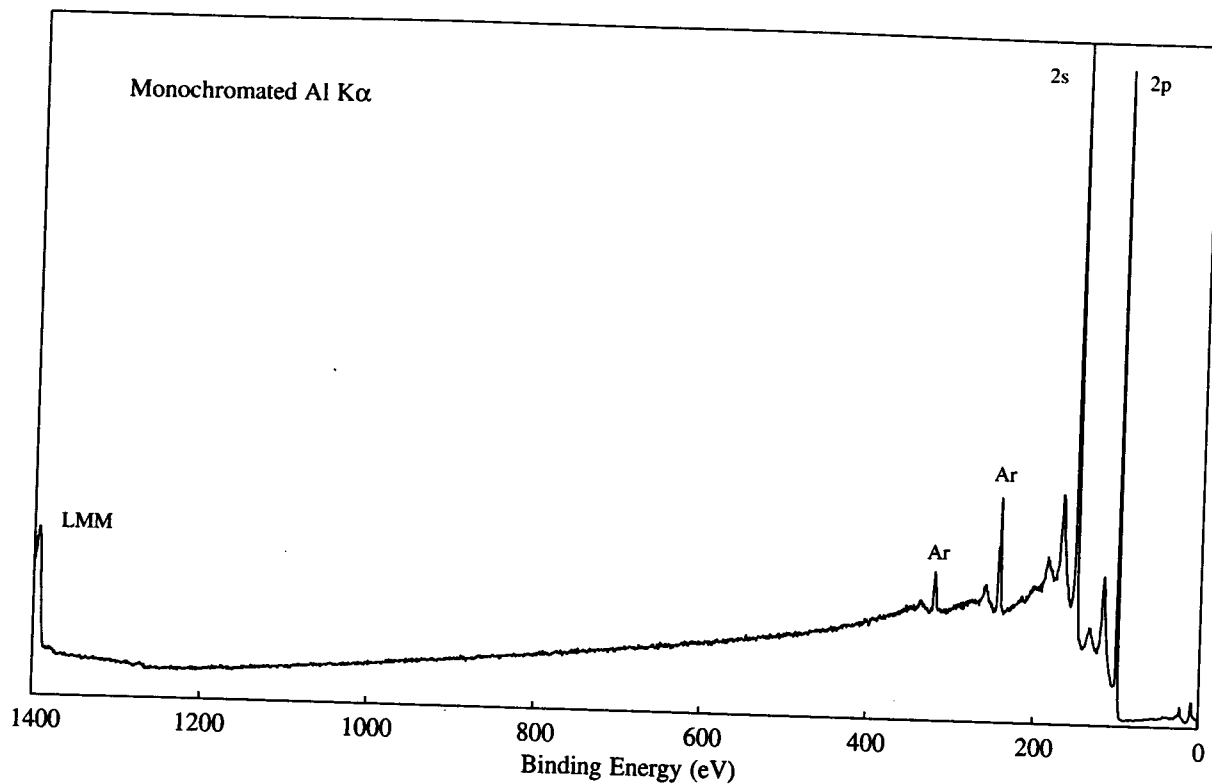


Line Positions (eV)	
<u>Photoelectron Lines</u>	
2s	2p
118	73
<u>Auger Lines</u>	
L ₂₃ M ₁ M ₂₃	
1419	(Al)
1186	(Mg)

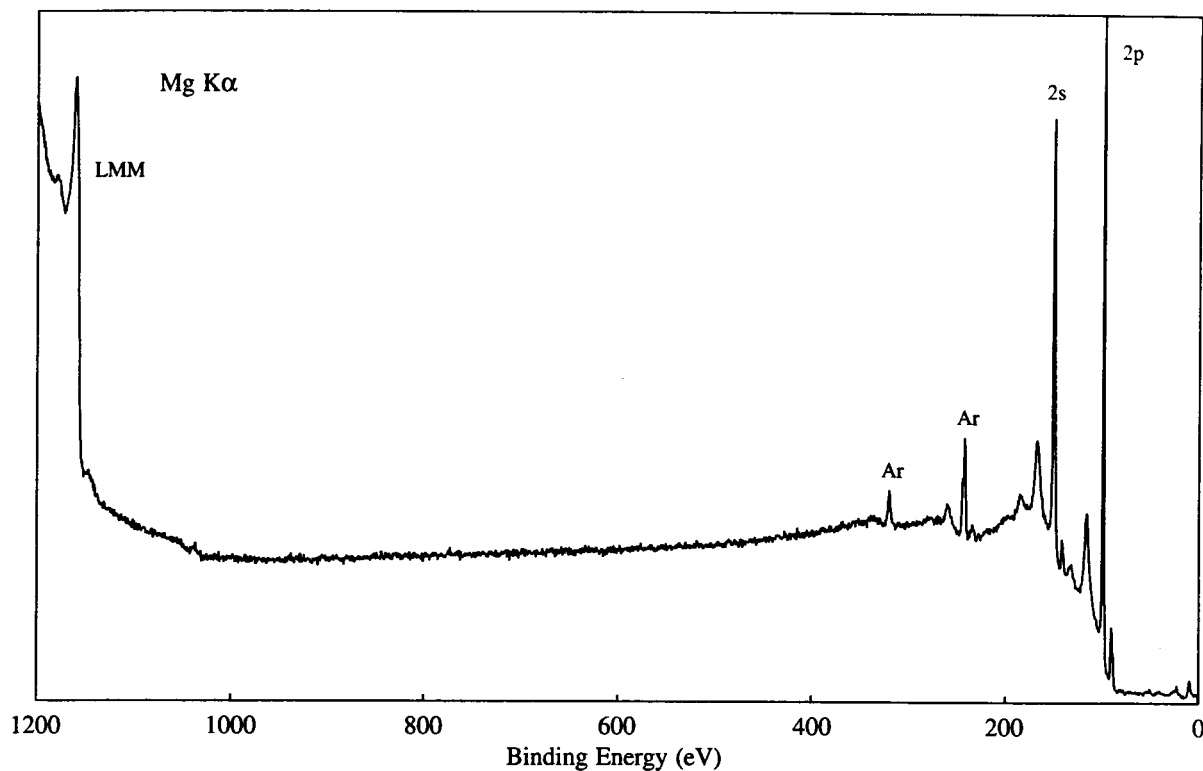


Compound Type	2p Binding Energy (eV)					
	72	73	74	75	76	77
Al		■				
AlAs			■			
AlGaAs			■			
LiAlH ₄					■	
Halides				■	■	
AlF ₃					■	
Oxides				■		
Al ₂ O ₃ , sapphire			■			
Al ₂ O ₃ , alpha			■			
Al ₂ O ₃ , gamma			■			
AlOOH, boehmite			■			

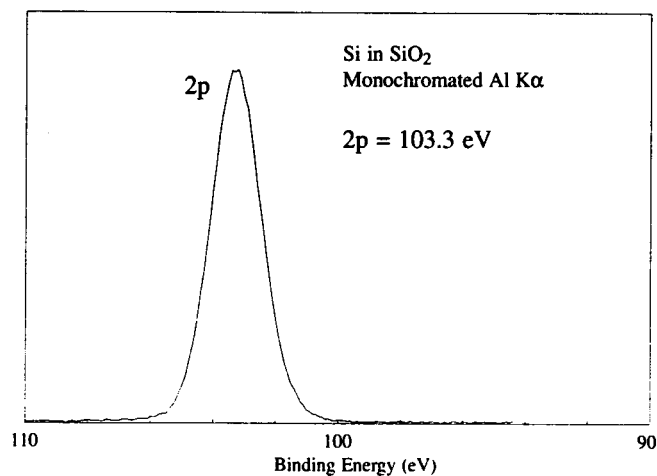


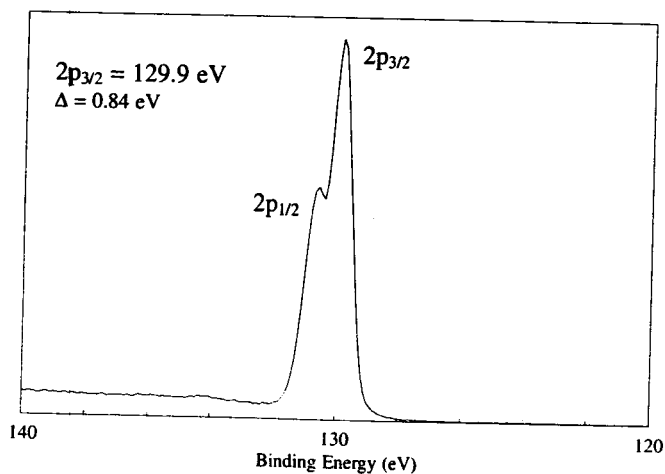
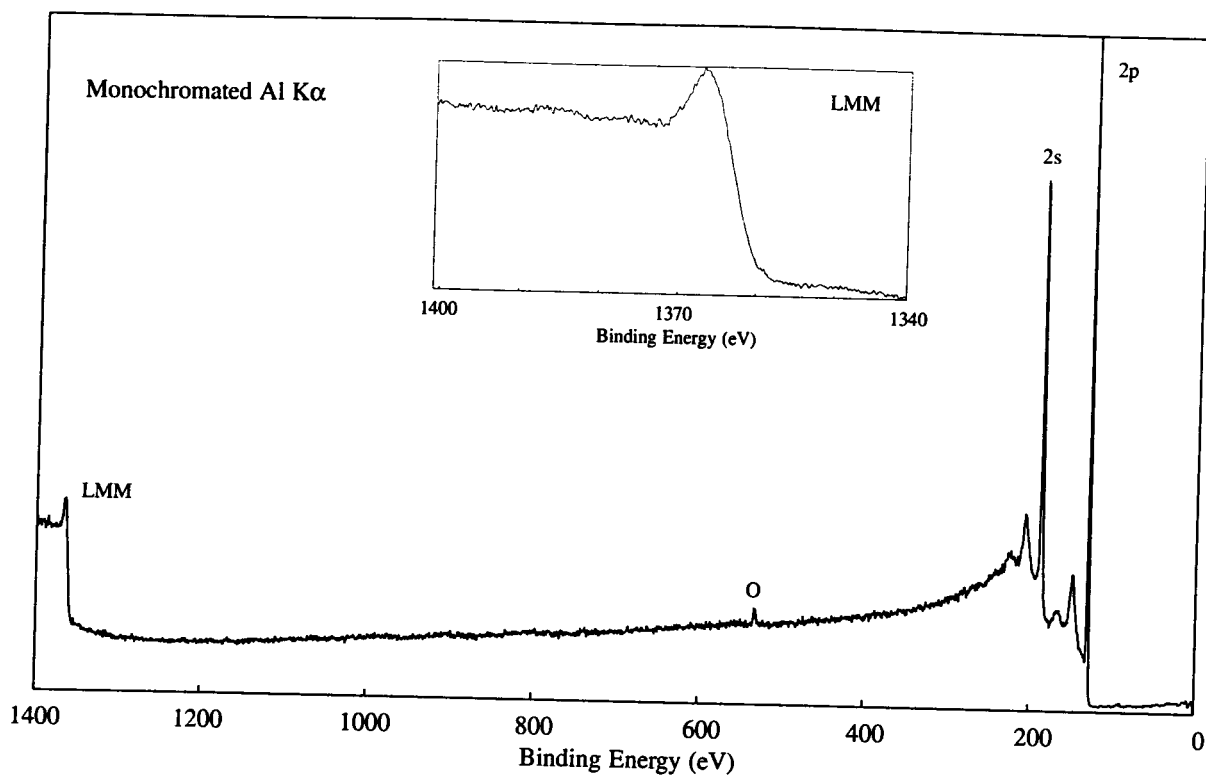


Line Positions (eV)	
<u>Photoelectron Lines</u>	
2s	2p
151	99
<u>Auger Lines</u>	
L ₂₃ M ₂₃ M ₂₃	
1394	(Al)
1161	(Mg)

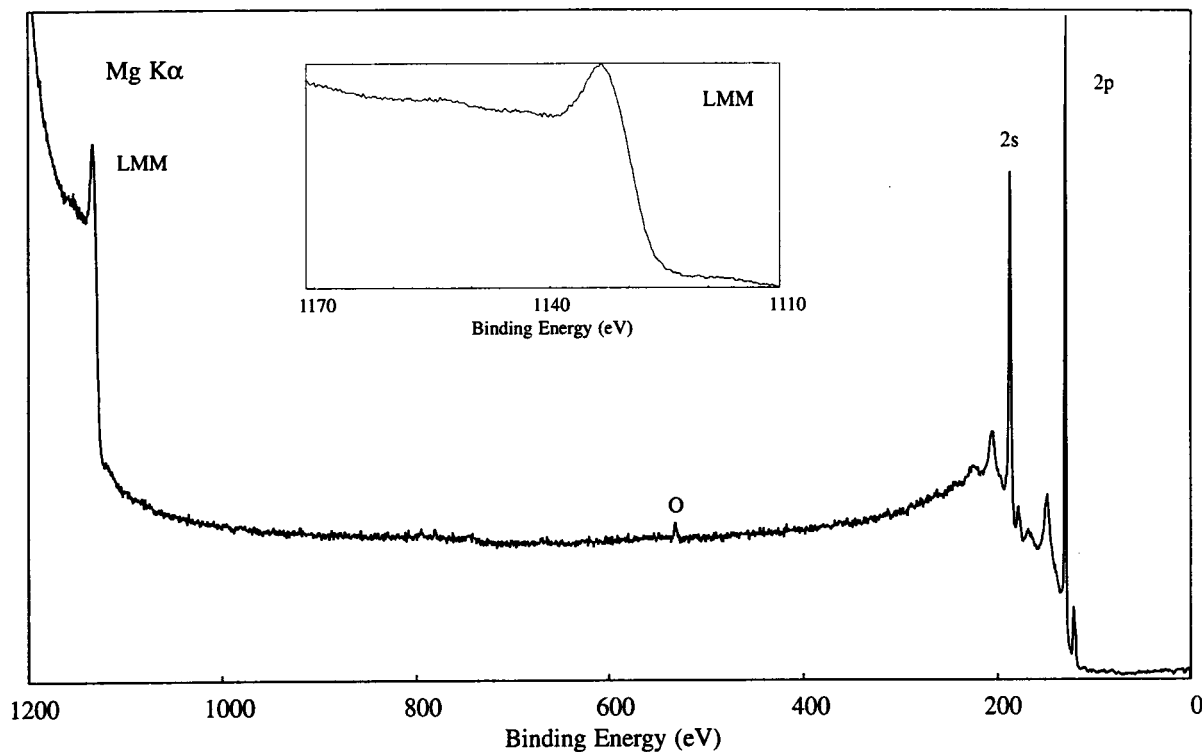


Compound Type	2p Binding Energy (eV)			
	98	101	104	
Silicides				
Silicon				
Carbides				
Nitrides				
Silicones (Silanes)				
Silicates				
Silica <chem>SiO2</chem>				

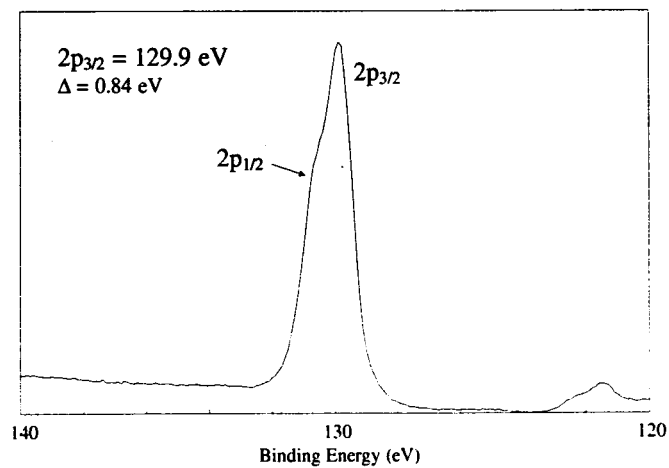


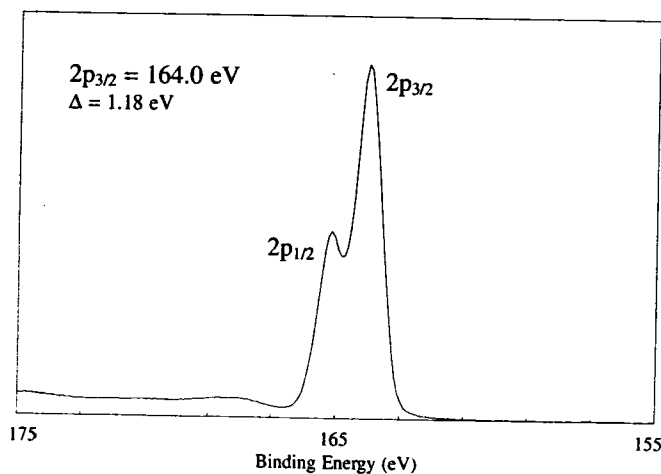
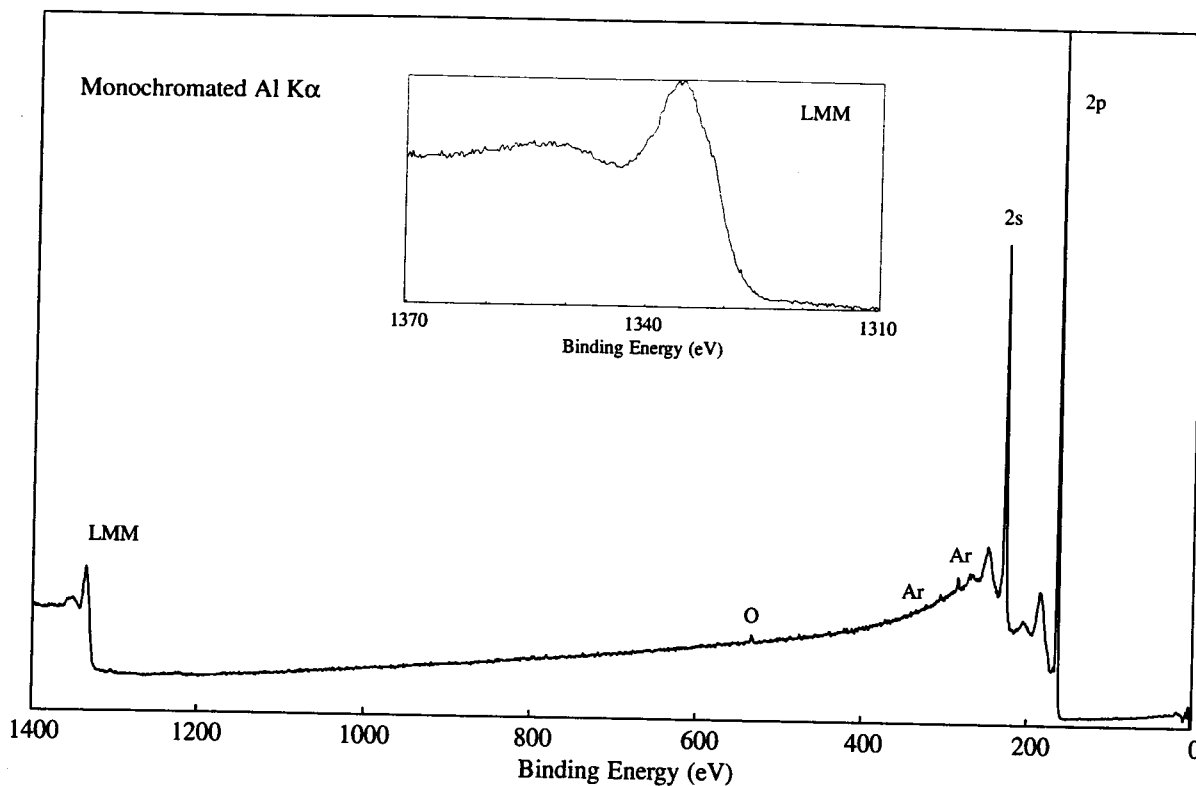


Line Positions (eV)			
Photoelectron Lines			
2s	2p _{1/2}	2p _{3/2}	3s
188	131	130	14
Auger Lines			
L ₂₃ M ₂₃ M ₂₃			
1367		(Al)	
1134		(Mg)	

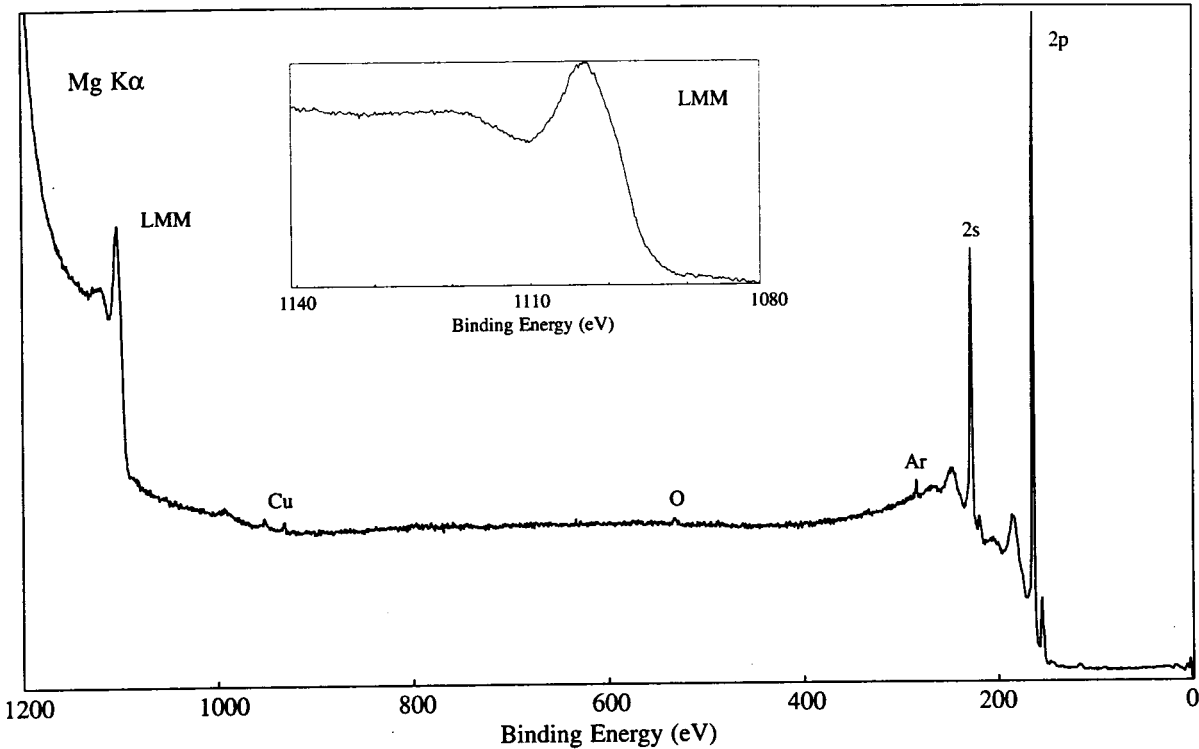


Compound Type	2p Binding Energy (eV)							
	128	129	130	131	132	133	134	135
P			■					
P (red)			■					
GaP		■	■					
InP	■	■						
Phosphate					■	■		
Pyrophosphate					■	■		
Metaphosphate							■	
P ₄ O ₁₀								■
Ph ₃ P			■					
Ph ₂ PSH					■			
(PhO) ₃ PO							■	■

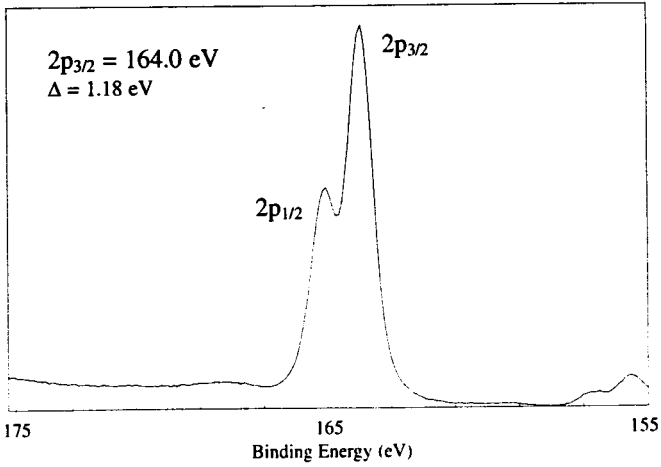


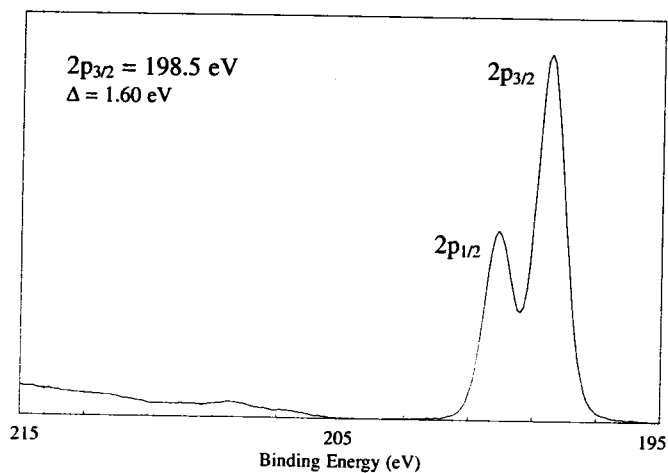
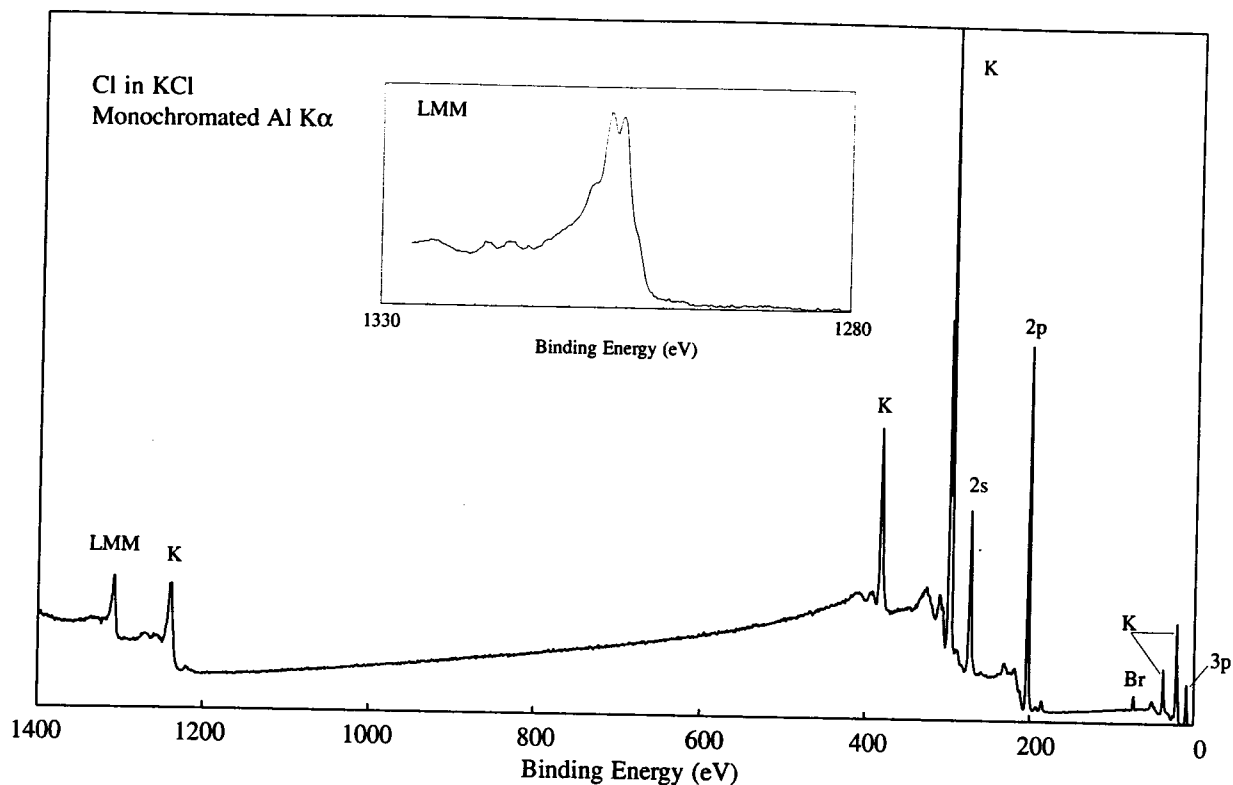


Line Positions (eV)			
Photoelectron Lines			
2s	2p _{1/2}	2p _{3/2}	3s
228	165	164	18
Auger Lines			
L ₂₃ M ₂₃ M ₂₃			
1336		(Al)	
1103		(Mg)	

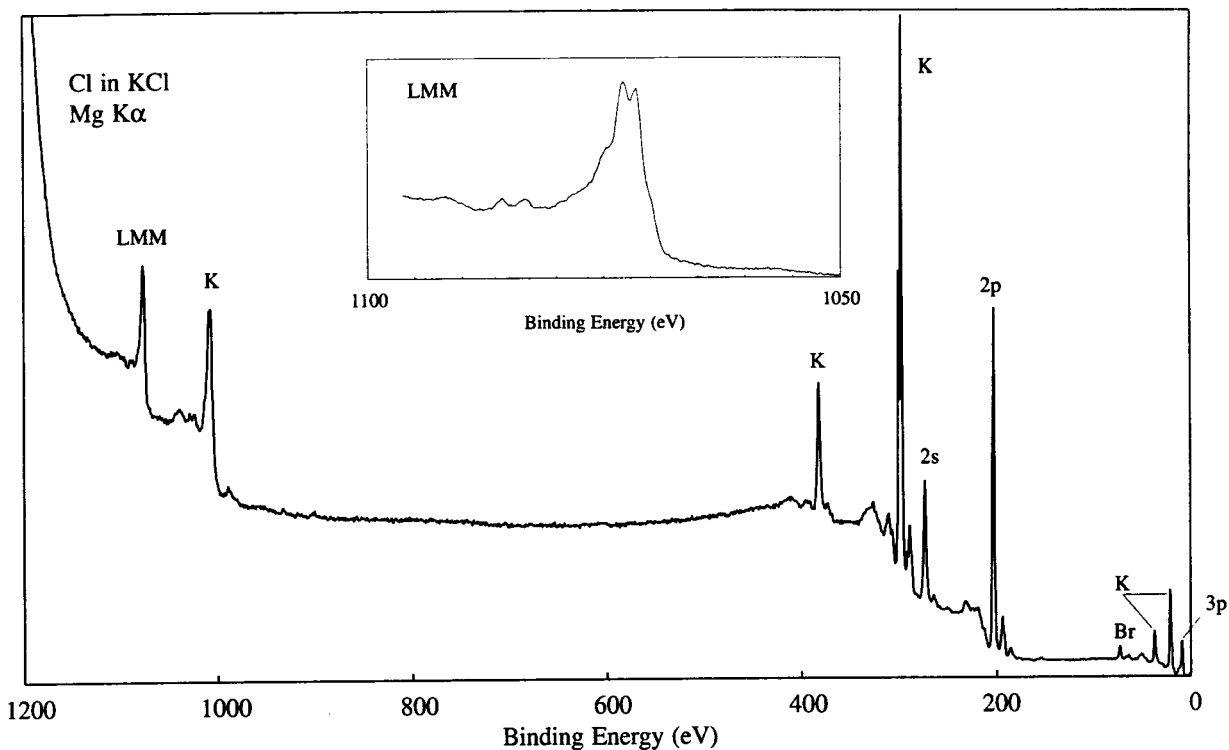


Compound Type	2p _{3/2} Binding Energy (eV)						
	160	163	166	169	172	175	178
S							
Sulfide							
Sulfite							
Sulfate							
SF ₆							
SO ₂							
Thiophene							
Mercaptan							
Cysteine							
Sulfone							

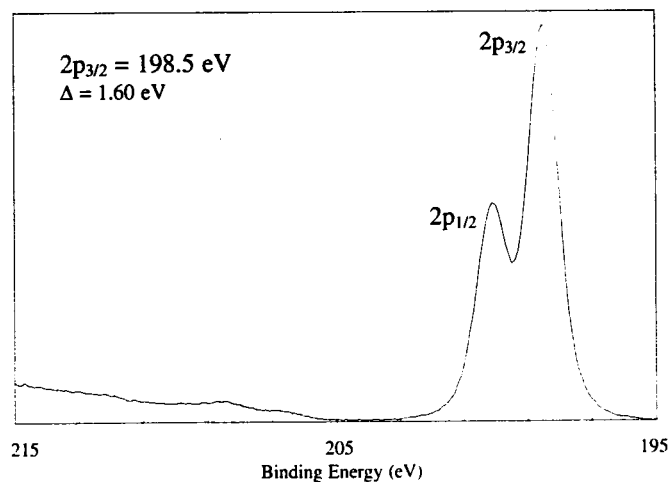


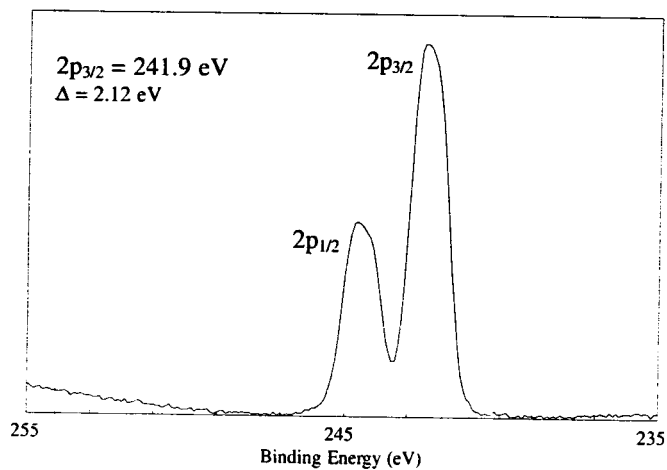
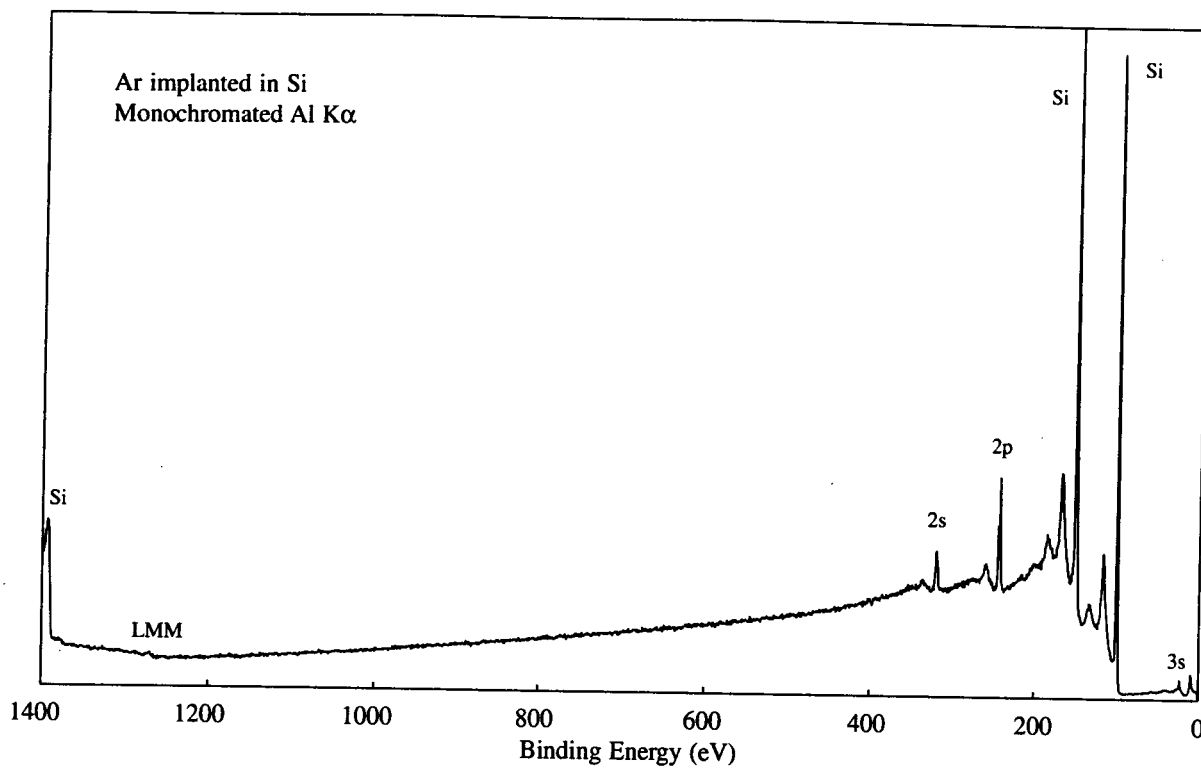


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
271	201	199	17	6
Auger Lines				
L ₂₃ M ₂₃ M ₂₃				
1304 (Al)				
1071 (Mg)				



Compound Type	2p _{3/2} Binding Energy (eV)						
	198	200	202	204	206	208	210
Alkali Chloride	■						
CuCl ₂		■					
NiCl ₂		■					
PdCl ₂	■						
K ₂ IrCl ₆	■						
Pt(NH ₃) ₂ Cl ₂	■						
Perchlorate						■	■
KClO ₃					■		
NaClO ₄						■	
C ₆ H ₅ Cl		■	■				
p(CH ₂ =CHCl)		■					





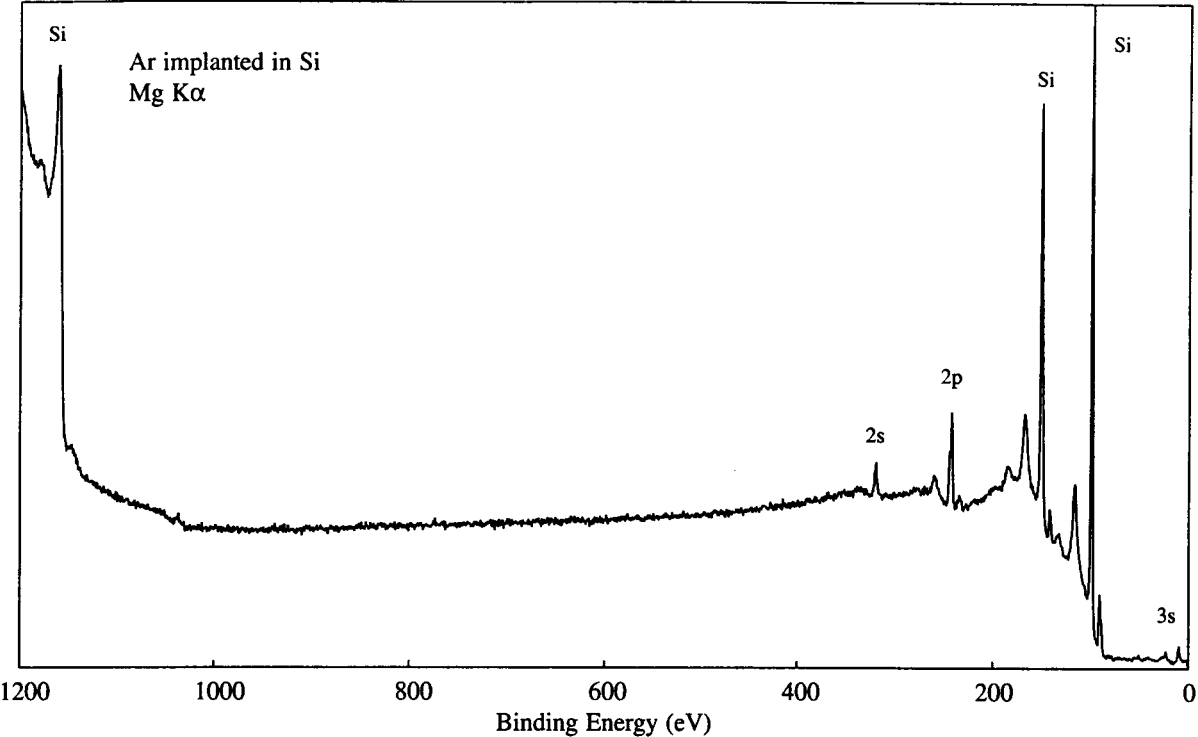
Line Positions (eV)

Photoelectron Lines

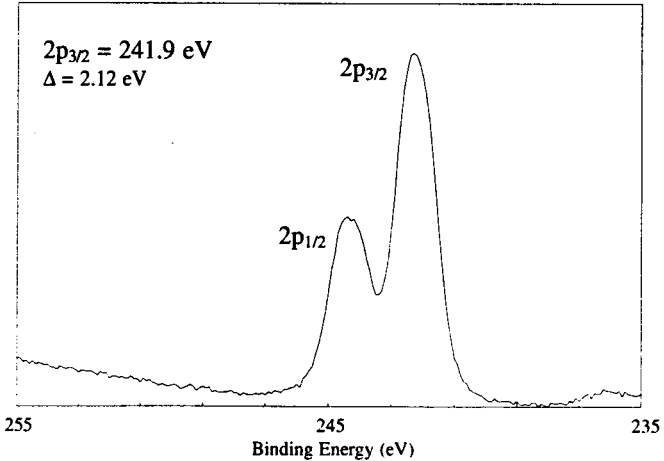
2s	2p _{1/2}	2p _{3/2}	3s
320	244	242	24

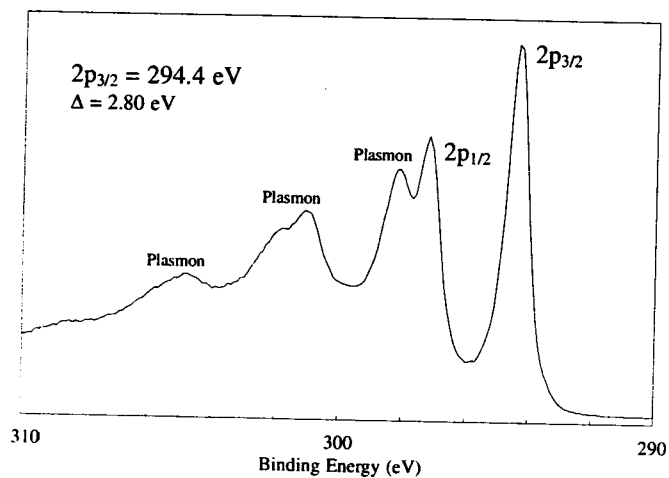
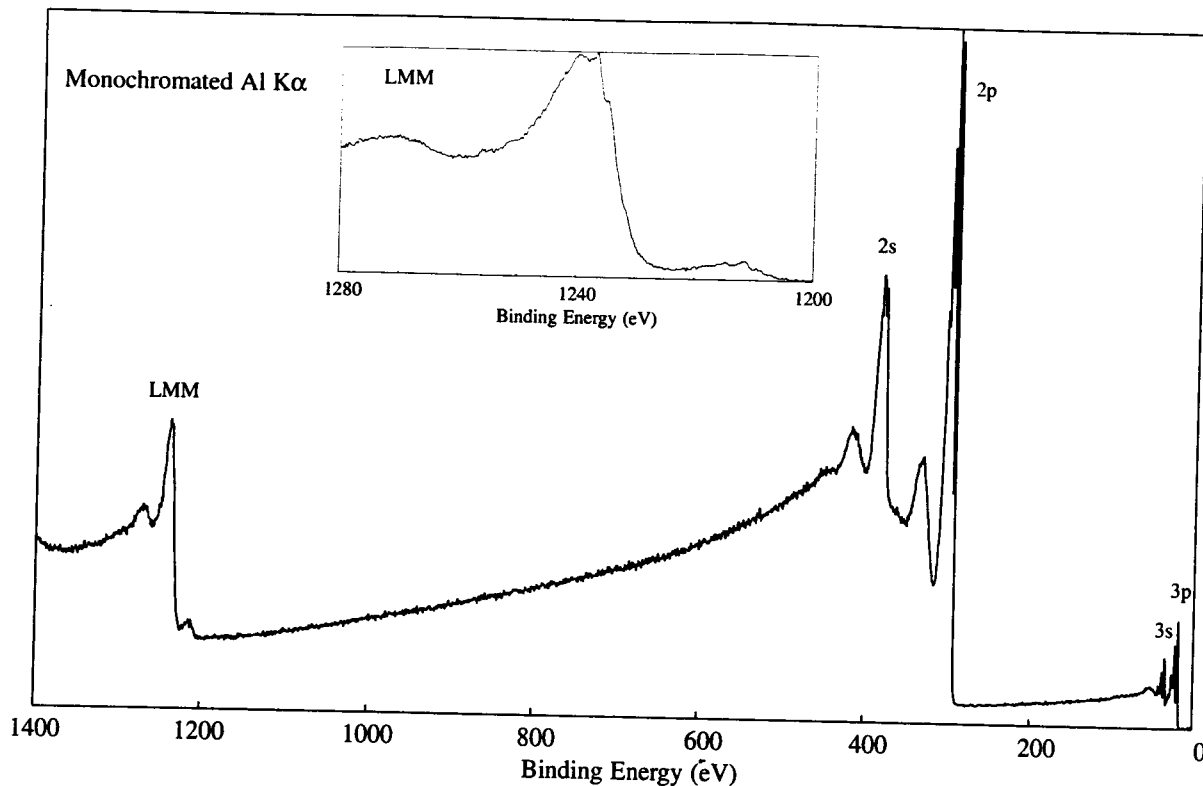
Auger Lines

L ₂₃ M ₂₃ M ₂₃	
1272	(Al)
1039	(Mg)

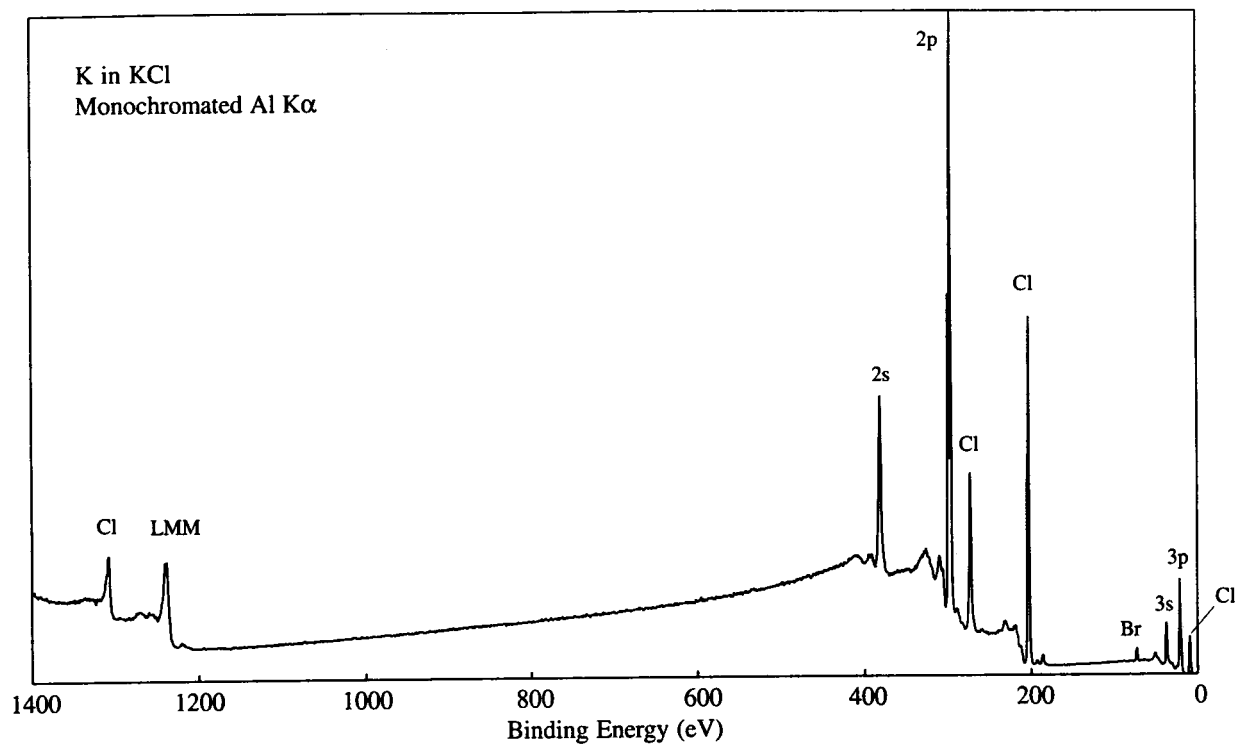


2p _{3/2} Binding Energy (eV)			
Compound Type	240	241	242
Ar in Ag			
Ar in Au			
Ar in Cu			
Ar in Pt			
Ar in graphite			
Ar in Si			

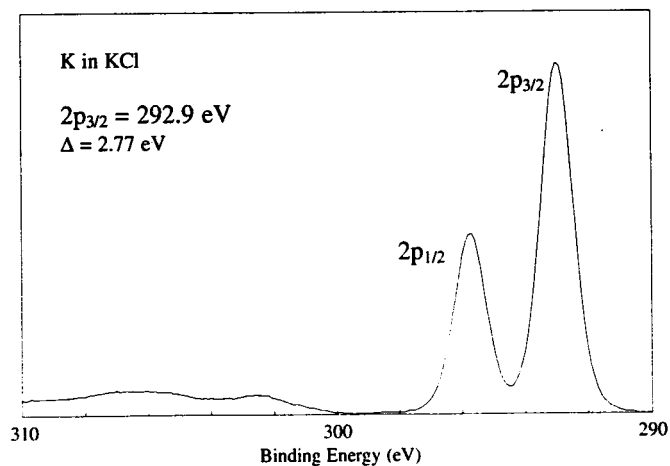


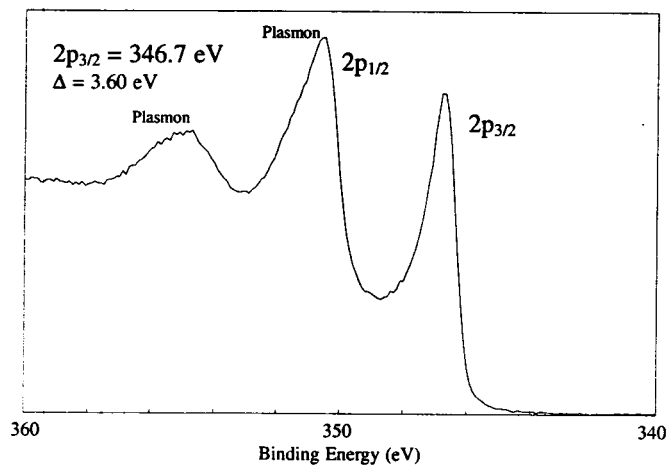
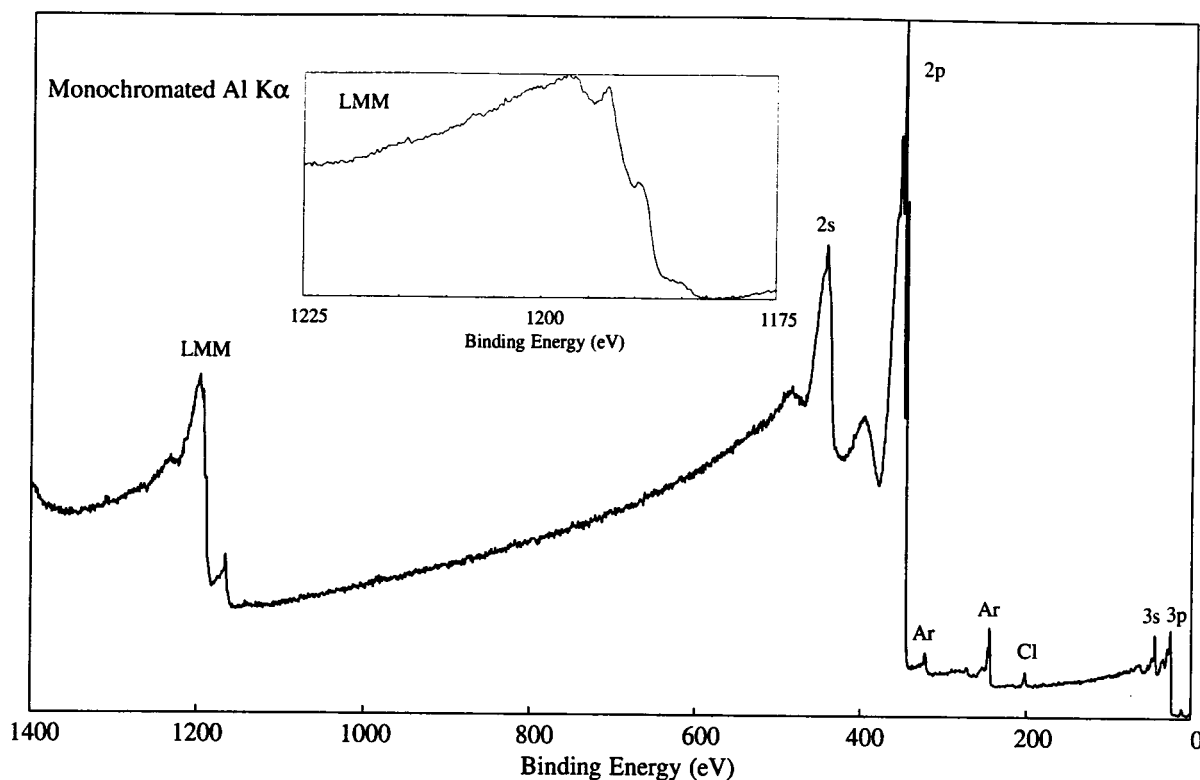


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
380	297	294	35	19
Auger Lines				
L ₂₃ M ₂₃ M ₂₃				
1239 (Al)				
1006 (Mg)				



Compound Type	2p _{3/2} Binding Energy (eV)				
	291	292	293	294	295
K					
Halides					
KCN					
KNO ₃					
KClO ₃					
KClO ₄					
K ₃ PO ₄					
K ₄ P ₂ O ₇					
K ₂ CrO ₄					
K ₂ Cr ₂ O ₇					





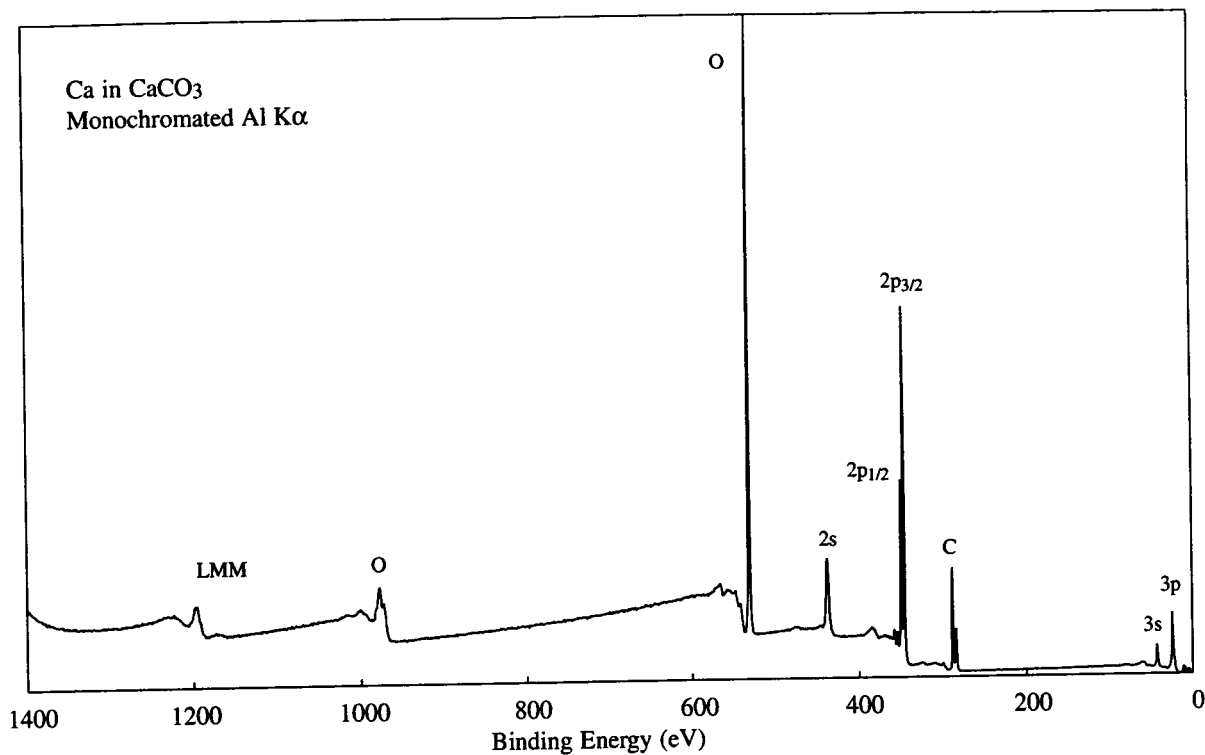
Line Positions (eV)

Photoelectron Lines

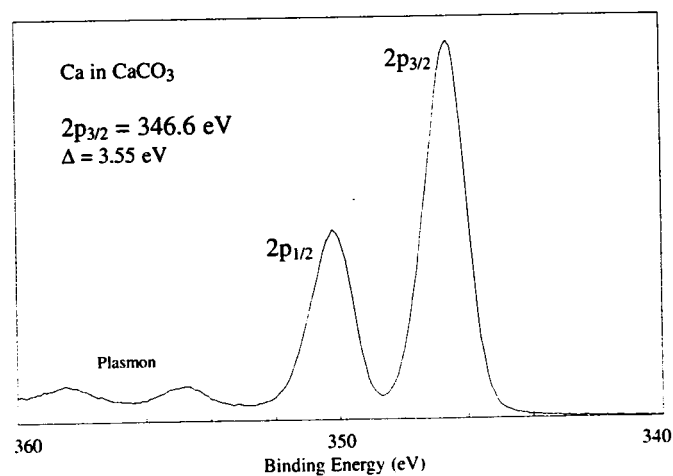
2s	2p _{1/2}	2p _{3/2}	3s	3p
440	351	347	45	26

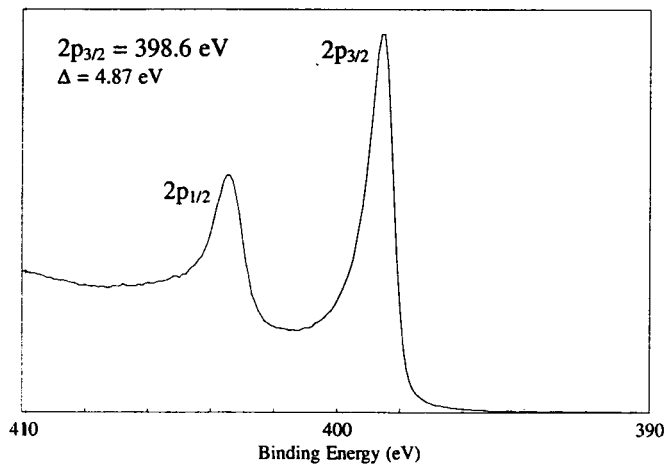
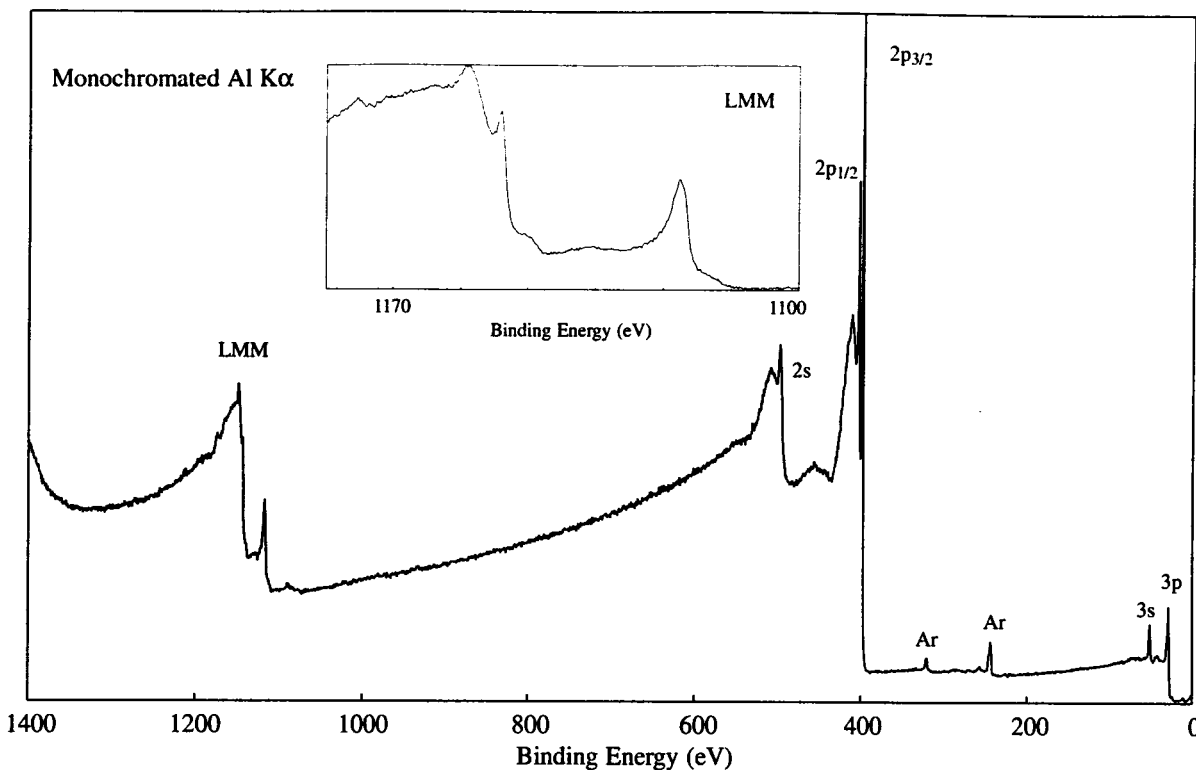
Auger Lines

L ₂₃ M ₂₃ M ₂₃	
1197	(Al)
964	(Mg)

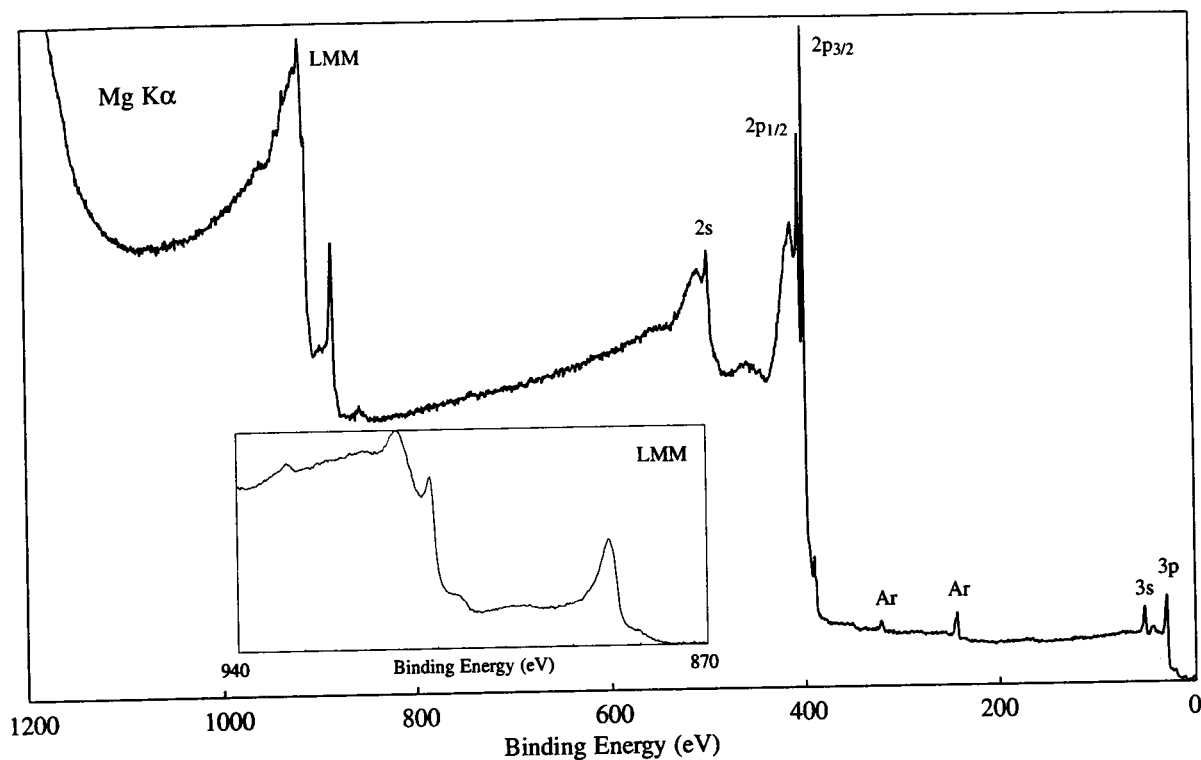


Compound Type	2p _{3/2} Binding Energy (eV)				
	345	346	347	348	349
Ca					
CaS					
CaCl ₂					
CaF ₂					
CaO					
CaCO ₃					
Ca(NO ₃) ₂					
CaCrO ₄					
CaMoO ₄					
CaSO ₄					
Ca ₃ Si ₃ O ₉					

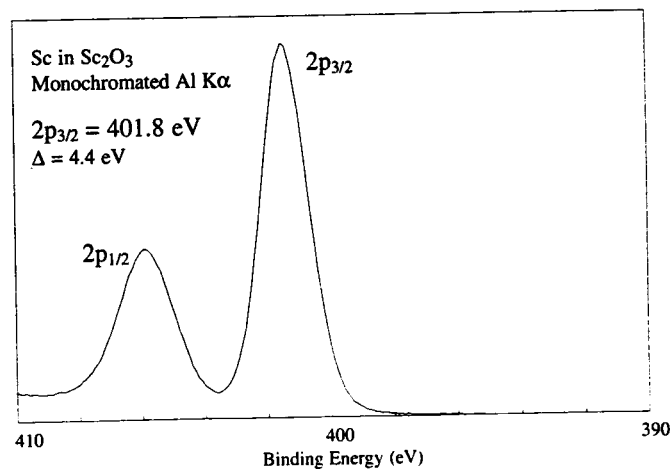


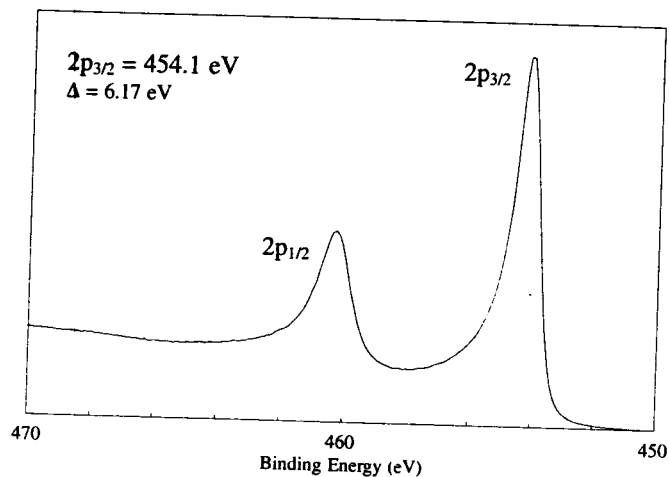
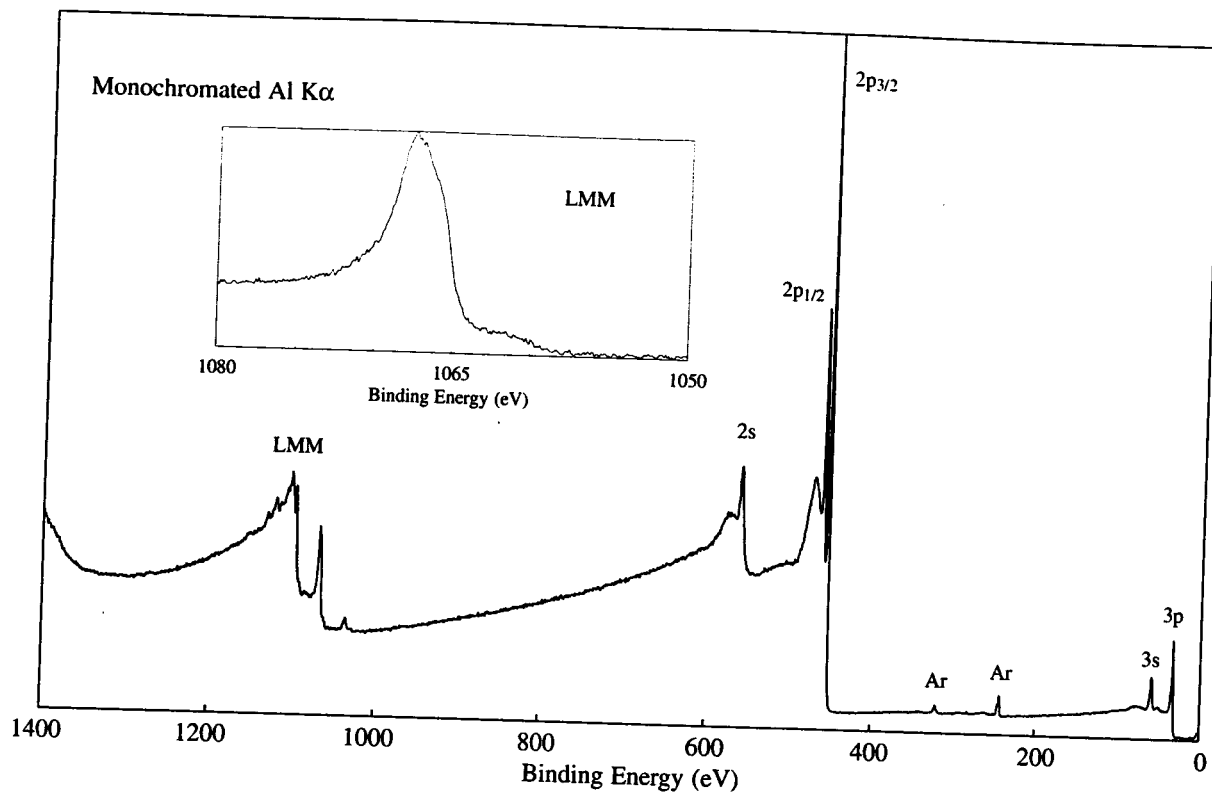


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
499	404	399	51	29
Auger Lines				
LM ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)			
1149	1118	(Al)		
916	885	(Mg)		

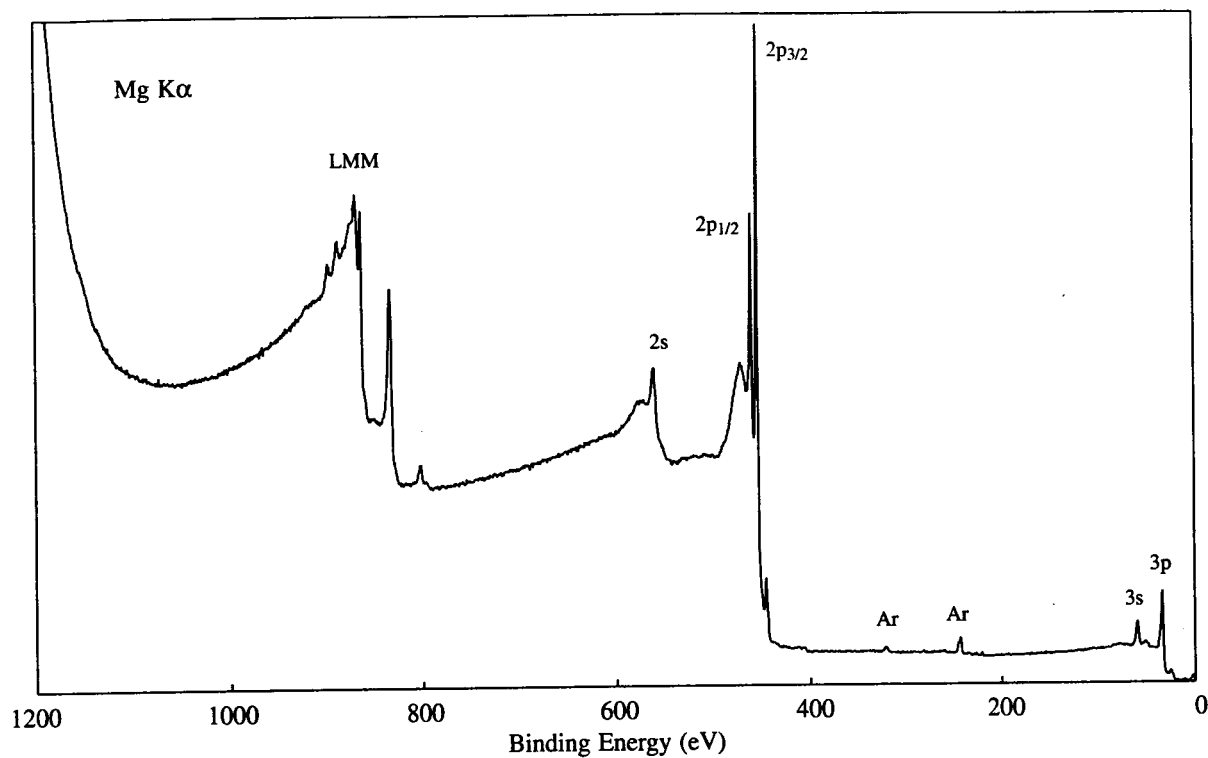


Compound Type	2p _{3/2} Binding Energy (eV)				
	398	399	400	401	402
Sc		■			
ScN			■		
Sc ₂ O ₃				■	■
ClSc(C ₅ H ₅) ₂				■	
Sc(C ₅ H ₅)(C ₈ H ₈)			■		

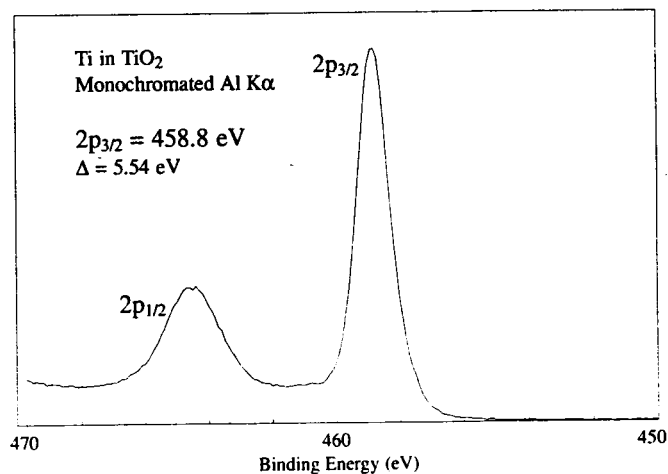


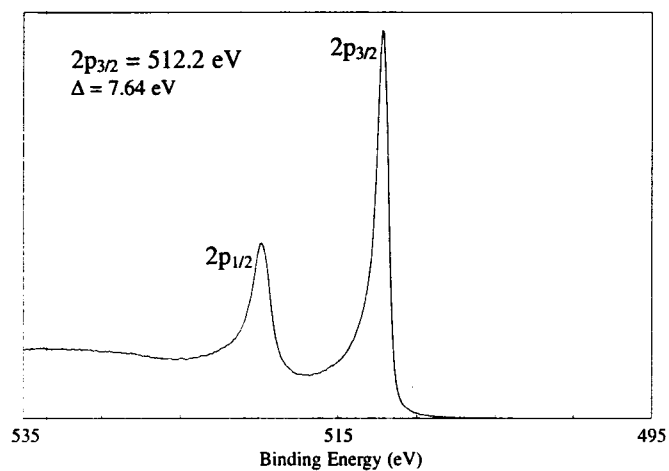
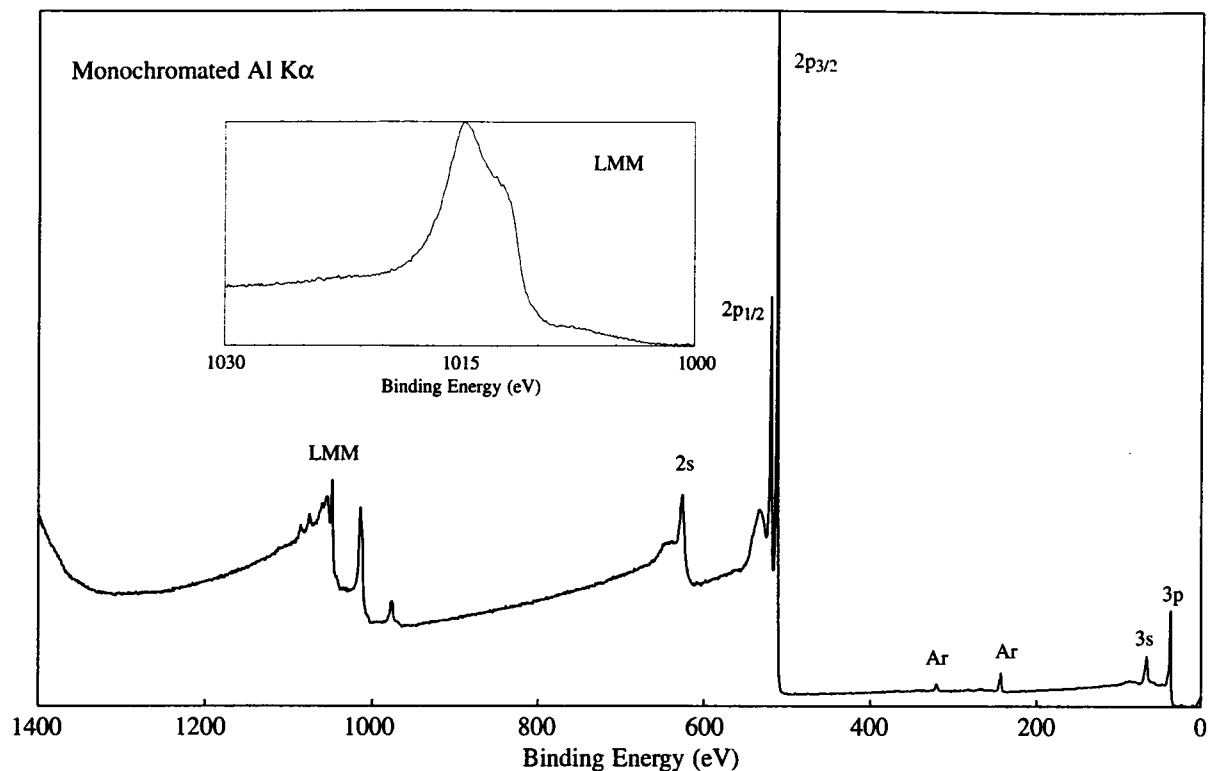


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
561	460	454	59	33
Auger Lines				
LM ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)			
1098	1068	(Al)		
865	835	(Mg)		



Compound Type	2p _{3/2} Binding Energy (eV)							
	453	454	455	456	457	458	459	460
Ti		■						
TiB ₂		■						
TiN				■			■	
TiCl ₄							■	
TiO			■					
TiO ₂							■	■
BaTiO ₃ (cubic, tetra.)							■	■
CaTiO ₃							■	■
PbTiO ₃							■	■
SrTiO ₃							■	■
Metallocene				■	■	■		





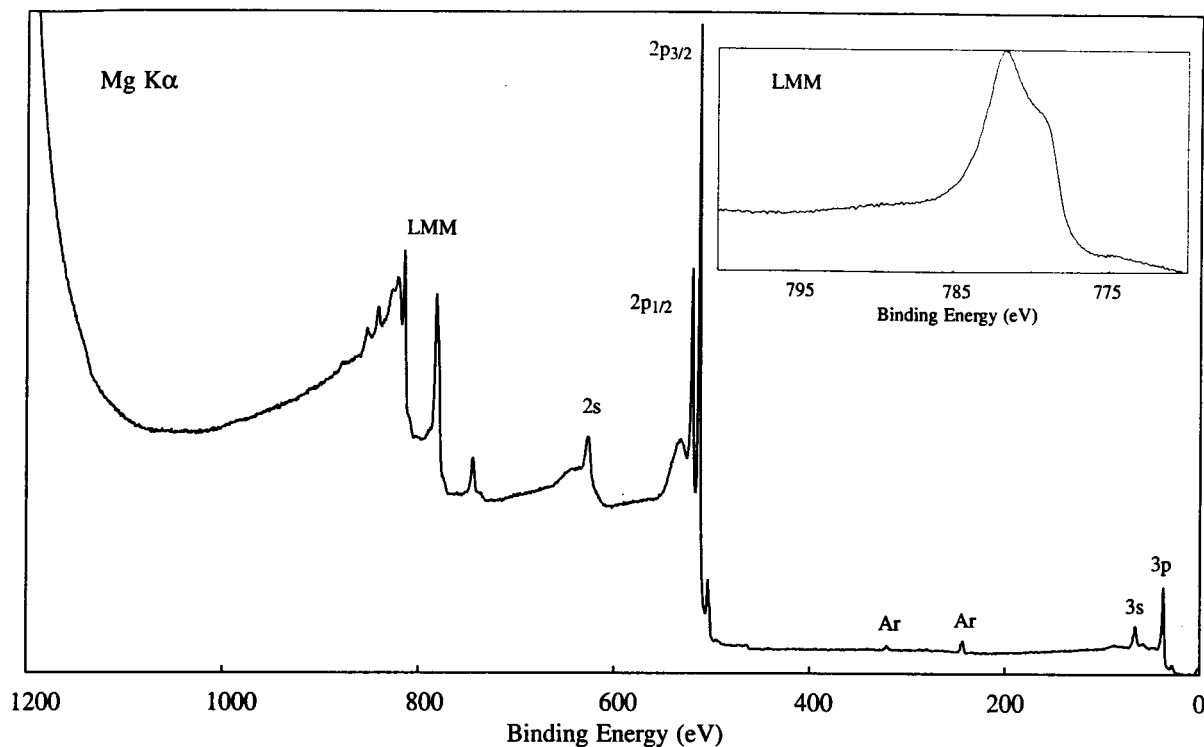
Line Positions (eV)

Photoelectron Lines

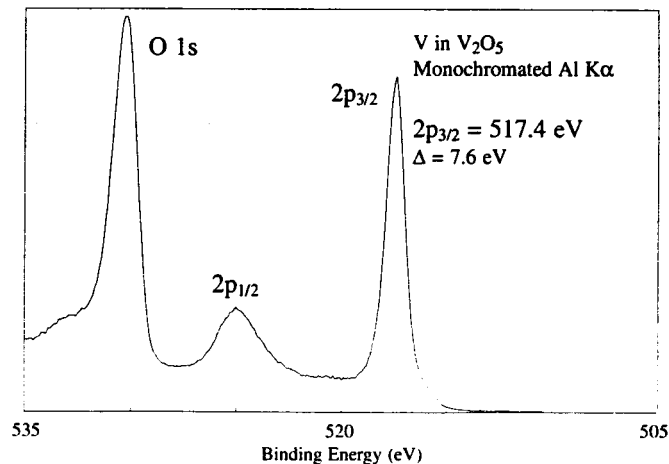
2s	2p _{1/2}	2p _{3/2}	3s	3p
627	520	512	66	37

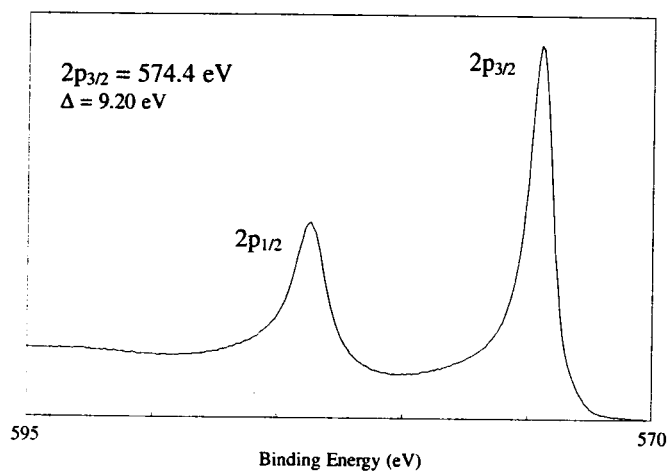
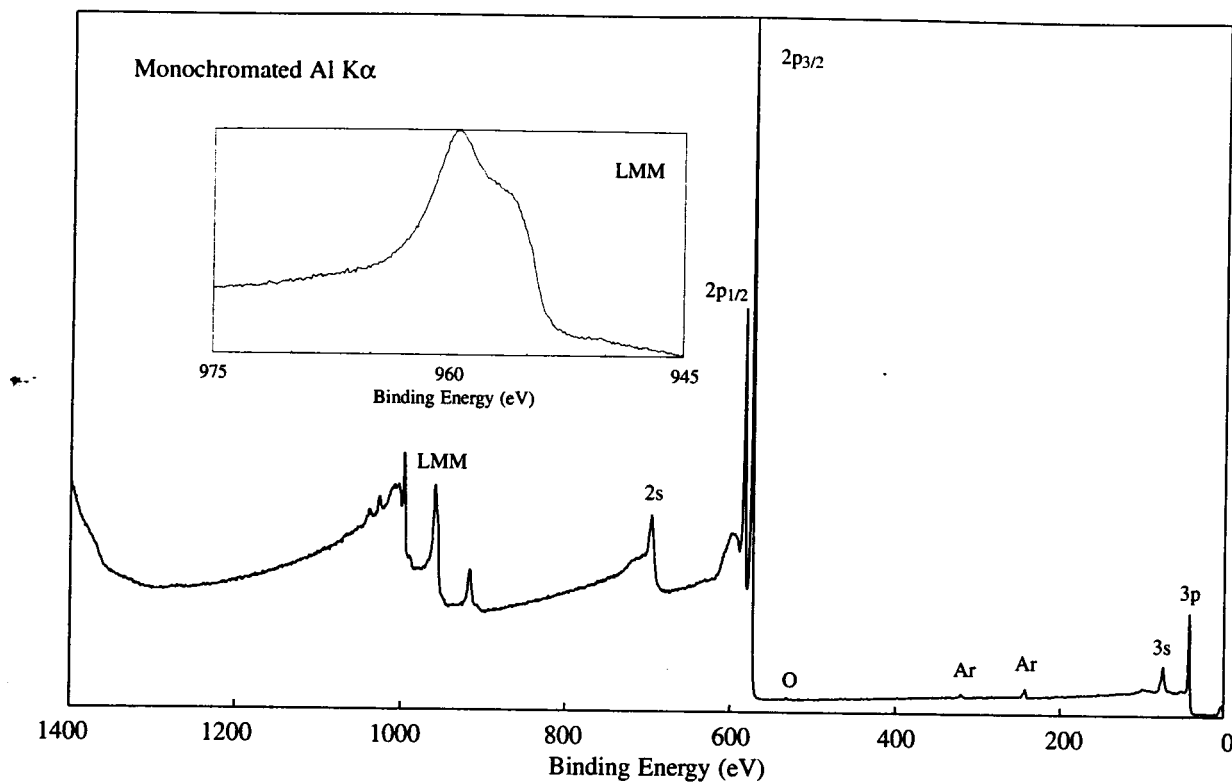
Auger Lines

L ₂₃ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅	
1048	1014	977	(Al)
815	781	744	(Mg)

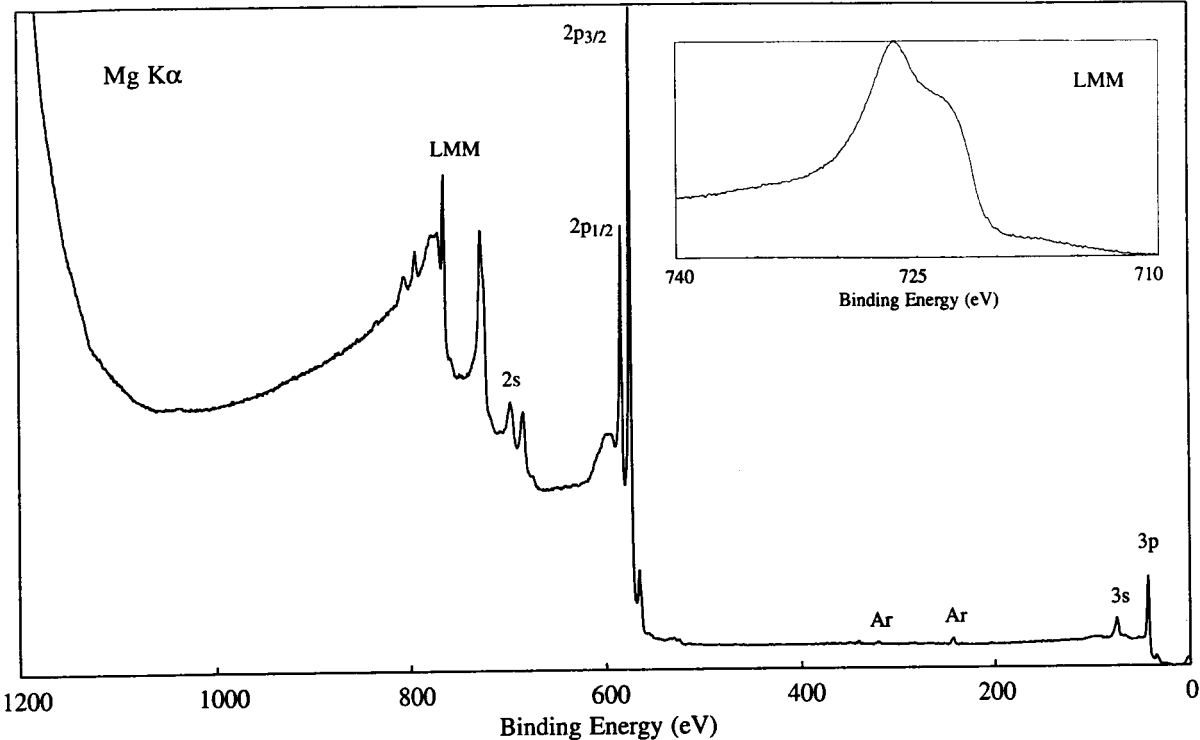


Compound Type	2p $_{3/2}$ Binding Energy (eV)						
	512	513	514	515	516	517	518
V	■						
VB ₂		■					
VN			■				
Oxide					■		
VOCl ₂						■	
VOSO ₄					■		
Vanadate						■	
K ₄ V(CN) ₆		■					
V(acac) ₃			■				
VO(acac) ₂				■			
Metallocene		■					

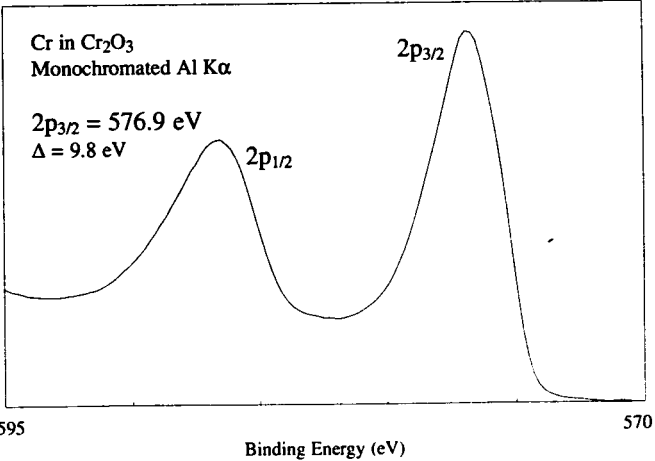


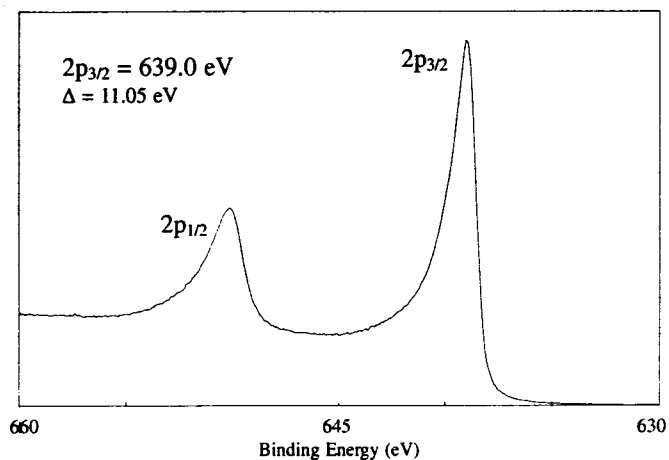
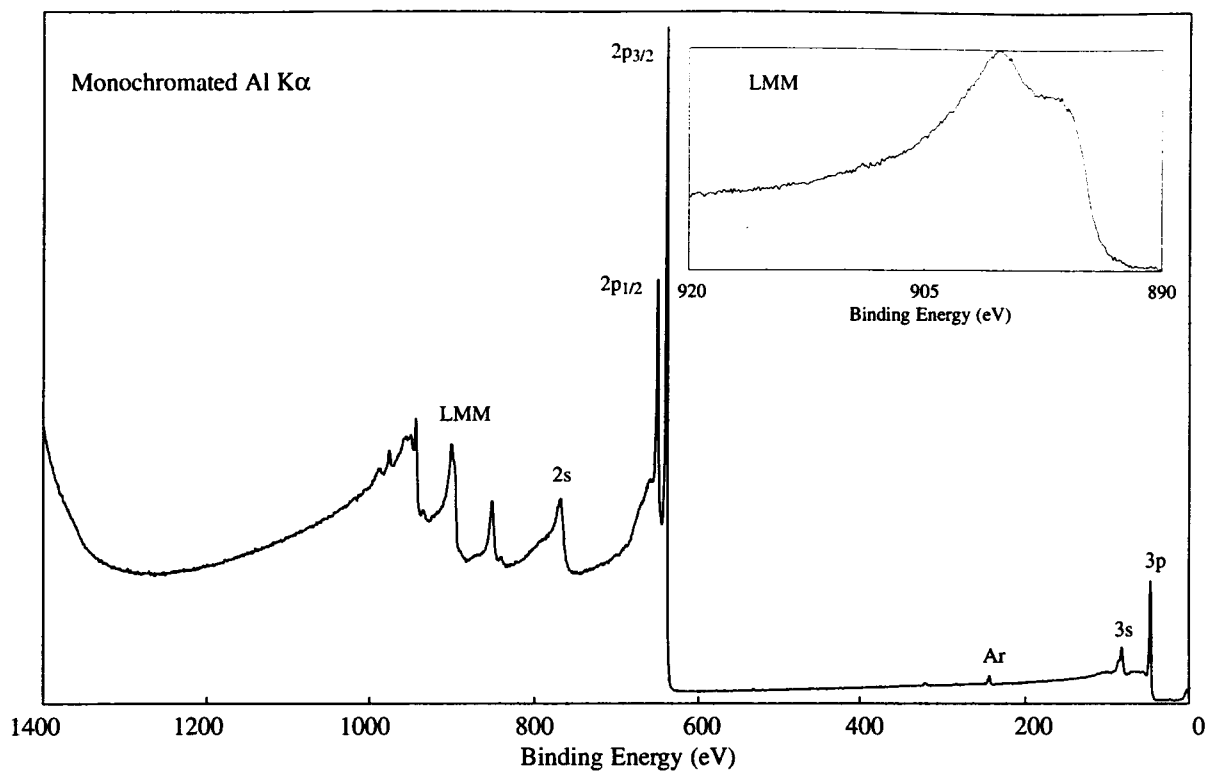


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
696	583	574	75	43
Auger Lines				
L ₂₃ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅		
997	959	917	(Al)	
764	726	684	(Mg)	



Compound Type	2p _{3/2} Binding Energy (eV)				
	574	576	578	580	582
Cr					
Cr Nitride					
CrBr ₃					
CrCl ₃					
Oxide					
CrF ₃					
Cr(OH) ₃					
CrOOH					
K ₂ Cr ₂ O ₇					
K ₃ Cr(CN) ₆					
Cr(acac) ₃					





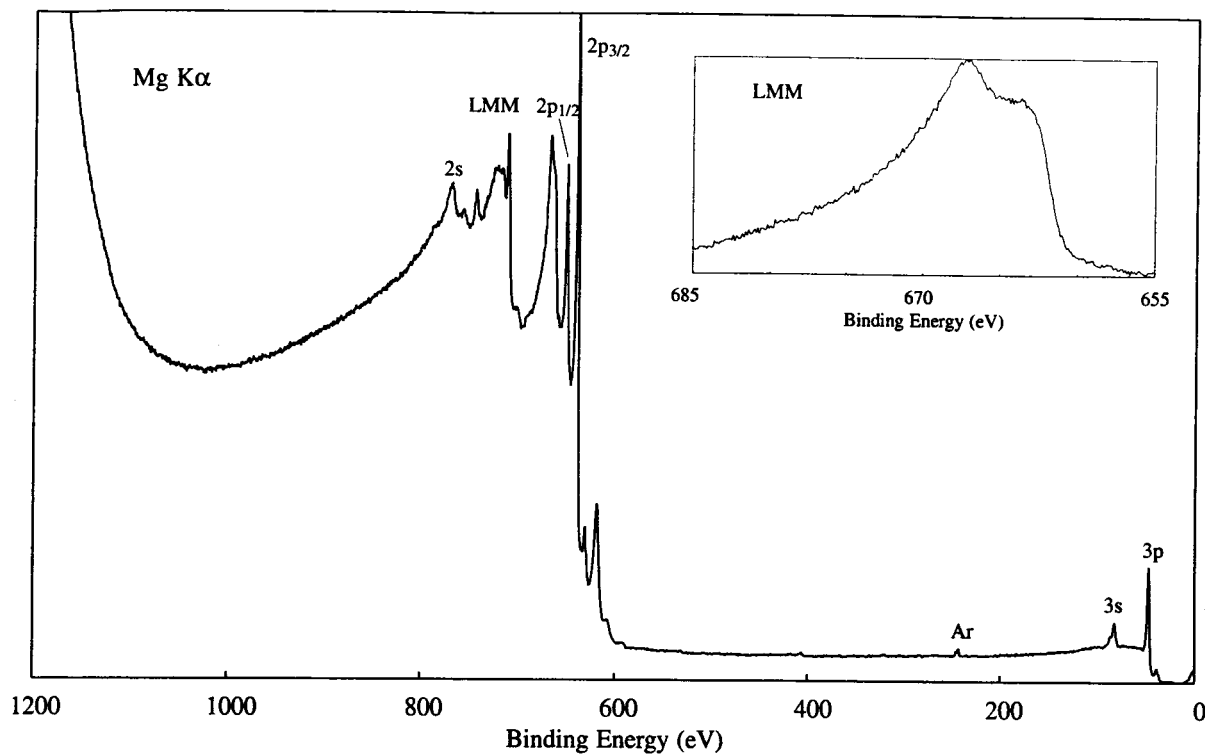
Line Positions (eV)

Photoelectron Lines

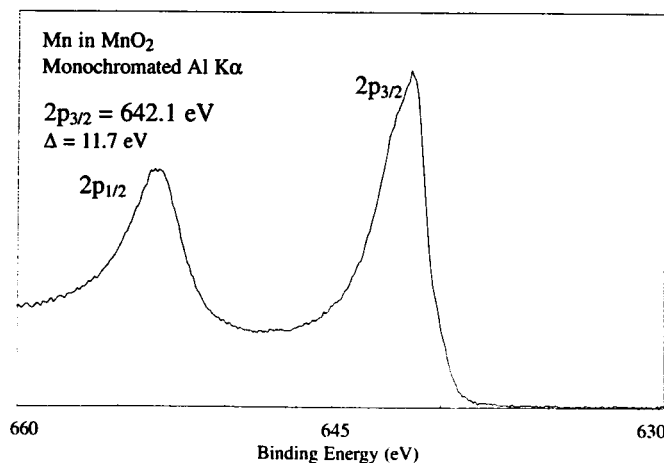
2s	2p _{1/2}	2p _{3/2}	3s	3p
769	650	639	83	48

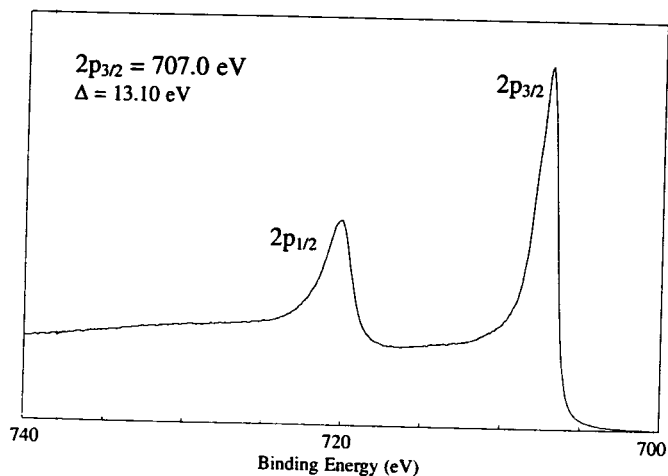
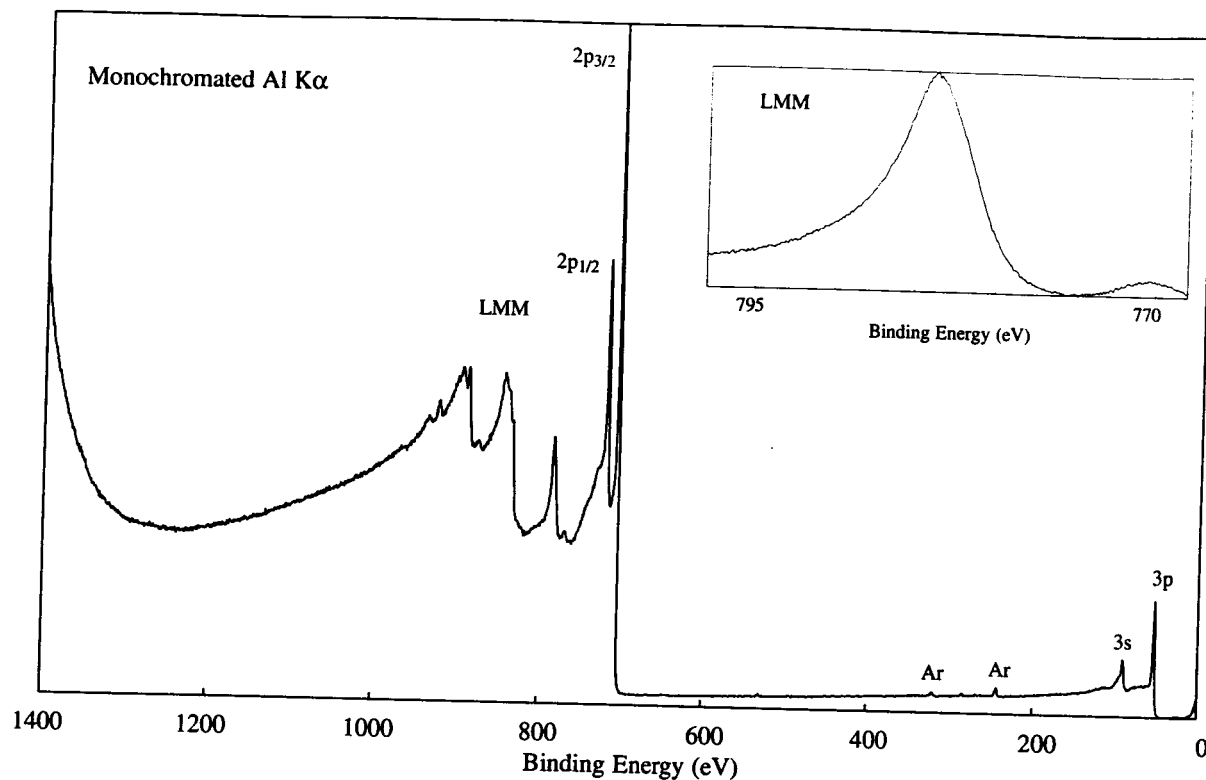
Auger Lines

L ₂₃ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅	L ₃ M ₄₅ M ₄₅	
944	900	852	(Al)
711	667	619	(Mg)

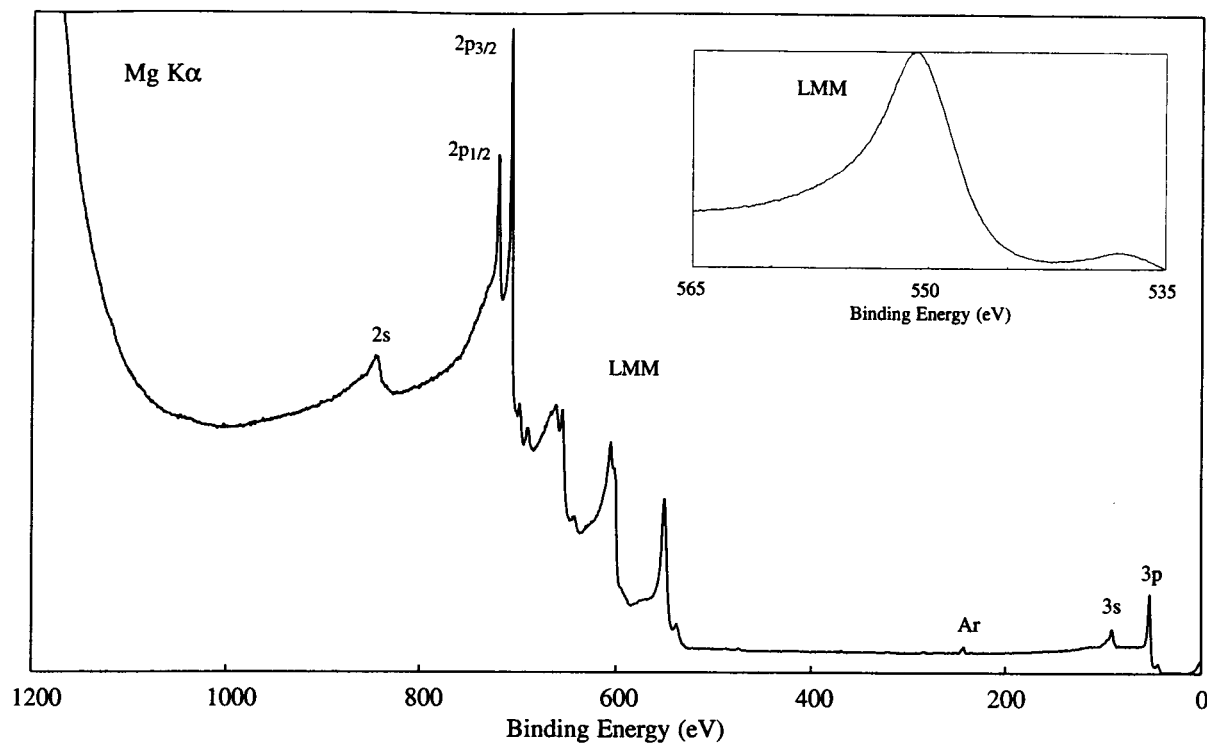


Compound Type	2p _{3/2} Binding Energy (eV)							
	638	639	640	641	642	643	644	645
Mn		■						
MnS			■	■	■			
MnCl ₂				■	■			
MnF ₃						■		
MnO			■	■	■			
Mn ₂ O ₃				■	■			
Mn ₂ O ₄				■	■			
MnO ₂			■	■	■			
MnOOH				■	■			
MnSO ₄							■	
Mn(C ₅ H ₅) ₂	■							

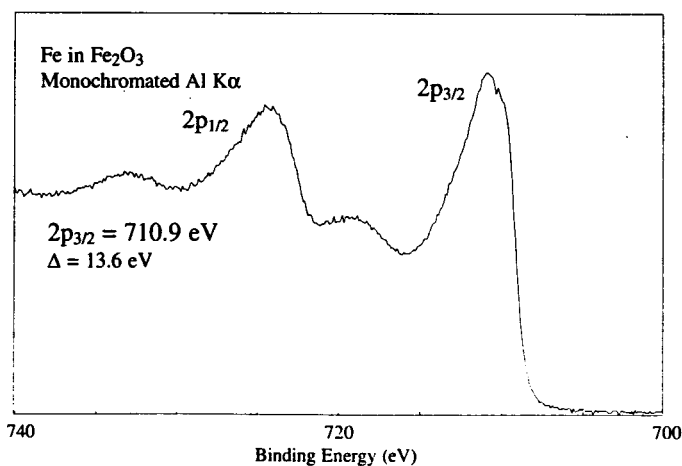


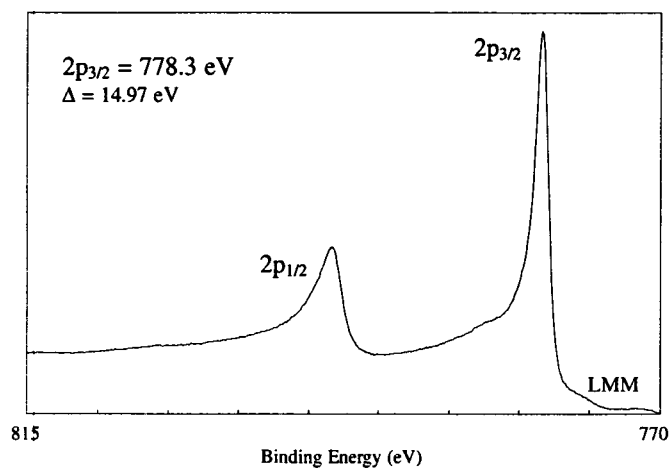
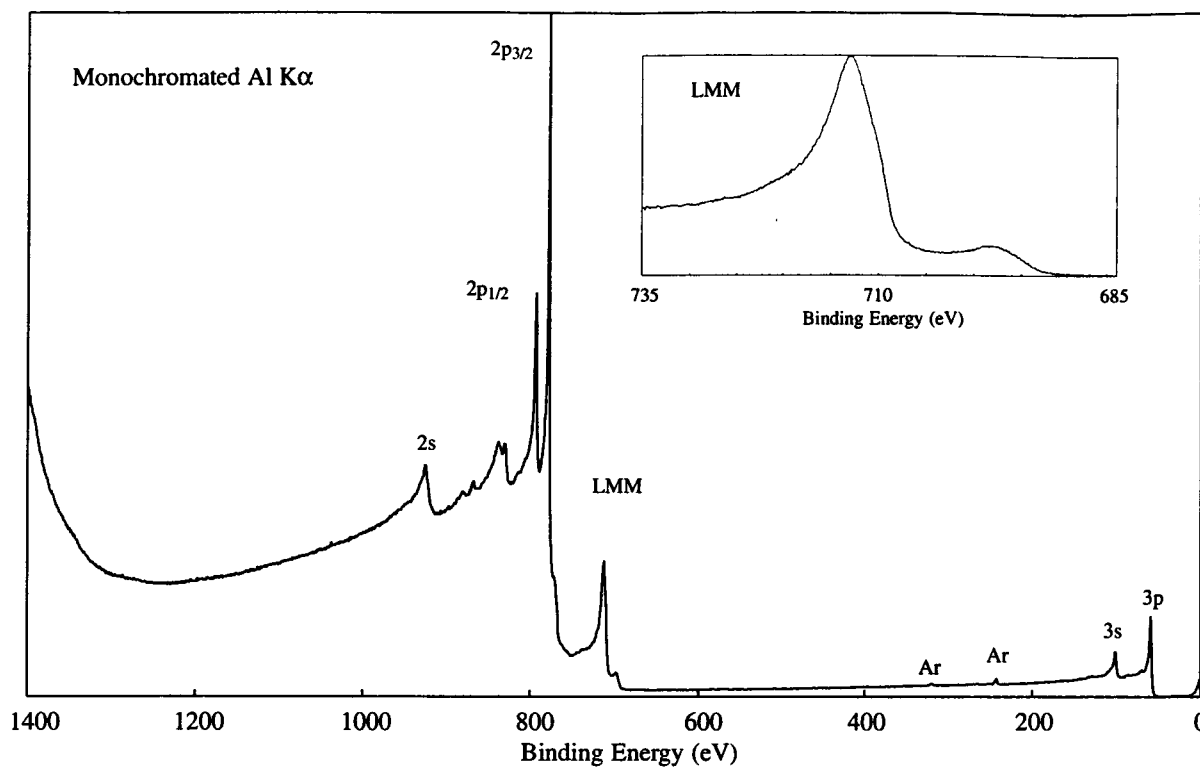


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
845	720	707	92	53
Auger Lines				
LM ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅		
888	839	784	(Al)	
655	606	551	(Mg)	

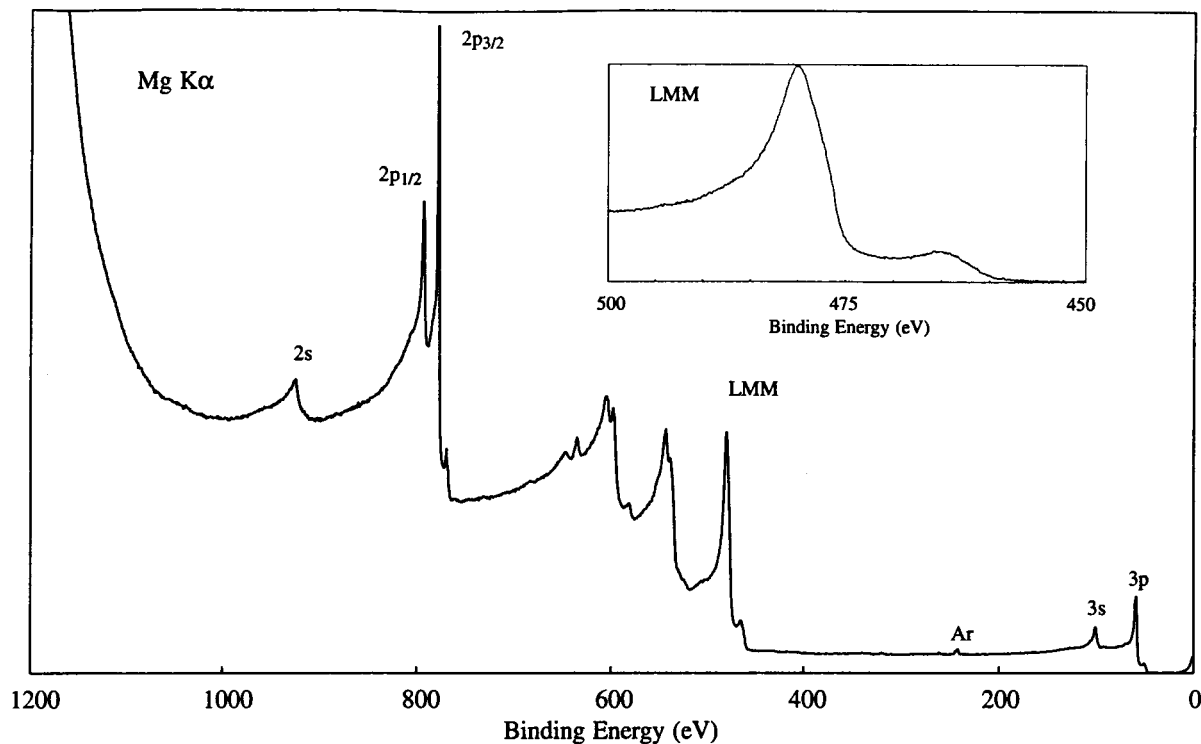


Compound Type	2p _{3/2} Binding Energy (eV)							
	706	707	708	709	710	711	712	713
Fe		■					■	
FeS		■					■	
FeS ₂ (markasite, pyr)	■						■	
FeCl ₂						■		
FeCl ₃						■		
FeO				■				
Fe ₂ O ₃					■			
FeOOH						■		
FeSO ₄							■	
K ₃ Fe(CN) ₆				■				
K ₄ Fe(CN) ₆		■	■	■				

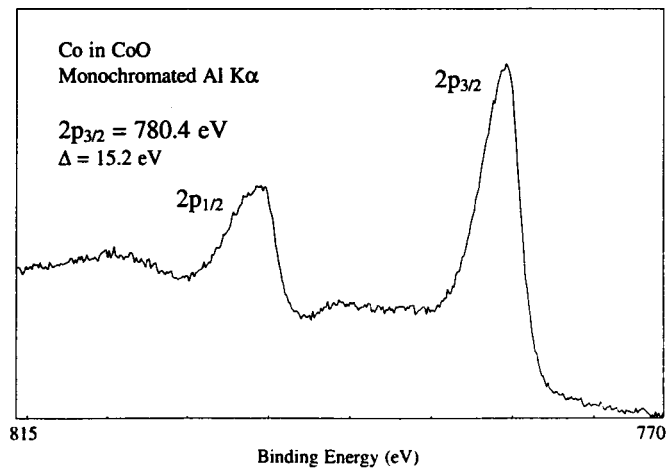


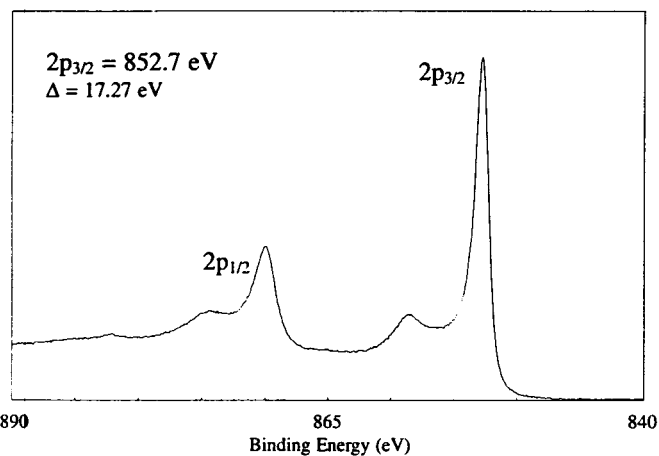


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
925	793	778	101	60
Auger Lines				
L ₃ M ₂₃ M ₂₃	L ₂ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)		
838	831	777	(Al)	
605	598	544	(Mg)	
L ₃ M ₂₃ M ₄₅ (³ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅		
771	713	698	(Al)	
538	480	465	(Mg)	

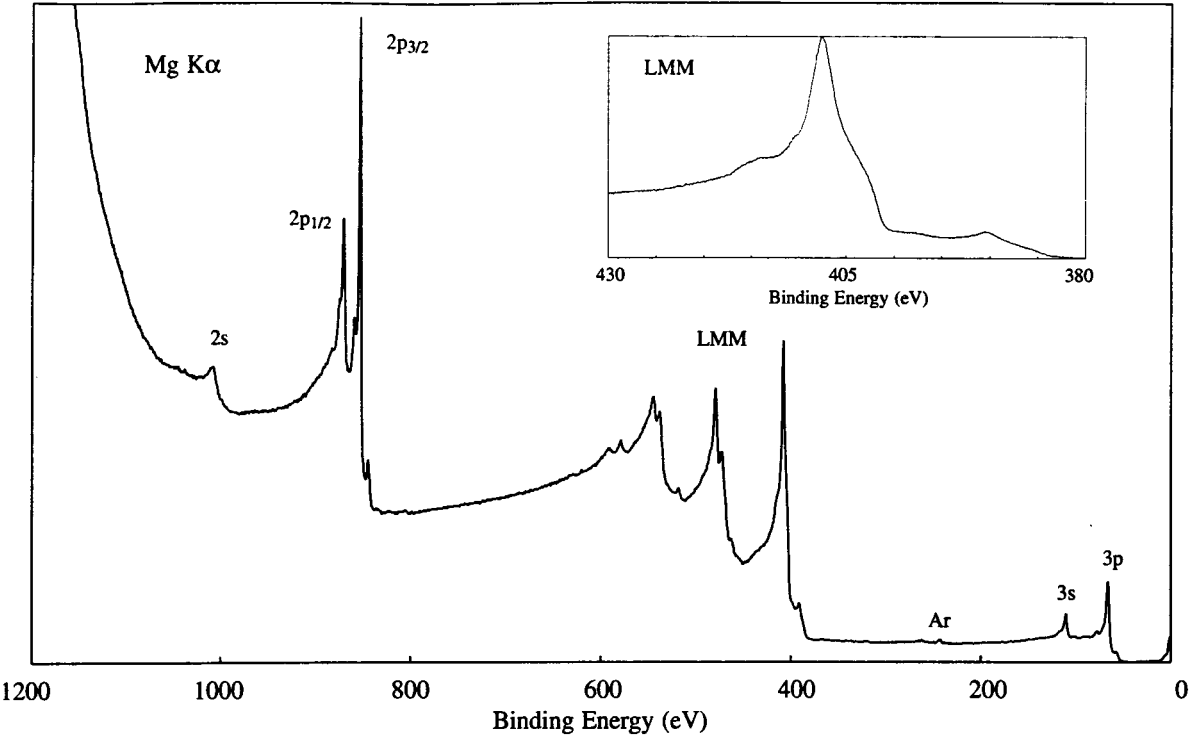


Compound Type	2p _{3/2} Binding Energy (eV)						
	778	779	780	781	782	783	784
Co	■						
CoF ₂						■	
CoF ₃					■	■	
CoO			■				
Co ₃ O ₄		■	■				
Co ₂ O ₃		■	■				
CoOOH		■	■				
Co(OH) ₂				■			
CoSO ₄							■
Co(NH ₃) ₃ Cl ₃				■	■		

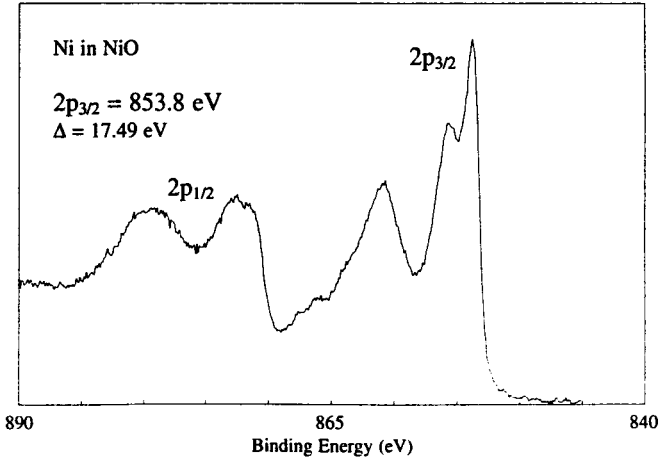


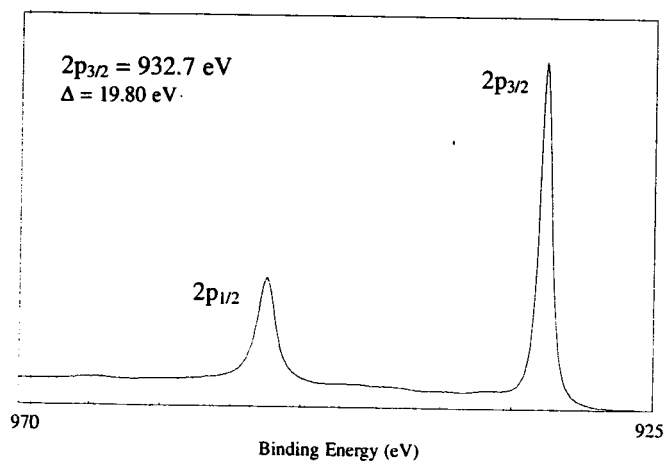
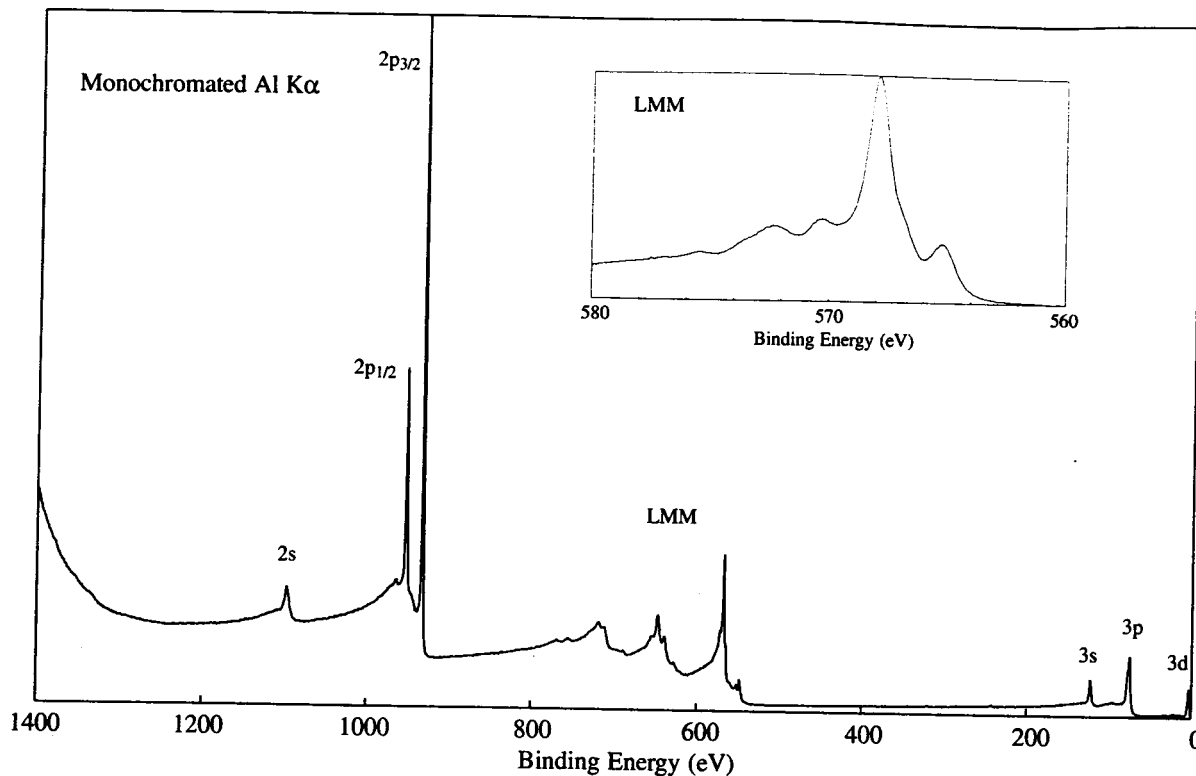


Line Positions (eV)				
<u>Photoelectron Lines</u>				
2s	2p _{1/2}	2p _{3/2}	3s	3p
1009	870	853	111	67
<u>Auger Lines</u>				
L ₃ M ₂₃ M ₂₃	L ₂ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)		
778	772	712		
545	539	479		
L ₃ M ₂₃ M ₄₅ (³ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅		
706	641	624	(Al)	
473	408	391	(Mg)	

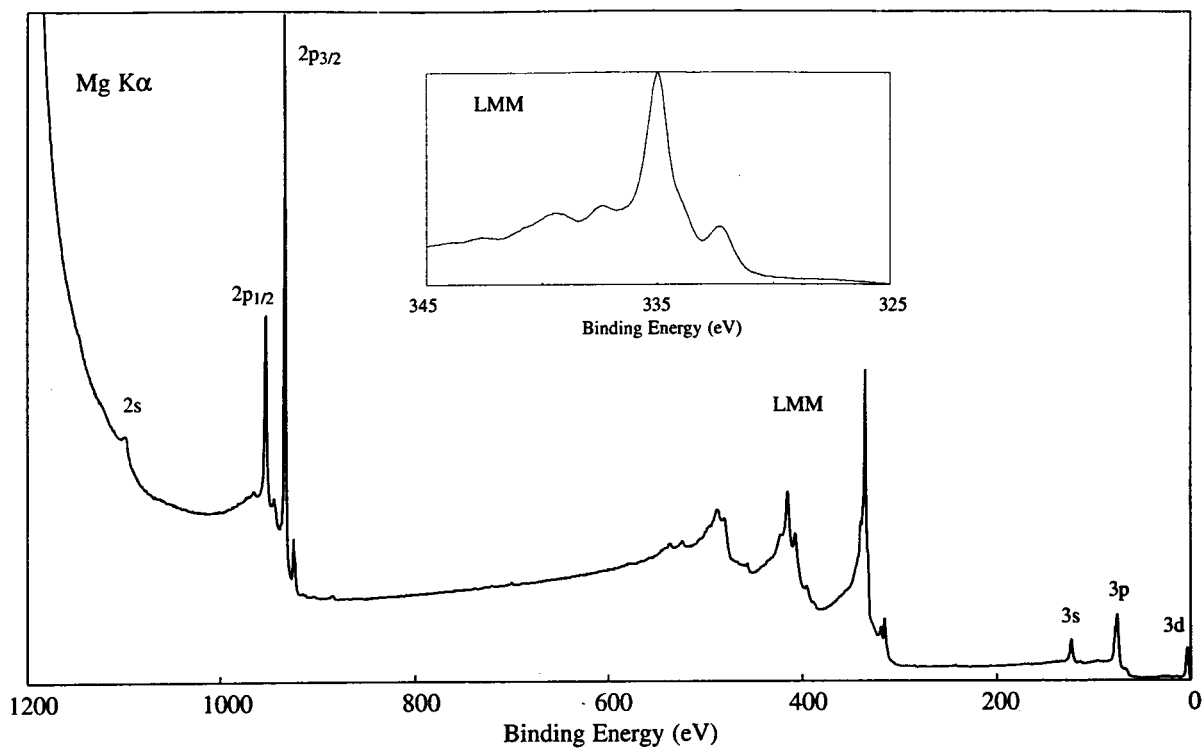


2p _{3/2} Binding Energy (eV)							
Compound Type	852	853	854	855	856	857	858
Ni		■					
Silicides		■	■				
NiS		■	■				
Halides					■	■	■
NiO			■	■			
Ni ₂ O ₃					■	■	■
Ni(NO ₃) ₂					■	■	
Ni(acac) ₂					■		
Ni(OAc) ₂ · 4H ₂ O						■	
Ni(dimethylglyoxim) ₂				■			

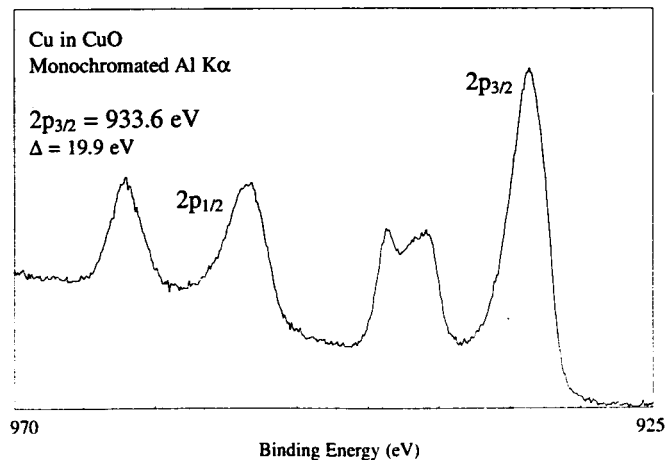


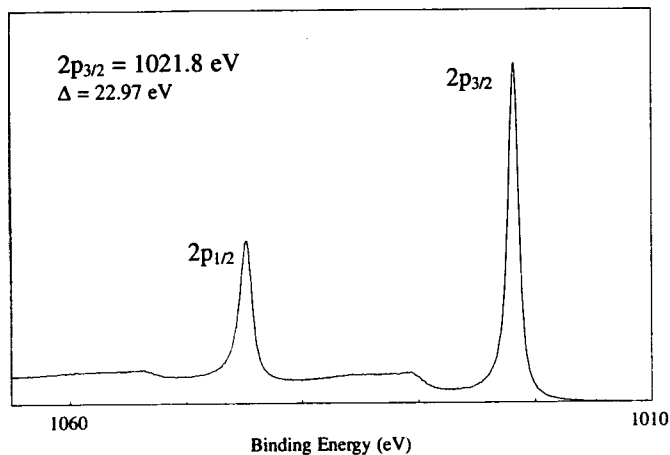
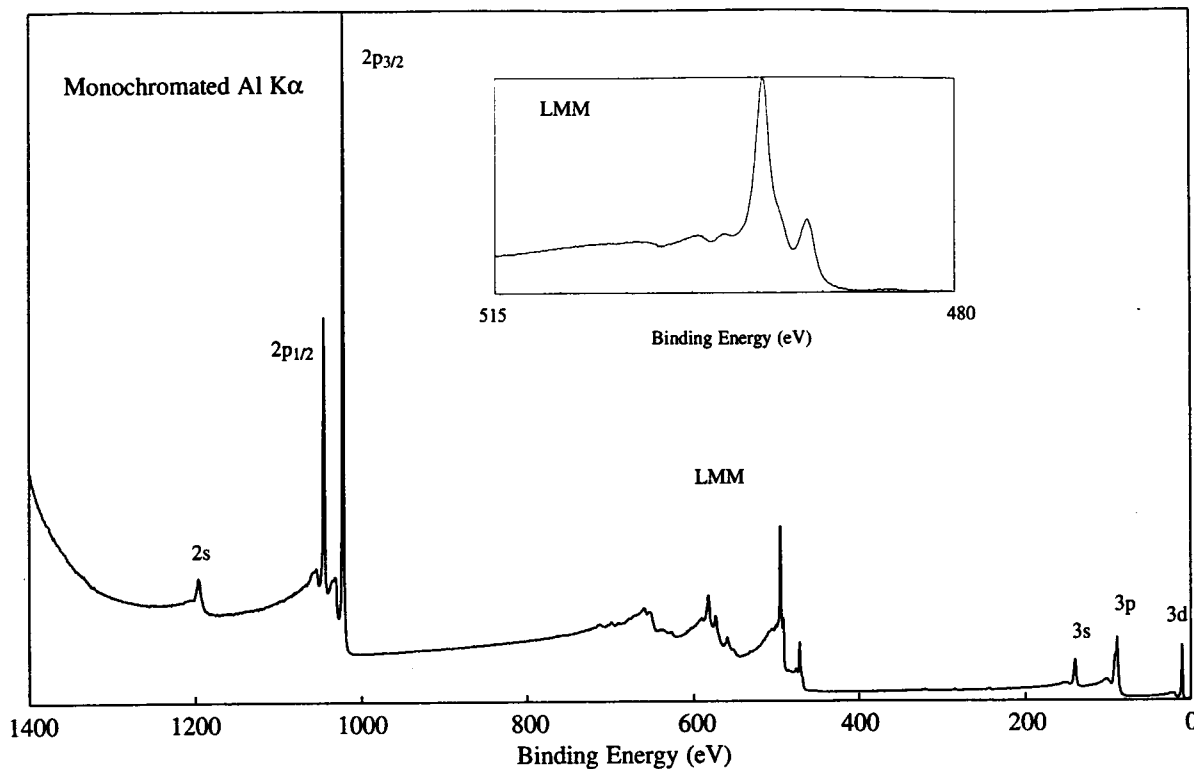


Line Positions (eV)					
Photoelectron Lines					
2s	2p $_{1/2}$	2p $_{3/2}$	3s	3p $_{1/2}$	3p $_{3/2}$
1097	953	933	123	77	75
Auger Lines					
L $_3$ M $_{23}$ M $_{23}$		L $_2$ M $_{23}$ M $_{23}$		L $_3$ M $_{23}$ M $_{45}$ (1 P)	
719		712		648 (Al)	
486		479		415 (Mg)	
L $_3$ M $_{23}$ M $_{45}$ (3 P)		L $_2$ M $_{23}$ M $_{45}$ (1 P)		L $_3$ M $_{45}$ M $_{45}$	
640		628		568	
407		395		335	
				L $_2$ M $_{45}$ M $_{45}$	
				548 (Al)	
				315 (Mg)	

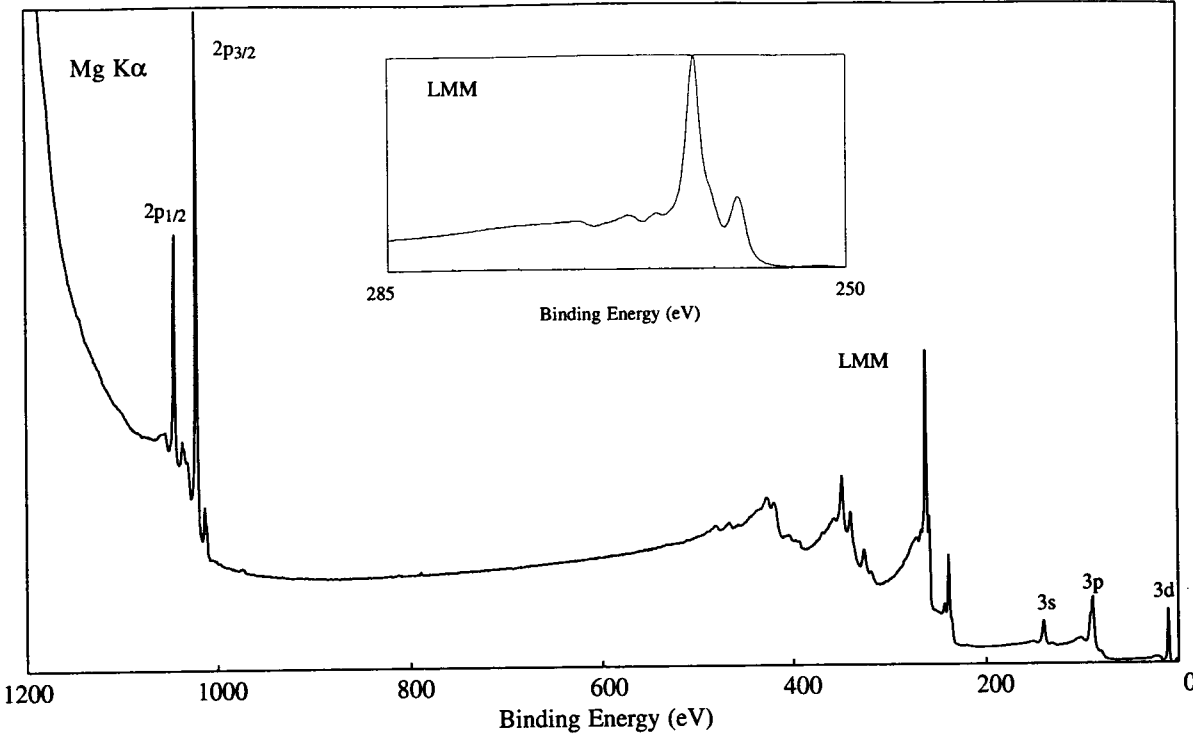


Compound Type	2p _{3/2} Binding Energy (eV)					
	931	932	933	934	935	936
Cu						
Cu ₂ S						
CuS						
CuCl						
CuCl ₂						
Cu ₂ O						
CuO						
Cu(OH) ₂						
CuSO ₄						
Cu(OAc) ₂						
Cu(salicylaloxime)						

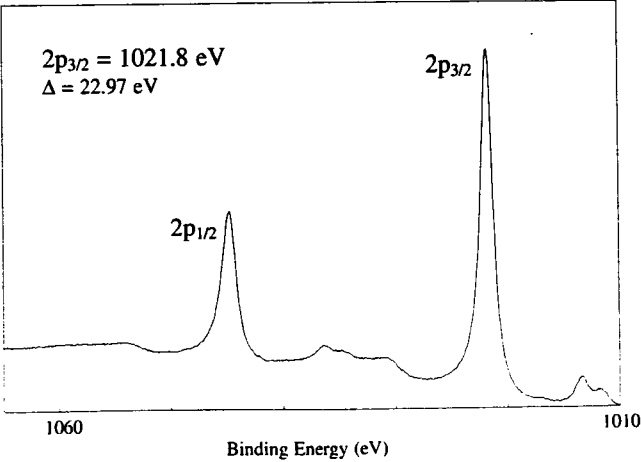


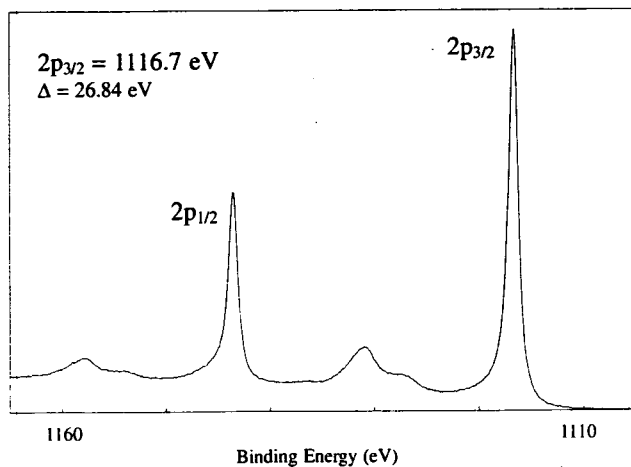
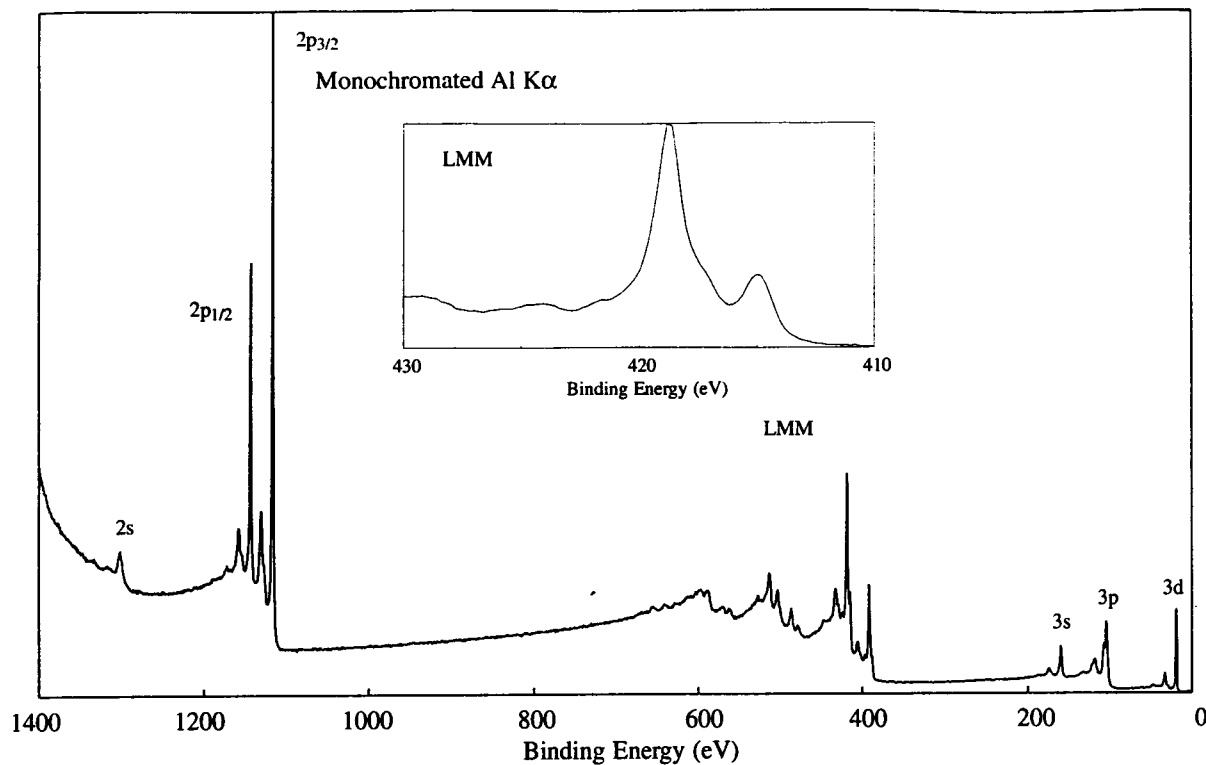


Line Positions (eV)						
Photoelectron Lines						
2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d
1195	1045	1022	140	91	89	10
Auger Lines						
L ₃ M ₂₃ M ₂₃		L ₂ M ₂₃ M ₂₃		L ₃ M ₂₃ M ₄₅ (¹ P)		
660		652		582 (Al)		
427		419		349 (Mg)		
L ₃ M ₂₃ M ₄₅ (³ P)		L ₂ M ₂₃ M ₄₅ (¹ P)		L ₃ M ₄₅ M ₄₅		L ₂ M ₄₅ M ₄₅
573		559		495		472 (Al)
340		326		262		239 (Mg)

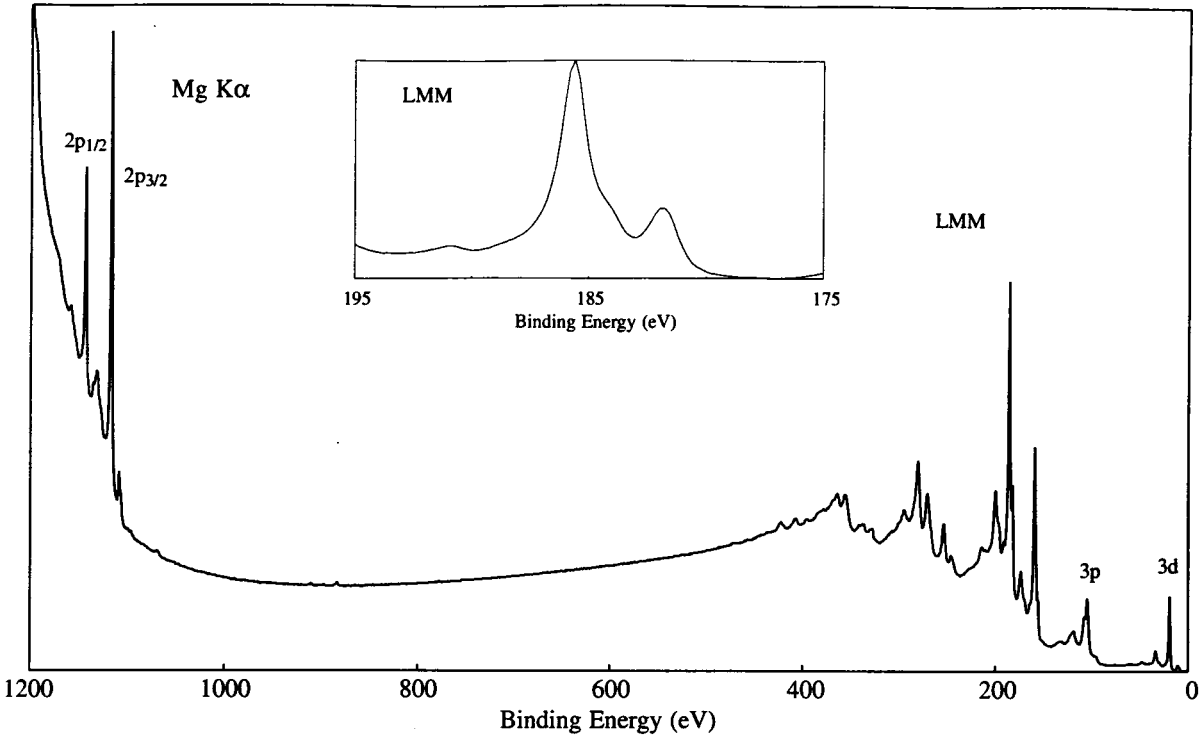


2p _{3/2} Binding Energy (eV)					
Compound Type	1020	1021	1022	1023	1024
Zn					
ZnS					
Phosphide					
Halides					
ZnO					
Zn(acac) ₂					
(Me ₄ N) ₂ ZnBr ₄					
ZnSO ₄					
Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O					
ZnCr ₂ O ₄					
ZnRh ₂ O ₄					



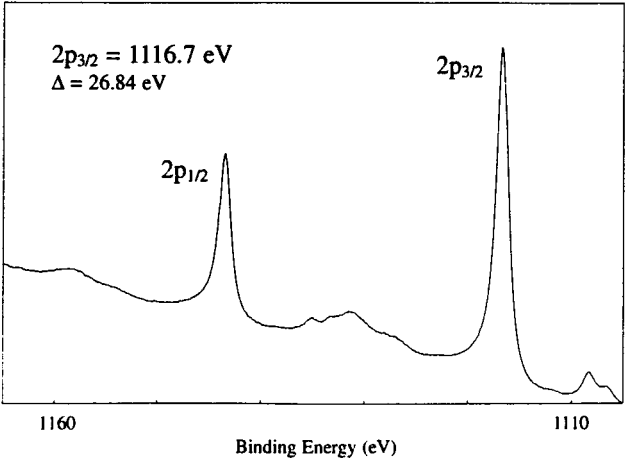


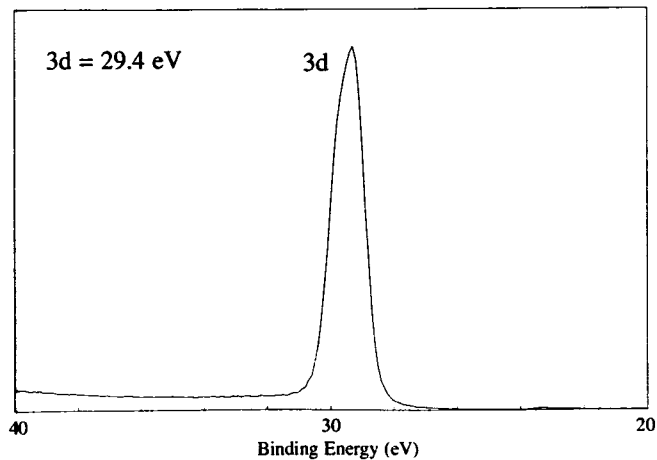
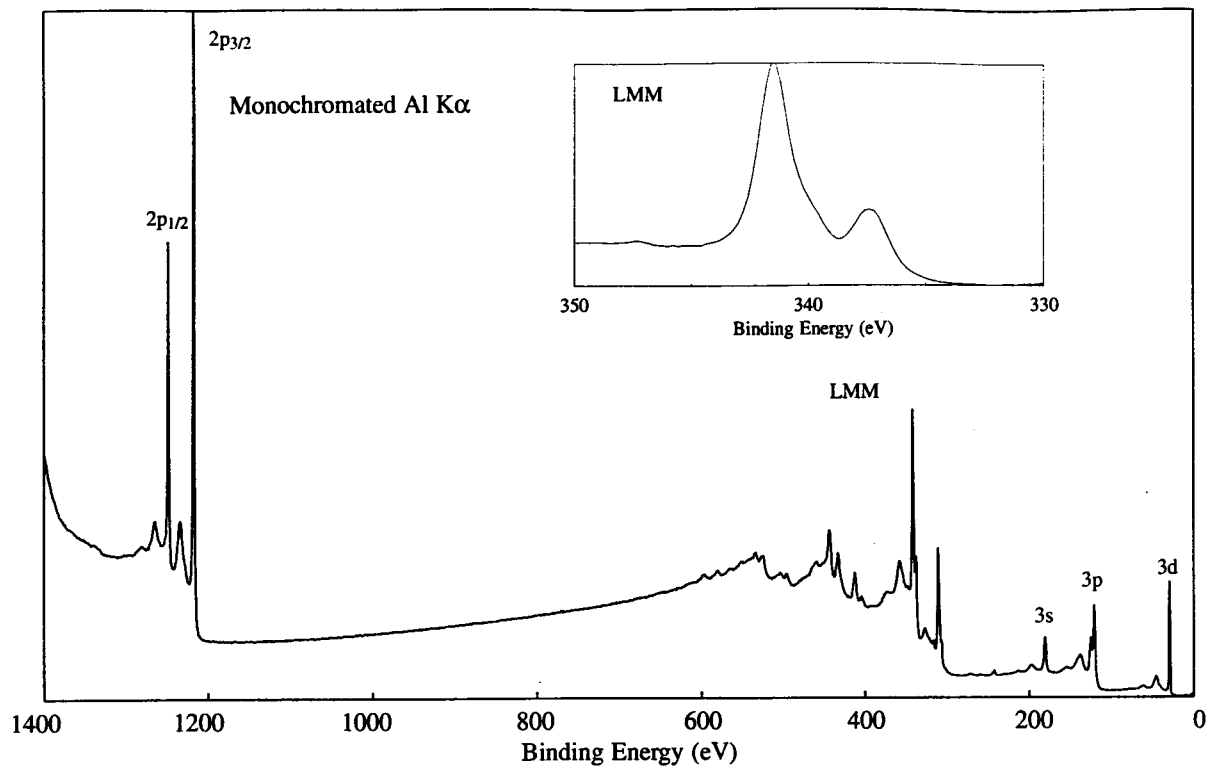
Line Positions (eV)						
Photoelectron Lines						
2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d
1301	1144	1117	160	107	104	19
Auger Lines						
L ₃ M ₂₃ M ₂₃		L ₂ M ₂₃ M ₂₃		L ₃ M ₂₃ M ₄₅ (¹ P)		
597		589		514 (Al)		
364		356		281 (Mg)		
L ₃ M ₂₃ M ₄₅ (³ P)		L ₂ M ₂₃ M ₄₅ (¹ P)		L ₃ M ₄₅ M ₄₅		L ₂ M ₄₅ M ₄₅
504		487		419		392 (Al)
271		254		186		159 (Mg)



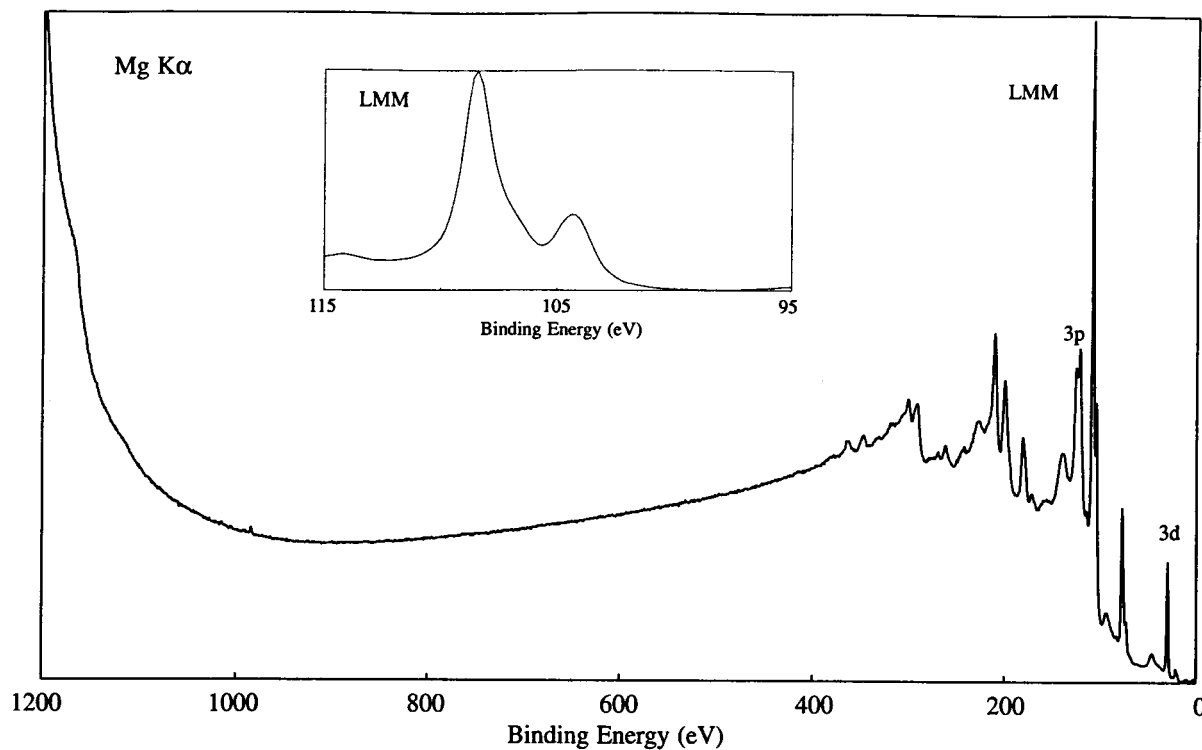
2p _{3/2} Binding Energy (eV)				
Compound Type	1116	1117	1118	
Ga				
GaP				
Ga ₂ O ₃				

3d Binding Energy (eV)				
Compound Type	18	19	20	21
Ga				
GaAs				
GaP				
AlGaAs				
Ga ₂ O ₃				

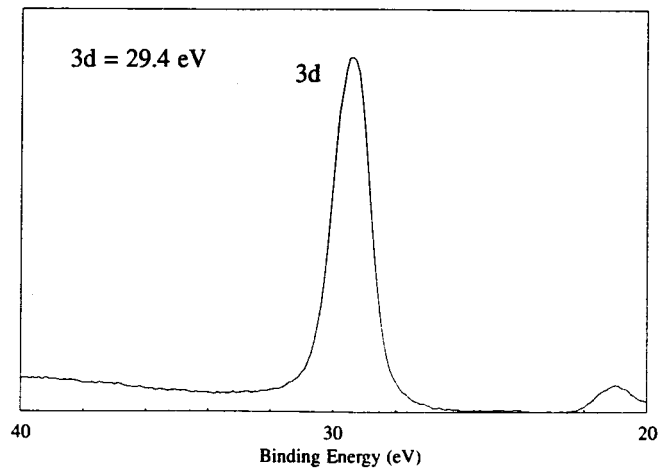


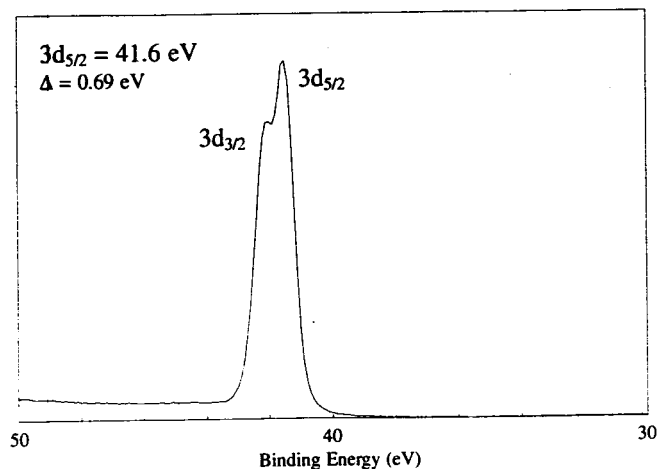
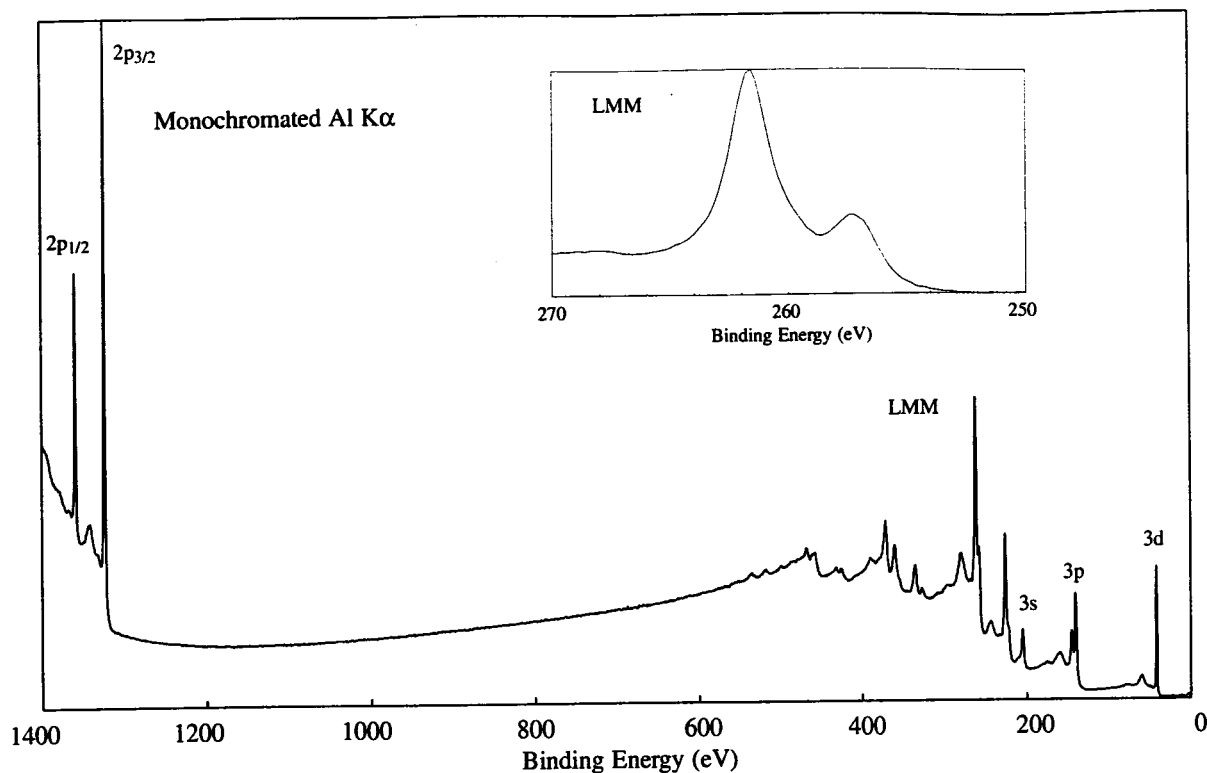


Line Positions (eV)					
Photoelectron Lines					
$2p_{1/2}$	$2p_{3/2}$	$3s$	$3p_{1/2}$	$3p_{3/2}$	$3d$
1248	1217	181	126	122	29
Auger Lines					
$L_3M_{23}M_{23}$		$L_2M_{23}M_{23}$	$L_3M_{23}M_{45} (^1P)$		
534		525	444	(Al)	
301		292	211	(Mg)	
$L_3M_{23}M_{45} (^3P)$		$L_2M_{23}M_{45} (^1P)$	$L_3M_{45}M_{45}$	$L_2M_{45}M_{45}$	
433		412	342	310	(Al)
200		179	109	77	(Mg)

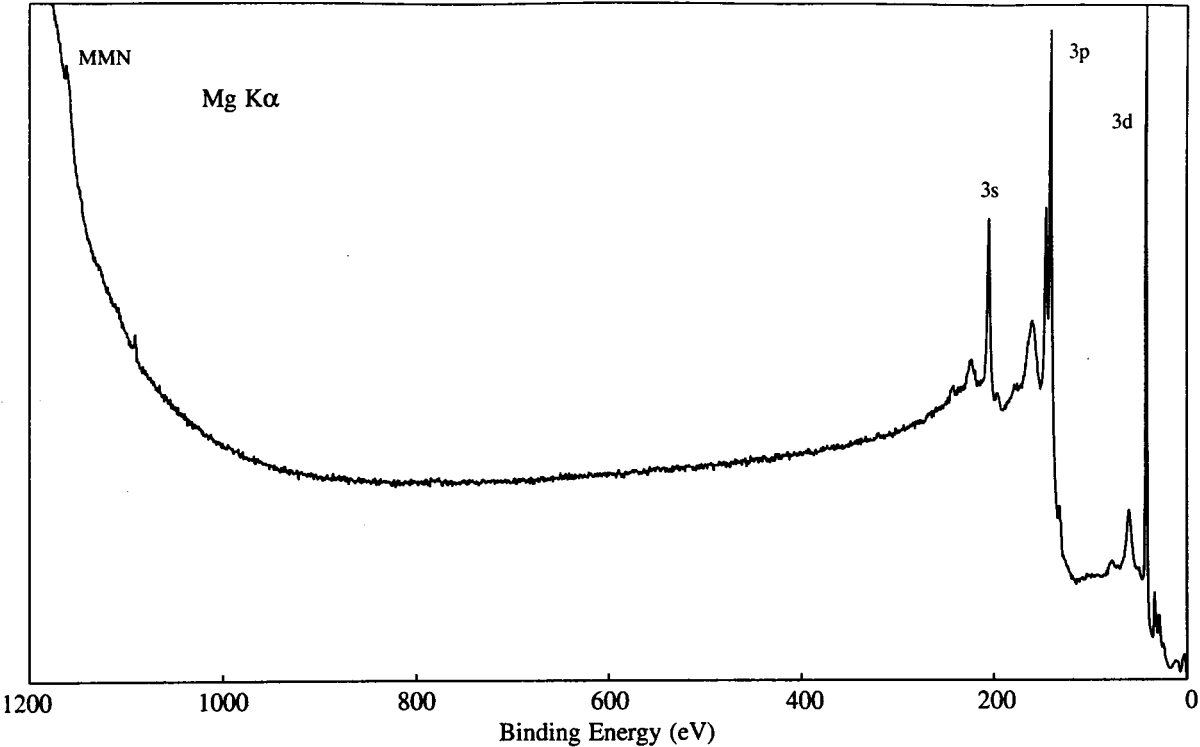


Compound Type	3d Binding Energy (eV)				
	29	30	31	32	33
Ge	■				
GeAs ₂	■	■			
GeTe ₃ As ₂	■	■			
GeS ₂ TeAs ₂	■	■			
GeS ₃ As	■	■			
GeTe ₂	■	■			
GeTe	■	■			
GeSe ₂		■	■		
GeSe		■	■		
Sulfides	■	■	■		
GeO ₂				■	

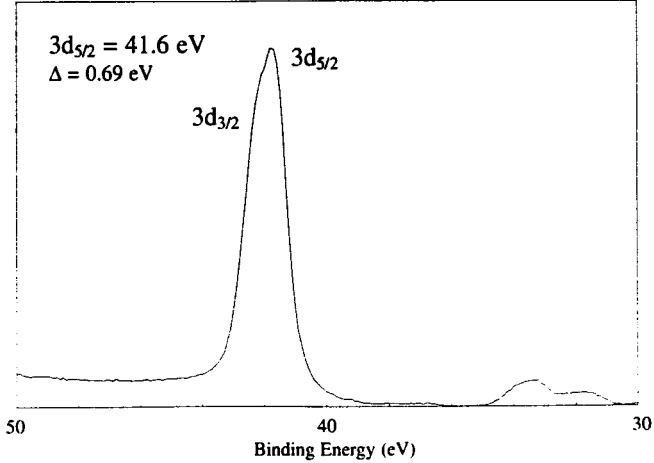


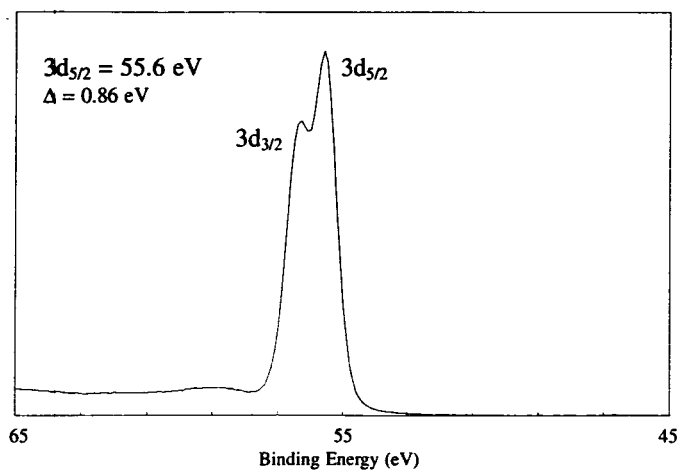
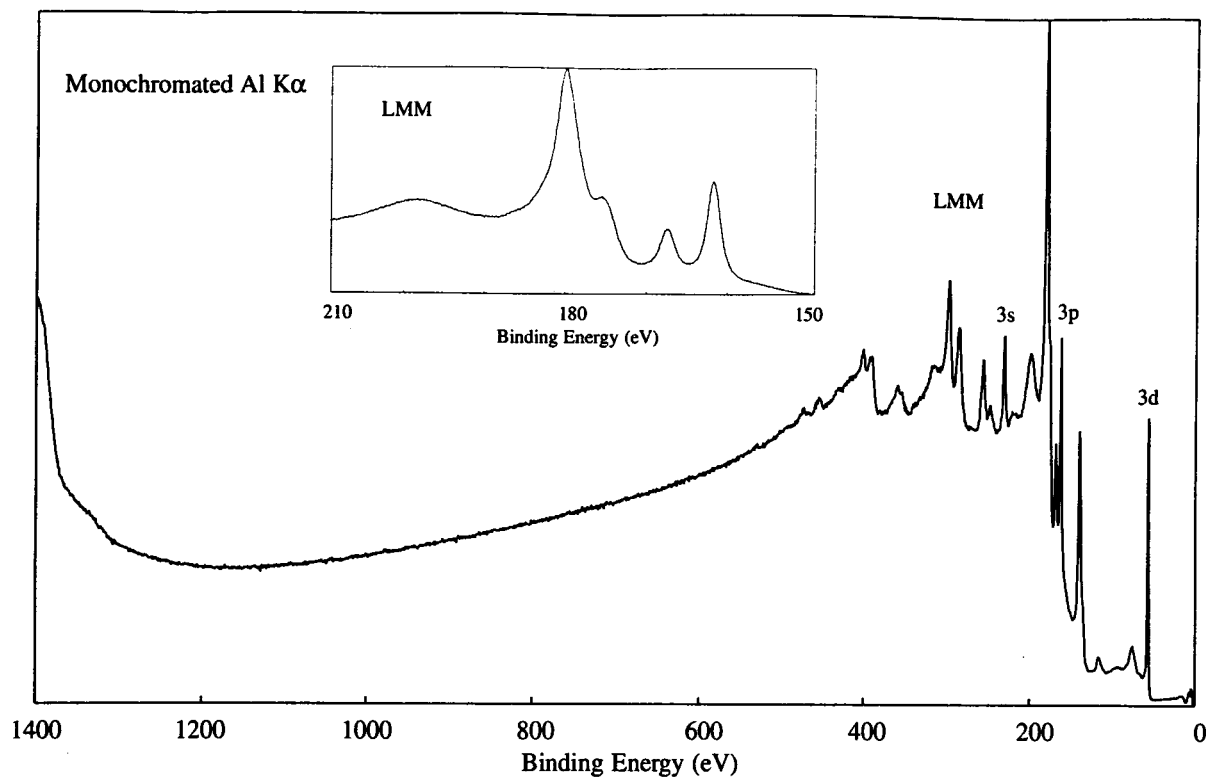


Line Positions (eV)						
Photoelectron Lines						
2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1359	1324	205	146	141	43	42
Auger Lines						
L ₃ M ₂₃ M ₄₅ (¹ P)		L ₃ M ₂₃ M ₄₅ (³ P)				
371		360 (Al)				
L ₂ M ₂₃ M ₄₅ (¹ P)		L ₃ M ₄₅ M ₄₅	L ₂ M ₄₅ M ₄₅		(Al)	
336		262	226			

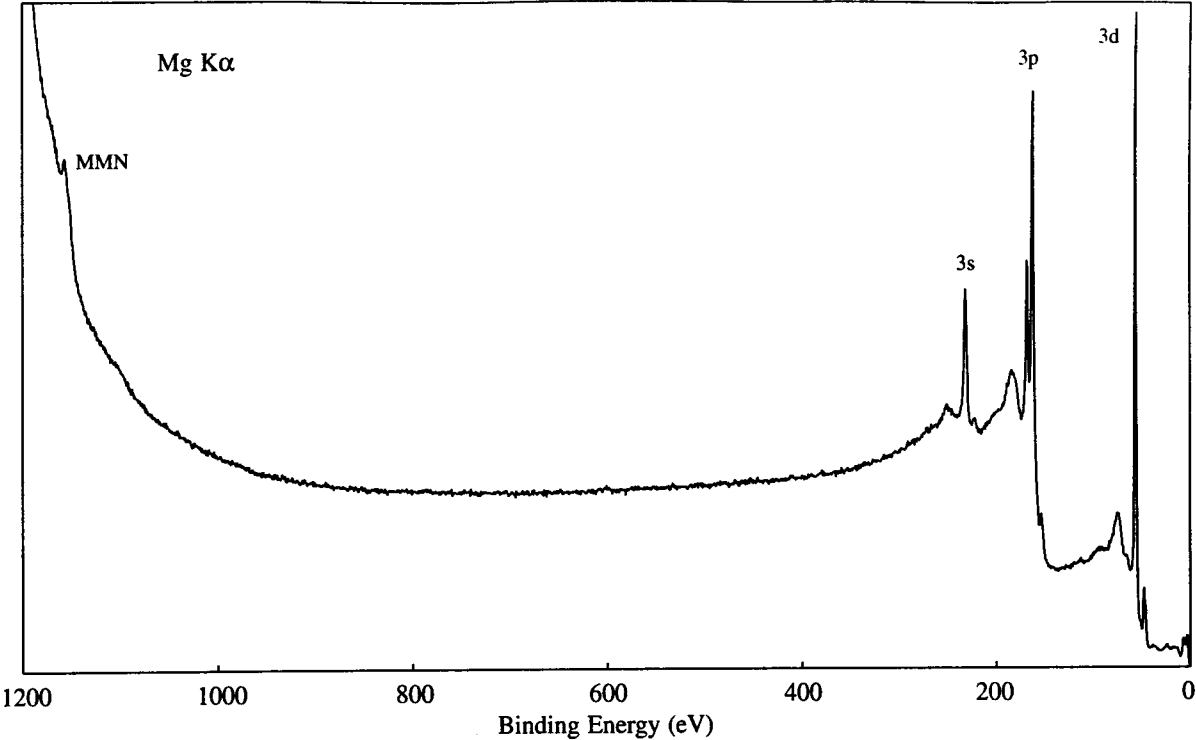


3d _{5/2} Binding Energy (eV)							
Compound Type	40	41	42	43	44	45	46
As							
AlAs							
AlGaAs							
GaAs							
InAs							
Sulfides							
AsI ₃							
AsBr ₃							
As ₂ O ₃							
As ₂ O ₅							

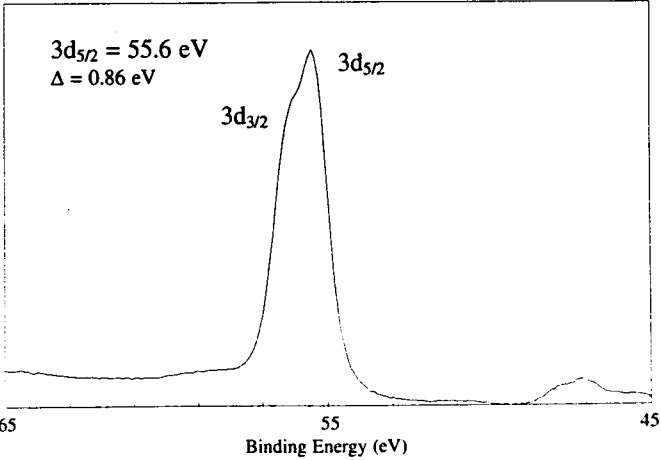


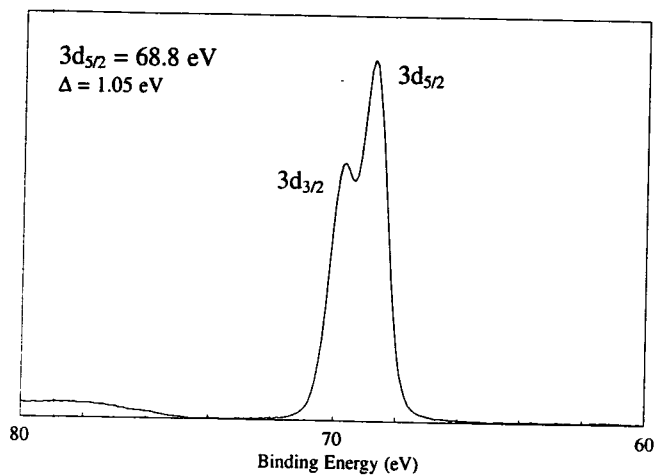
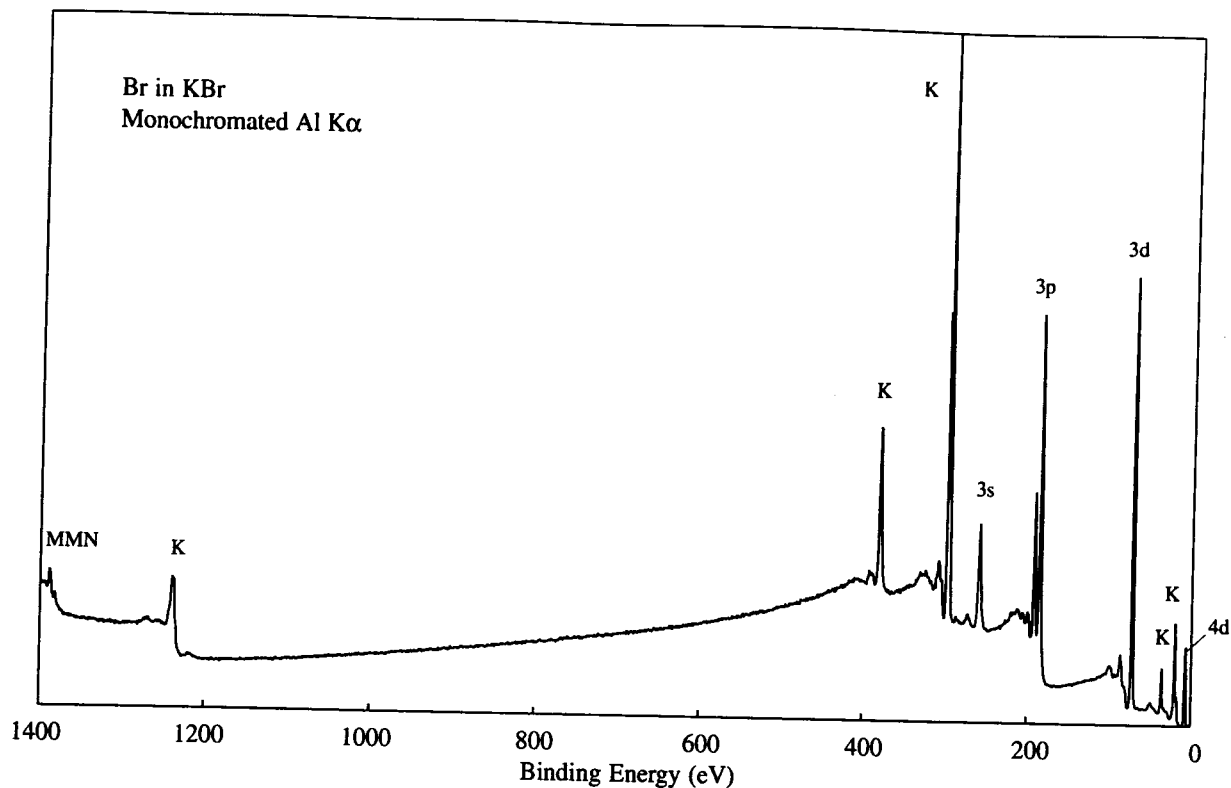


Line Positions (eV)				
Photoelectron Lines				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
232	169	163	57	56
Auger Lines				
L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₂₃ M ₄₅ (³ P)			
299	287	(Al)		
L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅	L ₂ M ₄₅ M ₄₅	(Al)	
257	181	140		



3d _{5/2} Binding Energy (eV)							
Compound Type	54	55	56	57	58	59	60
Se							
As ₂ Se ₃							
Ga ₂ Se ₃							
GeSe							
GeSe ₂							
Selenides							
SeO ₂							
H ₂ SeO ₃							
(BrC ₆ H ₄) ₂ Se ₂							
(C ₁₄ H ₂₉ Se) ₂							
(C ₄ H ₈ COOH) ₂ SeO							





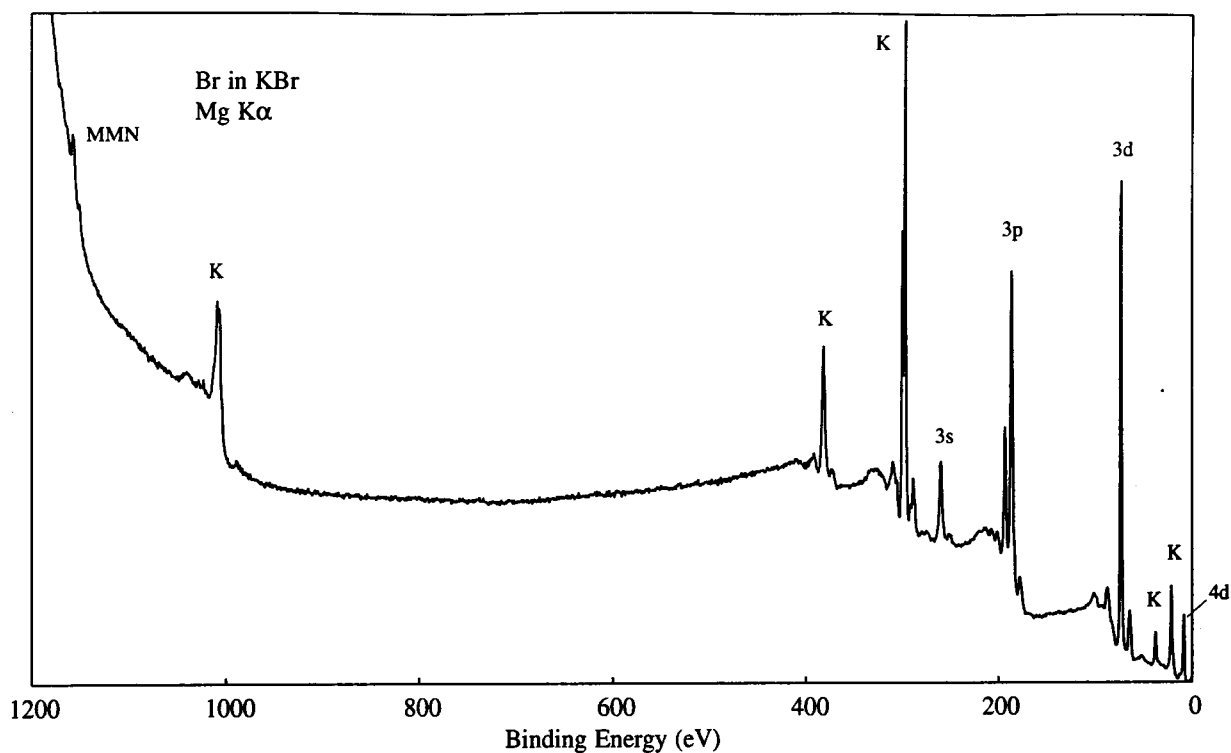
Line Positions (eV)

Photoelectron Lines

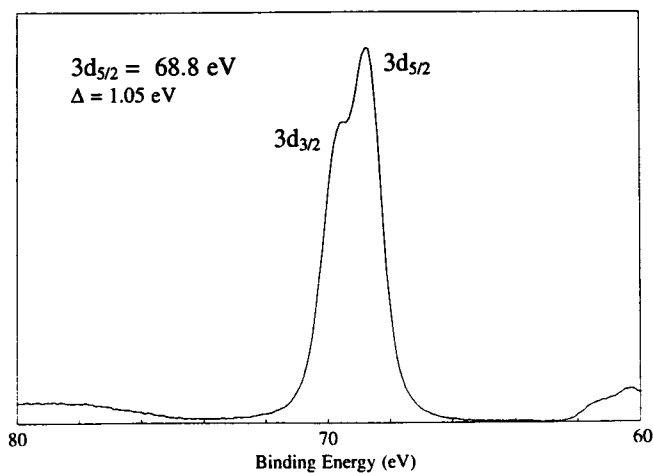
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4d
256	189	182	70	69	15	5

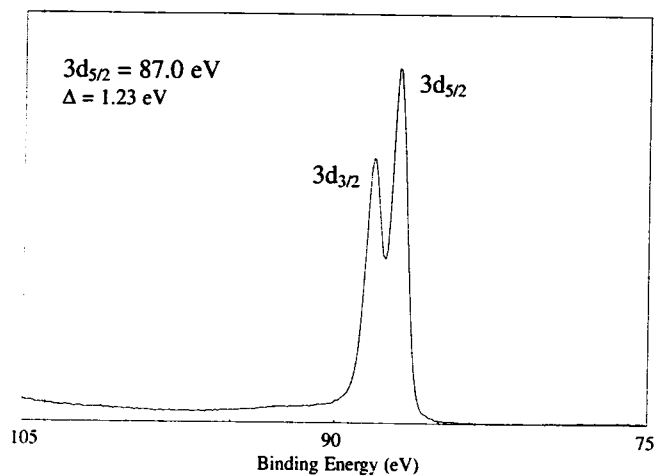
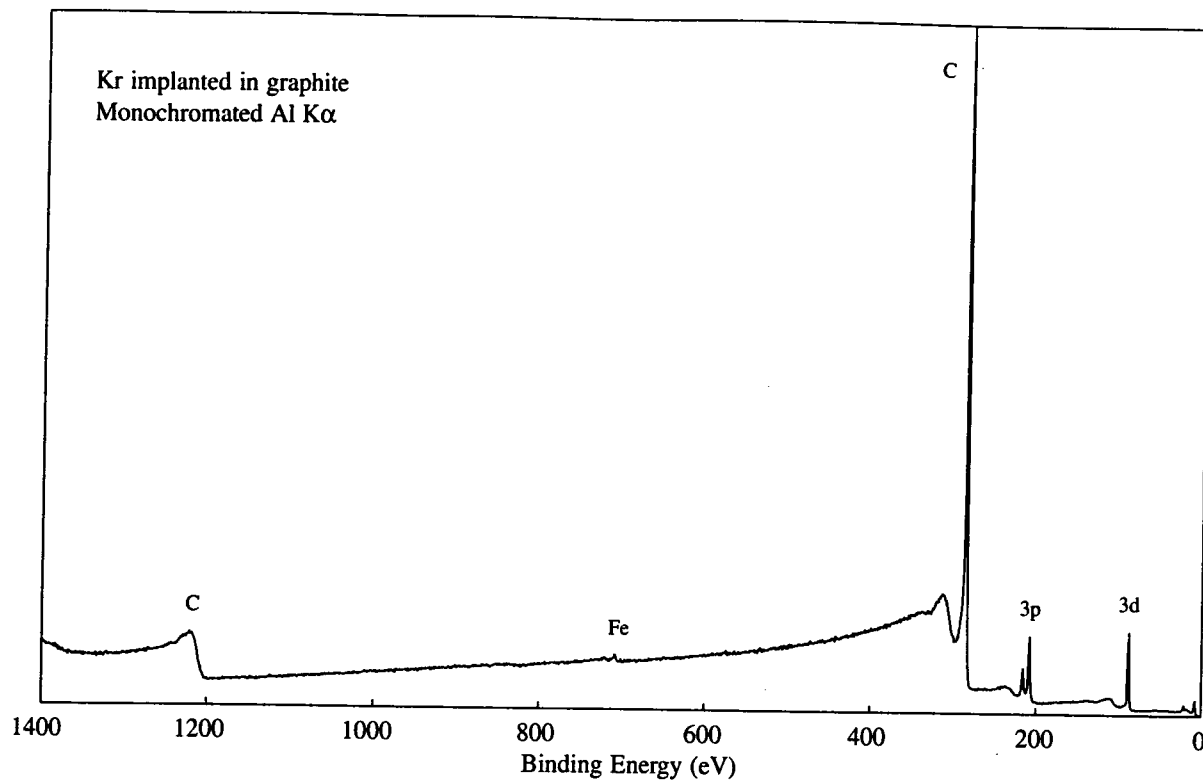
Auger Lines

M ₂₃ M ₄₅ N ₂₃		
1386	(Al)	
1153	(Mg)	



Compound Type	3d _{5/2} Binding Energy (eV)		
	68	69	70
CsBr	68.5		
RbBr	68.8		
KBr	69.1		
NaBr	69.4		
LiBr	69.7		
CuBr ₂	69.8		
PbBr ₂	69.9		
Ni(NH ₃) ₆ Br ₂	69.9		
Pt(NH ₃) ₄ Br ₂	70.0		
K ₂ PtBr ₄	70.1		
K ₂ PtBr ₆	70.2		



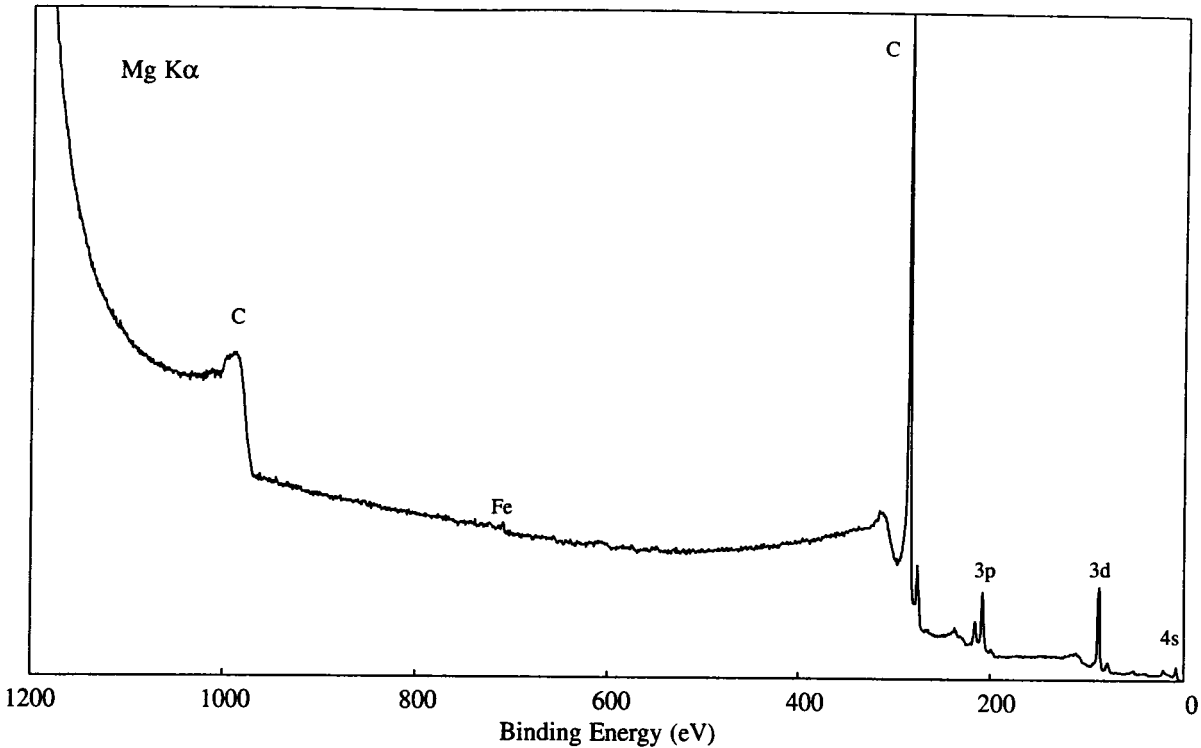


Line Positions (eV)

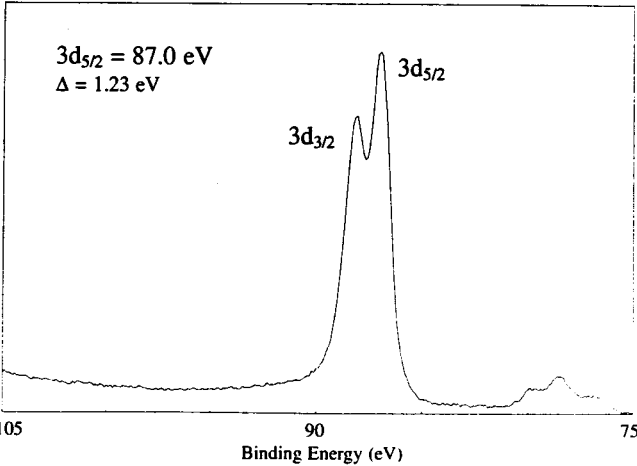
Photoelectron Lines

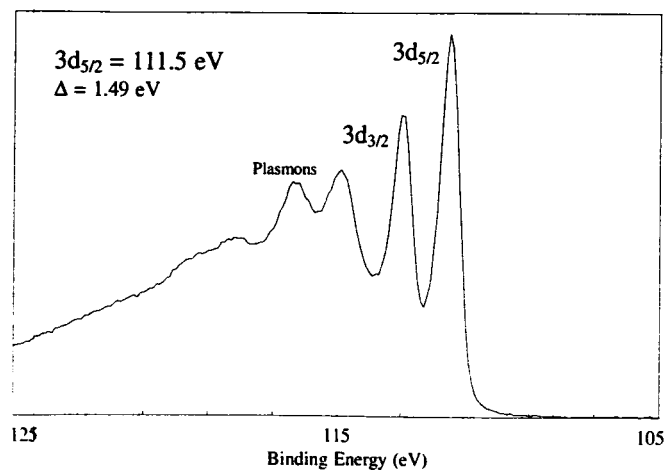
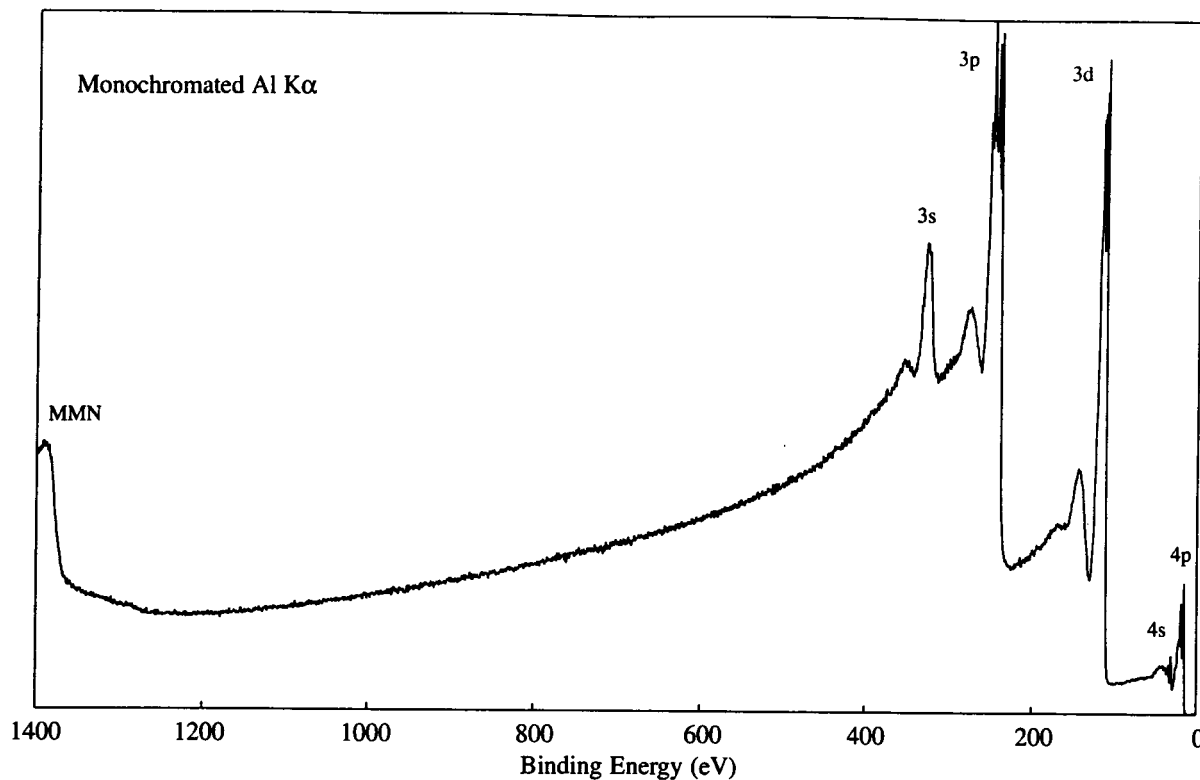
3s*	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
287	216	208	88	87	21	8

*Estimate



3d _{5/2} Binding Energy (eV)			
Compound Type	84	86	88
Kr in graphite			





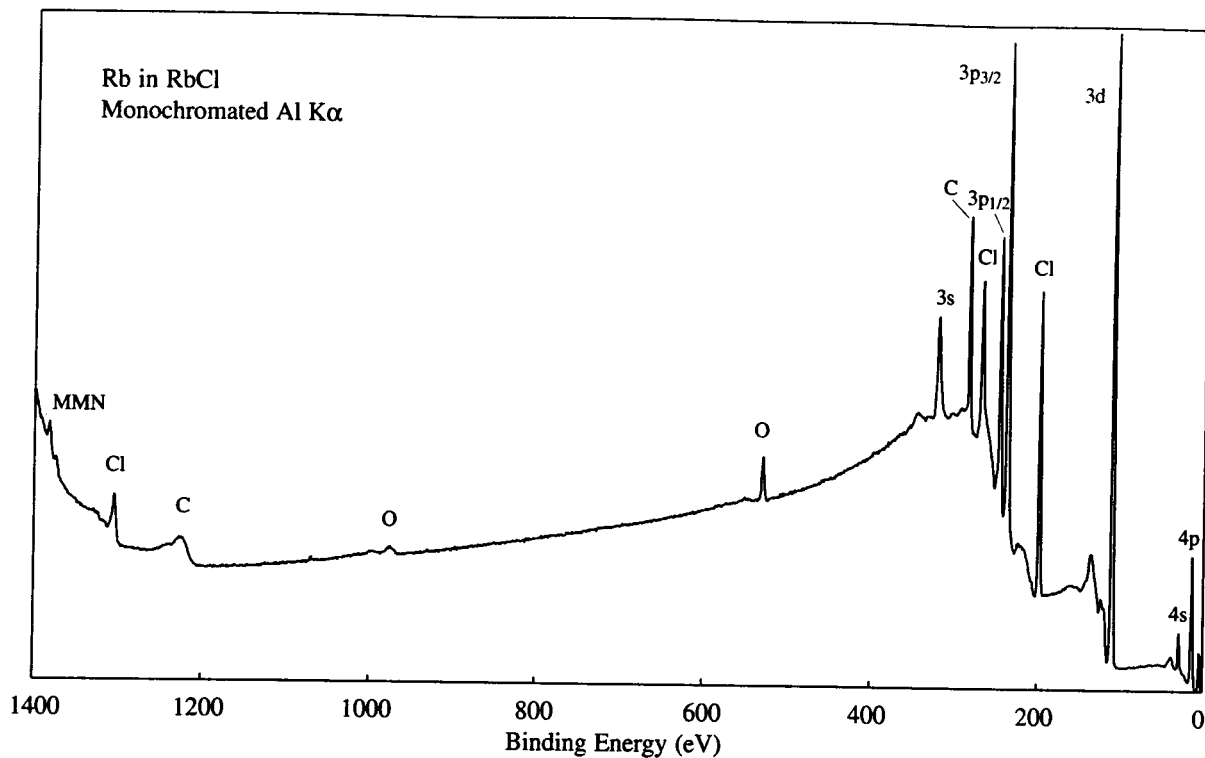
Line Positions (eV)

Photoelectron Lines

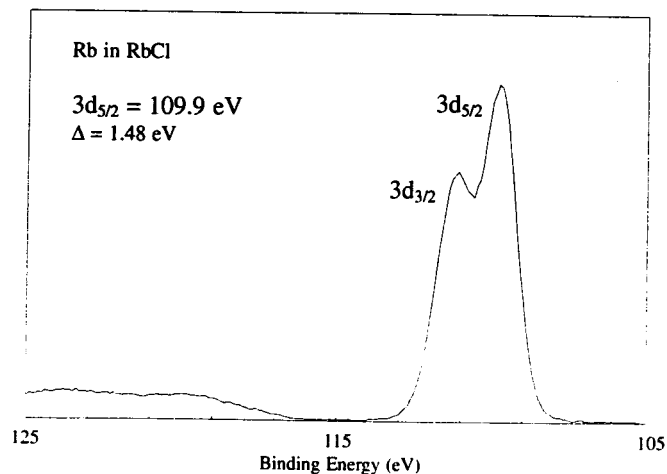
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
325	249	240	113	111	31	16

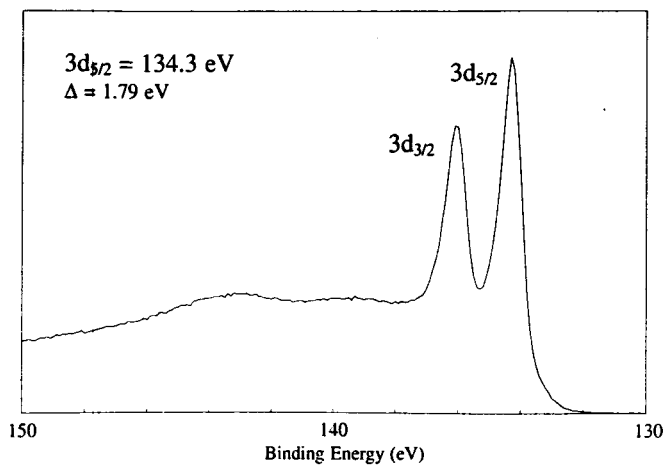
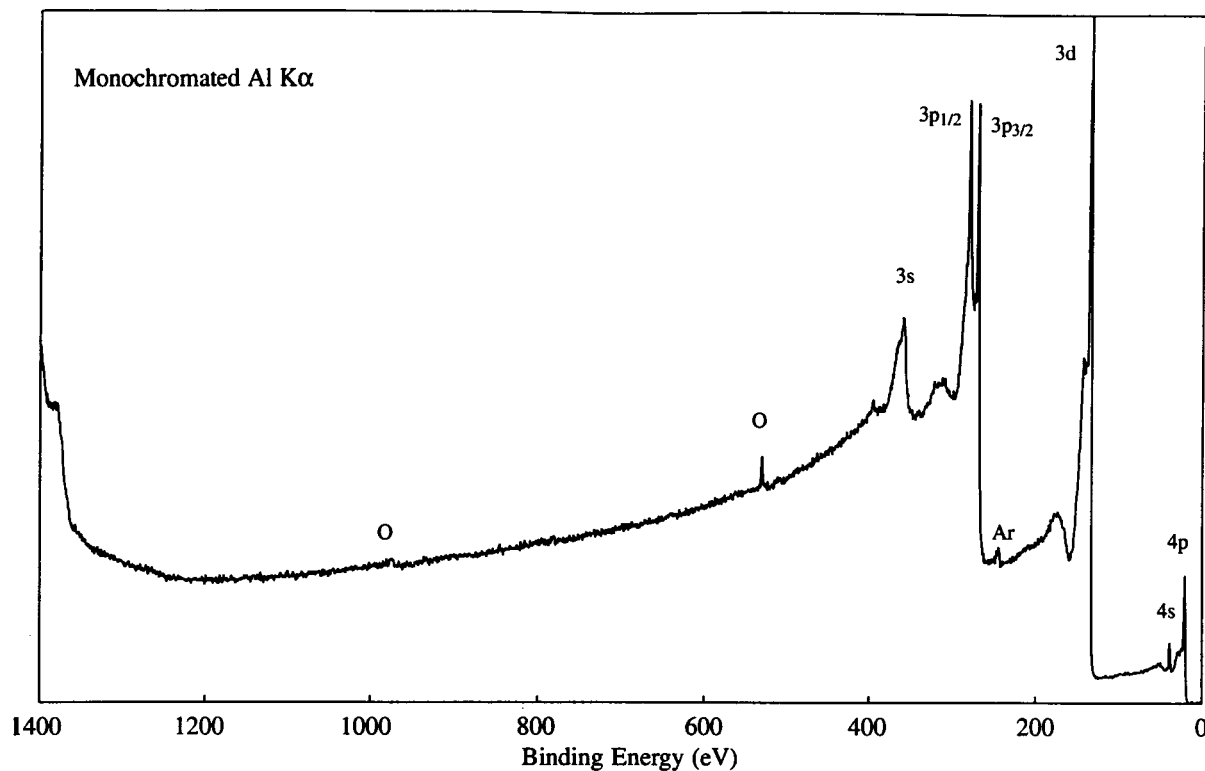
Auger Lines

M₂₃M₄₅N₂₃
1385
1152



Compound Type	3d _{5/2} Binding Energy		
	109	110	111
Rb			
RbN ₃			
RbI			
RbBr			
RbCl			
RbF			
Rb ₃ PO ₄			
Rb ₄ P ₂ O ₇			
RbClO ₄			

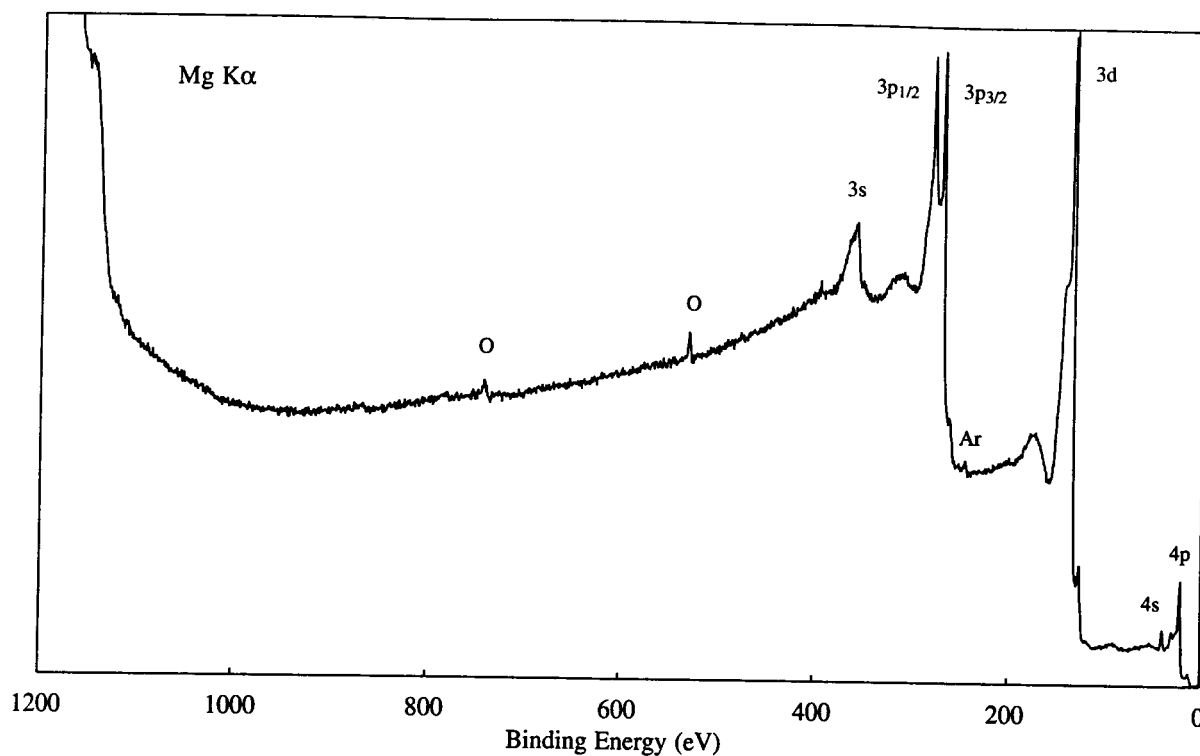




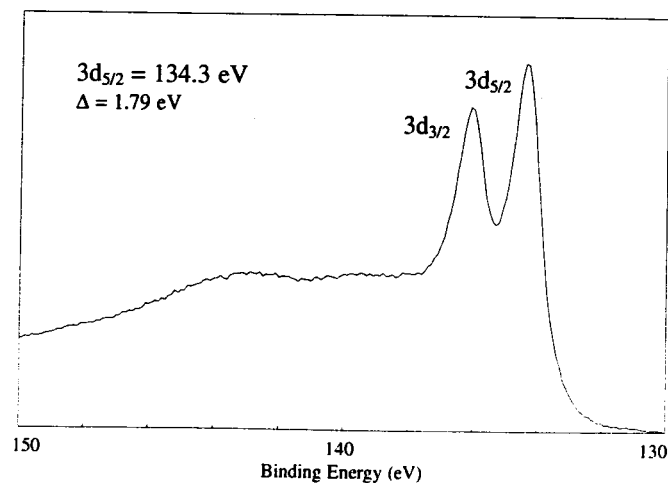
Line Positions (eV)

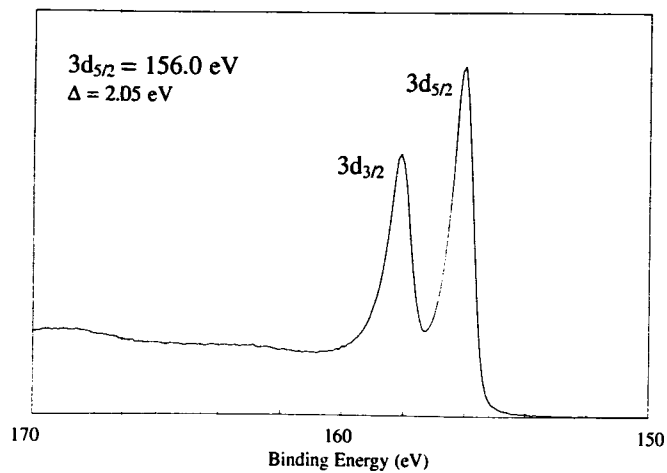
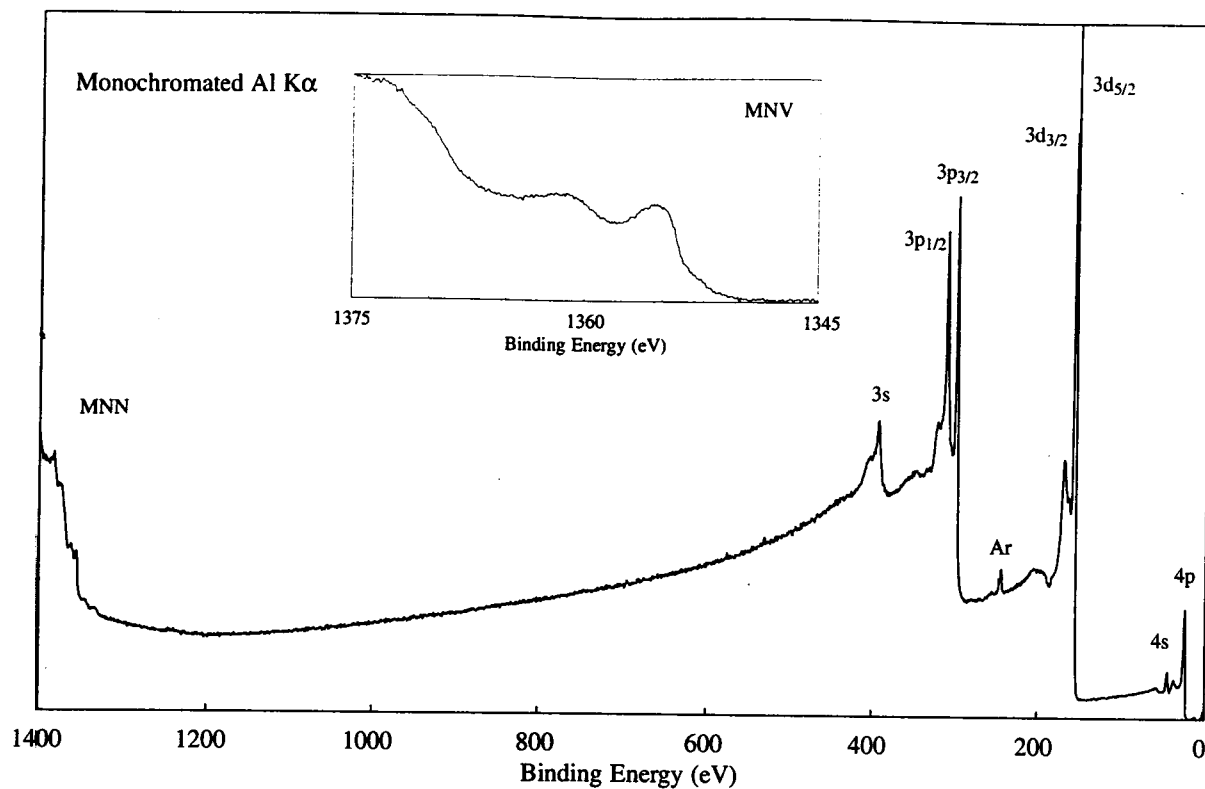
Photoelectron Lines

3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
360	281	270	136	134	39	21



3d _{5/2} Binding Energy (eV)				
Compound Type	133	134	135	136
Sr				
SrO				
SrF ₂				
SrCO ₃				
SrSO ₄				
Sr(NO ₃) ₂				
SrMoO ₄				
SrRh ₂ O ₄				





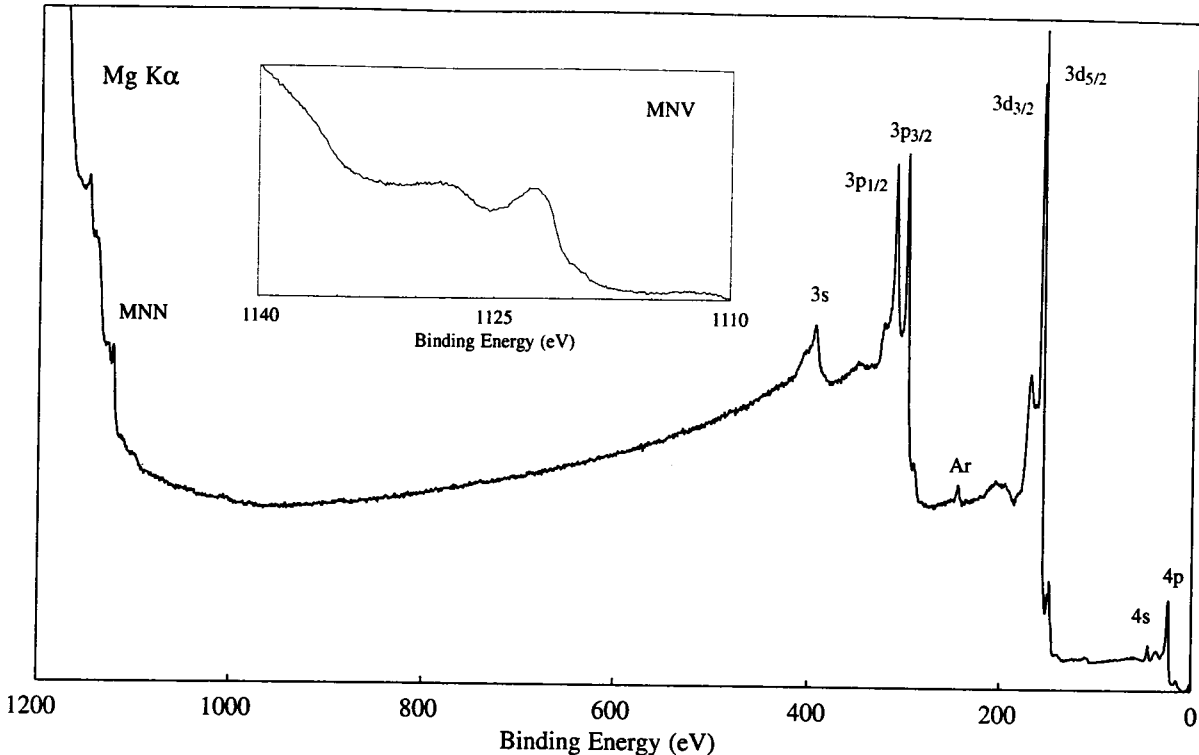
Line Positions (eV)

Photoelectron Lines

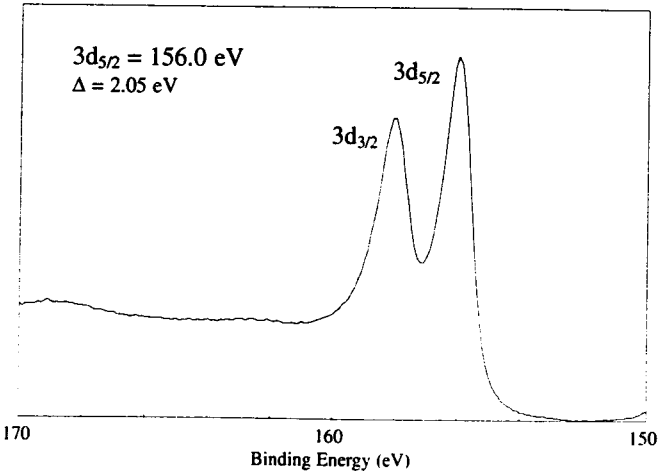
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
394	311	299	158	156	45	24

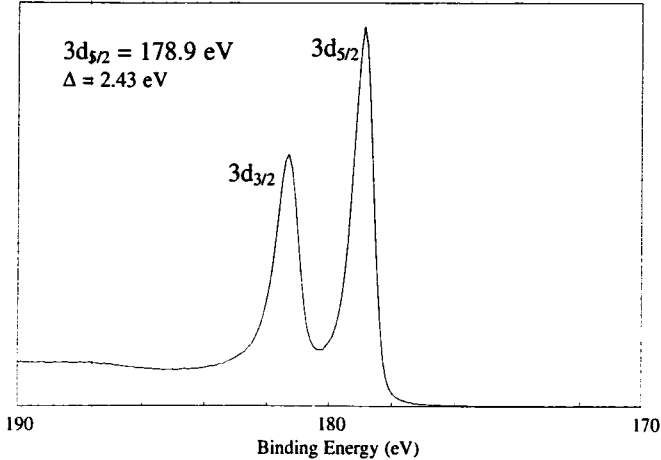
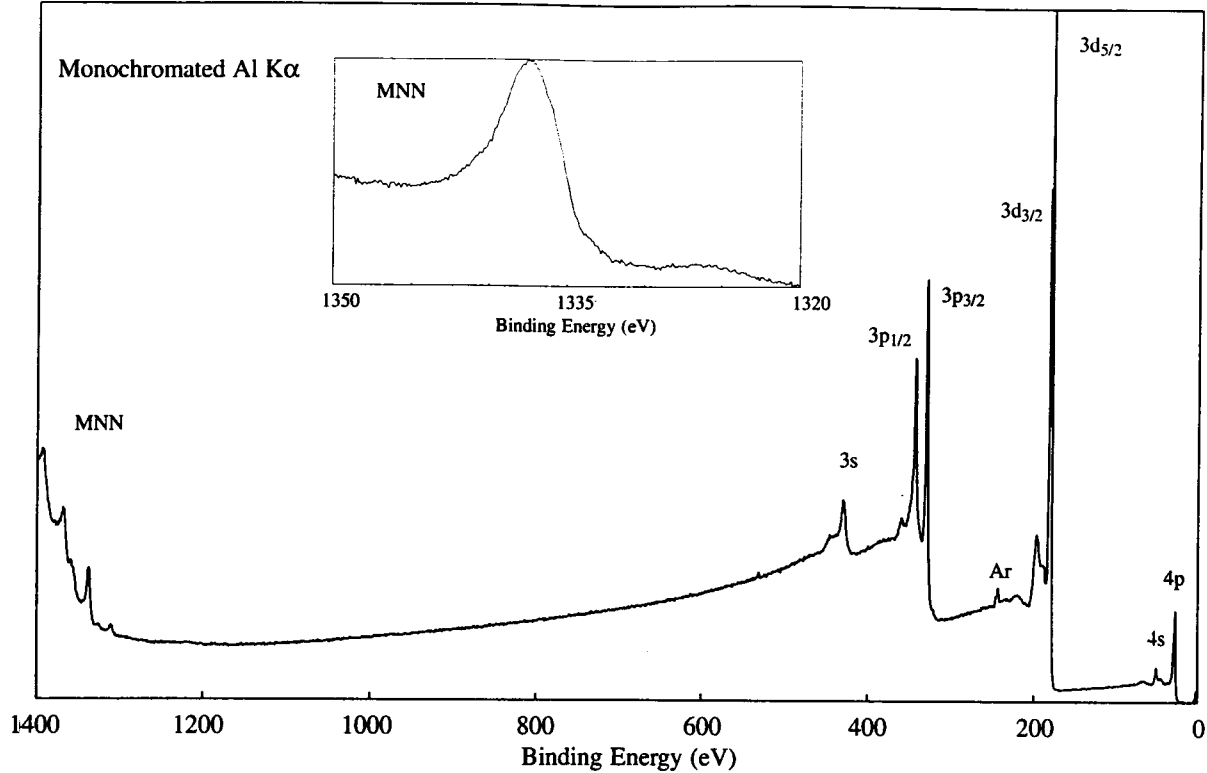
Auger Lines

M ₄₅ N ₂₃ V	
1356	(Al)
1123	(Mg)



3d _{5/2} Binding Energy (eV)			
Compound Type	155	156	157
Y			
Y ₂ O ₃			





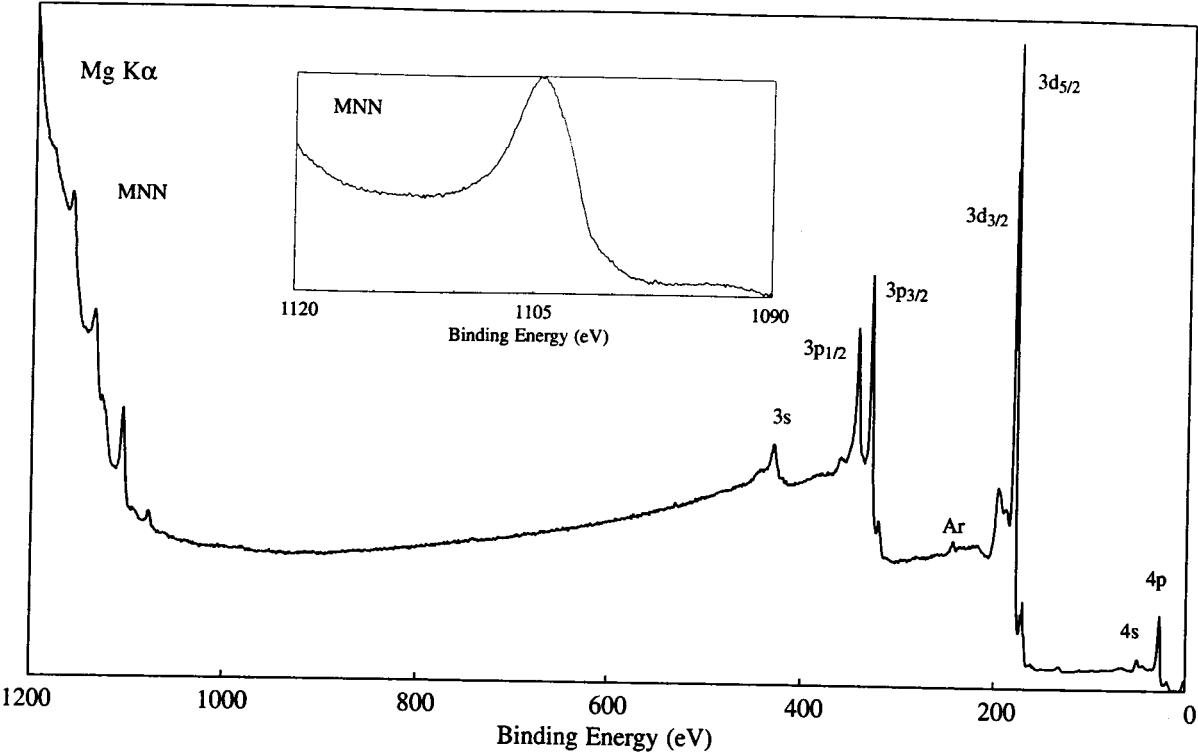
Line Positions (eV)

Photoelectron Lines

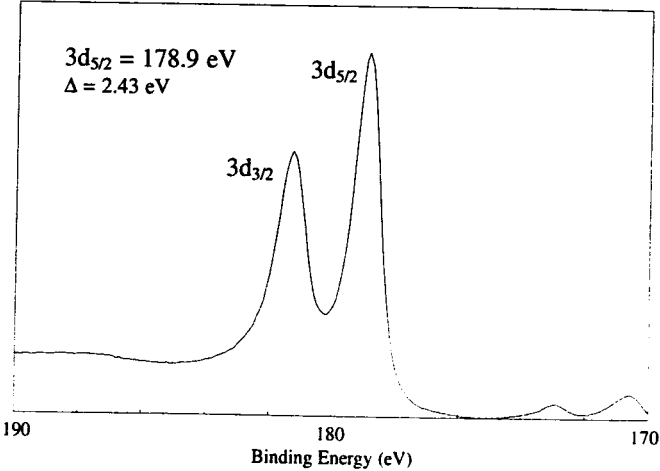
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
430	343	330	181	179	51	28

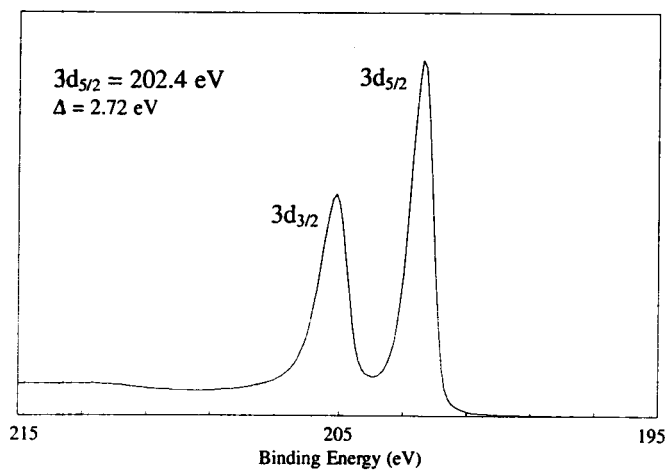
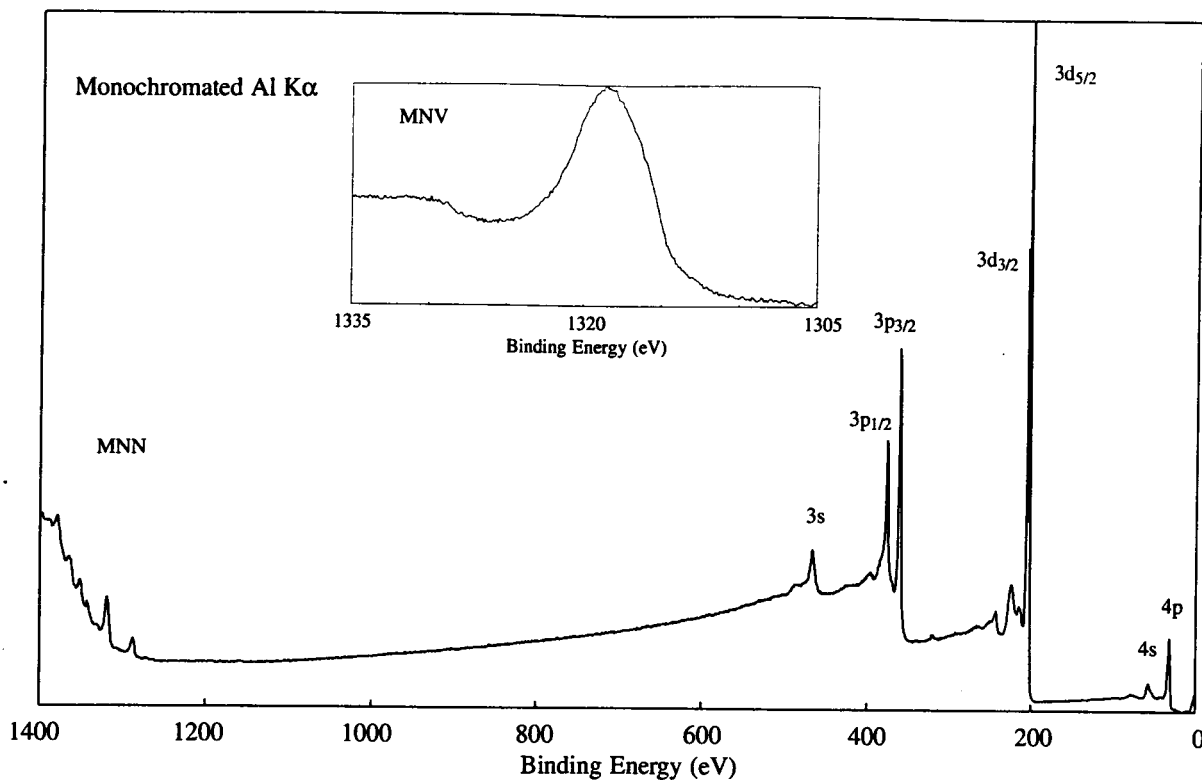
Auger Lines

M ₄₅ N ₂₃ N ₂₃	M ₄₅ N ₂₃ V	M ₄₅ N ₄₅ N ₄₅	
1393	1368	1337	(Al)
1160	1135	1104	(Mg)

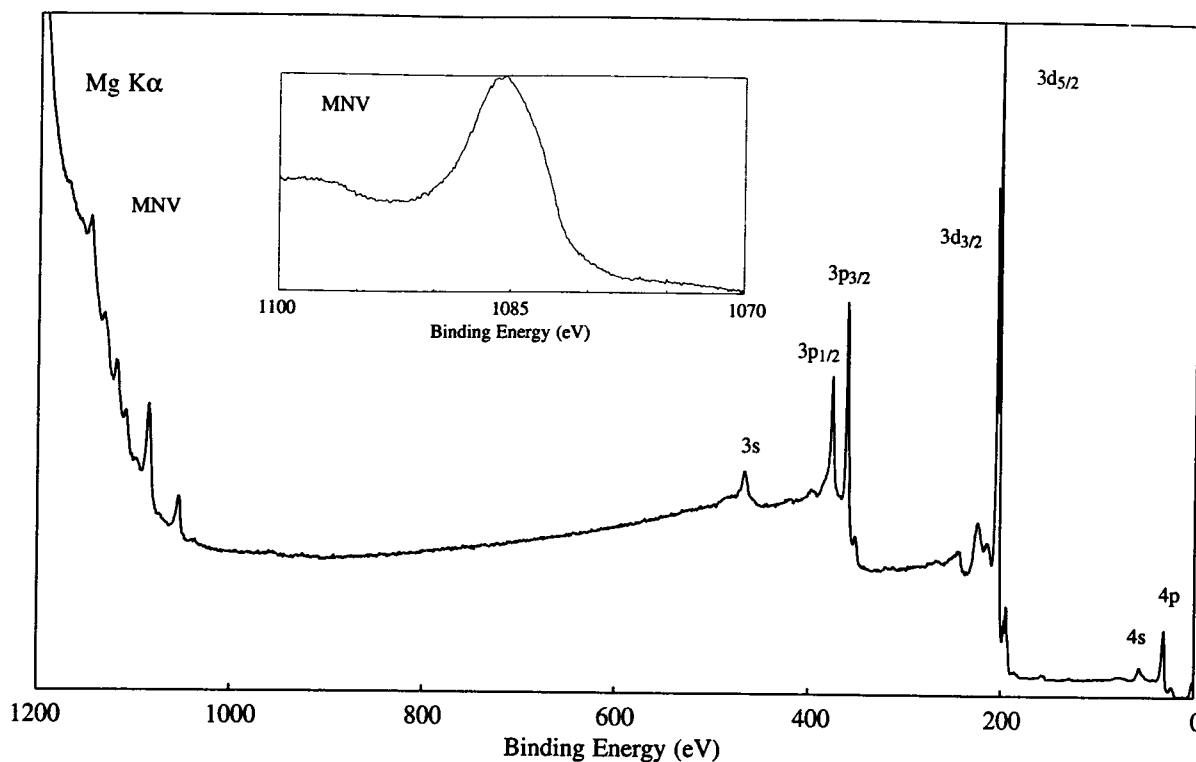


3d _{5/2} Binding Energy (eV)									
Compound Type	178	179	180	181	182	183	184	185	
Zr		■							
ZrO ₂					■				
ZrF ₅								■	
K ₂ ZrF ₆							■		
K ₃ ZrF ₇							■		
KZrF ₅ · H ₂ O								■	

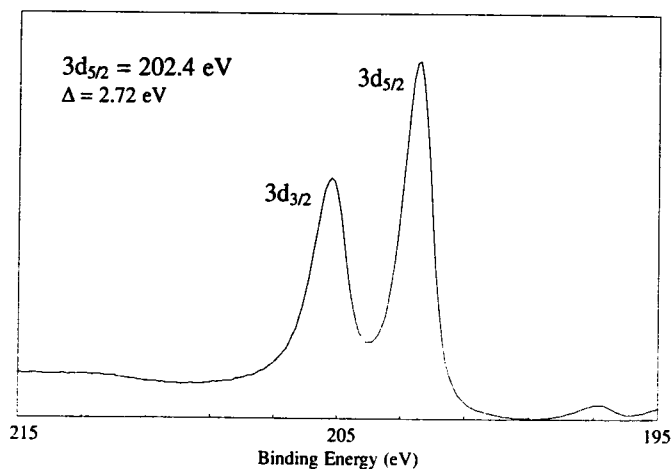


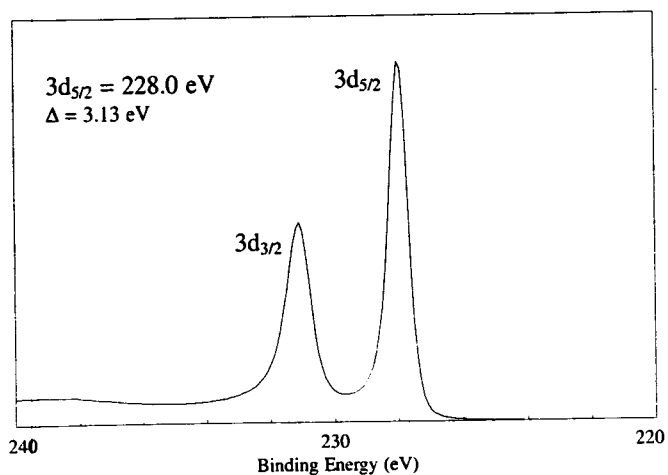
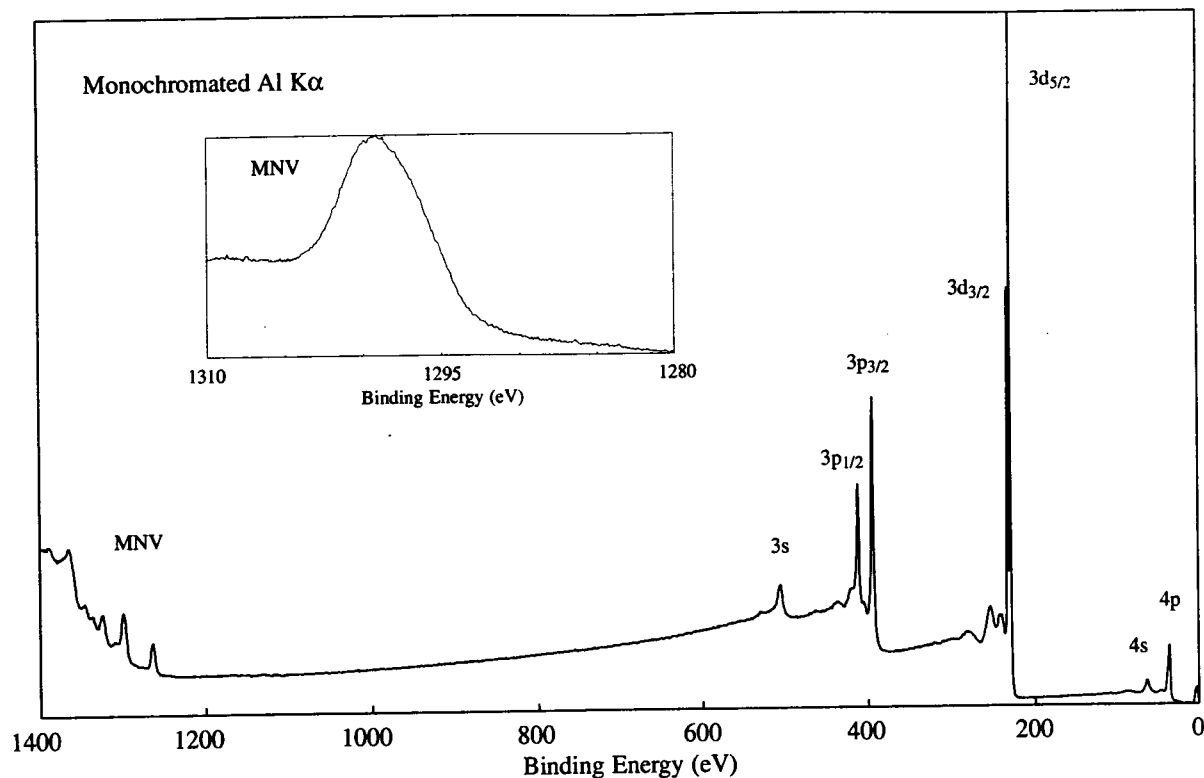


Line Positions (eV)						
Photoelectron Lines						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
467	376	361	205	202	56	31
Auger Lines						
M ₄₅ N ₂₃ V		M ₄₅ VV				
1319		1287 (Al)				
1086		1054 (Mg)				



3d _{5/2} Binding Energy (eV)								
Compound Type	201	202	203	204	205	206	207	208
Nb		■						
NbN				■				
NbO			■	■	■			
Nb ₂ O ₅			■	■	■			
LiNbO ₃								
CaNb ₂ O ₆								
Ca ₂ Nb ₂ O ₇								
Br ₆ (Nb ₆ Cl ₁₂)(Bu ₄ N) ₂					■			
Cl ₂ (Nb ₆ Cl ₁₂)(Pr ₃ P) ₄					■			
Cl ₂ (Nb ₆ Cl ₁₂)(Me ₂ SO) ₄					■			





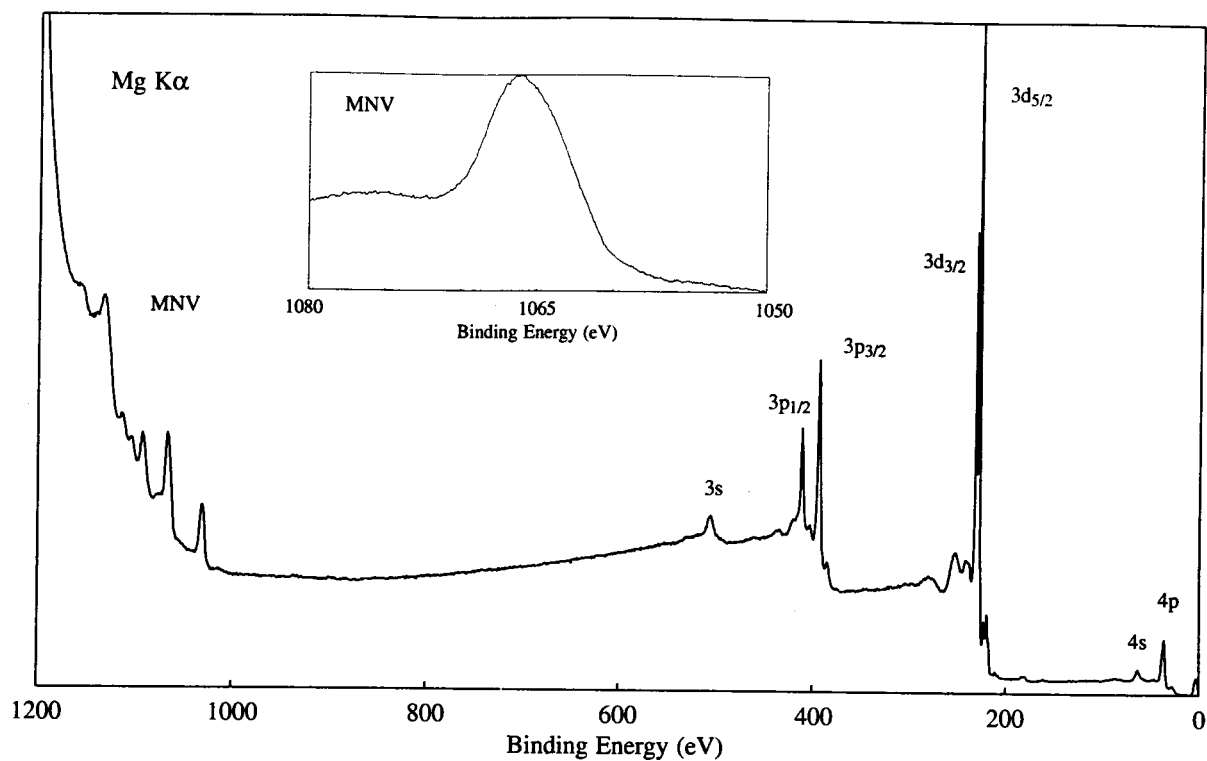
Line Positions (eV)

Photoelectron Lines

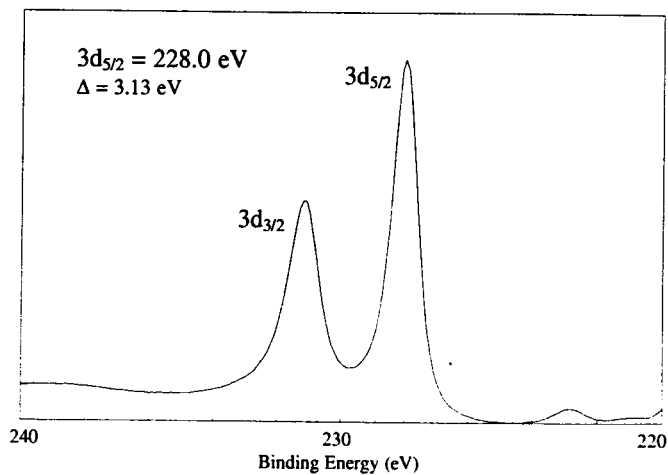
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
506	412	394	231	228	63	36

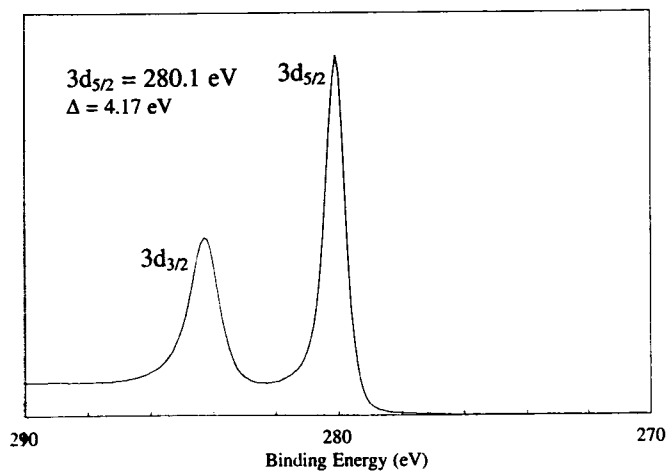
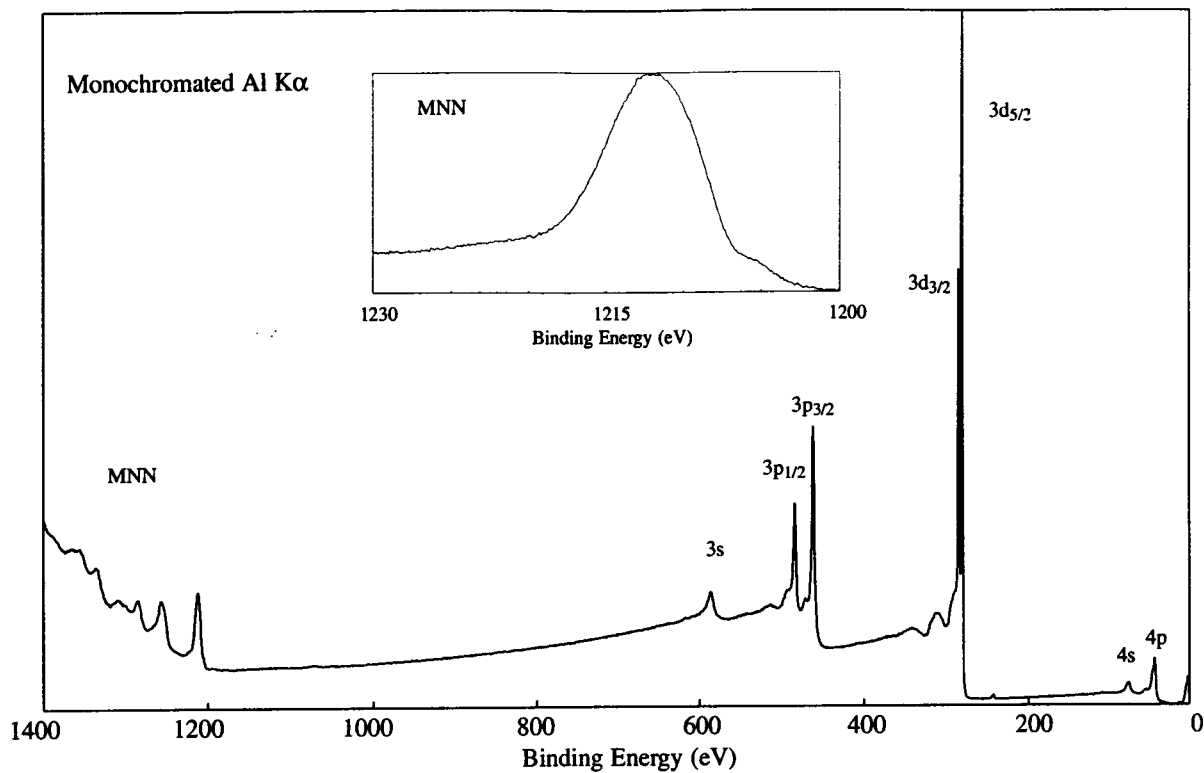
Auger Lines

M ₄₅ N ₂₃ V	M ₄₅ VV	
1299	1264	(Al)
1066	1031	(Mg)



3d _{5/2} Binding Energy (eV)								
Compound Type	226	227	228	229	230	231	232	233
Mo								
Boride								
Mo ₂ C								
MoS ₂								
MoCl ₃								
MoCl ₄								
MoCl ₅								
MoO ₂								
MoO ₃								
(NH ₄) ₄ MoO ₄								
(CO) _k Mo(Ph ₃ P) _y								





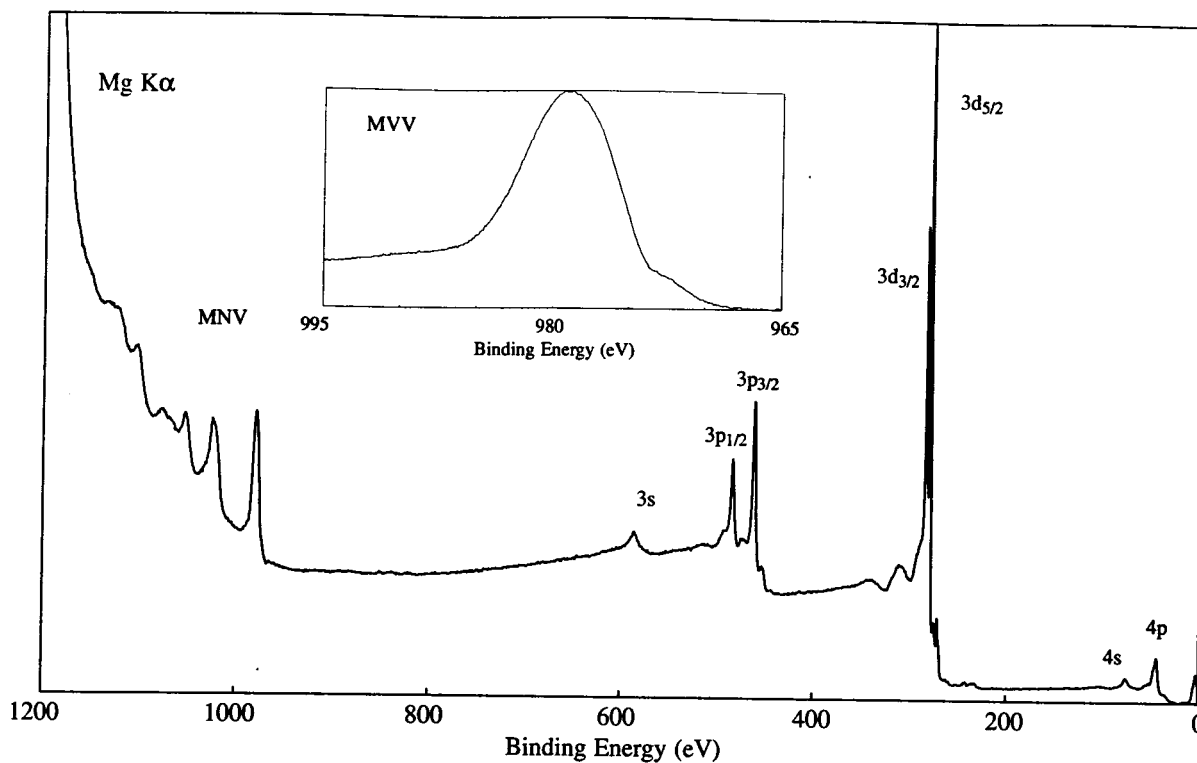
Line Positions (eV)

Photoelectron Lines

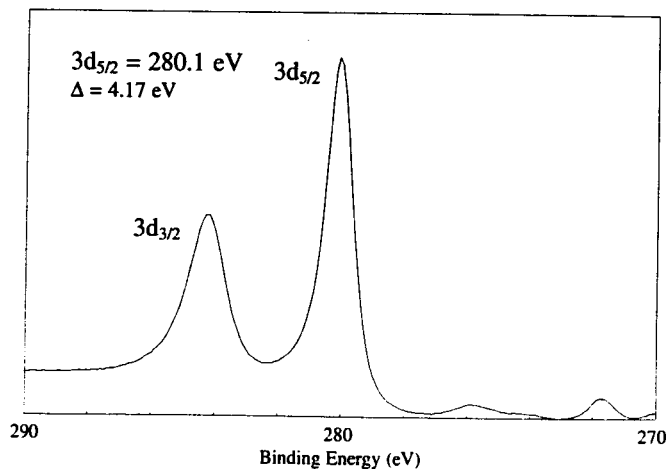
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
586	484	462	284	280	75	43

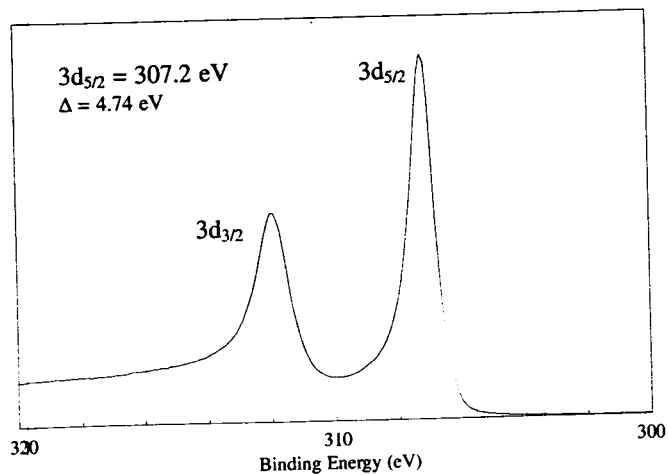
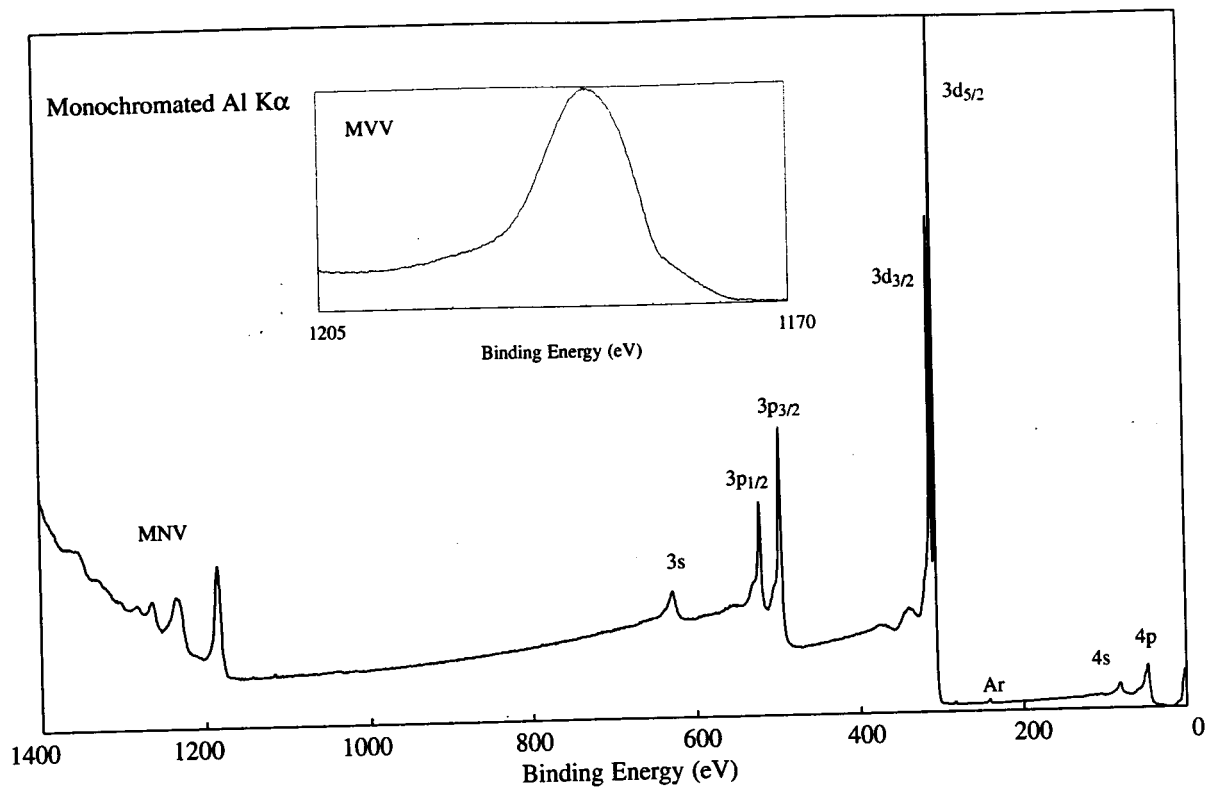
Auger Lines

M ₄₅ N ₂₃ V	M ₄₅ VV	
1256	1212	(Al)
1023	979	(Mg)

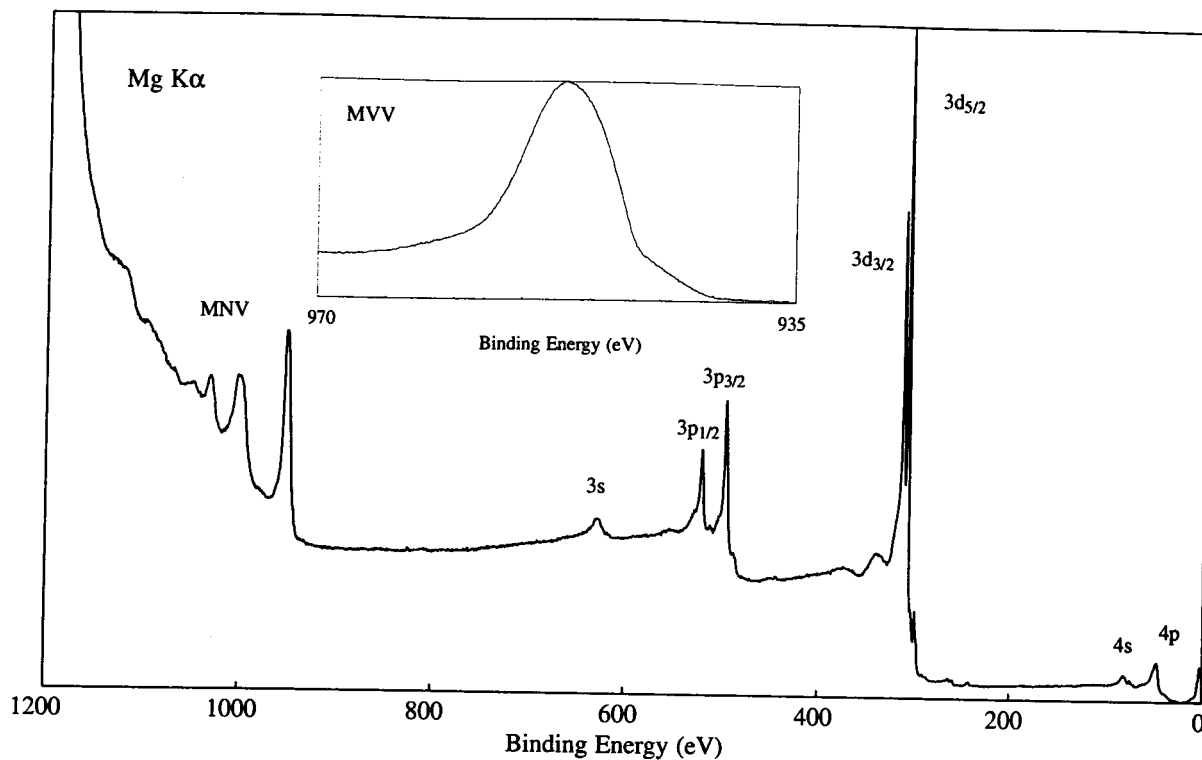


3d _{5/2} Binding Energy (eV)								
Compound Type	276	277	278	279	280	281	282	283
Ru					■			
RuCl ₃							■	
RuO ₂						■		
RuO ₃								■
RuO ₄								■
Ru(NH ₃) ₅ N ₂ I ₂							■	
Ru(NH ₃) ₅ N ₂ Br ₂					■			
Ru(NH ₃) ₅ N ₂ Cl ₂							■	

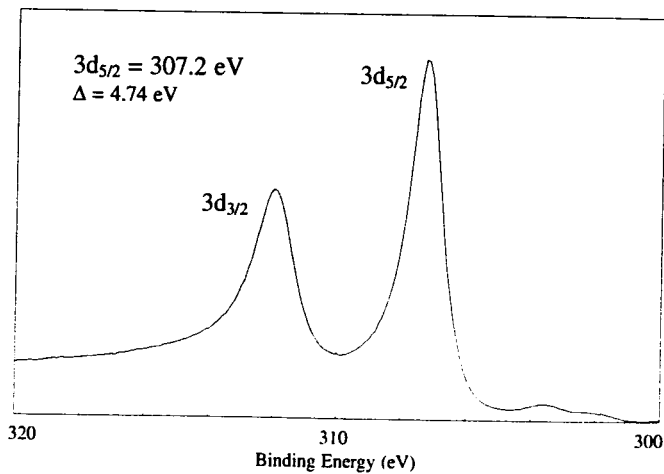


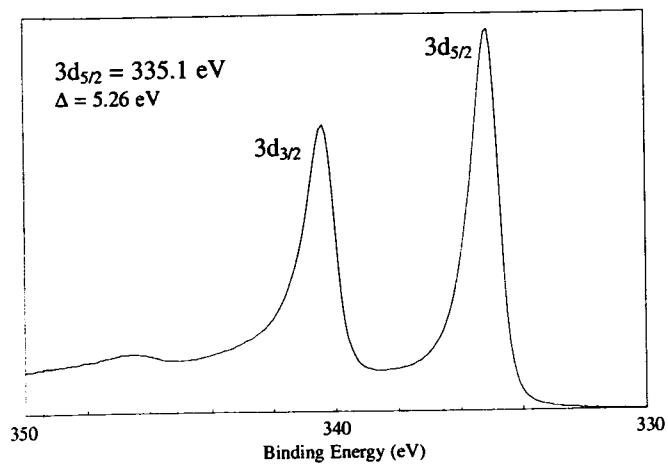
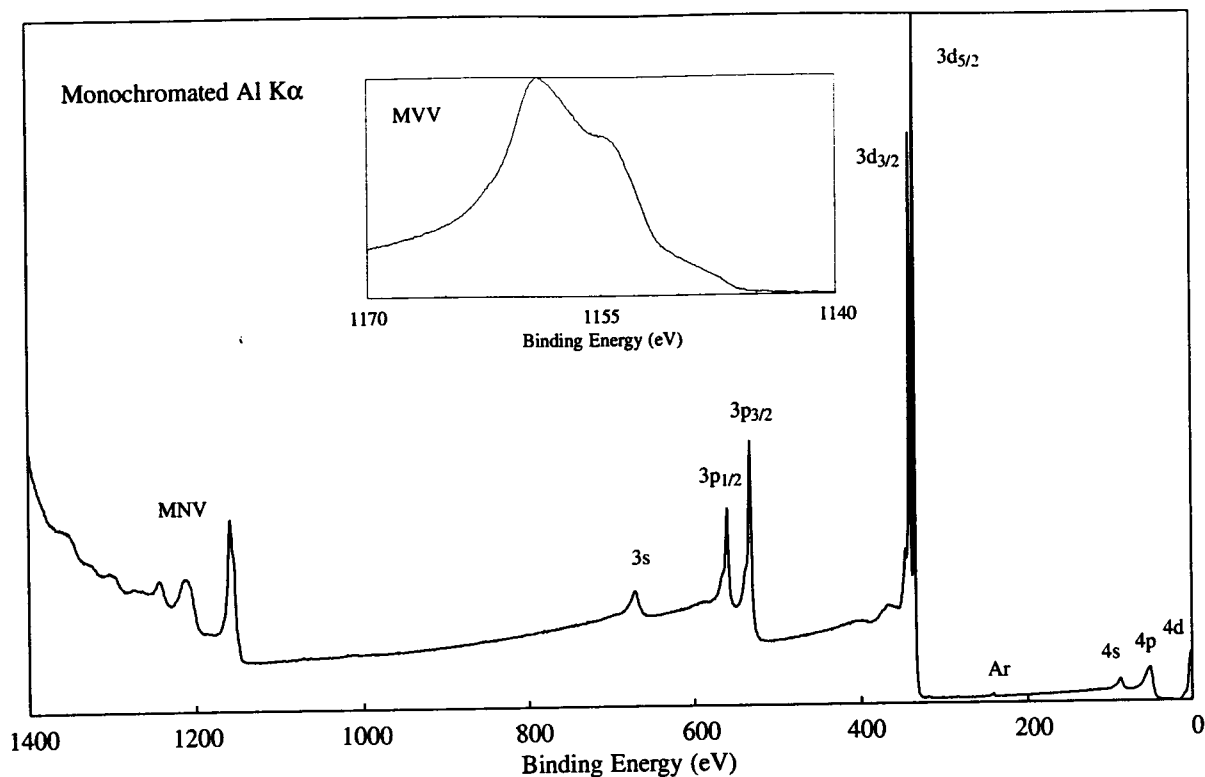


Line Positions (eV)							
Photoelectron Lines							
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	
629	521	497	312	307	81	48	
Auger Lines							
M ₄₅ N ₂₃ V		M ₄₅ VV					
1234		1185		(Al)			
1001		952		(Mg)			



Compound Type	3d _{5/2} Binding Energy (eV)				
	307	308	309	310	311
Rh					
Halides					
Rh ₂ O ₃					
ClRh(Ph ₃ P) ₃					
Cl ₃ Rh(Ph ₃ P) ₃					
Cl ₆ Rh(Ph ₃ P) ₃					
Br ₆ Rh(Ph ₃ P) ₃					
Cl ₂ Rh ₂ (cyclooctadiene) ₂					
Rh ₂ (OAc) ₄ • 2H ₂ O					
Rh(NH ₂ CH ₂ COO) ₃ • H ₂ O					





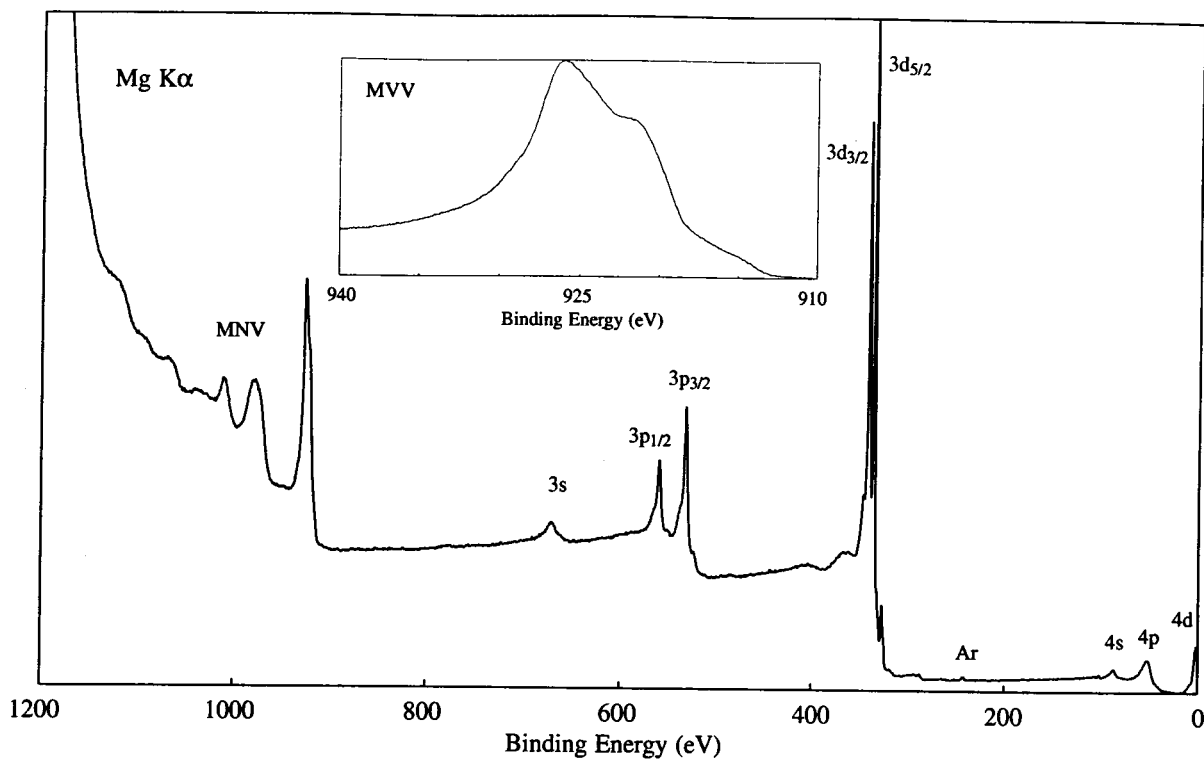
Line Positions (eV)

Photoelectron Lines

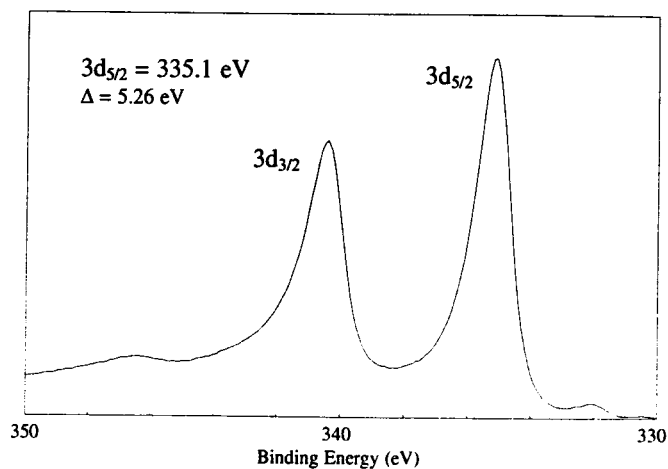
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
671	560	533	340	335	88	52

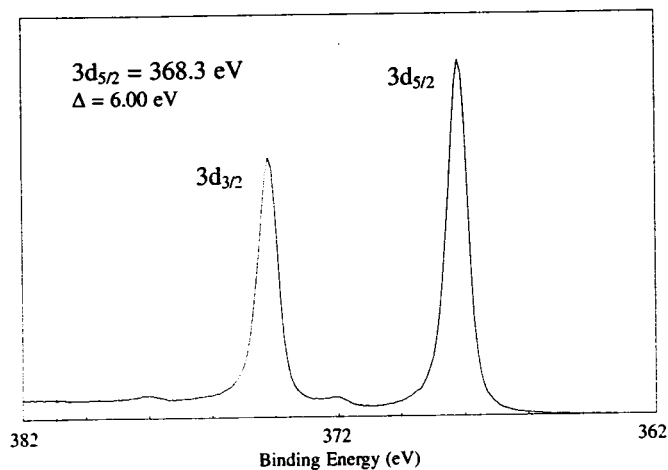
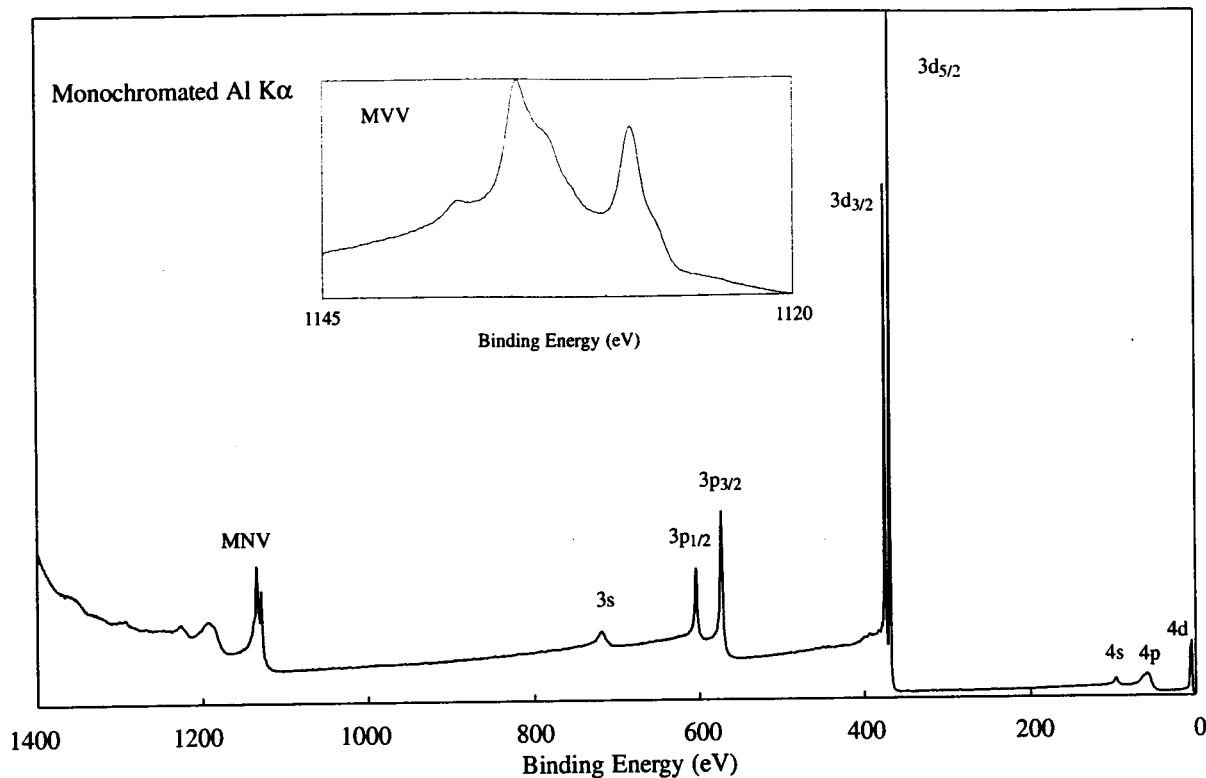
Auger Lines

M ₄₅ N ₂₃ V	M ₄₅ VV	
1211	1159	(Al)
978	926	(Mg)



Compound Type	3d _{5/2} Binding Energy (eV)						
	335	336	337	338	339	340	341
Pd	■						
Pd ₂ Si			■				
Pd ₃ Si		■	■				
Halides		■	■	■			
PdO		■					
PdO ₂				■			
K ₂ PdCl ₄				■			
K ₂ PdBr ₄			■				
K ₂ PdCl ₆						■	
Pd(OAc) ₂				■			
Pd(SPh) ₂				■			





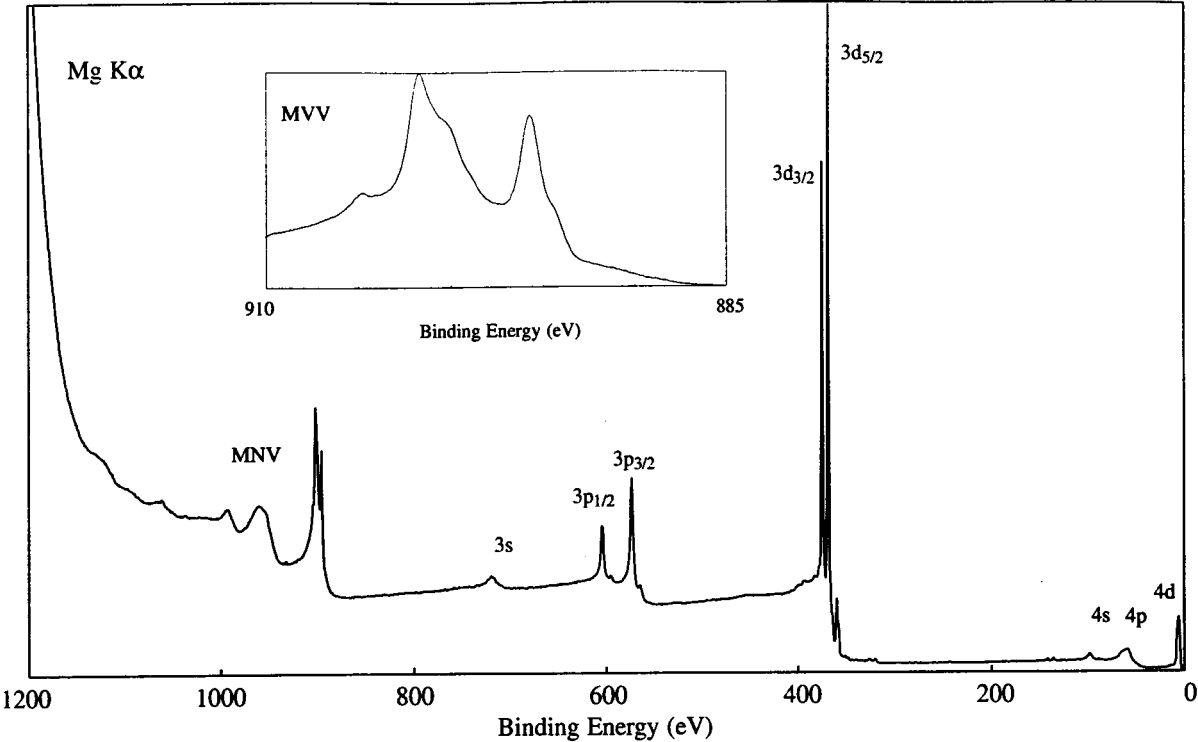
Line Positions (eV)

Photoelectron Lines

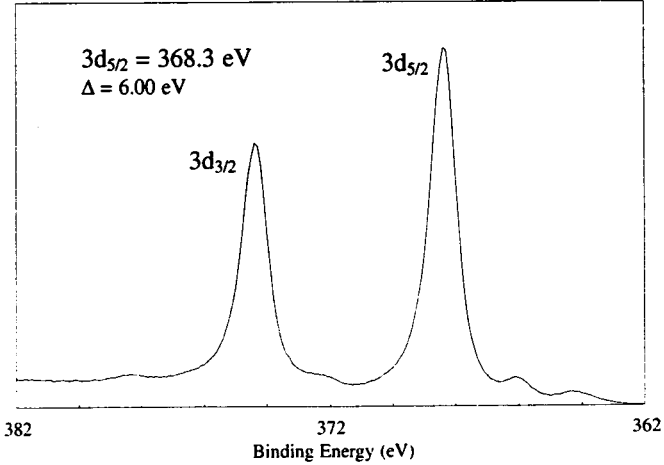
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
719	604	573	374	368	98	60

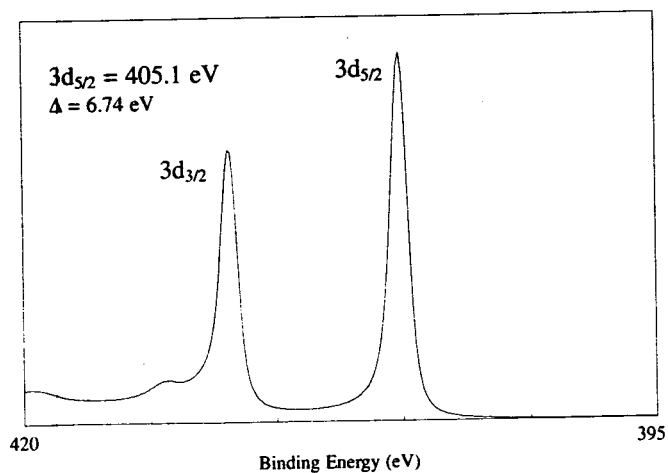
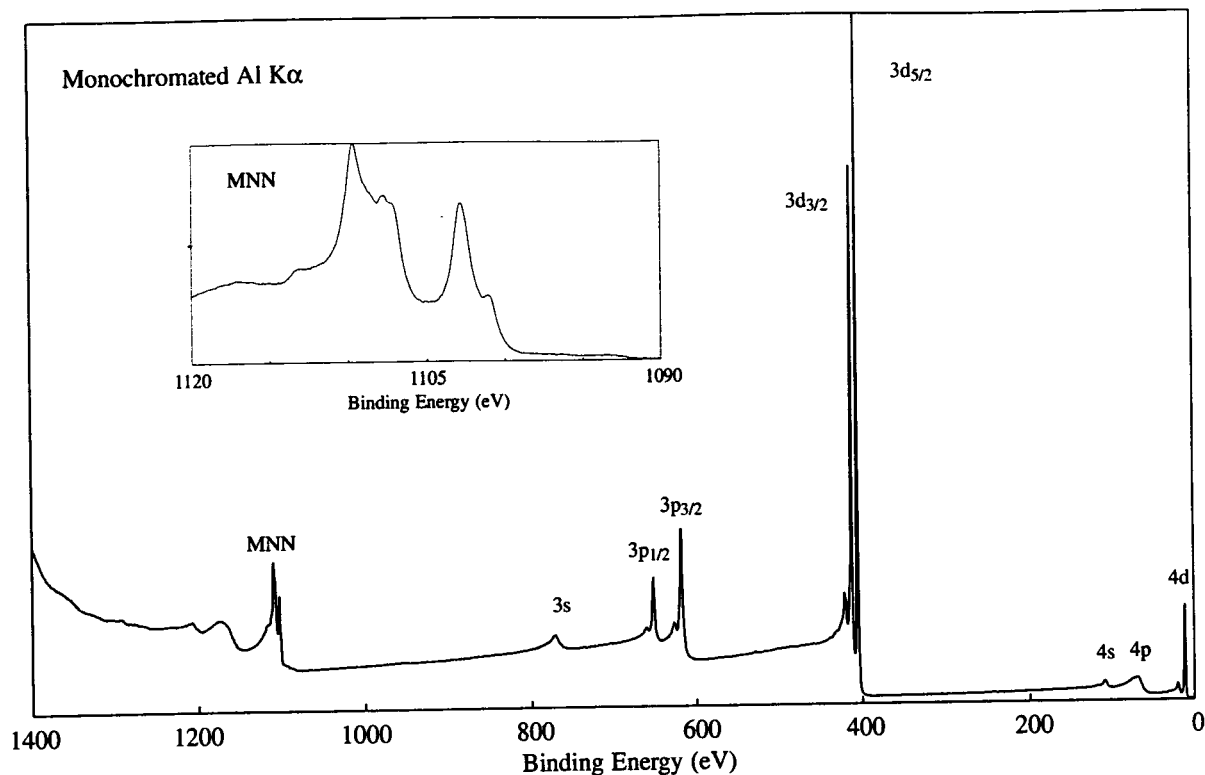
Auger Lines

M ₄₅ N ₂₃ V	M ₅ VV	M ₄ VV	
1191	1135	1129	(Al)
958	902	896	(Mg)



3d _{5/2} Binding Energy (eV)			
Compound Type	367	368	369
Ag			
Alloys			
Ag ₂ S			
AgI			
AgF			
AgF ₂			
Oxides			
Ag ₂ CO ₃			
Sulfate			
AgOOCF ₃			
Ag(OAc)			





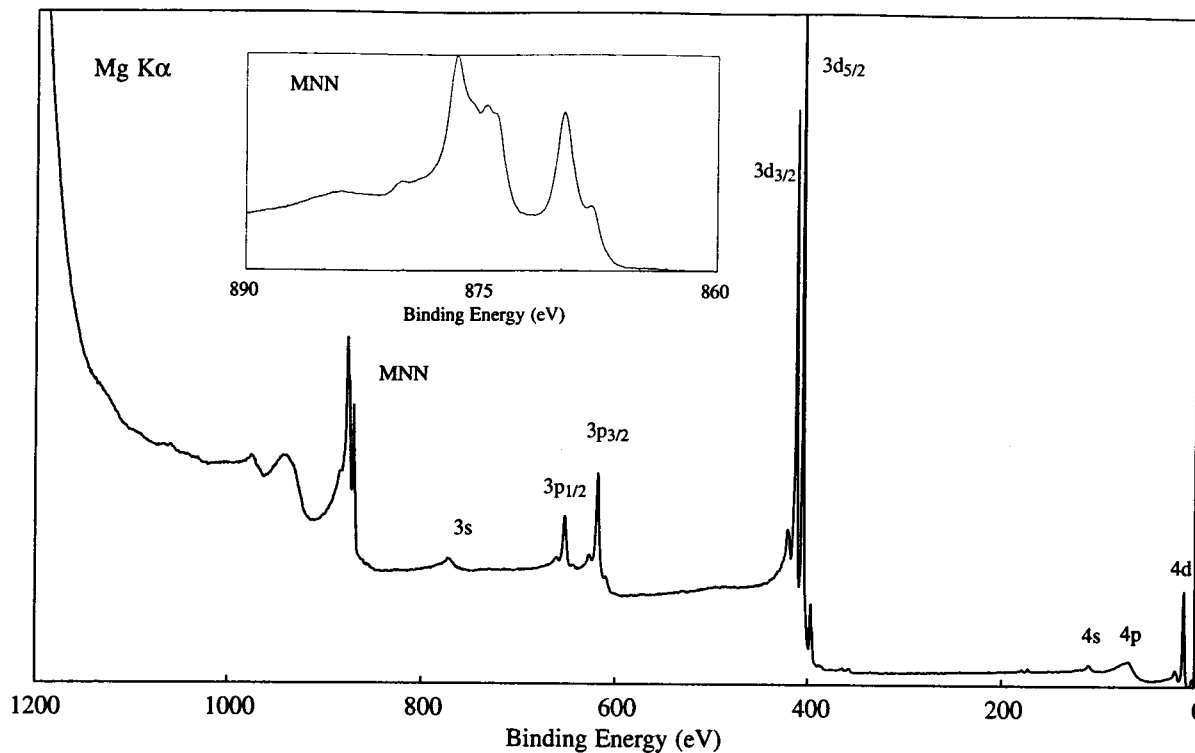
Line Positions (eV)

Photoelectron Lines

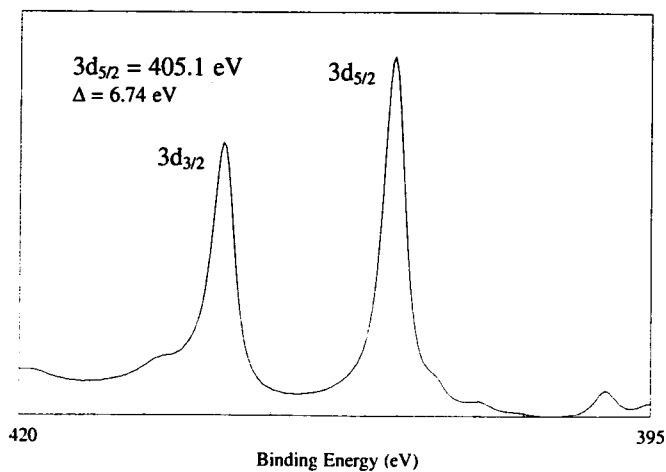
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
772	652	618	412	405	110	69	11

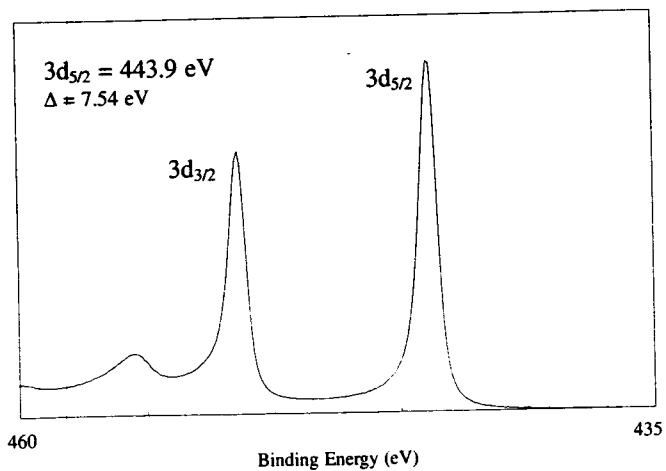
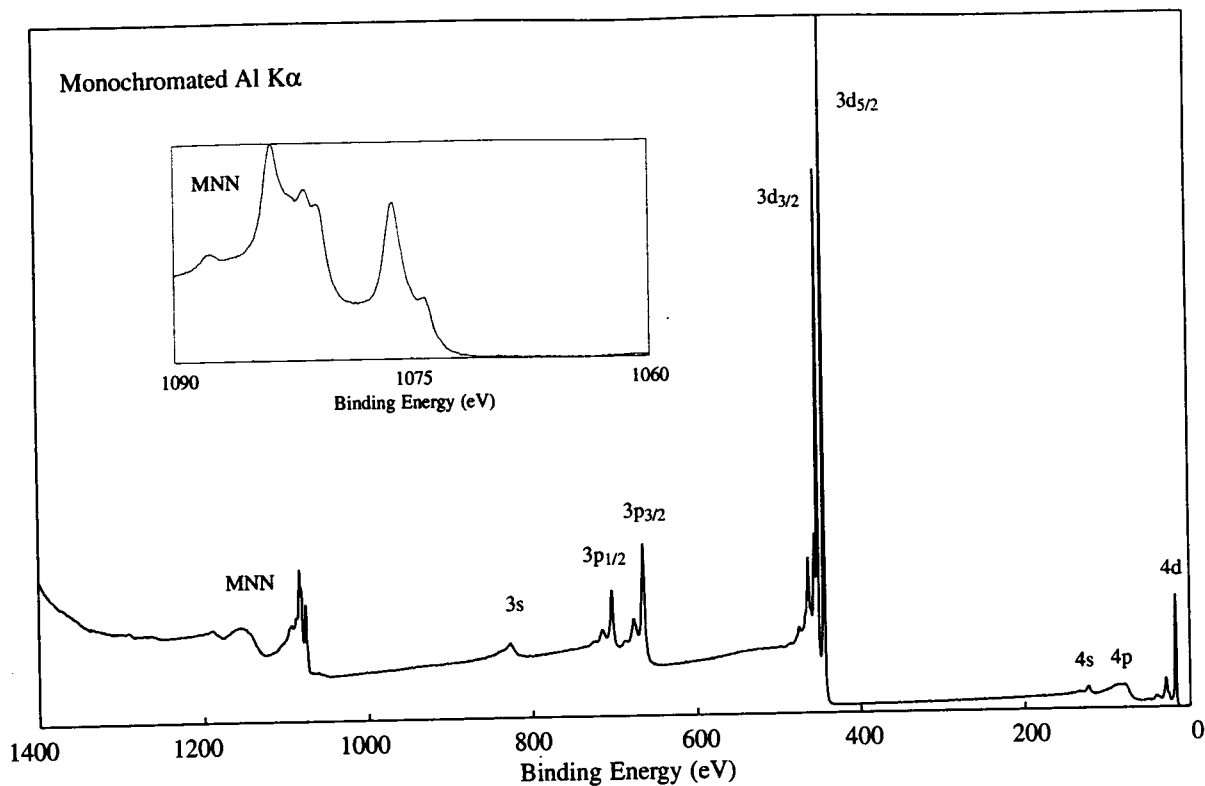
Auger Lines

M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
1110	1103	(Al)
877	870	(Mg)

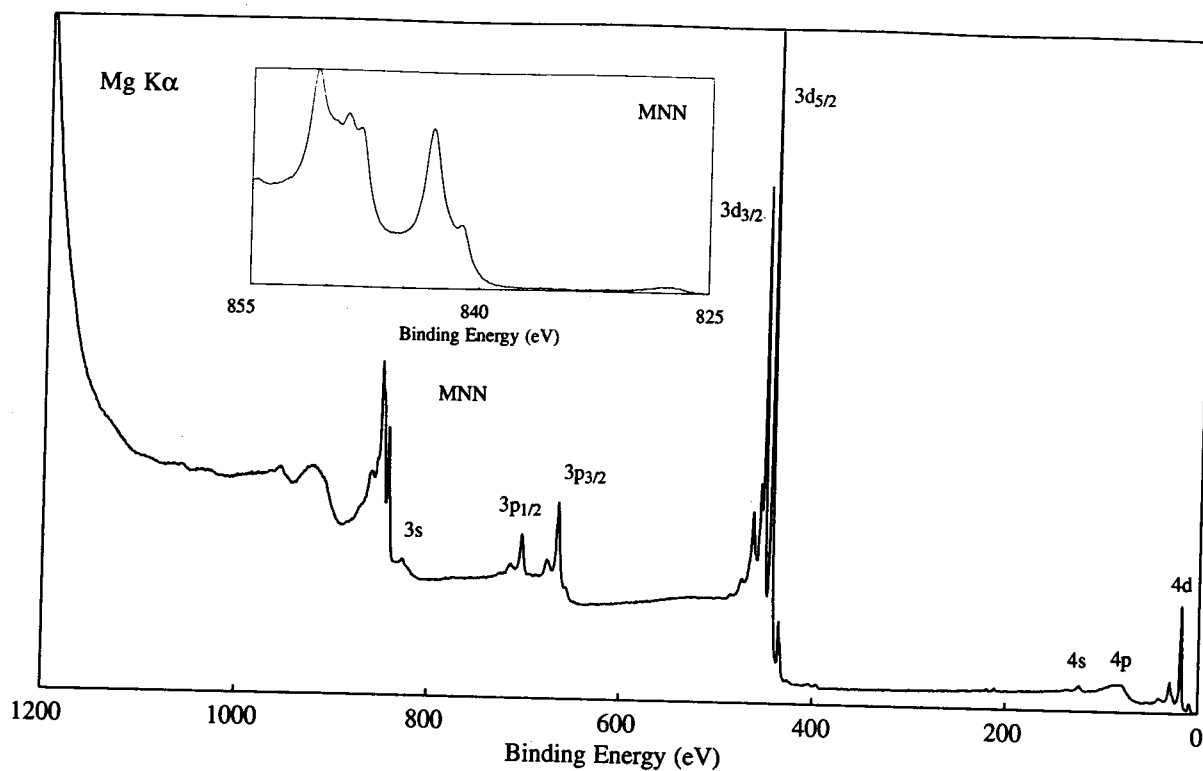


3d _{5/2} Binding Energy (eV)				
Compound Type	404	405	406	407
Cd				
Hg _{0.8} Cd _{0.2} Te				
CdTe				
CdSe				
CdS				
Halides				
CdO				
CdO ₂				
Cd(OH) ₂				
CdCO ₃				

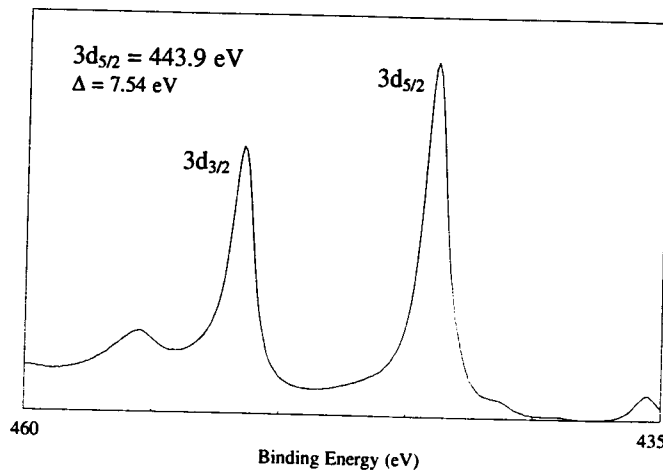




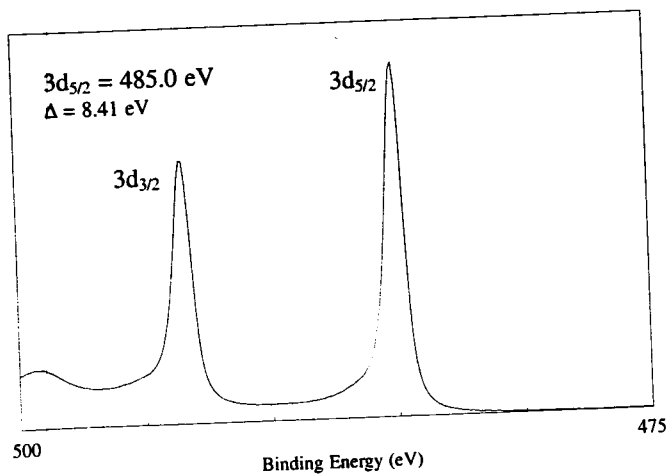
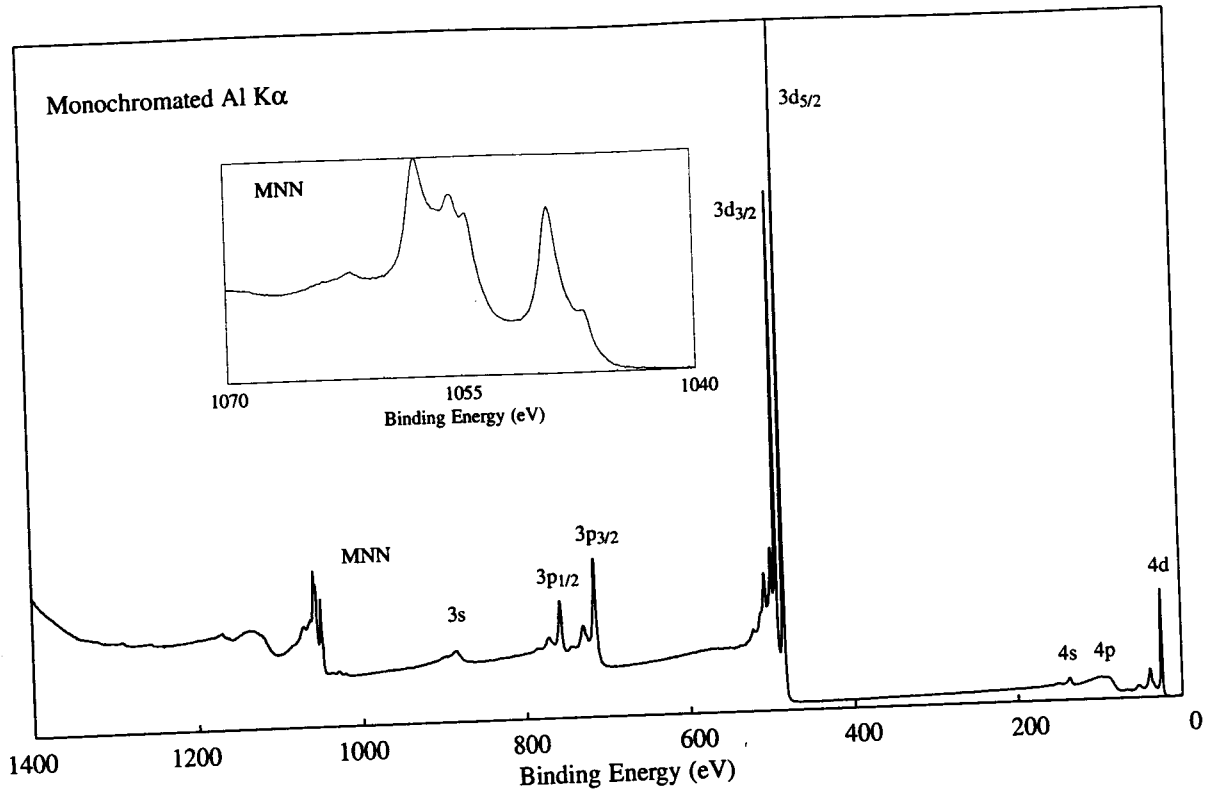
Line Positions (eV)							
Photoelectron Lines							
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
828	703	665	452	444	123	78	17
Auger Lines							
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅					
1084		1076		(Al)			
851		843		(Mg)			



Compound Type	3d _{5/2} Binding Energy (eV)				
	443	444	445	446	447
In					
InSb					
InP					
In ₂ Te ₃					
InCl ₃					
InCl					
In ₂ O ₃					
In(OH) ₃					
In(acac) ₃					
Br ₂ InEt ₄ N					
Br ₂ InPr ₄ N					



Tin **Sn**
Atomic Number 50



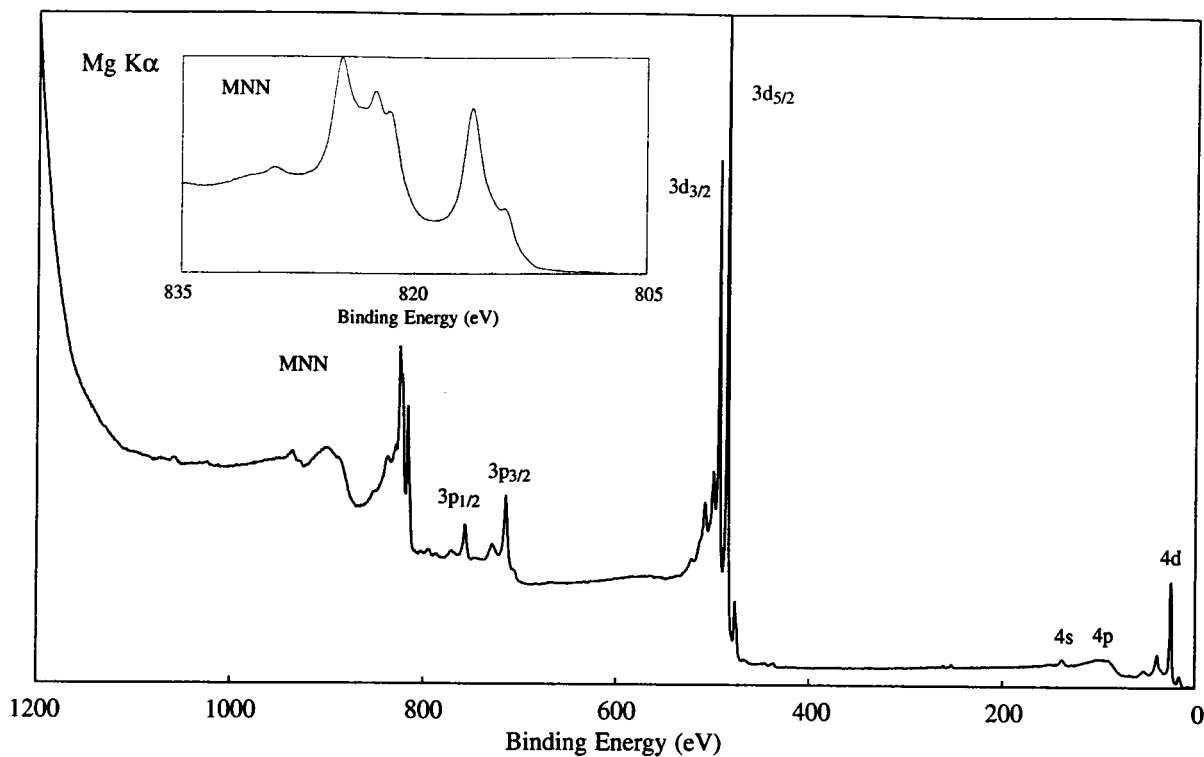
Line Positions (eV)

Photoelectron Lines

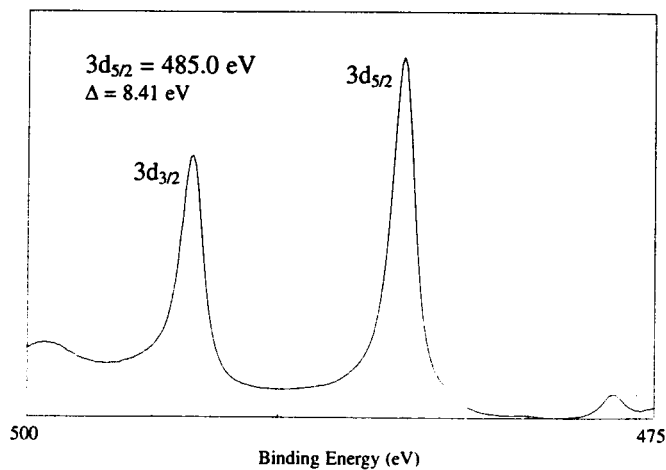
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
885	757	715	493	485	137	89	25

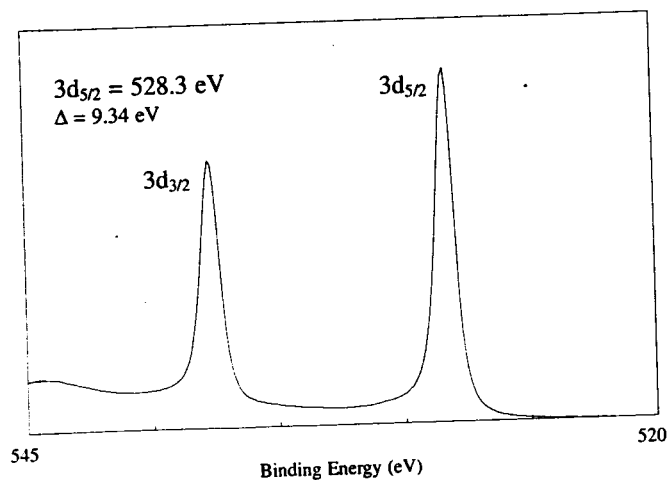
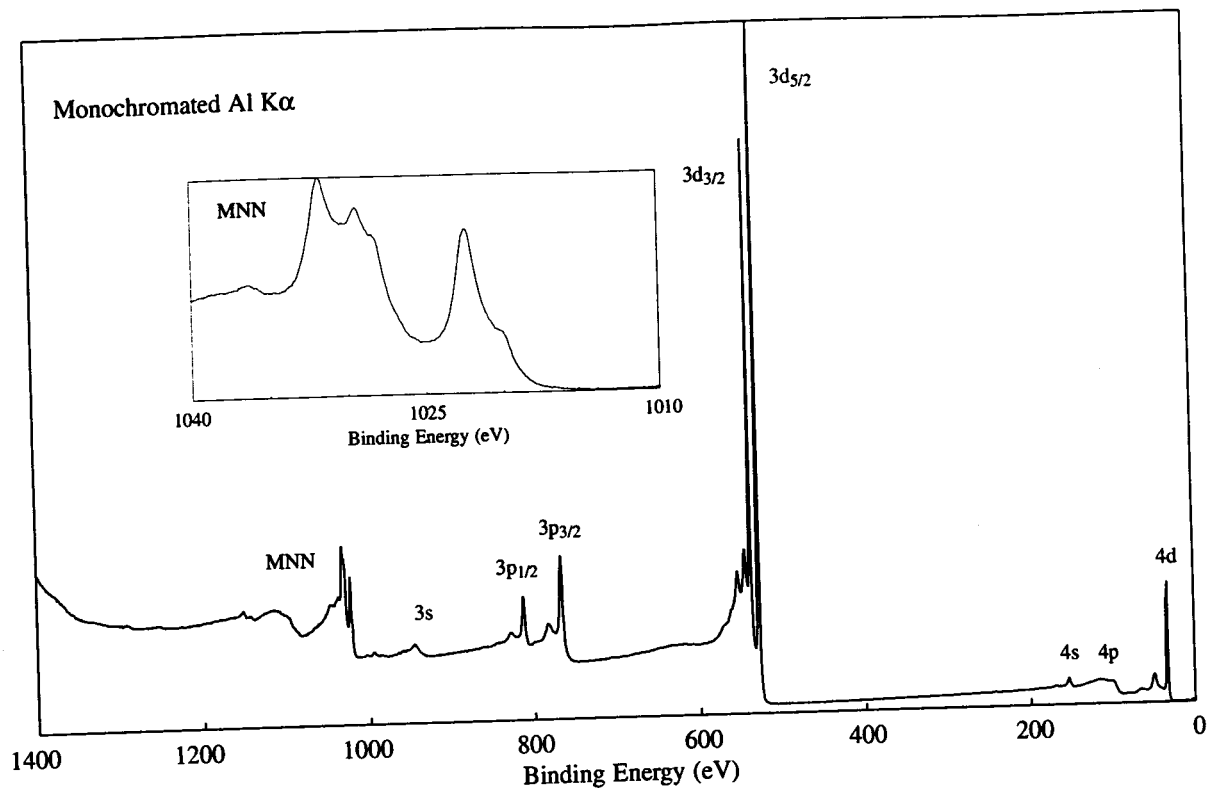
Auger Lines

M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
1058	1049	(Al)
825	816	(Mg)



Compound Type	3d $_{5/2}$ Binding Energy (eV)				
	484	485	486	487	488
Sn					
SnS					
Halides					
SnO					
SnO $_2$					
Na $_2$ SnO $_3$					
Ph $_4$ Sn					
Ph $_3$ Sn (Halide)					
Me $_3$ SnF					
Me $_2$ SnF $_2$					
Br $_6$ Sn(Et $_4$ N) $_2$					





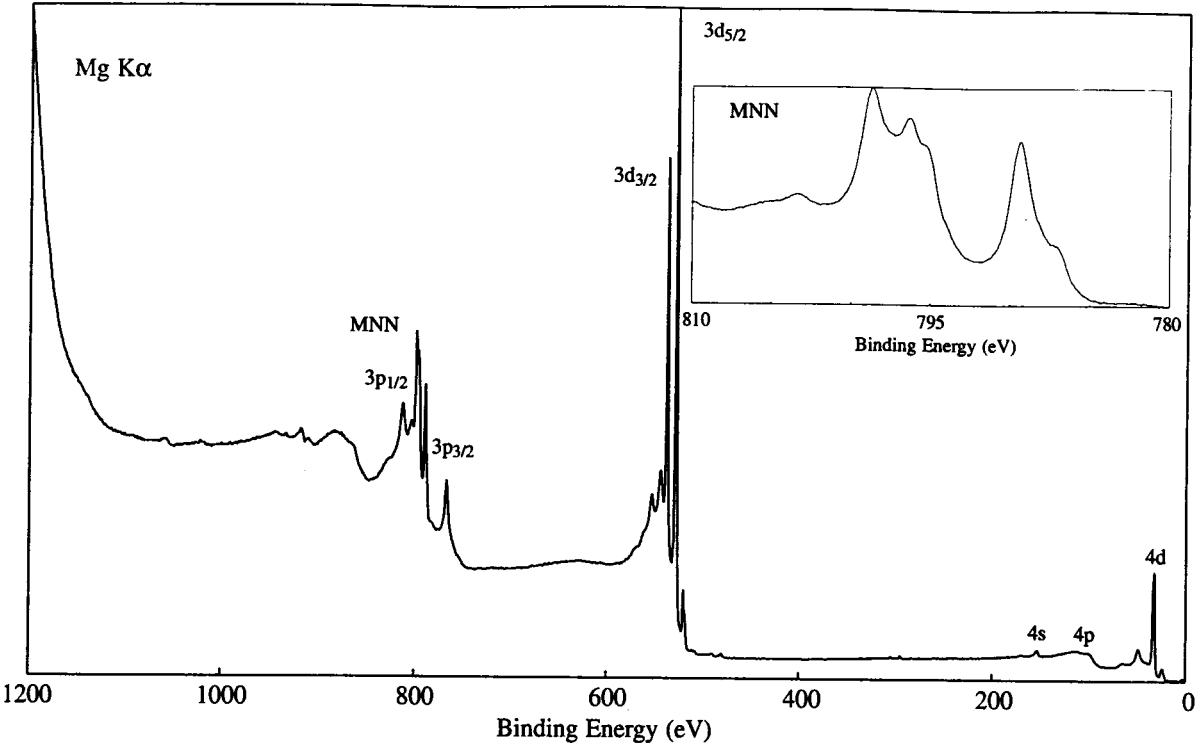
Line Positions (eV)

Photoelectron Lines

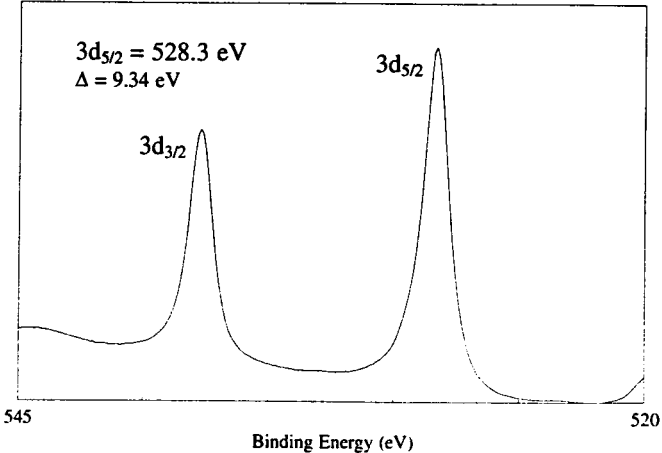
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
944	813	767	537	528	153	99	33

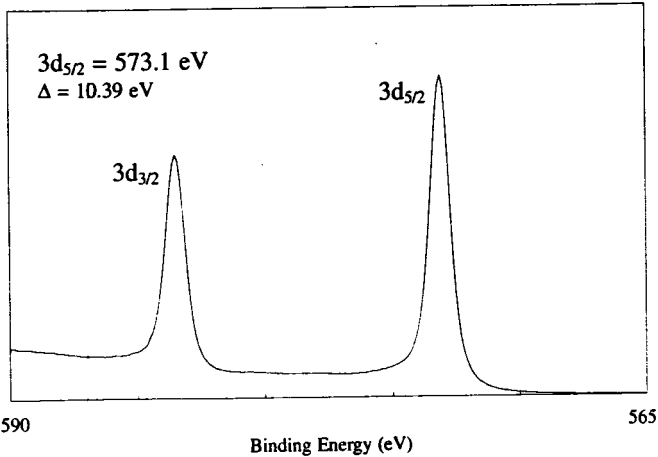
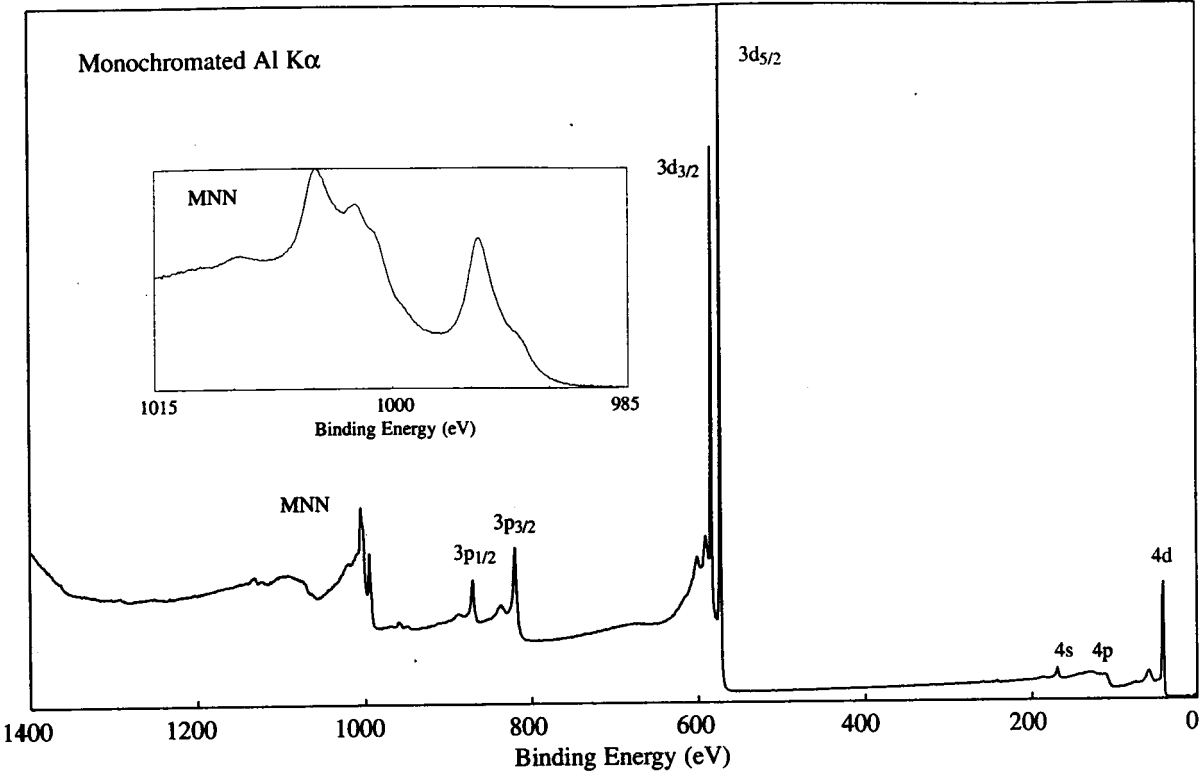
Auger Lines

M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
1032	1022	(Al)
799	789	(Mg)

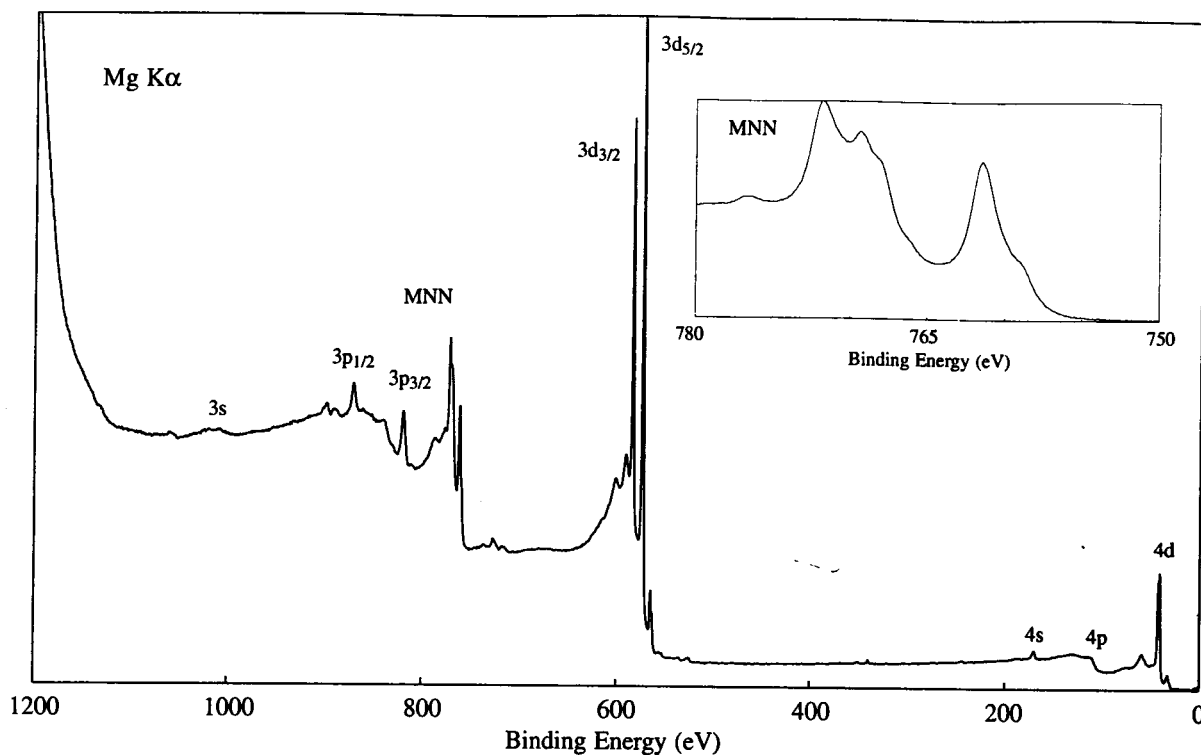


Compound Type	3d _{5/2} Binding Energy (eV)					
	528	529	530	531	532	533
Sb	■					
AlSb		■				
Sulfides			■			
Halides				■	■	
Sb ₂ O ₃			■			
Sb ₂ O ₅				■		
KSbF ₆						■
NaSbF ₆					■	
CsSbF ₄				■		
Ph ₃ Sb		■				
Bu ₃ Sb	■					

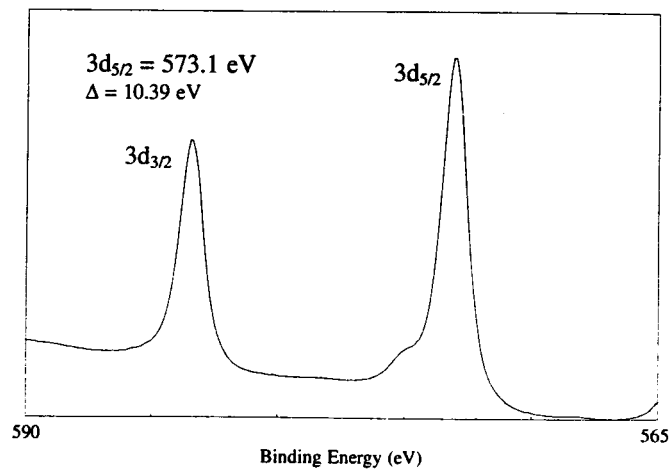


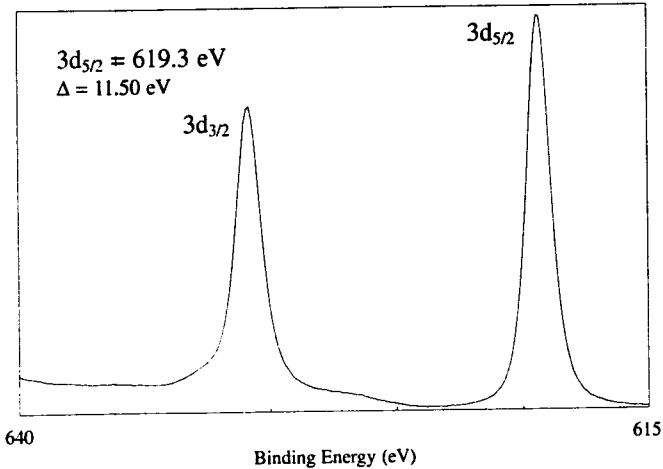
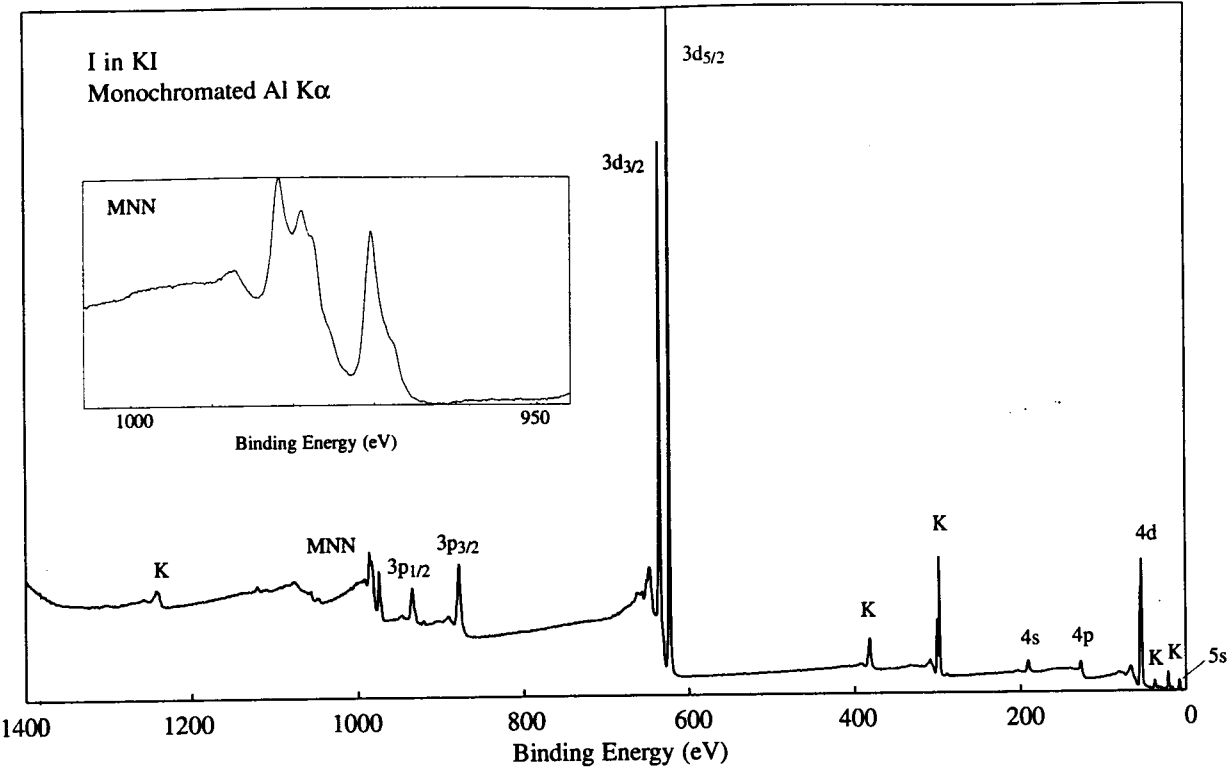


Line Positions (eV)				
Photoelectron Lines				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1009	871	820	583	573
4s	4p	4d _{3/2}	4d _{5/2}	5s
170	111	42	41	12
Auger Lines				
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅		
1005		995		(Al)
772		762		(Mg)

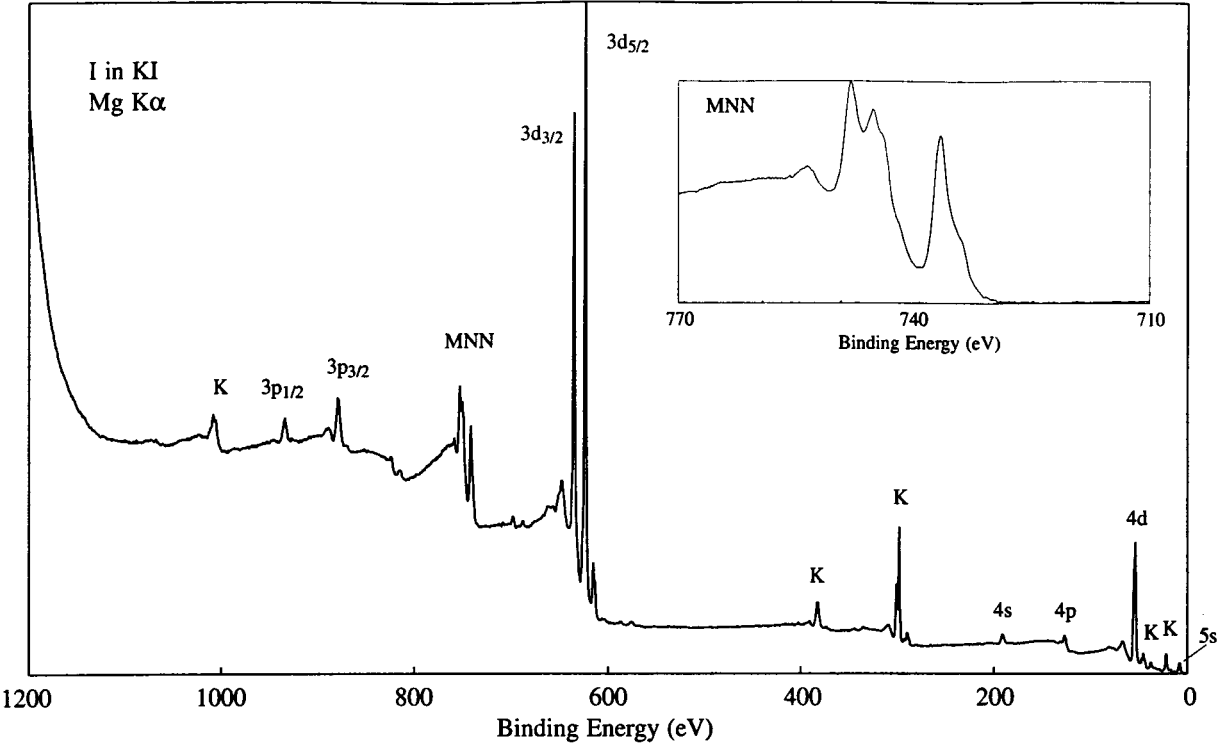


Compound Type	3d _{5/2} Binding Energy (eV)						
	572	573	574	575	576	577	578
Te		■					
CdTe	■						
GeTe	■	■					
Hg _{0.8} Cd _{0.2} Te	■	■					
Tellurides	■	■					
Halides					■	■	
TeO ₂					■		
TeO ₃						■	
Te(OH) ₆							■
Ph ₂ Te ₂			■				
Br ₃ TePh						■	

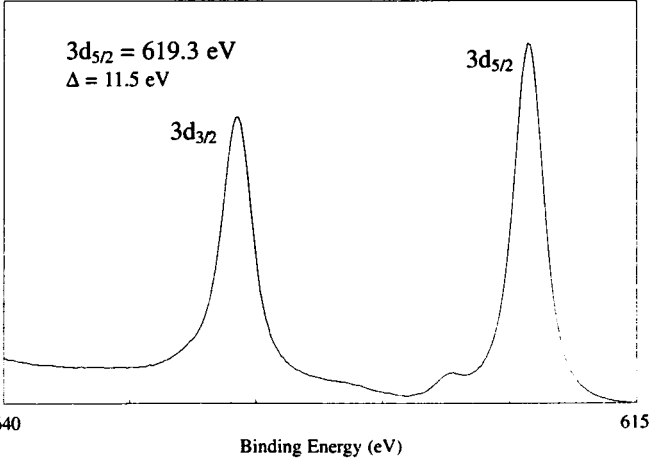


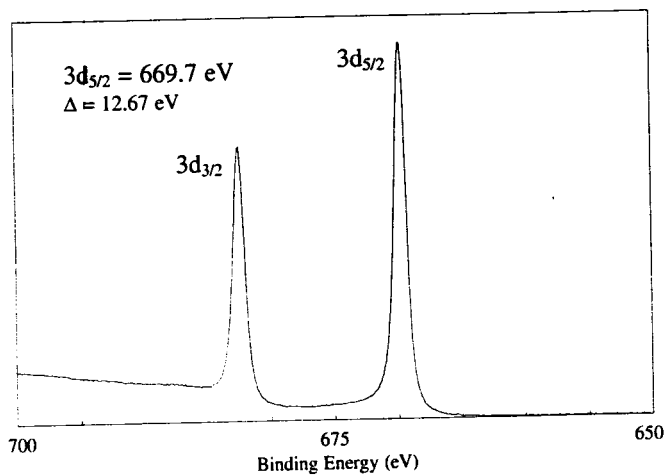
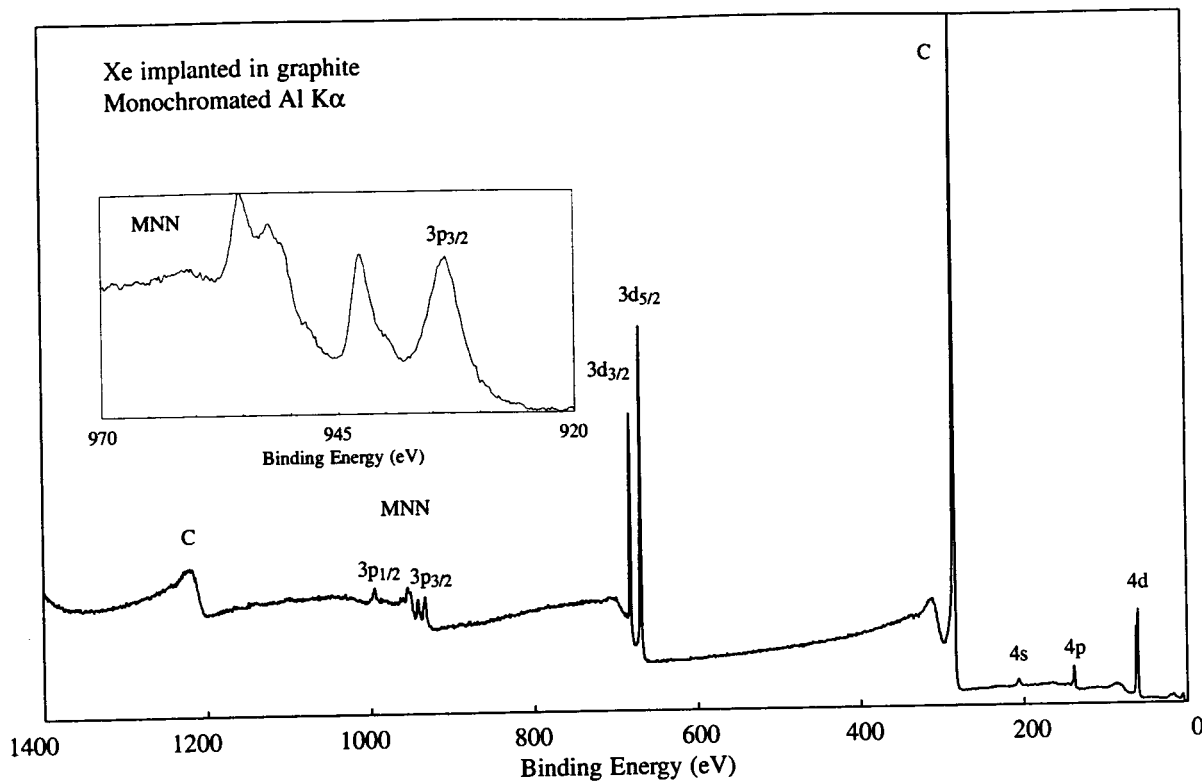


Line Positions (eV)				
Photoelectron Lines				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1071	930	875	630	619
4s	4p	4d _{3/2}	4d _{5/2}	5s
187	123	51	49	18
Auger Lines				
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅		
982		971		(Al)
749		738		(Mg)

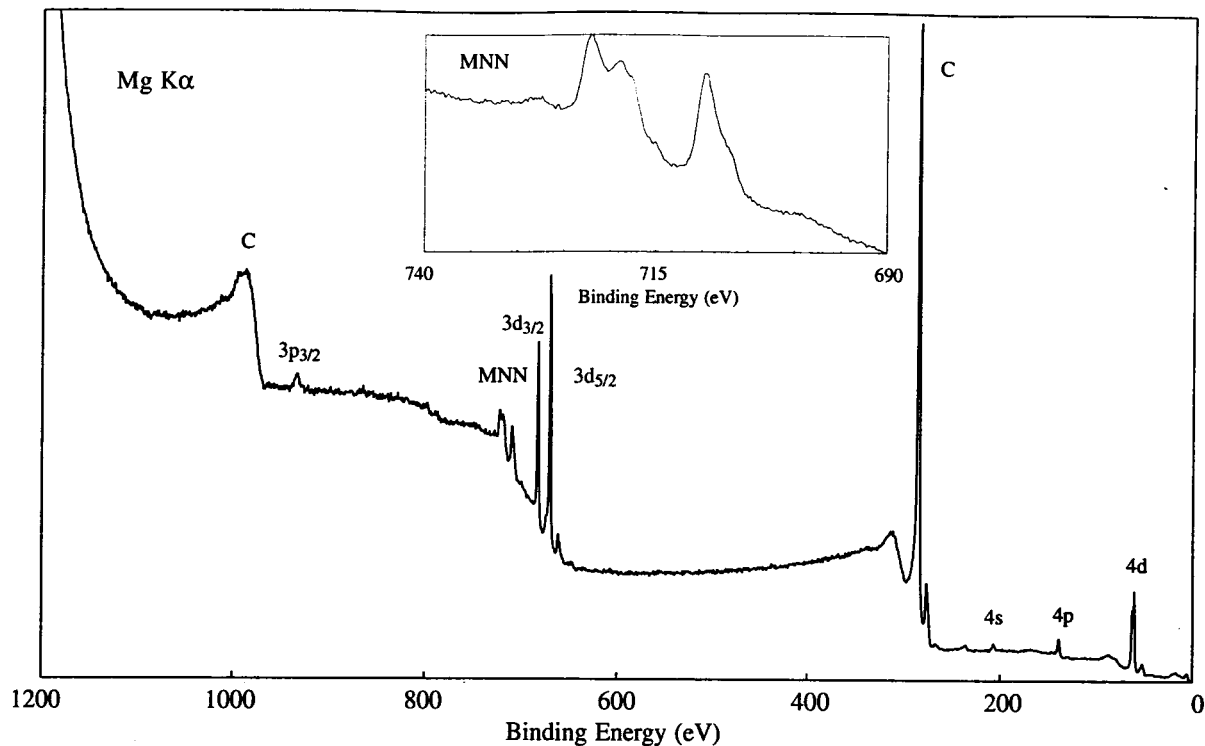


Compound Type	3d _{5/2} Binding Energy (eV)						
	618	619	620	621	622	623	624
I ₂							
Alkali iodides							
AgI							
NiI ₂							
NiI ₂ · 6H ₂ O							
NaIO ₃							
NaIO ₄							
H ₅ IO ₆							
I ₂ O ₅							
ICl							
ICl ₃							

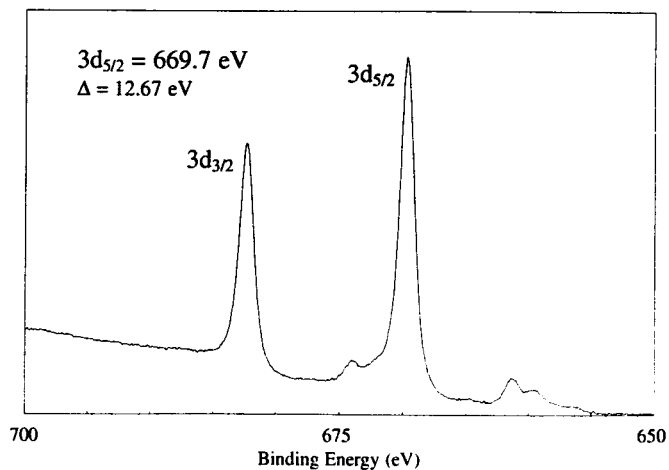


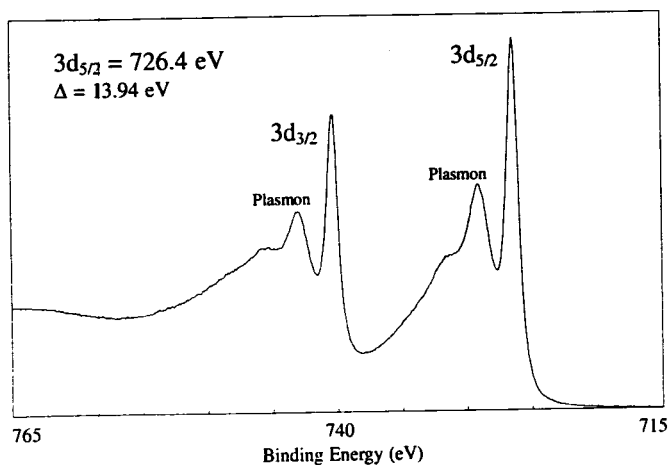
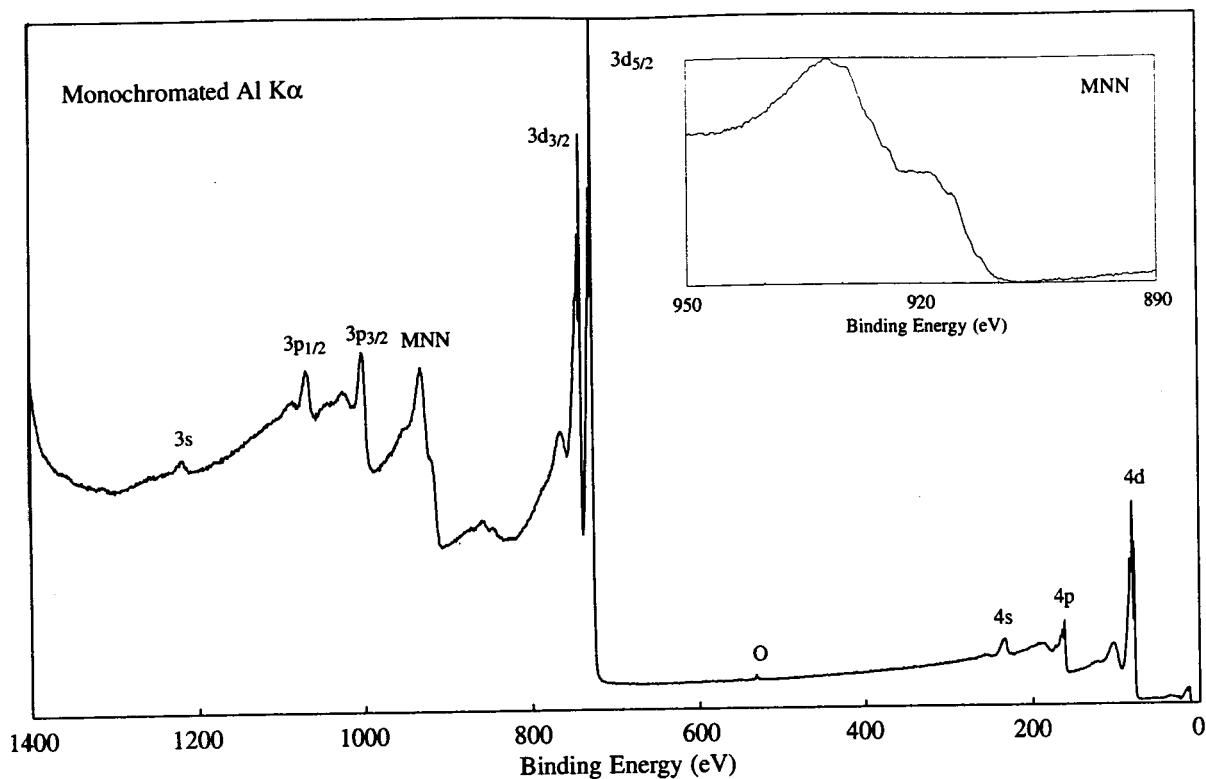


Line Positions (eV)				
Photoelectron Lines				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1141	996	934	683	670
4s	4p	4d _{3/2}	4d _{5/2}	5s
207	139	63	61	17
Auger Lines				
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅		
955		942 (Al)		
722		709 (Mg)		



Compound Type	3d _{5/2} Binding Energy (eV)						
	668	669	670	671	672	673	674
Xe in Ag			■				
Xe in Au	■						
Xe in Cu		■					
Xe in Fe			■				
Xe in graphite		■					
Na ₄ XeO ₆							■





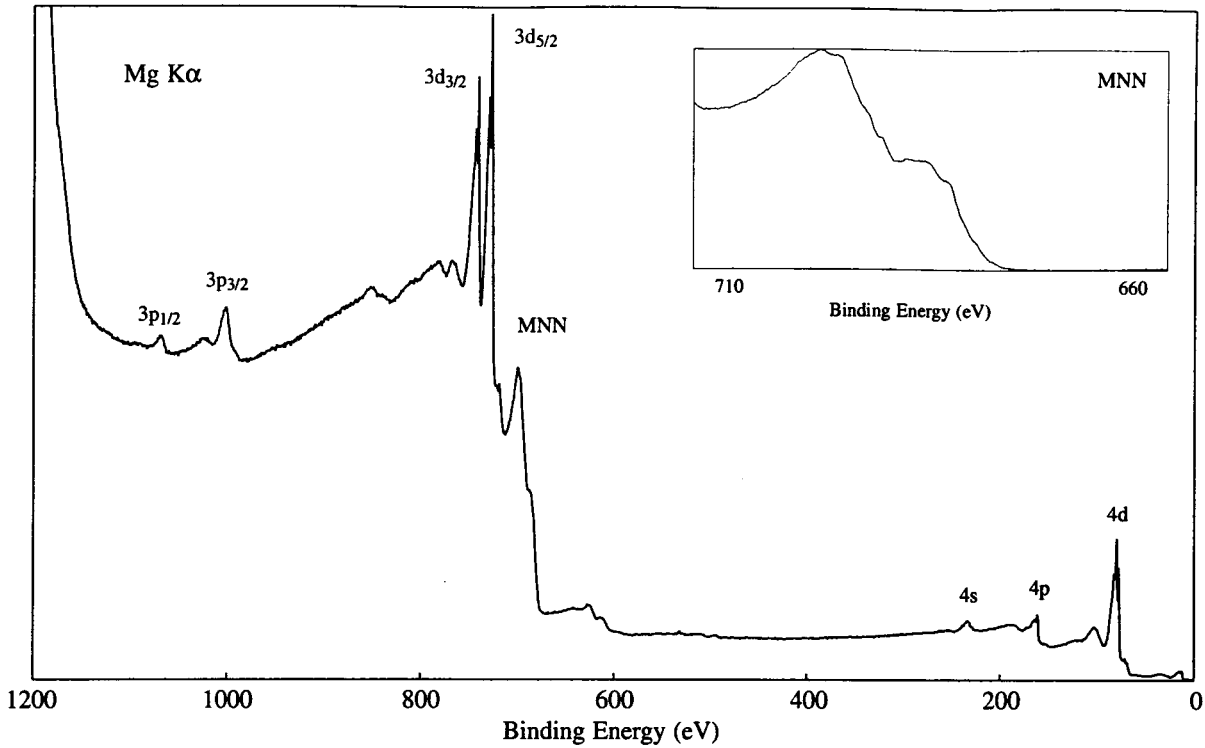
Line Positions (eV)

Photoelectron Lines

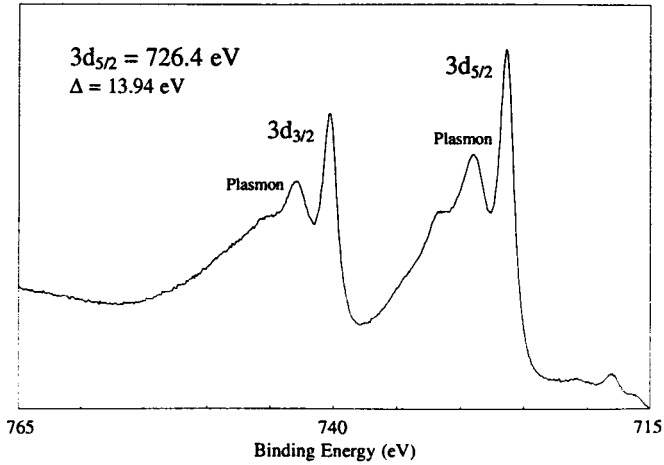
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1219	1069	1002	740	726
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
234	173	161	80	77

Auger Lines

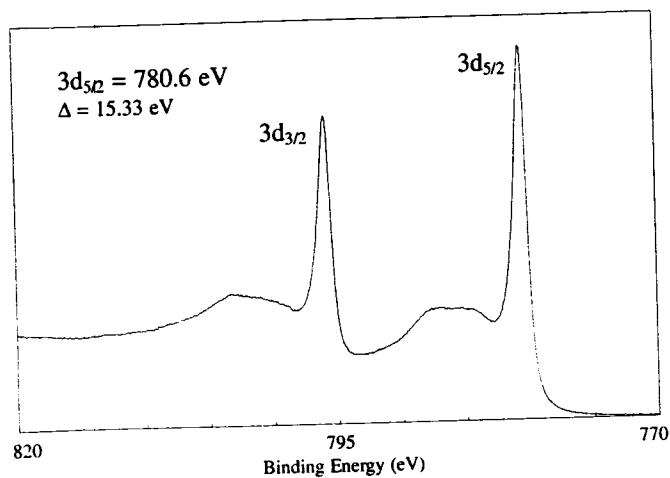
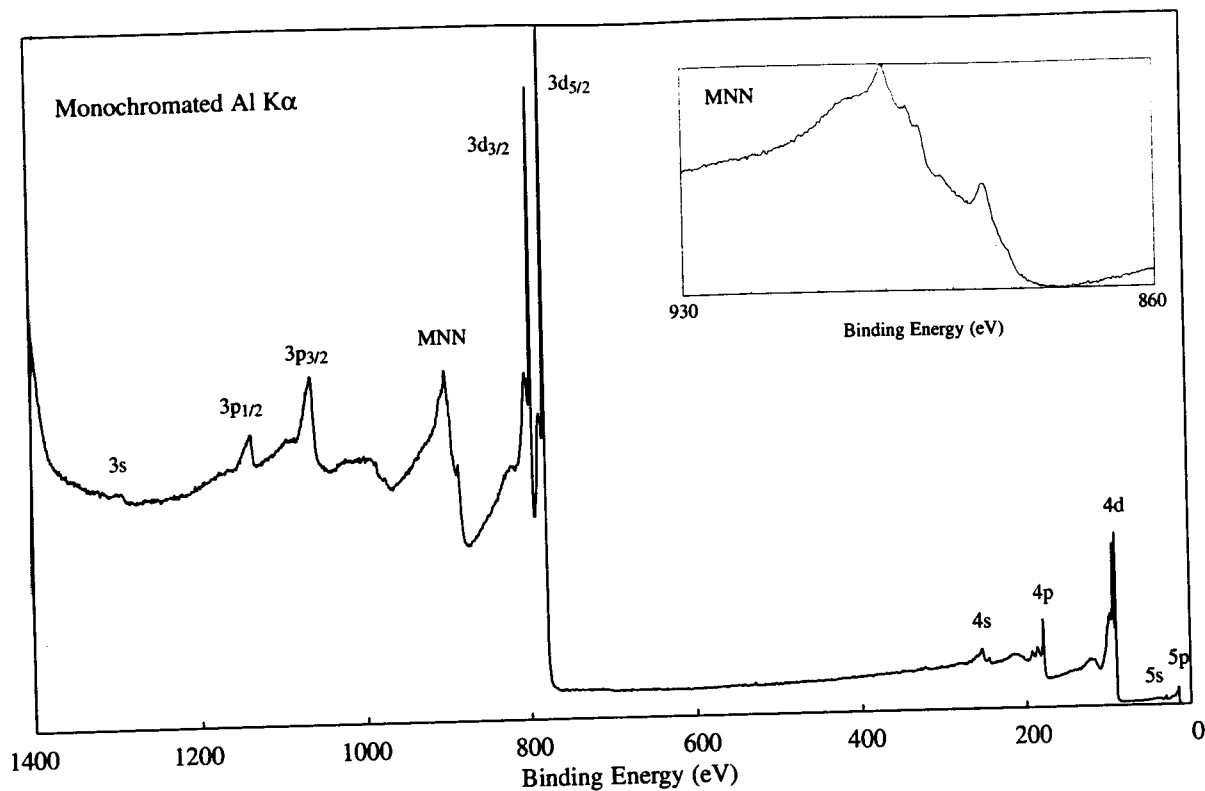
M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
931	918	(Al)
698	685	(Mg)



3d _{5/2} Binding Energy (eV)				
Compound Type	723	724	725	726
Cs				
Halides				
CsN ₃				
Cs ₂ SO ₄				
Cs ₃ PO ₄				
Cs ₄ P ₂ O ₇				
CsClO ₄				
Cs ₂ CrO ₄				
Cs ₂ Cr ₂ O ₇				
CsOH				



Barium **Ba**
Atomic Number 56



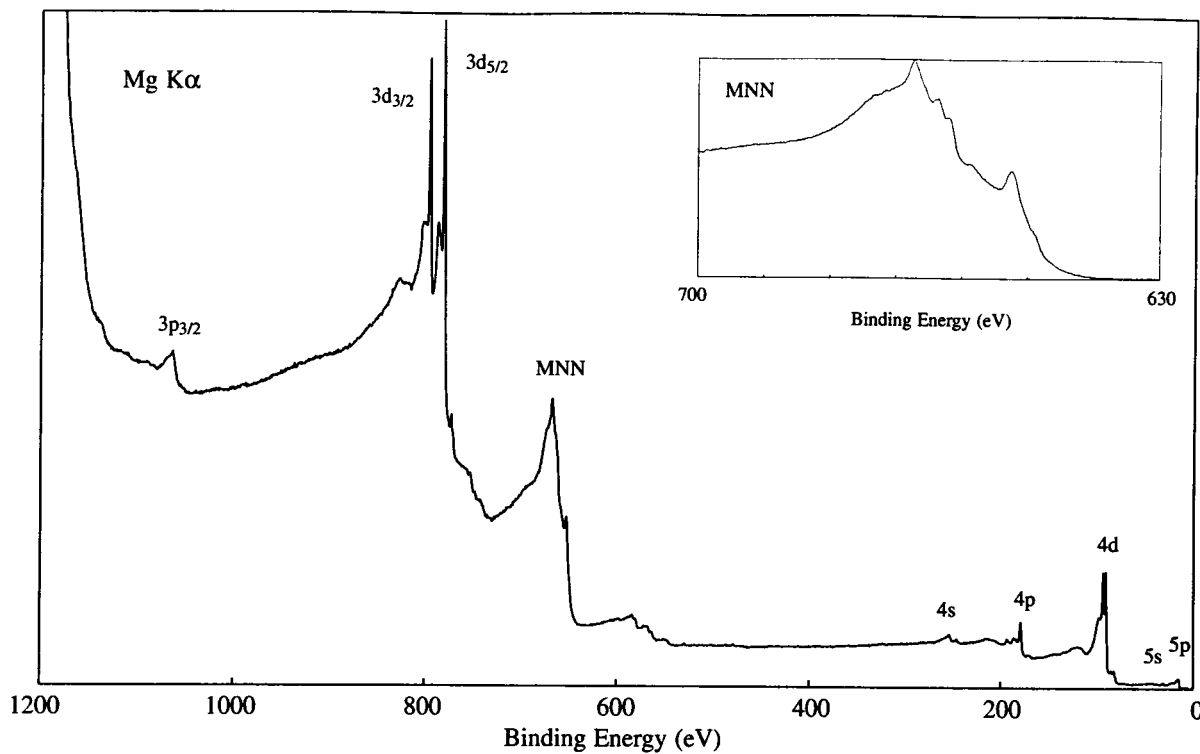
Line Positions (eV)

Photoelectron Lines

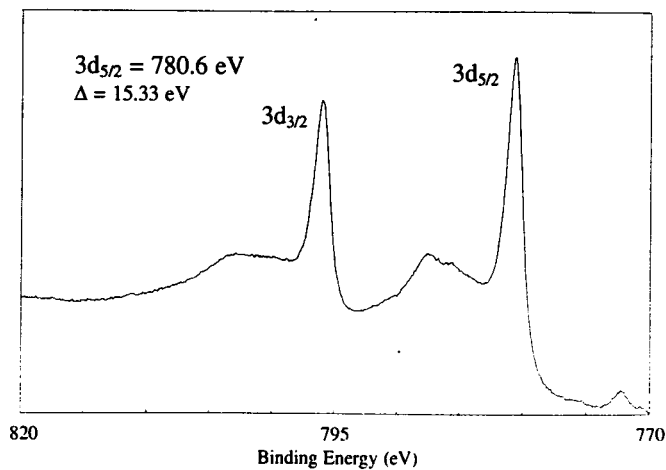
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}		
1292	1138	1064	796	781		
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s	5p
254	193	179	93	90	31	15

Auger Lines

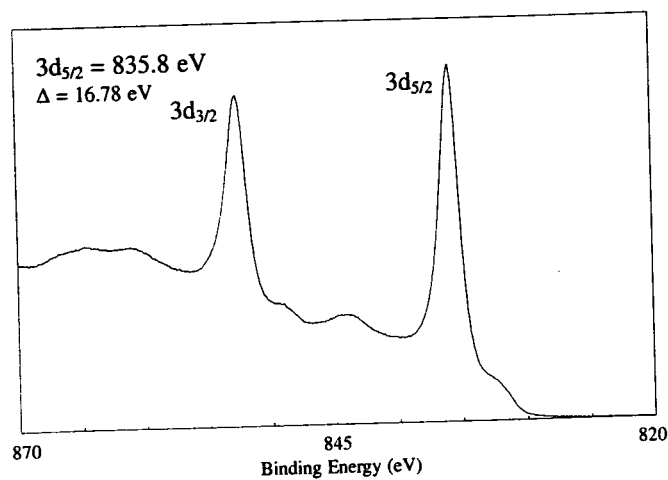
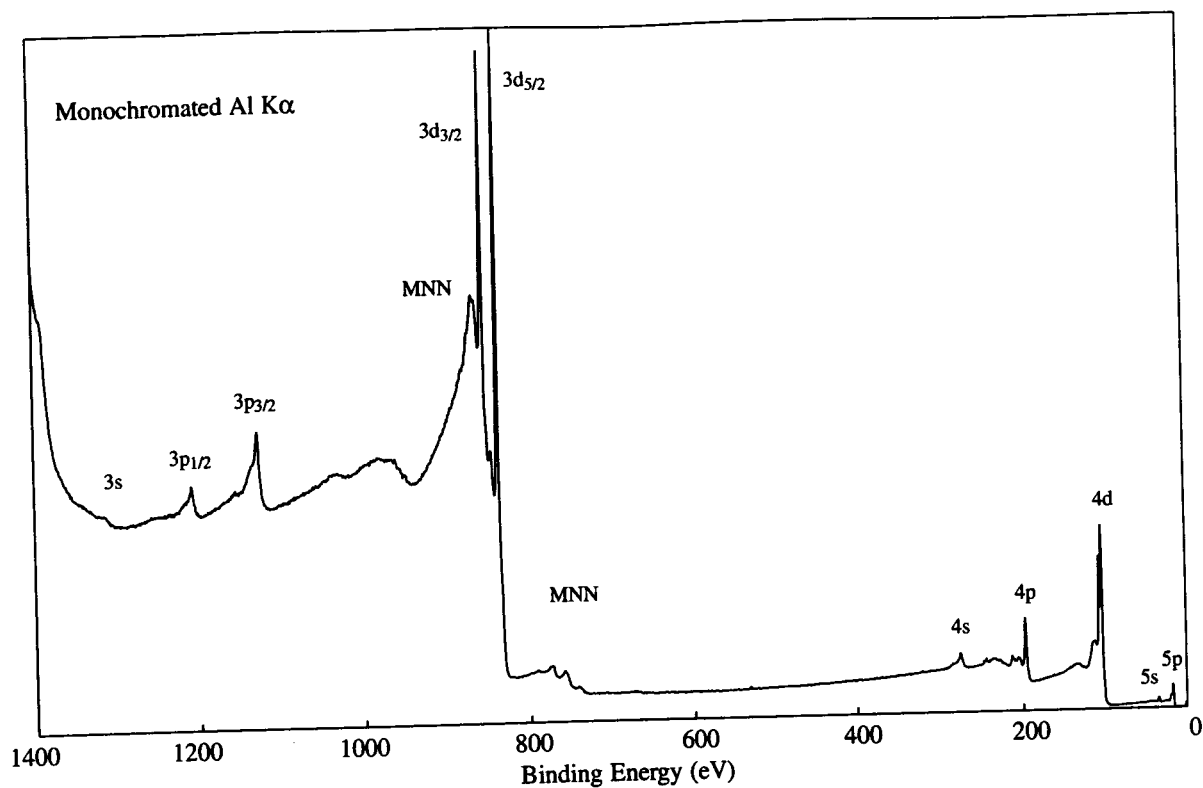
M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
900	886	(Al)
667	653	(Mg)



Compound Type	3d $_{5/2}$ Binding Energy (eV)			
	778	779	780	781
Ba				
BaS				
BaO				
Ba(NO $_3$) $_2$				
BaCO $_3$				
BaSO $_4$				
BaCrO $_4$				
BaMoO $_4$				
BaRh $_2$ O $_4$				



Lanthanum **La**
Atomic Number 57



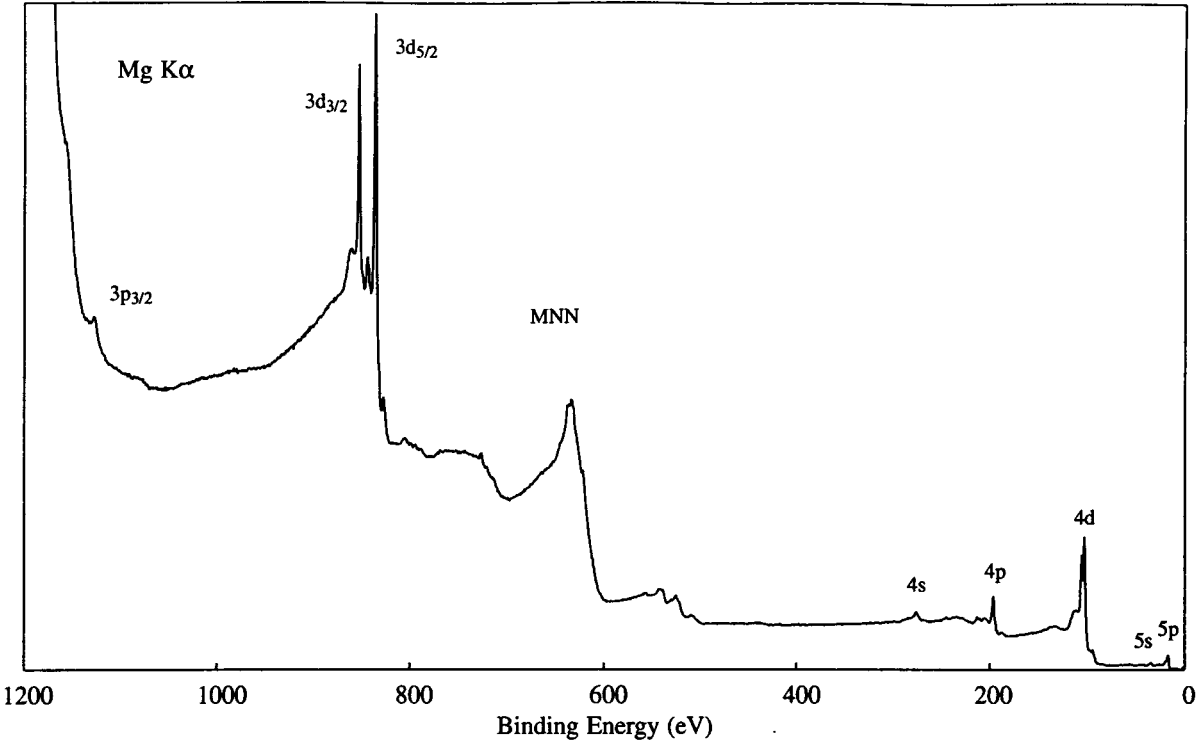
Line Positions (eV)

Photoelectron Lines

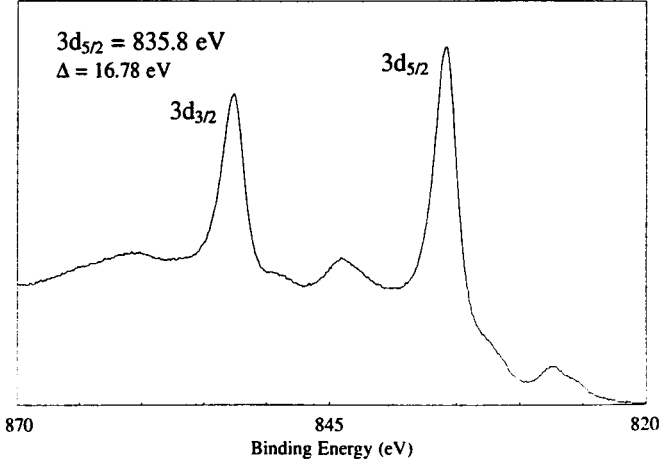
3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}			
1208	1128	853	836			
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s	5p
275	213	197	106	103	34	17

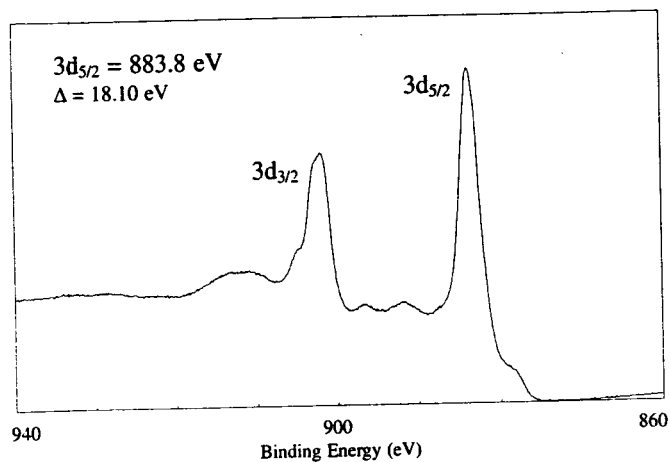
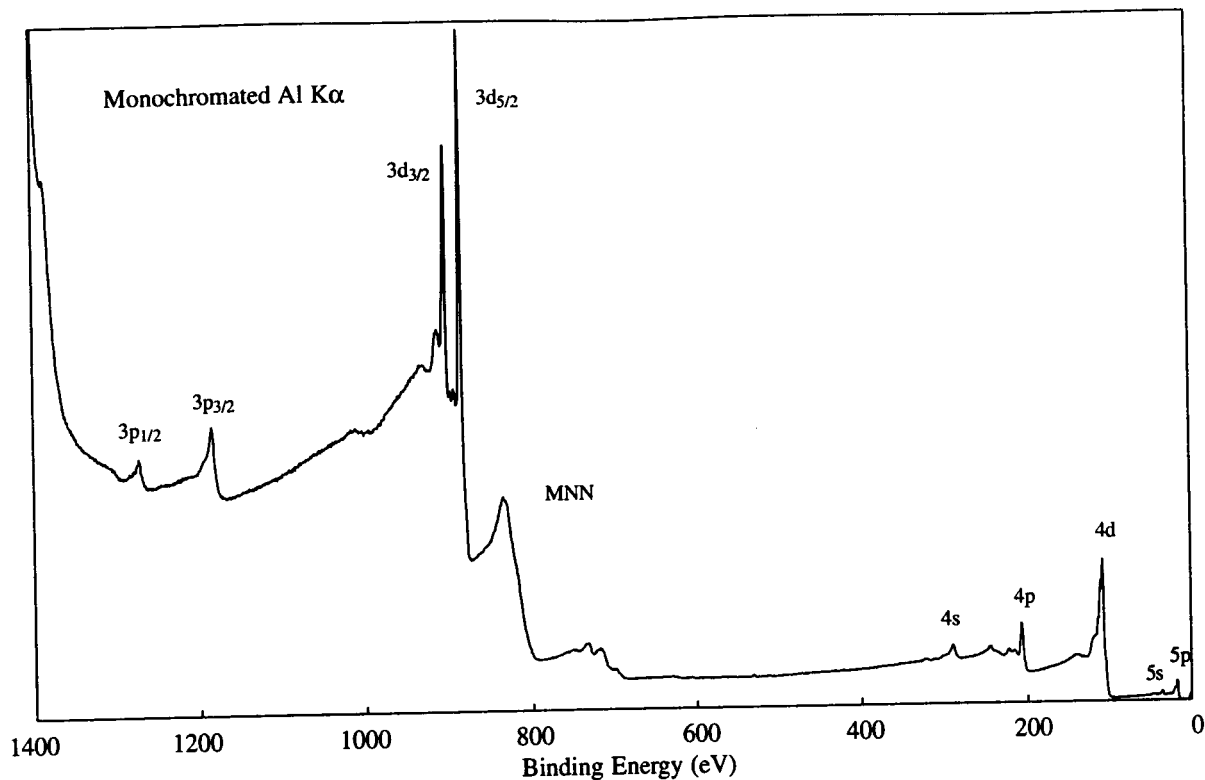
Auger Lines

M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
867	854	(Al)
634	621	(Mg)

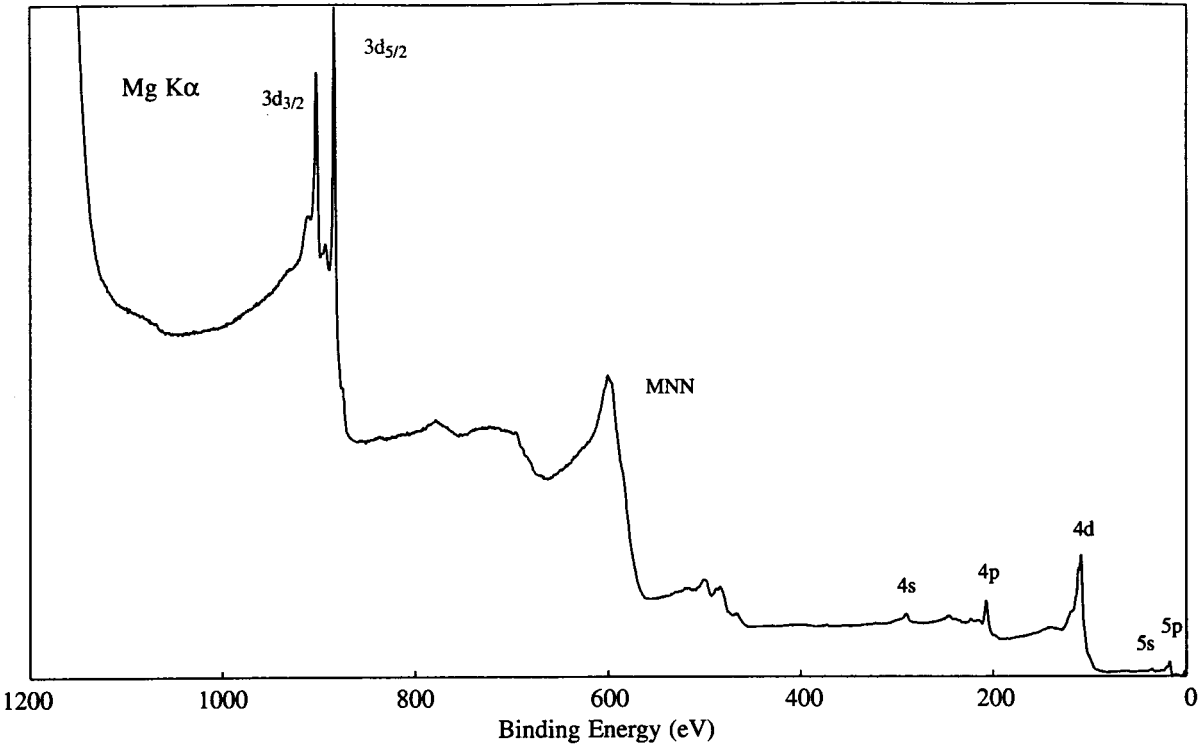


3d _{5/2} Binding Energy (eV)							
Compound Type	833	834	835	836	837	838	839
La							
LaH ₂							
La ₂ O ₃							

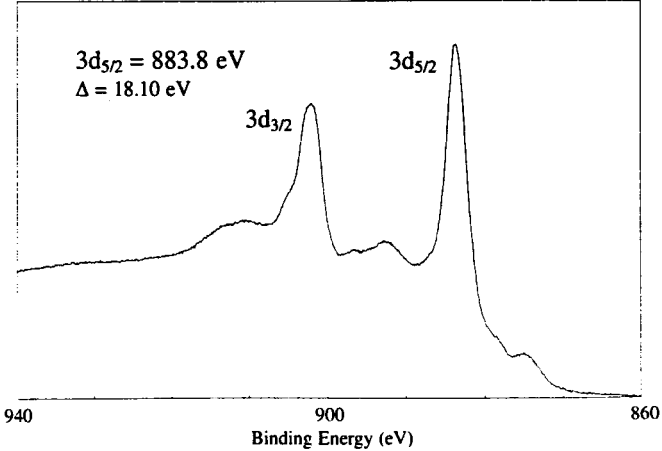


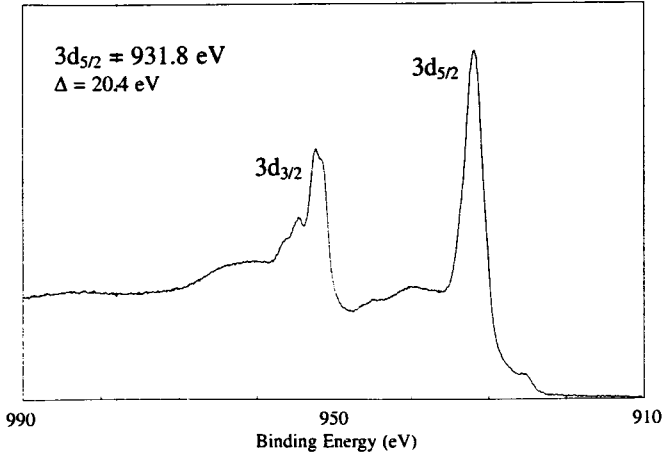
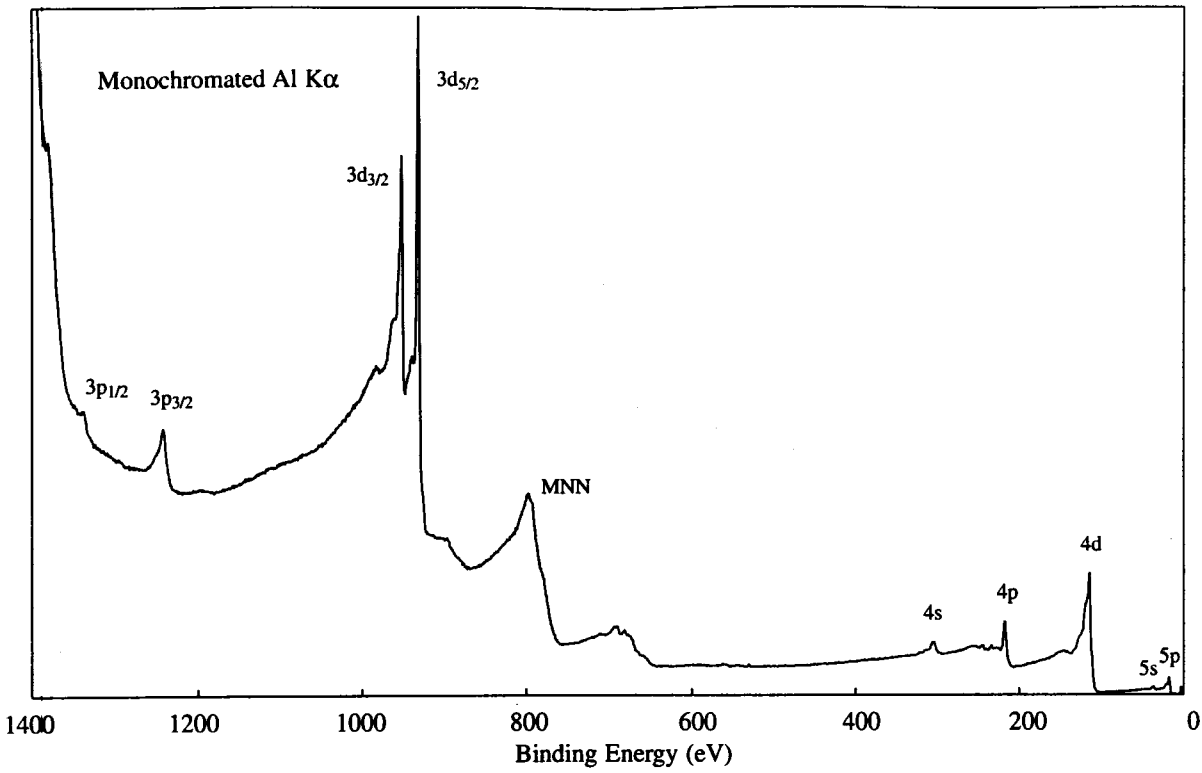


Line Positions (eV)						
Photoelectron Lines						
3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}			
1272	1184	902	884			
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s	5p
290	223	207	112	109	36	18
Auger Lines						
M ₄₅ N ₄₅ N ₄₅						
833 (Al)						
600 (Mg)						

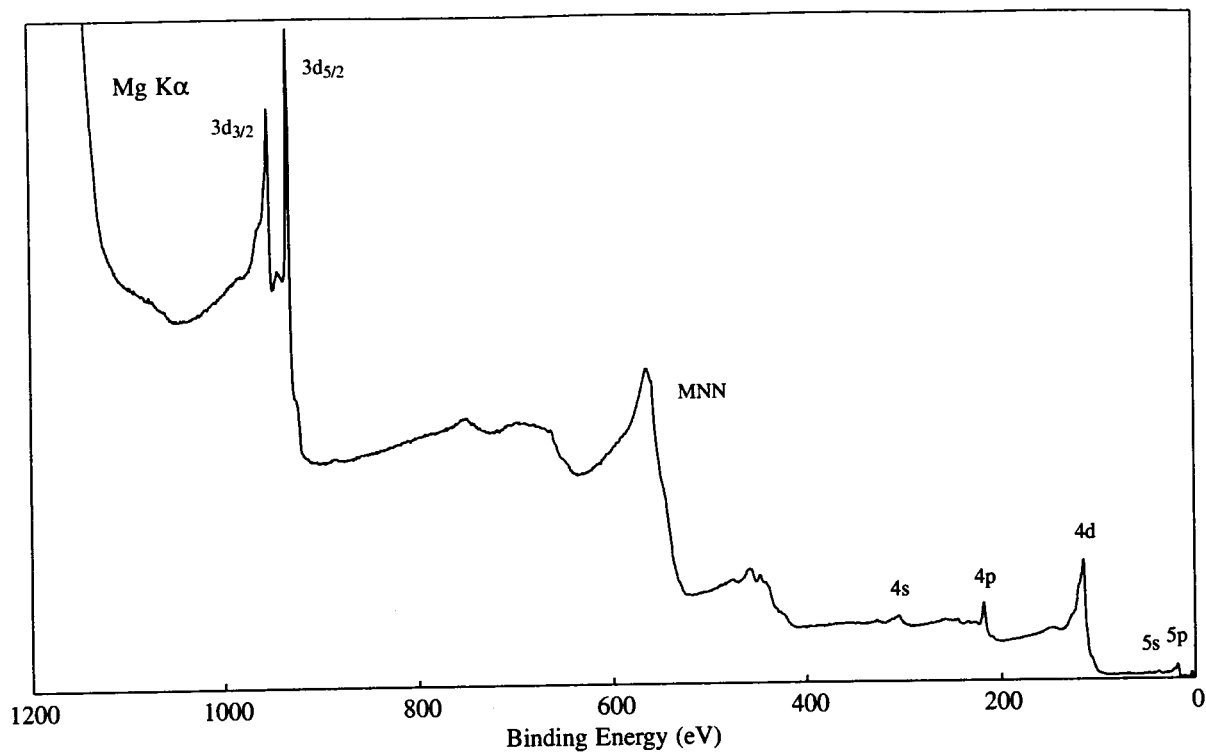


3d _{5/2} Binding Energy (eV)						
Compound Type	881	882	883	884	885	886
Ce						
CeAl ₂						
CePd ₃						
CeSe						
CeCu ₂ Si ₂						
CeO ₂						
CeH ₃						



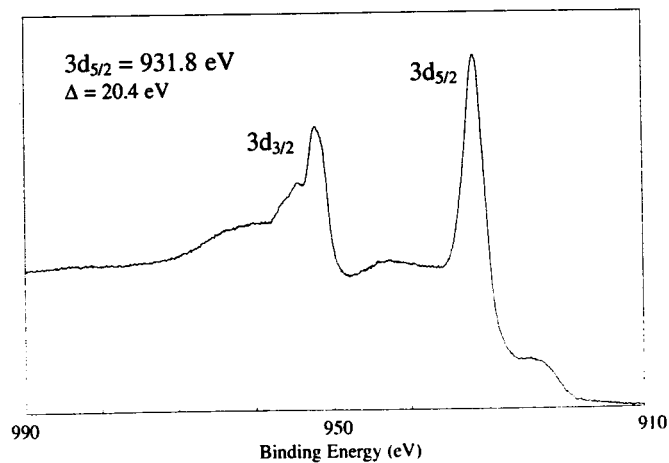


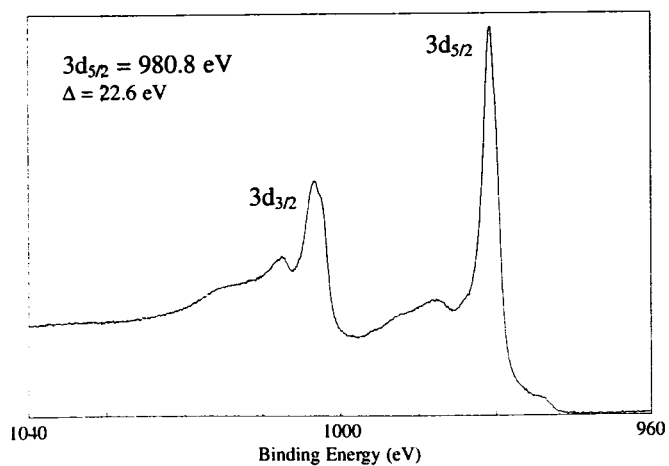
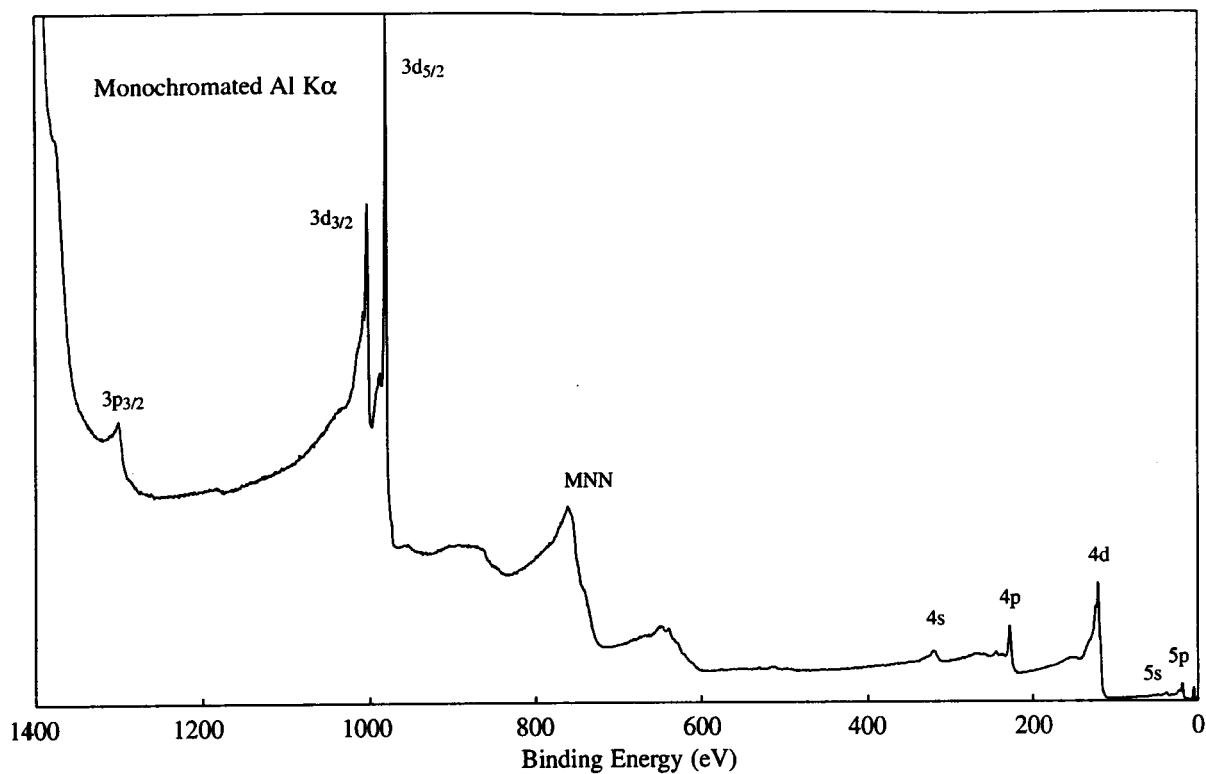
Line Positions (eV)					
Photoelectron Lines					
3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}		
1339	1242	952	932		
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
305	234	218	115	38	18
Auger Lines					
M ₄₅ N ₄₅ N ₄₅					
797 (Al)					
564 (Mg)					



3d $_{5/2}$ Binding Energy (eV)					
Compound Type	931	932	933	934	935
Pr		■			
Pr ₂ O ₃			■		
PrO ₂					■

4d Binding Energy (eV)			
Compound Type	115	116	117
Pr ₂ O ₃		■	
PrO ₂		■	





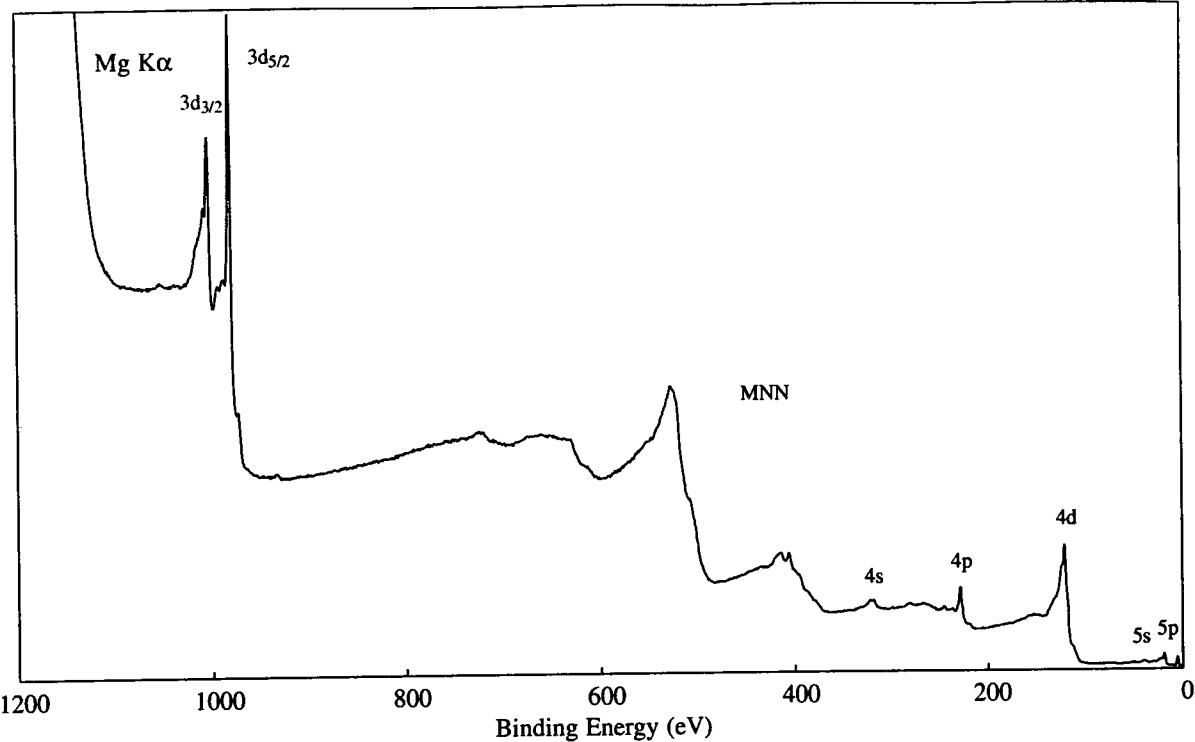
Line Positions (eV)

Photoelectron Lines

3p _{3/2}	3d _{3/2}	3d _{5/2}			
1301	1003	981			
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
320	245	228	121	39	19

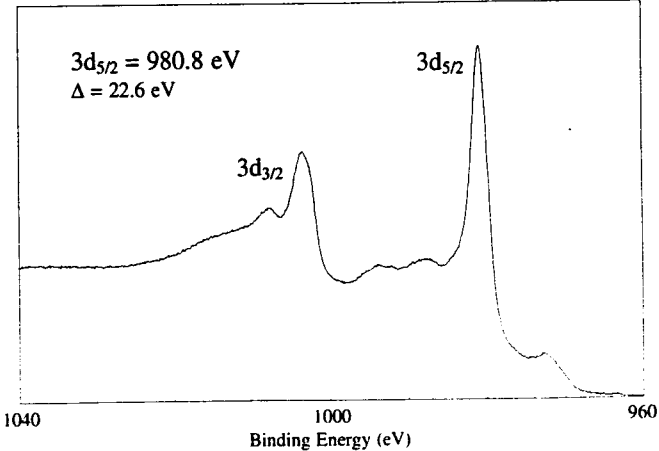
Auger Lines

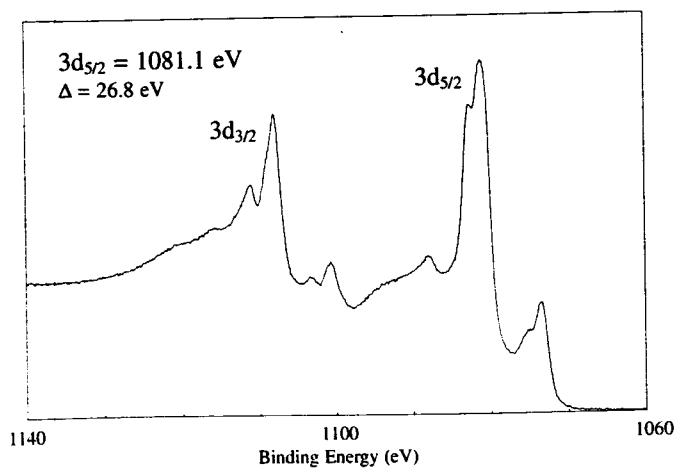
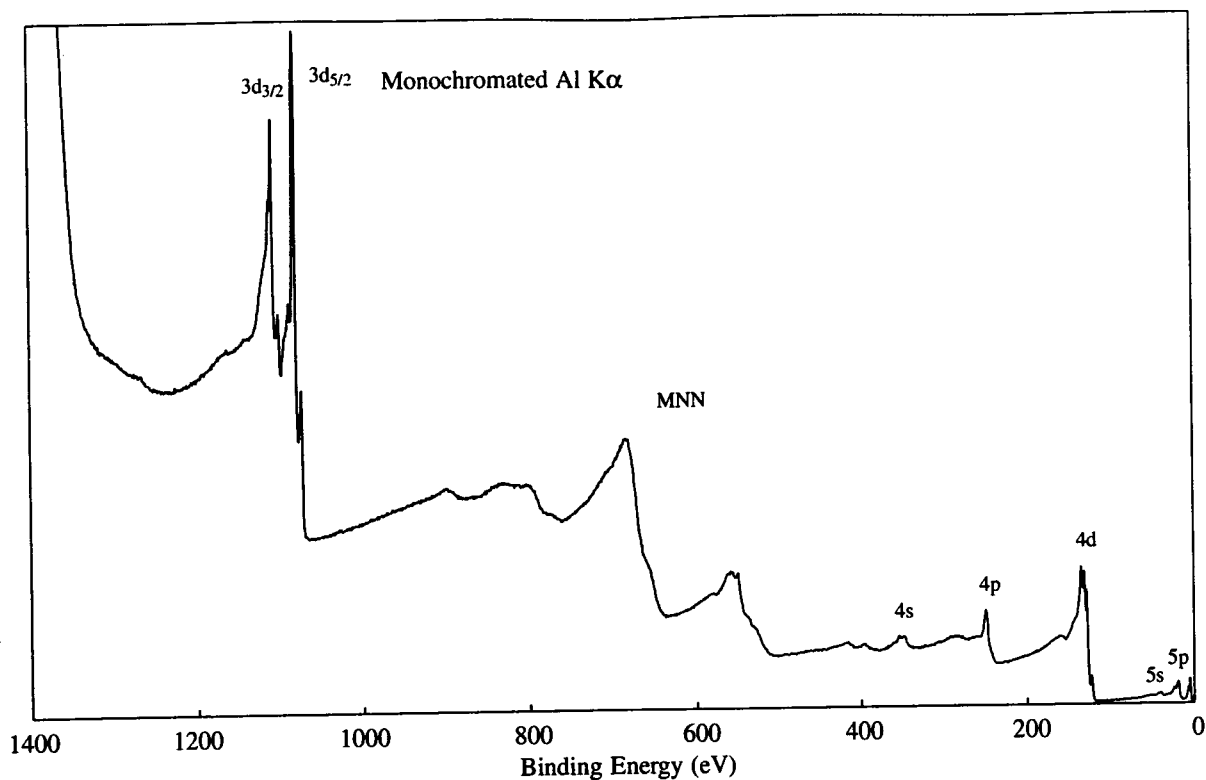
M ₄₅ N ₄₅ N ₄₅	
758	(Al)
525	(Mg)



3d _{5/2} Binding Energy (eV)			
Compound Type	980	981	982
Nd			
Nd ₂ O ₃			

4d Binding Energy (eV)			
Compound Type	119	120	121
Nd ₂ O ₃			





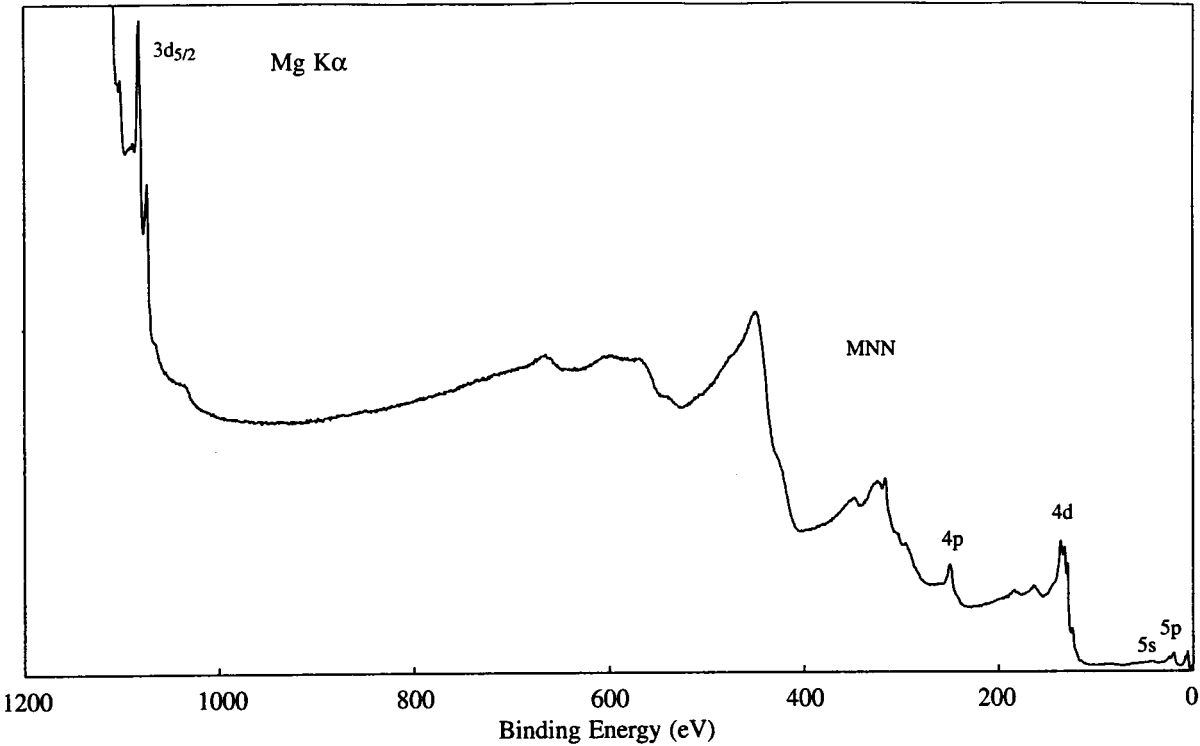
Line Positions (eV)

Photoelectron Lines

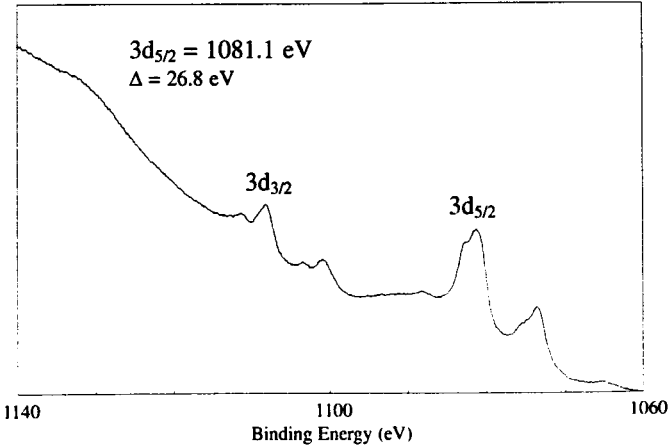
3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
1108	1081	349	283	250	129	41	19

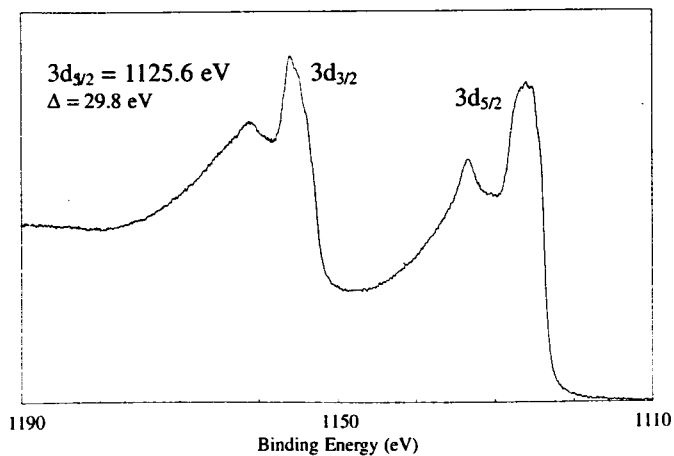
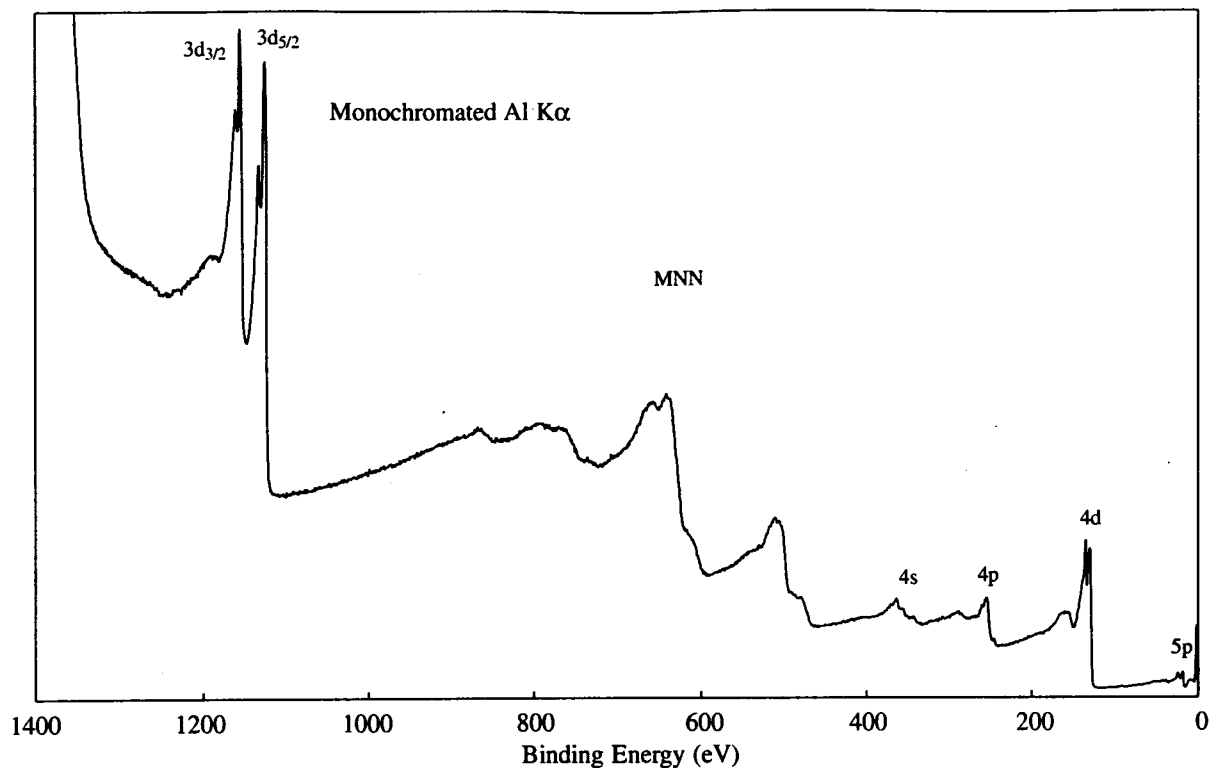
Auger Lines

M ₄₅ N ₄₅ N ₄₅	
682	(Al)
449	(Mg)

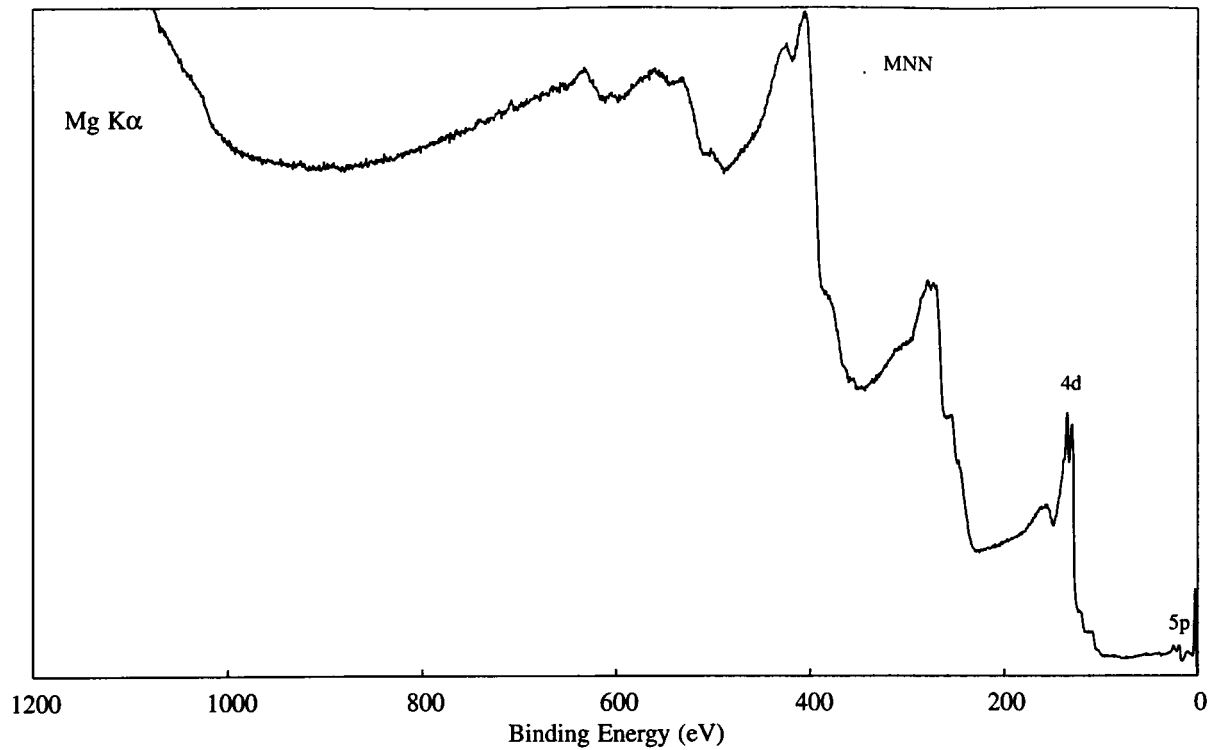


3d _{5/2} Binding Energy (eV)				
Compound Type	1081	1082	1083	1084
Sm				
Sm ₂ O ₃				



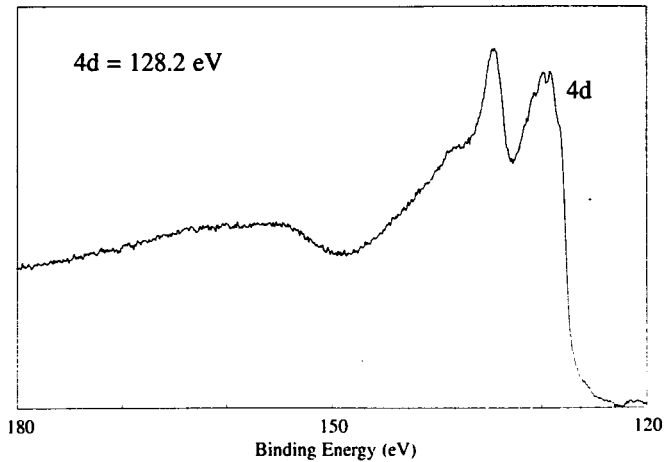


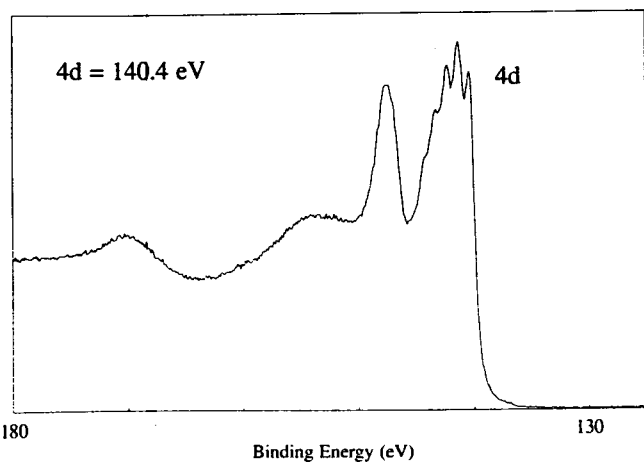
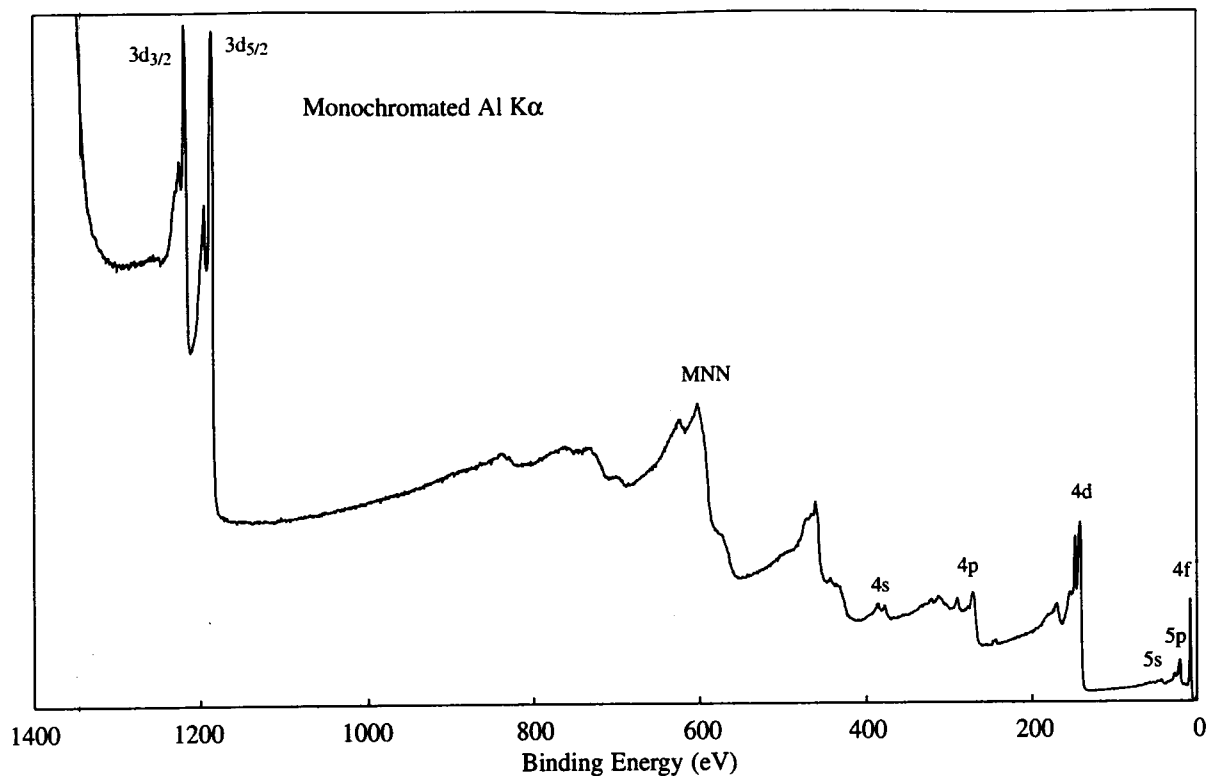
Line Positions (eV)							
Photoelectron Lines							
3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
1155	1126	363	289	255	128	39	19
Auger Lines							
M ₄₅ N ₄₅ N ₄₅							
637		(Al)					
404		(Mg)					



3d _{5/2} Binding Energy (eV)							
Compound Type	1123	1124	1125	1126	1127	1128	1129
E _u							

4d Binding Energy (eV)								
Compound Type	128	129	130	131	132	133	134	135
E _u								
E _{u2O3}								





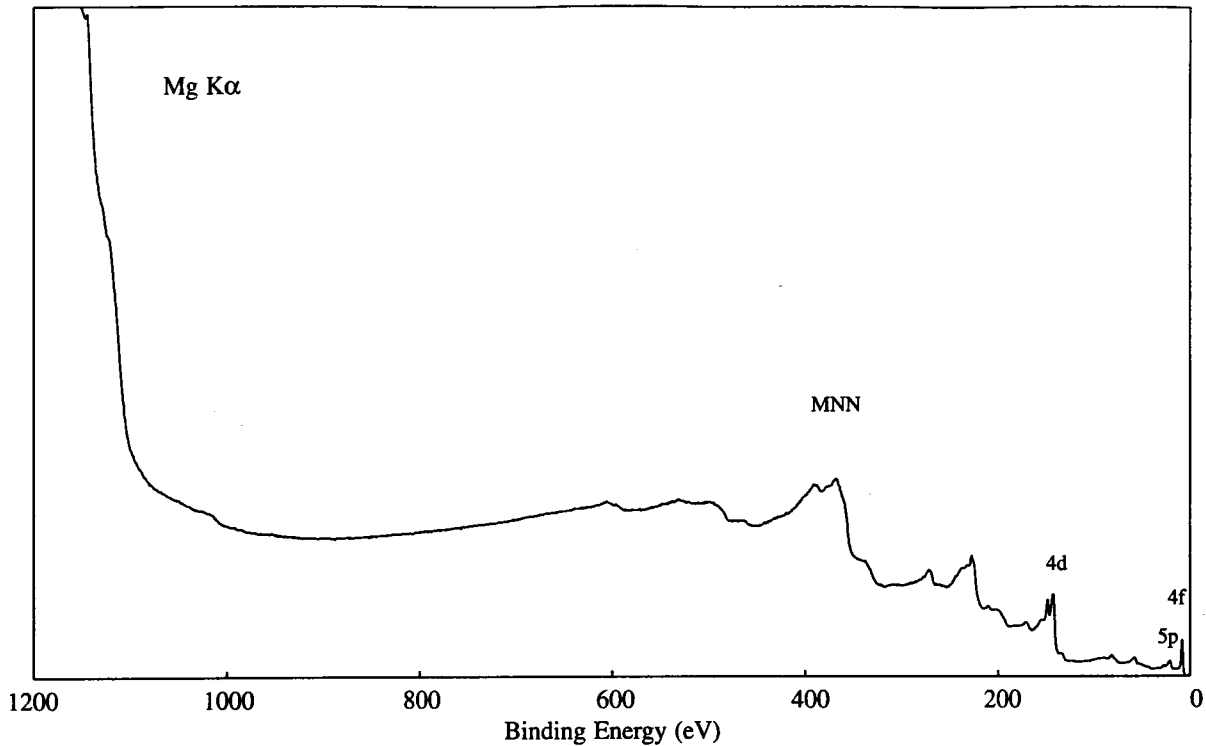
Line Positions (eV)

Photoelectron Lines

3d _{3/2}	3d _{5/2}					
1218	1186					
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p	4f
378	291	272	140	43	21	8

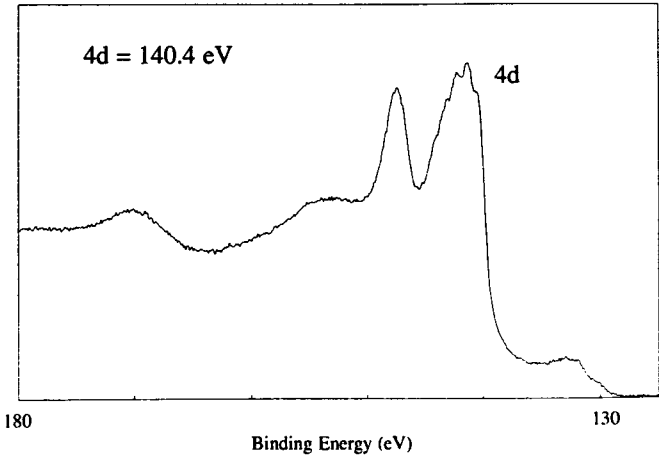
Auger Lines

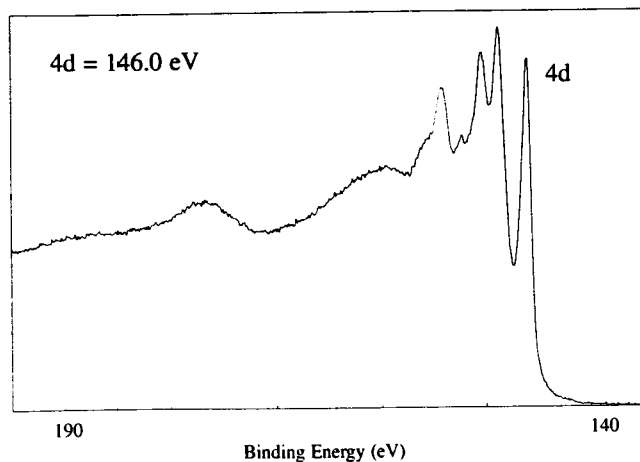
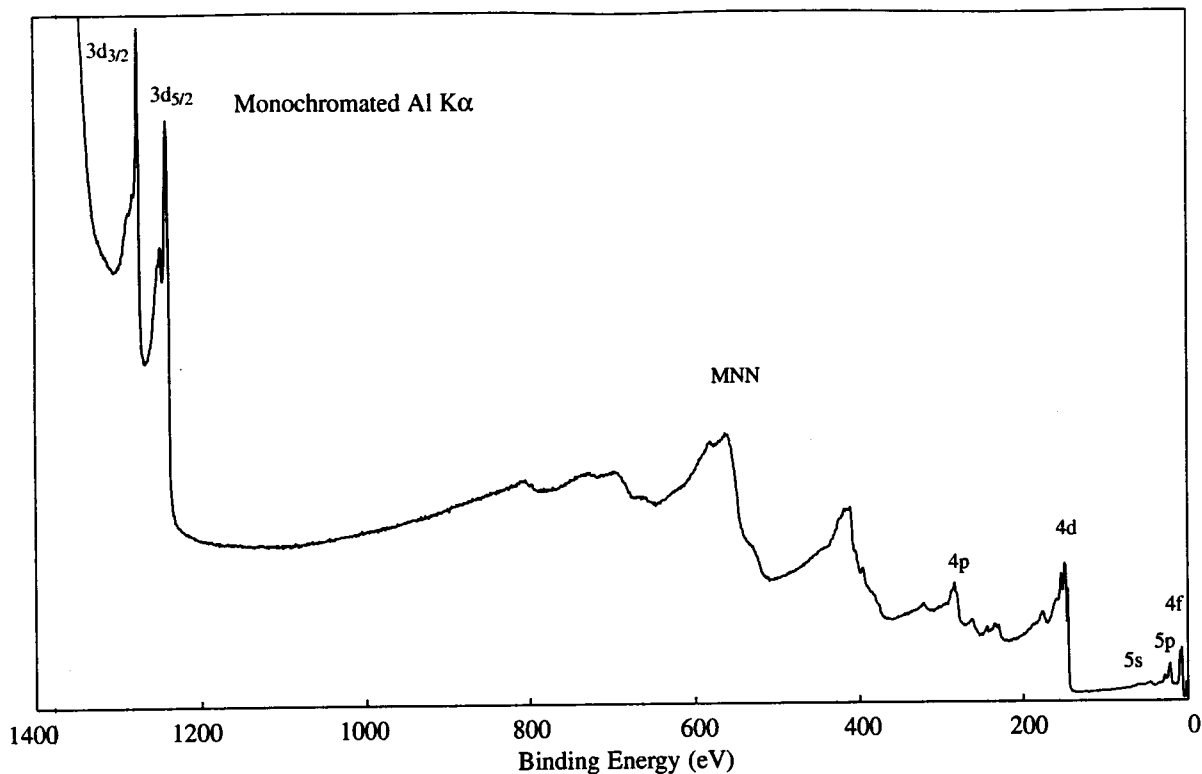
M ₄₅ N ₄₅ N ₄₅	
602	(Al)
369	(Mg)



4d Binding Energy (eV)					
Compound Type	140	141	142	143	144
Gd					
Gd ₂ O ₃					

3d _{5/2} Binding Energy (eV)		
Compound Type	1187	1188
Gd		
Gd ₂ O ₃		





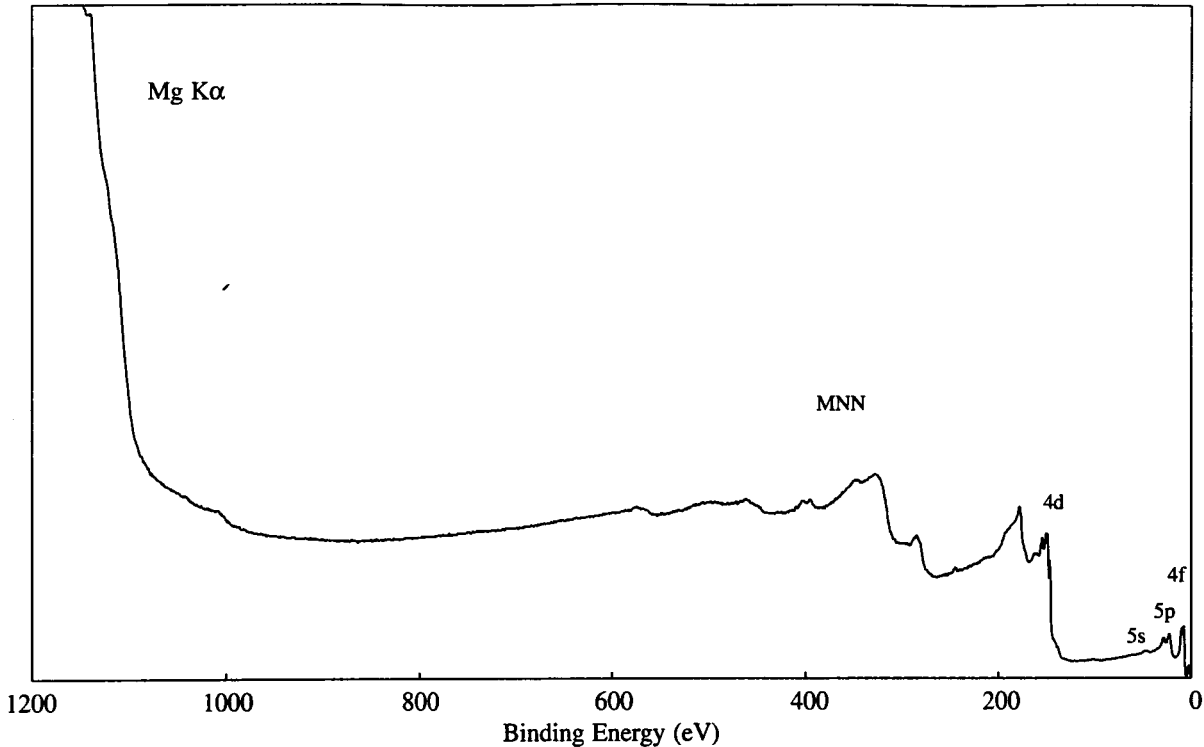
Line Positions (eV)

Photoelectron Lines

3d _{3/2}	3d _{5/2}					
1276	1241					
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p	4f
396	322	285	146	45	22	8

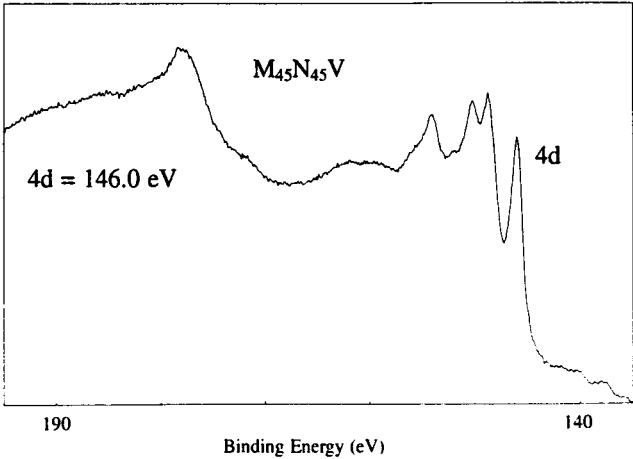
Auger Lines

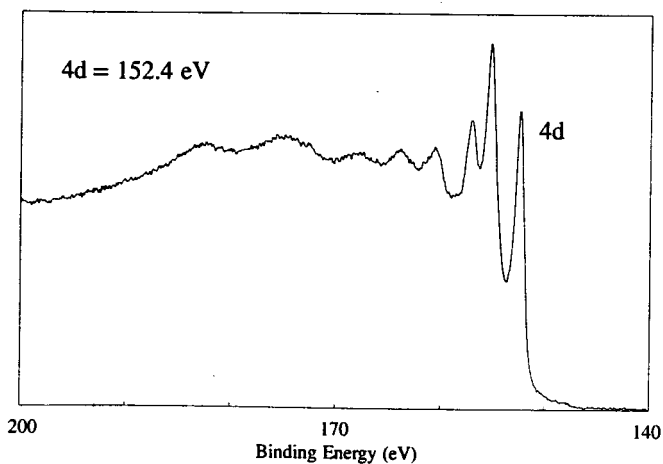
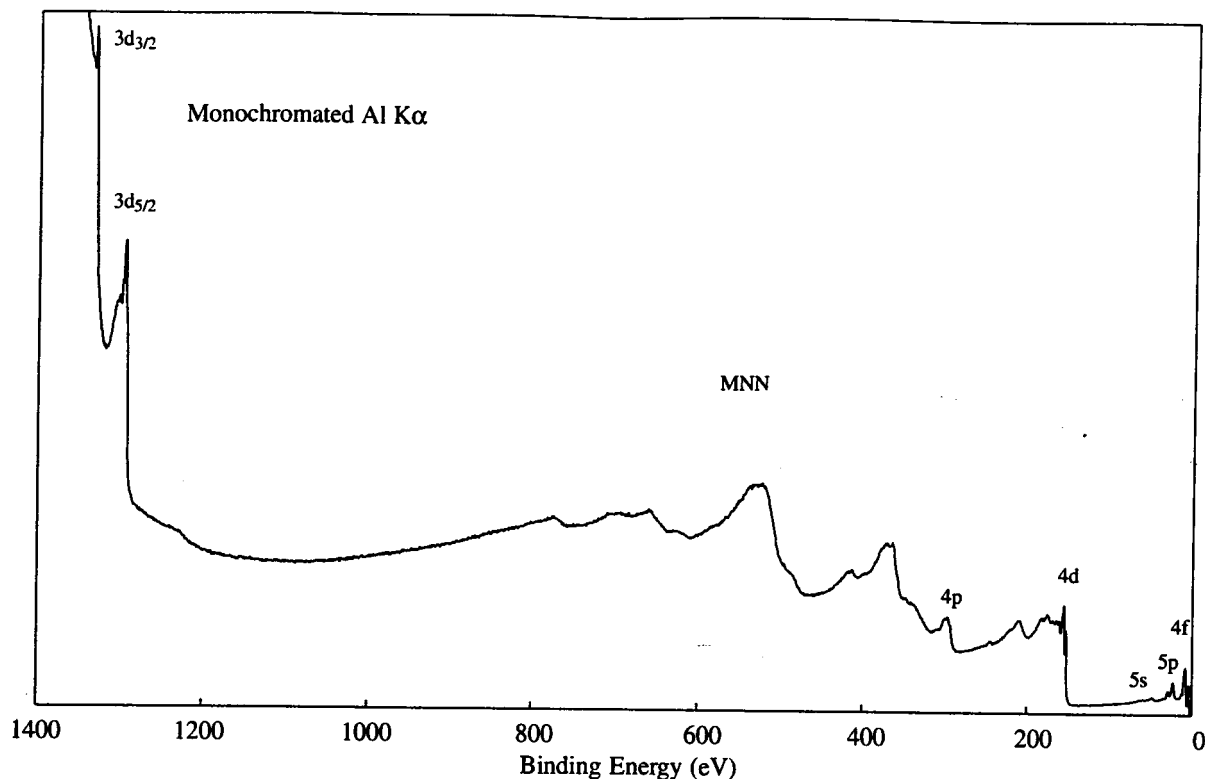
M ₄₅ N ₄₅ N ₄₅	M ₄₅ N ₄₅ V	M ₅ VV	M ₄ VV	(Al)
559	411	260	230	(Mg)
326	178			



4d Binding Energy (eV)					
Compound Type	145	146	147	148	149
Tb					
Tb ₂ O ₃					
TbO ₂					

3d _{5/2} Binding Energy (eV)			
Compound Type	1240	1241	1242
Tb			
Tb ₂ O ₃			
TbO ₂			





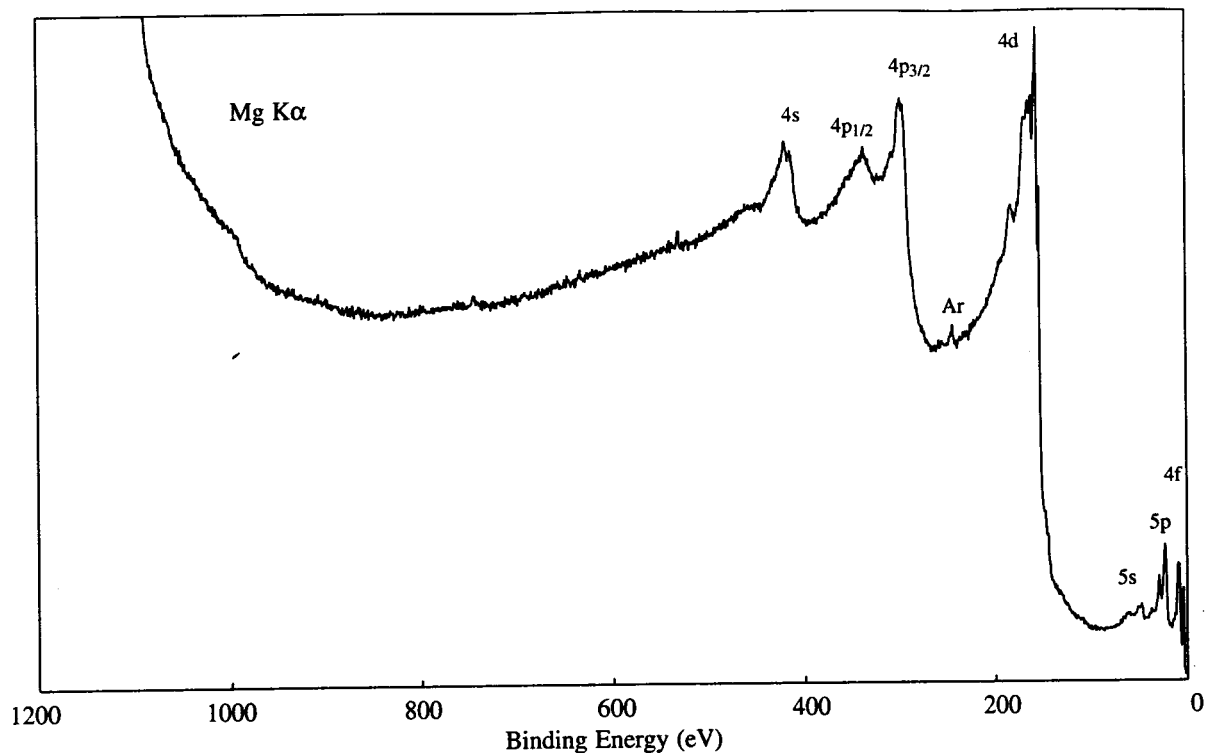
Line Positions (eV)

Photoelectron Lines

3d _{3/2}	3d _{5/2}					
1333	1296					
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p	4f
417	337	297	152	48	23	8

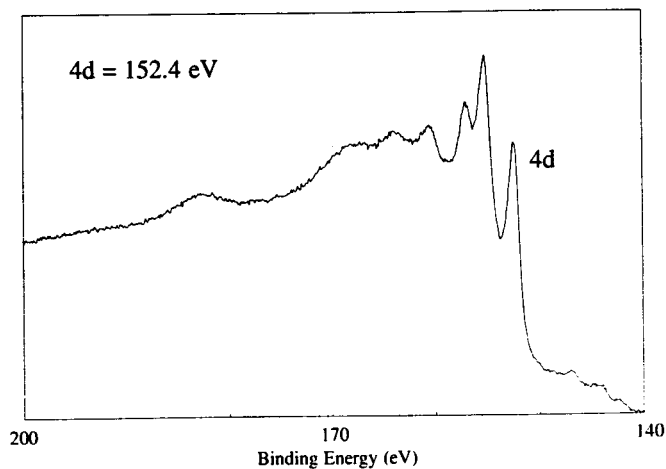
Auger Lines

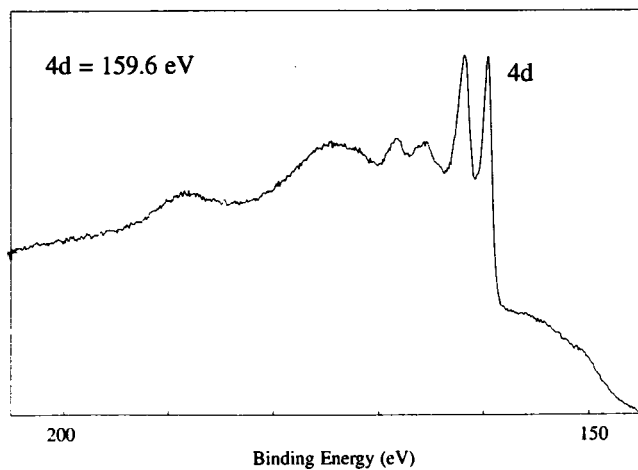
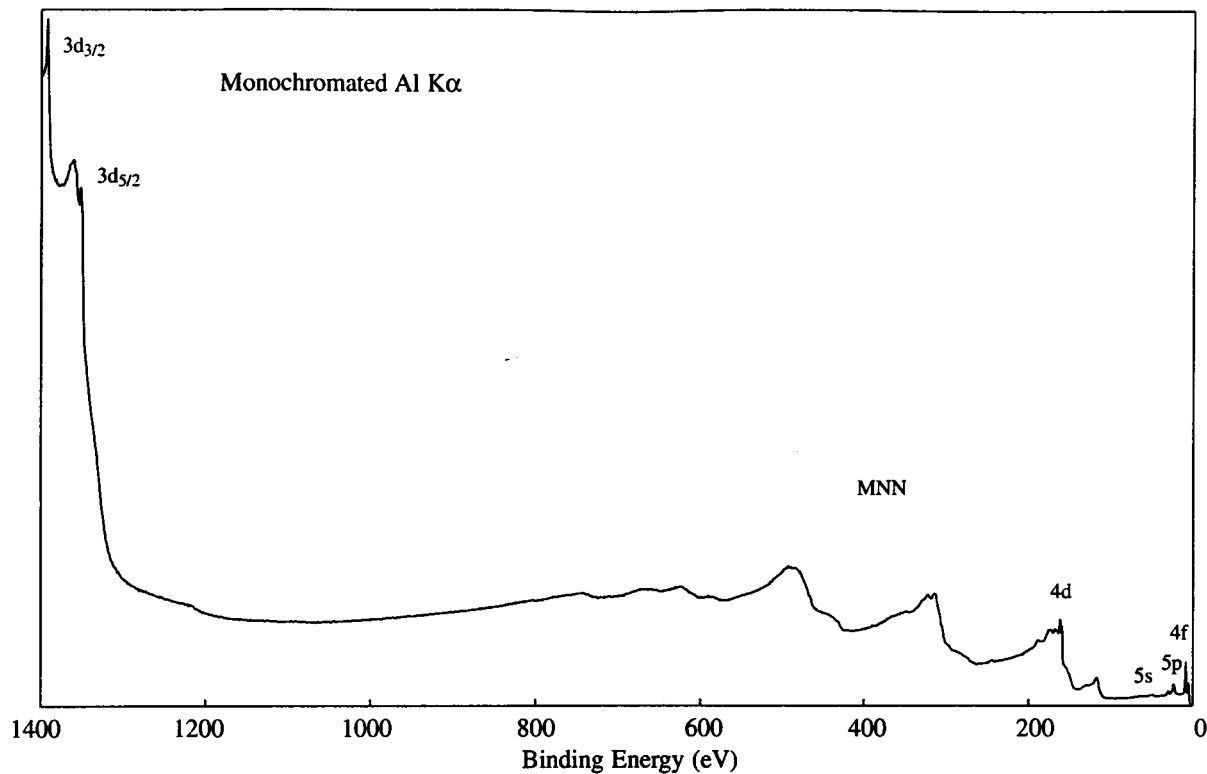
M ₄₅ N ₄₅ N ₄₅	M ₄₅ N ₄₅ V	
526	368	(Al)



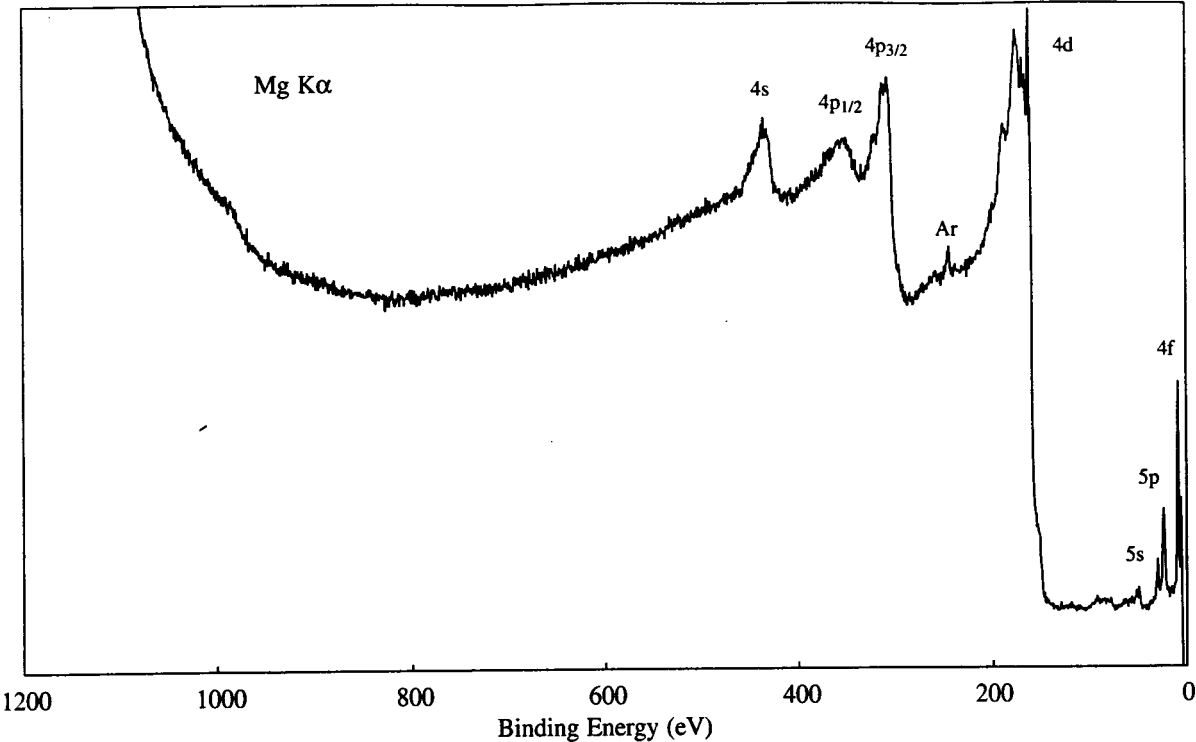
4d Binding Energy (eV)					
Compound Type	152	156	160	164	168
Dy	■				
Dy ₂ O ₃					■

3d _{5/2} Binding Energy (eV)					
Compound Type	1287	1289	1291	1293	1295
Dy					■
Dy ₂ O ₃		■			

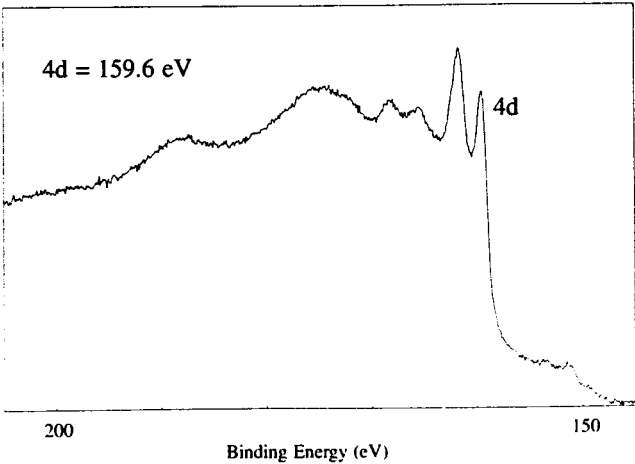


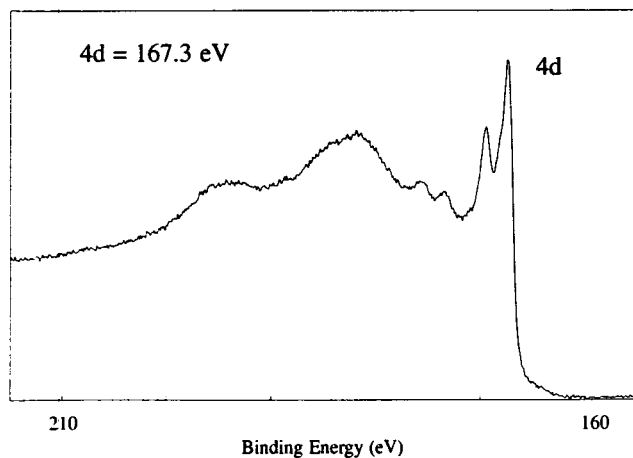
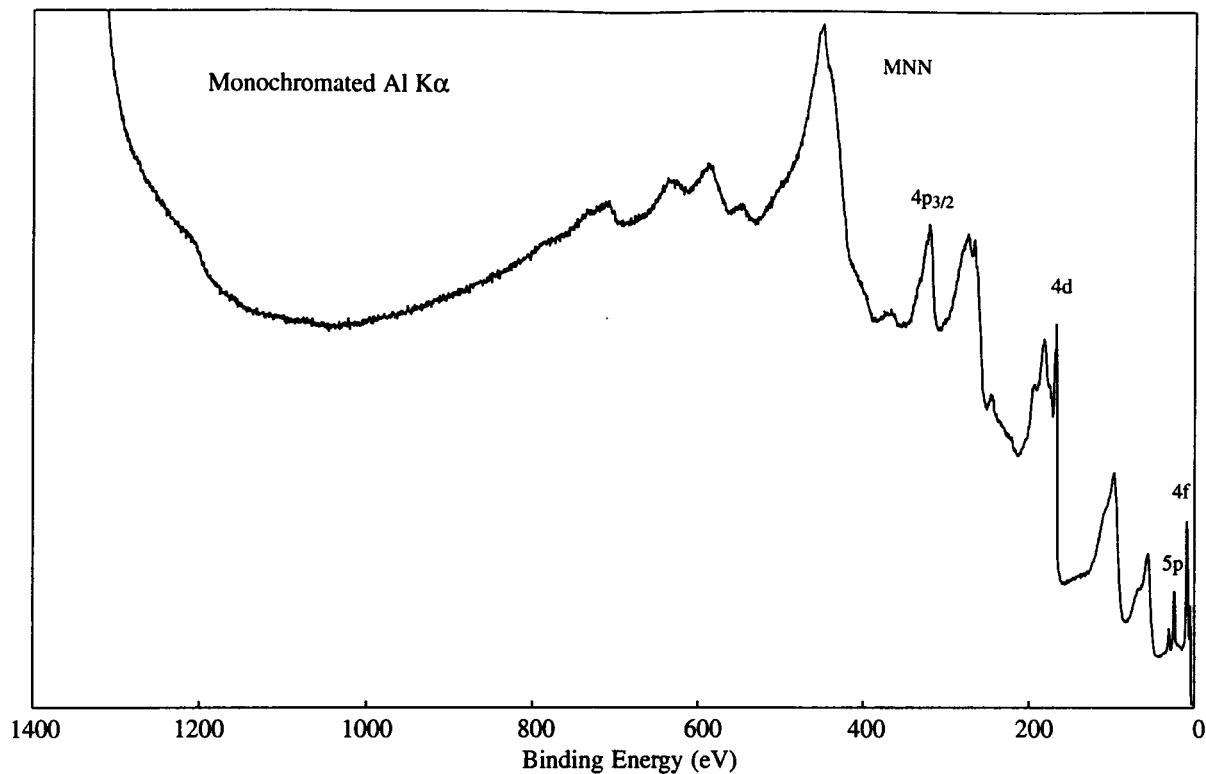


Line Positions (eV)					
Photoelectron Lines					
3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d
1393	1352	435	353	309	160
5s	5p _{1/2}	5p _{3/2}	4f		
49	30	24	9		
Auger Lines					
M ₄₅ N ₄₅ N ₄₅		M ₄₅ N ₄₅ V		M ₄ VV	
488		314		117 (Al)	

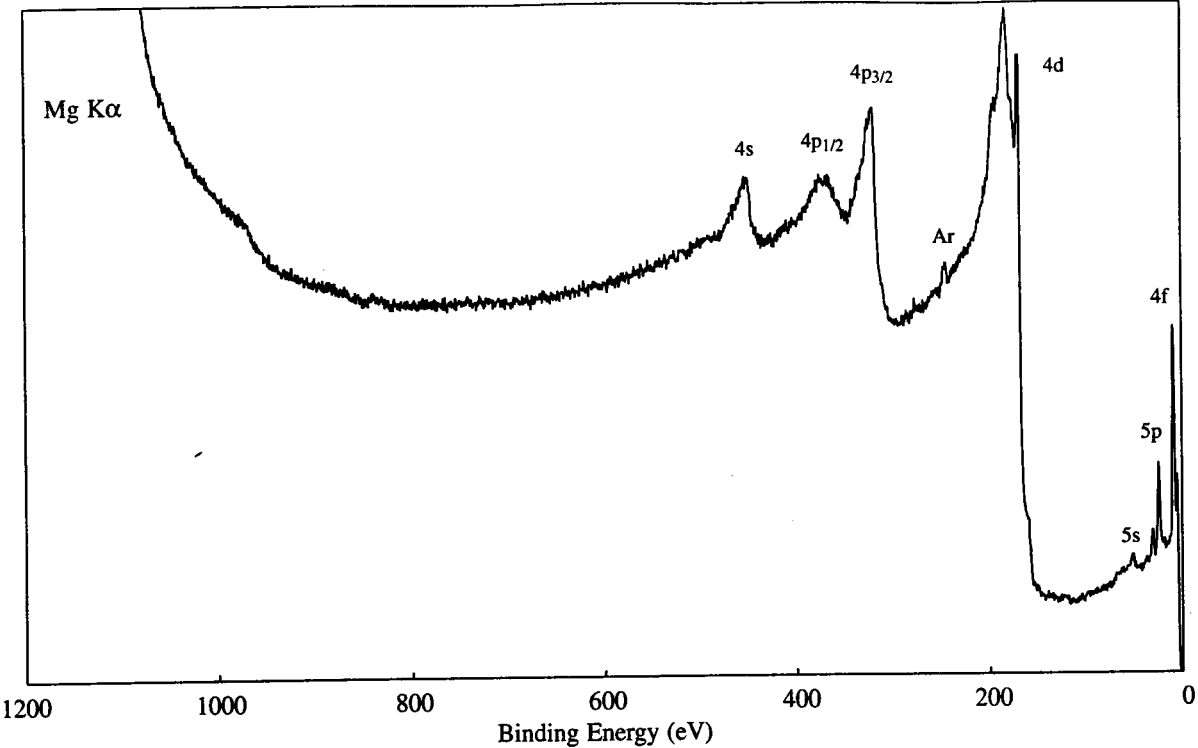


4d Binding Energy (eV)			
Compound Type	158	159	160
Ho			

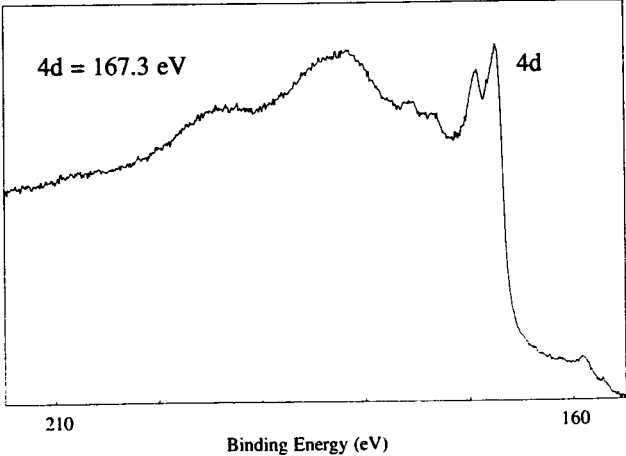


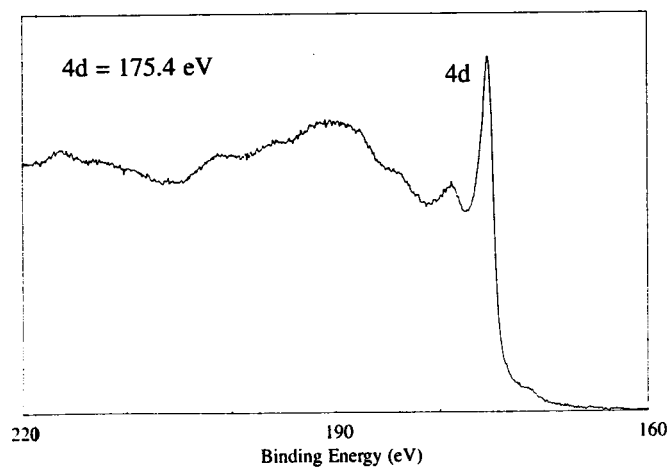
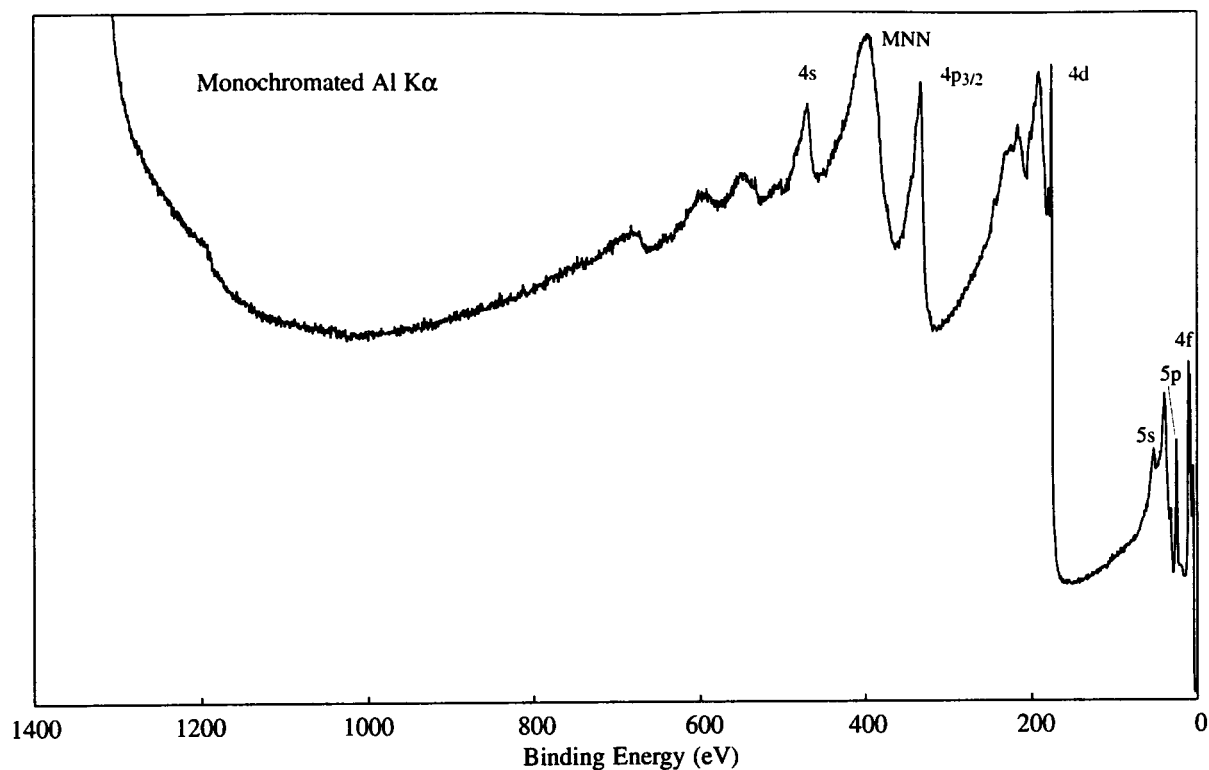


Line Positions (eV)								
Photoelectron Lines								
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p _{1/2}	5p _{3/2}	4f	
451	368	321	167	52	31	24	9	
Auger Lines								
M ₄₅ N ₄₅ N ₄₅	M ₄₅ N ₄₅ V	M ₅ VV	M ₄ VV					
440	273	98	56	(Al)				

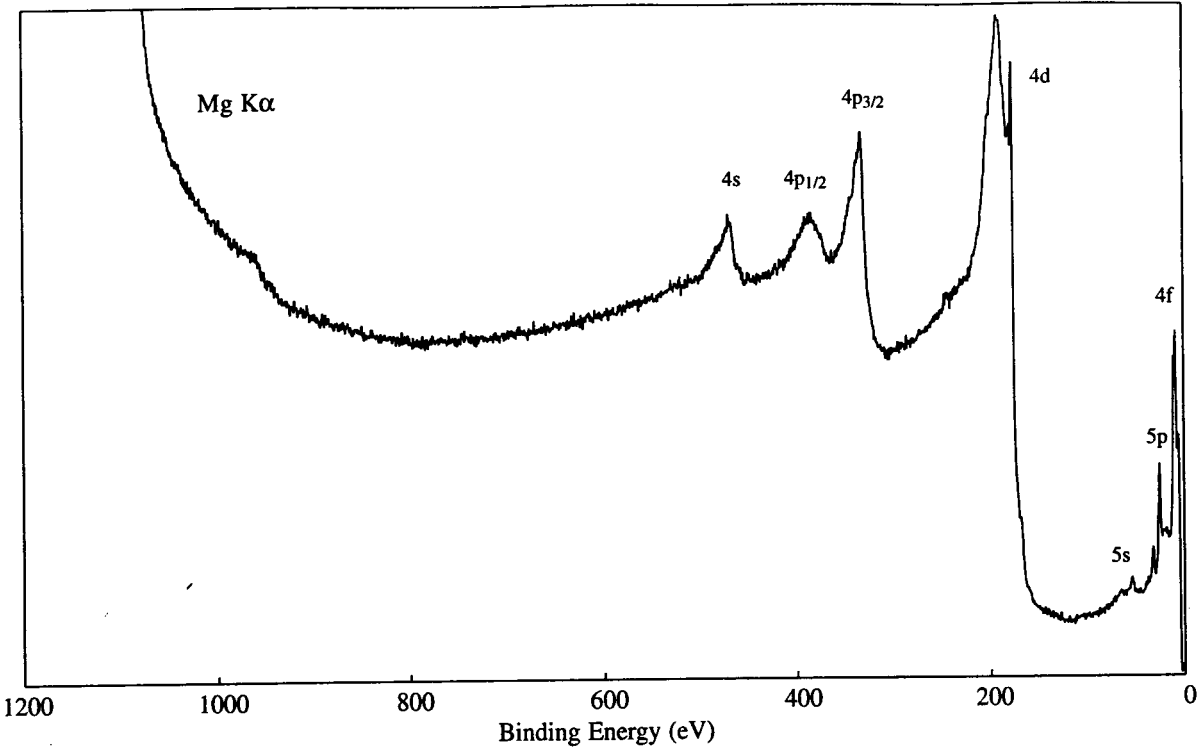


4d Binding Energy (eV)			
Compound Type	167	168	169
Er	■		
Er			■
Er ₂ O ₃		■	

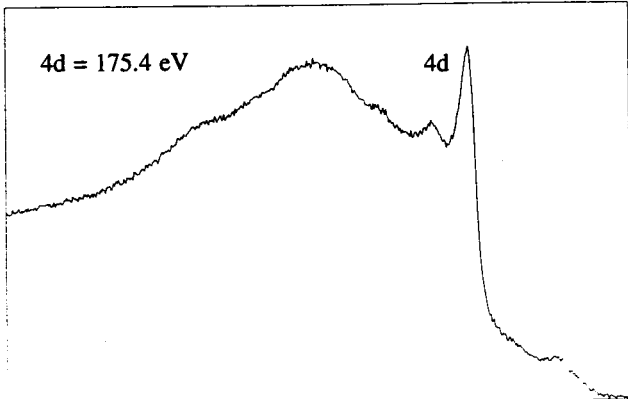


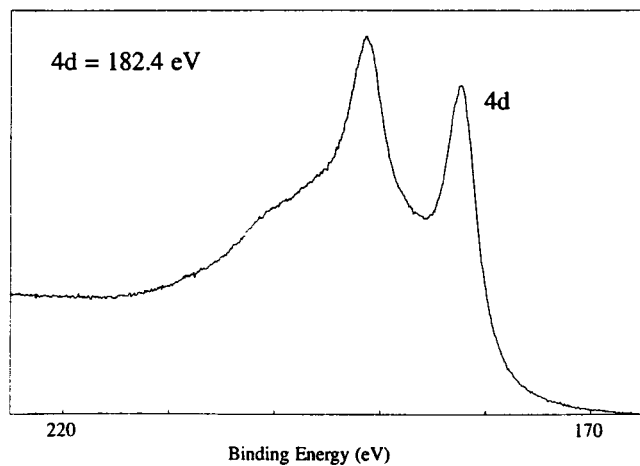
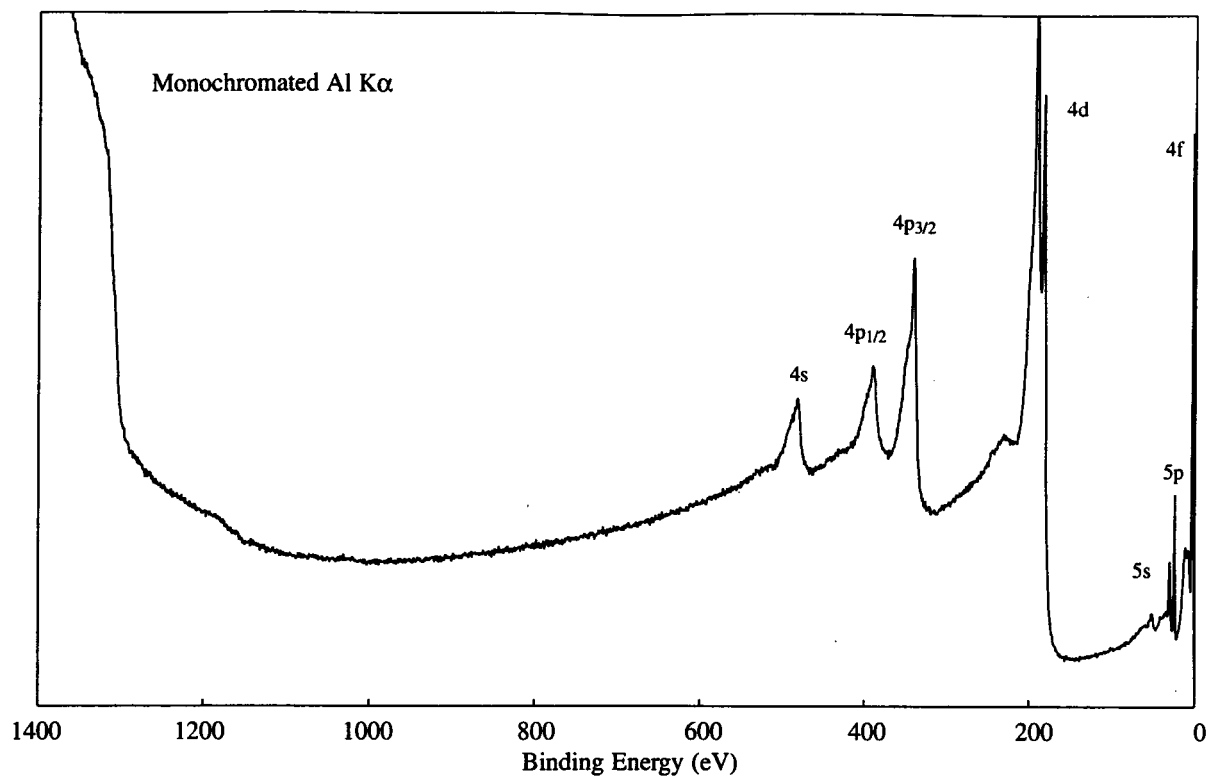


Line Positions (eV)							
Photoelectron Lines							
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p _{1/2}	5p _{3/2}	4f
470	384	333	175	53	32	25	8
Auger Lines							
M ₄₅ N ₄₅ N ₄₅							
398 (Al)							



4d Binding Energy (eV)			
Compound Type	174	175	176
Tm			

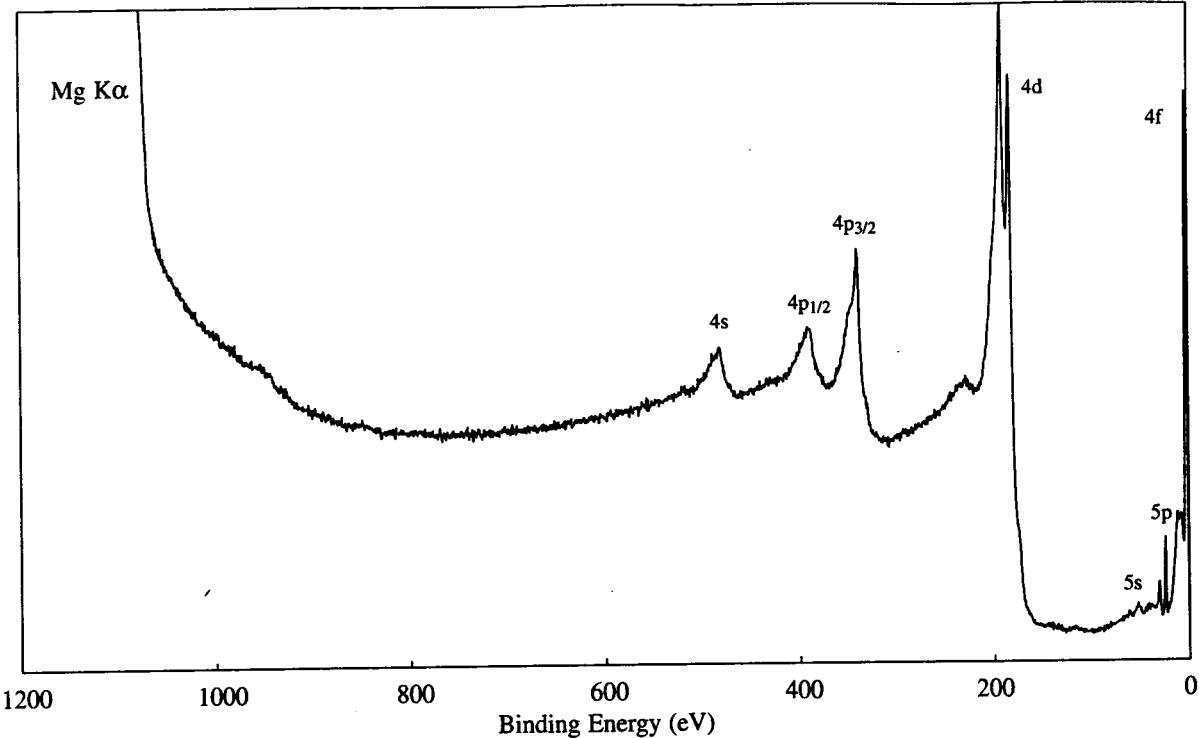




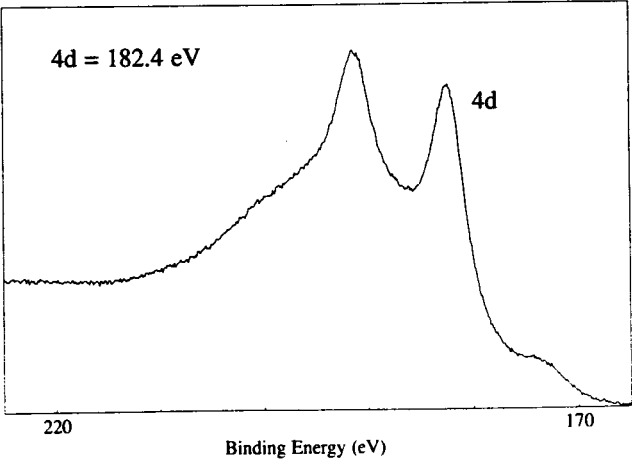
Line Positions (eV)

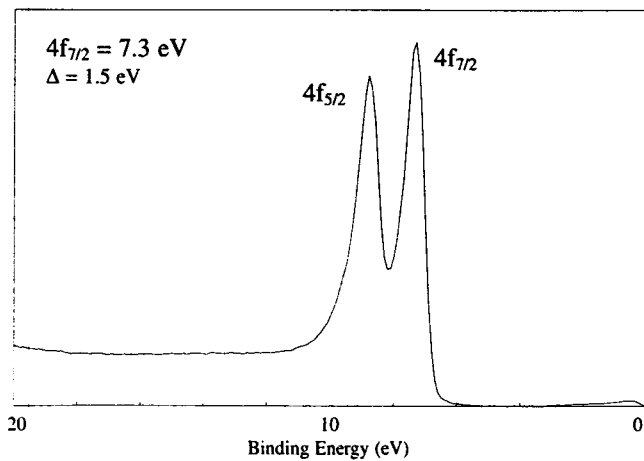
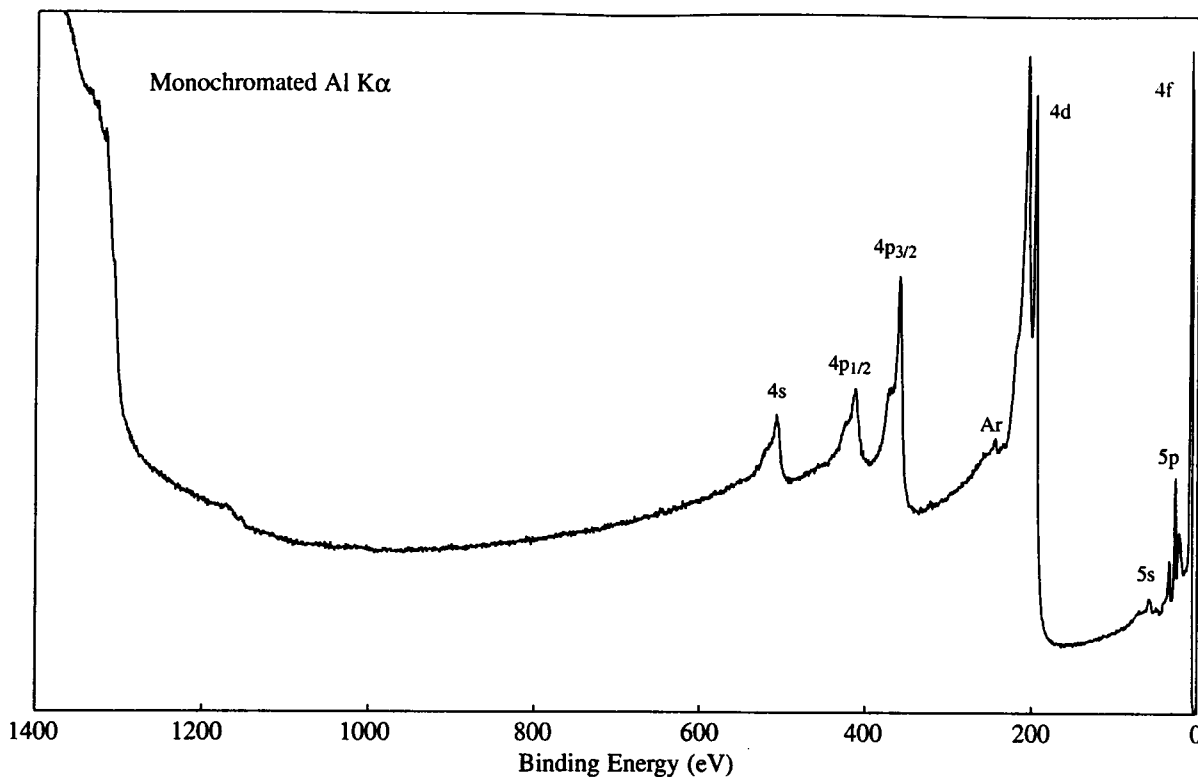
Photoelectron Lines

4s	4p _{1/2}	4p _{3/2}	4d	5s	5p _{1/2}	5p _{3/2}	4f
482	389	341	182	51	30	24	3



4d Binding Energy (eV)						
Compound Type	181	182	183	184	185	186
Yb						
Yb ₂ O ₃						

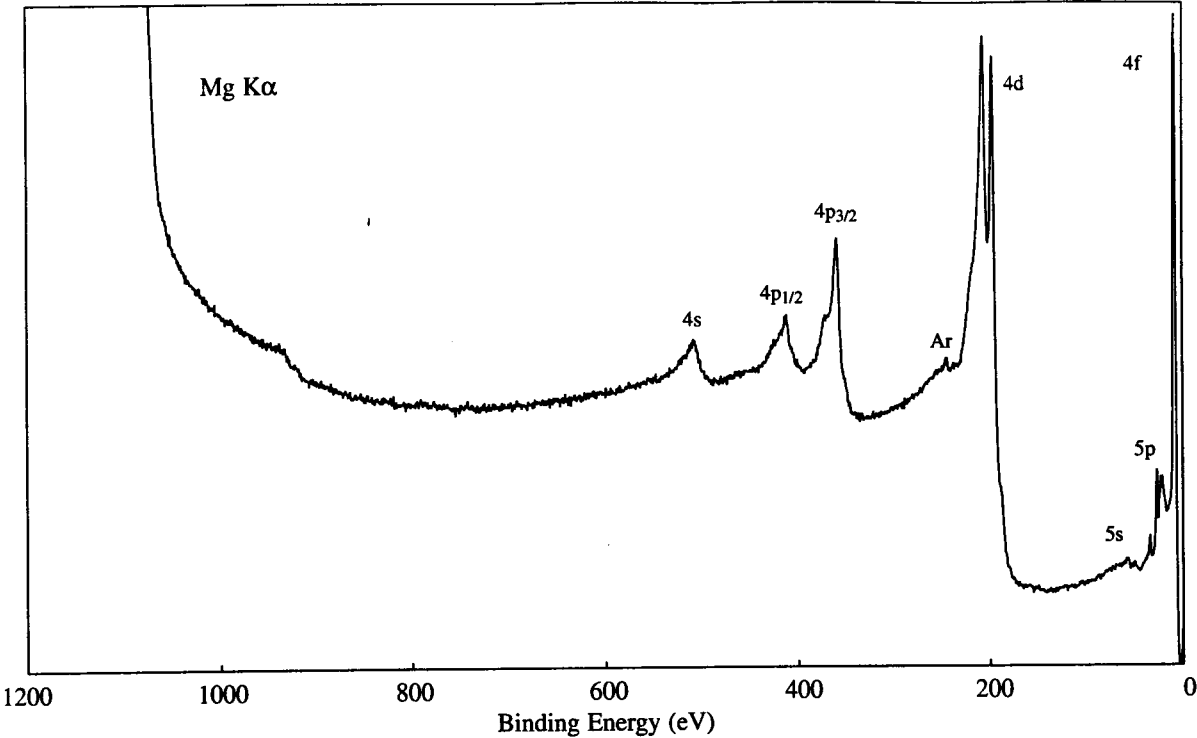




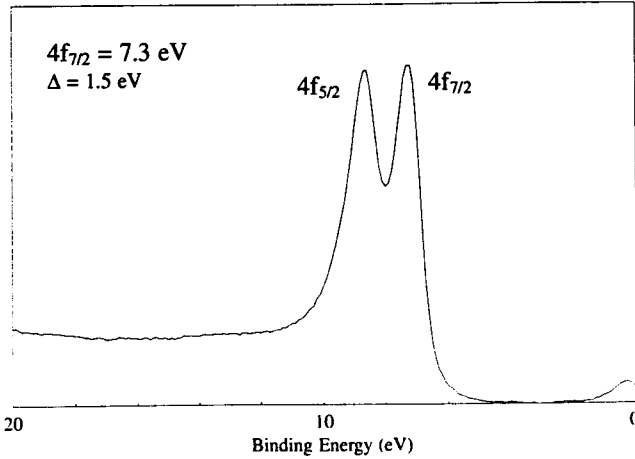
Line Positions (eV)

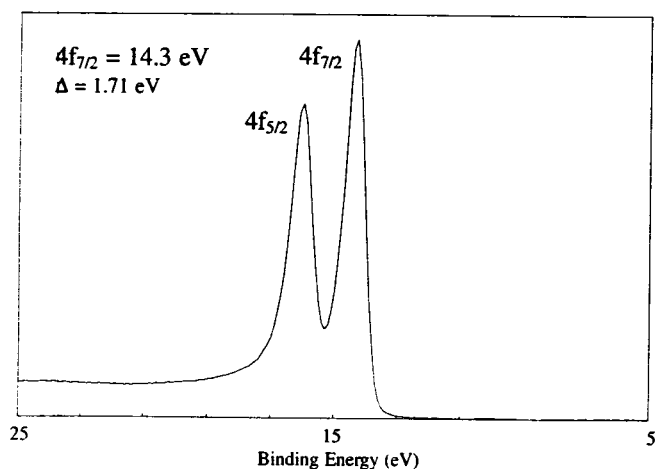
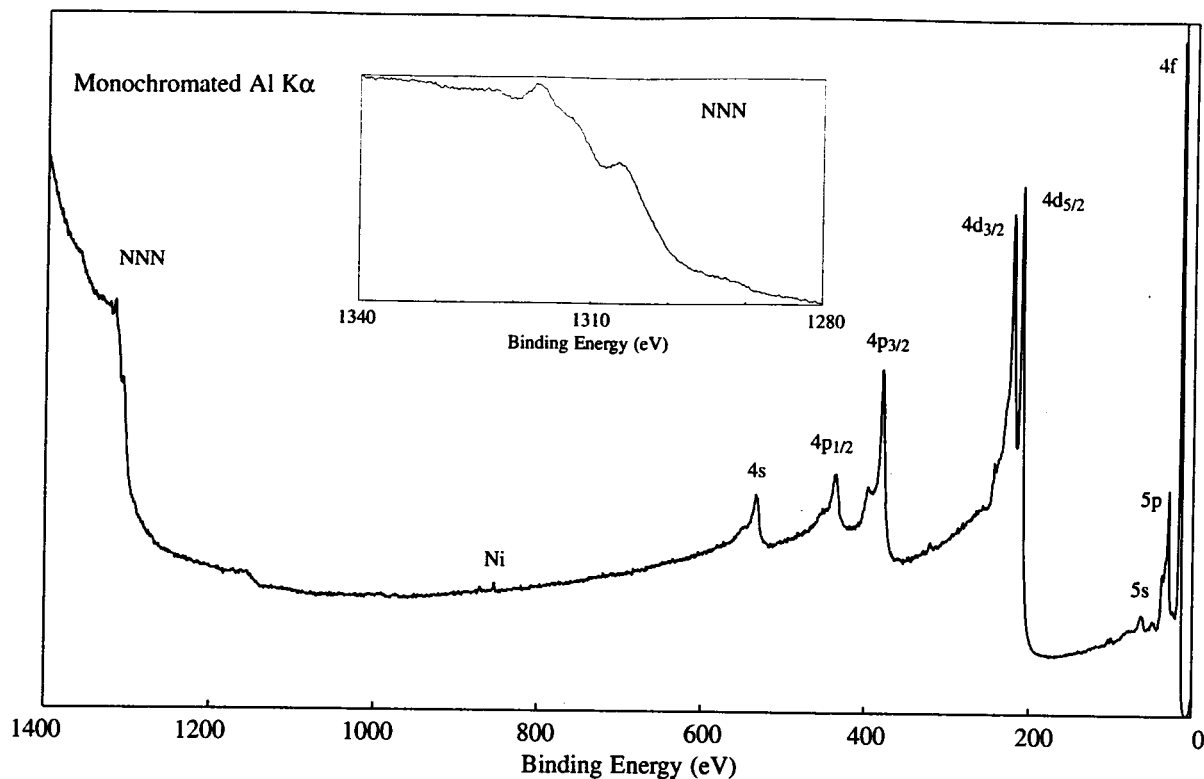
Photoelectron Lines

4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
509	413	360	206	196
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
57	34	27	9	7

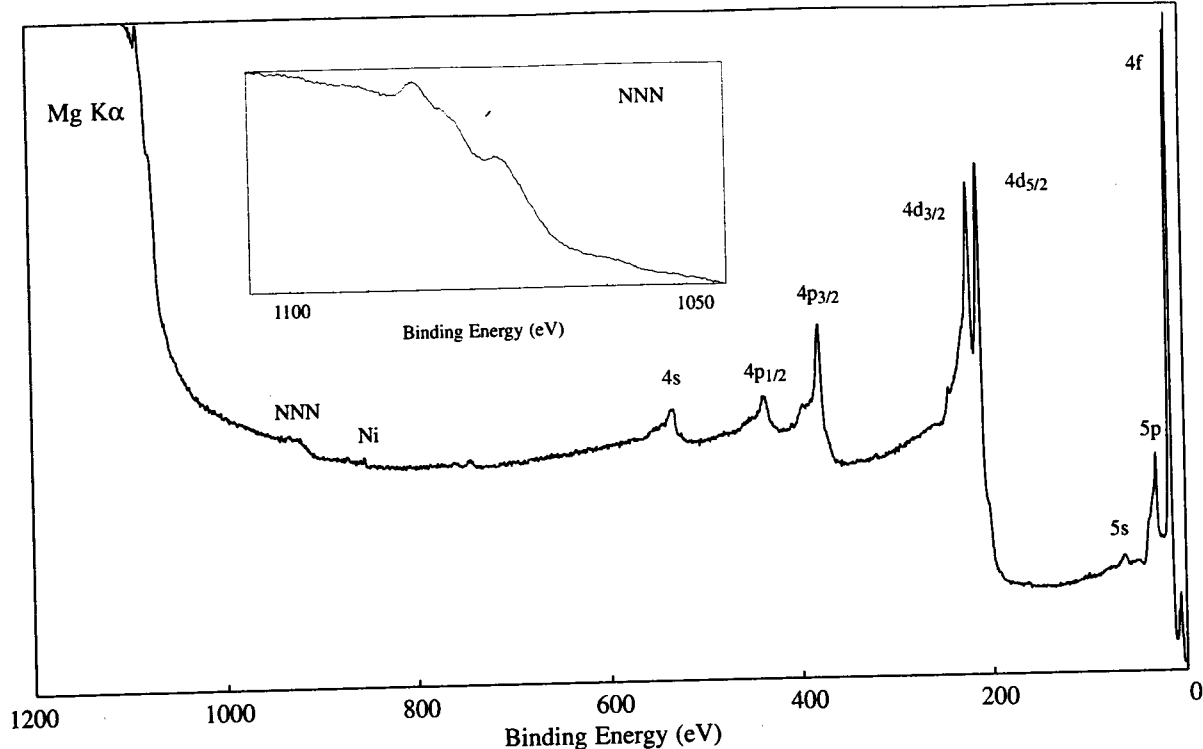


4f _{7/2} Binding Energy (eV)					
Compound Type	5	6	7	8	9
Lu					



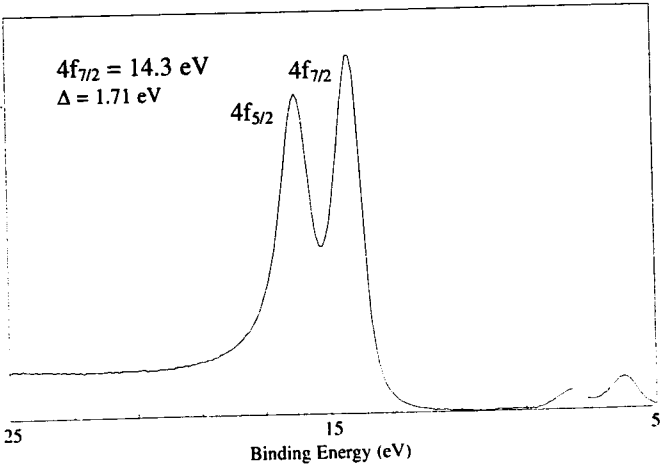


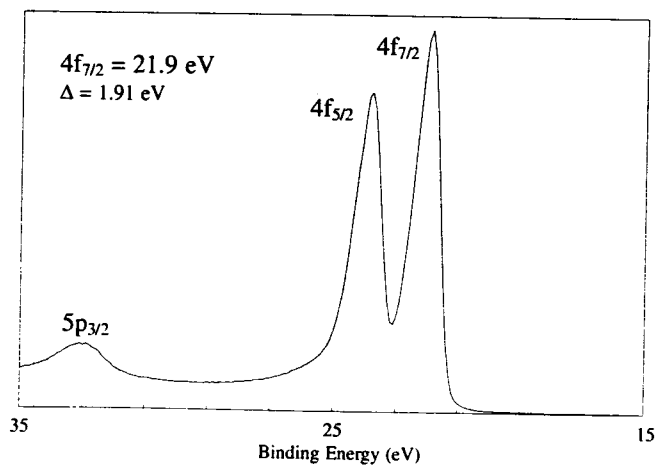
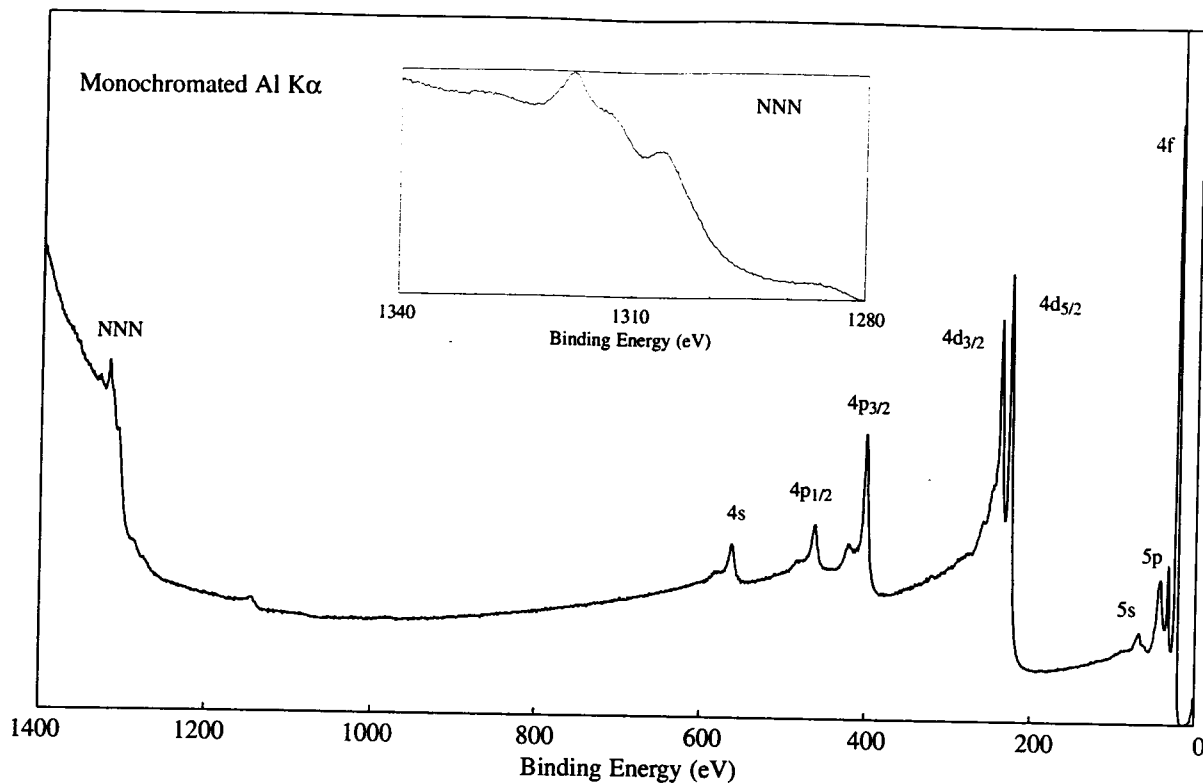
Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
534	437	380	222	211
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
63	38	30	16	14
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1317		1306		(Al)
1084		1073		(Mg)



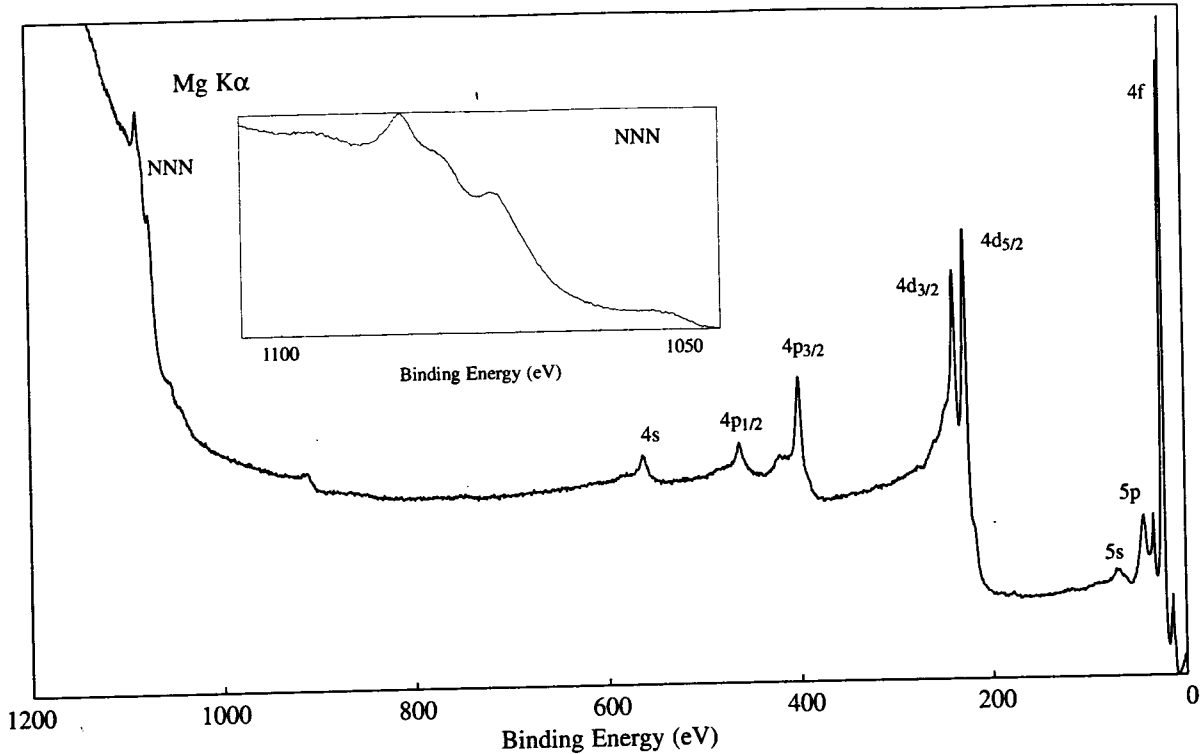
4f _{7/2} Binding Energy (eV)			
Compound Type	14	15	16
Hf			
HfO ₂			

4d _{5/2} Binding Energy (eV)			
Compound Type	212	213	214
Hf			
HfO ₂			

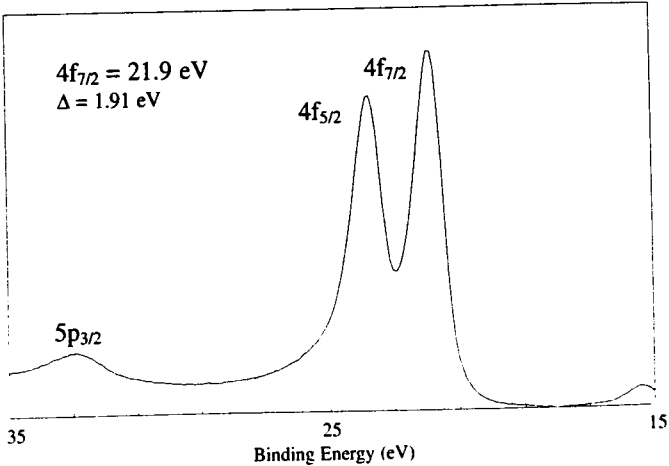


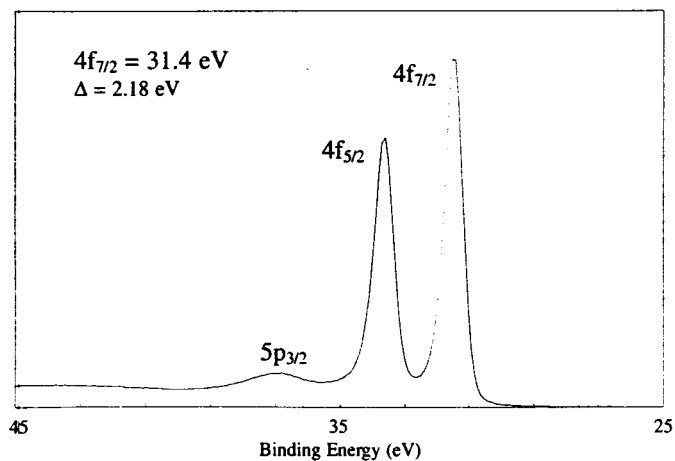
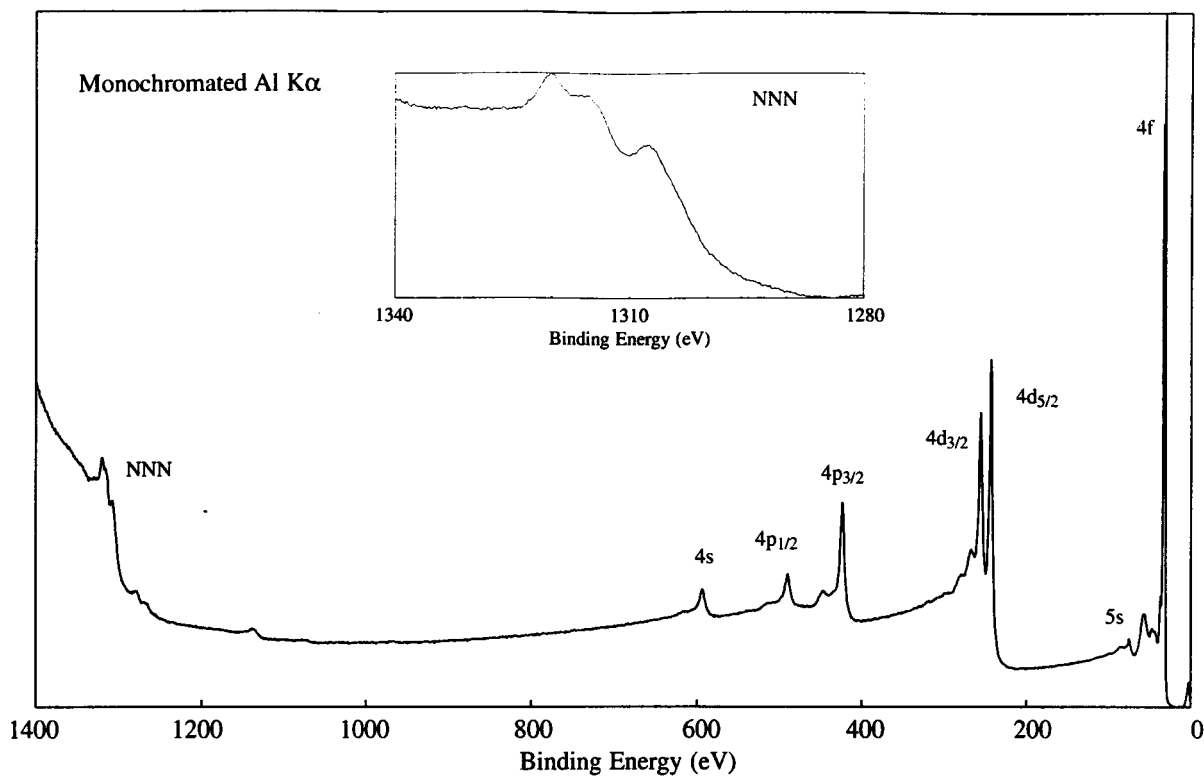


Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
563	463	401	238	226
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
69	43	33	24	22
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1318		1306		(Al)
1085		1073		(Mg)



4f $_{7/2}$ Binding Energy (eV)								
Compound Type	21	22	23	24	25	26	27	28
Ta		■						
TaS							■	
TaS ₂							■	
Halides							■	■
Ta ₂ O ₅							■	■
Br ₆ (Ta ₆ Cl ₁₂)(Bu ₄ N) ₂						■	■	
Cl ₆ (Ta ₆ Cl ₁₂)(Et ₄ N) ₂						■	■	





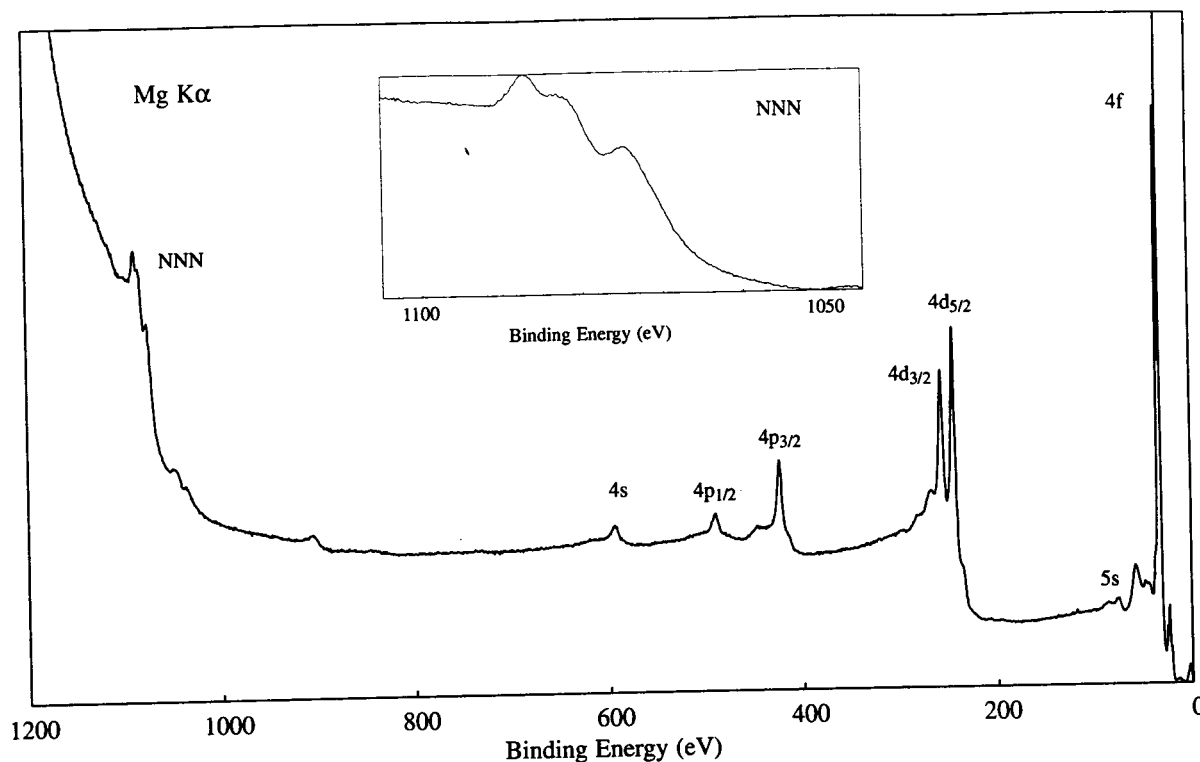
Line Positions (eV)

Photoelectron Lines

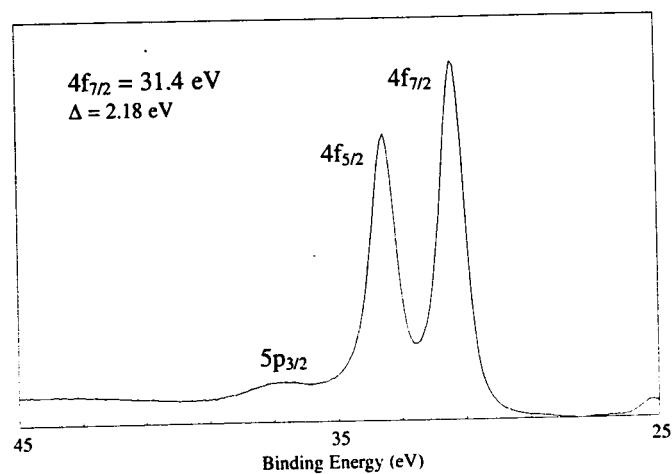
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
594	491	424	256	243
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
75	47	37	33	31

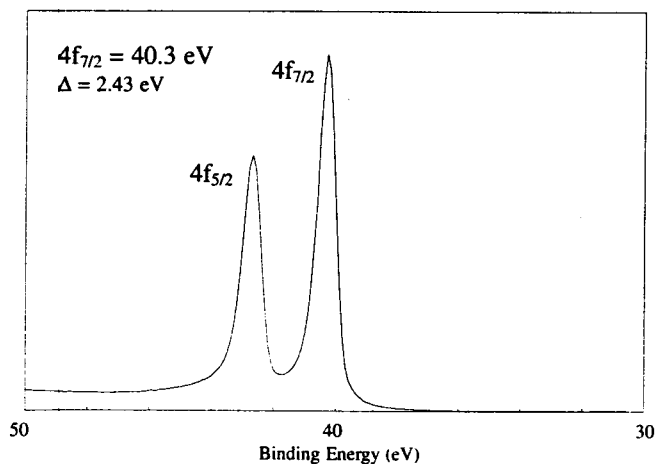
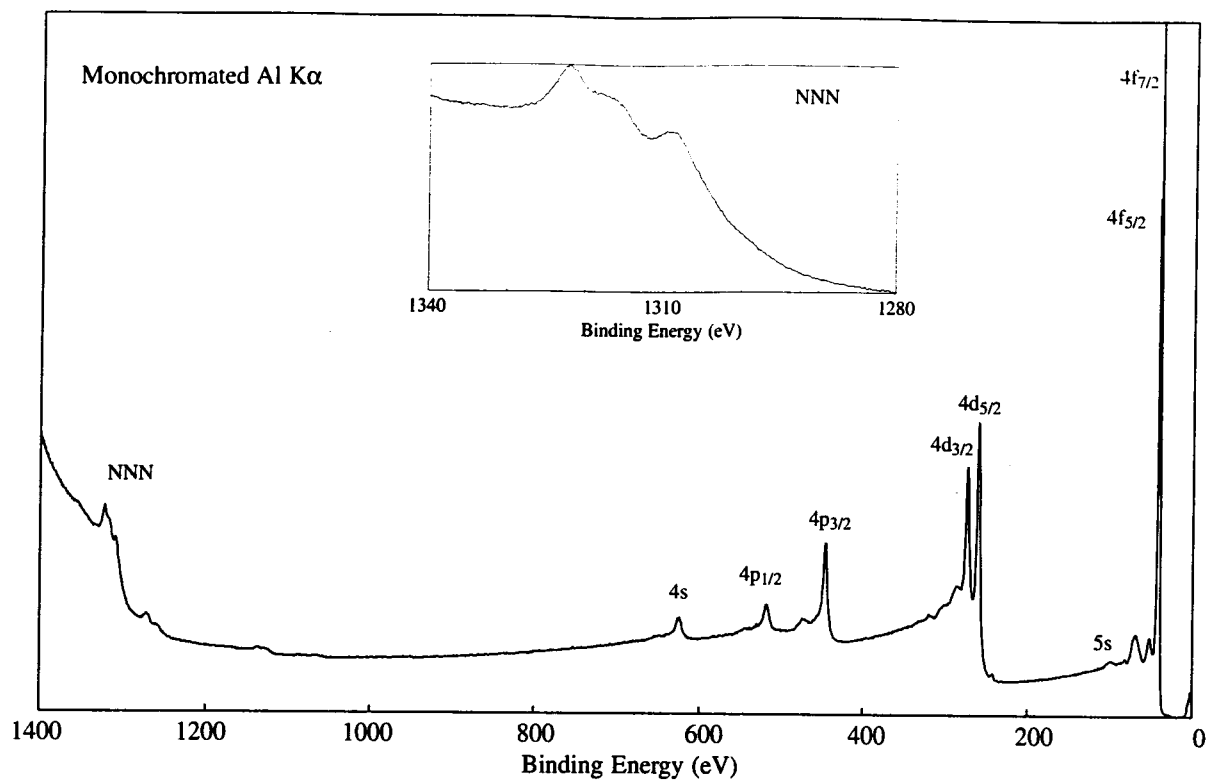
Auger Lines

N ₅ N ₆₇ N ₇	N ₄ N ₆₇ N ₇	
1320	1307	(Al)
1087	1074	(Mg)

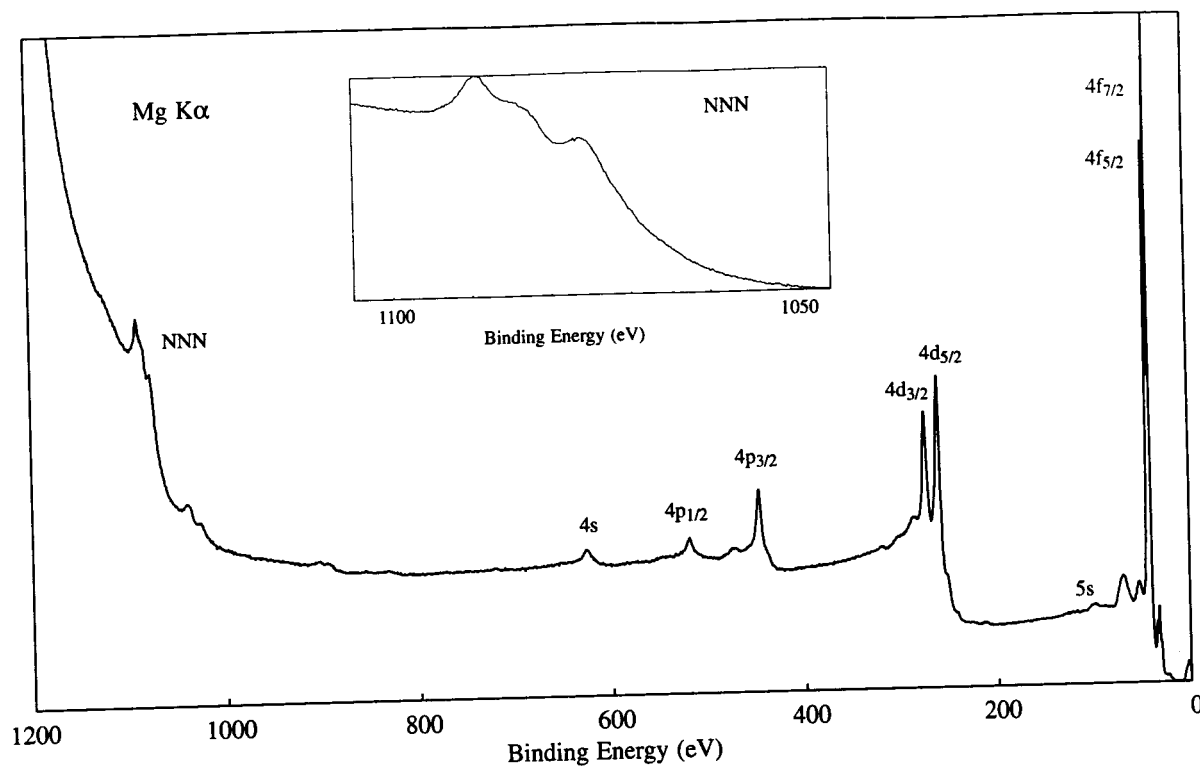


4f _{7/2} Binding Energy (eV)								
Compound Type	31	32	33	34	35	36	37	38
W	■							
WC	■	■						
WS ₂			■					
Halides						■	■	
WOCl ₄							■	
Oxides			■	■	■	■		
Tungstate					■	■		
Rh ₂ WO ₆					■	■		
Cl ₄ W(Et ₃ P) ₂				■				
Cl ₃ SnW(CO) ₃ (C ₅ H ₅)		■						
Ph ₃ PW(CO) ₅	■							

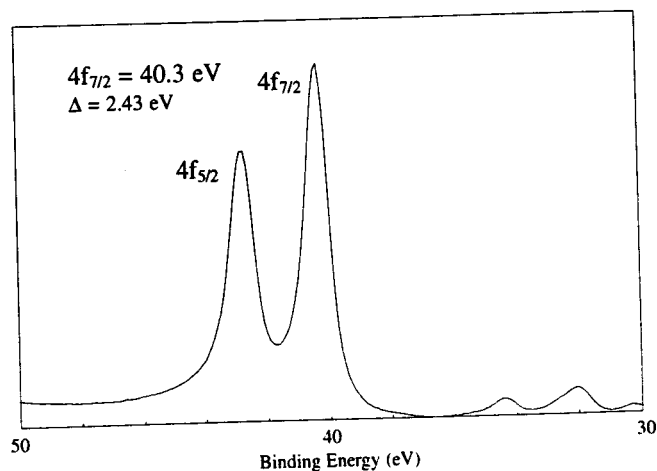


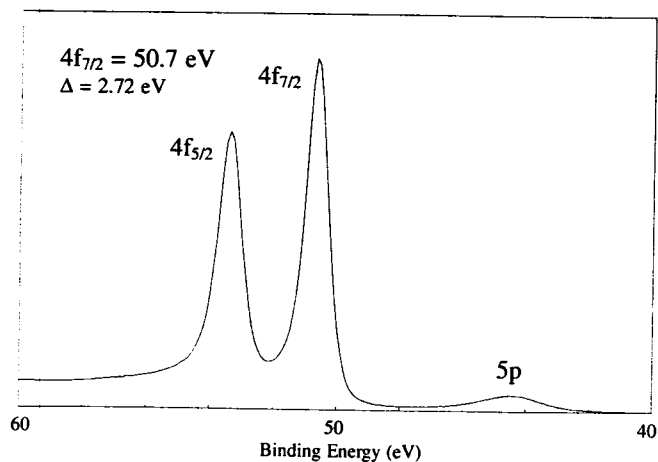
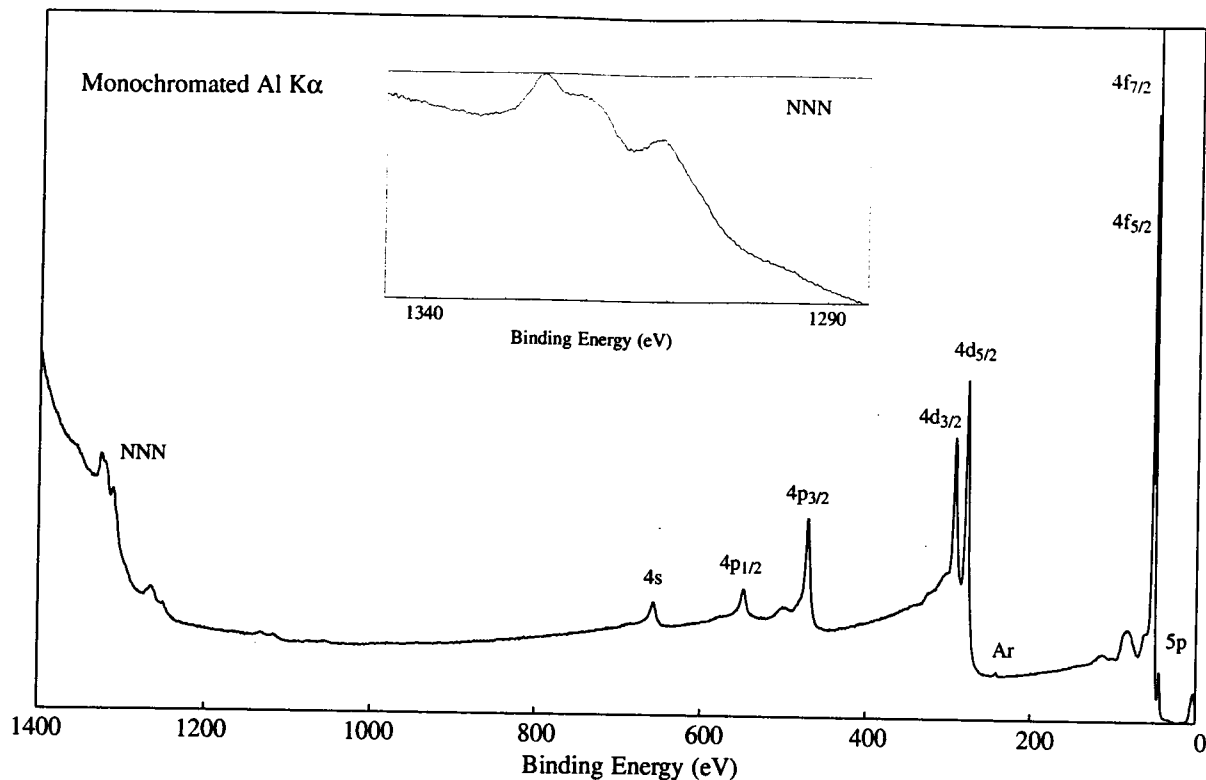


Line Positions (eV)							
Photoelectron Lines							
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s	4f _{5/2}	4f _{7/2}
625	518	446	274	260	99	42	40
Auger Lines							
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇					
1322		1309 (Al)					
1089		1076 (Mg)					



	4f _{7/2} Binding Energy (eV)							
Compound Type	40	41	42	43	44	45	46	47
Re		■						
ReO ₂					■			
ReO ₃								■
K ₂ ReCl ₆					■			
Cl ₃ ReO(Ph ₃ P) ₂					■			
Cl ₂ ReN(Ph ₃ P) ₂				■				
Cl ₄ Re(Et ₃ P) ₂				■				
Cl ₄ Re(PMe ₂ Ph) ₂					■			
Cl ₃ Re(PMe ₂ Ph) ₃ mer			■					
Cl ₂ Re(PMe ₂ Ph) ₄ trans		■						
ClReN ₂ (PMe ₂ Ph) ₄ trans	■							





Line Positions (eV)

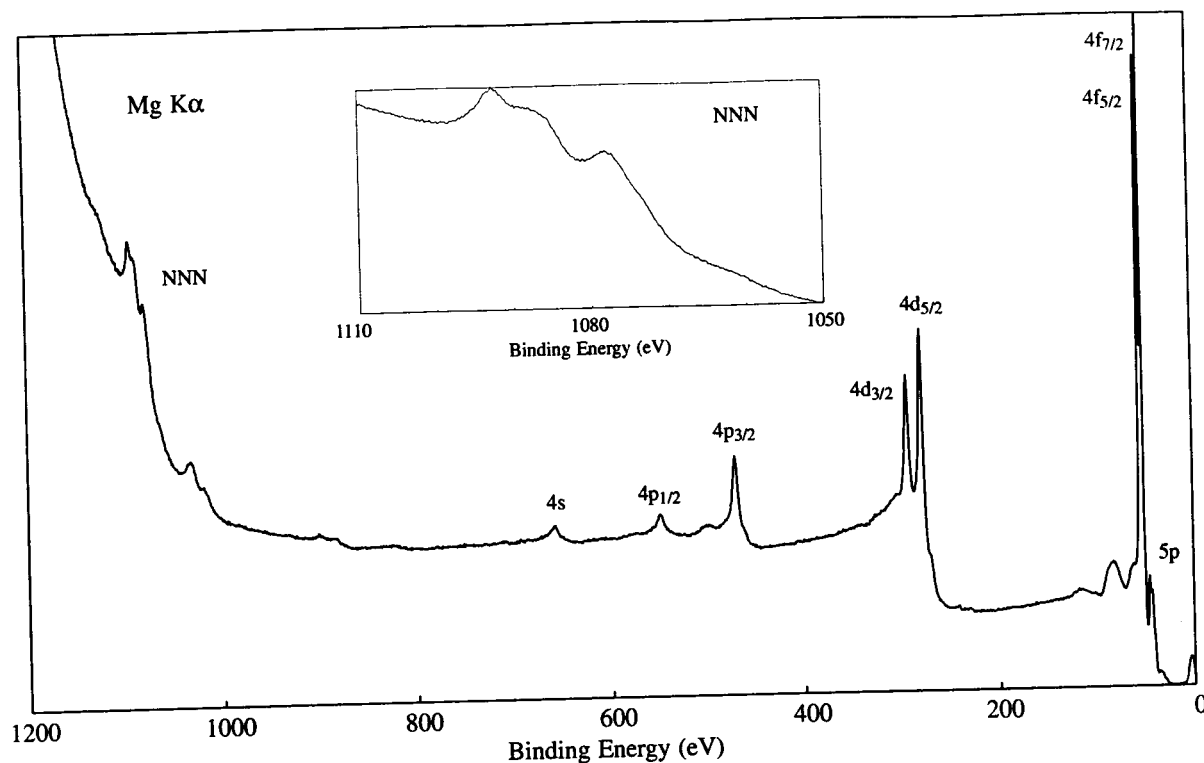
Photoelectron Lines

4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
658	548	471	293	279
5s*	4f _{5/2}	4f _{7/2}	5p	
89	54	51	44	

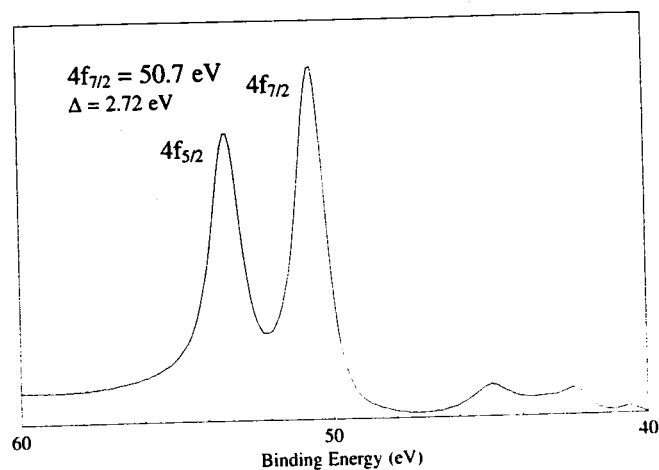
Auger Lines

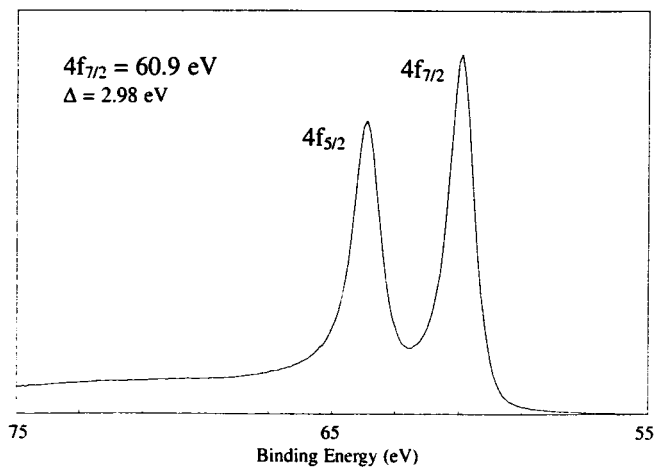
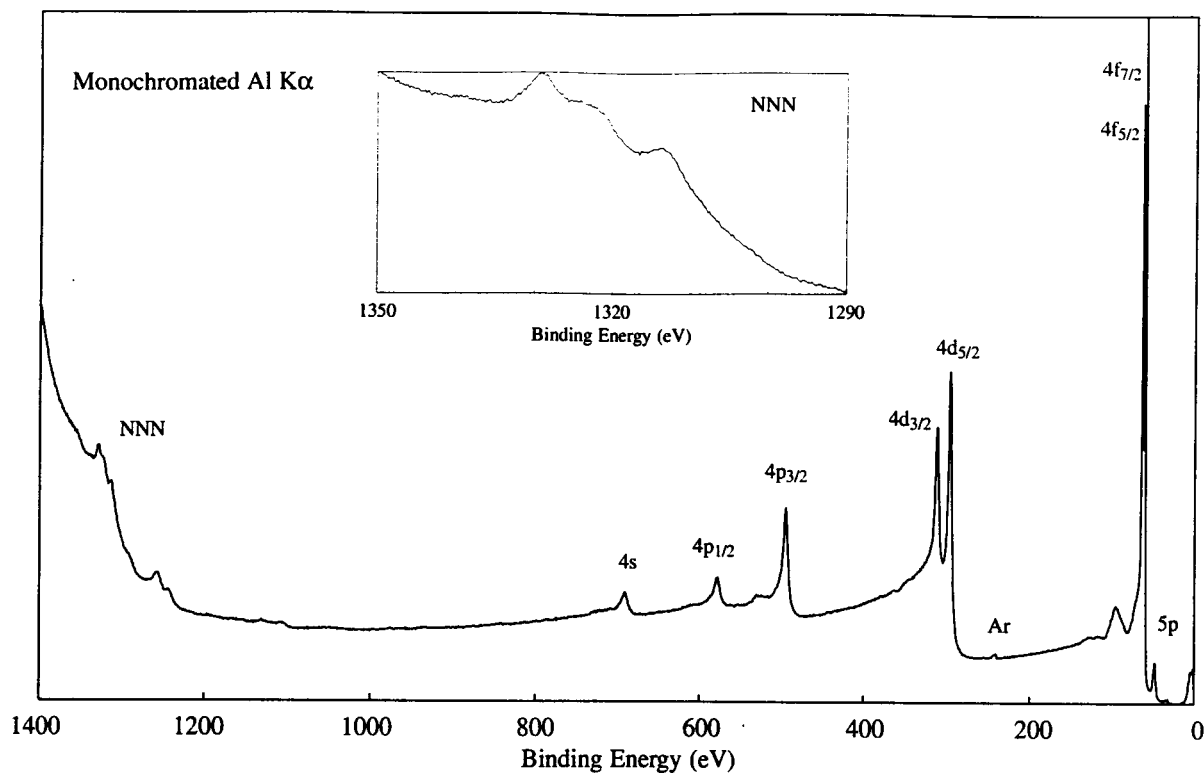
N ₅ N ₆₇ N ₇	N ₄ N ₆₇ N ₇	
1326	1311	(Al)
1093	1078	(Mg)

*Estimate

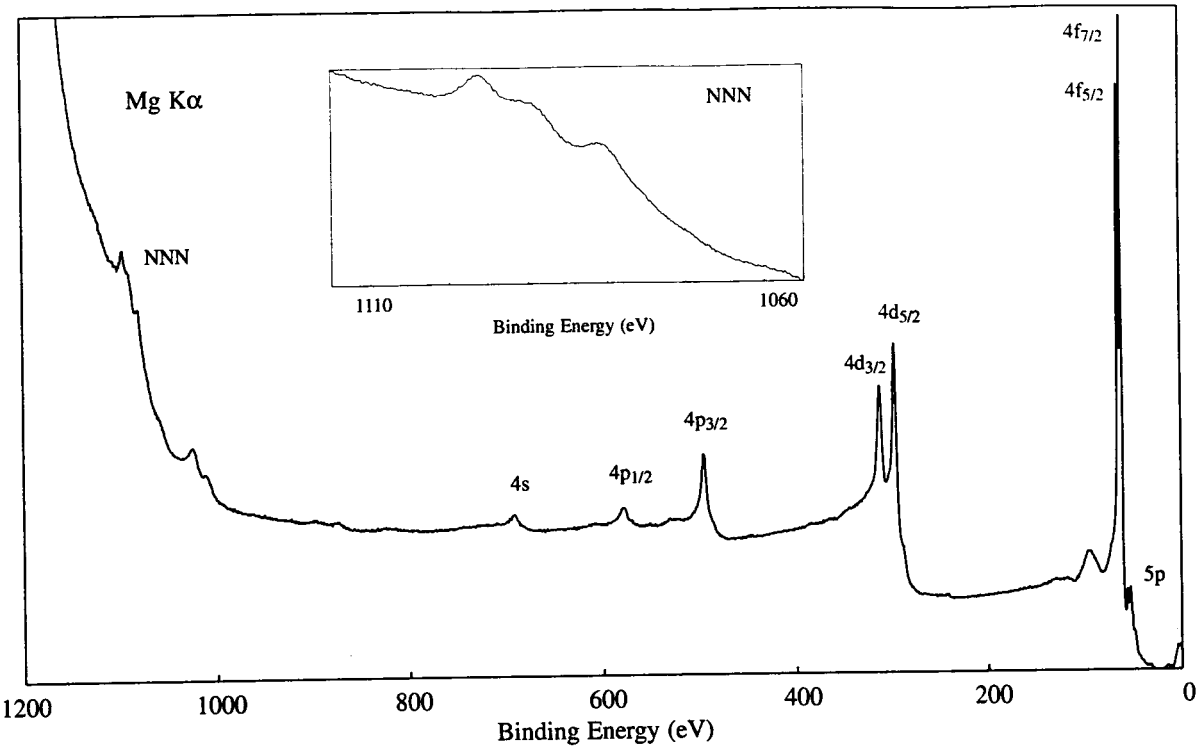


Compound Type	4f $_{7/2}$ Binding Energy (eV)				
	50	51	52	53	54
Os	■				
OsO $_2$			■	■	
K $_2$ OsI $_6$			■		
K $_2$ OsBr $_6$				■	
K $_2$ OsCl $_6$				■	■
OsCl $_4$ (Et $_3$ P) $_2$				■	
OsCl $_4$ (PhPMe $_2$) $_2$ trans				■	
OsCl $_3$ (PhPMe $_2$) $_3$ mer			■		
OsCl $_2$ (PhPMe $_2$) $_4$ trans	■				

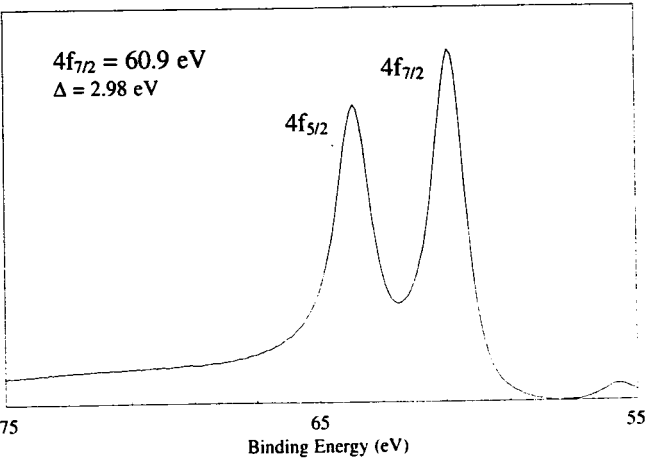


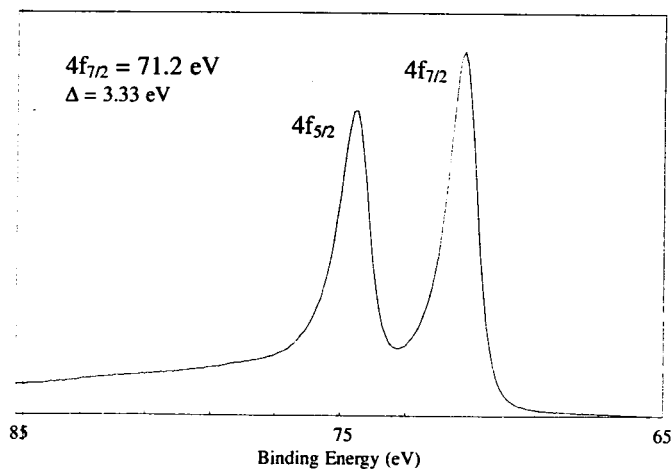
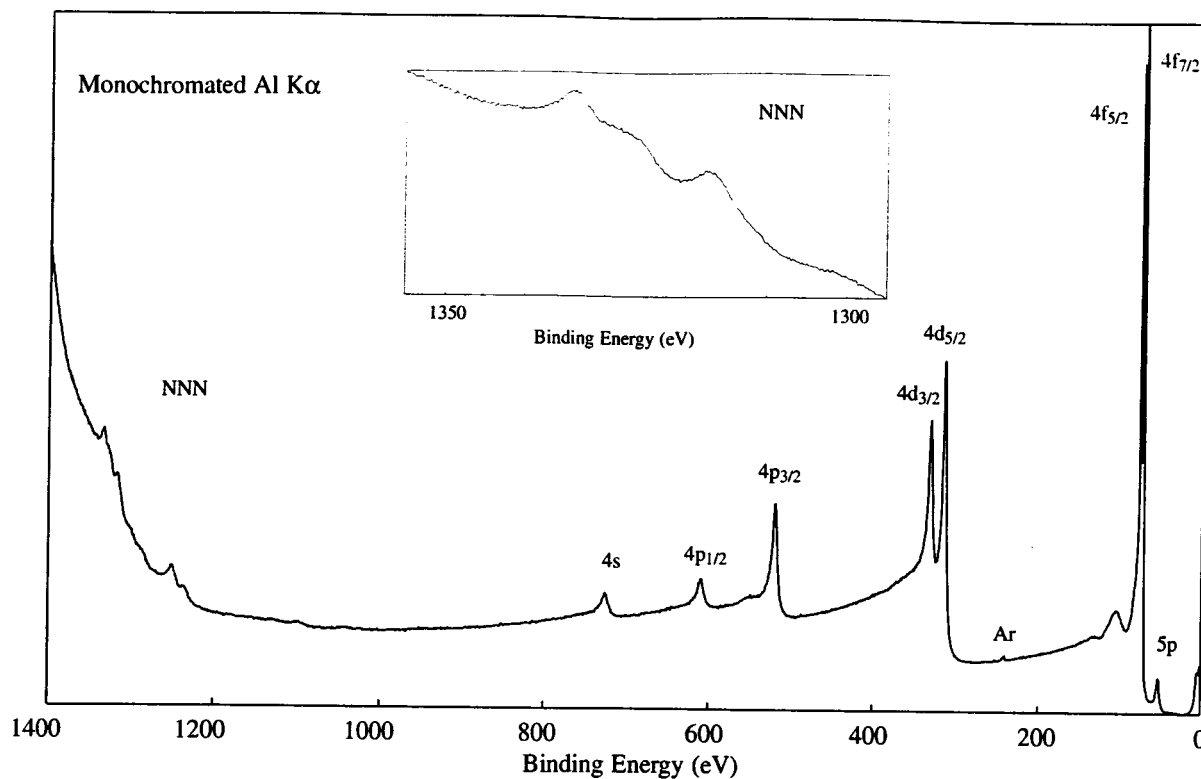


Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
692	578	495	312	297
5s*	4f _{5/2}	4f _{7/2}	5p	
96	64	61	48	
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1329		1314 (Al)		
1096		1081 (Mg)		
*Estimate				

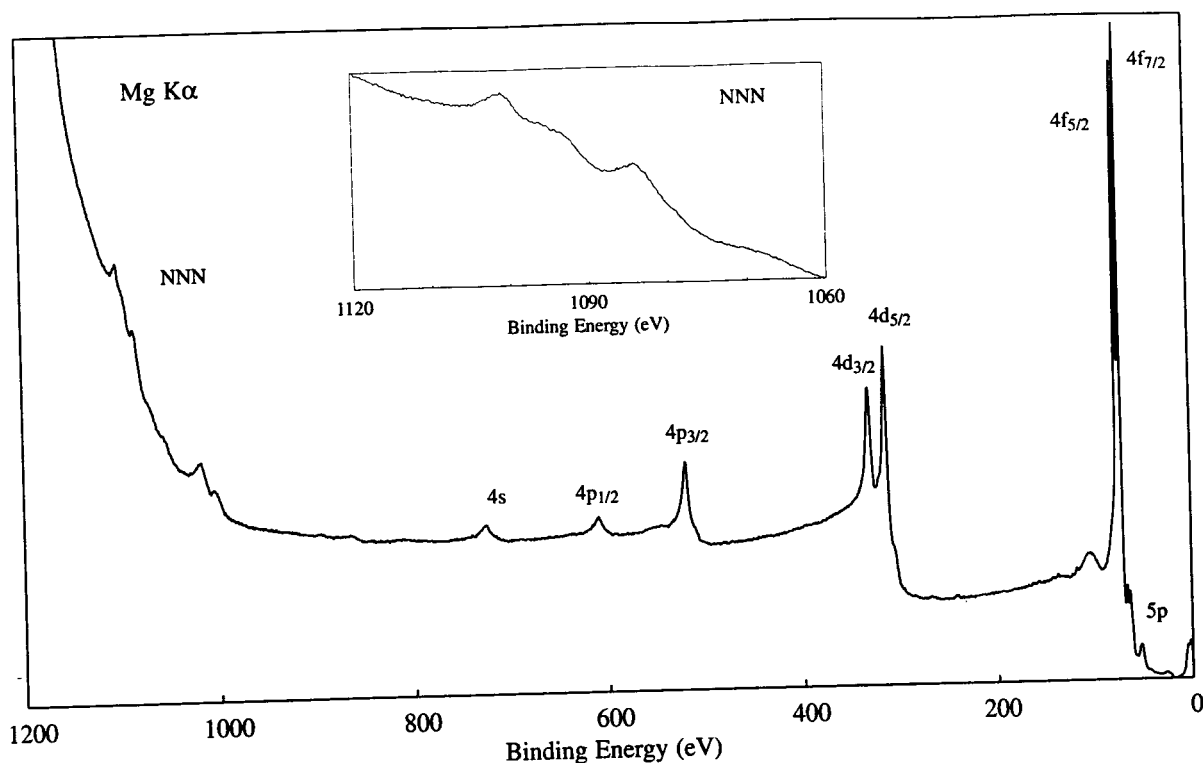


4f _{7/2} Binding Energy (eV)						
Compound Type	60	61	62	63	64	65
Ir						
IrCl ₃						
K ₂ IrBr ₆						
K ₃ IrBr ₆						
K ₂ IrCl ₆						
K ₃ IrCl ₆						
(NH ₄) ₂ IrCl ₆						
(NH ₄) ₃ IrCl ₆						
KIrCl ₅ NO						
KIr ₂ (CO) ₄ Cl ₄						
K ₂ Ir ₂ (CO) ₄ Cl ₅						

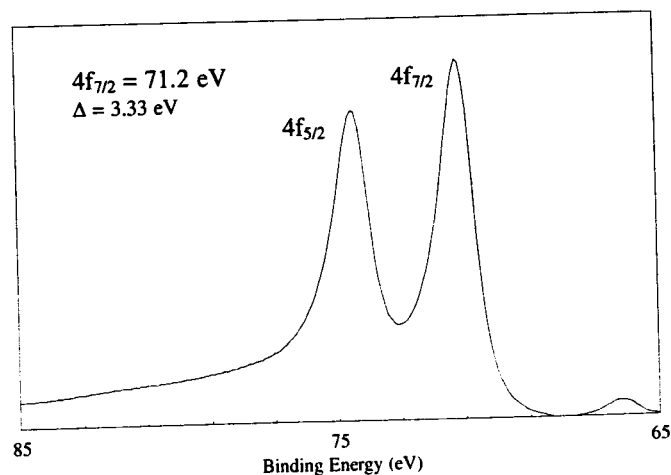


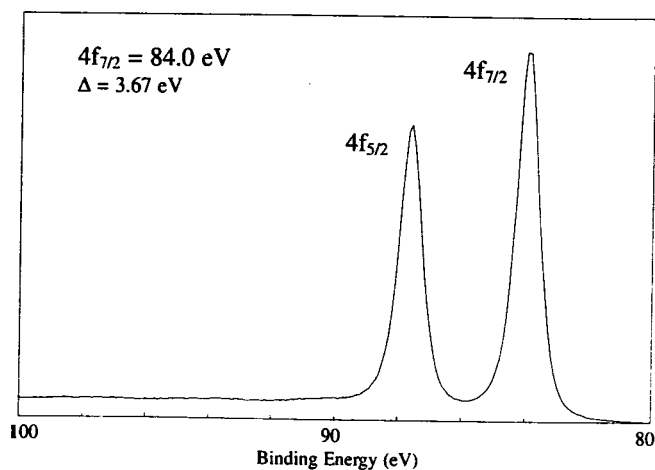
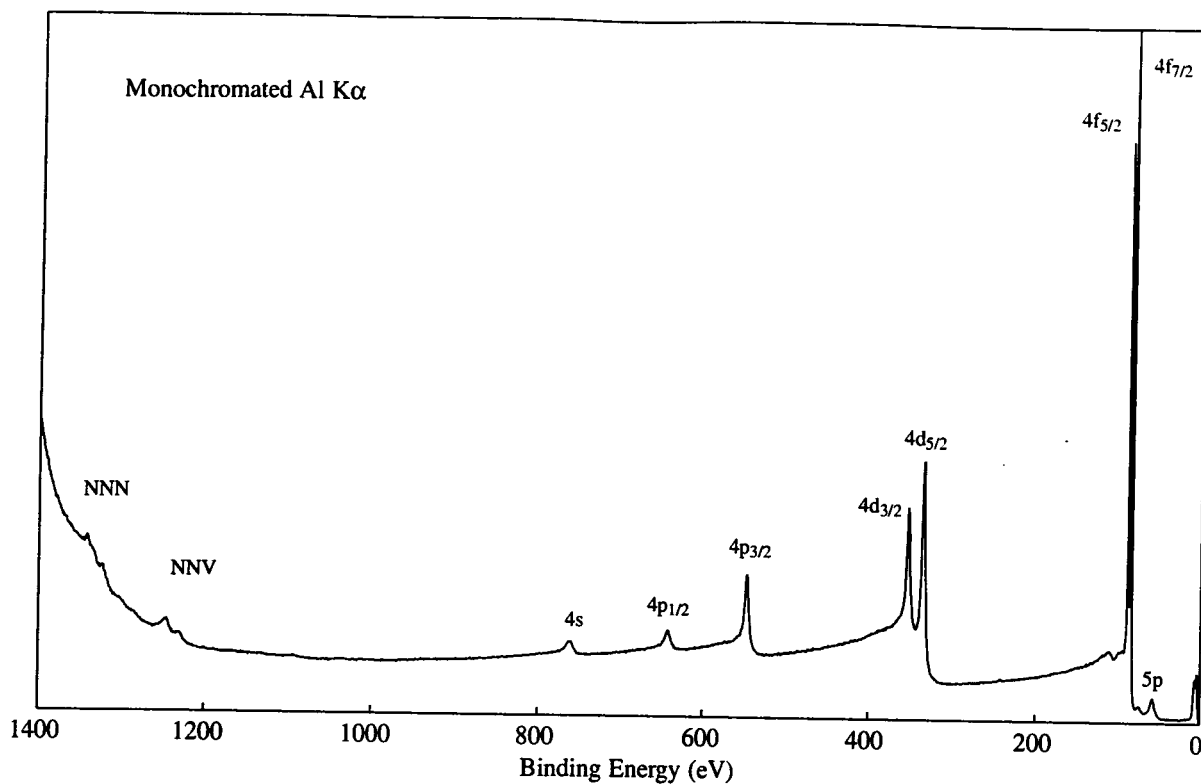


Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
725	609	520	332	315
5s*	4f _{5/2}	4f _{7/2}	5p	
103	74	71	52	
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1334		1317 (Al)		
1101		1084 (Mg)		
*Estimate				



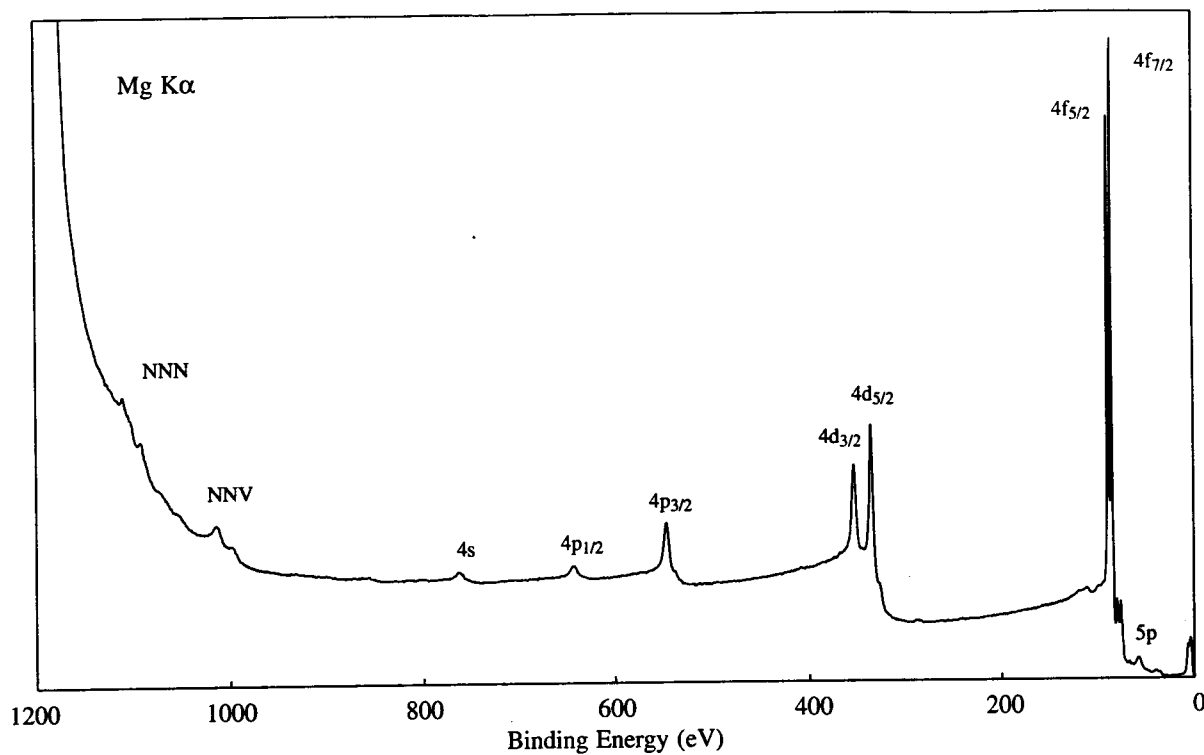
Compound Type	4f _{7/2} Binding Energy (eV)							
	71	72	73	74	75	76	77	78
Pt	■							
PtSi			■					
Pt ₂ Si		■						
PtCl ₂				■				
PtCl ₄					■			
Oxides				■	■			
Pt(OH) ₂		■						
(IV) Halides				■	■	■	■	■
Cl ₂ Pt(Ph ₃ P) ₂ cis		■	■					
I ₂ Pt(Me ₃ P) ₂ cis		■	■					
I ₂ Pt(Me ₃ P) ₂ trans			■					



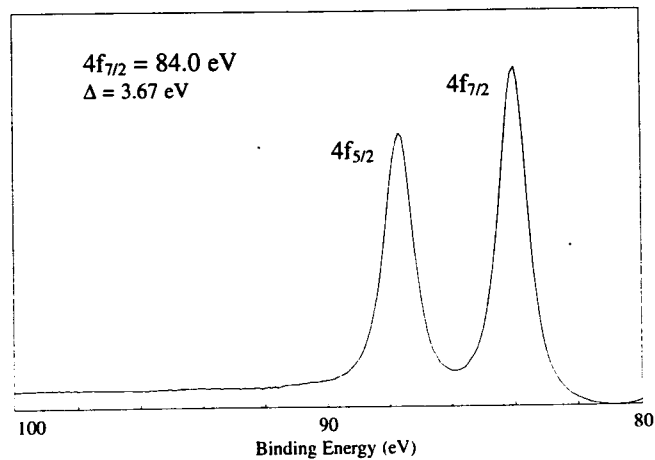


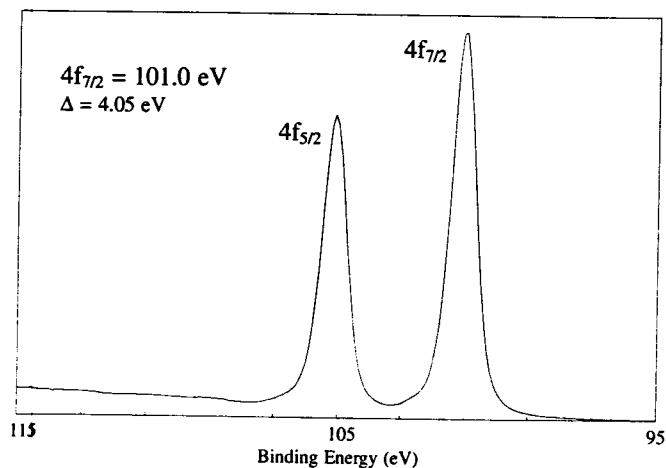
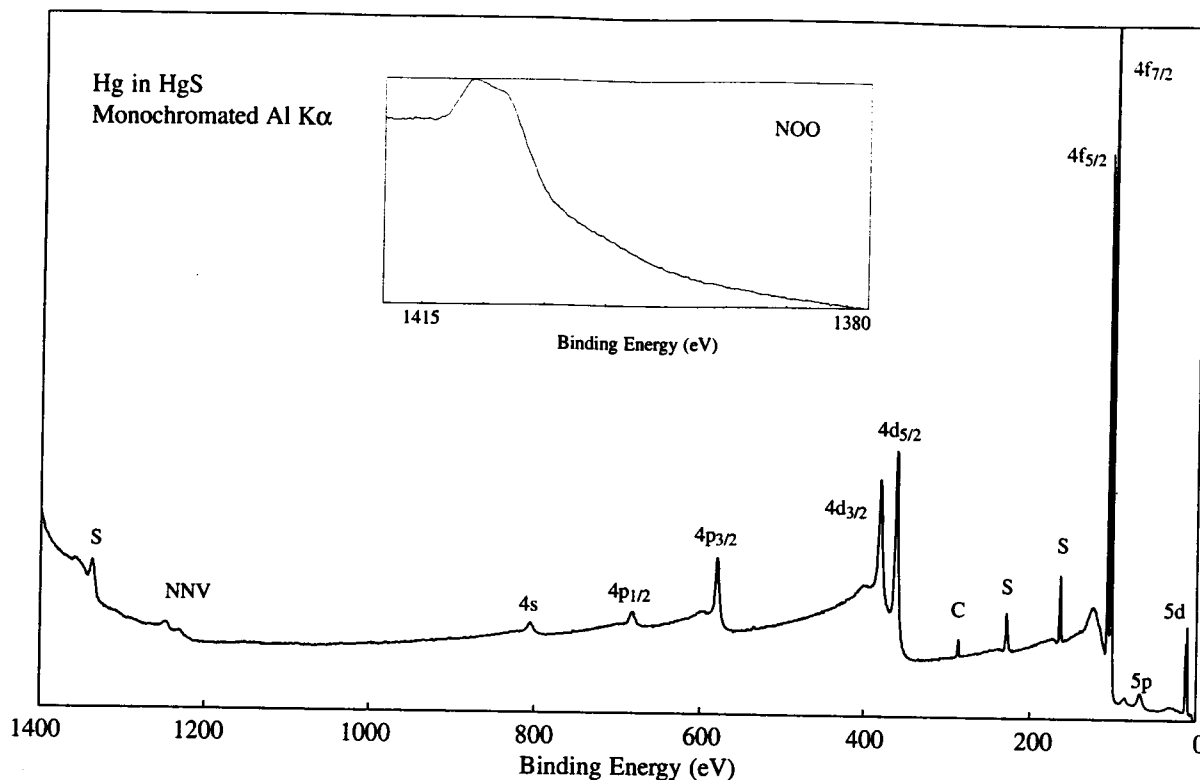
Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
763	643	547	353	335
5s*	4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}
110	88	84	74	57
Auger Lines				
N ₆₇ O ₄₅ O ₄₅	N ₅ N ₆ N ₆₇	N ₄ N ₆ N ₆₇	N ₅ N ₆₇ V	
1416	1342	1324	1247	(Al)
1183	1109	1091	1014	(Mg)

*Estimate



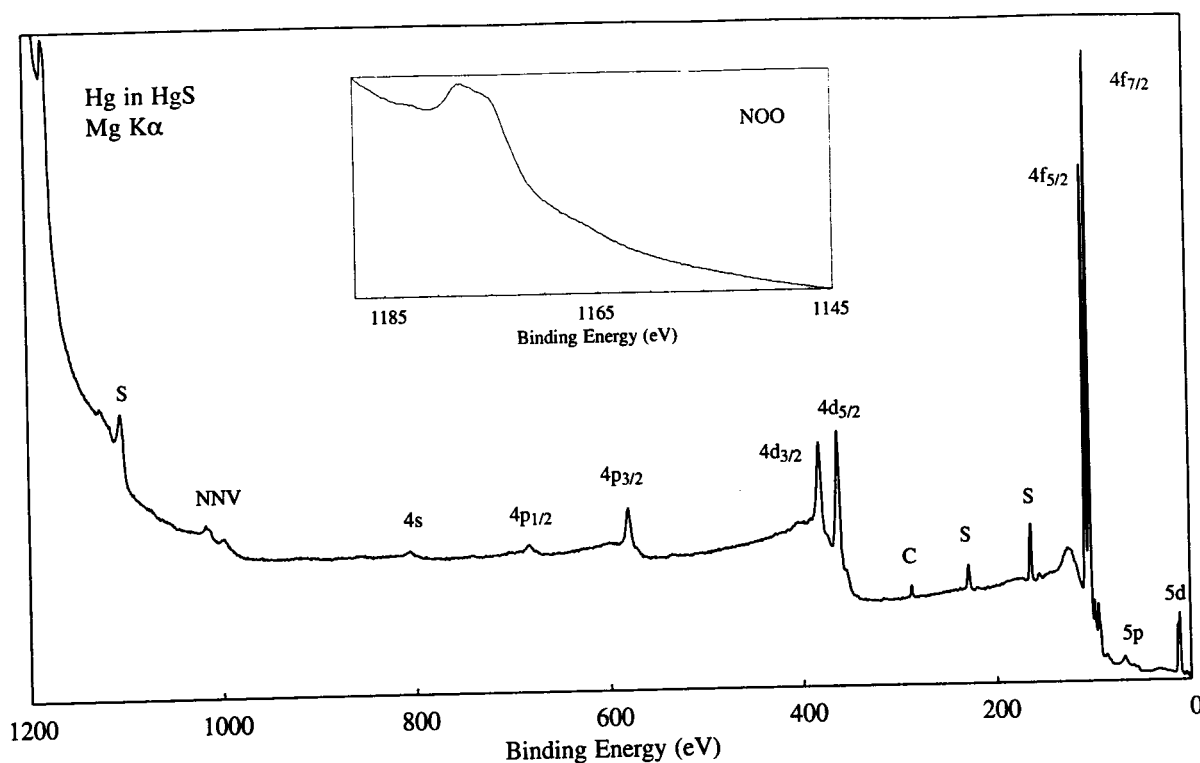
Compound Type	4f _{7/2} Binding Energy (eV)					
	83	84	85	86	87	88
Au		■				
AuSn			■			
AuSn ₄			■			
YbAu ₂			■			
ClAuPh ₃ P				■		
ClAu(Ph ₃ P) ₂				■		
Cl ₃ AuPh ₃ P					■	
(Ph ₃ P)AuNO ₃				■		
ClAu(Ph ₃ As)			■			
(-AuSPEt ₂ S-) ₂			■			
(-AuCH ₂ PEt ₂ CH ₂ -) ₂		■				



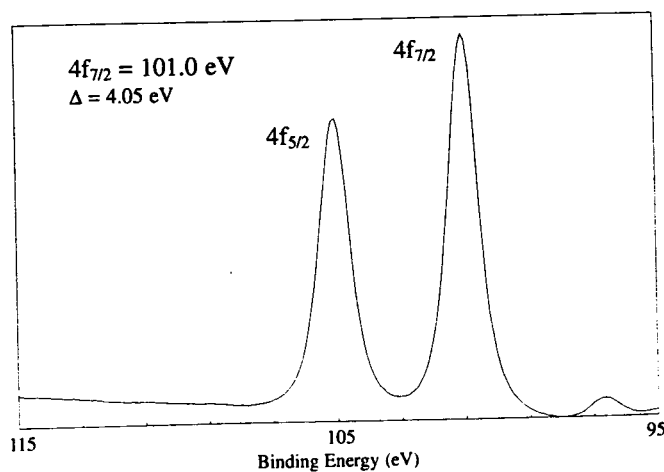


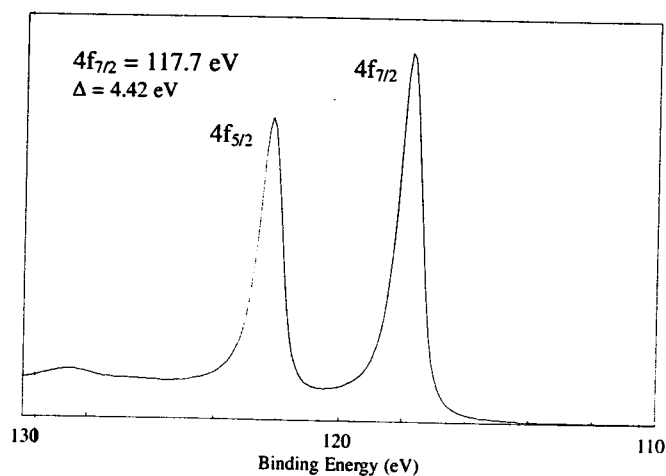
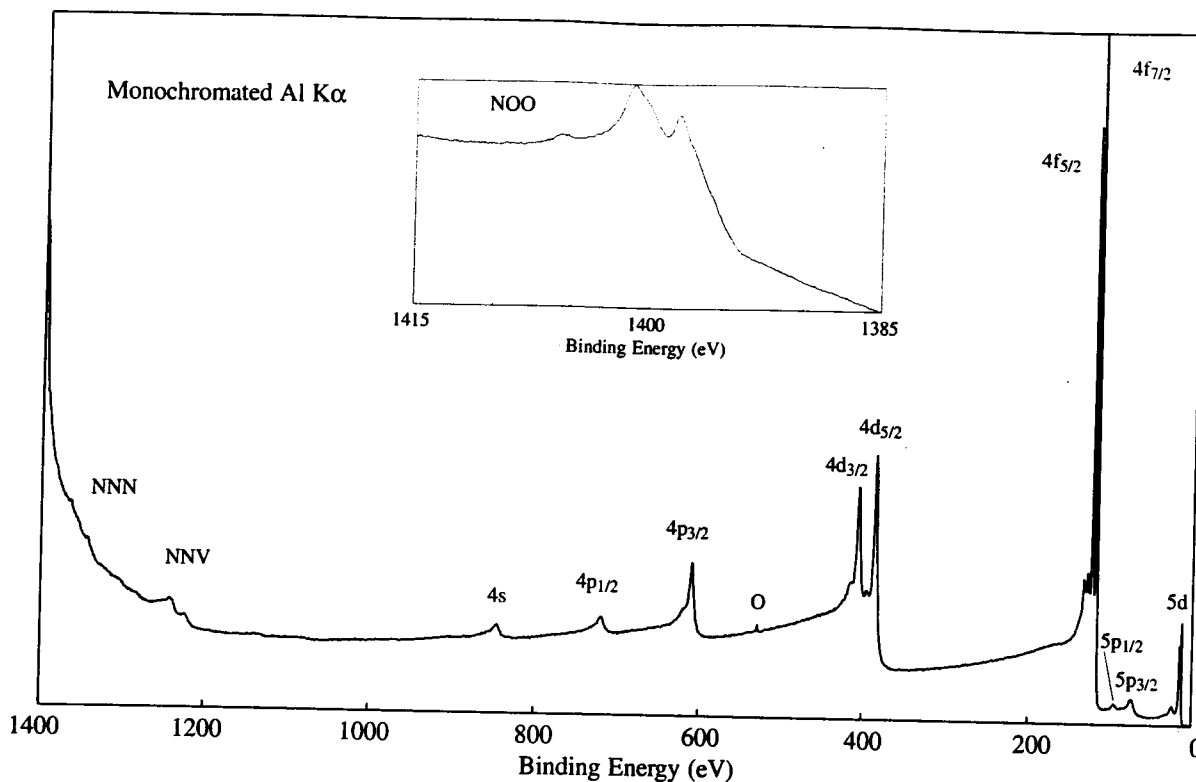
Line Positions (eV)					
Photoelectron Lines					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
805	682	579	381	361	125
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
105	101	85	67	12	10
Auger Lines					
N ₇ O ₄₅ O ₄₅		N ₅ N ₇ O		N ₄ N ₆ O	
1412		1246		1230 (Al)	
1179		1013		997 (Mg)	

*Estimate

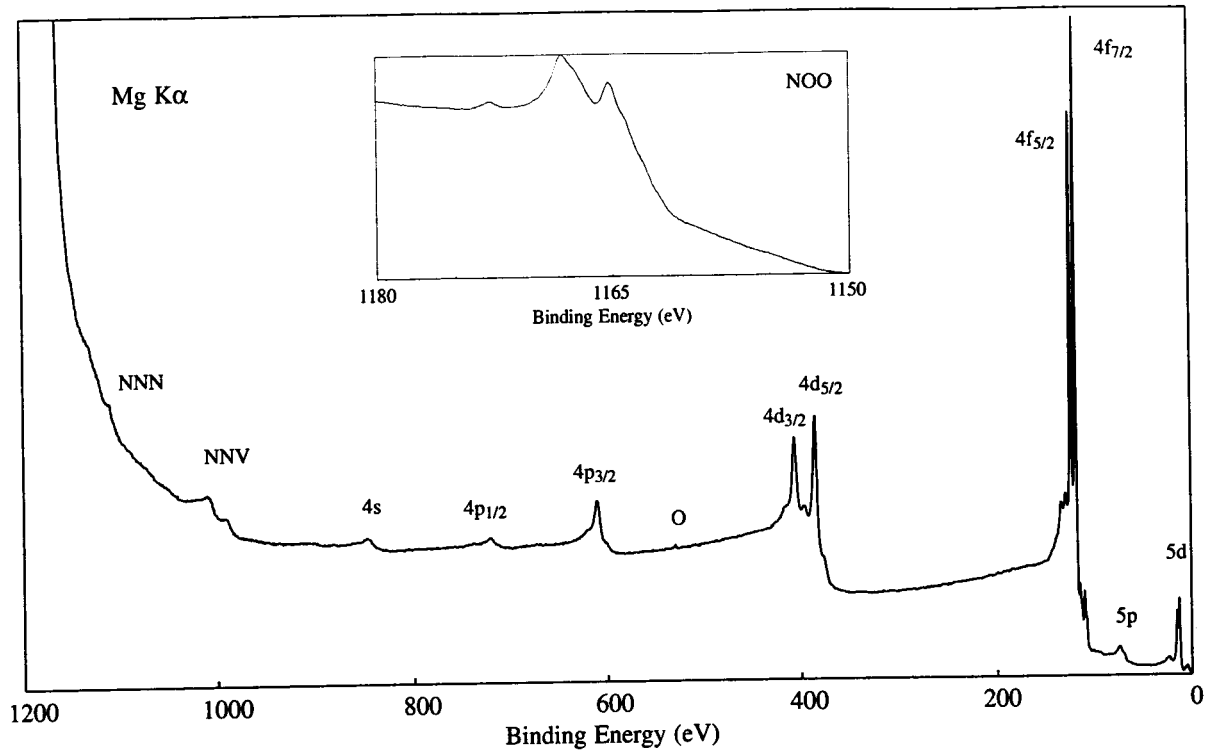


Compound Type	4f _{7/2} Binding Energy (eV)			
	99	100	101	102
Hg				
Hg _{0.8} Cd _{0.2} Te				
HgS				
HgI ₂				
HgBr ₂				
HgCl ₂				
HgF ₂				
HgO				
Et ₂ NC ₆ H ₄ HgOAc				
Hg(thiodibenzoylme) ₂				
(Ph ₄ P) ₂ Hg(SCN) ₄				

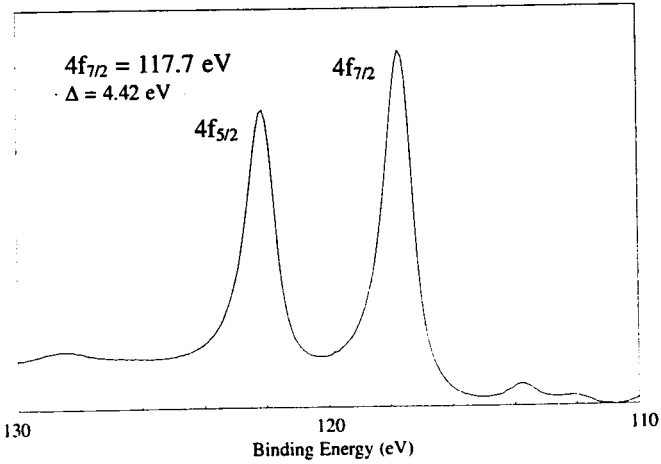


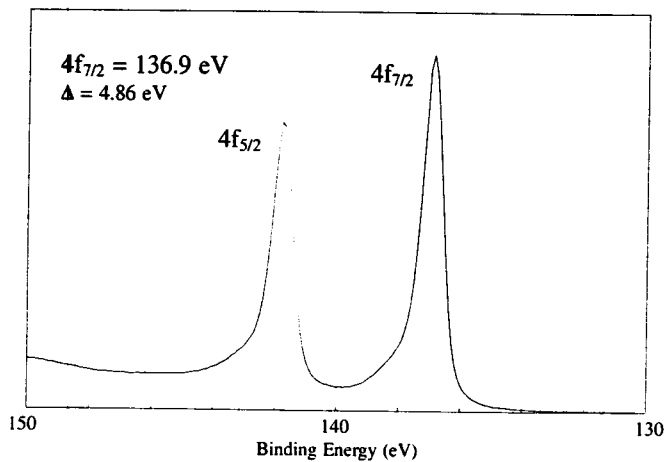
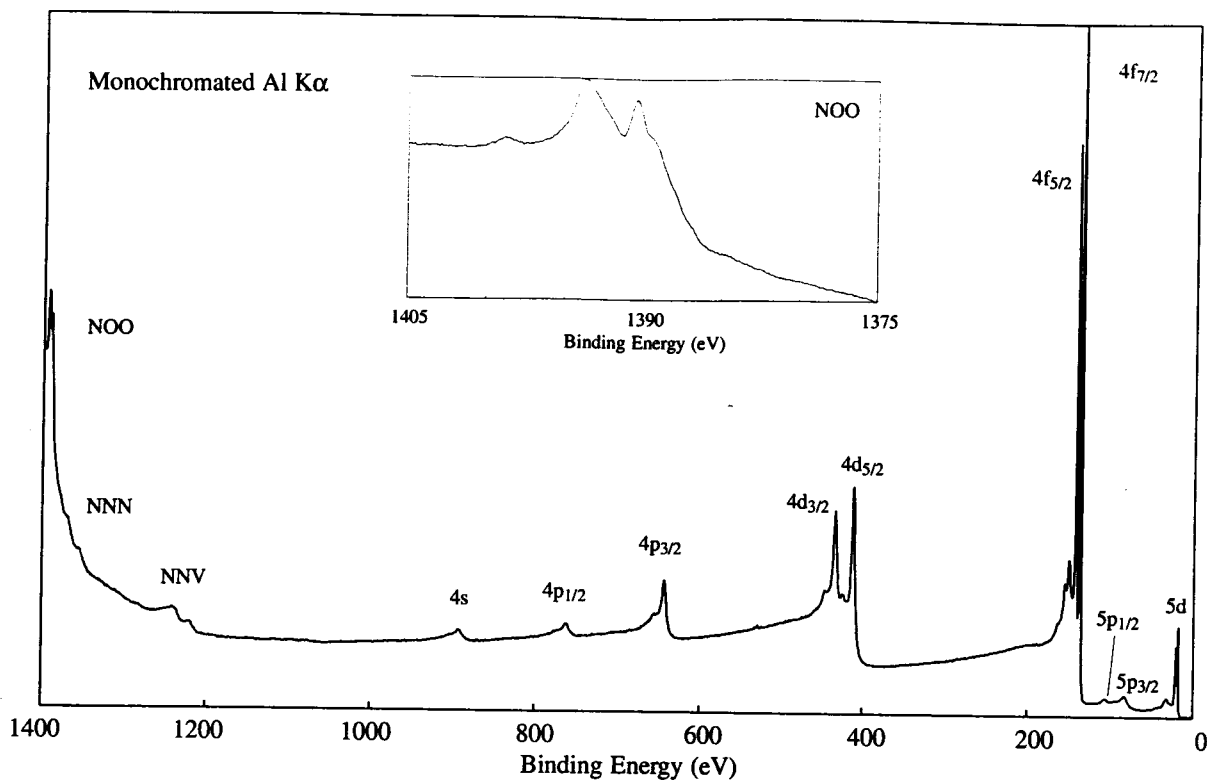


Line Positions (eV)					
Photoelectron Lines					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
847	720	610	406	385	133
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
122	118	95	74	15	13
Auger Lines					
N ₇ O ₄₅ O ₄₅	N ₆ O ₄₅ O ₄₅	N ₅ N ₇ O ₅	N ₄ N ₆₇ O ₅		
1401	1399	1241	1222	(Al)	
1168	1166	1008	989	(Mg)	
*Estimate					

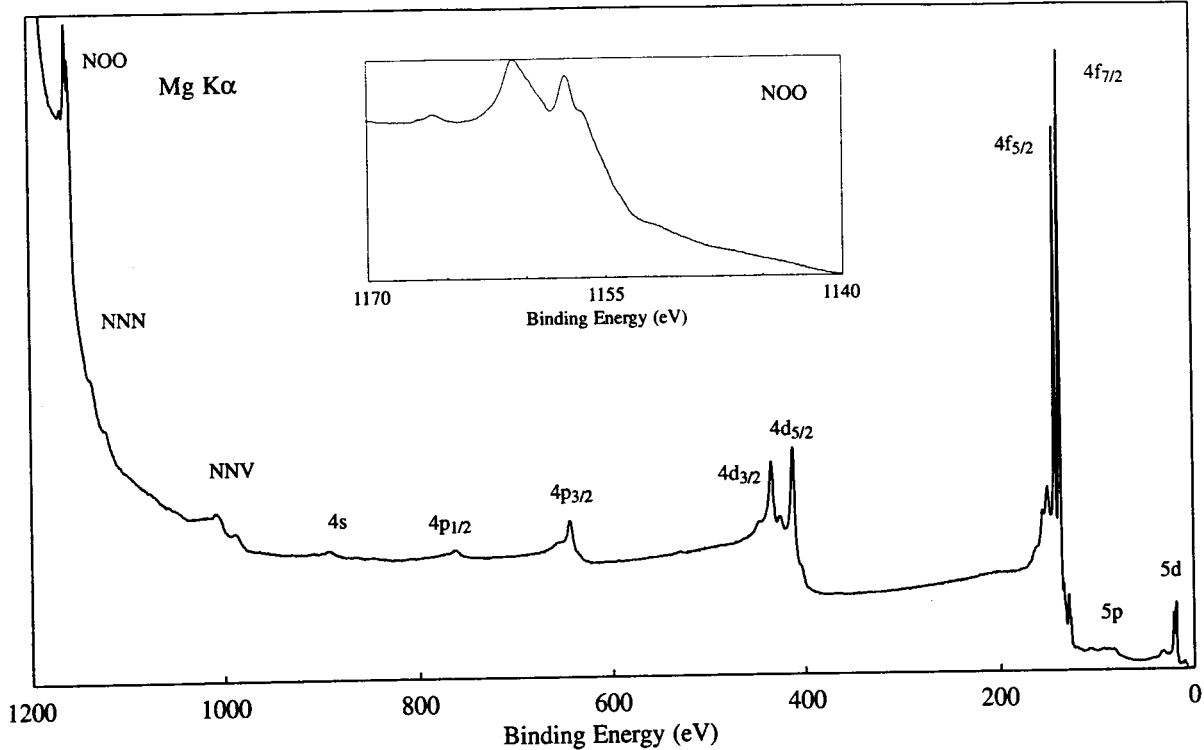


4f _{7/2} Binding Energy (eV)				
Compound Type	117	118	119	120
Tl				
TlI				
TlBr				
TlCl				
TlF				
Tl ₂ S				
Tl ₂ S ₃				
Tl ₂ O ₃				
Cl ₃ Tl(pyridine) ₂				
Cl ₆ Tl ₂ (PhPEt ₂) ₅				

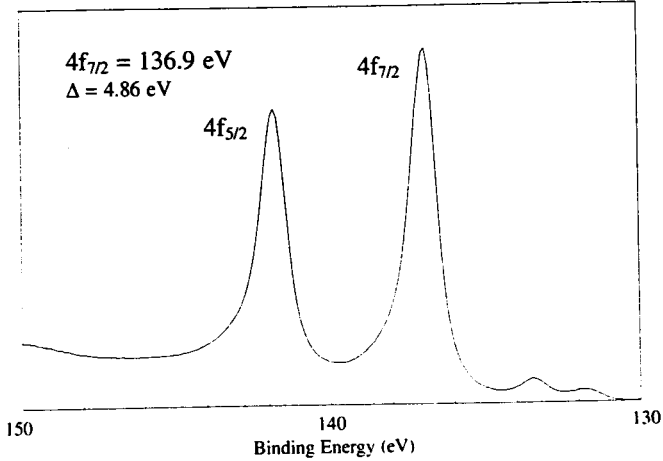


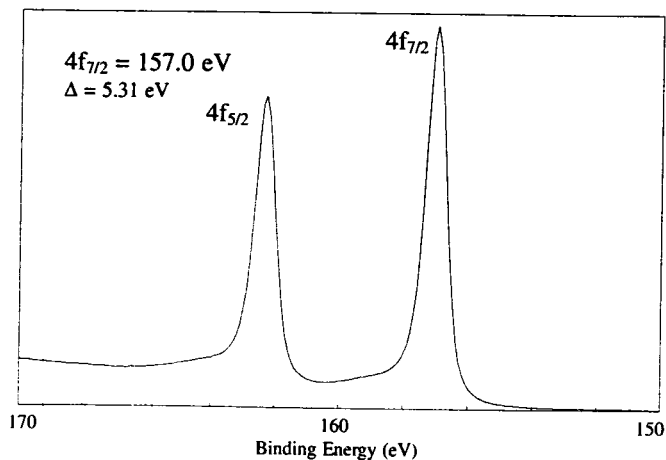
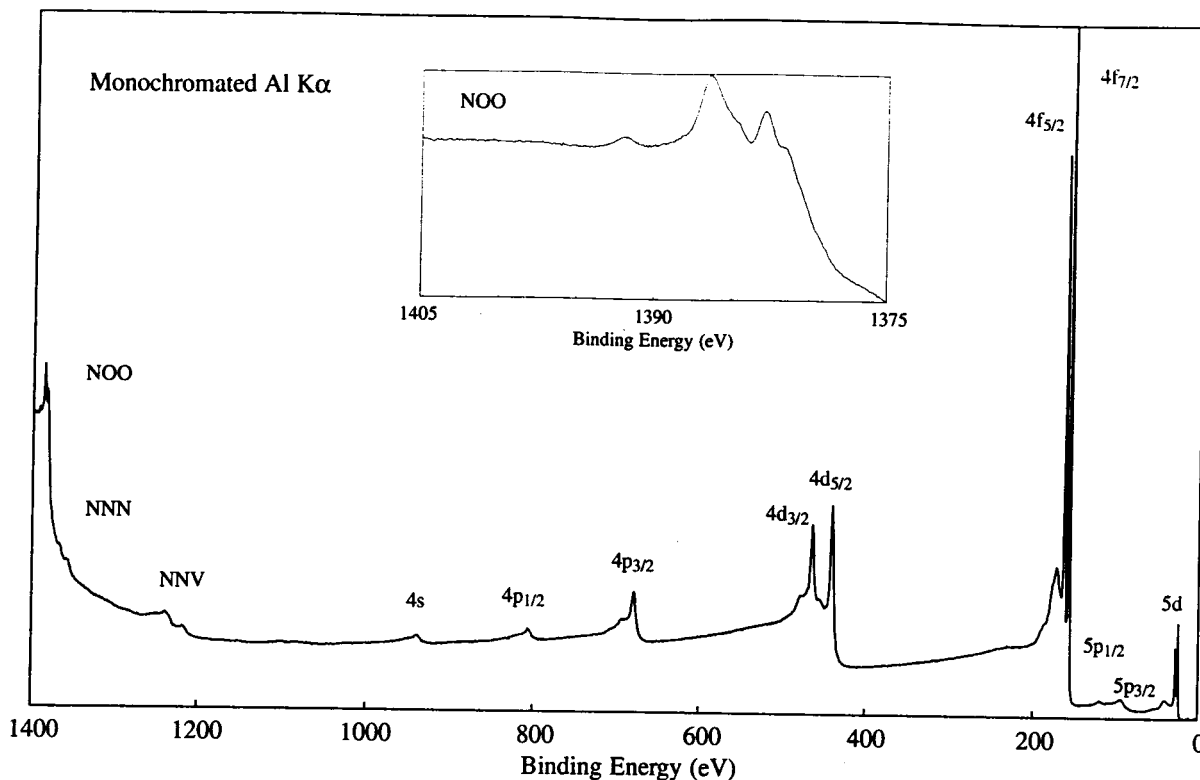


Line Positions (eV)					
Photoelectron Lines					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
893	762	644	434	412	150
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
142	137	107	84	21	18
Auger Lines					
N ₇ O ₄₅ O ₄₅		N ₆ O ₄₅ O ₄₅			
1394		1391 (Al)			
1161		1158 (Mg)			
*Estimate					

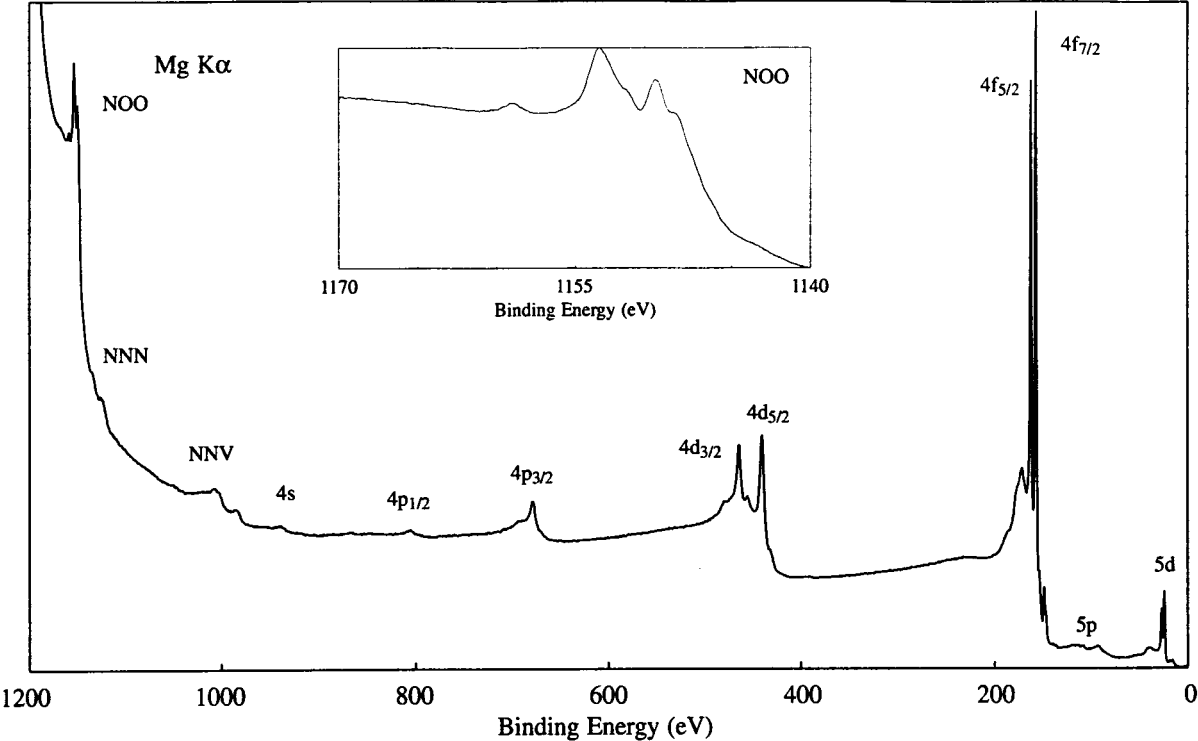


4f $_{7/2}$ Binding Energy (eV)					
Compound Type	136	137	138	139	140
Pb					
PbTe					
PbSe					
Halides					
PbO					
Pb $_3$ O $_4$					
PbO $_2$					
Pb(OH) $_2$					
Pb(NO $_3$) $_2$					
PbSO $_3$					
PbSO $_4$					

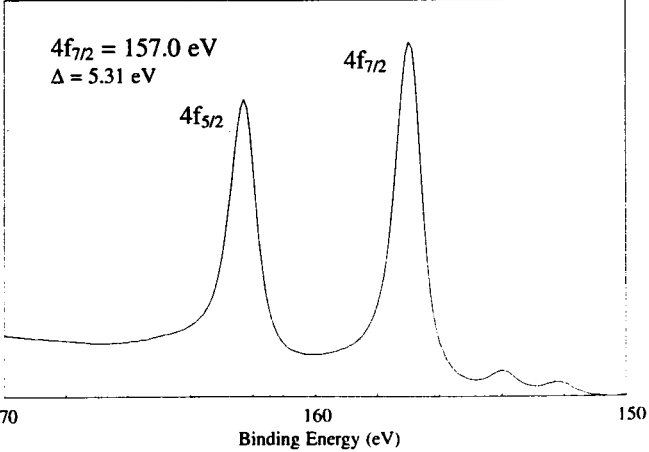


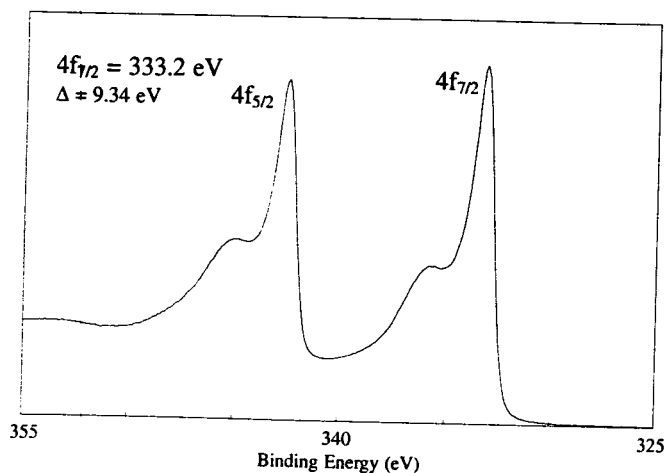
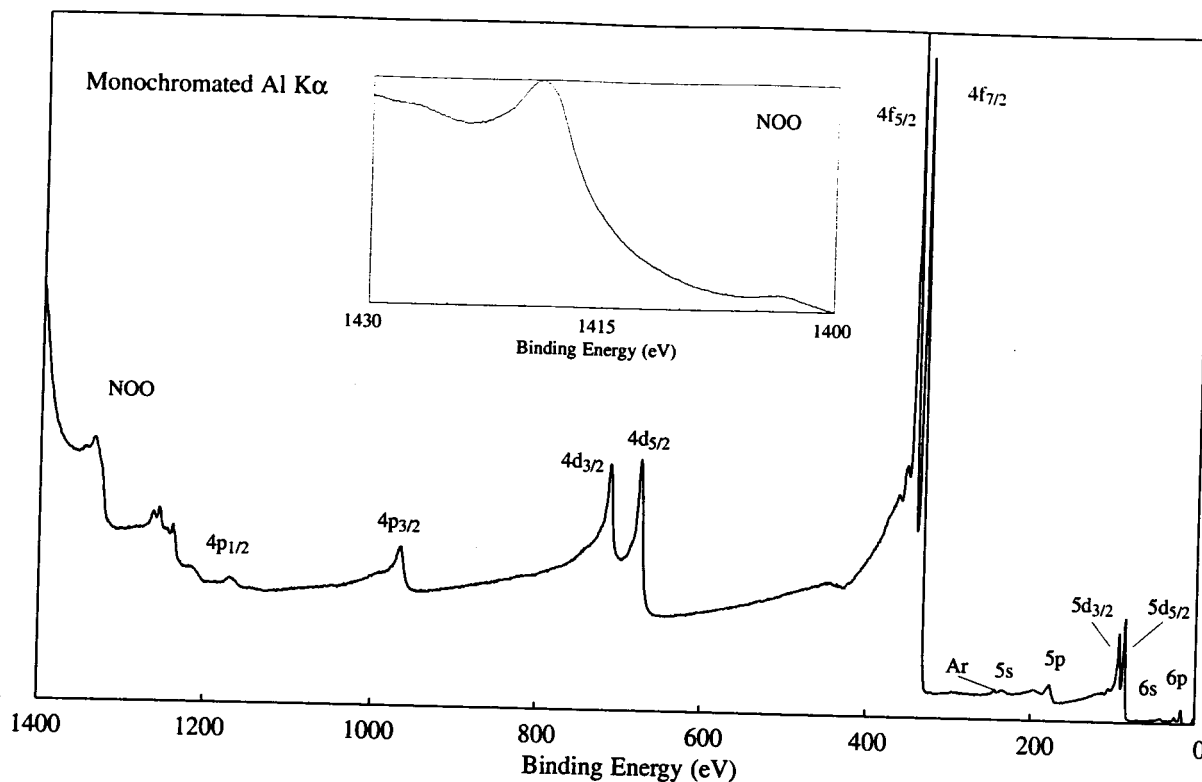


Line Positions (eV)					
Photoelectron Lines					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
940	806	679	464	440	161
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
162	157	119	93	27	24
Auger Lines					
N ₇ O ₄₅ O ₄₅		N ₆ O ₄₅ O ₄₅			
1387		1383		(Al)	
1154		1150		(Mg)	
*Estimate					

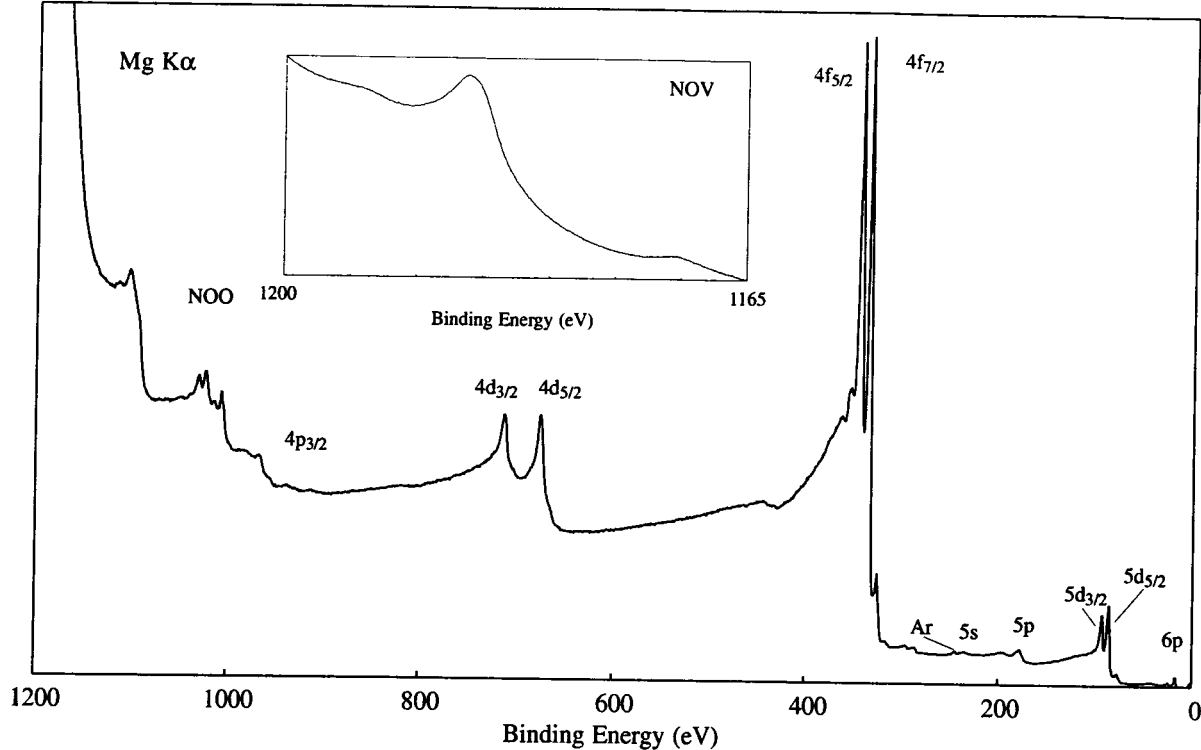


Compound Type	4f $_{7/2}$ Binding Energy (eV)						
	156	157	158	159	160	161	162
Bi							
Bi $_2$ S $_3$							
BiI $_3$							
BiF $_3$							
Bi $_2$ O $_3$							
BiOCl							
NaBiO $_3$							
Bi $_2$ MoO $_6$							
Bi $_2$ Ti $_2$ O $_7$							
(BiO) $_2$ Cr $_2$ O $_7$							
Bi $_2$ (SO $_4$) $_3$ · H $_2$ O							



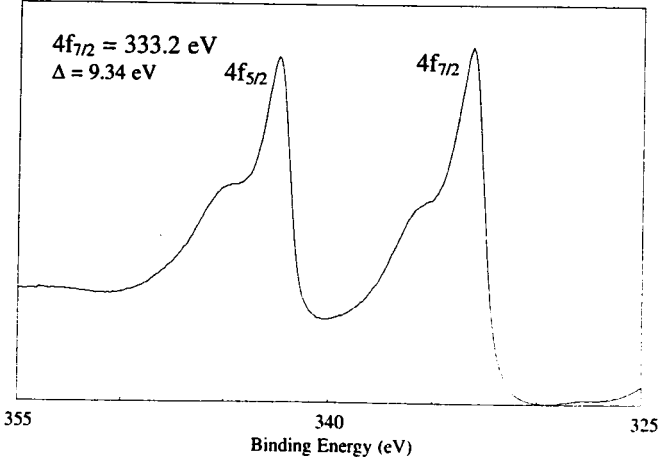


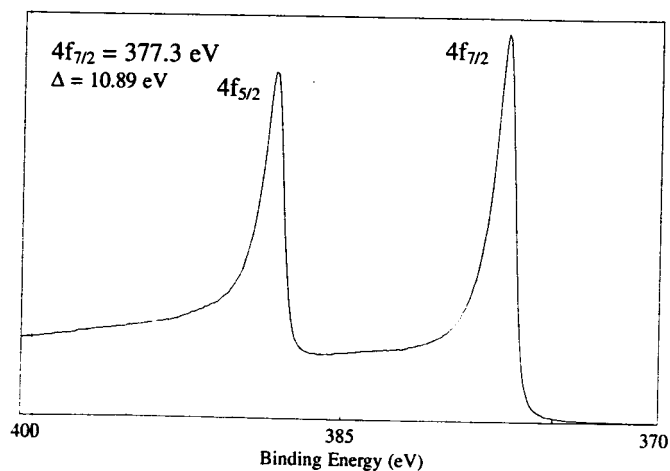
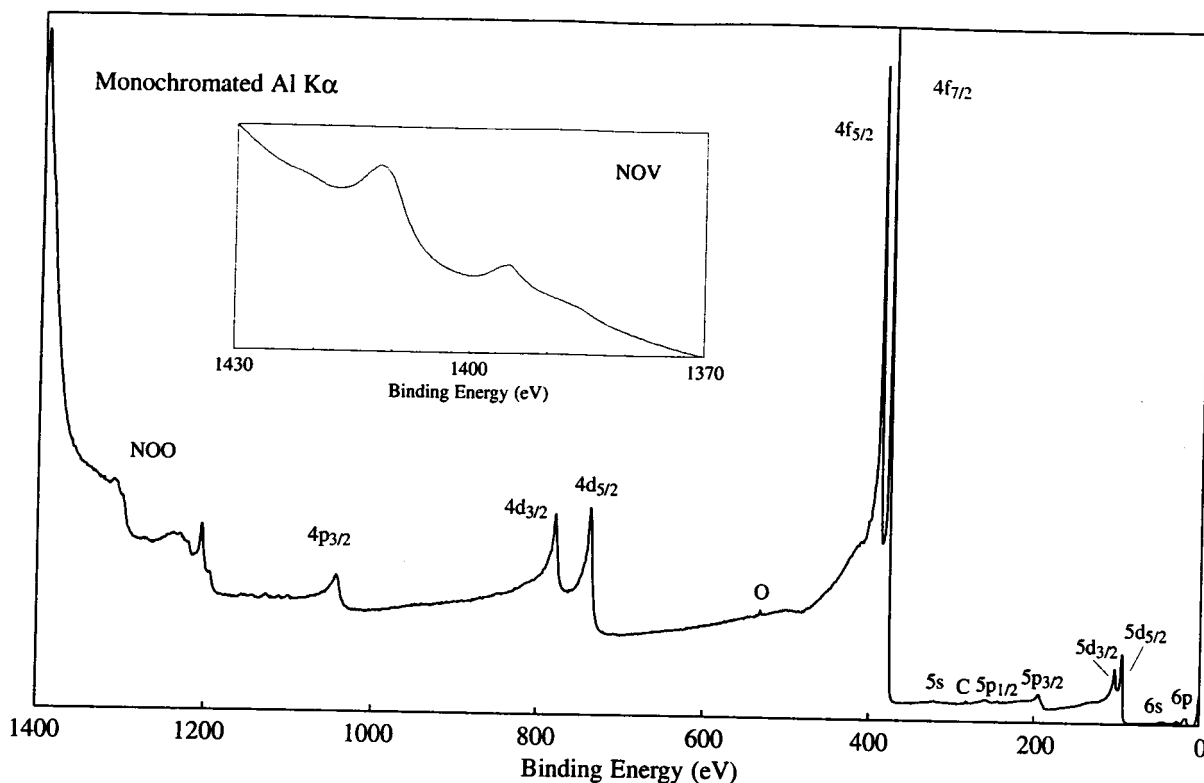
Line Positions (eV)								
Photoelectron Lines								
4s*	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	4f _{5/2}	4f _{7/2}		
1330	1170	965	713	676	342	333		
5s	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}	6s	6p _{1/2}	6p _{3/2}	
294	234	177	93	85	42	25	17	
Auger Lines								
N ₆ O ₂₃ V	N ₆₇ O ₄₅ O ₄₅		N ₇ O ₄ O ₅		N ₆₇ O ₄₅ V			
1419	1404		1335		1239 (Al)			
1186	1171		1102		1006 (Mg)			
*Estimate								



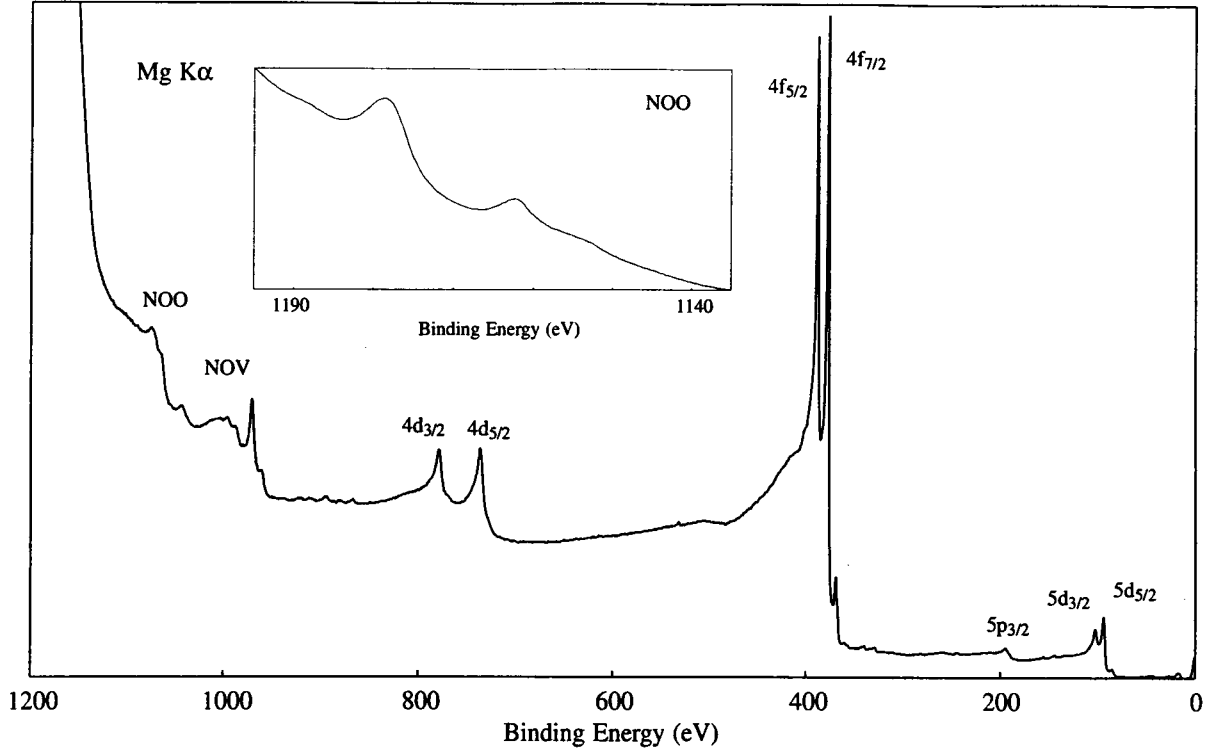
4f _{7/2} Binding Energy (eV)					
Compound Type	333	334	335	336	337
Th					
ThO ₂					
ThF ₄					

4d _{5/2} Binding Energy (eV)			
Compound Type	674	675	676
Th			
ThO ₂			

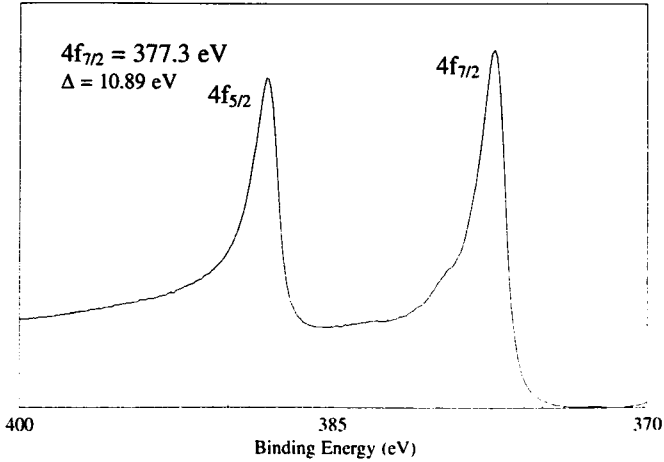




Line Positions (eV)							
Photoelectron Lines							
4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	4f _{5/2}	4f _{7/2}		
1272	1043	779	736	388	377		
5s	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}	6s	6p _{1/2}	6p _{3/2}
322	260	195	103	94	44	26	17
Auger Lines							
N ₆ O ₂₃ V	N ₇ O ₂₃ O ₅	N ₆ O ₄₅ O ₄₅	N ₆₇ O ₄₅ V				
1412	1396	1386	1204	(Al)			
1179	1163	1153	971	(Mg)			



Compound Type	4f _{7/2} Binding Energy (eV)						
	377	378	379	380	381	382	383
U	■						
Tellurides					■		
Selenides			■	■			
Sulfides			■	■			
Halides		■	■	■	■	■	
Oxides		■	■	■	■	■	
Oxy Halides		■	■	■	■	■	
U(SO ₄) ₂						■	
U(acac) ₄			■				
CaUO ₄				■			
K ₂ UF ₆							■



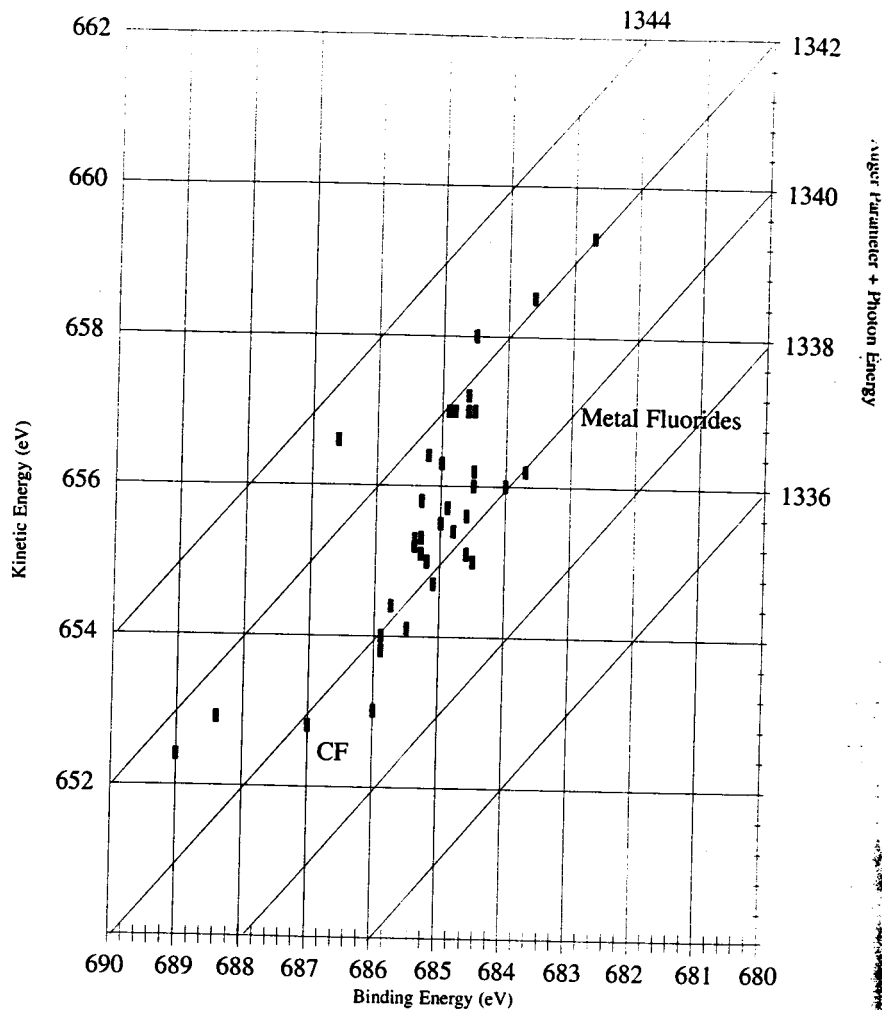
III. Appendix

Appendix A. Auger Parameters

The following tables plot the binding energy of the most intense photoelectron line versus the kinetic energy of the most intense Auger transition. The Auger parameter plots are useful for further separation of the chemical states.

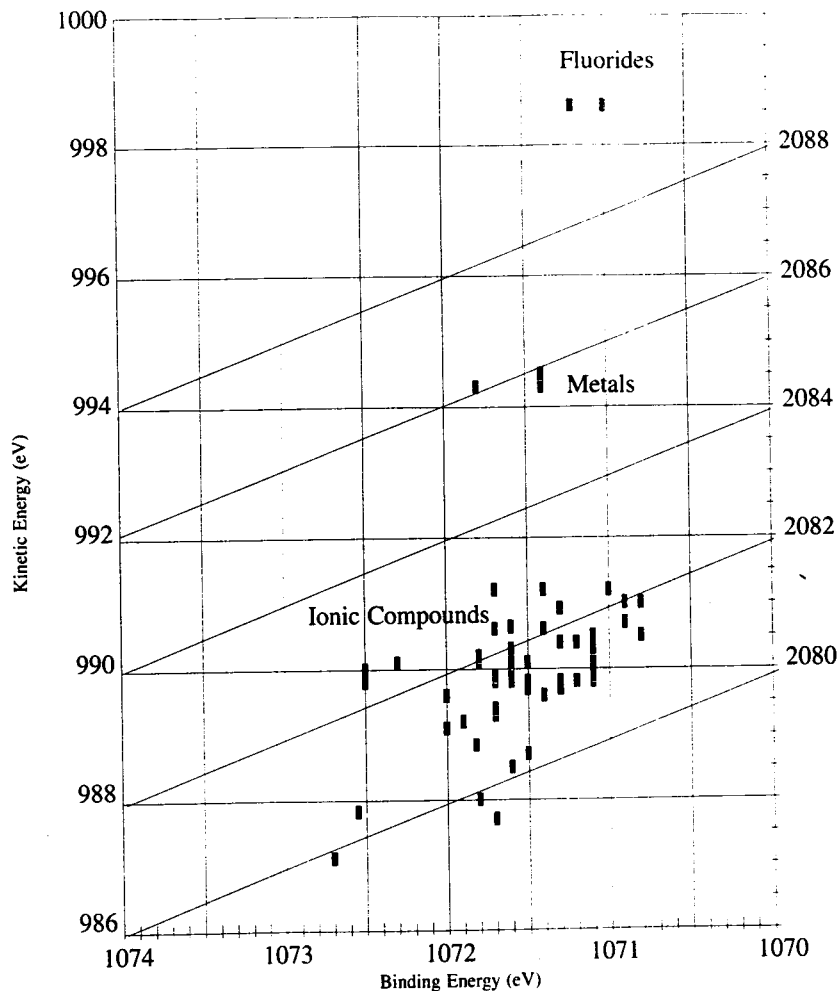
Fluorine

Compound	F 1s Binding Energy (eV)	F KLL Kinetic Energy (eV)
AgF	682.7	659.3
PbF ₂	683.6	658.5
BaF ₂	683.7	656.2
K ₃ FeF ₆	684.0	656.0
NaF	684.5	655.0
CdF ₂	684.5	656.0
CuF ₂	684.5	657.0
CuF ₂	684.5	656.2
CaF ₂	684.5	656.2
LaF ₃	684.5	658.0
ZnF ₂	684.6	655.6
PrF ₃	684.6	657.2
SmF ₃	684.6	657.0
K ₂ ZrF ₆	684.6	655.1
CaF ₂	684.8	655.4
NdF ₃	684.8	657.0
ThF ₄	684.9	657.0
K ₂ TiF ₆	684.9	655.7
SrF ₂	685.0	656.3
NiF ₂	685.0	655.5
LiF	685.1	654.7
InF ₃	685.2	656.4
K ₂ TaF ₇	685.2	655.0
YF ₃	685.3	655.8
Na ₂ TiF ₆	685.3	655.1
Na ₂ SnF ₃	685.3	655.3
HfF ₄	685.4	655.3
K ₂ NbF ₇	685.4	655.2
Na ₃ AlF ₆	685.5	654.1
MgF ₂	685.8	654.4
CsF	685.9	653.8
Na ₂ GeF ₆	685.9	654.0
Na ₂ SiF ₆	686.0	653.0
KSbF ₆	686.6	656.6
NaBF ₄	687.0	652.8
NiOCCF ₃	688.4	652.9
p-(CF ₂ =CF ₂)	689.0	652.4



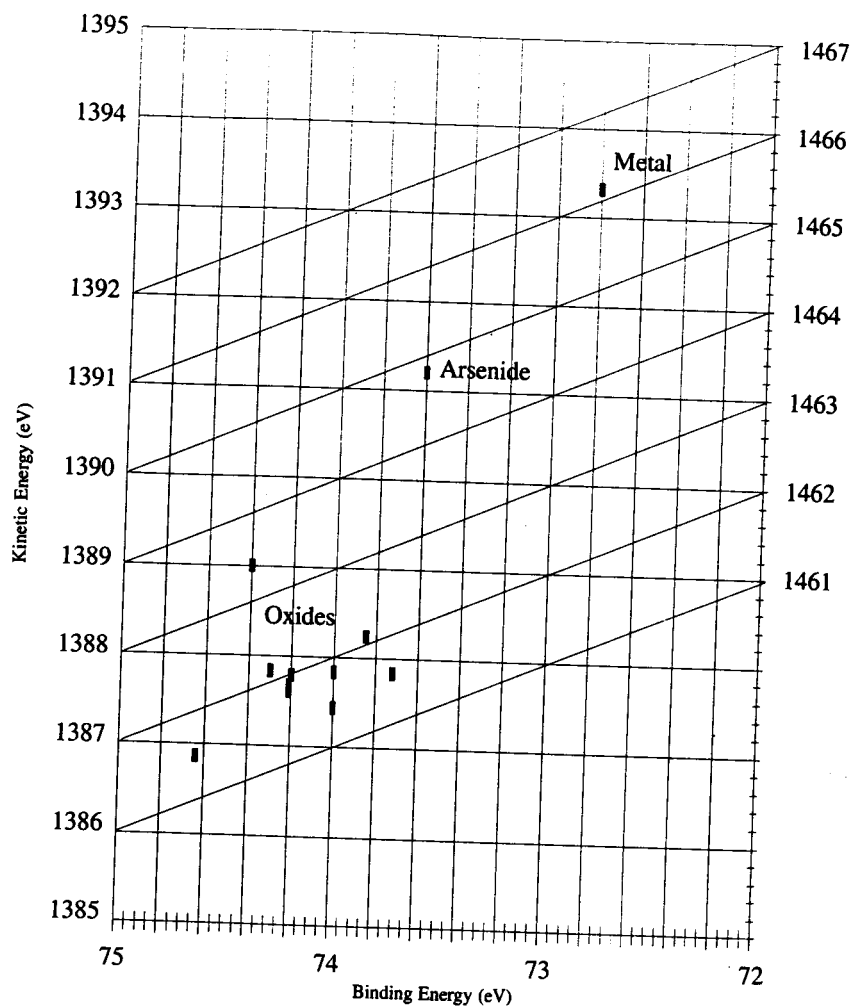
Sodium

Compound	Na 1s	Na KLL
	Binding Energy (eV)	Kinetic Energy (eV)
Na ₂ SeO ₃	1070.8	991.0
Na ₂ C ₂ O ₄	1070.8	990.5
Na ₂ MoO ₄	1070.9	991.0
NaAsO ₂	1070.9	990.7
NaF	1071.0	998.6
Na ₂ CrO ₄	1071.0	991.2
Na ₃ PO ₄	1071.1	990.1
NaH ₂ PO ₂	1071.1	989.8
Na ₂ SnO ₃ · 3H ₂ O	1071.1	990.3
NaOAc	1071.1	989.9
NaF	1071.2	998.6
Na ₂ SO ₄	1071.2	989.8
NaOOCCH ₂ SH	1071.2	990.4
Na ₂ SO ₃	1071.3	990.4
Na	1071.4	994.3
Na	1071.4	994.5
NaBr	1071.4	990.6
NaNO ₃	1071.4	989.6
Na ₂ CrO ₄	1071.4	991.2
NaCl	1071.5	990.1
Na ₂ CO ₃	1071.5	989.8
Na ₂ HPO ₄	1071.5	989.7
Na ₂ S ₂ O ₃	1071.6	990.1
NaNO ₂	1071.6	989.8
Na ₂ Cr ₂ O ₇	1071.6	990.6
NaI	1071.7	991.2
NaBr	1071.7	990.6
Na ₂ CO ₃	1071.7	989.8
NaOAc	1071.7	989.9
Na	1071.8	994.3
NaCl	1071.8	990.1
NaCl	1072.5	990.0
Na ₂ O	1072.5	989.8
Mol Sieve Y	1072.6	987.8
NaBF ₄	1072.7	987.1



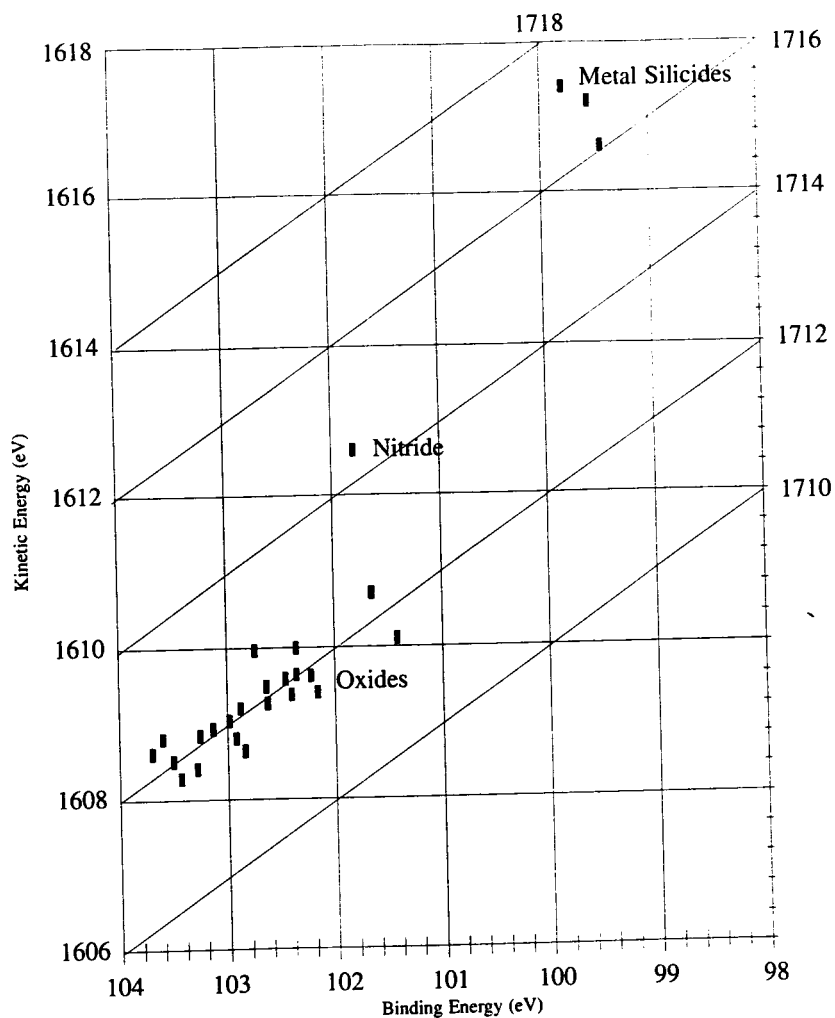
Aluminum

Compound	Al 2p	Al KLL
	Binding Energy (eV)	Kinetic Energy (eV)
Al	72.8	1393.3
AlAs	73.6	1391.2
Al ₂ O ₃ , gamma	73.7	1387.8
Al ₂ O ₃ , alpha	73.9	1388.2
Al ₂ O ₃ , gamma	74.0	1387.8
Al(OH) ₃ , gibbsite	74.0	1387.4
Al ₂ O ₃ , sapphire	74.2	1387.8
AlOOH, boehmite	74.2	1387.6
Al(OH) ₃ , bayerite	74.2	1387.7
Al ₂ O ₃ , gamma	74.3	1387.8
AlN	74.4	1389.0
Al ₂ SiO ₅ , sillimanite	74.6	1386.9



Silicon

Compound	Si 2p Binding Energy (eV)	Si (KLL) Kinetic Energy (eV)
Si	99.5	1616.6
MoSi ₂	99.6	1617.2
PdSi	99.8	1617.4
Mol Sieve A	101.4	1610.1
Hydroxysodalite	101.7	1610.7
Si ₃ N ₄	101.8	1612.6
Mol Sieve X	102.2	1609.4
Natrolite	102.2	1609.6
Mica, muscovite	102.4	1609.6
Wollastonite, Ca ₃ Si ₃ O ₉	102.4	1610.0
p-Methylsil. (linear)	102.4	1609.4
LiAlSi ₂ O ₆ , spodumene	102.5	1609.6
NaAlSi ₃ O ₈ , albite	102.6	1609.2
AlSiO ₅ , sillimanite	102.6	1609.5
p-Phenylsil. (resin)	102.7	1610.0
Mol Sieve Y	102.8	1608.7
Pyrophyllite	102.9	1609.2
p-Methylsil. (resin)	102.9	1608.8
Kaolinite	103.0	1609.0
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	103.1	1608.9
SiO ₂ , alpha cristobal	103.3	1608.8
H Zeolon	103.3	1608.4
SiO ₂ , gel	103.4	1608.3
SiO ₂ , Vycor	103.5	1608.5
SiO ₂	103.6	1608.8
SiO ₂ , quartz	103.7	1608.6



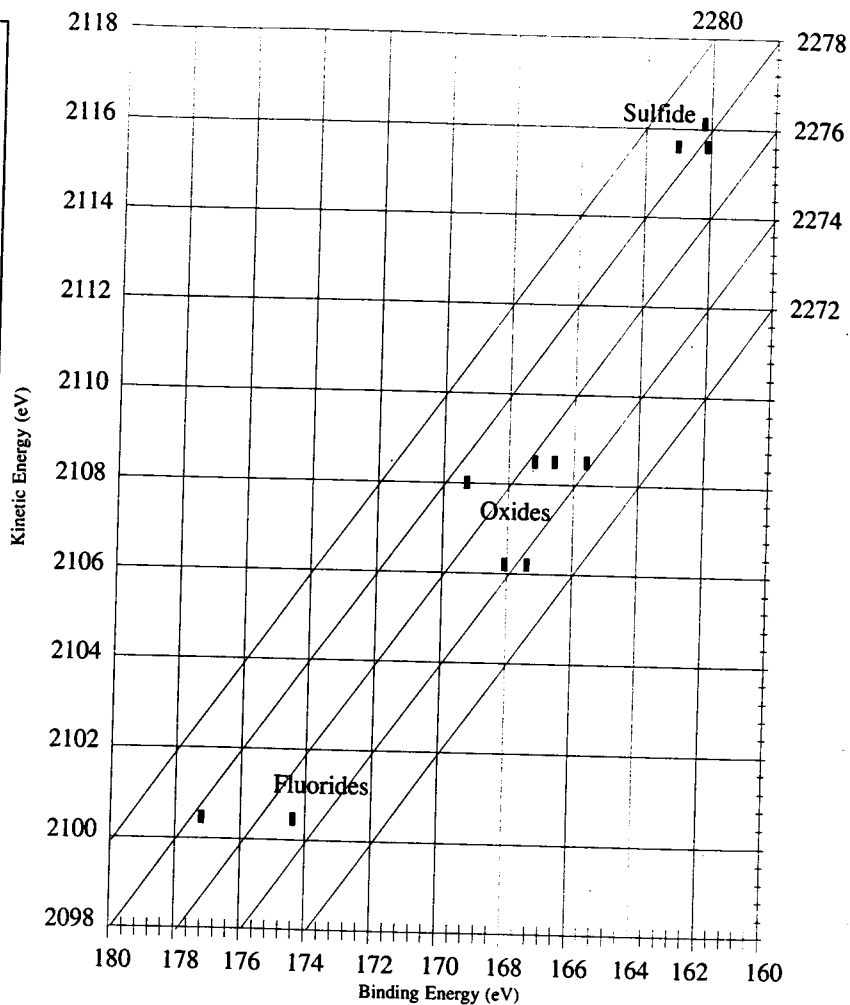
Sulfur**Compound****S 2p**

Binding Energy (eV)

S KLL

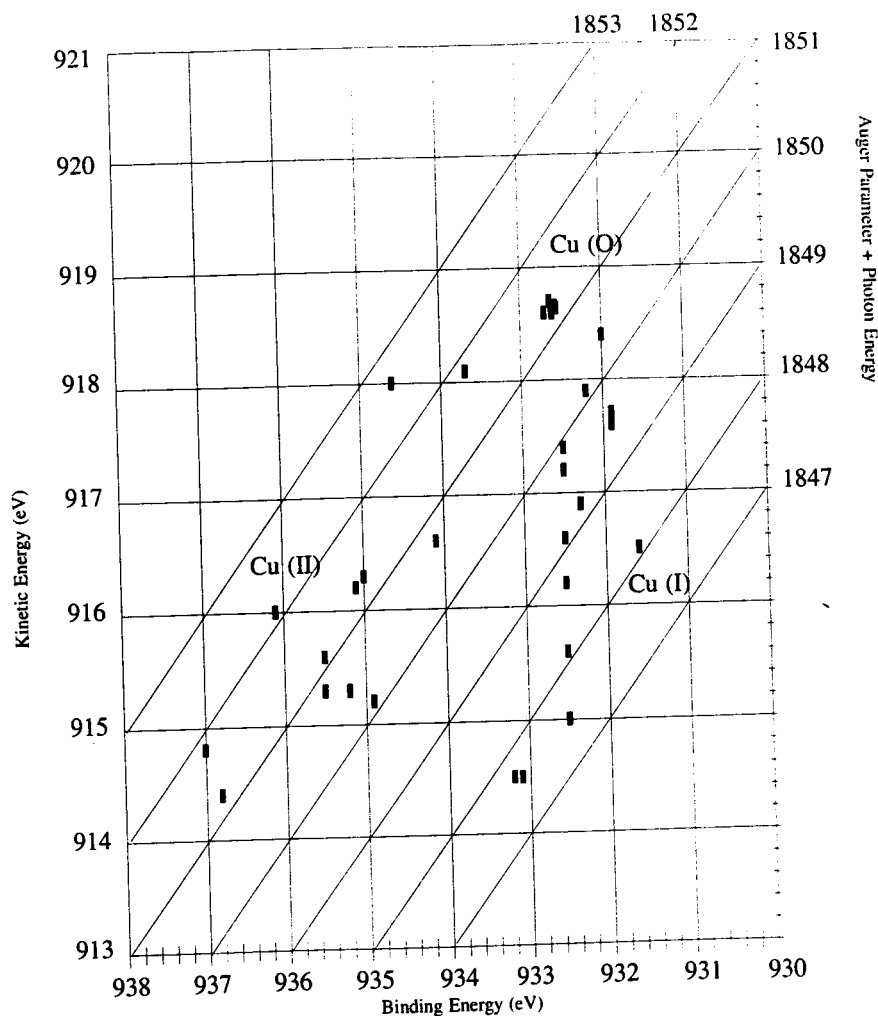
Kinetic Energy (eV)

WS ₂	162.1	2115.6
NiS	162.2	2116.1
WS ₂	163.0	2115.6
Na ₂ SO ₃	165.6	2108.5
Na ₂ SO ₃	166.6	2108.5
Na ₂ SO ₃	167.2	2108.5
SO ₂	167.4	2106.2
SO ₂	168.1	2106.2
CuSO ₄	169.3	2108.0
SF ₆	174.4	2100.5
SF ₆	177.2	2100.5



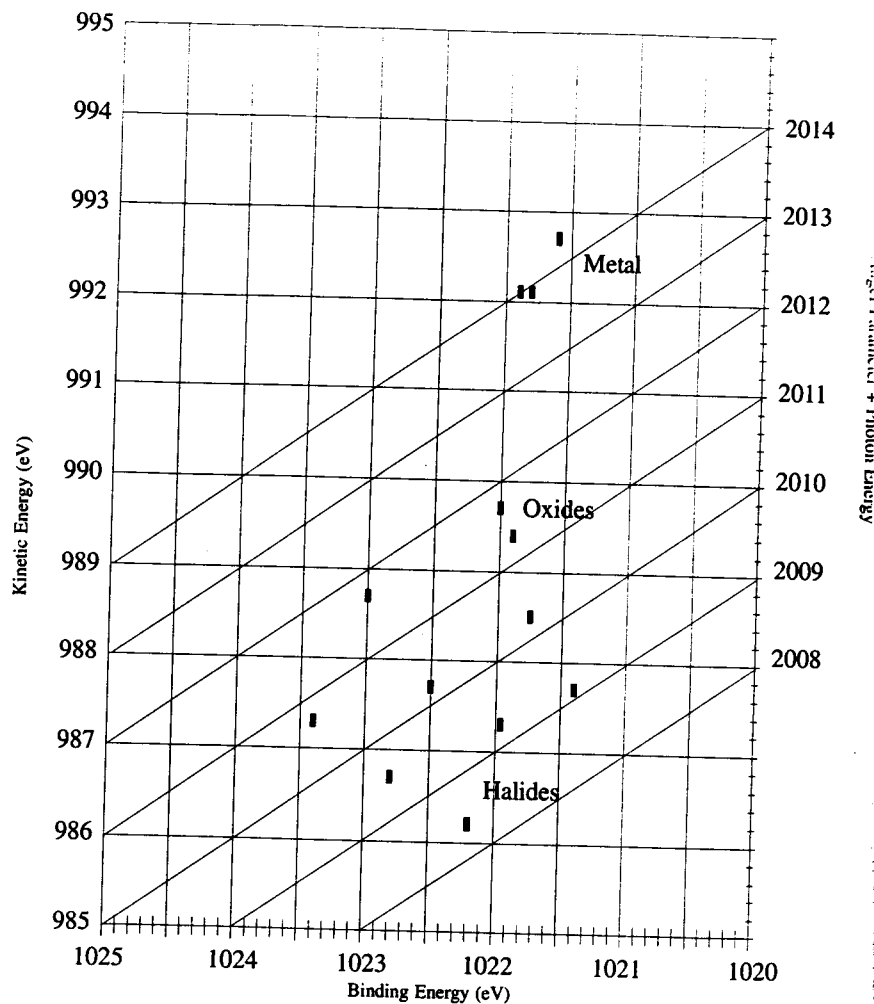
Copper

Compound	Cu 2p Binding Energy (eV)	Cu LMM Kinetic Energy (eV)
Cu ₂ Mo ₃ O ₁₀	931.6	916.5
Cu ₂ Se	931.9	917.6
Cu ₂ AgSe	931.9	917.7
Cu ₂ Se	932.0	918.4
CuS	932.2	917.9
CuBr ₂	932.3	916.9
Cu ₂ S	932.5	917.4
CuCl	932.5	915.0
CuCl	932.5	915.6
Cu ₂ O	932.5	916.2
Cu ₂ O	932.5	916.2
Cu ₂ O	932.5	916.6
Cu ₂ O	932.5	917.2
Cu	932.6	918.6
Cu	932.6	918.7
Cu ₆₄ Zn ₃₆	932.6	918.6
Cu	932.6	918.6
Cu	932.6	918.7
Cu	932.7	918.6
CuCN	933.1	914.5
CuC(CN) ₃	933.2	914.5
CuO	933.7	918.1
Cu ₃ Mo ₂ O ₉	934.1	916.6
CuMoO ₄	934.1	916.6
CuCr ₂ O ₄	934.6	918.0
CuSiO ₃	934.9	915.2
CuCO ₃	935.0	916.3
Cu(OH) ₂	935.1	916.2
CuCl ₂	935.2	915.3
Cu(NO ₃) ₂	935.5	915.3
CuSO ₄	935.5	915.6
CuF ₂	936.1	916.0
CuF ₂	936.8	914.4
CuF ₂	937.0	914.8



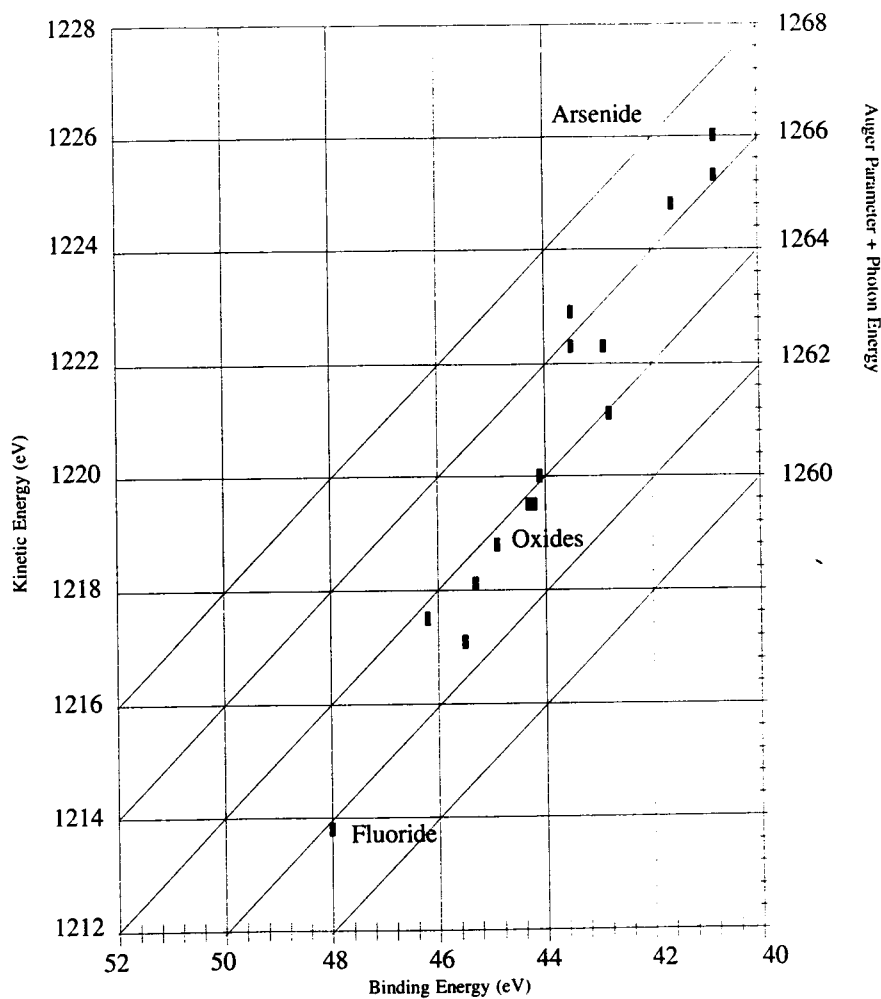
Zinc

Compound	Zn 2p _{3/2}	Zn LMM
	Binding Energy (eV)	Kinetic Energy (eV)
Zn(acac) ₂	1021.4	987.7
Cu ₆₄ Zn ₃₆	1021.6	992.7
ZnO	1021.75	988.5
Zn	1021.8	992.1
Zn	1021.89	992.1
ZnCl ₂	1021.9	989.4
Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O	1021.96	987.3
ZnS	1022	989.7
ZnF ₂	1022.2	986.2
ZnO	1022.5	987.7
ZnF ₂	1022.8	986.7
ZnI ₂	1023	988.7
ZnBr ₂	1023.4	987.3



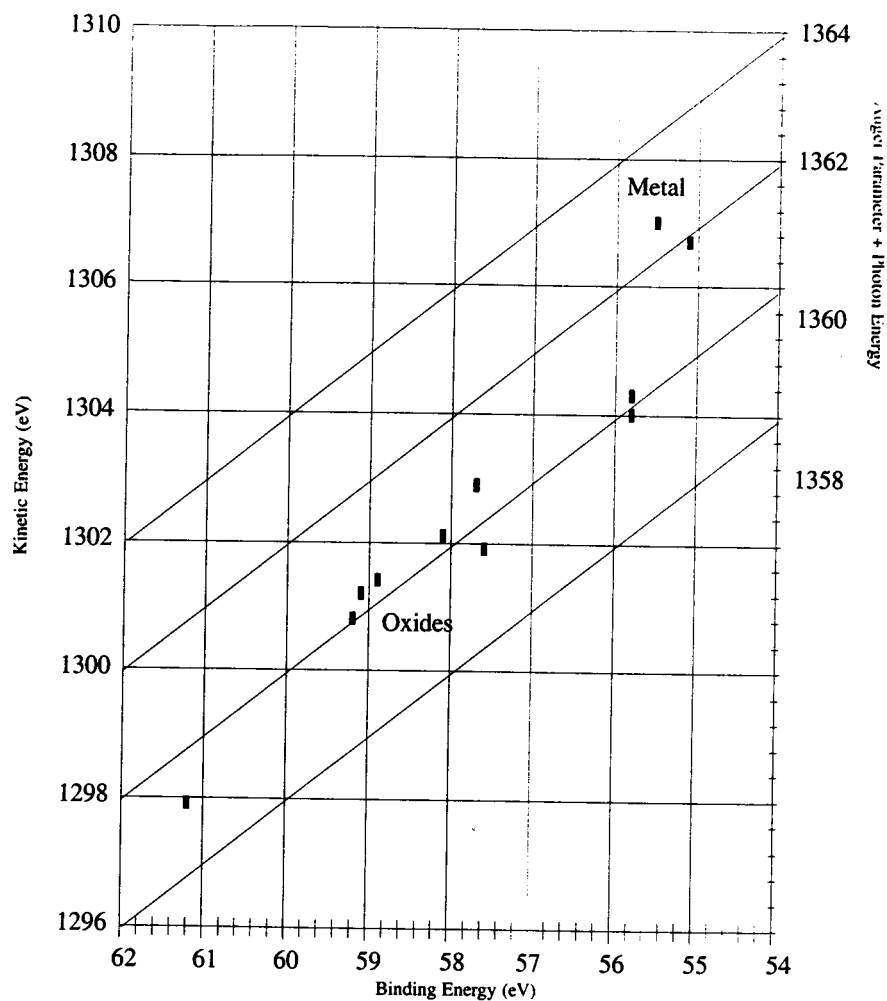
Arsenic

Compound	As 3d	As LMM
	Binding Energy (eV)	Kinetic Energy (eV)
NbAs	40.8	1226.0
GaAs	40.8	1225.3
As	41.6	1224.8
Ph ₃ As	42.8	1221.1
As ₂ Se ₃	42.9	1222.3
AsI ₃	43.5	1222.9
MeAsI ₂	43.5	1222.3
Ph ₃ AsS	44.1	1220.0
NaAsO ₂	44.2	1219.5
Ph ₃ AsO	44.3	1219.5
As ₂ O ₃	44.9	1218.8
AsBr ₃	45.3	1218.1
NaH ₂ AsO ₄	45.5	1217.1
As ₂ O ₅	46.2	1217.5
KAsF ₆	48.0	1213.8



Selenium

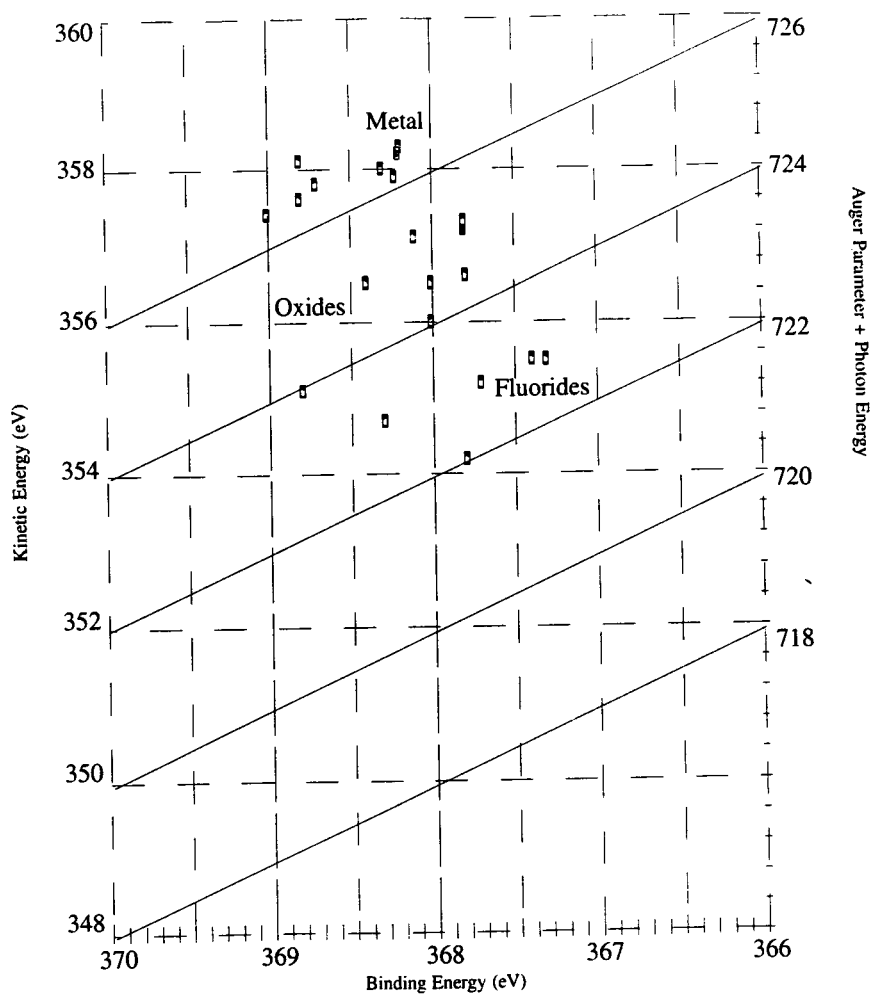
Compound	Se 3d Binding Energy (eV)	Se LMM Kinetic Energy (eV)
Se	55.1	1306.7
Se	55.5	1307.0
Ph ₂ Se	55.8	1304.0
Ph ₂ Se ₂	55.8	1304.3
Ph ₂ SeO	57.6	1301.9
Cl ₂ SePh ₂	57.7	1302.9
I ₂ SePh ₂	58.1	1302.1
SeO ₂	58.9	1301.4
Na ₂ SeO ₃	59.1	1301.2
H ₂ SeO ₃	59.2	1300.8
H ₂ SeO ₄	61.2	1297.9



Silver

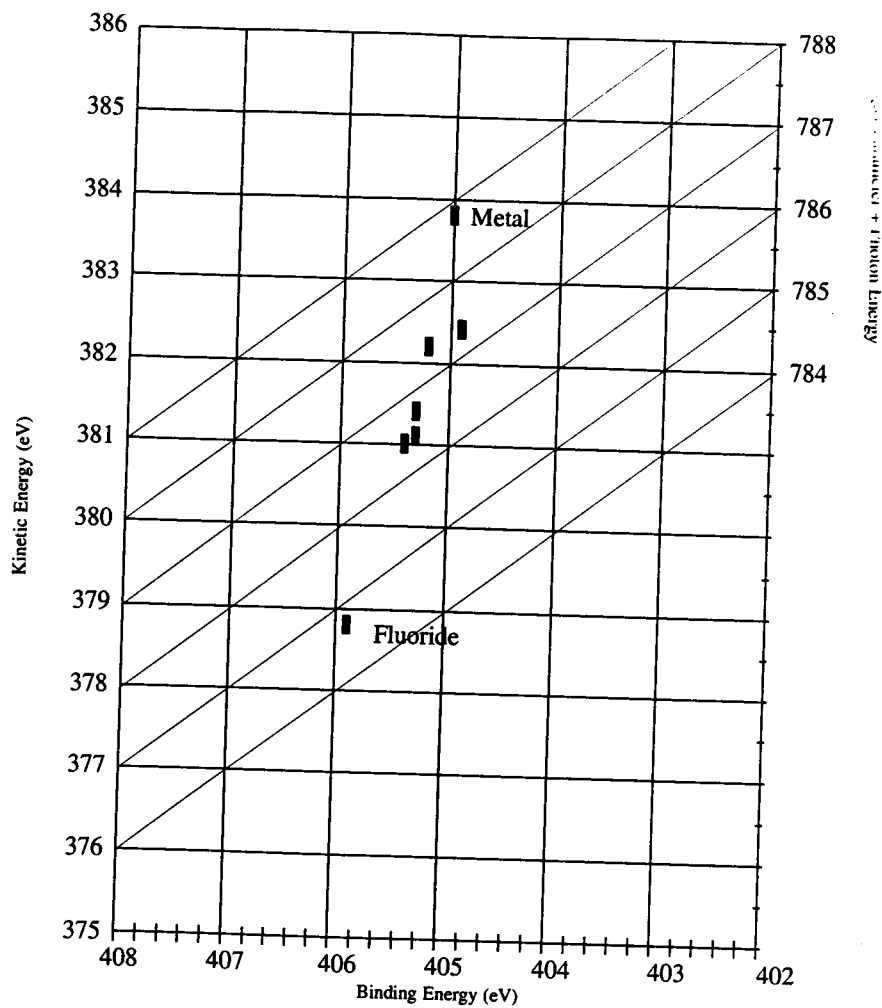
Compound	Ag 3d Binding Energy (eV)	Ag M ₄ N ₅ N ₅ Kinetic Energy (eV)
AgF ₂	367.3	355.6*
AgO	367.4	355.5
AgF	367.7	355.3*
CuAgSe	367.8	357.3*
Ag ₂ Se	367.8	357.4*
Ag ₂ O	367.8	356.6
Ag ₂ SO ₄	367.8	354.2
AgI	368.0	356.1*
AgO	368.0	356.6*
Ag ₂ S	368.1	357.2*
Ag	368.2	358.2
Ag	368.2	357.9
Mg ₂₁ Ag ₇₉	368.3	358.1*
Ag ₂ SO ₄	368.3	354.7
Ag ₂ O	368.4	356.6*
Mg ₃₀ Ag ₅₀	368.7	357.9*
Al ₄₀ Ag ₆₀	368.8	357.7*
Mg ₉₇ Ag ₃	368.8	358.2*
AgOOCF ₃	368.8	355.1
Al ₉₅ Ag ₅	369.0	357.5*

* 6.0 eV added to the kinetic energy data on M₅N₅N₅ to obtain kinetic energy of M₄N₅N₅ line.

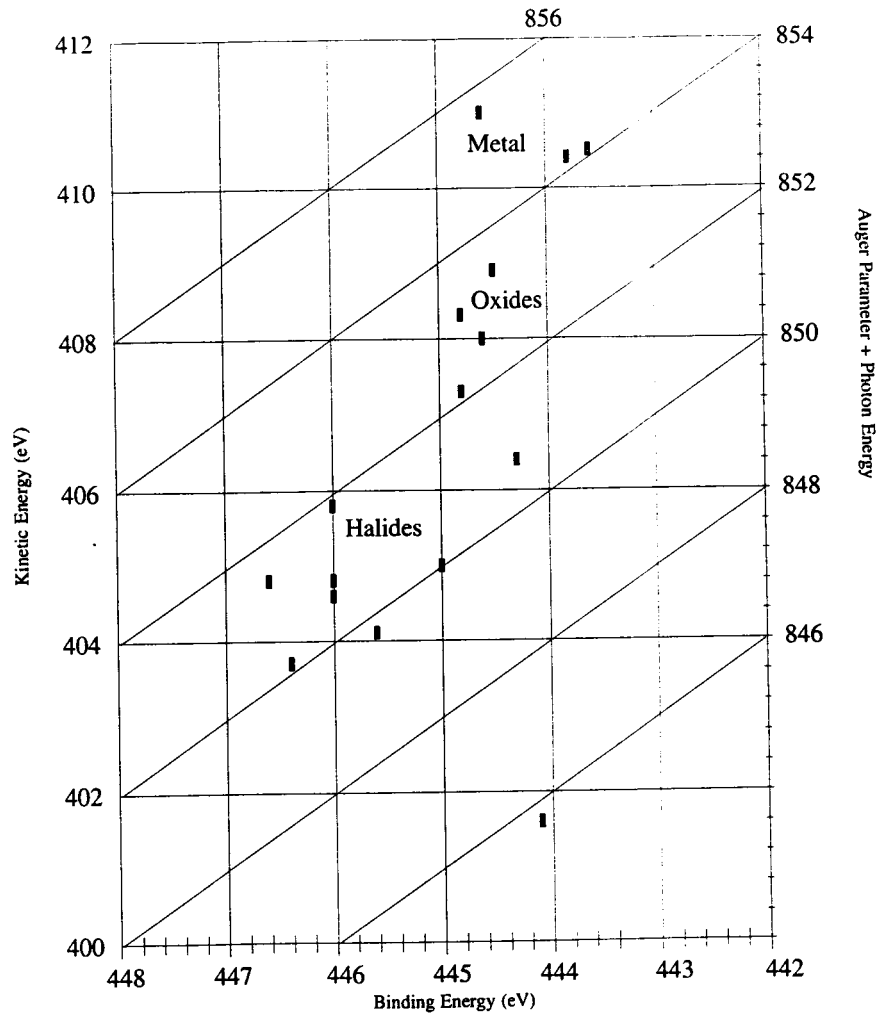


Cadmium

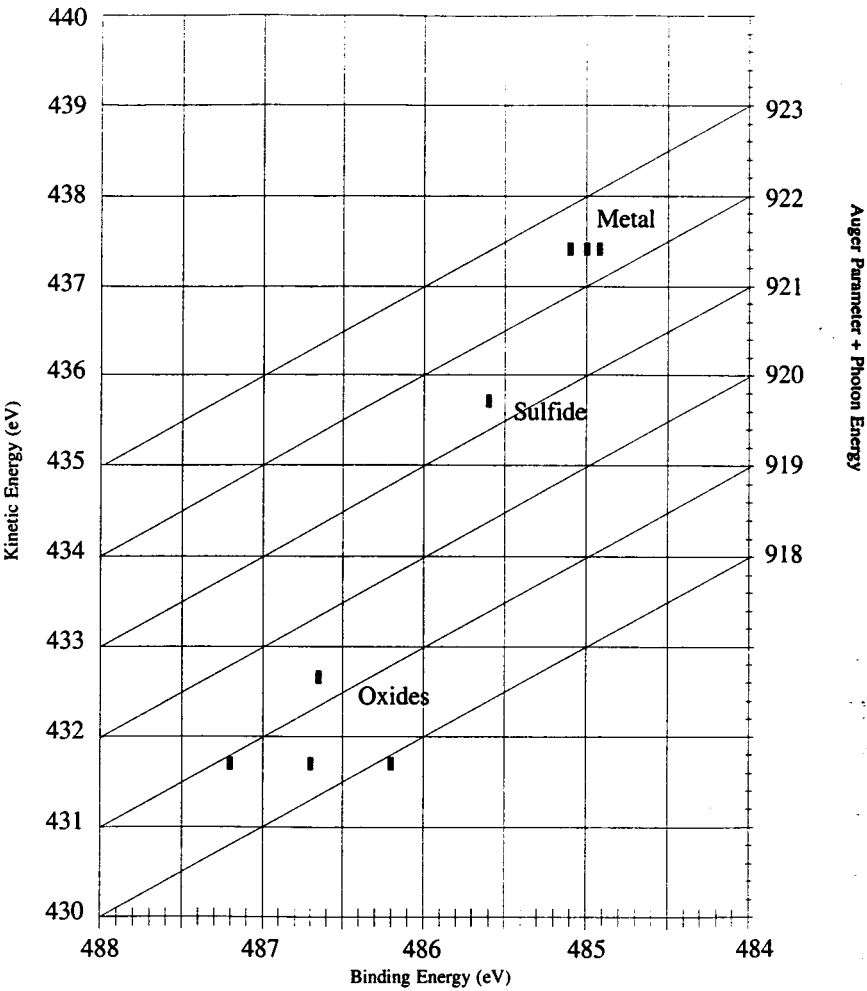
Compound	Cd 3d _{5/2}	Cd MNN
	Binding Energy (eV)	Kinetic Energy (eV)
CdTe	404.9	382.4
Cd	405.0	383.8
CdO	405.2	382.2
CdSe	405.3	381.4
CdS	405.3	381.1
CdI ₂	405.4	381.0
CdF ₂	405.9	378.8



Indium		
Compound	In 3d5/2 Binding Energy (eV)	In MNN Kinetic Energy (eV)
In ₉₅ Sn ₅	443.6	410.5
In	443.8	410.4
InSb	444.1	401.6
In ₂ O ₃	444.3	406.4
In ₂ Te ₃	444.5	408.9
InP	444.6	408.0
InP	444.6	411.0
In ₂ Se ₃	444.8	408.3
In ₂ S ₃	444.8	407.3
In(OH) ₃	445.0	405.0
(NH ₄) ₃ InF ₆	445.6	404.1
InI ₃	446.0	405.8
InBr ₃	446.0	404.8
InCl ₃	446.0	404.6
InF ₃	446.4	403.7
InBr ₃	446.6	404.8

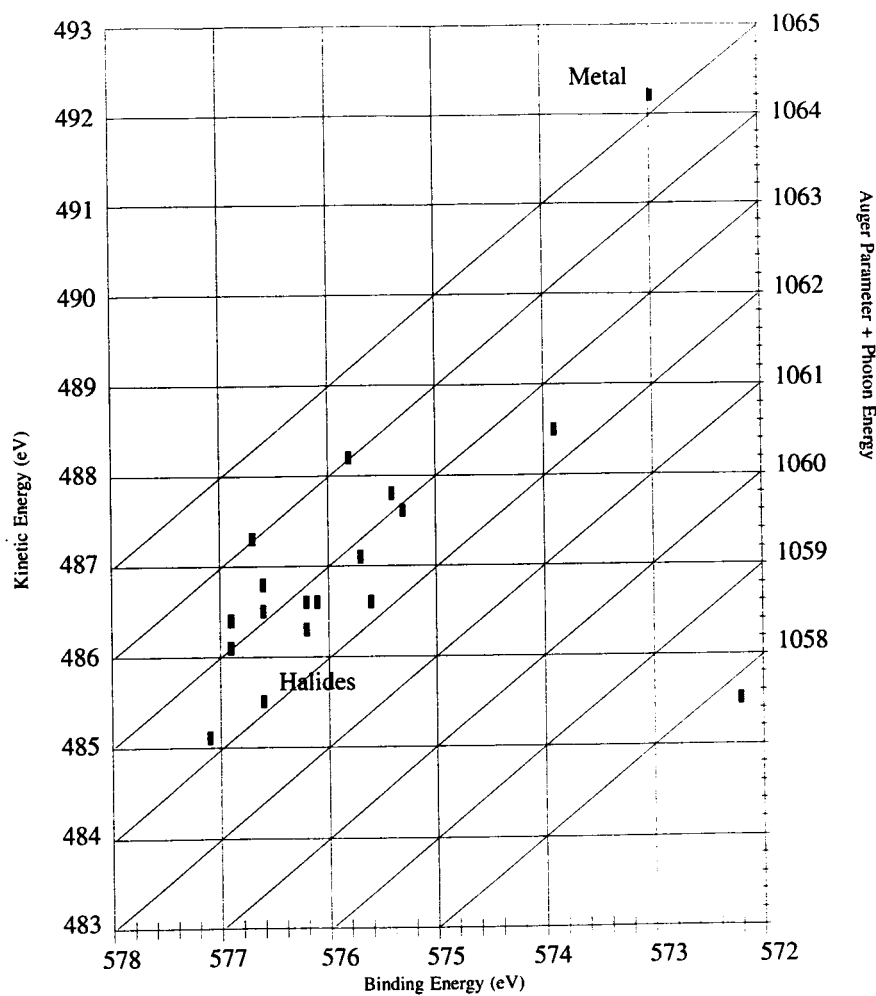


Tin		
Compound	Sn 3d _{5/2}	Sn MNN
	Binding Energy (eV)	Kinetic Energy (eV)
Sn	484.9	437.4
Sn	485.0	437.4
Sn	485.1	437.4
SnS	485.6	435.7
Na ₂ SnO ₃	486.2	431.7
SnO ₂	486.7	432.7
Na ₂ SnO ₃	486.7	431.7
Na ₂ SnO ₃	487.2	431.7
NaSnF ₃	487.4	430.8



Tellurium

Compound	Te 3d _{5/2}	Te MNN
	Binding Energy (eV)	Kinetic Energy (eV)
Na ₂ Te	572.2	485.5
Te	573.0	492.2
Ph ₂ Te ₂	573.9	488.5
I ₂ TeEt ₂	575.3	487.6
I ₂ TePh ₂	575.4	487.8
I ₂ TeMe ₂	575.6	486.6
TeO ₂	575.7	487.1
I ₃ TePh	575.8	488.2
p-tolylTeOOH	576.1	486.6
Cl ₂ TePh ₂	576.2	486.3
Br ₂ TePh ₂	576.2	486.6
TeO ₃	576.6	485.5
Br ₃ TePh	576.6	486.8
Br ₃ TeBu	576.6	486.5
TeBr ₂	576.7	487.3
TeCl ₄	576.9	486.1
(NH ₄) ₂ TeCl ₆	576.9	486.4
Te(OH) ₆	577.1	485.1



Appendix B. Chemical States Tables

This compilation of all the elements, listed alphabetically, provides specific binding energies of various compounds and pure elements, and a reference in abbreviated notation. When Auger lines are listed, they are in kinetic energy. For compounds with more than one chemical state, an asterisk denotes the atom whose binding energy is listed. The references are expanded in Appendix C. Any listing with a Φ refers to the work contained in this handbook.

This appendix, most of which was compiled by Dr. Charles Wagner for Physical Electronics, is part of the chemical state identification algorithm of the PHI software and is also the basis for the XPS database SRD-20 of the National Institute for Standards and Technology (NIST). Further references may also be found in the journal Surface Science Spectra published by the American Vacuum Society.

Ag 3d			Ag₂Se(M₅N₅N₅)			351.4	RRD78
Ag	368.3	Φ	Ag ₂ S(M ₅ N ₅ N ₅)			351.2	RRD78
Ag	368.2	Asam76	AgI(M ₅ N ₅ N ₅)			350.1	GaWi77
Ag	368.2	BiSw80	AgF(M ₅ N ₅ N ₅)			349.3	GaWi77
Ag	368.1	BiSw80	AgF ₂ (M ₅ N ₅ N ₅)			349.6	GaWi77
Ag	368.2	BiSw80	Ag ₂ O			356.6	Scho73
Ag	368.2	JHBK73	Ag ₂ O(M ₅ N ₅ N ₅)			350.6	RRD78, GaWi77
Ag	368.2	NyMa80	AgO			355.5	WRDM79
Ag	368.2	HGW75, Scho73, WRDM79,	AgO(M ₅ N ₅ N ₅)			350.6	GaWi77
Ag	368.2	GaWi77, SFS77, Wagn75	Ag ₂ SO ₄			354.2	Wagn75
Ag	368.2	RRD78, Scho72	Ag ₂ SO ₄			354.7	TMR80
Ag	368.2	HSBS81	AgOOCF ₃			355.1	Wagn75
Ag ₉₅ Sn ₅	368.0	WeAn80					
Al ₄₀ Ag ₆₀	368.8	WeAn80	Al 2p				
Al ₉₅ Ag ₅	369.0	WeAn80	Al		72.9	Φ	
Mg ₂₁ Ag ₇₉	368.3	WeAn80	Al ₂ O ₃ , sapphire		74.4	Φ	
Mg ₃₀ Ag ₅₀	368.7	WeAn80	Al		72.8	LMKJ75, Tayl82, WPHK82,	
Mg ₉₇ Ag ₃	368.8	WeAn80				WRDM79, WaTa80	
Ag ₂ Yb	368.8	WWC78	AlB ₂		71.9	MECC73	
CuAgSe	367.8	RRD78	AlAs		73.6	Tayl82	
Ag ₂ Se	367.8	RRD78	AlGaAs		73.6	Tayl82	
Ag ₂ S	368.1	RRD78	Fe ₃ Al		73.4	ShT75	
AgI	368.0	GaWi77	LiAlH ₄		75.6	MSC73	
AgF	367.7	GaWi77	AlN		74.4	MSC73	
AgF ₂	367.3	GaWi77	Al ₂ S ₃		74.6	MSC73	
Ag ₂ O	367.8	HGW75, GaWi77, Scho73	AlI ₃		74.6	MSC73	
Ag ₂ O	368.4	RRD78	AlBr ₃		75.2	MSC73	
AgO	367.4	HGW75, GaWi77, Scho73	AlCl ₃		74.7	MSC73	
AgO	368.0	WRDM79	AlF ₃		76.3	MSC73	
Ag ₂ CO ₃	367.5	HGW75	Al ₂ (MoO ₄) ₃		74.2	PCLH76	
Ag ₂ SO ₄	367.8	TMR80	Al ₂ (WO ₄) ₃		74.3	NgHe76	
Ag ₂ SO ₄	368.3	Wagn75	CoAl ₂ O ₄		73.6	PCLH76	
AgOOCF ₃	368.8	Wagn75	MgAl ₂ O ₄		74.7	HNUW78	
Ag(OAc)	368.4	HHDD81	NiAl ₂ O ₄		74.2	LFWS79, NgHe76	
Ag(3-Cl-pyridin) ₂ NO ₃	368.6	SmWa77	NiAl ₂ O ₄		74.3	Nefe82, MSC73, NSLS77	
			Al ₂ O ₃		74.7	KIHe83, NGDS75	
			Al ₂ O ₃		74.7	Tayl82, WPHK82	
			Al ₂ O ₃ , sapphire		74.2	WPHK82	
			Al ₂ O ₃ , alpha		73.9	WPHK82	
			Al ₂ O ₃ , gamma		73.7	WPHK82	
			Al ₂ O ₃ , gamma		74.0	Barr83	
			Al ₂ O ₃ , gamma		74.3	NgHe76	
			AlO ₂ H, boehmite		74.2	Tayl82, WPHK82	
			Al(OH) ₃ , bayerite		74.2	Tayl82, WPHK82	
			Al(OH) ₃ , gibbsite		74.0	WPHK82	
			Al ₂ SiO ₅ , kyanite		74.7	AnSw74	
			Al ₂ SiO ₅ , mullite		74.8	AnSw74	
			Al ₂ SiO ₅ , sillimanite		74.6	AnSw74, WPHK82	
			Albite, NaAlSi ₃ O ₈		74.3	WPHK82	
Ag M₄N₅N₅							
Ag	357.9	WRDM79					
Ag	358.2	Wagn75					
Ag (M ₅ N ₅ N ₅)	351.9	RRD 78, PWA 79					
Ag (M ₅ N ₅ N ₅)	351.6	GaWi77					
Ag	358.3	Scho73, FKWF77					
Ag	351.7	WeAn80					
Al ₄ OAg ₆₀ (M ₅ N ₅ N ₅)	351.5	WeAn80					
Al ₉₅ Ag ₅ (M ₅ N ₅ N ₅)	352.1	WeAn80					
Mg ₂₁ Ag ₇₉ (M ₅ N ₅ N ₅)	351.9	WeAn80					
Mg ₃₀ Ag ₅₀ (M ₅ N ₅ N ₅)	352.2	WeAn80					
Mg ₉₇ Ag ₃ (M ₅ N ₅ N ₅)	351.3	RRD78					
CuAgSe (M ₅ N ₅ N ₅)							

Bentonite	75.0	Barr83	As ₄ S ₄	43.1	BWWI76
Kaolinite	74.6	Barr83, WPHK82	As ₂ S ₃	43.4	BWWI76
Mica, muscovite	74.3	WPHK82	As ₂ S ₅	44.4	SMAV72
Natrolite	74.3	WPHK82	AsI ₃	43.5	BWWI76
Pyrophyllite	74.7	WPHK82	AsBr ₃	45.3	BWWI76
Spodumene	74.3	WPHK82	As ₂ O ₃	44.9	LPGC77, MINN78, Tayl82, WRDM79
H Zeolon	74.8	WPHK82	As ₂ O ₅	46.2	Bert81, BWWI76, MINN78, SMAV72
Hydroxysodalite	75.0	WPHK82	KH ₂ AsO ₄	46.7	SMAV72
Mol Sieve A	73.6	WPHK82, Barr83	NaH ₂ AsO ₄	45.5	WRDM79
Al(acac) ₃	72.9	MSC73	NaAsO ₂	44.2	Tayl82, WRDM79
Al KLL					
Al	1393.3	WPHK82, WaTa80	K ₃ AsO ₄	44.4	SMAV72
AlAs	1391.2	Tayl82	Na ₃ AsO ₄	44.9	SMAV72
AlN	1389.0	TaRa81	Na ₄ As ₂ O ₇	45.4	SMAV72
Al ₂ O ₃ , sapphire	1387.8	Tayl82, WPHK82	KAsF ₆	48.0	SMAV72, WRDM79
Al ₂ O ₃ , alpha	1388.2	WPHK82	LiAsF ₆	49.4	SMAV72
Al ₂ O ₃ , gamma	1387.8	WPHK82	Ph ₃ As	42.8	HVV79, SMAV72
AlOOH	1387.6	WPHK82, Tayl82	Ph ₃ AsS	44.1	BWWI76, HVV79
Al(OH) ₃ , bayerite	1387.7	WPHK82, Tayl82	Ph ₃ AsO	44.3	BWWI76, SMAV72, HVV79
Al(OH) ₃ , gibbsite	1387.4	WPHK82	Ph ₃ As(OH) ₂	44.5	SMAV72
Al ₂ SiO ₅ , sillimanite	1386.9	WPHK82	MeAsI ₂	43.5	BWWI76
Albite, NaAlSi ₃ O ₈	1386.5	WPHK82	Ph ₄ AsI	44.6	HVV79
Kaolinite	1386.7	WPHK82	Ph ₄ AsBr	44.6	HVV79, SMAV72
Mica, muscovite	1387.1	WPHK82	As LMM		
Natrolite	1386.5	WPHK82	As	1224.8	Wagn75, BWWI76
Pyrophyllite	1386.8	WPHK82	NbAs	1226.0	BWWI76
Spodumene	1387.1	WPHK82	GaAs	1225.3	Tayl82, WRDM79
H Zeolon	1385.5	WPHK82	As ₂ Te ₃	1225.0	BWWI76
Hydroxysodalite	1386.4	WPHK82	As ₂ Se ₃	1223.3	BWWI76
Mol Sieve	1386.9	WPHK82	As ₂ S ₃	1222.1	BWWI76
Ar 2p					
Ar in Si	241.9	Φ	AsI ₃	1222.9	BWWI76
Ar in Ag	241.2	CiHa74	AsBr ₃	1218.1	BWWI76
Ar in Ag	241.9	KiWi75	As ₂ O ₃	1218.8	Tayl82, WRDM79, BWWI76
Ar in Au	240.3	CiHa74	As ₂ O ₅	1217.5	BWWI76
Ar in Au	240.7	KiWi75	NaH ₂ AsO ₄	1217.1	WRDM79
Ar in Cu	241.1	CiHa74	NaAsO ₂	1219.5	Tayl82, WRDM79
Ar in Pt	240.4	KiWi75	K ₂ AsF ₆	1213.8	WRDM79
Ar in graphite	241.8	KiWi75	Ph ₃ As	1221.1	BWWI76
Ar in graphite	241.5	WRDM79	Ph ₃ AsS	1220.0	BWWI76
As 3d					
As	41.6	Φ	Ph ₃ AsO	1219.5	BWWI76
As	41.6	Bert81, BWWI76, MINN78, SMAV72, UeOd81	MeAsI ₂	1222.3	BWWI76
NbAs	40.8	BWWI76	Au 4f		
AlAs	41.0	Tayl82	Au	84.0	Φ
AlGaAs	41.0	Tayl82	Au	84.1	Asam76
GaAs	40.8	LPMK74	Au	84.0	BiSw80
GaAs	40.9	GGVL79, WRDM79, Tayl82, MINN78, IMNN79	Au	83.9	BiSw80
InAs	40.6	LPMK74	Au	84.1	PEJ 82
As ₂ Se ₃	42.9	BWWI76, UeOd82	Au	84.2	ALMP82
			AuSn	84.5	FHPW73
			AuSn ₄	85.1	FHPW73
			YbAu ₂	84.6	WWC 78
			ClAuPh ₃ P	85.4	BMCK77, VVSW77

Ba 3d5/2		
Ba	780.6	Φ
Ba	779.3	VaVe80
BaS	779.8	SiWo80
BaO	779.9	WRDM79
BaO	779.6	SiWo80
BaO	779.1	VaVe80
Ba(NO ₃) ₂	780.7	CLSW83
BaCO ₃	779.9	CLSW83
BaSO ₄	780.8	Wagn77
BaSO ₄	780.4	CLSW83
BaSO ₄	779.9	SiWo80
BaCrO ₄	778.9	ACHT73
BaMoO ₄	779.1	NFS82
BaRh ₂ O ₄	779.6	NFS82
Ba MNN		
Ba	602.0	VaVe80
BaO	597.5	WRDM79
BaO	598.4	VaVe80
BaSO ₄	596.1	Wagn77
Be 1s		
Be	111.8	Φ
Be	111.7	HJGN70, SMKM77, WRDM79
BeO	113.8	HJGN70, KOK83, NFS82
BeMoO ₄	113.7	NFS82
BeRh ₂ O ₄	113.8	NFS82
BeF ₂	115.3	NKBP73
BeF ₂	116.1	HJGN70
NaBeF ₃	115.3	NKBP73
Na ₂ BeF ₄	114.7	NKBP73
Bi 4f		
Bi	157.0	Φ
Bi	156.9	SFS77
Bi	157.0	LKMP73
Bi	157.0	WRDM79, MSV73
Bi ₂ S ₃	158.9	MSV73
BiI ₃	159.3	MSV73
BiF ₃	160.8	MSV73
Bi ₂ O ₃	158.8	NGDS75
Bi ₂ O ₃	159.3	MSV73
Bi ₂ O ₃	159.8	DSBG82
BiOCl	159.9	MSV73
NaBiO ₃	159.1	MSV73
Bi ₂ MoO ₆	158.3	MaWo75
Bi ₂ Ti ₂ O ₇	159.7	MSV73
(BiO) ₂ Cr ₂ O ₇	159.6	MSV73
Bi ₂ (SO ₄) ₃ · H ₂ O	161.2	MSV73
Br 3d		
KBr	68.8	Φ
CsBr	68.1	MVS73
CsBr	69.6	Shiq78

RbBr	68.4	MVS73	Cr(CO) ₆	287.9	BCGH72, BCHM72, KTWY76, PFD73
KBr	68.8	MVS73, WaTa80	Co(CO) ₃ NO	288.2	BCGH72
NaBr	68.8	MVS73, Shlq78	Fe(CO) ₅	288.0	BCGH72
LiBr	69.2	MVS73	Fe(CO) ₂ (NO) ₂	288.2	BCGH72
CdBr ₂	69.2	SATD73	Mn ₂ (CO) ₁₀	287.5	VWVB77
CuBr ₂	68.9	VWHS81	Ni(CO) ₄	288.2	BCGH72
HgBr ₂	69.0	SATD73	(Mn(CO) ₅ Br) ₂	287.6	VWVB77
PbBr ₂	68.7	Nefe82	BrMn(CO) ₅	288.0	VWVB77
ZnBr ₂	70.0	SATD73	Ag ₂ CO ₃	288.4	HGW 75
Co(NH ₃) ₆ SbBr ₆	68.9	Tric74	BaCO ₃	289.4	CLSW83
Ni(NH ₃) ₆ Br ₂	68.7	NZB 78	CaCO ₃	289.6	CLSW83
Pt(NH ₃) ₄ Br ₂	68.4	SNMK78	CdCO ₃	289.3	HGW 75
K ₂ PtBr ₄	69.3	SNMK78	Li ₂ CO ₃	289.8	CSFG79
K ₂ PtBr ₆	69.2	SNMK78	Na ₂ CO ₃	289.4	GHHL70, HHDD81
Cs ₃ Sb ₂ Br ₉	70.8	Tric71	NaHCO ₃	290.0	GHHL70
Rb ₃ Sb ₂ Br ₉	70.1	Tric74	SiCO ₃	289.5	CLSW83
Bromanil	70.1	OYK74	CS ₂	287.0	GHHL70
Ph ₄ AsBr	66.7	HVV79	CO ₂	291.9	GHHL70
Ph ₄ SbBr	68.0	HVV79	CCl ₄	292.4	GHHL70
(Me ₄ N) ₂ ZnBr ₄	67.8	EMGK74	CF ₄	296.7	GHHL70
(Et ₄ N) ₂ MnBr ₄	67.9	EMGK74	Cyclohexane	285.2	GHHL70
(Et ₄ N) ₂ NiBr ₄	68.9	EMGK74	Benzene	284.7	GHHL70, LaFo76, CKAM72
H ₃ POBBBr ₃	69.3	HVV79	C ₆ H ₅ C*H ₃	285.1	CKM71
H ₃ PBBBr ₃	69.6	HVV79	C ₆ H ₅ CH ₃ (C*CH ₃)	285.0	CKM71
Br ₂ Pt(CH ₃ CONH) ₄	68.7	NeSa78	C ₆ H ₅ CH ₃ (C*-H)	284.5	BCDH73
Br LMM			Fe(C ₃ H ₅) ₂	284.4	KTWY76
LiBr	1389.2	Wagn78	Cr(C ₆ H ₆) ₂	286.3	GHHL70
NaBr	1388.3	Wagn78	CH ₃ C*H ₂ OH	286.9	GHHL70
KBr	1388.0	WaTa80	CH ₃ COOC*H ₂ CH ₃	289.5	CKAM72
KBrO ₃	1384.4	Wagn78	C ₆ F ₆	286.7	GHHL70
Cl ₆ H ₃ Me ₃ NBr	1390.1	Wagn78	Inositol	286.4	GHHL70
C 1s			Hydroquinone	284.8	OYK74
Graphite	284.5	Φ	(C*HCOH) ₃	286.6	GHHL70
Graphite	284.3	JHBK73	(CHC*OH) ₃	286.5	GHHL70, CITH78
Cr ₃ C ₂	282.8	RHJF69	(CH ₃ C*H ₂) ₂ O	287.7	GHHL70
Fe ₃ C	283.9	ShTr75	HCHO	287.6	GHHL70
HfC	280.8	RHJF69	(CH ₃ C*HO) ₃	287.9	GHHL70
Mo ₂ C	282.7	RHJF69	CH ₃ C*OCH ₃	288.5	GHHL70
NbC	281.9	RHJF69	CF ₃ C*OCH ₃	292.6	GHHL70
Ni ₃ C	283.9	SiLe78	C*F ₃ COCH ₃	288.3	GHHL70
TaC	281.9	RHJF69	(CO) ₆	289.3	GHHL70
TiC	281.6	RHJF69, IKIM73	CH ₃ C*OOH	288.2	HHDD81
VC	282.2	RHJF69	CH ₃ C*OONa	288.8	GHHL70
WC	282.8	RHJF69, CoRa76	CH ₃ C*OONa	288.3	HHDD81
ZrC	281.1	RHJF69	HOOCOOH	289.9	GHHL70
KCN	286.1	Vann76	(COONa) ₂	289.0	GHHL70
NaCN	286.2	Vann76	CF ₃ C*OOEt	290.4	GHHL70
K ₃ Co(CN) ₆	285.9	Vann76	C*F ₃ COOEt	292.9	GHHL70
K ₃ Cr(CN) ₆	283.9	Vann76, ZeHa71	Cl ₃ C*COONa	289.5	GHHL70
K ₃ Fe(CN) ₆	283.9	Vann76, ZeHa71	Cl ₃ CC*OONa	288.3	GHHL70
K ₄ Fe(CN) ₆	283.5	Vann76	F ₃ C*COONa	292.1	GHHL70
K ₃ Mn(CN) ₆	284.0	Vann76	F ₃ CC*OONa	288.9	GHHL70
Na ₄ Mn(CN) ₆	284.0	Vann76	p-Benzoquinone	287.4	OYK74
K ₄ V(CN) ₆	285.5	Vann76			

Φ PHYSICAL ELECTRONICS

Hg _{0.8} Cd _{0.2} Te	404.6	SBB80	K ₂ ReCl ₆	198.4	CoHe72
CdTe	404.9	SBB80, GaWi77	K ₂ ReCl ₆	199.3	LeBr72
CdSe	405.3	GaWi77	K ₂ SnCl ₆	198.4	CoHe72
CdS	405.3	GaWi77	K ₂ WCl ₆	199.0	LeBr72
CdI ₂	405.4	GaWi77	K ₃ IrCl ₆	198.7	NSBN77
CdBr ₂	406.0	SATD73	K ₃ RhCl ₆	198.4	SNMK78
CdCl ₂	406.1	SATD73	K ₄ Mo ₂ Cl ₈	198.8	HUGH79
CdF ₂	405.9	GaWi77, SATD73, Wagn77	Na ₂ PdCl ₄	199.3	SeTs76
CdO	405.2	GaWi77, NGDS75, NFS82, SBB80	Co(NH ₃) ₆ SbCl ₆	198.9	Tric74
CdO ₂	403.6	HGW75	Pt(NH ₃) ₂ Cl ₂	198.8	CMHL77, Nefe78
Cd(OH) ₂	405.0	WRDM79, HGW75	Pt(NH ₃) ₄ Cl ₂	197.8	SNMK78
CdCO ₃	405.1	HGW75	Pt(NH ₃) ₆ Cl ₄	197.8	SNMK78
CdRh ₂ O ₄	404.7	NFS82	Rh(NH ₃) ₆ Cl ₃	198.1	Nefe78
Cd MNN			Cs ₃ Sb ₂ Cl ₉	198.0	BCH75, Tric74
Cd	383.8	WRDM79, Wagn75,	CsSbCl ₆	199.2	Tric74
		GaWi77	KIrCl ₃ NO	198.9	NSBN77
CdTe	382.4	GaWi77	ICI	200.1	Sher76
CdSe	381.4	GaWi77	CsClO ₄	208.2	MVS73
CdS	381.1	GaWi77	KClO ₃	206.5	MVS73
CdI ₂	381.0	GaWi77	KClO ₄	208.8	MVS73
CdF ₂	378.8	GaWi77	LiClO ₄	209.0	MVS73
CdO	382.2	GaWi77	NaClO ₄	208.5	MVS73
Ce 3d			Ni(NH ₃) ₆ (ClO ₄) ₂	208.2	NZB78
Ce	883.8	Φ	NiClO ₄ · 6H ₂ O	208.6	NZB78
Ce	883.9	ScOs82	RbClO ₄	208.4	MVS73
CeAl ₂	883.5	LFBC80	Me ₄ NCl	196.2	EMGK74
CePd ₃	884.3	LFBC80	Eu ₄ NCl	196.4	EMGK74
CeSe	884.3	LFBC80	Ph ₄ NCl	196.1	HVV79
CeCu ₂ Si ₂	883.6	LFBC80	NH ₄ Cl	197.9	EMGK74
CeO ₂	881.8	WRDM79	Chlorobenzene	200.1	CKAM75
CeO ₂	882.4	NGDS75, SaRa80	Pentachlorobenzene	200.0	CKAM75
CeH ₃	886.0	ScOs82	ClRh(Ph ₃ P) ₃	198.0	Nefe78, OIIT79, MMRC72
Cl 2p			(Et ₃ P) ₂ PtHCl	198.0	Rigg72
KCl	198.5	Φ	(Ph ₃ P) ₂ PtHCl, trans	197.1	CBA73
CsCl	196.3	MVS73	(Et ₃ P) ₂ PtCl ₄	199.2	LeBr72, Nefe78, Rigg72
KCl	198.2	MVS73, NSLS77, YYS78	(Et ₃ P) ₂ PtCl ₂	198.1	Rigg72
NaCl	198.4	MVS73, NSLS77, SGSO70	(Ph ₃ P) ₂ NiCl ₂	199.0	BNSA70, STHU76
LiCl	198.5	MVS73, CSFG79	(Ph ₃ P) ₂ NiCl ₂	198.3	NZB78
RbCl	197.9	MVS73	Ph ₃ PBCl ₃	199.4	HVV79
CuCl ₂	200.0	VWHS81	Ph ₃ POBCl ₃	198.9	HVV79
NiCl ₂	199.4	KIHe83, TRLK73, YYS 78	(Nb ₆ Cl [*] ₁₂)Cl ₆ (Et ₄ N) ₃	199.4	BeWa79
PdCl ₂	198.9	NKBP73	(Nb ₆ Cl ₁₂)Cl [*] ₆ (Et ₄ N) ₃	197.5	BeWa79
RhCl ₃	199.3	OIIT79	CdCl ₂	199.0	SATD73
RhCl ₃ · 12H ₂ O	199.2	CMHL77	CuCl ₂	199.2	YYS78
SbCl ₅	199.7	BCH 75	HgCl ₂	198.7	SATD73
ZnCl ₂	198.5	KIHe83	InCl	198.4	FHT77
K ₂ IrCl ₆	198.6	NSBN77, LeBr72, CoHe72	InCl ₃	199.0	FHT77
K ₂ MoCl ₆	198.4	CoHe72	TiCl ₄	198.2	MRV83
K ₂ OsCl ₆	198.6	CoHe72, LeBr72	UCl ₃	198.1	TBVL82
K ₂ PdCl ₄	198.8	NKBP73	UCl ₄	197.7	TBVL82
K ₂ PtCl ₄	198.8	CMHL77, SNMK78	UOCl	198.5	TBVL82
K ₂ PtCl ₆	198.8	CoHe72, LeBr72, SNMK78	UOCl ₂	198.3	TBVL82
			ZnCl ₂	199.7	SATD73
			(NH ₄) ₂ PtCl ₄	198.2	KaEl79
			OPCl ₃	201.7	FIWe75

KClO ₃	206.5	NZK77	Br ₃ Co(Et ₄ N) ₂	780.1	EMGK74
KClO ₄	208.7	NZK77	Cl ₄ Co(Et ₄ N) ₂	780.6	EMGK74
HClPt(Ph ₃ P) ₂	197.9	AL77	Cl ₂ Co(thiourea) ₂	780.9	NBMO73
HClPt(Et ₃ P) ₂	198.0	AL77			
Cl ₂ Pt(Ph ₃ P) ₂	198.0	AL77	Cr 2p		
Ph ₃ PCuCl ₂	198.9	FSJL83	Cr	574.4	Φ
Ph ₃ PCuCl ₃	199.0	FSJL83	Cr ₂ O ₃	576.9	Φ
C ₆ H ₅ Cl	201.0	CKM71	Cr	574.3	LANM81
C ₆ H ₅ CCl ₃	201.0	CKM71	Cr	574.3	WRDM79
C(NH ₂) ₃ Cl	198.0	LeRa77	Cr ₂ N	576.1	RoRo76
p(CH ₂ =CHCl)	200.0	PRCV77, WRDM79	CrN	575.8	STAB76
			CrB ₂	574.3	MECC73
			Cr ₂ S ₃	574.8	CSC72
			CrI ₃	576.7	CSC72
			CrBr ₃	576.2	CSC72
			CrCl ₃	577.4	CSC72
			Cr ₂ O ₃	576.8	BDFP81, CDFM82, CSC72, WRDM79, NGDS75
			CrO ₂	576.3	IKK76
			CrO ₃	578.3	ACHT73
			CrF ₃	580.3	CSC72
			CrO ₃	579.8	CDFM82
			Cr(OH) ₃	577.3	CDFM82
			CrOOH	577.0	IKK76
			Cr(CO) ₆	576.3	BCGH72, BCHM72
			Cr(CO) ₆	577.0	PFD73
			Cr ₂ CrO ₄	579.8	AT76
			Cr ₂ Cr ₂ O ₇	579.5	AT76
			CuCrO ₂	576.4	ACHT73
			CuCr ₂ O ₄	577.1	CDFM82
			K ₂ Cr ₂ O ₇	579.9	NSSP80
			LaCrO ₃	575.8	HoTh80
			Li ₂ CrO ₄	579.8	ACHT73
			LiCrO ₂	577.0	ACHT73
			Na ₂ CrO ₄	579.8	ACHT73
			Na ₂ CrO ₄	580.5	LaKe76
			Na ₂ Cr ₂ O ₇	579.4	ACHT73
			Na ₃ CrO ₄	578.5	LaKe76
			Na ₄ CrO ₄	577.9	LaKe76
			NaCrO ₂	577.1	LaKe76, ACHT73
			ZnCr ₂ O ₄	577.2	BDFP81
			BaCrO ₄	579.1	AlTu76
			CaCrO ₄	578.9	ACHT73
			(NH ₄) ₃ CrF ₆	579.5	AlTu76
			Cr(NH ₃) ₆ Cl ₃	578.5	AlTu76
			K ₃ Cr(CN) ₆	576.3	Vann76, ZeHa71
			K ₃ CrF ₆	583.0	AlTu76
			Cr(acac) ₃	577.7	AlTu76
			Cr(acac) ₃	576.1	ZeHa71
			Cl ₃ Cr(urea) ₆	579.9	AlTu76
			Cr(C ₃ H ₅) ₂	574.8	BCDH73, CDH 74, GSMJ74
			Cr(C ₃ H ₅) ₂	576.3	ClAd71
			Cr(C ₃ H ₅)(C-H)	574.4	CDH74, GSMJ74
			Cr(C ₆ H ₅) ₂	574.1	CDH74
			Cr(C ₆ H ₅) ₂	575.4	PFD73
			Cr(CO) ₅ PH ₃	575.3	BCGH72
Co 2p					
Co	778.3	Φ			
CoO	778.4	Φ			
Co	778.3	LANM81			
Co	778.1	WRDM79			
Co ₂ OSn ₈₀	777.9	ThSh78			
Co ₂ B	778.0	MECC73			
CoB	778.0	MECC73			
CoS	781.9	Limo81			
CoF ₂	783.0	CSC72			
CoF ₂ · 4H ₂ O	782.6	NBMO73			
CoF ₃	782.4	CSC72			
CoO	780.2	WRDM79			
CoO	780.4	Kim75, NGDS75, NFS82, CBR76			
		NGDS75, OkHi76			
Co ₃ O ₄	780.2	GPDG79			
Co ₂ O ₄	779.5	McCo75			
Co ₂ O ₃	779.9	McCo75			
CoOOH	780.0	McCo75			
Co(OH) ₂	781.0	OkHi76			
CoAl ₂ O ₄	780.8	PCLH76			
CoAl ₂ O ₄	781.9	OkHi76			
CoCr ₂ O ₄	780.2	OkHi76			
CoFe ₂ O ₄	779.7	OkHi76			
CoMn ₂ O ₄	780.0	OkHi76			
CoMoO ₄	780.9	GPDG79			
CoMoO ₄	782.8	PCLH76			
CoRh ₂ O ₄	781.2	NFS82			
CoSO ₄	784.0	Limo81			
ZnCo ₂ O ₄	780.4	OkHi76			
Cs ₂ CoI ₄	780.5	NBMO73			
Cs ₂ CoBr ₄	780.8	NBMO73			
Cs ₂ CoCl ₄	781.0	NBMO73			
K ₃ Co(C ₂ O ₄) ₃	780.9	CSC72			
K ₃ Co(NO ₂) ₆	781.8	NBMO73			
Co(CO) ₃ NO	780.7	BCGH72			
K ₃ Co(CN) ₆	781.2	OkHi76			
K ₃ Co(CN) ₆	782.1	Vann76			
Co(NH ₃) ₃ Cl ₃	781.4	NBMO73			
Co(NH ₃) ₃ Cl ₃	781.9	YNAB77			
Co(NH ₃) ₃ Cl ₃	781.1	CSC72			
Co(NH ₃) ₃ Cl ₃	781.8	NBMO73			
Co(C ₃ H ₅) ₂	779.1	BCDH73			
Co(C ₃ H ₅) ₂	781.3	ClAd71			

$\text{Cr}(\text{CO})_5\text{NH}_3$	575.5	BCGH72, BCHM72	CuBr_2	932.3	VWHS81
$\text{Cr}(\text{CO})_5\text{C}_6\text{H}_6$	575.7	CDH74	CuCl	932.5	GaWi77, Wagn75
$\text{Cr}(\text{CO})_5\text{C}_6\text{H}_6$	576.3	PFD73	CuCl_2	934.4	GaWi77
$\text{Cr}(\text{CO})_5(\text{Me}_3\text{P})$	575.2	BCGH72, BCHM72	CuCl_2	935.2	WRDM79
$\text{Cl}_3\text{Cr}(\text{C}_5\text{H}_5)$	576.1	GSMJ74	CuCl_2	934.8	VWHS81
$\text{ICr}(\text{C}_6\text{H}_6)$	576.4	CDH74	CuCl_2	935.6	YYS78
Cr LMM			CuF_2	936.1	GaWi77
Cr	527.2	WRDM79	CuF_2	937.0	WRDM79
Cs 3d_{5/2}			CuF_2	936.8	VWHS81
Cs	726.4	Φ	Cu_2O	932.5	CDFM82, GaWi77, Wagn75,
C	726.0	KDR77			HMUZ78, MSSS81, Scho73b
CsI	723.9	MVS73	CuO	933.7	HMUZ78, GaWi77,
CsBr	724.0	MVS73			WRDM79, MSSS81
CsCl	723.7	MVS73	$\text{Cu}(\text{OH})_2$	935.1	MSSS81
CsF	724.0	MVS73	$\text{Cu}(\text{NO}_3)_2$	935.5	NZK77
CsN_3	723.6	SGRS72	CuCN	933.1	Wagn75
Cs_2SO_4	723.9	Wagn77	$\text{CuC}(\text{CN})_3$	933.2	NZK77
Cs_3PO_4	723.9	MVS73	CuCO_3	935.0	WRDM79
$\text{Cs}_4\text{P}_2\text{O}_7$	723.8	MVS73	CuSO_4	934.9	Limo81
CsClO_4	724.2	MVS73	Cu_2SO_4	935.5	NZK77
Cs_2CrO_4	724.5	ACHT73	C SiO ₃	934.9	WRDM79
$\text{Cs}_2\text{Cr}_2\text{O}_7$	723.9	ACHT73	$\text{Cu}_2\text{Mo}_3\text{O}_{10}$	931.6	HMUZ78
CsOH	724.5	WRDM79	$\text{Cu}_3\text{Mo}_2\text{O}_9$	934.1	HMUZ78
Cs MNN			CuCr_2O_4	934.6	CDFM82
Cs_2SO_4	568.4	Wagn77	CuCrO_2	932.3	ACHT73
CsOH	586.7	WRDM79	CuFe_2O_4	933.8	LDDDB80
Cu 2p			CuFeO_2	932.6	LDDDB80
Cu	932.7	Φ	CuMoO_4	934.1	HMUZ78
CuO	933.6	Φ	CuRh_2O_4	934.4	NFS82
Cu	932.6	ALMP82	$\text{Cu}(\text{OAc})_2$	931.8	BrFr74
Cu	932.6	LANM81	$\text{Cu}(\text{OAc})_2$	935.0	YYS79
Cu	932.6	BiSw80	$\text{Cu}(\text{acac})_2$	934.5	BrFr74
Cu	932.6	BiSw80	$\text{Cu}(\text{8-Hydroxyquinol.})$	935.0	BrFr74
Cu	932.7	BiSw80	Cu Salicylaldehyde	934.0	BuBu74
Cu	932.7	PEJ82	$\text{Cu}_4\text{Cu}(\text{Et}_4\text{N})_2$	932.5	EMGK74
Cu	932.6	Asam76, GaWi77, KPML73,	$\text{Cu}_2\text{Cu}(\text{H}_2\text{NCONHCONH}_2)_{20}$	935.8	YYS78
		WRDM79, Wagn75	Cu LMM		
$\text{Cu}_{64}\text{Zn}_{36}$	932.6	VanO77	Cu	918.6	BiSw80
$\text{Cu}_{95}\text{Sn}_5$	932.5	Hegd82	Cu	918.7	BiSw80
Cu_3P	932.2	NSDU75	Cu	918.6	BiSw80
Cu_3P	932.2	NSDU75	Cu	918.7	PEJ82
Cu_2Se	931.9	RRD78	Cu	918.6	KPML73, WRDM79, Wagn75,
CuSe	932.0	RRD78			Asam76, GaWi77
CuAgSe	931.9	RRD78	$\text{Cu}_{64}\text{Zn}_{36}$	918.6	VanO77
CuInSe_2	931.9	KJID81	Cu_2Se	917.6	RRD78
Cu_2S	932.5	Wagn75	CuSe	918.4	RRD78
CuS	932.2	RRD78	CuAgSe	917.7	RRD78
CuS	933.2	Limo81	Cu_2S	917.4	Wagn75
CuS	931.9	BSRR81	CuS	917.9	RRD78
CuS	935.0	NSSP80	CuBr_2	916.9	VWHS81
CuBr	932.1	BrFr74	CuCl	915.0	Wagn75
			CuCl	915.6	GaWi77
			CuCl_2	915.3	WRDM79, VWHS81, GaWi77
			CuF_2	916.0	GaWi77
			CuF_2	914.8	WRDM79

CuF ₂	914.4	VWHS81	MgF ₂	685.8	Wagn80
Cu ₂ O	916.2	CDFM82, HMUZ78	MgF ₂	685.7	NBK74
Cu ₂ O	916.2	CDFM82, GaWi77, Wagn75, HMUZ78, MSSS81, Scho73b	SrF ₂	685.0	WRDM79
Cu ₂ O	916.6	MSSS81, Wagn75	SrF ₂	684.5	NBK74
Cu ₂ O	917.2	GaWi77	AgF	682.7	GaWi77
CuO	918.1	GaWi77, MSSS81, Scho73b	BeF ₂	685.8	NBK74, NKBP73
Cu(OH) ₂	916.2	MSSS81	CdF ₂	684.5	GaWi77, WRDM79
Cu(NO ₃) ₂	915.3	NZK77	CdF ₂	684.8	NBK74, SATD73
CuCN	914.5	Wagn75	CdF ₂	684.2	NSLS77
Cu(CN) ₃	914.5	NZK77	CuF ₂	684.5	GaWi77, WRDM79
CuCO ₃	916.3	WRDM79	CuF ₂	685.9	VWHS81
CuSO ₄	915.6	NZK77	HgF ₂	686.0	SATD73
C ₄ SiO ₃	915.2	WRDM79	MnF ₂	684.8	WRDM79
Cu ₂ Mo ₃ O ₁₀	916.5	HMUZ78	NiF ₂	685.0	GaWi77, WRDM79
Cu ₃ Mo ₂ O ₉	916.6	HMUZ78	NiF ₂ · 4H ₂ O	684.7	NSLS77
CuCr ₂ O ₄	918.0	CDFM82	PbF ₂	683.6	WRDM79
CuMoO ₄	916.6	HMUZ78	ZnF ₂	684.6	GaWi77, Wagn77
			ZnF ₂	685.1	NBK74
			AlF ₃ · 3H ₂ O	686.3	NBK74, NKBP73
			GaF ₃ · 3H ₂ O	685.2	NBK74, NKBP73
			GdF ₃	684.8	McTh76
			InF ₃	685.2	WRDM79
			InF ₃ · 3H ₂ O	685.3	NBK74, NKBP73
			LaF ₃	684.5	WRDM79
			NdF ₃	684.8	WRDM79
			PrF ₃	684.6	WRDM79
			SmF ₃	684.6	WRDM79
			YF ₃	685.3	WRDM79
			UF ₃	685.3	TBVL82
			UF ₄	684.8	TBVL82, PMDS77
			UF ₅	684.8	TBVL82
			ThF ₄	684.9	WRDM79
			HfF ₄	685.4	WRDM79
			ZrF ₄	685.1	NKBP73
			NaBeF ₃	685.7	NKBP73
			Na ₂ BeF ₄	685.2	NKBP73
			NaBF ₄	687.0	WRDM79
			NF ₄ BF ₄	694.2	RNS73
			Na ₃ AlF ₆	685.5	WRDM79
			Na ₂ SiF ₆	686.0	Wagn77
			Na ₂ SiF ₆	686.4	NSLS77
			K ₂ SiF ₆	686.6	NBK74
			K ₂ TiF ₆	685.0	WRDM79
			K ₂ TiF ₆	684.9	NBK74
			Na ₂ TiF ₆	685.3	Wagn77
			K ₃ FeF ₆	684.0	WRDM79
			K ₂ NiF ₆	687.6	TRLK73
			K ₂ GeF ₆	685.2	NBK74
			Na ₂ GeF ₆	685.9	WRDM79
			K ₂ ZrF ₆	684.6	NBK74, NKBP73
			Na ₂ ZrF ₆	685.0	WRDM79
			KZrF ₃ · H ₂ O	684.8	NKBP73
			K ₃ ZrF ₇	684.3	NKBP73
			NaSnF ₃	685.3	WRDM79
			K ₂ SnF ₆ · H ₂ O	685.1	NBK74
			CsSbF ₄	683.6	BCH75
Dy 4d					
Dy	152.4	Φ			
Dy ₂ O ₃	167.7	SaRa80			
Dy 3d _{5/2}					
Dy	1295.5	Φ			
Dy ₂ O ₃	1298.9	SaRa80			
Er 4d					
Er	167.3	Φ			
Er	169.4	WRDM79			
Er ₂ O ₃	168.7	WRDM79			
Eu 3d _{5/2}					
Eu	1125.6	Φ			
Eu 4d					
Eu	128.2	NNBF68			
Eu ₂ O ₃	135.9	NNBF68			
F 1s					
LiF	684.9	Φ			
C ₆ F	685.9	WRDM79			
KF	683.9	NBK74, MVS73			
KF	684.4	PMDS77			
LiF	685.1	WRDM79			
LiF	685.0	MVS73, NBK74			
NaF	684.5	WRDM79			
NaF	684.5	NBK74, NSLS77			
NaF	683.7	MVS73			
RbF	683.6	MVS73			
RbF	682.9	NBK74			
BaF ₂	683.7	WRDM79			
BaF ₂	684.3	NBK74			
CaF ₂	684.8	WRDM79			
CaF ₂	684.8	NBK74, NSLS77			

K ₂ SbF ₅	683.9	Tric74
KSbF ₆	686.6	Wagn77
KSb ₂ F ₇	684.3	Tric74
Na ₂ SbF ₅	683.4	Tric74
NaSbF ₆	685.1	BCH75
K ₃ RhF ₆	685.7	Nefe78
K ₂ NbF ₇	685.4	WRDM79
K ₂ NbF ₇	685.2	NBK74
K ₂ TaF ₇	685.2	WRDM79
K ₂ TaF ₇	685.1	NBK74
NaTaF ₆	685.2	NKBP73
Na ₂ TaF ₇	685.6	NKBP73
Na ₃ TaF ₈	685.5	NKBP73
K ₂ UF ₆	684.7	PMDS77
EuOF	685.3	PGBH80
LaOF	685.2	RGBH80
NdOF	685.1	RGBH80
PrOF	685.0	RGBH80
YOF	685.5	RGBH80
Cs ₂ MoO ₂ F ₄	684.7	NKBP73
Cs ₂ WO ₂ F ₄	684.7	NKBP73
UO ₂ F ₂	685.6	TBVL82
p-(CF ₂ =CF ₂)	689.0	Wagn77
NiOCCF ₃	688.4	WRDM79
CH ₃ CNBF ₃	687.0	BCGH73
NH ₃ BF ₃	686.6	BCGH73
C ₃ H ₃ NBF ₃	685.6	BCGH73
EtNH ₂ BF ₃	686.6	BCGH73
Et ₄ NSbF ₆	684.7	BCH 75
Ph ₃ PBF ₃	685.7	HVV79
Ph ₃ POBF ₃	685.8	HVV79

F KLL

CsF	653.8	WRDM79
LiF	654.7	WRDM79
NaF	655.0	Wagn77
BaF ₂	656.2	WRDM79
CaF ₂	655.4	WRDM79
MgF ₂	654.4	Wagn77
SrF ₂	656.3	WRDM79
AgF	659.3	GaWi77
CdF ₂	656.0	GaWi77, WRDM79
CuF ₂	657.0	GaWi77
CuF ₂	656.2	WRDM79
CuF ₂	656.2	WRDM79
NiF ₂	655.5	GaWi77, WRDM79
PbF ₂	658.5	WRDM79
ZnF ₂	655.6	GaWi77, WRDM79
InF ₃	656.4	WRDM79
LaF ₃	658.0	WRDM79
NdF ₃	657.0	WRDM79
PrF ₃	657.2	WRDM79
SmF ₃	657.0	WRDM79
YF ₃	655.8	WRDM79
ThF ₄	657.0	WRDM79
HfF ₄	655.3	WRDM79

NaBF ₄	652.8	WRDM79
Na ₃ AlF ₆	654.1	WRDM79
Na ₂ SiF ₆	653.0	Wagn77
K ₂ TiF ₆	655.7	WRDM79
Na ₂ TiF ₆	655.1	Wagn77
K ₃ FeF ₆	656.0	WRDM79
Na ₂ GeF ₆	654.0	WRDM79
Na ₂ ZrF ₆	655.1	WRDM79
NaSnF ₃	655.3	WRDM79
KSbF ₆	656.6	Wagn77
K ₂ NbF ₇	655.2	WRDM79
K ₂ TaF ₇	655.0	WRDM79
p-(CF ₃ =CF ₂)	652.4	Wagn77
NiOCCF ₃	52.9	WRDM79

Fe 2p

Fe	707.0	Φ
Fe ₂ O ₃	710.9	Φ
Fe	706.7	LANM81
Fe	706.8	Asam76
Fe	707.0	WRDM79, McZe77
Fe ₃ Al	707.6	ShTr75
Fe ₃ Si	707.5	ShTr75
Fe ₂ B	706.9	MECC73
FeB	707.1	MECC73
Fe ₃ C	708.1	ShTr75
FeS	710.3	CSC72
FeS	712.2	Bind73, Limo81
FeS ₂ (markasite, pyr)	706.7	Bind73
KFeS ₂	708.7	Bind73
FeBr ₂	710.3	CSC72
FeBr ₃	710.1	CSC72
FeCl ₂	710.6	CSC72
FeCl ₃	711.3	CSC72
FeF ₂	711.3	CSC72
FeF ₃	714.2	CSC72
FeO	709.4	McZe77
Fe ₃ O ₄	708.2	McZe77
Fe ₃ O ₄	710.4	OkHi76
Fe ₂ O ₃	710.8	WRDM79, NGDS75
Fe ₂ O ₃ , alpha	710.9	McZe77
Fe ₂ O ₃ , gamma	710.9	McZe77
FeOOH, alpha	711.8	McZe77
FeOOH, gamma	711.3	KoNa80
CoFe ₂ O ₄	710.5	McZe77
Fe(C ₂ O ₄) ₃ · 6H ₂ O	713.6	Kilk73
FeSO ₄	712.1	Limo81
K ₃ FeF ₆	714.4	CSC72
NiFe ₂ O ₄	710.5	McZe77
K ₃ Fe(CN) ₆	709.6	Vann76
K ₄ Fe(CN) ₆	707.1	Vann76
K ₄ Fe(CN) ₆	708.5	YNNA77
Na ₂ Fe(CN) ₅ (NO)	709.7	YNNA77
Na ₃ Fe(CN) ₅ (N ₂ O)	707.4	YNNA77
Na ₄ Fe(CN) ₅ (NO ₂)	706.8	YNNA77
Na ₃ Fe(CN) ₅ NH ₃	707.6	YNNA77

$\text{Na}_3\text{Fe}(\text{CN})_5\text{N}_2\text{H}_4$	707.7	YNNA77
$\text{Fe}(\text{CO})_5$	709.6	BCGH72
$\text{Fe}(\text{CO})_2(\text{NO})_2$	709.5	BCGH72
$\text{KFe}_4(\text{NO})_7\text{S}_3 \cdot 2\text{H}_2\text{O}$	708.9	Nefe78
$\text{Fe}(\text{SMe})(\text{CO})_3$	708.6	BBFR77
$\text{Fe}(\text{C}_5\text{H}_5)_2$	707.7	FWUM79, BCDH73, CDH74, Nefe78
$\text{I}_3\text{Fe}(\text{C}_5\text{H}_5)_2$	709.9	CDH74
$\text{Fe}(\text{C}_5\text{H}_4\text{COOH})_2$	708.4	FWUM79
$\text{Fe}(\text{phthalocyanine})$	709.1	MSV79
Fe LMM		
Fe	702.4	WRDM79
Ga 2p_{3/2}		
Ga	1116.7	Φ
Ga	1116.5	Scho73a
GaP	1116.8	Ni J75
Ga_2O_3	1116.9	PE1
Ga_2O_3	1117.8	Scho73a
Ga LMM		
Ga	1068.2	WRDM79, MINN78, Scho73a
GaAs	1066.3	MINN78
GaAs	1067.1	MINN78
GaP	1065.6	MINN78, MIN81
GaP	1066.8	MIN81
GaN	1064.5	HeMa80
Ga_2Se_3	1065.2	ITI82
Ga_2Se_3	1065.6	ITI82
Ga_2O_3	1061.6	MINN78
Ga_2O_3	1062.4	ITI82
Ga_2O_3	1062.9	Scho72a
Ga 3d		
Ga	18.6	MINN78, LBHK73, Scho73a, WRDM79
GaSb	20.2	LBHK73
GaAs	18.8	LPMK74
GaAs	19.2	IMNN79, MINN78, Tayl82,
GaP	18.8	MIN81
GaP	19.3	MINN78, IMNN79
GaP	19.9	LBHK73, MIN81
GaP	18.7	LPMK74
GaN	19.5	HeMa80
AlGaAs	19.0	Tayl82
Ga_2Se_3	19.7	ITI82
Ga_2Se_3	19.9	ITI82
Ga_2O_3	20.5	GGVL79
Ga_2O_3	20.2	LBHK73, Scho73a
Ga_2O_3	20.5	ITI82
Ga_2O_3	21.0	MINN78
Gd 4d		
Gd	140.4	Φ

Gd_2O_3	143.8	SaRa80
Gd 3d		
Gd	1187.0	Φ
Gd_2O_3	1189.0	SaRa80
Ge 2p_{3/2}		
Ge	1217.2	McWe76
Ge	1217.4	TLR78, MoVa73, Wagn75
GeS_2	1219.8	MoVa73
GeS_2	1219.8	MoVa73
GeN_4	1218.8	TLR78
GeI_2	1218.2	MoVa73
GeF_2	1220.7	MoVa73
GeO_2	1220.4	MoVa73, Wagn75
Na_2GeO_3	1218.9	MoVa73
Na-GeF_6	1221.3	Wagn75
K_2GeF_6	1220.7	MoVa73
Ph_4Ge	1218.9	MoVa73
Ge LMM		
Ge	1146.2	McWe76
Ge	1145.4	SFS77
Ge	1145.1	Wagn75, WRDM79
GeTe	1144.8	SFS77
GeSe	1143.8	SFS77
GeS	1143.7	SFS77
GeO_2	1137.7	Wagn75
Na_2GeF_6	1135.7	Wagn75
Ge 3d		
Ge	29.4	Φ
Ge	29.3	McWe76
Ge	29.0	SFS77
Ge	29.1	HKMP74, UeOd82, WRDM79
GeAs_2	29.7	HKMP74
GeTe_3As_2	29.9	HKMP74
$\text{GeS}_2\text{TeAs}_2$	30.2	HKMP74
GeS_3As	30.4	HKMP74
GeTe_2	30.1	HKMP74
GeTe	30.0	SFS77
GeTe	29.7	HKMP74
GeSe_2	31.0	UeOd82
GeSe	30.9	SFS77
GeS_2	30.4	HKMP74
GeS	30.5	SFS77
GeS	29.5	HKMP74
GeO_2	32.5	HKMP74
Ph_4Ge	31.2	HWVV74
Ph_3GeI	31.8	HWVV74
Ph_3GeBr	31.8	HWVV74
Ph_3GeCl	31.8	HWVV74
Hf 4f		
Hf	14.3	Φ

Hf	14.4	WRDM79	I ₂ Ni(Ph ₃ P) ₂	619.3	NZB78
HfO ₂	16.7	SaRa80	I ₂ Pt(Et ₃ P) ₂	619.2	Rigg72
Hf 4d			L ₁ In(Pr ₄ N)	619.6	FHT77
HfO ₂	213.2	SaRa80, NGDS75	I ₂ Pt(Me ₃ P) ₂ cis	621.1	CAB71
Hg 4f			I ₂ Pt(Me ₃ P) ₂ tran	621.9	CAB71
HgS (cinnabar)	101.0	Φ	L ₁ (Mo ₆ I ⁸)	620.6	BeWa79
Hg	99.8	BrMc72, SATD73, SMBM76, WRDM79	I ⁸ ₄ (Mo ₆ I ₈)	619.3	BeWa79
Hg _{0.8} Cd _{0.2} Te	100.2	SBB80	I MNN		
HgS	100.8	NSSP80	LiI	517.0	WRDM79
HgI ₂	100.7	SATD73	AgI	506.8	GaWi77
HgBr ₂	101.0	SATD73	CdI	507.0	GaWi77
HgCl ₂	101.4	SATD73	CuI	507.1	GaWi77
HgF ₂	101.2	SATD73	NiI ₂	507.3	GaWi77
HgO	100.8	NSSP80	ZnI ₂	506.0	GaWi77
Et ₂ NC ₄ H ₄ HgOAc	101.3	NSSP80	In 3d_{5/2}		
Cl ₂ Hg(H ₂ NCONHCONH ₂) ₂	101.3	YY578	In	443.9	Φ
Hg(thiodibenzoylme) ₂	101.3	TBHH77	In	443.8	Bert81, Hegd82, WRDM79, PVVA79, LAK77
(Ph ₄ P) ₂ Hg(SCN) ₄	101.4	FoLa82	In ₉₅ Sn ₅	443.6	Hegd82
Ho 4d			InSb	444.1	IMNN79
Ho	159.6	Φ	InP	444.6	Bert81, CFRS80
I 3d_{5/2}			In ₂ Te ₃	444.5	WRDM79
KI	619.3	Φ	In ₂ Se ₃	444.8	WRDM79
I ₂	619.9	Sher76	In ₂ S ₃	444.8	Wagn77, MSC73
CsI	618.2	MVS73	InI ₃	446.0	Wagn77, MSC73
RbI	618.2	MVS73	InI	443.9	FHT77
KI	618.8	MVS73	InBr ₃	446.0	Wagn77
NaI	618.6	MVS73, Sher76	InBr ₃	446.6	MSC73
LiI	619.7	WRDM79	InBr	445.1	FHT77
LiI	618.9	MVS73	InCl ₃	446.0	Wagn77
AgI	619.4	GaWi77	InCl ₃	446.9	MSC73
CdI	619.2	GaWi77	InCl	444.9	MSC73
CdI	619.4	SATD73	InF ₃	446.4	Wagn75, MSC73
CuI	619.0	GaWi77	In ₂ O ₃	444.3	Wagn77, NGDS75, Bert81
HgI ₂	619.4	SATD73	In ₂ O ₃	444.6	CFRS80
InI	619.0	FHT77	In ₂ O ₃	444.9	LAK77, MSC73
InI ₃	619.1	FHT77	In(OH) ₃	445.0	WRDM79
NiI ₂	619.0	GaWi77	(NH ₄) ₃ InF ₆	445.6	Wagn77
NiI ₂ · 6H ₂ O	619.7	NZB78	CuInSe ₂	444.7	KJID81
ZnI ₂	619.8	GaWi77	In(acac) ₃	445.4	MSC73
ZnI ₂	619.7	SATD73	Br ₂ InEt ₄ N	445.7	FHT77
NaIO ₃	623.5	Sher76	Cl ₂ InEt ₄ N	445.2	FHT77
NaIO ₄	624.0	Sher76	Br ₄ InPr ₄ N	445.9	FHT77
HIO ₃	623.1	Sher76	L ₁ InPr ₄ N	445.4	FHT77
H ₂ IO ₆	623.0	Sher76	Cl ₄ InPr ₄ N	445.8	FHT77
I ₂ O ₅	623.3	Sher76	In MNN		
ICI	621.5	Sher76	In	410.4	WRDM79
ICl ₃	622.5	Sher76	In ₉₅ Sn ₅	410.5	PVVA79, KISC80, LAK77
Cs ₃ Sb ₂ I ₉	618.5	BCH75	InSb	401.6	IMNN79
Rb ₃ Sb ₂ I ₉	620.8	Tric74	InP	408.0	Bert81
Na(NiO ₆) · H ₂ O	624.4	NZB78	InP	411.0	KISC80
			In ₂ Te ₃	408.9	WRDM79

In_2Se_3	408.3	WRDM79	K_2PtCl_6	292.8	CoHe72, LeBr72
In_2S_3	407.3	Wagn77	K_2ReCl_6	292.8	CoHe72
InI_3	405.8	Wagn77	K_2ReCl_6	293.7	LeBr72
InBr_3	404.8	Wagn77	K_2SnCl_6	292.8	CoHe72
InCl_3	404.6	Wagn77	K_2WCl_6	293.3	LeBr72
InF_3	403.7	Wagn75	K_3IrCl_6	293.0	NSBN77
In_2O_3	406.4	Wagn77	$\text{K}_4\text{Mo}_2\text{Cl}_8$	293.2	HUGH79
$\text{In}(\text{OH})_3$	405.0	WRDM79	KSbFF_6	293.7	Wagn77
$(\text{NH}_4)_3\text{InF}_6$	404.1	Wagn77	$\text{KZrFF}_3 \cdot \text{H}_2\text{O}$	292.7	NKBP73
Ir 4f			K_2NiF_6	294.2	TRLK73
Ir	60.9	Φ	K_2UF_6	293.1	PMDS77
Ir	60.8	WRDM79, BHHK70, EPC75	K_2ZrF_6	292.6	NKBP73
IrCl_3	62.7	Folk73	K_3ZrF_7	292.8	NKBP73
K_2IrBr_6	62.6	$\text{Nefe78K}_3\text{IrBr}_6$ 61.8Nefe78	$\text{K}_3\text{Co}(\text{CN})_6$	293.7	Vann76
K_2IrCl_6	63.0	CoHe72, LeBr72	$\text{K}_3\text{Cr}(\text{CN})_6$	292.2	ZeHa7
K_2IrCl_6	63.6	KSPB76, NSBN77	$\text{K}_3\text{Fe}(\text{CN})_6$	291.9	Vann76
K_3IrCl_6	62.5	NSBN77	$\text{K}_3\text{Mn}(\text{CN})_6$	291.9	Vann76
$(\text{NH}_4)_2\text{IrCl}_6$	63.7	EPC75	$\text{K}_4\text{Fe}(\text{CN})_6$	291.9	Vann76
$(\text{NH}_4)_3\text{IrCl}_6$	63.0	EPC75	$\text{K}_4\text{V}(\text{CN})_6$	293.7	Vann76
$\text{Ir}(\text{CO})_3\text{Cl}$	63.4	KSPB76	KIrCl_3NO	293.1	NSBN77
KIrCl_3NO	65.0	NSBN77	$\text{K}_2\text{Pt}(\text{CN})_4 \cdot 3\text{H}_2\text{O}$	293.3	CaLe73
$\text{KIr}_2(\text{CO})_4\text{Cl}_4$	62.7	KSPB76	$\text{K}_2\text{Pt}(\text{CN})_4\text{Cl}_2 \cdot 3\text{H}_2\text{O}$	292.9	CaLe73
$\text{K}_2\text{Ir}_2(\text{CO})_4\text{Cl}_5$	63.0	KSPB76	$\text{K}_3\text{Co}(\text{SCH}_2\text{CHNH}_2\text{COO})_3$	292.8	SSEW79
$\text{IrCl}_4(\text{EtEP})_2$	63.6	LeBr72	K LMM		
$\text{IrClIN}_2(\text{Ph}_3\text{P})_2$	60.7	Folk73	KBr	250.7	WRDM79
$\text{IrI}_3(\text{H}_2\text{NCH}_2\text{CH}_2\text{NH}_2)_3$	63.1	NeBa72	KF	250.1	Wagn77
$\text{IrCl}_3(\text{H}_2\text{NCH}_2\text{CH}_2\text{NH}_2)_3$	63.2	NeBa72	KSbF_6	249.3	Wagn77
$\text{IrCl}_4(\text{H}_2\text{NCH}_2\text{CH}_2\text{NH}_2)_3$	63.2	Nefe78	Kr 3d		
K 2p			Kr in graphite	87.0	Φ
K	294.4	Φ	La 3d		
KCl	292.9	Φ	La	835.8	Φ
K	294.6	SMKM77, PeKa77	La	835.9	ScSc82
KI	292.8	MVS73	LaH_2	838.8	ScSc82
KBr	293.0	MVS73, WRDM79	La_2O_3	835.1	WRDM79
KCl	292.8	MVS73, NSLS77	La_2O_3	833.7	SaRa80
KF	292.5	Wagn75	La 4d		
KF	292.8	PMDS77	La	103.9	NIS72, KEML74
KF	293.1	MVS73	La_2O_3	101.3	$\text{SaRa80, NGDS75, HoTh80}$
KCN	294.7	Vann76	LaCrO_3	101.7	HoTh80
KN_3	292.5	SGRS72	Li 1s		
KNO_3	292.9	NSLS77	LiF	55.6	Φ
KClO_3	293.2	MVS73	Li	54.7	KLMP73, CSFG79
KClO_4	293.4	MVS73	LiN_3	55.2	SGRS72
K_3PO_4	293.5	MVS73	LiBr	56.8	MVS73
$\text{K}_4\text{P}_2\text{O}_7$	292.2	MVS73	LiCl	56.0	CSFG79, MVS73
K_2CrO_4	292.6	ACHT73	LiF	55.7	MVS73, WRDM79
$\text{K}_2\text{Cr}_2\text{O}_7$	292.1	ACHT73	Li_2O	55.6	CSFG79
$\text{K}_2\text{Cr}_2\text{O}_7$	292.8	NSSP80	LiOH	54.9	CSFG79
K_2MoO_4	292.6	NFS82	Li_2CO_3	55.2	CSFG79
KRhO_2	292.5	NFS82	Li_3PO_4	55.4	MVS73
$\text{KAl}(\text{AlSi}_3\text{O}_{10})_2(\text{OH})_2$	293.0	WPHK82			
K_2IrCl_6	292.8	$\text{NSBN77, LeBr72, CoHe72}$			
K_2MoCl_6	292.7	CoHe72			
K_2OsCl_6	293.0	CoHe72, LeBr72			

Li ₄ P ₂ O ₇	55.6	MVS73	MnF ₃	642.6	CSC72
LiClO ₄	57.2	MVS73	MnO	640.7	OHI75
Li ₂ CrO ₄	57.1	ACHT73	MnO	640.5	OkHi76
LiC ₆ O ₂	55.6	ACHT73	MnO	641.4	Aoki76, CSC72
LiNbO ₃	54.8	StHo79	Mn ₂ O ₃ , alpha	641.2	OHI75
Lu 4f			Mn ₂ O ₃	641.6	CSC72
Lu	7.3	Φ	Mn ₂ O ₃ , alpha	641.7	OkHi76
Lu 4d			Mn ₂ O ₃ , gamma	641.5	OkHi76
Lu	196.2	KEML74, LPWF75	Mn ₃ O ₄	641.4	OHI75
Lu ₂ O ₃	196.0	SaRa80, NGDS75	MnO ₂	642.4	WRDM79
Mg 2p			MnO ₂ , beta	641.1	OHI75
Mg	49.8	Φ	MnO ₂	642.3	Aoki76, CSC72, NGDS75
Mg	49.6	HAS75, LMKJ75, HFV 77, Fugg77, WRDM79	MnOOH	641.7	OHI75
Mg ₂ Cu	49.8	FWFA75	CoMn ₂ O ₄	641.5	OkHi76
Mg ₃ Bi ₂	50.6	FWFA75	CuMn ₂ O ₄	641.0	OkHi76
MgF ₂	51.0	Wagn80	MnCr ₂ O ₄	640.6	OkHi76
MgO	50.8	InYa81	MnSO ₄	644.9	Limo81
Mg(OH) ₂	49.5	HNUW78a	KMnO ₄	647.0	UmRe78
MgAl ₂ O ₄	50.4	HNUW78b	Mn ₂ (CO) ₁₀	641.6	VWVB77
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	50.5	WPHK82	BrMn(CO) ₅	641.9	VWVB77
Mg 1s			(BrMn(CO) ₄) ₂	641.7	VWVB77
Mg	1303.1	HAS75, LMKJ75, Fugg77	BrMn(CO) ₄ (Ph ₃ P)	641.5	VWVB77
Mg ₂ Cu	1303.0	FWFA75	BrMn(CO) ₃ (P(OMe) ₃) ₂	641.0	VWVB77
Mg ₃ Bi ₂	1304.0	FWFA75	Mn ₂ (CO) ₈ (Ph ₃ P) ₂	640.7	VWVB77
MgF ₂	1305.0	Wagn80	K ₃ Mn(CN) ₆	639.7	Vann76
Mg(OH) ₂	1302.7	HNUW78a	Na ₄ Mn(CN) ₆	638.3	Vann76
MgAl ₂ O ₄	1304.0	HNUW78b	Mn(C ₅ H ₅) ₂	638.5	BCDH73, CDH74
Mg KLL			Mn(CO) ₃ (C ₅ H ₅)	640.6	CDH74
Mg	1185.5	LMKJ75, SRHH78, WRDM79, Fugg77, HFV 77	Mn(CO) ₃ (C ₅ H ₅)	641.8	CIAD71
Mg ₂ Cu	1185.7	FWFA75	Mn LMM		
Mg ₃ Bi ₂	1184.6	FWFA75	Mn	617.6	Vayr81
MgF ₂	1178.2	Wagn80	Mo 3d		
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	1180.3	WPHK82	Mo	228.0	Φ
Mn 2p			Mo	227.9	NyMa80
Mn	639.0	Φ	Mo	228.0	CiDe75, WRDM79, CGR 78, GrMa75, KBAW74, WaTa80
MnO ₂	642.1	Φ	MoB ₂	227.9	MECC73
Mn	638.8	LANM81	Mo ₂ B ₅	227.3	BrWh78
Mn	639.0	WRDM79	Mo ₂ C	227.8	BrWh78
MnN	641.3	CSC72	MoSi ₂	227.7	WPHK82
MnS	640.3	CSC72	MoSe ₂	228.3	GrMa75
MnS, beta	640.8	Aoki76	MoS ₂	229.0	PCLH76, GrMa75
MnS, alpha	641.9	Aoki76	MoS ₂	229.6	SSOT81, StEd75
MnS	642.1	Limo81	MoCl ₃	230.0	GrMa75
MnI ₂	641.9	Aoki76, CSC72	MoCl ₄	230.6	GrMa75
MnBr ₂	642.0	Aoki76, CSC72	MoCl ₅	231.0	GrMa75, SwHe71
MnCl ₂	642.0	Aoki76, CSC72	MoO ₂	229.3	SaRa80, CGR78, CiDe75, KBAW74
MnF ₂	642.6	Aoki76, CSC72	MoO ₃	232.6	GPDG79, KBAW74, SaRa80, CiDe75, CGR78, GrMa75
			MoO ₃	232.6	WRDM79
			(NH) ₄ MoO ₄	232.1	SwHe71
			Al ₂ (MoO ₄) ₃	232.5	PCLH76
			Al ₂ (MoO ₄) ₃	233.3	NFS82

CaMoO ₄	232.8	NFS82	VN	397.4	STAB76
CoMoO ₄	232.4	GPDG79, CiDe75, AMFL74	BN	398.1	WRDM79, HJGN70
CrMoO ₄	232.2	TVG76	Si ₃ N ₄	397.4	TLR78
CuMoO ₄	232.7	HMUZ78	S ₂ N ₂	398.9	SDIO77
K ₂ MoO ₄	232.1	NFS82	SP(NH ₃) ₃	398.8	FIWe75
Na ₂ MoO ₄	232.1	CiDe75, NFS82, SwHe71,	S ₄ N ₃ Cl	400.4	HHJ69
		NSLS77	(NPCl ₂) ₃	400.3	HHJ69
Na ₂ MoO ₄ · 2H ₂ O	232.5	GrMa75	Cs(N*NN*)	397.9	SGRS72
(NH ₄) ₂ Mo ₂ O ₇	232.5	AMFL74	Cs(NN*N)	402.2	SGRS72
(NH ₄) ₂ Mo ₇ O ₂₄ · 4H ₂ O	232.7	GrMa75	K(N*NN*)	398.5	SGRS72
Cu ₃ Mo ₃ O ₁₀	232.4	HMUZ78	K(NN*N)	402.8	SGRS72
Cu ₃ Mo ₂ O ₉	232.8	HMUZ78	Li(N*NN*)	398.7	SGRS72
Rh ₃ MoO ₆	231.8	NFS82	Li(NN*N)	403.1	SGRS72
Cl ₂ Mo(NO) ₂	230.4	Nefe78	Na(N*NN*)	398.5	SGRS72
K ₄ Mo ₂ Cl ₈	229.2	HUGH79	Na(N*NN*)	400.1	HHJ69
I ₄ (Mo ₆ I ₈)	228.8	BeWa79	Na(NN*N)	402.9	SGRS72
Br ₄ (Mo ₆ Br ₈)	229.3	BeWa79	Na(NN*N)	404.5	HHJ69
Cl ₄ Mo(Ph ₃ P) ₂	231.9	HuBa74	Rb(N*NN*)	398.1	SGRS72
Cl ₄ Mo ₂ (Et ₃ P) ₄	228.7	Walt77	Rb(NN*N)	402.4	SGRS72
Cl ₃ Mo(PhPMe ₂) ₃ mer	229.4	LeBr72	K ₃ Co(CN) ₆	399.6	Vann76
Cl ₄ Mo ₂ (PhPMe ₂) ₄	228.7	Walt77	K ₃ Cr(CN) ₆	397.6	Vann76, ZeHa71
(CO) ₅ Mo(Ph ₃ P)	228.3	HVV79	K ₃ Fe(CN) ₆	398.1	Vann76
(CO) ₄ Mo(Ph ₃ P) ₂	227.8	HuBa74	K ₃ Mn(CN) ₆	398.3	Vann76
(CO) ₃ Mo(Ph ₃ P) ₃	227.4	HuBa74	K ₄ Fe(CN) ₆	398.0	Vann76
Cl ₂ Mo(CO) ₂ (Ph ₃ P) ₂	229.3	Nefe78	K ₄ Fe(CN) ₆	397.8	YNNA77
Cl ₂ Mo(CO) ₃ (Ph ₃ P) ₂	228.8	HuBa74	K ₄ V(CN) ₆	398.5	Vann76
Cl ₂ Mo(NO) ₂ (Ph ₃ P) ₂	230.3	HuBa74	Na ₄ Mn(CN) ₆	397.6	Vann76
Cl ₃ Mo(NO) ₂ (MeCN) ₂	231.5	Nefe78	Na ₂ Fe(CN) ₃ (N*O)	402.7	YNNA77
Cl ₃ Mo(pyridyl) ₃	229.5	CELC76	Na ₂ Fe(CN*) ₃ (NO)	397.4	YNNA77
Cl ₄ Mo ₂ (pyridyl) ₄	228.9	Walt77	Na ₄ Fe(CN) ₃ N*O ₂	404.3	YNNA77
Cl ₄ Mo(pyridyl) ₂	230.8	SwHe71	Na ₄ Fe(CN*) ₃ NO ₂	396.6	YNNA77
Br ₄ (Mo ₆ Br ₈)(pyridyl) ₂	229.7	BeWa79	KCN	399.8	HHJ69
Cl ₃ Mo ₆ (pyridyl)	229.6	HaWa74	KCN	398.3	YNNA74
Cl ₄ Mo(bipyridyl)	232.0	CELC76	KCN	400.6	Vann76
Cl ₃ MoO(bipyridyl)	231.9	CELC76	NaCN	400.2	Vann76
Cl ₂ MoO ₂ (bipyridyl)	232.3	CELC76	(NH ₄) ₂ PtCl ₄	400.3	KaEl79
(CO) ₄ Mo(bipyridyl)	226.3	GrMa75	(NH ₄) ₂ SO ₄	401.3	SwAl74
Cl ₁₂ Mo ₆ (Ph ₃ P) ₂	229.6	HaWa74	N*H ₄ NO ₃	401.9	SwAl74, BCM78
Cl ₆ (Mo ₆ Br ₈)(Et ₄ N) ₂	229.2	BeWa79	N*H ₄ NO ₃	402.3	BTE77
Br ₆ (Mo ₆ Br ₈)(Et ₄ N) ₂	229.3	BeWa79	N*H ₄ NO ₃	403.1	HHJ69
(Bu ₄ N) ₂ Mo(CO) ₄	227.4	GrMa75	N ₂ H ₆ SO ₄	403.3	HHJ69
(Bu ₄ N) ₂ MoAl ₁₁	229.0	BeWa79	N ₂ H ₆ SO ₄	401.7	Folk73
(Bu ₄ N) ₃ Mo ₂ Cl ₉	229.5	Walt77	NH ₃ OHCl, ionic	402.9	HHJ69
(C ₇ H ₅)Mo(CO) ₃	227.4	GrMa75	NH ₃ OHCl, ionic	401.4	Folk73
MoO ₂ (acac) ₂	232.0	GrMa75	NH ₃ SO ₃	402.6	HHJ69
			NaN ₂ O ₂	402.1	HHJ69
			KSCN	399.3	HHJ69
			KOCN	399.1	HHJ69
			KOCN	397.9	Folk73
			NF ₄ BF ₄	417.1	RNS73
			NaNO ₂	404.9	HHJ69, LiHe75
			NaNO ₂	403.9	BTE77
			Ba(NO ₃) ₂	407.5	CLSW83
			Ca(NO ₃) ₂	408.0	CLSW83
			KNO ₃	407.2	NSLS77
			NH ₄ N*O ₃	407.3	BTE77
N 1s					
BN	398.1	Φ			
NH ₃	399.6	HHJ69			
NH ₃	398.7	LaLu79, RNS73			
Cr ₂ N	397.4	RoRo76			
CrN	396.7	STAB76			
GaN	397.0	HeMa80			
Ge ₃ N ₄	397.4	TLR78			
ScN	396.2	STAB76			
TiN	396.9	STAB76			

NH ₄ N*O ₃	408.0	HHJ69
NH ₄ N*O ₃	405.8	BCM78
NaNO ₃	408.1	HHJ69, LiHe75
NaNO ₃	407.4	BTE77
Ni(NO ₃) ₂	407.0	TRLK73
Ni(NO ₃) ₂ · 6H ₂ O	407.6	NZB78
Pb(NO ₃) ₂	407.2	TLR78
Sr(NO ₃) ₂	408.1	CLSW83
K ₂ Pt(NO ₂) ₄	404.7	SNMK78
K ₂ Pt(NO ₂) ₆	404.7	SNMK78
K ₃ Co(NO ₂) ₆	404.2	NBMO73
K ₃ Rh(NO ₂) ₆	404.1	SNMK78
K ₃ Rh(NO ₃) ₆	407.3	SNMK78
MoCl ₂ (NO) ₂	401.4	Nefe78
K ₂ Os(NO)Cl ₅	402.8	Nefe78
K ₂ Ru(NO)I ₅	402.5	Nefe78
K ₃ Ru(NO)Br ₅	403.30	Nefe78
Rh ₃ (NO) ₆ Cl ₃	401.90	Nefe78
Co(CO) ₃ NO	402.20	BCGH72
Fe(CO) ₂ (NO) ₂	401.80	BCGH72
Co(NH ₃) ₅ Cl ₃	400.10	YNAB77
Ni(NH ₃) ₆ Br ₂	399.60	NZB 78
Ni(NH ₃) ₆ (ClO ₄) ₂	399.90	NZB 78
Pt(N*H ₃) ₂ (NO ₂) ₂	400.40	Nefe78, CMHL77
Pt(NH ₃) ₂ (N*O ₂) ₂	404.40	Nefe78, CMHL77
Pt(NH ₃) ₂ Cl ₂	400.20	Nefe78, CMHL77
Rh(NH ₃) ₆ Cl ₃	400.10	Nefe78
Me ₄ NBr	401.40	SGCT74
Me ₄ NCl	401.50	EMGK74
Me ₄ NCl	402.30	LiHe75
Et ₄ NCl	401.40	EMGK74
Et ₃ NHCl	401.20	LiHe75
Et ₃ NHHSO ₄	401.80	EvRe81
Bu ₃ N	398.90	LiHe75
BuNH ₃ HSO ₄	401.00	EvRe81
Bu ₄ NHSO ₄	402.20	EvRe81
EtNH ₂	398.90	BCGH73
EtNH ₂ BF ₃	401.40	BCGH73
NH ₄ Cl	400.80	SwAl74
NH ₄ Cl	401.50	EMGK74, BTE 77
NH ₄ BF ₃	401.90	BCGH73
C ₃ H ₅ N	398.80	LiHe75
C ₃ H ₅ N	399.30	BCGH73
C ₃ H ₅ NHCl	401.00	HHJ 69
C ₃ H ₅ NBF ₃	401.40	BCGH73
Hexamethylenetetramn	399.40	LiHe75
PhCN	399.20	LiHe75
C(NH ₂) ₃ Cl	400.10	LeRa77
PhNH ₂	399.40	LiHe75
Me ₃ NO	403.00	LiHe75
OP(NMe ₃) ₃	399.10	FIWe75
P(NMe ₂) ₃	398.30	GBMP79
Cysteine HCl Hydrate	401.20	SSEW79
Cysteine	400.00	LIMa79
H ₃ N(CH ₂) ₃ COOH ionic	400.80	YoSa74
HN(CH ₂ COOH) ₃ ionic	400.70	YoSa74

N(CH ₂ COOH) ₃	398.70	YoSa74
H ₃ NCH ₂ COOH	398.70	YoSa74
H ₃ NCH ₂ COO ionic	400.60	YoSa74
EtCHNH ₂ COOH	400.60	YNAB77
H ₂ N(CH ₂) ₃ COOH	398.80	YoSa74
CH ₃ CHNH ₂ COOH	401.00	YNAB77, KNPP74
H ₂ NCONH ₂	399.50	LeRa77
H ₂ NCSNH ₂	399.80	SrWa77, NBMO73
H ₂ NCSNH ₂	399.20	LeRa77
CH ₃ CONH ₂	399.60	SNMK78
PhCONH ₂	399.50	LBNN78, HHJ 69
PhN=NPh	399.60	BrFe76
PhN=NPh	400.10	LiHe75
PhCH=NPh	399.10	SZNS77
1,1'-azonaphthalene	400.00	Yosh80
NCN=C(N*H ₂) ₂	399.20	LeRa77
AmONO	404.5	LiHe75
PhC=NOHC=NOHPh	400.6	Yosh78
MeC=NOHC=NOHMe	399.8	Yosh78
Ni(dimethylglyoxime) ₂	400.4	NZB78
Cu Salicylaldoxime	400.3	BuBu74
Cu(8-hydroxyquinol) ₂	399.5	YoSa74
8-Quinolinol	398.9	Yosh80
Cr(CO) ₅ NH ₃	399.5	BCGH72
N(EtO) ₃ SiCl	400.5	GrHe77
N(EtO) ₃ SiH	399.8	GrHe77
Morphine	398.5	SCKK75
Morphine H ₂ SO ₄	401.2	SCKK75

Na 1s

Na	1071.8	Φ
NaCl	1072.1	Φ
Na	1071.8	BaSt75
Na	1071.4	KLMP73
NaI	1071.7	WRDM79
NaBr	1071.7	Wagn75
NaBr	1071.4	MVS73
NaCl	1071.6	Wagn75
NaCl	1072.5	SGSO70
NaCl	1071.5	KOK83
NaCl	1071.8	NSLS77
NaCl	1072.3	HHDD81
NaF	1071.2	Wagn75
NaF	1071.0	MVS73, NSLS77
Na ₂ CO ₃	1071.5	WRDM79
Na ₂ CO ₃	1071.7	HHDD81
Na ₂ HPO ₄	1071.6	WRDM79
Na ₂ HPO ₄	1071.5	Swif82
Na ₂ S ₂ O ₃	1071.6	Wagn75
Na ₂ SO ₃	1071.3	Wagn75
Na ₂ SO ₄	1071.2	Wagn75
Na ₂ SeO ₃	1070.8	Wagn75
Na ₂ TeO ₄	1071.1	Wagn75
Na ₃ PO ₄	1071.1	MVS73, Swif82, GMD79
Na ₄ P ₂ O ₇	1070.8	MVS73
Na ₄ P ₂ O ₇	1071.6	GMD79

NaClO ₄	1071.8	MVS73
NaH ₂ PO ₂	1071.1	Swif82
NaH ₂ PO ₄	1072.0	Swif82
NaHCO ₃	1071.3	WRDM79
NaN ₃	1070.8	SGRS72
NaNO ₂	1071.6	Wagn75
NaNO ₃	1071.4	Wagn75
NaPO ₃	1071.7	Wagn75
NaPO ₃	1071.7	Swif82, GMD 79
Na ₂ Cr ₂ O ₇	1071.6	WRDM79
Na ₂ CrO ₄	1071.4	Wagn75
Na ₂ CrO ₄	1071.0	ACHT73
Na ₂ IrCl ₆	1071.9	Wagn75
Na ₂ MoO ₄	1070.9	Wagn75
Na ₂ MoO ₄	1071.8	NSLS77
Na ₂ PdCl ₄	1071.8	Wagn75
Na ₂ SnO ₃ · 3H ₂ O	1071.1	WRDM79
Na ₂ WO ₄	1072.0	Wagn75
NaAsO ₂	1070.9	Wagn75
NaBiO ₃	1071.3	WRDM79
NaCrO ₂	1072.4	ACHT73
Na ₂ BeF ₄	1071.8	NKBP73
Na ₂ GeF ₆	1071.7	Wagn75
Na ₂ SiF ₆	1071.7	Wagn75
Na ₂ SiF ₆	1072.1	NSLS77
Na ₂ TaF ₇	1071.9	NKBP73
Na ₂ TiF ₆	1071.6	Wagn75
Na ₂ ZrF ₆	1071.5	Wagn75
Na ₃ AlF ₆	1071.8	Wagn75
Na ₃ TaF ₈	1071.8	NKBP73
NaBF ₄	1072.7	Wagn75
NaBeF ₃	1071.9	NKBP73
NaTaF ₆	1071.7	NKBP73
Na ₂ O	1072.5	BaSt75
NaOOCH	1071.1	WRDM79
Na ₂ C ₂ O ₄	1070.8	WRDM79
NaAlSi ₃ O ₈ , albite	1072.2	WPHK82
Hydroxysodalite	1070.5	WPHK82
Natrolite	1072.4	WPHK82
Mol Sieve A	1071.8	WPHK82
Mol Sieve X	1072.3	WPHK82
Mol Sieve Y	1072.6	WPHK82
NaOAc	1071.1	Wagn75
NaOAc	1071.7	HHDD81
NaOOCCH ₂ SH	1071.2	WRDM79
NaO ₃ SPh	1071.3	WRDM79
p-(NaOCOCMe=CH ₂)	1072.2	HHDD81

Na KLL

Na	994.3	BaSt75
Na	994.3	KLMP73
Na	994.5	SRHH78
NaI	991.2	WRDM79
NaBr	990.6	Wagn75
NaCl	990.3	Wagn75
NaCl	990.0	SGSO70

NaCl	990.1	KOK83
NaF	998.6	Wagn75
Na ₂ CO ₃	989.8	WRDM79
Na ₂ HPO ₄	989.9	WRDM79
Na ₂ HPO ₄	989.7	Swif82
Na ₂ S ₂ O ₃	990.1	Wagn75
Na ₂ SO ₃	990.4	Wagn75
Na ₂ SO ₄	989.8	Wagn75
Na ₂ SeO ₃	991.0	Wagn75
Na ₂ TeO ₄	990.5	Wagn75
Na ₃ PO ₄	990.1	Swif82
NaH ₂ PO ₂	989.8	Swif82
NaH ₂ PO ₄	989.1	Swif82
NaHCO ₃	989.8	WRDM79
NaNO ₂	989.8	Wagn75
NaNO ₃	989.6	Wagn75
NaPO ₃	989.3	Wagn75
NaPO ₃	989.4	Swif82
Na ₂ Cr ₂ O ₇	990.6	WRDM79
Na ₂ CrO ₄	991.2	Wagn75
Na ₂ IrCl ₆	989.2	Wagn75
Na ₂ MoO ₄	991.0	Wagn75
Na ₂ PdCl ₄	990.2	Wagn75
Na ₂ SnO ₃ · 3H ₂ O	990.3	WRDM79
Na ₂ WO ₄	989.6	Wagn75
NaAsO ₂	990.7	Wagn75
NaBiO ₃	990.9	WRDM79
Na ₂ GeF ₆	998.1	Wagn75
Na ₂ SiF ₆	987.7	Wagn75
Na ₂ TiF ₆	988.5	Wagn75
Na ₂ ZrF ₆	988.7	Wagn75
Na ₃ AlF ₆	988.0	Wagn75
NaBF ₄	987.1	Wagn75
Na ₂ O	989.8	BaSt75
NaOOCH	989.8	WRDM79
Na ₂ C ₂ O ₄	990.5	WRDM79
Mol Sieve A	988.8	WPHK82
Mol Sieve X	988.4	WPHK82
Mol Sieve Y	987.8	WPHK82
NaOAc	989.9	Wagn75
NaOOCCH ₂ SH	990.4	WRDM79
NaO ₃ SPh	989.7	WRDM79

Nb 3d

Nb	202.4	Φ
Nb	202.3	NyMa80
Nb	202.2	MSC73, NSCP74, WRDM79
Nb	201.8	Bahl75
Nb ₃ Te ₄	202.8	Bahl75
NbTe ₄	203.8	Bahl75
Nb ₃ Se ₄	203.0	Bahl75
NbSe ₂	203.4	Bahl75
NbS ₂	207.7	MSC73
NbN	203.8	Bahl75
NbBr ₅	207.1	MSC73
NbCl ₅	208.0	MSC73

NbO	202.8	SPB76	Ni ₂ O ₃	855.8	KiWi74
NbO	203.7	Bahl75	Ni(OH) ₂	855.6	DPS77, LFWS79, McCo75
NbO	204.7	FCFG77	Ni(NO ₃) ₂	857.1	TRLK73
Nb ₂ O ₅	207.5	SPB76, MSC73, FCFG77, NFS82, NGDS75	Ni(NO ₃) ₂ · 6H ₂ O	856.9	NZB78
LiNbO ₃	207.1	StHo79	NiAl ₂ O ₄	855.8	SDR 80, LFWS79
KNbO ₃	206.5	MSC73	NiAl ₂ O ₄	857.4	NgHe76
CaNb ₂ O ₆	206.8	Bahl75	Ni ₂ SiO ₄	856.1	LFWS79
CdNb ₂ O ₆	207.0	Bahl75	NiClO ₄ · 6H ₂ O	857.2	NZB78
Ca ₂ Nb ₂ O ₇	206.7	Bahl75	NiFe ₂ O ₄	855.4	McCo75
RhNbO ₄	206.5	NFS82	NiRh ₂ O ₄	855.9	NFS82
Cl ₂ Nb ₆ Cl ₁₂ (H ₂ O) ₄ · 4H ₂ O	204.7	BeWa79	NiSO ₄	856.8	ShRe79
Cl ₆ (Nb ₆ Cl ₁₂)(Et ₄ N) ₃	204.7	BeWa79	NiSiO ₃	856.5	SRD79
Br ₆ (Nb ₆ Cl ₁₂)(Bu ₄ N) ₂	204.7	BeWa79	NiWO ₄	857.7	NgHe76
Cl ₂ (Nb ₆ Cl ₁₂)(Pr ₃ P) ₄	204.6	BeWa79	NaNiO ₆ · H ₂ O	856.4	NZB78
Cl ₂ (Nb ₆ Cl ₁₂)(Me ₂ SO) ₄	204.6	BeWa79	K ₂ NiF ₆	861.0	TRLK73
Nd 3d			Ni(CO) ₄	854.8	BCGH72
Nd	980.8	Φ	Br ₂ Ni(NH ₃) ₆	855.9	NZB78
Nd ₂ O ₃	982.0	SaRa80	Ni(NH ₃) ₆ (ClO ₄) ₂	856.5	NZB78
Nd 4d			Ni(acac) ₂	855.9	NZB78, TRLK73
Nd ₂ O ₃	120.8	SaRa80	Ni(OAc) ₂ · 4H ₂ O	856.5	NZB78
Ne 1s			Ni(C ₃ H ₅)	854.2	BCDH73
Ne in graphite	863.1	Φ	Ni(C ₃ H ₅)	856.8	CIAd71, TRLK73
Ne in Ag	862.4	CiHa74	Cl ₂ Ni(Ph ₃ P) ₂	855.0	BNSA70
Ne in Au	861.6	CiHa74	Cl ₂ Ni(Ph ₃ P) ₂	854.4	NZB78
Ne in Cu	862.2	CiHa74	Cl ₂ Ni(Ph ₃ P) ₂	857.0	STHU76
Ne in Fe	863.4	Wagn75	Ni(dimethylglyoxim) ₂	855.0	NZB78, YoYa81
Ne KLL			Cl ₂ Ni(bipyridyl)	855.7	NSWU77, NZB78
Ne in Fe	818.0	Wagn75	Ni(SPh) ₂	854.6	BBFR77
Ni 2p			Cl ₂ Ni(NH ₂ CONHCONH ₂) ₂	856.7	YYS78
Ni	852.7	Φ	Ni(2-aminobenzoate) ₂	855.9	YoYa81
NiO	853.8	Φ	Ni(P(OEt) ₃) ₄	853.8	TRLK73
Ni	852.7	LANM81	Cl ₂ Ni(Et ₃ P) ₂	854.7	FaBa79
Ni	852.7	ALMP82	Br ₄ Ni(Et ₄ N) ₂	855.2	EMGK74
Ni	852.8	PEJ82	Ni LMM		
Ni	852.7	WRDM79, ShRe79	Ni	846.1	PEJ82
Ni ₃ Yb	852.7	WWC78	Ni	846.2	WRDM79
Ni ₂ Si	853.0	GGM82	Ni	846.1	KiWi74, KGW76
NiSi	853.5	GGM82	O 1s		
NiS	852.8	ShRe79	Al ₂ O ₃ , sapphire	531.0	Φ
NiS	853.2	DPS77	Ag ₂ O	529.2	Scho73
NiS	855.1	NgHe76	AgO	528.6	Scho73, SRD80
NiI ₂ · 6H ₂ O	855.3	NZB78	Al ₂ O ₃	531.3	Nefe82, SDR80,
NiCl ₂	856.7	TRLK73, KiHe83, YYS78	Al ₂ O ₃ , sapphire	531.0	BGD75, ZSOS79
NiF ₂ · 4H ₂ O	857.5	NSLS77	Al ₂ O ₃ , alpha	531.8	Tayl82, WPHK82
NiO	853.5	WRDM79	Al ₂ O ₃ , gamma	530.9	WPHK82
NiO	854.3	DPS77, KiHe83, LFWS79, NFS82, NZB78, SRD79	As ₂ O ₃	531.7	Tayl82, MINN78
NiO	854.3	KiWi74, McCo75	As ₂ O ₃	531.6	WZR80
Ni ₂ O ₃	857.3	NgHe76	B ₂ O ₃	533.0	NGDS75
			BaO	528.3	InYa81
			BeO	531.7	NGDS75, NFS75, HJGN70
			Bi ₂ O ₃	530.0	NGDS75, DSBG82
			CaO	529.4	InYa81

CaO	531.3	WZR80	Nb ₂ O ₅	530.6	NGDS75, NFS82
CdO	529.2	NFS75, NGDS75, SBB80	Nb ₂ O ₅	531.3	SaRa80
CdO ₂	530.3	HGW75	NbO ₂	530.7	SaRa80
Ce ₂ O ₃	530.3	PKHL80	Nd ₂ O ₃	530.6	SaRa80
CeO ₂	529.2	NGDS75	Ni ₂ O ₃	531.8	KiWi74, NgHe76
Co ₂ O ₃	529.9	McCo75	NiO	529.6	DPS77, LFWS79, NFS82, NGDS75, SRD79, WZR80
Co ₃ O ₄	530.2	NGDS75, WZR80	P ₂ O ₅ (bridging O)	532.2	NGDS75
Co ₃ O ₄	529.6	BGD75	P ₂ O ₅ (bridging O)	532.6	GMD79
Co ₃ O ₄	529.7	CBR76, GPDG79, HSU76	P ₂ O ₅ (nonbridging O)	533.6	NGDS75
CoO	530.1	BGD75, NFS82, NGDS75	P ₂ O ₅ (nonbridging O)	534.3	GMD79
Cr ₂ O ₃	531.0	HoTh80, DPS76, WZR80, BDFP81	PbO	528.9	NFS82
Cr ₂ O ₃	531.5	NGDS75	PbO	531.6	WZR80
CrO ₂	529.3	IIKK76	PbO, rhombic	529.4	KOW73
CrO ₃	530.2	DPS76	PbO, rhombic	530.9	ZiHe78
Cs ₂ O	527.5	YaBa80	PbO, tetragonal	527.5	KOW73
Cs ₂ O ₄	530.5	YaBa80	PbO, tetragonal	528.9	ZiHe78
Cu ₂ O	530.3	HMUZ78, MSSS81, RBO72, Scho73b	PbO ₂	527.4	KOW73
CuO	529.6	MSSS81, McCo75, HMUZ78, RBO72, Scho73b	PbO ₂	529.0	TLR78
Fe ₂ O ₃	530.2	NGDS75, WZR80, KiIk73, Limo81	PdO	529.3	KGW74
Fe ₂ O ₃	529.6	HSU76, NSLS77	Pr ₂ O ₃	529.3	SaRa80
Fe ₂ O ₃ , alpha	529.6	McZe77	PrO ₂	528.6	SaRa80
Fe ₂ O ₃ , gamma	529.8	McZe77	PtO ₂	531.4	CMHL77
Fe ₃ O ₄	530.0	McZe77	ReO ₂	530.1	BHU81
FeO	529.8	McZe77	ReO ₃	531.9	BHU81
Ga ₂ O ₃	530.8	NGDS75, Scho73a, WZR80, ZSOS79	Rh ₂ O ₃	530.4	CMHL77, NFS82
GeO ₂	520.0	NGDS75, WZR80	RuO ₂	529.4	MWLF78
H ₂ O	533.2	NGDS75, WZR80	RuO ₂	529.4	KiWi74, McGi82, SaRa80
HfO ₂	530.4	NGDS75	RuO ₃	530.7	KiWi74
I ₂ O ₅	529.9	Sher76	Sb ₂ O ₃	530.0	WZR80
In ₂ O ₃	529.8	NGDS75	Sc ₂ O ₃	530.0	NGDS75, WZR80
In ₂ O ₃	530.3	CFRS80	SiO ₂	533.0	Barr83, KMH78, NGDS75
In ₂ O ₃	530.5	LAK77	SiO ₂	534.3	KiIk73
La ₂ O ₃	528.6	NGDS75	SiO ₂	532.5	NSLS77, SRD79
Li ₂ O	531.3	CSFG79	SiO ₂ , gel	532.8	WPHK82
Lu ₂ O ₃	529.5	NGDS75	SiO ₂ , Vycor	532.9	WPHK82
MgO	530.0	NFS82, NGDS75	SiO ₂ , alpha cristobal	532.5	WPHK82
MgO	531.2	InYa81	SiO ₂ , alpha quartz	532.7	WPHK82
MgO	532.1	WZR80	SiO ₂ , alpha quartz	533.2	TLR78
MnO	529.7	OHI75	SnO	530.1	ADPS77
Mn ₃ O ₄	529.6	OHI75	SnO ₂	530.6	ADPS77, LAK77, MWLF78, NGDS75, TLR78
Mn ₂ O ₃	529.6	OHI75	SrO	530.5	VaVe80
MnO ₂	530.0	NGDS75, WZR80	Tb ₂ O ₃	528.8	SaRa80
MnO ₂ , beta	529.6	OHI75	TbO ₂	528.8	SaRa80
MoO ₂	531.1	PCLH76	TeO ₂	530.2	GBP81, SBB80
MoO ₂	530.7	CGR78, KBAW74	ThO ₂	530.0	NGDS75
MoO ₂	529.9	SaRa80	TiO ₂	529.9	MWLF78, WZR80, NGDS75
MoO ₃	530.9	NGDS75, NFS82	UO ₂	530.4	MSSS81
MoO ₃	531.6	PCLH76	UO ₃	529.9	MSSS81
MoO ₃	530.4	SaRa80, KBAW74, HMUZ78, CGR78	V ₂ O ₃	530.5	CGR78
Na ₂ O	529.7	BaSi75	V ₂ O ₄	530.0	KKL83
Nb ₂ O ₅	529.6	GBP81	V ₂ O ₅	529.9	BCM78, KKL83
			VO ₂	530.5	NSLS77, NGDS75, NFS82
				530.4	CoRa76

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OsCl ₄ (PhPMe ₂) ₂ trans	53.0	LeBr72
OsCl ₃ (PhPMe ₂) ₃ mer	51.7	LeBr72
OsCl ₂ (PhPMe ₂) ₄ trans	50.5	LeBr72
P 2p		
P	129.9	Φ
P	130.0	NSDU75
P (red)	130.0	ScBr81
Cu ₃ P	129.6	NSDU75
CuP ₂	129.7	NSDU75
GaP	128.8	WaTa80, LMNN79, NIMN78
GaP, anodically oxid.	128.5	MIN81
GaP, thermally oxid.	129.7	MIN81
InP	128.3	CFRS80
InP	129.4	Bert81
Zn ₃ P ₂	128.3	NSDU75
ZnP ₂	129.8	NSDU75
AlPO ₄	132.9	CFRS80
C ₃ PO ₄	132.1	MVS73
K ₂ HPO ₄	132.8	Bert81
K ₃ PO ₄	133.2	MVS73
Li ₃ PO ₄	133.6	MVS73
Na ₂ HPO ₄	133.1	Swif82, WRDM79, WaTa80
Na ₃ PO ₄	132.4	MVS73, GMD79, Swif82
NaH ₂ PO ₄	134.2	Swif82
NaPO ₃	134.2	Swif82, GMD79
Rb ₃ PO ₄	132.5	MVS73
NaH ₂ PO ₂	132.6	Swif82
Cs ₄ P ₂ O ₇	132.6	MVS73
K ₄ P ₂ O ₇	132.6	MVS73
Li ₄ P ₂ O ₇	134.3	MVS73
Na ₄ P ₂ O ₇	133.2	MVS73, GMD79, Bert81
Rb ₄ P ₂ O ₇	133.1	MVS73
P ₄ O ₁₀	135.3	NIMN78, NGDS75, CFRS80, Bert81, GMD79
OPCl ₃	135.7	FIWe75
SPCl ₃	135.3	FIWe75
SP(NH ₃) ₃	133.4	FIWe75
Ph ₃ P	130.9	Dale76, NSMS79, TRLK73, GBMP79
Ph ₃ P	130.9	HVV79, LMF80, SRH72
Ph ₃ P	130.9	MSAV71, GZF73
Ph ₃ PS	132.5	HVV79, STA74, FIWe75, MSAV71
Ph ₃ PSe	132.6	HVV79, MSAV71
Ph ₃ PO	132.5	GZF73, STA74, FIWe75, MSAV71, HVV79, BNSA70
Ph ₃ PBI ₃	132.2	HVV79
Ph ₃ PBBBr ₃	132.1	HVV79
Ph ₃ PBCl ₃	132.2	HVV79
Ph ₃ PBF ₃	132.0	HVV79
Ph ₂ PSH	132.3	NSWM80
Ph ₂ PSeH	132.3	NSWM80
(PhS) ₃ P	134.3	MSAV71
(PhS) ₃ PS	133.1	MSAV71
(PhO) ₃ P	134.7	MSAV71

(PhO) ₃ PS	134.7	MSAV71
(PhO) ₃ PSe	134.3	MSAV71
(PhO) ₃ PO	133.6	CFRS80
(PhO) ₃ PO	134.8	FIWe75
Ph ₃ POBBBr ₃	133.7	HVV79
Ph ₃ POBCl ₃	133.4	HVV79
Ph ₃ POBF ₃	133.3	HVV79
Ph ₂ PO(OH)	133.3	MSAV71
OPCl(OEt) ₂	134.8	FIWe75
OPF ₂ NPh ₂	135.8	FIWe75
OPCl ₂ OEt	135.2	FIWe75
OP(NMe ₃) ₃	133.4	FIWe75
Ph ₄ PI	133.0	HVV79
Ph ₄ PBr	133.5	LMF80, SRH72
Ph ₄ PCl	132.8	HVV79
MePPh ₃ Br	133.0	SRH 2
(Ph ₃ P) ₃ P*F ₆	136.7	LMF80
(Ph ₃ P*) ₃ PF ₆	133.5	LMF80
Pt(Ph ₃ P) ₄	131.2	Rigg72
Ph ₃ P=CHCOPh	132.2	Dale76, STA74
Ph ₃ P=CHCOOMe	132.5	STA74
Cl ₂ Ni(Ph ₃ P) ₂	132.4	BNSA70
Ni(CO) ₂ (Ph ₃ P) ₂	131.4	TRLK73

Pb 4f

Pb	136.9	Φ
Pb	136.4	LKMP73
Pb	136.8	SFS77
Pb	136.8	BeFI80, KOW73, KiWi73, TLR78, WRDM79, WaTa80
Pb	136.8	HSBS81, OCH79
Pb ₉₆ Sn ₂	136.8	HSBS81
PbTe	137.4	SFS77
PbSe	137.4	SFS77
PbS	137.6	MoVa73, SFS77, ZiHe78
PbI ₂	138.7	MoVa73
PbBr ₂	138.8	NeFe82
PbF ₂	139.0	MoVa73
PbO	138.9	KOW73, ZiHe78, WRDM79, NFS82, NSSP80, MoVa73
PbO	138.9	MoVa73, BeFI80
Pb ₃ O ₄	138.0	MoVa73
PbO ₂	137.4	BeFI80, KOW73, TLR78, MoVa73
Pb(OH) ₂	138.4	NSSP80
Pb(NO ₃) ₂	139.3	BeFI80, TLR78, NSSP80
PbSO ₃	138.6	ZiHe78
PbSO ₄	139.4	NSSP80, ZiHe78
PbS ₂ O ₃	138.4	ZiHe78
PbRh ₂ O ₄	137.3	NFS82
Ph ₄ Pb	138.2	MoVa73
Ph ₃ PbCl	138.9	MoVa73
Ph ₂ PbCl ₂	139.4	MoVa73
Pb(OAc) ₂	138.5	BeFI80
Pb(OAc) ₄	137.2	BeFI80

Pd 3d

Pd	335.1	Φ
Pd	335.1	NyMa80
Pd	335.2	BiSw80
Pd	335.2	BiSw80
Pd	335.5	BiSw80
Pd	335.2	JHBK73, Asam76
Pd	335.3	WRDM79, WeAn80, BHHK70, Scho72, GGM82, KBAM72
Ag ₃ OPd ₅ O	334.6	WeAn80
Ag ₅ OPd ₇ O	334.9	WeAn80
Ag ₉ OPd ₁ O	334.9	WeAn80
Al ₅ OPd ₂ O	337.4	WeAn80
Mg ₇₅ Pd ₂₅	336.2	WeAn80
Pd ₂ Si	336.8	GGM82
Pd ₃ Si	336.2	AWL80
PdI ₂	336.4	KBAM72
PdBr ₂	337.1	KBAM72
PdCl ₂	337.8	KBAM72, NKBP73
PdO	336.3	KGW74
PdO ₂	337.9	KGW74
Na ₂ PdCl ₄	338.0	SeTs76
K ₂ PdCl ₄	338.2	KBAM72, NKBP73
K ₂ PdBr ₄	337.3	KBAM72
K ₂ Pd(NO ₂) ₄	339.0	KBAM72
K ₂ PdCl ₆	340.2	KBAM72, Nefe78
Br ₂ Pd(Ph ₃ P) ₂	337.8	KBAM72
Cl ₂ Pd(Ph ₃ P) ₂	337.8	KBAM72, NSMS79
I ₂ Pd(Ph ₃ P) ₂	337.5	KBAM72
(CN) ₂ Pd(Ph ₃ P) ₂	338.2	KBAM72
Pd ₂ (Ph ₃ P) ₂	336.6	NSMS79
Cl ₂ Pd(Ph ₃ P) ₃	342.9	BNSA70
Pd(Ph ₃ P) ₄	336.0	NSMS79
Pd(OAc) ₂	338.6	NSMS79
Pd(SPh) ₂	337.7	BBFR77

Pd MNN

Pd	327.8	WeAn80, WRDM79
Ag ₃ OPd ₅ O	328.8	WeAn80
Ag ₅ OPd ₇ O	329.8	WeAn80
Ag ₉ OPd ₁ O	329.7	WeAn80
Al ₅ OPd ₂ O	325.5	WeAn80
Mg ₇₅ Pd ₂₅	326.4	WeAn80

Pm 3d

PmCl ₃	1033.5	MNTB70
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Pm 4d

PmCl ₃	128.3	MNTB70
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Pr 3d

Pr	931.8	Φ
Pr ₂ O ₃	933.2	SaRa80
PrO ₂	935.3	SaRa80

Pr 4d

Pr ₂ O ₃	116.1	SaRa80
PrO ₂	116.2	SaRa80

Pt 4f

Pt	71.2	Φ
Pt	71.0	JHBK73
Pt	71.2	BHHK70, KWD71, Nefe78, Scho72, WRDM79, Wagn75
Pt	71.2	CMHL77, CaLe73, HaWi77, BACB75
PtSi	73.0	GGM82
Pt ₂ Si	72.5	GGM82
PtCl ₂	73.6	EPCC75
PtCl ₄	75.5	EPCC75
PtO	73.8	KWD71
PtO	74.2	EPCC75
PtO ₂	74.6	KWD71
PtO ₂	75.0	EPCC75
Pt(OH) ₂	72.6	HaWi77
K ₂ PtI ₆	73.4	SNMK78
K ₂ PtBr ₄	72.6	SNMK78
K ₂ PtBr ₆	74.6	SNMK78
K ₂ PtCl ₄	73.0	CMHL77, EPCC75, SNMK78
K ₂ PtCl ₄	73.4	Wagn75
K ₂ PtCl ₆	75.4	CoHe72, EPCC75, LeBr72, SNMK78
K ₂ PtF ₆	77.6	SNMK78
Pt(NH ₃) ₄ Br ₂	73.4	Nefe78
Pt(NH ₃) ₂ Cl ₂	73.2	CMHL77, Nefe78
Pt(NH ₃) ₄ Cl ₂	73.4	SNMK78
Pt(NH ₃) ₆ Cl ₄	76.3	SNMK78
Pt(NH ₃) ₂ (NO ₂) ₂	73.7	Nefe78
Pt(NH ₃) ₂ (NO ₂) ₂	74.4	CMHL77
K ₂ Pt(OH) ₆	75.1	SNMK78
K ₂ Pt(NO ₂) ₄	74.1	SNMK78
K ₂ Pt(NO ₂) ₆	75.9	SNMK78
(NH ₄) ₂ PtCl ₄	72.4	KaEl79
Pt(Ph ₃ P) ₃	71.4	Nefe78
Pt(Ph ₃ P) ₄	71.4	Rigg72
Cl ₂ Pt(Ph ₃ P) ₂ cis	72.3	CAB71
Cl ₂ Pt(Ph ₃ P) ₂ cis	73.0	Rigg72
Cl ₄ Pt(Et ₃ P) ₂	75.3	LeBr72
Cl ₄ Pt(Et ₃ P) ₂	75.9	Nefe78, Rigg72
HClPt(Et ₃ P) ₂	72.6	Rigg72
O ₂ Pt(Ph ₃ P) ₂	73.0	Rigg72
Pt(SPh) ₂	72.8	BBFR77
Ph ₃ PPt(SPPH ₂)	71.8	NeSa78
Cl ₂ Pt(Et ₃ P) ₂	73.1	Rigg72
I ₂ Pt(Et ₃ P) ₂	72.5	Rigg72
I ₂ Pt(Me ₃ P) ₂ cis	72.6	CAB71
I ₂ Pt(Me ₃ P) ₂ trans	72.7	CAB71
I ₂ Pt(CH ₃ CONH) ₄	74.6	NeSa78
Br ₂ Pt(CH ₃ CONH) ₄	74.9	NeSa78
Cl ₂ Pt(CH ₃ CONH) ₄	74.8	NeSa78

Cl ₂ Pt(H ₂ NCH ₂ CH ₂ NH ₂) ₂	73.0	YMK78	Rh ₂ WO ₆	309.4	NFS82
Cl ₂ Pt(cyclooctadien)	73.9	CMHL77	RhNbO ₄	309.2	NFS82
K ₂ PtCl ₆	318.1	EPCC75	RhTaO ₄	309.5	NFS82
Pt M₅N₇N₇			RhVO ₄	309.2	NFS82
Pt	1960.7	Wagn78	K ₃ RhCl ₆	309.8	SNMK78
Pt(M ₄ N ₇ N ₇)	2041.1	Wagn78	K ₃ RhF ₆	312.2	Nefe78
Rb 3d			K ₃ Rh(NO ₂) ₆	310.5	SNMK78
Rb	111.5	Φ	K ₃ Rh(NO ₃) ₆	311.1	SNMK78
RbCl	109.9	Φ	Rh(NH ₃) ₆ Cl ₃	310.5	Nefe78
RbN ₃	109.8	SGRS72	Rh(NO) ₆ Cl ₃	309.8	Nefe78
RbI	110.4	MVS 73	ClRh(Ph ₃ P) ₃	307.4	CWH82, Nefe78, OIIT79
RbBr	110.0	MVS 73	Cl ₃ Rh(Ph ₃ P) ₃	309.7	CWH82
RbCl	109.9	MVS 73	Cl ₆ Rh(Ph ₃ P) ₃	309.7	Nefe78
RbF	109.8	MVS 73	Br ₆ Rh(Ph ₃ P) ₃	307.9	Nefe78
Rb ₃ PO ₄	110.0	MVS 73	NORh(Ph ₃ P) ₃	308.2	Nefe78
Rb ₄ P ₂ O ₇	110.0	MVS 73	Cl ₃ Rh(Ph ₃ P) ₂ MeCN	309.6	GIWa79
RbClO ₄	110.4	MVS73	H(CO)Rh(Ph ₃ P) ₂	308.5	OIIT79
Re 4f			Cl(CO) ₂ Rh(Ph ₃ P)	308.7	Nefe78
Re	40.3	Φ	Cl(CO)Rh(Ph ₃ P) ₂	308.6	CWH82, OIIT79
Re	40.5	FHR80	Cl ₂ Rh ₂ (cyclooctadi) ₂	308.7	CMHL77, CWH82
Re	40.5	SSHU83, WRDM79	Rh ₂ (OAc) ₄ · 2H ₂ O	309.0	Nefe78
Re	41.0	BHU81	Rh(NH ₂ CH ₂ COO) ₃ · H ₂ O	310.3	NPBS74
ReO ₂	43.6	BHU81	Ru 3d		
ReO ₃	46.8	BHU81	Ru	280.1	Φ
K ₂ ReCl ₆	44.2	CoHe72, LeBr72	Ru	280.0	NyMa80
Cl ₃ ReO(Ph ₃ P) ₂	43.9	Folk73, Nefe78	Ru	280.1	Folk73, BHHK70, KiWi74, FEMY77, WRDM79
Cl ₂ ReN(Ph ₃ P) ₂	42.7	Nefe78	RuCl ₃	281.8	Folk73
Cl ₄ Re(Et ₃ P) ₂	43.3	LeBr72	RuO ₂	280.7	SaRa80, KiWi74, McGi82
Cl ₄ Re(PMe ₂ Ph) ₂	43.6	LeBr72	RuO ₃	282.5	KiWi74
Cl ₃ Re(PMe ₂ Ph) ₃ , mer	41.8	LeBr72	RuO ₄	283.3	KiWi74
Cl ₂ Re(PMe ₂ Ph) ₄ , trans	40.5	LeBr72	Ru(NH ₃) ₅ N ₂ I ₂	282.2	Folk73
ClReN ₂ (PMe ₂ Ph) ₄ , trans	40.3	LeBr72, Folk73	Ru(NH ₃) ₅ N ₂ Br ₂	280.5	Folk73
Rh 3d			Ru(NH ₃) ₅ N ₂ Cl ₂	282.5	Folk73
Rh	307.2	Φ	Cl ₃ Ru(PhPMe ₂) ₃ mer	276.6	LeBr72
Rh	307.2	NyMa80	S 2p		
Rh	307.2	OIIT79, WRDM79, FHPW73	S	164.0	Φ
RhI ₃	308.6	Nefe78	S	164.1	SNRS76, WRDM79, RiVe83, LHJG70
RhCl ₃	310.1	OIIT79	BaS	160.1	SiWo80
RhCl ₃ · 3H ₂ O	310.0	CWH82	CdS	161.7	BSRR81
RhCl ₃ · 12H ₂ O	310.1	CMHL77	CoS	162.0	Limo81
Rh ₂ O ₃	308.8	NFS82, CMHL77	Cu ₂ S	161.3	BSRR81
Rh ₂ O ₃	308.2	OIIT79	Cu ₂ S	162.4	NSSP80
BaRh ₂ O ₄	308.4	NFS82	CuS	162.0	Limo81, NSSP80
BeRh ₂ O ₄	308.9	NFS82	CuS	161.3	BSRR81
CaRh ₂ O ₄	308.8	NFS82	FeS	161.6	Bind73, Limo81
CoRh ₂ O ₄	308.8	NFS82	FeS ₂	162.9	Bind73, Limo81
PbRh ₂ O ₄	308.6	NFS82	Ga ₂ S ₃	162.2	TIWB72
KRhO ₂	308.5	NFS82	GeS	161.8	SFS77
LiRhO ₂	308.9	NFS82	GeS ₂	161.7	HKMP74
ZnRh ₂ O ₄	308.7	NFS82	HgS	162.0	NSSP80
Rh ₂ MnO ₆	309.2	NFS82	MnS	162.5	Limo81

MoS ₂	162.5	SSOT81, SiEd75, PCLH76
Na ₂ S	160.6	SWH71
Na ₂ S	161.8	LHJG70
NiS	162.2	ShRe79, NgHe76, DPS77
PbS	160.8	SFS77
Sb ₂ S ₃	161.8	BCH75
SnS	161.1	SFS77
US	161.5	SNRS76
US ₃	162.6	SNRS76
WS ₂	162.1	NgHe76
WS ₂	163.0	Wagn75
ZnS	164.0	Limo81
GeS ₂ TeAs ₂	161.5	HKMP74
GeS ₃ As ₂	161.6	HKMP74
KFeS ₂	161.6	Bind73
Na ₂ (S*SO ₃)	162.5	Wagn75
Na ₂ (S*SO ₃)	161.7	LHJG70
Na ₂ (SS*O ₃)	167.7	LHJG70
K ₂ SO ₃	167.5	TMR80
Na ₂ SO ₃	165.6	SWH71
Na ₂ SO ₃	166.6	WaTa82, LHJG70
Na ₂ SO ₃	167.2	TMR80
Ag ₂ SO ₄	168.6	TMR80
Al ₂ (SO ₄) ₃	168.8	LHJG70
BaSO ₄	168.8	SiWo80, CLSW83
CaSO ₄	169.0	CLSW83
CoSO ₄	169.7	Limo81
CuSO ₄	169.3	WaTa80, NSSP80, Limo81
FeSO ₄	168.8	Limo81, LHJG70
Fe ₂ (SO ₄) ₃	169.1	LHJG70
K ₂ SO ₄	169.1	TMR80
MnSO ₄	171.0	Limo81
Na ₂ SO ₄	168.8	TMR80
NiSO ₄	169.2	Limo81, NSLS77, Nefe82, ShRe79
PbSO ₄	168.6	NSSP80
SiSO ₄	169.1	CLSW83
U(SO ₄) ₂	169.1	Chad73
ZnSO ₄	169.5	Nefe82
NO ₂ SO ₃	166.8	BCM78
S ₂ N ₂	164.6	SDIO77
SF ₆	174.4	WaTa82
SF ₆	177.2	LHJG70
SO ₂	167.4	WaTa82
SO ₂	168.1	LHJG70
SOCl ₂	168.1	LHJG70
SOF ₂	170.0	LHJG70
SP(NH ₃) ₃	162.3	FIWe75
SPCl ₃	163.7	FIWe75
S ₂ Cl ₂	163.5	LHJG70
S ₂ Cl ₁₀	174.4	LHJG70
CS ₂	163.7	LHJG70
(CH ₂ COOH) ₂ S	163.7	LHJG70
(CH ₂ Ph) ₂ S	163.3	LHJG70
PhSH	163.1	LHJG70
Ph ₂ S	163.2	LHJG70

Thiophene	164.3	LHJG70
Ph ₃ PS	162.4	FIWe75, MSAV71
Ph ₃ PS	161.8	HVV79
Ph ₃ AsS	161.7	HVV79
PhSSPh	164.4	RiVe83, LHJG70
PhCH ₂ SSCH ₂ Ph	164.2	RiVe83
(PhS) ₃ P	163.6	MSAV71
(PhS) ₃ PS	163.5	MSAV71
BuSSBu	164.1	RiVe83
MeSSMe	164.3	RiVe83
NH ₂ CSNH ₂	162.1	LeRa77, NBMO73, SrWa77
2-Mercaptobenzimidaz	162.2	YYS79
2-Mercaptobenzimidaz	162.8	ChHa79
BuNH ₂ HSO ₄	167.3	EvRe81
Bu ₄ NHSO ₄	168.0	EvRe81
Et ₃ NHHSO ₄	168.5	EvRe81
PhSCMe ₃	162.4	PiLu72
Tetrathionaphthalene	164.4	RiVe83
Cysteine	163.2	LiMa79, LHJG70
Cysteine HCl hydrate	163.1	SSEW79
Cysteine HCl hydrate	163.6	LHJG70
Methionine	162.8	BBFR77
NH ₂ C ₆ H ₄ SO ₃ H	167.8	HaSh73
(MeOS) ₂	164.5	LHJG70
Me ₂ SO	166.5	LHJG70
(PhCH ₂) ₂ SO	165.9	LHJG70
Ph ₂ SO	166.0	LHJG70
Me ₂ SO ₂	169.0	LHJG70
CH ₃ OS(O)OCH ₃	168.4	LHJG70
MeSO ₂ Cl	169.3	LHJG70
ClC ₆ H ₄ CH ₂ SO ₂ Cl	168.5	LHJG70
PhSO ₂ Na	166.3	LHJG70
p-NH ₂ C ₆ H ₄ SO ₂ C ₆ H ₄ NH ₂	167.9	LHJG70
p-NH ₂ C ₆ H ₄ SO ₂ NH ₂	168.4	LHJG70
p-CH ₃ C ₆ H ₄ SO ₂ Cl	168.4	LHJG70
p-NH ₂ C ₆ H ₄ SO ₃ Na	168.1	LHJG70
p-O ₂ NC ₆ H ₄ SNa	161.0	LHJG70
CO ₂ NC ₆ H ₄ SH	163.5	LHJG70
o-O ₂ NC ₆ H ₄ SH	163.9	LHJG70
p-O ₂ NC ₆ H ₄ SMe	163.5	LHJG70
o-O ₂ NC ₆ H ₄ SNH ₂	164.1	LHJG70
o-O ₂ NC ₆ H ₄ SCl	163.9	LHJG70
p-O ₂ NC ₆ H ₄ SO ₂ F	169.6	LHJG70
o-O ₂ NC ₆ H ₄ SO ₂ F	170.0	LHJG70
PhCH ₂ SSCH ₂ Ph	163.6	LHJG70
PhCH ₂ S*SOCH ₂ Ph	163.7	LHJG70
PhCH ₂ SS*OCH ₂ Ph	165.9	LHJG70
PhCH ₂ S*SO ₂ CH ₂ Ph	163.9	LHJG70
PhCH ₂ SS*O ₂ CH ₂ Ph	168.0	LHJG70
(CH ₃) ₃ S+I-	165.8	LHJG70
(CH ₃) ₃ S+(O)I-	168.2	LHJG70
(HOOCCH ₂) ₂ S+CH ₂ COO-	166.2	LHJG70

S KLL

NiS	2116.1	WaTa80
NiW ₂ S	2115.9	Wagn78

WS ₂	2115.6	Wagn78	Sc 2p		
Na ₂ SO ₃	2108.5	WaTa82	Sc	398.6	Φ
Na ₂ (SS*O ₃)	2107.8	Wagn75	Sc ₂ O ₃	401.8	Φ
Na ₂ (S*SO ₃)	2112.5	Wagn75	Sc	398.7	SMKM77
CuSO ₄	2108.0	WaTa80	ScN	400.7	STAB76
SO ₂	2106.2	WaTa82	Sc ₂ O ₃	401.9	NGDS75, WRDM79
SF ₆	2100.5	WaTa82	ClSc(C ₃ H ₅) ₂	401.4	WeMe78
			Sc(C ₃ H ₅)(C ₈ H ₈)	400.2	WeMe78
Sb 3d_{5/2}			Se 3d		
\$b	528.3	Φ	Se	55.6	Φ
\$b	528.2	HSBS81, MSV 73, PVVA79, SFS77, WRDM79, Wagn75	Se	55.5	SFS77, BWI80, UeOd82, WRDM79, WSP77, MTHB71
AlSb	528.6	MSV73	Se	55.1	BWI80
\$b_{0.5}Sn_{0.5}	528.0	HSBS81	As ₂ Se ₃	55.1	UeOd82, WSP77
\$b_2S_3	529.5	MSV73, Wagn75	Ga ₂ Se ₃	54.6	ITI82, TIWB72
\$b_2S_5	529.2	MSV73, Wagn75	GeSe	54.8	SFS77
\$bI_3	530.4	MSV73	GeSe ₂	54.5	UeOd82
\$bCl_5	530.9	BCH75	CuInSe ₂	54.0	KJID81
\$bF_3	531.7	MSV73	In ₂ Se ₃	54.8	KJID81
\$b_2O_3	530.0	MSV73, Wagn75	Nb ₃ Se ₄	54.9	Bahl75
\$b_2O_5	530.8	MSV73	NbSe ₂	53.7	Bahl75
Rb ₃ Sb ₂ Br ₉	529.9	Tric74	PbSe	53.4	SFS77
Rb ₃ Sb ₂ I ₉	529.9	Tric74	PbSe	54.1	WSP7
C ₅ Sb ₂ I ₉	529.2	BCH75	SnSe	53.7	SFS77
C ₅ Sb ₂ Br ₉	530.0	BCH75, Tric74	SnSe	55.0	WSP77
C ₅ Sb ₂ Cl ₉	529.3	BCH75	MoSe ₂	54.6	BWI79
C ₅ Sb ₂ Cl ₉	530.5	Tric74	FeSe ₂	54.9	BWI79
C ₃ SbCl ₆	530.9	Tric74	SeO ₂	58.9	BWI81, ITI82
Co(NH ₃) ₆ SbBr ₆	530.1	Tric74	SeO ₂	59.8	MTHB71, WSP77
Co(NH ₃) ₆ SbCl ₆	530.8	Tric74	H ₂ SeO ₃	59.2	BWI81
KSbF ₆	532.3	MSV73	H ₂ SeO ₃	59.9	MTHB71
KSbF ₆	532.9	Wagn75	H ₂ SeO ₄	61.2	BWI81
NaSbF ₆	532.1	BCH75	Na ₂ SeO ₃	59.1	WSP77
C ₅ SbF ₄	530.6	BCH75	Na ₂ SeO ₄	61.6	WSP77
KSb ₂ F ₇	531.2	Tric74	Na ₂ SeS ₄ O ₆	56.9	WSP77
K ₂ SbF ₅	531.0	Tric74	Ph ₂ Se	55.8	BWI81
Na ₂ SbF ₅	531.3	Tric74	(BrC ₆ H ₄) ₂ Se	56.4	MTHB71
BuNH ₃ SbI ₄	529.6	BCH75	Ph ₂ Se ₂	55.8	BWI81
BuNH ₃ Sb ₂ I ₉	529.9	BCH75	(BrC ₆ H ₄) ₂ Se ₂	56.0	BWI81
Et ₄ NSbF ₆	532.4	BCH75	(C ₁₄ H ₂₉ Se) ₂	56.1	MTHB71
Ph ₃ Sb	528.9	BCH75	I ₂ SePh ₂	58.1	BWI81
Bu ₃ Sb	528.1	BCH75	Br ₂ SePh ₂	57.8	BWI81
Ph ₃ SbBr ₂	529.8	BCH75	Cl ₂ SePh ₂	57.7	BWI81
Me ₃ SbBr ₂	530.3	BCH75	Cl ₂ SePh ₂	58.8	MTHB71
Ph ₃ SbS	528.7	BCH75	C ₁₆ H ₃₃ SeCN	57.7	MTHB71
(C ₁₂ H ₂₅) ₃ SSb	529.8	MSV73	HSePh ₂ P	54.5	NSWM80
Ph ₃ PSbCl ₆	531.7	MSV73	SePh ₃ P	54.3	HVV79
Sb MNN			Ph ₂ SeO	57.6	BWI81
Sb	464.1	WRDM79, PVVA79, Wagn75	(PhCH ₂) ₂ SeO	58.2	MTHB71
Sb ₂ S ₃	462.1	Wagn75	(BrC ₆ H ₄) ₂ SeO	58.4	MTHB71
Sb ₂ S ₅	462.2	Wagn75	(C ₄ H ₉ COOH) ₂ SeO	58.5	MTHB71
Sb ₂ O ₃	462.1	Wagn75	PhSeO(OH)	58.8	MTHB71
KSbF ₆	454.4	Wagn75	ClC ₆ H ₄ SeO(OH)	59.3	MTHB71

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Natrolite	1609.6	WPHK82	Ph ₄ Sn	487.1	HWVV74
Pyrophyllite	1609.2	WPHK82	Ph ₃ SnI	486.3	WVV79
AlSiO ₅ , sillimanite	1609.5	WPHK82	Ph ₃ SnI	487.5	HWVV74
LiAlSi ₂ O ₆ , spodumene	1609.6	WPHK82	Ph ₃ SnBr	487.5	HWVV74
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	1608.9	WPHK82	Ph ₃ SnCl	486.3	WVV79
Wollastonite, Ca ₃ Si ₃ O ₉	1610.0	WPHK82	Ph ₃ SnCl	487.0	MoVa73
Mol Sieve A	1610.1	WPHK82	Ph ₃ SnCl	487.6	HWVV74
Mol Sieve X	1609.4	WPHK82	Ph ₃ SnF	486.2	WVV79
Mol Sieve Y	1608.6	WPHK82	Ph ₃ SnF	487.3	HWVV74
p-Methylsil. (linear)	1609.4	WPHK82	Ph ₃ SnOH	485.6	WVV79
p-Methylsil. (resin)	1608.8	WPHK82	Cl ₄ Sn(pyridine) ₂	487.3	WVV79
p-Phenylsil. (resin)	1610.0	WPHK82	Cl ₃ SnEt(pyridine) ₂	487.2	WVV79
			Cl ₃ SnPh(pyridine) ₂	487.2	WVV79
			Me ₃ SnF	486.7	WVV79
			Me ₂ SnF ₂	487.1	WVV79
			Me ₂ SnSO ₄	487.0	WVV79
			Bu ₂ SnO	485.6	WVV79
			Br ₆ Sn(Et ₄ N) ₂	487.0	WVV79
			Cl ₃ Sn(Me ₄ N)	486.1	GZF73
			Cl ₄ Sn(Me ₂ SO) ₂	487.0	GZF73, WVV79
Sm 3d_{5/2}			Sn MNN		
Sm	1081.1	Φ	Sn	437.4	PVVA79, Wagn75, WRDM79, LAK 77
Sm	1081.2	DKMB76	SnS	435.7	Wagn75
Sm ₂ O ₃	1083.4	WRDM79	SnO ₂	432.7	LAK77
			NaSnF ₃	430.8	Wagn75
			Na ₂ SnO ₃	431.7	Wagn75
Sn 3d_{5/2}			Sr 3d		
Sn	485.0	Φ	Sr	134.3	Φ
Sn	484.9	NyMa80	Sr	134.4	VaVe80
Sn	485.1	SFS77	SrO	135.3	VaVe80
Sn	485.0	WRDM79, PVVA79, LAK 77, Wagn75, OCH 79	SrF ₂	133.8	WRDM79
Sn alpha	485.0	Hegd82	SrCO ₃	133.2	CLSW83
Sn beta	484.6	Hegd82, HSBS81	SrSO ₄	134.3	CLSW83
Ag ₉₅ Sn ₅	485.6	HSBS81, Hegd82	Sr(NO ₃) ₂	134.7	CLSW83
AuSn	485.2	FHPW73	SrMoO ₄	133.5	NFS82
AuSn ₄	484.9	FHPW73	SrRh ₂ O ₄	133.0	NFS82
Cd ₉₉ · 5Sn · OO ₅	485.3	Hegd82	Ta 4f		
Cd ₉₅ Sn ₅	485.6	Hegd82	Ta	21.9	Φ
In ₉₅ Sn ₅	485.2	Hegd82	Ta	21.6	VHE82
Pb ₉₅ Sn ₅	486.4	Hegd82	Ta	21.6	MSC73
Sb ₉₅ Sn ₅	485.2	Hegd82	Ta	21.9	WRDM79, WaTa80
SnTe	485.6	SFS77	TaS	26.6	MSC73
SnSe	485.7	SFS77	Ta ₂ S ₂	26.7	MSC73
SnS	485.6	SFS77	TaBr ₅	26.9	MSC73
SnBr ₂	486.9	GZF73	TaCl ₅	27.3	MSC73
SnCl ₂	486.7	WVV79	TaF ₅	27.8	MSC73
SnF ₂	487.0	MoVa73	Ta ₂ O ₅	26.7	SaRa80, MSC 73, NFS82, NGDS75
SnF ₂	487.0	MoVa73			
SnO	486.0	ADPS77	KTaO ₄	25.9	MSC73
SnO	486.9	WVV79, MoVa73	RhTaO ₄	25.8	NFS82
SnO ₂	486.7	LAK 77, MoVa73, WRDM79, NGDS75, WVV79	K ₂ TaF ₇	29.4	MSC73
(NH ₄) ₂ SnCl ₆	486.7	GZF73			
BaSnCl ₄	486.8	WVV79			
Ba(SnCl ₃) ₂	486.8	WVV79			
KSnF ₃	486.7	GZF73			
K ₂ SnF ₆	487.6	MoVa73			
NaSnF ₃	487.4	Wagn75			
Na ₂ SnO ₃	486.2	MoVa73			
Na ₂ SnO ₃	486.7	Wagn75			
Na ₂ SnO ₃	487.2	ADPS77			
Ph ₄ Sn	485.1	WVV79			
Ph ₄ Sn	486.3	MoVa73			

$\text{Cl}_2\text{Ta}_6\text{Cl}_{18}(\text{H}_2\text{O})_4 \cdot 4\text{H}_2\text{O}$	25.8	BeWa79			
$\text{Br}_n(\text{Ta}_6\text{Cl}_{12})(\text{Bu}_4\text{N})_2$	26.3	BeWa79			
$\text{Cl}_6(\text{Ta}_6\text{Cl}_{12})(\text{Et}_4\text{N})_2$	26.2	BeWa79			
Ta MNN					
Ta	1674.8	WaTa80			
Tb 4d					
Tb	146.0	Φ			
Tb_2O_3	148.7	SaRa80			
TbO_2	149.2	SaRa80			
Tb 3d					
Tb	1242.0	Φ			
Tb_2O_3	1241.5	SaRa80			
TbO_2	1241.4	SaRa80			
Te 3d5/2					
Te	573.1	Φ			
Te	573.0	NyMa80			
Te	573.0	SFS77			
Te	573.0	PVVA79, WRDM79, BWI77, Bahl75			
Te	572.7	SNRS76, SWH71			
CdTe	572.3	SBB80			
GeTe	572.7	SFS77			
$\text{Hg}_{0.8}\text{Cd}_{0.2}\text{Te}$	572.3	SBB80			
Na_2Te	572.2	SWH71			
Nb_3Te_4	572.6	Bahl75			
NbTe_4	572.8	Bahl75			
PbTe	572.0	SFS77			
SnTe	572.3	SFS77			
U_2Te_3	572.9	SNRS76			
UTe_3	573.0	SNRS76			
ZnTe	572.9	SWH71			
TeL_4	575.8	BWI77			
TeBr_2	576.7	BWI77			
TeCl_4	576.9	BWI77			
TeO_2	575.7	GBP81, SBB80			
TeO_3	576.6	SWH71			
$\text{Te}(\text{OH})_6$	577.1	BWI77			
$(\text{NH}_4)_2\text{TeCl}_6$	576.9	BWI77			
$(\text{NH}_4)_2\text{TeO}_4$	576.5	SWH71			
K_2TeO_3	575.5	SWH71			
Na_2TeO_4	576.8	Wagn75			
Cl_2TePh_2	576.2	BWI77			
Br_2TePh_2	576.2	BWI77			
I_2TePh_2	575.4	BWI77			
I_2TeEt_2	575.3	BWI77			
Ph_2Te_2	573.9	BWI77			
Br_3TePh	576.6	BWI77			
I_3TePh	575.8	BWI77			
I_2TeMe_2	575.6	BWI77			
p-tolyI TeOOH	576.1	BWI77			
Br_3TeBu	576.6	BWI77			
Te MNN					
Te	492.2		WRDM79		
TeBr_2	487.3		BWI78		
TeCl_4	486.1		BWI78		
TeO_2	487.1		BWI78		
TeO_3	485.5		BWI78		
$\text{Te}(\text{OH})_6$	485.1		BWI78		
$(\text{NH}_4)_2\text{TeCl}_6$	486.4		BWI78		
Na_2TeO_4	485.5		Wagn75		
Cl_2TePh_2	486.3		BWI78		
Br_2TePh_2	486.6		BWI78		
I_2TePh_2	487.8		BWI78		
I_2TeEt_2	487.6		BWI78		
Ph_2Te_2	488.5		BWI78		
Br_3TePh	486.8		BWI78		
I_3TePh	488.2		BWI78		
I_2TeMe_2	486.6		BWI78		
p-tolyI TeOOH	486.6		BWI78		
Br_3TeBu	486.5		BWI78		
Th 4f7/2					
Th	333.2		Φ		
Th	333.2		WRDM79		
ThO_2	334.4		VLDH77		
ThF_4	336.5		WRDM79		
Th 4d5/2					
Th	675.3		FBWF74		
ThO_2	675.5		VLDH77		
Ti 2p					
Ti	454.1		Φ		
TiO_2	458.8		Φ		
Ti	453.7		ALMP82		
Ti	453.9		LANM81		
Ti	453.9		NSCP74, WRDM79		
TiB_2	454.4		MECC73		
TiN	455.8		STAB76		
TiCl_4	458.5		MRV83		
TiO	455.1		SPB76a		
TiO_2	458.7		NSCP74, SPB76a, WRDM79, NGDS75		
TiO_2 (anatase, rutile)	459.2		MWI75		
BaTiO_3 (cubic, tetra.)	458.5		MWI75		
CaTiO_3	458.9		MWI75		
PbTiO_3	458.6		MWI75		
SrTiO_3	458.8		MWI75		
$\text{Cl}_2\text{Ti}(\text{C}_5\text{H}_5)_2$	457.1		GSMJ74		
$\text{ClTi}(\text{C}_5\text{H}_5)_2$	455.8		GSMJ74		
$\text{Ti}(\text{C}_5\text{H}_5)(\text{C}_7\text{H}_7)$	455.4		GSMJ74		
Ti LMM					
Ti	419.1		WRDM79		

Tl 4f			V 2p		
Tl	117.7	Φ	V	512.2	Φ
Tl	117.8	MBN80, WRDM79	V ₂ O ₅	517.4	Φ
TlI	118.5	MSC73	V	512.1	LANM81
TlBr	119.2	MSC73	V	512.3	WRDM79, NSCP74
TlCl	119.0	MSC73	V	512.9	KKL83
TlF	119.2	MSC73	V	513.4	SMKM77
Tl ₂ S	118.7	MSC73	V	512.4	RoRo76, LFS 73, FrSa75
Tl ₂ S ₃	118.7	MSC73	VB ₂	513.2	MECC73
Tl ₂ O ₃	117.5	MSC73	VN	514.4	RoRo76, STAB76
Cl ₃ Tl(pyridine) ₂	118.5	Walt77	V ₂ O ₃	515.7	CGR78
Cl ₆ Tl ₂ (PhPEt ₃) ₅	117.9	Walt77	VO ₂	516.3	KKL83
			V ₂ O ₅	517.6	NSLS77, NSCP74, WRDM79, NGDS75, NFS82
Tm 4d			VOCl ₂	516.4	LFS73
Tm	175.4	Φ	VOSO ₄	515.9	LFS73
U 4f_{7/2}			Cs ₃ VO ₄	516.9	NFS82
U	377.3	Φ	Rb ₃ VO ₄	516.9	NFS82
U	377.2	VRPC74, Chad73, WRDM79	Na ₃ VO ₄	517.3	NFS82
U ₂ Te ₃	380.5	SNRS76	Li ₃ VO ₄	517.5	NFS82
U ₂ Te ₃	381.3	SNRS76	Rh ₃ VO ₄	516.9	NFS82
U ₂ Se	380.3	SNRS76	K ₄ V(CN) ₆	513.3	Vann76
U ₂ Se ₃	379.1	SNRS76	V(acac) ₃	514.2	LFS73
U ₂ S	380.1	SNRS76	VO(acac) ₂	515.1	LFS73
U ₂ S ₃	379.4	SNRS76	ClV(C ₃ H ₅) ₂	513.8	GSMJ74
U ₂ Br ₃	378.4	TBVL82	V(C ₃ H ₅) ₂	512.9	GSMJ74, BCDH73
U ₂ Br ₄	379.9	TBVL82	V(C ₃ H ₅)(C ₇ H ₇)	513.3	GSMJ74
U ₂ Cl ₃	378.3	TBVL82			
U ₂ Cl ₄	380.2	TBVL82	V LMM		
U ₂ Cl ₅	381.9	TBVL82	V	472.0	WRDM79
UF ₃	380.1	TBVL82	VO ₂	468.6	KKL83
UF ₄	382.2	TBVL82	V ₂ O ₅	468.0	KKL83
UF ₄	382.7	Chad73			
UF ₅	382.6	TBVL82	W 4f		
UO ₂	380.0	VRPC74, Chad73, MSSS81	W	31.4	Φ
U ₂ O ₈	381.0	Chad73, ChGr72	W	31.4	VHE82
U ₂ O ₉	379.9	HoTh79	W	31.4	WRDM79, CoRa76, CGR 78, BiPo73, NSLS77
UO ₃	381.7	MSSS81, Chad73, ChGr72	WC	31.5	CoRa76
UOBr	380.1	TBVL82	WC	32.2	MSC73
UOBr ₂	380.4	TBVL82	WS ₂	33.2	Wagn75
UOCl	380.0	TBVL82	WBr ₅	36.3	MSC73
UOCl ₂	380.3	TBVL82	WBr ₆	35.9	MSC73
UO ₂ Br	380.5	TBVL82	WCl ₆	36.9	MSC73
UO ₂ Br ₂	381.1	TBVL82	WOCl ₄	37.2	MSC73
UO ₂ Cl ₂	381.6	TBVL82	WO ₂	32.8	CGR78, CoRa76, NgHe76
UO ₂ F ₂	382.9	TBVL82, Chad73	W ₁₈ O ₄₉	34.3	BiPo73
U ₂ SO ₄	381.6	Chad73	WO ₃	35.8	SaRa80, CoRa76, CGR 78, BiPo73, KMH 78
U ₂ (NO ₃) ₂ · 6H ₂ O	382.0	Chad73			NFS82, NGDS75
U ₂ (acac) ₄	379.7	Chad73	WO ₃	35.8	BiPo73
U ₂ (AcO) ₂ · 2H ₂ O	381.0	Chad73	Al ₂ (WO ₄) ₃	36.1	Nefe82, NFS 82
Ca ₂ UO ₂	380.7	Chad73	CaWO ₄	35.0	CGR78
La ₂ UO ₂	381.4	Chad73	H ₂ WO ₄	35.3	BiPo73
K ₂ UF ₆	382.4	PMDS77	H ₂ WO ₄	36.2	NFS82

Li ₂ WO ₄	36.0	NFS 82, MSC 73
Na ₂ WO ₄	36.3	Wagn75
Na _{0.6} WO ₃	35.8	BiPo73
Na _{0.1} WO ₃	35.6	BiPo73
NiWO ₄	35.4	NgHe76
Rh ₂ WO ₆	35.6	NFS82
(NH ₄) ₆ W ₇ O ₂₄ · 4H ₂ O	36.3	BiPo73
K ₂ WCl ₆	34.9	LeBr72
Cl ₄ W(Et ₃ P) ₂	34.6	LeBr72
Cl ₃ SnW(CO) ₆ (C ₅ H ₅)	32.4	WWVV77
Ph ₃ PW(CO) ₃	31.6	HVV79
Xe 3d_{5/2}		
Xe in graphite	669.7	Φ
Xe in Ag	669.6	CiHa74
Xe in Au	668.9	CiHa74
Xe in Cu	669.6	CiHa74
Xe in Fe	670.2	Wagn75
Xe in graphite	669.7	WRDM79
Na ₄ XeO ₆	674.1	Wagn77
Xe MNN		
Xe in Fe	544.8	Wagn75
Xe in graphite	545.2	WRDM79
Na ₄ XeO ₆	541.4	Wagn77
Y 3d		
Y	156.0	Φ
Y	155.8	NyMa80
Y ₂ O ₃	156.8	WRDM79, NGDS75
Yb 4d		
Yb	182.4	Φ
Yb	181.3	HHL70, KEML74
Yb	182.7	LPWF75
Yb ₂ O ₃	185.4	HHL70
Zn 2p_{3/2}		
Zn	1021.8	Φ
Zn	1021.9	LANM81, LKMP73
Zn	1021.8	GaWi77, KLMP74, MaDu77, Scho73a, KPML73, KIHe83
Zn	1021.8	WRDM79, Wagn75, SMKM77
Zn	1021.6	VanO77
Cu ₆₄ Zn ₃₆	1021.6	
ZnS	1022.0	GaWi77

Zn ₃ P ₂	1020.6	NSDU75
ZnP ₂	1020.9	NSDU75
ZnI ₂	1023.0	GaWi77, SATD73
ZnBr ₂	1023.4	Wagn75, SATD73
ZnCl ₂	1021.9	KIHe83
ZnCl ₂	1023.1	SATD73
ZnF ₂	1022.2	GaWi77
ZnF ₂	1022.8	Wagn75
ZnO	1021.8	Scho73a, WRDM79
ZnO	1022.5	GaWi77
Zn(acac) ₂	1021.4	Wagn75
(Me ₄ N) ₂ ZnBr ₄	1020.9	EMGK74
ZnSO ₄	1023.1	Nefe82
Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O	1022.0	WPHK82
ZnCr ₂ O ₄	1022.1	BDFP81
ZnRh ₂ O ₄	1021.7	NFS82

Zn LMM

Zn	992.1	GaWi77, KLMP74, MaDu77, Scho73a, KPML73, KIHe83
Zn	992.1	WRDM79, Wagn75
Cu ₆₄ Zn ₃₆	992.7	VanO77
ZnS	989.7	GaWi77
ZnI ₂	988.7	GaWi77
ZnBr ₂	987.3	Wagn75
ZnCl ₂	989.4	KIHe83
ZnF ₂	986.2	GaWi77
ZnF ₂	986.7	Wagn75
ZnO	988.5	Scho73a
ZnO	987.7	GaWi77
ZnO	988.2	KIHe83
Zn(acac) ₂	987.7	Wagn75
Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O	987.3	WPHK82

Zr 3d

Zr	178.9	Φ
Zr	178.8	NyMa80
Zr	178.3	NSCP74
Zr	178.9	WRDM79
ZrO ₂	182.2	SaRa80, NGDS75, NSCP74
ZrF ₃	185.3	NKBP73
K ₂ ZrF ₆	184.2	NKBP73
K ₃ ZrF ₇	183.7	NKBP73
KZrF ₅ · H ₂ O	184.7	NKBP73
Br ₂ Zr(OH) ₂ CH ₃ CHNH ₂ C	182.9	KNPP74
Cl ₂ Zr(OH) ₂ CH ₃ CHNH ₂ C	183.0	KNPP74

Appendix C. Chemical States Tables References

Note: The references in the Chemical States Tables are made with three or four letters which represent the authors' initials. Three or four capital letters indicate three or more authors; alternating upper- and lower-case letters represent two authors (the letters are the first two letters of each last name); and a capital letter followed by three lower case letters indicates a single author. The initials are followed by two digits, which represent the last two digits of the year of publication. This may be followed by a small letter, to distinguish between two otherwise identical reference notations.

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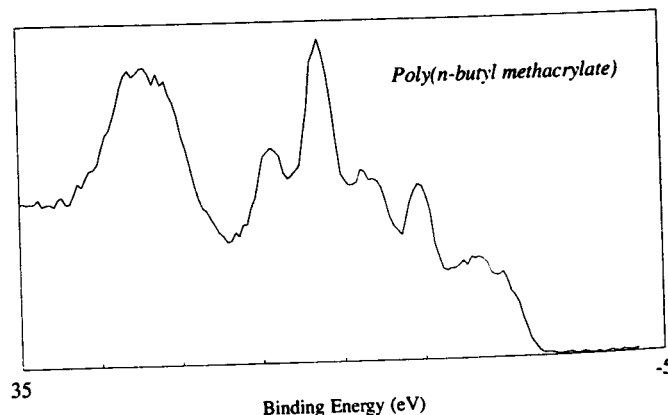
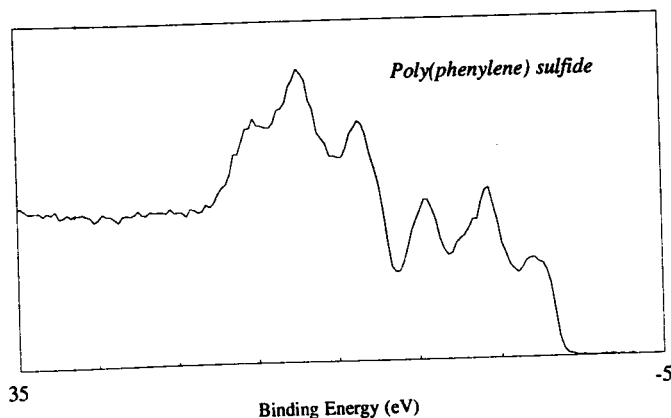
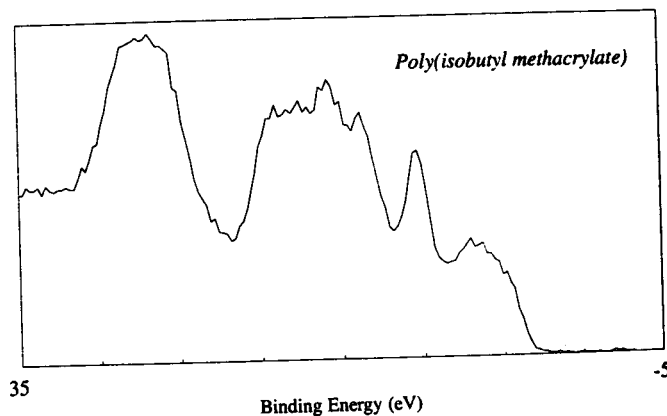
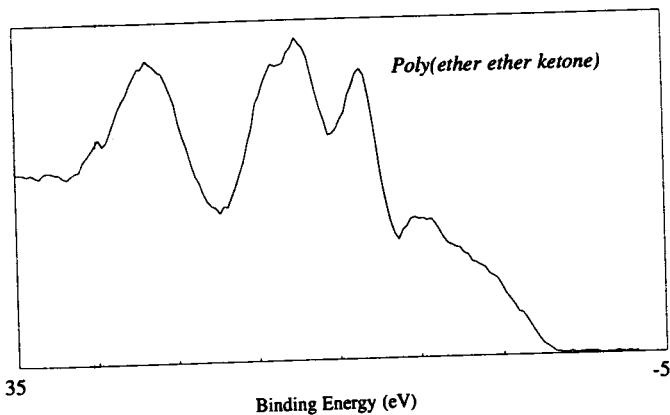
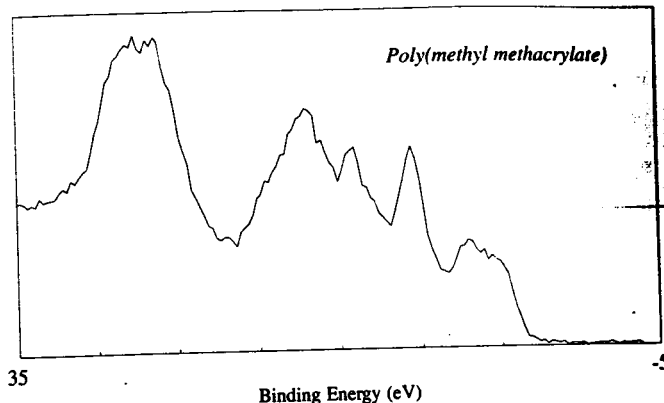
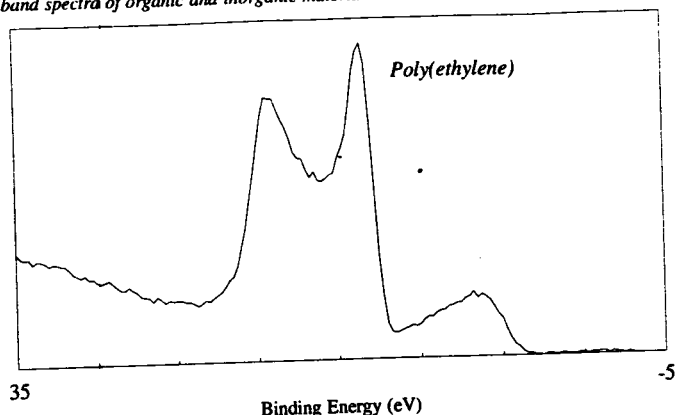
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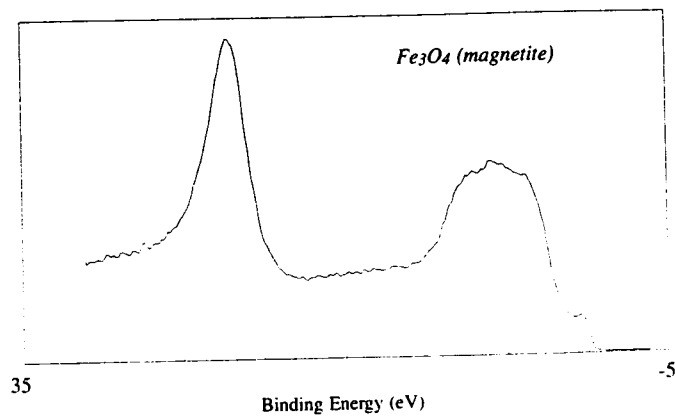
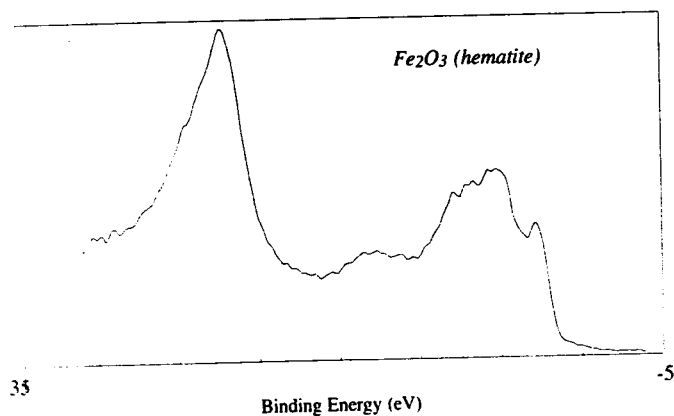
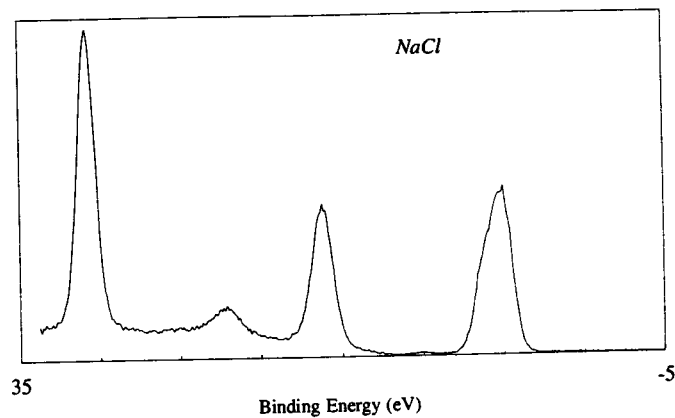
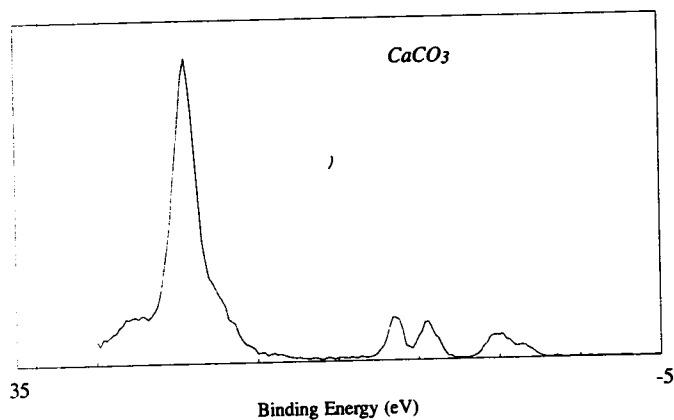
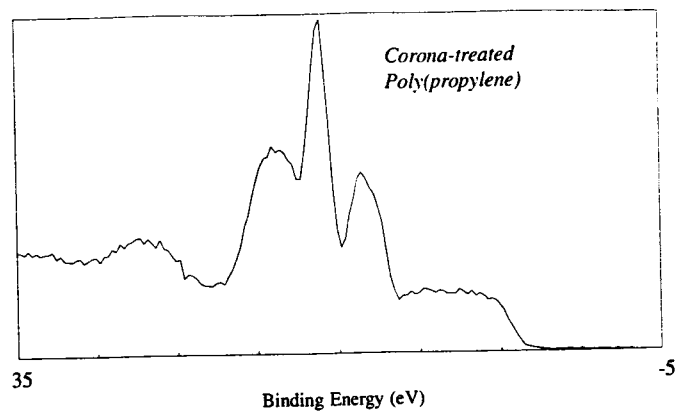
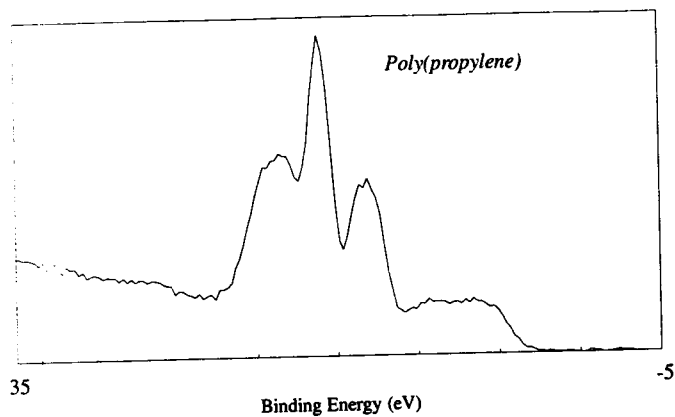
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Appendix D. Valence Band Spectra

In some cases, the chemical shifts observed in core level XPS are not sufficient to identify the surface chemistry of a particular sample. In the case of XPS analysis of polymers, the changes in carbon chemistry may be quite subtle in core level XPS or the chemical shifts may be only a secondary or tertiary effect. With the routine use of monochromators in XPS and the high counting rates made possible by current spectrometer technologies, many analysts use valence bands for identification of materials. In many cases, the valence bands and the high counting rates made possible by current spectrometer technologies, many analysts use valence bands for identification of materials. In many cases, the valence bands are used as fingerprints for a sample or a surface treatment, rather than for identifying specific molecular orbitals. The fingerprints of the valence bands may then be used to aid in both the identification of polymers and the quantification of polymer mixtures by using methods such as linear least squares fitting. The following is a small compilation of valence band spectra of organic and inorganic materials to illustrate the utility of valence band data.





Appendix E. Atomic Sensitivity Factors for X-ray Sources at 90°

This table is based upon empirical peak area values corrected for the system's transmission function. The values are only valid for and should only be applied when the electron energy analyzer used has the transmission characteristics of the spherical capacitor type analyzer equipped with an Omni Focus III lens supplied by Physical Electronics. The data are calculated for x-rays at 90° relative to the analyzer.*

Element	Line	ASF	Element	Line	ASF	Element	Line	ASF	Element	Line	ASF
Ag	3d	5.198	Eu	4d	2.210	Na	1s	1.685	Si	2p	0.283
Al	2p	0.193	F	1s	1.000	Nb	3d	2.517	Sm	3d _{5/2}	2.907
Ar	2p	1.011	Fe	2p	2.686	Nd	3d	4.697	Sn	3d _{5/2}	4.095
As	3d	0.570	Ga	2p _{3/2}	3.341	Ne	1s	1.340	Sr	3d	1.578
Au	4f	5.240	Gd	4d	2.207	Ni	2p	3.653	Ta	4f	2.589
B	1s	0.159	Ge	2p _{3/2}	3.100	O	1s	0.711	Tb	4d	2.201
Ba	4d	2.627	Hf	4f	2.221	Os	4f	3.747	Tc	3d	3.266
Be	1s	0.074	Hg	4f	5.797	P	2p	0.412	Te	3d _{5/2}	4.925
Bi	4f	7.632	Ho	4d	2.189	Pb	4f	6.968	Th	4f _{7/2}	7.498
Br	3d	0.895	I	3d _{5/2}	5.337	Pd	3d	4.642	Ti	2p	1.798
C	1s	0.296	In	3d _{5/2}	3.777	Pm	3d	3.754	Tl	4f	6.447
Ca	2p	1.634	Ir	4f	4.217	Pr	3d	6.356	Tm	4d	2.172
Cd	3d _{5/2}	3.444	K	2p	1.300	Pt	4f	4.674	U	4f _{7/2}	8.476
Ce	3d	7.399	Kr	3d	1.096	Rb	3d	1.316	V	2p	1.912
Cl	2p	0.770	La	3d	7.708	Re	4f	3.327	W	4f	2.959
Co	2p	3.255	Li	1s	0.025	Rh	3d	4.179	Xe	3d _{5/2}	5.702
Cr	2p	2.201	Lu	4d	2.156	Ru	3d	3.696	Y	3d	1.867
Cs	3d _{5/2}	6.032	Mg	2s	0.252	S	2p	0.570	Yb	4d	2.169
Cu	2p	4.798	Mn	2p	2.420	Sb	3d _{5/2}	4.473	Zn	2p _{3/2}	3.354
Dy	4d	2.198	Mo	3d	2.867	Sc	2p	1.678	Zr	3d	2.216
Er	4d	2.184	N	1s	0.477	Se	3d	0.722			

*C.D Wagner, et al. *Surf. Interface Anal.* 3, 211 (1981).

Appendix F. Atomic Sensitivity Factors for X-ray Sources at 54.7°

This table is based upon empirical peak area values corrected for the system's transmission function. The values are only valid for and should only be applied when the electron energy analyzer used has the transmission characteristics of the spherical capacitor type analyzer equipped with an Omni Focus III lens supplied by Physical Electronics. The data are calculated for x-rays at 54.7° relative to the analyzer.*

Element	Line	ASF	Element	Line	ASF	Element	Line	ASF	Element	Line	ASF
Ag	3d	5.987	Eu	4d	2.488	Na	1s	1.685	Si	2p	0.339
Al	2p	0.234	F	1s	1.000	Nb	3d	2.921	Sm	3d _{5/2}	3.611
Ar	2p	1.155	Fe	2p	2.957	Nd	3d	5.671	Sn	3d _{5/2}	4.725
As	3d	0.677	Ga	2p _{3/2}	3.720	Ne	1s	1.340	Sr	3d	1.843
Au	4f	6.250	Gd	4d	2.484	Ni	2p	4.044	Ta	4f	3.082
B	1s	0.159	Ge	2p _{3/2}	3.457	O	1s	0.711	Tb	4d	2.477
Ba	3d _{5/2}	7.469	Hf	4f	2.639	Os	4f	4.461	Tc	3d	3.776
Be	1s	0.074	Hg	4f	6.915	P	2p	0.486	Te	3d _{5/2}	5.705
Bi	4f	9.140	Ho	4d	2.469	Pb	4f	8.329	Th	4f _{7/2}	9.089
Br	3d	1.053	I	3d _{5/2}	6.206	Pd	3d	5.356	Ti	2p	2.001
C	1s	0.296	In	3d _{5/2}	4.359	Pm	3d	4.597	Tl	4f	7.691
Ca	2p	1.833	Ir	4f	5.021	Pr	3d	7.627	Tm	4d	2.454
Cd	3d _{5/2}	3.974	K	2p	1.466	Pt	4f	5.575	U	4f _{7/2}	10.315
Ce	3d	8.808	Kr	3d	1.287	Rb	3d	1.542	V	2p	2.116
Cl	2p	0.891	La	3d	9.122	Re	4f	3.961	W	4f	3.523
Co	2p	3.590	Li	1s	0.025	Rh	3d	4.822	Xe	3d _{5/2}	6.64
Cr	2p	2.427	Lu	4d	2.441	Ru	3d	4.273	Y	3d	2.175
Cs	3d _{5/2}	7.041	Mg	2s	0.252	S	2p	0.666	Yb	4d	2.451
Cu	2p	5.321	Mn	2p	2.659	Sb	3d _{5/2}	5.176	Zn	2p _{3/2}	3.726
Dy	4d	2.474	Mo	3d	3.321	Sc	2p	1.875	Zr	3d	2.576
Er	4d	2.463	N	1s	0.477	Se	3d	0.853			

*C.D Wagner, et al. *Surf. Interface Anal.* 3, 211 (1981).

Appendix G. Line Positions^{a)} by Element for Al K α X-rays

Atomic Number/Element		Photoelectron Lines										Auger Lines				
		1s	2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃ ^h
3	Li	56														
4	Be	112														1384
5	B	189														1310
6	C	285														1223
7	N	398														1107
8	O	531	23										1013	999		978
9	F	685	30										878	859		832
10	Ne	863	41	14									725	702		669
11	Na	1072	64	31									561	532		493
12	Mg	1303	89	50									381	347		301
13	Al		118	73												
14	Si		151	100	99											
15	P		188	131	130	14										
16	S		228	165	164	18										
17	Cl		271	201	199	17	6									
18	Ar		320	244	242	24										
19	K		380	297	294	35	19									
20	Ca		440	351	347	45	26									
21	Sc		499	404	399	51	29									
22	Ti		561	460	454	59	33									
23	V		626	520	512	66	37									
24	Cr		696	583	574	75	43									
25	Mn		769	650	639	83	48									
26	Fe		845	720	707	92	53									
27	Co		925	793	778	101	60									
28	Ni		1009	870	853	111	67									
29	Cu		1097	953	933	123	77	75								
30	Zn		1195	1045	1022	140	91	89	10							
31	Ga		1301	1144	1117	160	107	104	19							
32	Ge		1248	1217	1181	126	122	30	29							
33	As		1359	1324	1285	146	141	43	42							
34	Se					232	169	163	57	56						
35	Br					256	189	182	70	69	15	5				
36	Kr					287	216	208	88	87	21	8				
37	Rb					325	249	240	113	111	31	16				
38	Sr					360	281	270	136	134	39	21				
39	Y					394	311	299	158	156	45	24				
40	Zr					430	343	330	181	179	51	28				

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- a) Lines enclosed in boxes are the ones which are most useful for identifying chemical states.
- b) Includes KVV designation when L_{23} is not a core level.
- c) Designation is oversimplified.
- d) Includes LVV when M levels are not in core and MVV when N levels are not in core.
- e) No simple $4p_{1/2}$ line exists for this group of elements.
- f) The 4d doublet for these elements is complex and is variable with chemical state because of multiplet splitting and multi-electron processes.
- g) The 5s is of low intensity and is often in the shake-up structure of the 4f lines. These values are estimates of the energy.

Atomic Number/Element	Photoelectron Lines																Auger Lines										
	3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	4f _{5/2}	4f _{7/2}	5s	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}	6s	6p _{1/2}	6p _{3/2}	M ₄ N ₂₃ V	M ₅ N ₄₅ N ₄₅ ^{d1}	M ₄ N ₄₅ N ₄₅ ^{d1}	M ₄ N ₄₅ V	M ₄ VV	M ₄ VV	
41 Nb	467	376	361	205	202	56	31														1319		1287				
42 Mo	506	412	394	231	228	63	36														1299		1264				
43 Tc	544	445	425	257	253	68	39															1280		1241			
44 Ru	586	484	462	284	280	75		43 ^(c)													1256		1212				
45 Rh	629	521	497	312	307	81		48													1234		1185				
46 Pd	671	560	533	340	335	88		52													1211		1159				
47 Ag	719	604	573	374	368	98		60													1191	1135		1129			
48 Cd	772	652	618	412	405	110		69	11													1110		1103			
49 In	828	703	665	452	444	123		78	17													1084		1076			
50 Sn	885	757	715	493	485	137		89	25													1058		1049			
51 Sb	944	813	767	537	528	153		99	33													1032		1022			
52 Te	1009	871	820	583	573	170		111	42	41			12									1005		995			
53 I	1071	930	875	630	619	187		123	51	49			17									982		971			
54 Xe	1141	996	934	683	670	207		139	63	61			17									955		942			
55 Cs	1219	1069	1002	740	726	234	173	161	80	77			25									931		918			
56 Ba	1292	1138	1064	796	781	254	193	179	93	90			31	15								900		886			
57 La		1208	1128	853	836	275	213	197	106	103			34	17								867		854			
58 Ce		1272	1184	902	884	290	223	207	112	109			36	18									833				
59 Pr		1339	1242	952	932	305	234	218	115 ^d				38	18									797				
60 Nd			1301	1003	981	320	245	228	121				39	19									758				
61 Pm				1060	1034	337	264	242	129				38	22									714				
62 Sm				1108	1081	349	283	250	129				41	19									682				
63 Eu				1155	1126	363	289	255	128				39	19									637				
64 Gd				1218	1186	378	291	272	140		8		43	21									602				
65 Tb				1276	1241	396	322	285	146		8		45	22									559		411	260	230
66 Dy				1333	1296	417	337	297	152		8		48	23									526		368		
67 Ho				1393	1352	435	353	309	160		9		49	30	24								488		314		117
68 Er						451	368	321	167		9		52	31	24								440		273	98	56
69 Tm						470	384	333	175		8		53	32	25								398				
70 Yb						482	389	341	182		3		51	30	24												
71 Lu						509	413	360	206	196	9	7	57	34	27												
72 Hf						534	437	380	222	211	16	14	63	38	30												
73 Ta						563	463	401	238	226	24	22	69	43	33												
74 W						594	491	424	256	243	33	31	75	47	37												
75 Re						625	518	446	274	260	42	40	99														
76 Os						658	548	471	293	279	54	51	89 ^{d1}		44												
77 Ir						692	578	495	312	297	64	61	96 ^{d1}		48												
78 Pt						725	609	520	332	315	74	71	103 ^{d1}		52												
79 Au						763	643	547	353	335	88	84	110 ^{d1}	57	74												
80 Hg						805	682	579	381	361	105	101	125 ^{d1}	85	67	12	10										
81 Tl						847	720	610	406	385	122	118	133 ^{d1}	95	74	15	13										
82 Pb						893	762	644	434	412	142	137	150 ^{d1}	107	84	21	18										
83 Bi						940	806	679	464	440	162	157	161 ^{d1}	119	93	27	24										
90 Th						1330	1170	965	713	676	342	333	294	234	177	93	85	42	25	17							
92 U							1272	1043	779	736	388	377	322	260	195	103	94	44	26	17							
93 Np								1086	816	771	414	402			206		101		29	18							
94 Pu									1121	850	802	439	427		216		105		31	18							
95 Am										883	832	463	449	351	216	119	109		31	18							
96 Cm										919	865	487	473		232		113		32	18							
97 Bk										958	901	514	498		246		120		34	18							
98 Cf										994	933	541	523				124		35	19							

NeN₆₇N₇

NaN₆₇N₇

1317

1306

1316

1306

1320

1307

1322

1309

1326

1311

1329

1314

1334

1317

NeN₇O

NaN₆O

N₇O₆₅O₆₅

NeO₆₅O₆₅

1342

1324

1247

1231

1412

1406

1364

1343

1241

1222

1401

1399

1369

1354

1394

1391

NeO₂₃V

NeO₆₅V

1419

1239

1387

1383

1412

1204

1335

1404

1386

Appendix H. Line Positions^{a)} by Element for Mg K α X-rays

Atomic Number/Element		Photoelectron Lines										Auger Lines								
		1s	2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	KL ₁ L ₁	KL ₁ L _{2,3}	KL _{2,3} L _{2,3} ^b				
3	Li	56																		
4	Be	112																		
5	B	189																		
6	C	285																		
7	N	398																		
8	O	531	23											780	766	745				
9	F	685	30											645	626	599				
10	Ne	863	41	14										492	469	436				
11	Na	1072	64	31										328	299	260				
12	Mg	1305	89	50										148	114	68				
13	Al		118	73										L ₃ M ₂₃ M ₂₃ ^c	L ₃ M ₂₃ M ₂₃ ^c	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅ ^d	L ₂ M ₄₅ M ₄₅
14	Si		151	100	99									1186		1151				
15	P		188	131	130	14								1161		1077				
16	S		228	165	164	18								1134		990				
17	Cl		271	201	199	17								1103		874				
18	Ar		320	244	242	24								1071		745				
19	K		380	297	294	35	19							1039		599				
20	Ca		440	351	347	45	26							1006		436				
21	Sc		499	404	399	51	29							964		260				
22	Ti		561	460	454	59	33							916		68				
23	V		627	520	512	66	37							865						
24	Cr		696	583	574	75	43							815						
25	Mn		769	650	639	83	48							764						
26	Fe		845	720	707	92	53							711						
27	Co		925	793	778	101	60							655						
28	Ni		1009	870	853	111	67								895					
29	Cu		1097	953	933	123	77	75							835					
30	Zn		1195		1022	140	91	89							781					
31	Ga			1144	1117	160	107	104							726					
32	Ge			1248	1217	181	126	122	30	29					667					
33	As					205	146	141	43	42					606					
34	Se					232	169	163	57	56										
35	Br					256	189	182	70	69										
36	Kr					287	216	208	88	87	15	5								
37	Rb					325	249	240	113	111	31	16								
38	Sr					360	281	270	136	134	39	21								
39	Y					394	311	299	158	156	45	24								
40	Zr					430	343	330	181	179	51	28								

- a) Lines enclosed in boxes are the ones which are most useful for identifying chemical states.
- b) Includes KVV designation when L₂₃ is not a core level.
- c) Designation is oversimplified.
- d) Includes LVV when M levels are not in core and MVV when N levels are not in core.
- e) No simple $4p_{1/2}$ line exists for this group of elements.
- f) The 4d doublet for these elements is complex and is variable with chemical state because of multiplet splitting and multi-electron processes.
- g) The 5s is of low intensity and is often in the shake-up structure of the 4f lines. These values are estimates of the energy.

Atomic Number/Element	Photoelectron Lines																Auger Lines									
	3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	4f _{5/2}	4f _{7/2}	5s	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}	6s	6p _{1/2}	6p _{3/2}	M _{4s} N ₂₃ V	M _{4s} N _{4s} N _{4s} ^{di}	M _{4s} N _{4s} N _{4s} ^{di}	M _{4s} N _{4s} V	M ₅ VV	M ₄ VV
41 Nb	467	376	361	205	202	56		31													1086		1054			
42 Mo	506	412	394	231	228	63		36													1066		1031			
43 Tc	544	445	425	257	253	68		39													1047		1008			
44 Ru	586	484	462	284	280	75		43 ^{e1}													1023		979			
45 Rh	629	521	497	312	307	81		48													1001		952			
46 Pd	671	560	533	340	335	88		52													978		926			
47 Ag	719	604	573	374	368	98		60													958		902		896	
48 Cd	772	652	618	412	405	110		69	11															877		870
49 In	828	703	665	452	444	123		78	17															851		843
50 Sn	885	757	715	493	485	137		89	25															825		816
51 Sb	944	813	767	537	528	153		99	33															799		789
52 Te	1009	871	820	583	573	170		111	42	41			12											772		762
53 I	1071	930	875	630	619	187		123	51	49			18											749		738
54 Xe	1141	996	934	683	670	207		139	63	61			17											722		709
55 Cs	1219	1069	1002	740	726	234	173	161	80	77			25											698		685
56 Ba		1138	1064	796	781	254	193	179	93	90			31	15										667		653
57 La		1208	1128	853	836	275	213	197	106	103			34	17										634		621
58 Ce			1184	902	884	290	223	207	112	109			36	18												600
59 Pr			1242	952	932	305	234	218		115 ⁰			38	18												564
60 Nd				1003	981	320	245	228	121				39	19												525
61 Pm				1060	1034	337	264	242	129				38	22												481
62 Sm				1108	1081	349	283	250	129				41	19												449
63 Eu				1155	1126	363	289	255		128			39	19												404
64 Gd				1218	1186	378	291	272		140			43	21												369
65 Tb					1241	396	322	285		146			45	22												326
66 Dy						417	337	297		152			48	23												
67 Ho						435	353	309		159			9	49	30	24										
68 Er						451	368	321		167			9	52	31	24										
69 Tm						470	384	333		175			8	53	32	25										
70 Yb						482	389	341		182			3	51	30	24										
71 Lu						509	413	360	206	196	9	7	57	34	27											
72 Hf						534	437	380	222	211	16	14	63	38	30											
73 Ta						563	463	401	238	226	24	22	69	43	33											
74 W						594	491	424	256	243	33	31	75	47	37											
75 Re						625	518	446	274	260	42	40	99													
76 Os						658	548	471	293	279	54	51	89	44												
77 Ir						692	578	495	312	297	64	61	96 ⁰	48												
78 Pt						725	609	520	332	315	74	71	103 ⁰	52												
79 Au						763	643	547	353	335	88	84	110 ⁰	74												
80 Hg						805	682	579	381	361	107	103	125 ⁰	85	67	12	10									
81 Tl						847	720	610	406	385	122	118	133 ⁰	95	74	15	13									
82 Pb						893	762	644	434	412	142	137	150 ⁰	107	84	21	18									
83 Bi						940	806	679	464	440	162	157	161 ⁰	119	93	27	24									
90 Th							1170	965	713	676	342	333	294	234	177	93	85	42	25	17						
92 U							1272	1043	779	736	388	377	322	260	195	103	94	44	26	17						
93 Np								1086	816	771	414	402			206		101		29	18						
94 Pu									1121	850	802	439	427		216		105		31	18						
95 Am										883	832	463	449	351	216	119	109		31	18						
96 Cm										919	865	487	473		232		113		32	18						
97 Bk										958	901	514	498		246		120		34	18						
98 Cf										994	933	541	523				124		35	19						

1086	1054
1066	1031
1047	1008
1023	979
1001	952
978	926
958	902
	877
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	825
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	772
	749
	722
	698
	667
	634
	600
	564
	525
	481
	449
	404
	369
	326
	170
Na ₆ N ₇ N ₇	
1084	1073
1085	1073
1087	1075
1089	1076
1093	1078
1096	1081
1101	1084
1109	1091
1119	1103
1131	1110
1136	1121
Na ₆ N ₇ O	
1101	1084
1109	1091
1119	1103
1131	1110
1136	1121
Na ₆ N ₇ O _{4s}	
1101	1084
1109	1091
1119	1103
1131	1110
1136	1121
Na ₆ N ₇ O _{4s}	
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1109	1091
1119	1103
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1136	1121
Na ₆ N ₇ O _{4s}	
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1136	1121
Na ₆ N ₇ O _{4s}	
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Na ₆ N ₇ O _{4s}	
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1119	1103
1131	1110
1136	1121
Na ₆ N ₇ O _{4s}	
1101	1084
1109	1091
1119	1103
1131	1110
1136	1121
Na ₆ N ₇ O _{4s}	
1101	1084
1109	1091
1119	

Appendix J. Line Positions in Numerical Order

For photoelectron lines, the spin orbit splitting is indicated in parentheses. Auger lines are in italics, and the photon source for the Auger excitation is indicated in parentheses.

7	Lu 4f _{7/2}	(2)	89	Mg 2s		175	Tm 4d		299	Y 3p _{3/2}	(12)
14	Hf 4f _{7/2}	(2)	90	Ba 4d _{5/2}	(3)	179	Zr 3d _{5/2}	(2)	301	<i>Mg</i>	(Al)
23	O 2s		98	<i>Er</i>	(Al)	181	<i>Se</i>	(Al)	307	Rh 3d _{5/2}	(5)
22	Ta 4f	(2)	99	Si 2p _{3/2}	(1)	182	Yb 4d		309	Ho 4p _{3/2}	(44)
25	Sn 4d		101	Hg 4f _{7/2}	(4)		Br 3p _{3/2}	(7)	315	Pt 4d _{5/2}	(17)
29	Ge 3d _{5/2}	(1)	103	La 4d _{5/2}	(3)	186	<i>Ga</i>	(Mg)	320	Ar 2s	
30	F 2s		104	Ga 3p _{3/2}	(3)	188	P 2s		321	Er 4p _{3/2}	(47)
31	W 4f _{7/2}	(2)	109	Ce 4d _{5/2}	(3)	189	B 1s		330	Zr 3p _{3/2}	(14)
37	V 3p			<i>Ge</i>	(Mg)	196	Lu 4d _{5/2}	(10)	333	Th 4f _{7/2}	(9)
40	Re 4f _{7/2}	(2)	112	Rb 3d _{5/2}	(1)	199	Cl 2p _{3/2}	(2)		Tm 4p _{3/2}	(51)
41	Ne 2s			Be 1s		202	Nb 3d _{5/2}	(3)	335	Pd 3d _{5/2}	(5)
42	As 3d _{5/2}	(1)	115	Pr 4d		208	Kr 3p _{3/2}	(8)		Au 4d _{5/2}	(18)
43	Cr 3p		117	<i>Ho</i>	(Al)	211	Hf 4d _{5/2}	(11)		<i>Cu</i>	(Mg)
48	Mn 3p		118	Tl 4f _{7/2}	(4)	226	Ta 4d _{5/2}	(12)	341	Yb 4p _{3/2}	(48)
49	I 4d _{5/2}	(2)		Al 2s		228	S 2s		342	<i>Ge</i>	(Al)
50	Mg 2p		121	Nd 4d			Mo 3d _{5/2}	(3)	347	Ca 2p _{3/2}	(3)
51	Os 4f _{7/2}	(3)	122	Ge 3p _{3/2}	(4)	240	Rb 3p _{3/2}	(9)	360	Lu 4p _{3/2}	(53)
53	Fe 3p		128	Eu 4d		242	Ar 2p _{3/2}	(2)	361	Hg 4d _{5/2}	(20)
56	Li 1s		129	Sm 4d		243	W 4d _{5/2}	(13)		Nb 3p _{3/2}	(15)
	Se 3d _{5/2}	(1)	131	P 2p _{3/2}	(1)	260	Re 4d _{5/2}	(14)	368	Ag 3d _{5/2}	(6)
60	Co 3p		134	Sr 3d _{5/2}	(2)		<i>Na</i>	(Mg)	369	<i>Gd</i>	(Mg)
61	Ir 4f _{7/2}	(3)	137	Pb 4f _{7/2}	(5)		<i>Tb</i>	(Al)	377	U 4f _{7/2}	(11)
	Xe 4d _{5/2}	(2)	140	Gd 4d		262	<i>Zn</i>	(Mg)	380	K 2s	
64	Na 2s		141	As 3p _{3/2}	(5)		As	(Al)	385	Tl 4d _{5/2}	(21)
67	Ni 3p		146	Tb 4d		270	Sr 3p _{3/2}	(11)	394	Mo 3p _{3/2}	(17)
69	Br 3d _{5/2}	(1)	151	Si 2s		271	Cl 2s		398	N 1s	
71	Pt 4f _{7/2}	(3)	152	Dy 4d		279	Os 4d _{5/2}	(14)	399	Sc 2p _{3/2}	(5)
73	Al 2p		156	Y 3d _{5/2}	(2)	280	Ru 3d _{5/2}	(4)	404	<i>Eu</i>	(Mg)
75	Cu 3p _{3/2}	(2)	157	Bi 4f _{7/2}	(5)	285	Tb 4p _{3/2}	(37)	405	Cd 3d _{5/2}	(7)
77	Cs 4d _{5/2}	(3)	160	Ho 4d			C 1s		408	<i>Ni</i>	(Mg)
84	Au 4f _{7/2}	(4)	163	Se 3p _{3/2}	(6)	294	K 2p _{3/2}	(3)	412	Pb 4d _{5/2}	(22)
87	Kr 3d _{5/2}	(1)	164	S 2p _{3/2}	(1)	297	Dy 4p _{3/2}	(40)	419	<i>Ga</i>	(Al)
89	Zn 3p _{3/2}	(2)	167	Er 4d			Ir 4d _{5/2}	(15)	436	<i>Ne</i>	(Mg)

440	Ca 2s		669	Ne	(Al)	874	N	(Mg)	1103	Cd	(Al)
449	Sm	(Mg)	670	Xe 3d _{5/2}	(13)	884	Ce 3d _{5/2}	(18)	1107	N	(Al)
441	Bi 4d _{5/2}	(24)	676	Th 4d _{5/2}	(37)	886	Ba	(Al)	1117	Ga 2p _{3/2}	(27)
444	In 3d _{5/2}	(8)	682	Sm	(Al)	896	Ag	(Mg)	1126	Eu 3d _{5/2}	(30)
454	Ti 2p _{3/2}	(6)	685	F 1s		900	Mn	(Al)	1129	Ag	(Al)
462	Ru 3p _{3/2}	(22)		Cs	(Mg)	916	Sc	(Mg)	1149	Sc	(Al)
480	Co	(Mg)	696	Cr 2s		918	Cs	(Al)	1154	Bi	(Mg)
485	Sn 3d _{5/2}	(8)	707	Fe 2p _{3/2}	(13)	926	Pd	(Mg)	1159	Pd	(Al)
493	Na	(Al)	709	Xe	(Mg)	932	Pr 3d _{5/2}	(20)	1161	Pb	(Mg)
495	Zn	(Al)	713	Co	(Al)	933	Cu 2p _{3/2}	(20)	1168	Tl	(Mg)
497	Rh 3p _{3/2}	(24)	715	Sn 3p _{3/2}	(42)	942	Xe	(Al)	1179	Hg	(Mg)
499	Sc 2s		726	Cs 3d _{5/2}	(14)	952	Rh	(Mg)	1183	Au	(Mg)
512	V 2p _{3/2}	(8)		Cr	(Mg)	959	Cr	(Al)	1185	Rh	(Al)
525	Nd	(Mg)	736	U 4d _{5/2}	(42)	964	Ca	(Mg)	1186	Gd 3d _{5/2}	(32)
526	Dy	(Al)	738	I	(Mg)	971	U	(Mg)	1197	Ca	(Al)
528	Sb 3d _{5/2}	(9)	745	O	(Mg)		I	(Al)	1204	U	(Al)
531	O 1s		758	Nd	(Al)	978	O	(Al)	1212	Ru	(Al)
533	Pd 3p _{3/2}	(27)	767	Sb 3p _{3/2}	(46)	979	Ru	(Mg)	1217	Ge 2p _{3/2}	(31)
551	Fe	(Mg)	772	Te	(Mg)	981	Nd 3d _{5/2}	(21)	1223	C	(Al)
561	Ti 2s		778	Co 2p _{3/2}	(15)	990	C	(Mg)	1239	Th	(Al)
564	Pr	(Mg)	781	Ba 3d _{5/2}	(15)	1005	Te	(Al)		K	(Al)
568	Cu	(Al)		V	(Mg)	1006	K	(Mg)	1241	Tb 3d _{5/2}	(35)
573	Ag 3p _{3/2}	(31)	784	Fe	(Al)		Th	(Mg)	1272	Ar	(Al)
	Te 3d _{5/2}	(10)	797	Pr	(Al)	1014	V	(Al)	1296	Dy 3d _{5/2}	(37)
574	Cr 2p _{3/2}	(9)	799	Sb	(Mg)	1022	Zn 2p _{3/2}	(23)	1299	Mo	(Al)
599	F	(Mg)	816	Sn	(Mg)	1032	Sb	(Al)	1303	Mg 1s	
600	Ce	(Mg)	820	Te 3p _{3/2}	(51)	1039	Ar	(Mg)	1304	Cl	(Al)
602	Gd	(Al)	832	F	(Al)	1049	Sn	(Al)	1310	B	(Al)
619	Cd 3p _{3/2}	(34)	833	Ce	(Al)	1068	Ti	(Al)	1319	Nb	(Al)
	I 3d _{5/2}	(12)	835	Ti	(Mg)	1071	Cl	(Mg)	1324	As 2p _{3/2}	(35)
634	La	(Mg)	836	La 3d _{5/2}	(17)	1072	Na 1s		1336	S	(Al)
637	Eu	(Al)	843	In	(Mg)	1076	In	(Al)	1387	Bi	(Al)
639	Mn 2p _{3/2}	(11)	853	Ni 2p _{3/2}	(18)	1077	B	(Mg)	1394	Pb	(Al)
641	Ni	(Al)	863	Ne 1s		1081	Sm 3d _{5/2}	(27)	1401	Tl	(Al)
653	Ba	(Mg)	867	La	(Al)	1086	Nb	(Mg)	1412	Hg	(Al)
665	In 3p _{3/2}	(38)	870	Cd	(Mg)	1103	S	(Mg)	1416	Au	(Al)
667	Mn	(Mg)									

Appendix K. Periodic Table

Atomic number

9 1.0

PHI sensitivity factor for designated photoelectron transition

Element symbol

F

Most intense photoelectron transition

1s 685

Binding energy, most intense photoelectron transition

Most intense Auger transition

KLL 647

Kinetic energy, most intense Auger transition

1 H												Most intense photoelectron transition Most intense Auger transition												1s 685 KLL 647		Binding energy, most intense photoelectron transition Kinetic energy, most intense Auger transition												2 He							
3 0.025 Li 1s 56 KLL 43		4 0.074 Be 1s 112 KLL 103														5 0.159 B 1s 187 KLL 177		6 0.296 C 1s 285 KLL 264		7 0.477 N 1s 402 KLL 380		8 0.711 O 1s 531 KLL 509		9 1.0 F 1s 685 KLL 655		10 1.340 Ne 1s 863 KLL 818																			
11 1.685 Na 1s 1072 KLL 994		12 0.252 Mg 2p 50 KLL 1186														13 0.193 Al 2p 73 LMM 68		14 0.283 Si 2p 99 LMM 93		15 0.412 P 2p 130 LMM 120		16 0.570 S 2p 164 LMM 151		17 0.770 Cl 2p 198 LMM 183		18 1.011 Ar 2p 242 LMM 215																			
19 1.30 K 2p 294 LMM 248		20 1.634 Ca 2p 347 LMM 290		21 1.678 Sc 2p 398 LMM 338		22 1.798 Ti 2p 454 LMM 418		23 1.912 V 2p 512 LMM 473		24 2.201 Cr 2p 574 LMM 528		25 2.42 Mn 2p 638 LMM 587		26 2.686 Fe 2p 707 LMM 703		27 3.255 Co 2p 778 LMM 774		28 3.653 Ni 2p 853 LMM 846		29 4.798 Cu 2p 933 LMM 918		30 3.354 Zn 2p _{1/2} 1022 LMM 992		31 3.341 Ga 2p _{1/2} 1117 LMM1068		32 3.100 Ge 2p _{1/2} 1217 LMM1145		33 0.570 As 3d 42 LMM1225		34 0.722 Se 3d 56 LMM1306		35 0.895 Br 3d 69 MNV 101		36 1.096 Kr 3d 87											
37 1.318 Rb 3d 111 MNV 102		38 1.578 Sr 3d 134		39 1.867 Y 3d 156 MNV 131		40 2.216 Zr 3d 179 MNV 150		41 2.517 Nb 3d 202 MNV 168		42 2.867 Mo 3d 228 MNV 188		43 3.266 Tc 3d 253 MNN 248		44 3.696 Ru 3d 280 MNN 275		45 4.179 Rh 3d 307 MNN 302		46 4.643 Pd 3d 335 MNN 328		47 5.198 Ag 3d 368 MNN 358		48 3.444 Cd 3d _{5/2} 405 MNN 384		49 3.777 In 3d _{5/2} 444 MNN 411		50 4.095 Sn 3d _{5/2} 485 MNN 438		51 4.473 Sb 3d _{5/2} 528 MNN 465		52 4.925 Te 3d _{5/2} 573 MNN 492		53 5.337 I 3d _{5/2} 619 MNN 516		54 5.702 Xe 3d _{5/2} 670 MNN 545											
55 6.032 Cs 3d _{5/2} 728 MNN 568		56 6.361 Ba 3d _{5/2} 781 MNN 601		57 7.708 La 3d 836 MNN 633		72 2.221 Hf 4f 14 NNN 181		73 2.589 Ta 4f 22 NNN 181		74 2.959 W 4f 31 NNN 180		75 3.327 Re 4f 40 NNN 178		76 3.747 Os 4f 51 NNN 176		77 4.217 Ir 4f 61 NNN 153		78 4.674 Pt 4f 71 NNN 170		79 5.240 Au 4f 84 NNN 163		80 5.797 Hg 4f 101 NOO 81		81 6.447 Tl 4f 118 NOO 88		82 6.968 Pb 4f 137 NOO 96		83 7.632 Bi 4f 157 NOO 104		84 Po		85 At		86 Rn											
87 Fr		88 Ra		89 Ac														58 7.399 Ce 3d 884 MNN 654		59 6.356 Pr 3d 932 MNN 690		60 4.697 Nd 3d 981 MNN 729		61 3.754 Pm 3d 1034 MNN 773		62 2.907 Sm 3d _{5/2} 1081 MNN 805		63 2.210 Eu 4d 128 MNN 850		64 2.207 Gd 4d 140 MNN 885		65 2.201 Tb 4d 146 MNN1076		66 2.198 Dy 4d 152 MVV1119		67 2.189 Ho 4d 160 MVV1173		68 2.184 Er 4d 167 MVV1214		69 2.172 Tm 4d 175		70 2.169 Yb 4d 182		71 2.156 Lu 4f 7	
90 7.498 Th 4f _{7/2} 333 NOV 68		91 Pa		92 8.476 U 4f _{7/2} 337 NOV 75		93 Np		94 Pu		95 Am		96 Cm		97 Bk		98 Cf		99 Es		100 Fm		101 Md		102 No		103 Lr																			

*The values are for area measurements of the designated transitions and are only valid when the electron energy analyzer used has the transmission characteristics of the spherical capacitor type analyzer equipped with an Omni Focus III lens supplied by Physical Electronics and with x-rays at 90° relative to the analyzer. When a spin-orbit splitting is not designated, the value is for a measurement including both spin-orbit components.